

Handbook of X-ray Photoelectron Spectroscopy

A Reference Book of Standard Spectra
for Identification and Interpretation of XPS Data

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Published by:

Physical Electronics, Inc.
6509 Flying Cloud Drive
Eden Prairie, Minnesota 55344
United States of America

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ISBN: 0-9648124-1-X

Library of Congress Catalog Card Number: 95-071385

Printed in the United States of America

Preface

X-ray Photoelectron Spectroscopy (XPS), also known as Electron Spectroscopy for Chemical Analysis (ESCA), is widely used to investigate the chemical composition of surfaces. The use of XPS in analytical laboratories throughout the world attests to the problem-solving capability of this technique. The ability to explore the first few atomic layers and assign chemical states to the detected atoms has shown XPS to be a powerful addition to any analytical laboratory.

A great deal of information has been published on the principles of the technique and the diverse range of applications for which it is used. Volumes of XPS spectra exist in the scientific literature, and international committees are establishing databases with reference spectra that will be made available to the general public. It is not the authors' intent to exclude these spectra or to ignore these databases. Rather the intent is to assemble a concise volume of standard spectra to aid in the identification of XPS data.

The previous version of this handbook, published in 1978, contained data acquired with a cylindrical mirror analyzer (CMA). Since that time, our XPS hardware has evolved. We currently use a spherical capacitance analyzer (SCA) in conjunction with improved detector technology and the choice of either a high-performance Al x-ray monochromator or an achromatic Mg/Al dual anode x-ray source. A 1992 version of this handbook was updated from the previous handbook with data acquired using our current SCA, which has a transmission function different from that of a CMA, and both monochromatic and achromatic x-ray sources. In addition, data are included from several elements not contained in the 1978 version of the handbook. The current 1995 version of the handbook is a reprint of the 1992 version which includes a few minor modifications. This handbook is meant to serve as a guide and reference work for the identification, quantification, calibration and interpretation of XPS spectra for users of Physical Electronics XPS systems equipped with SCAs and Omni Focus™ lenses. It is the authors' hope that this handbook will play a useful role in the practice of XPS.

Physical Electronics, Inc.
October 1995

Acknowledgments: The authors and editor would like to thank the following individuals for their contributions to the completion of this handbook: Dr. Charles Wagner, Surfex, for his contributions to the chemical states database; Dr. Albert Bevolo, Iowa State University, Ames Laboratory (USDOE), for providing the rare earth samples; Linda Wirtjes, Physical Electronics Laboratory; Teresa Salvati; Dr. Douglas Stickle; and Dr. Michael Burrell, General Electric Company. The National Museum of Natural History - Smithsonian Institution provided the cinnabar sample (NMNH R630) used for the mercury data. We also gratefully acknowledge the authors of the previous handbook.

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I. X-ray Photoelectron Spectroscopy

A. Introduction

X-ray Photoelectron Spectroscopy (XPS) was developed in the mid-1960s by Kai Siegbahn and his research group at the University of Uppsala, Sweden. The technique was first known by the acronym ESCA (Electron Spectroscopy for Chemical Analysis). The advent of commercial manufacturing of surface analysis equipment in the early 1970s enabled the placement of equipment in laboratories throughout the world. In 1981, Siegbahn was awarded the Nobel Prize for Physics for his work with XPS.

This handbook is meant to furnish the user with much of the information necessary to use XPS for diverse types of surface analysis. Information is provided on methods of sample preparation, data gathering, elemental identification, chemical state identification, quantitative calculation and elemental distribution.

Surface analysis by XPS involves irradiating a solid *in vacuo* with monoenergetic soft x-rays and analyzing the emitted

electrons by energy. The spectrum is obtained as a plot of the number of detected electrons per energy interval versus their kinetic energy. Each element has a unique spectrum. The spectrum from a mixture of elements is approximately the sum of the peaks of the individual constituents. Because the mean free path of electrons in solids is very small, the detected electrons originate from only the top few atomic layers, making XPS a unique surface-sensitive technique for chemical analysis. Quantitative data can be obtained from peak heights or peak areas, and identification of chemical states often can be made from exact measurement of peak positions and separations, as well as from certain spectral features.

Included in this handbook are survey spectra, strong line spectra and x-ray excited Auger spectra for most of the elements and some of their compounds, in addition to plots and tables of energy shift data which aid in the identification of chemical states.

B. Principles of the Technique

Surface analysis by XPS is accomplished by irradiating a sample with monoenergetic soft x-rays and analyzing the energy of the detected electrons. Mg K α (1253.6 eV), Al K α (1486.6 eV), or monochromatic Al K α (1486.7 eV) x-rays are usually used. These photons have limited penetrating power in a solid on the order of 1-10 micrometers. They interact with atoms in the surface region, causing electrons to be emitted by the photoelectric effect. The emitted electrons have measured kinetic energies given by:

$$KE = h\nu - BE - \phi_s \quad (1)$$

where $h\nu$ is the energy of the photon, BE is the binding energy of the atomic orbital from which the electron originates, and ϕ_s is the spectrometer work function.

The binding energy may be regarded as the energy difference between the initial and final states after the photoelectron has left the atom. Because there is a variety of possible final states of the ions from each type of atom, there is a corresponding variety of kinetic energies of the emitted electrons. Moreover, there is a different probability or cross-section for each final state. Relative binding energies and ionization cross-sections for an atom are shown schematically in Figure 1. The Fermi level corresponds to zero binding energy (by definition), and the depth beneath the Fermi level in the figure indicates the relative energy of the ion remaining after electron emission, or the binding energy of the electron. The line lengths indicate the relative probabilities of the various ionization processes. The p, d and f levels become split upon ionization, leading to vacancies in the $p_{1/2}$, $p_{3/2}$, $d_{3/2}$, $d_{5/2}$, $f_{5/2}$ and $f_{7/2}$. The spin-orbit splitting ratio is 1:2 for p levels, 2:3 for d levels and 3:4 for f levels. As an example, the spin-orbit splitting of the Si 2p is shown in Figure 2.

Because each element has a unique set of binding energies, XPS can be used to identify and determine the concentration of the elements in the surface. Variations in the elemental binding energies (the chemical shifts) arise from differences in the

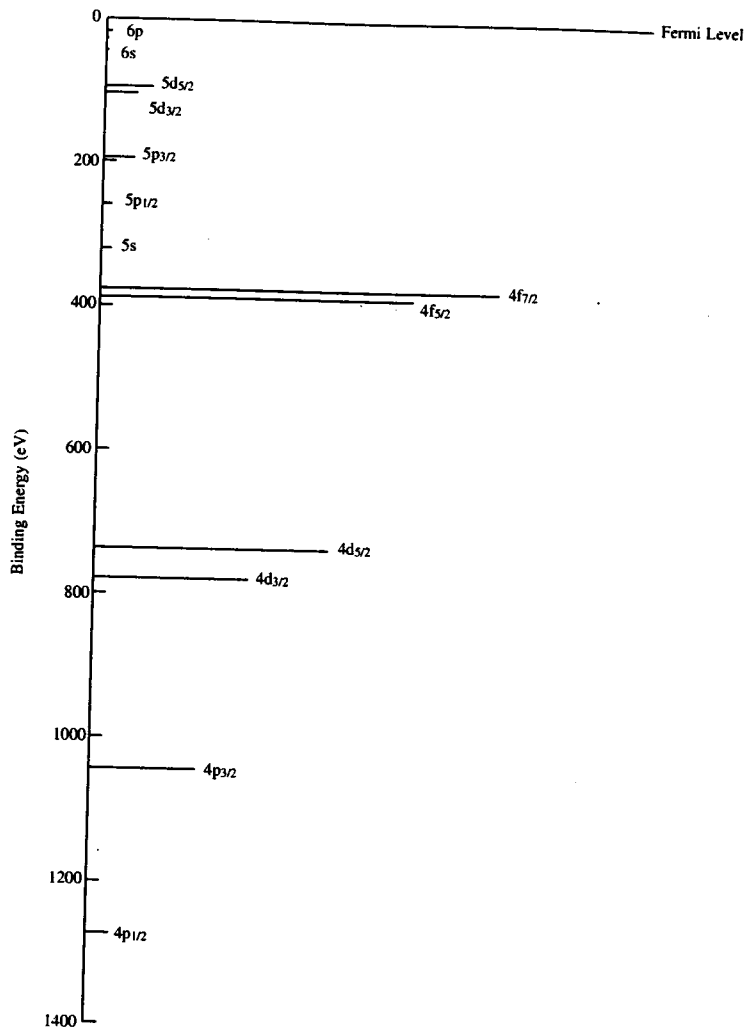


Figure 1. Relative binding energies and ionization cross-sections for U. The binding energy is proportional to the distance below the line indicating the Fermi level, and the ionization cross-section is proportional to the length of the line.

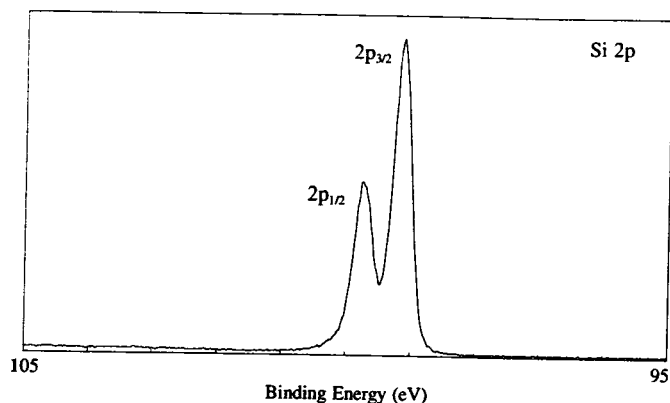


Figure 2. High-resolution spectrum of single-crystal Si showing the spin-orbit splitting of the 2p level.

chemical potential and polarizability of compounds. These chemical shifts can be used to identify the chemical state of the materials being analyzed.

In addition to photoelectrons emitted in the photoelectric process, Auger electrons may be emitted because of relaxation of the excited ions remaining after photoemission. This Auger electron emission occurs roughly 10^{-14} seconds after the photoelectric event. The competing emission of a fluorescent x-ray photon is a minor process in this energy range. In the Auger process (Figure 3), an outer electron falls into the inner orbital vacancy, and a second electron is simultaneously emitted, carrying off the excess energy. The Auger electron possesses kinetic energy equal to the difference between the energy of the initial ion and the doubly charged final ion, and is independent of the mode of the initial ionization. Thus, photoionization normally leads to two emitted electrons — a photoelectron and an Auger electron. The sum of the kinetic energies of the electrons emitted cannot exceed the energy of the ionizing photons.

Probabilities of electron interaction with matter far exceed those of the photons, so while the path length of the photons is of the order of micrometers, that of the electrons is of the order of tens of angstroms. Thus, while ionization occurs to a depth of a few

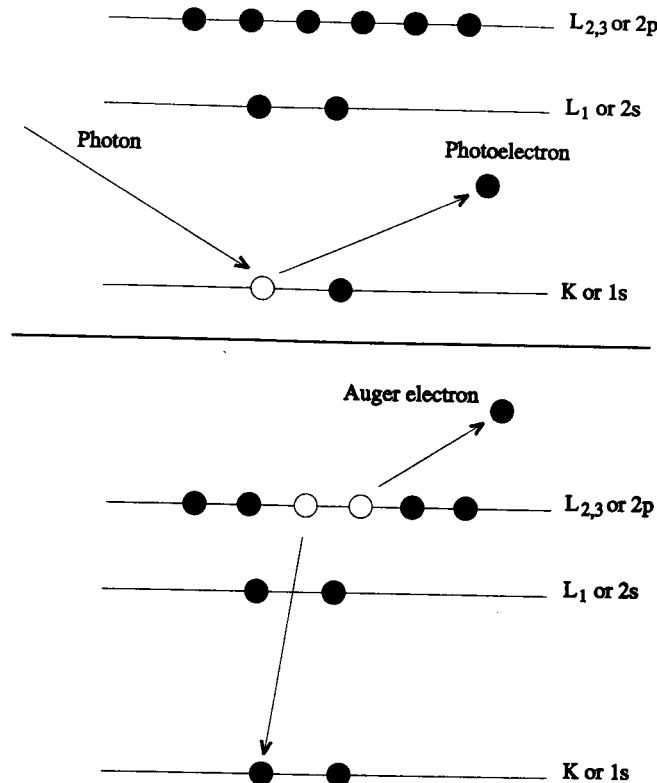


Figure 3. The XPS emission process (top) for a model atom. An incoming photon causes the ejection of the photoelectron. The relaxation process (bottom) for a model atom resulting in the emission of a $KL_{23}L_{23}$ electron. The simultaneous two-electron coulombic rearrangement results in a final state with two electron vacancies.

micrometers, only those electrons that originate within tens of angstroms below the solid surface can leave the surface without energy loss. These electrons which leave the surface without energy loss produce the peaks in the spectra and are the most useful. The electrons that undergo inelastic loss processes before emerging form the background. Calculations of the inelastic mean free paths of electrons in various materials are shown in Figure 4.

The electrons leaving the sample are detected by an electron spectrometer according to their kinetic energy. The analyzer is usually operated as an energy window, referred to as the pass energy, accepting only those electrons having an energy within the range of this window. To maintain a constant energy resolution, the pass energy is fixed. Incoming electrons are adjusted to the pass energy before entering the energy analyzer. Scanning for different energies is accomplished by applying a variable electrostatic field before the analyzer. This retardation voltage may be varied from zero up to and beyond the photon energy. Electrons are detected as discrete events, and the number of electrons for a given detection time and energy is stored and displayed.

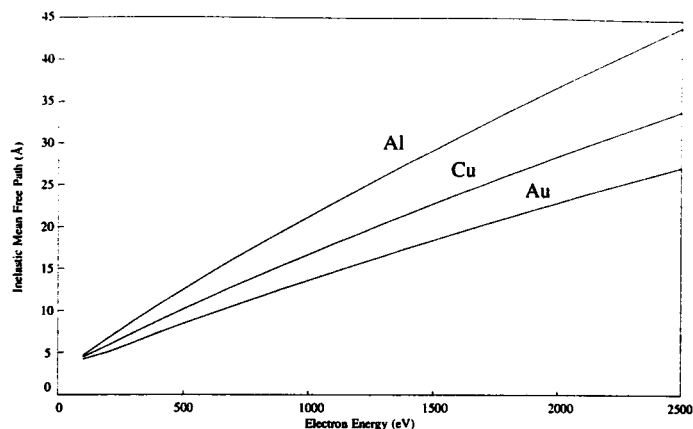


Figure 4. Calculated inelastic electron mean free paths in various metals from the method of S. Tanuma, C.J. Powell and D.R. Penn, *Surf. Interface Anal.* 17, 911 (1991).

C. Preparing and Mounting Samples

In the majority of XPS applications, sample preparation and mounting are not critical. Typically, the sample is mechanically attached to the specimen mount, and analysis is begun with the sample in the as-received condition. Additional sample preparation is discouraged in many cases because any preparation might modify the surface composition. For those samples where special preparation or mounting cannot be avoided, the following techniques are recommended.

1. Removing Volatile Material

Ordinarily, volatile material is removed from the sample before analysis. In exceptional cases, when the volatile layer is of interest, the sample may be cooled for analysis. The cooling must be to a sufficiently low temperature to guarantee that the volatile element is not warmed to evaporation by any heat load that the analysis conditions may impart.

Removal of unwanted volatile materials is usually accomplished by long-term pumping in a separate vacuum system or by washing with a suitable solvent. Use freshly distilled solvent to avoid contamination by high boiling point impurities within the solvent. Choice of the solvent can be critical. Hexane or other light hydrocarbon solvents are probably least likely to alter the surface, providing the solvent properties are satisfactory. Samples may also be washed efficiently in a Soxhlet extractor using a suitable solvent.

2. Removing Nonvolatile Organic Contaminants

When the nature of an organic contaminant is not of interest or when a contaminant obscures underlying material that is of interest, the contaminant may be removed with appropriate organic solvents. As with volatile materials, the choice of solvent can be critical.

3. Surface Etching

Ion sputter-etching or other erosion techniques, such as the use of an oxygen plasma on organic materials (see Section E.5.a.(3), p. 27), may be used to remove surface contaminants. This technique is particularly useful when removing adventitious hydrocarbons from the sample or when the native oxides, formed by exposure to the atmosphere, are not of interest.

Argon ion etching is commonly used to obtain information on composition as a function of the exposure time to ion etching. Calibration of the sputter rates can be used to convert sputter time to information on depth into the specimen. Because sputtering may cause changes in the surface chemistry, identification of the changes in chemical states with depth may not reflect the true composition.

4. Abrasion

Abrasion of a surface can be done without significant contamination by using a laboratory wipe, a cork, a file or a knife blade. This may cause local heating, and reaction with environmental gases may occur (e.g., oxidation in air and formation of nitrides in nitrogen). To prevent oxidation of more active materials, perform abrasion in an inert atmosphere such as a glove box. The abraded material should then be transferred to the ultra-high vacuum (UHV) chamber in a sealed vessel to preserve the clean surface.

5. Fracturing and Scraping

With proper equipment, many materials can be fractured or scraped within the test chamber under UHV conditions. While this obviates contamination by reaction with atmospheric gases, attention must be given to unexpected results which might occur. Fracturing might occur along the grain boundaries which may not be representative of the bulk material. Scraping can cover hard material with soft material when the sample is multiphase.

6. Grinding to Powder

If spectra characteristic of bulk composition are desired, samples may be ground to a powder in a mortar. Protection of the fresh surfaces from the atmosphere is required. When grinding samples, localized high temperatures can be produced, so grinding should be done slowly to minimize heat-induced chemical changes at the newly created surfaces. The mortar should be well cleaned before reuse.

7. Mounting Powders for Analysis

There are a number of methods which can be used to mount powders for analysis. Perhaps the most widely used method is dusting the powder onto a polymer-based adhesive tape with a camel-hair brush. The powder must be dusted across the surface carefully and lightly, with no wiping strokes. Some researchers shun organic tape for UHV work, but others have successfully used certain types of tape in the 10^{-10} Torr range.

Alternative methods for mounting powders include pressing the powder into indium or other soft foils, supporting the powder on a metallic mesh, pressing the powder into pellets or simply depositing the powder by gravity. With the foil method, the powder is pressed between two pieces of pure foil. The pieces are then separated, and one of them is mounted for analysis. Success with this technique has been varied. Sometimes bare foil remains exposed and, if the sample is an insulator, parts of the powder can charge differently. Differential charging can also be a problem when a metallic mesh is used to support the powder. If a press is used to form the powder into a pellet of workable dimensions, a press with hard and extremely clean working surfaces should be used. Gravity can effectively hold some materials in place, particularly if a shallow well or depression is cut in the surface of the sample mount. Allowing a liquid suspension of the powder to dry on the specimen holder is an effective way of producing a

uniform layer. With these methods, care must be taken in pump-down to ensure that gas evolution does not disturb

the sample. A throttled roughing valve is especially effective.

D. Experimental Procedure

1. Technique for Obtaining Spectra

All spectra in this handbook were obtained using a PHI Model 5600 MultiTechnique system. A schematic diagram of the apparatus (Figure 5) illustrates the relationship of major components, including the electron energy analyzer, the x-ray source, and the ion gun used for sputter-etching. The Model 10-360 Electron Energy Analyzer incorporated into the 5600 is an SCA, and the input lens to the analyzer is an Omni Focus III lens. The excitation sources used were a Model 10-550 x-ray source with a Model 10-410 monochromator and a Model 04-548 dual-anode source which was used with a magnesium anode. All of the spectra in the handbook were taken with the x-ray source operating at 400 W (15 kV - 27 mA). The specimens were analyzed at an electron take-off angle of 70°, measured with respect to the surface plane. The monochromatic x-ray source is located perpendicular to the analyzer axis, and the standard x-ray source is located at 54.7° relative to the analyzer axis.

In the PHI Model 5600 MultiTechnique system, energy distribution, energy resolution and analysis area are all a function of the analyzer. For all of the spectra in this handbook, the spectrometer was operated in a standard mode. The Omni Focus III lens was used to scan the spectrum while the SCA was operated at a constant pass energy. This resulted in constant resolution (ΔE) across the entire energy spectrum. The size of the analysis area was defined by the aperture selection of the Omni Focus III lens. Analyzer energy resolution ($\Delta E/E$) was determined by the choice of pass energy and the selected

aperture. All of the spectra in this handbook were obtained using an 800 μm diameter analysis area.

All of the spectra in this handbook were recorded and stored using the PHI ACCESS™ data system. The instrument was calibrated daily, and the calibration was checked several times each day during data acquisition. The analyzer work function was determined assuming the binding energy of the Au 4f_{7/2} peak to be 84.0 eV. All survey spectra scans were taken at a pass energy of 58.7 eV. The narrow scans of strong lines were, in most cases, just wide enough to encompass the peak(s) of interest and were obtained with a pass energy of 23.5 eV. A lower pass energy may show more structure for some materials. The narrow spectra were necessary to accurately determine the energy, shape and spin-orbit splitting of the strong lines. On insulating samples, a high-resolution spectrum was taken of the adventitious hydrocarbon on the surface of the sample to use as a reference for charge correction. The generally accepted binding energy for adventitious carbon is 284.8 eV.

The samples analyzed to obtain the spectra in this handbook are standard materials of known composition. Metal foils and polycrystalline materials with large surface areas were mechanically fastened to the specimen mount. Powder samples were ground with a mortar and pestle to expose fresh surfaces and were dusted onto adhesive tape. Most elemental standards were sputter-etched immediately prior to analysis to remove surface contamination. Most compounds, however, were ground or cleaved, and the freshly exposed surface was analyzed

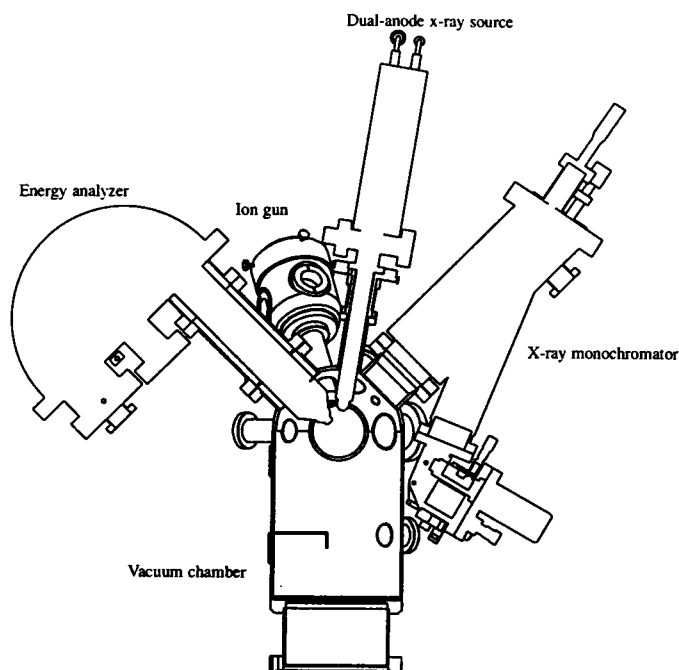


Figure 5. A schematic diagram of the PHI Model 5600 MultiTechnique system.

without etching in order to avoid possible changes in surface chemistry. Ne, Xe and Kr were implanted in graphite and Ar in silicon via ion implantation to unknown concentrations prior to analysis.

2. Instrument Calibration

To ensure the accuracy of the data presented in this handbook, the instrument used to obtain the data was calibrated regularly throughout the data-gathering process. The best way to check calibration, and the method used here, is to record suitable lines from a known, conducting specimen. Typically, the Au 4f or Cu 2p and 3p lines are used. The lines should be recorded with a narrow sweep width in the range of 5-10 eV, and

a pass energy of 23.5 eV or less (corresponding to the pass energy normally used for high resolution scans) should be used.

There is general agreement on accurate values of Cu, Au and Ag standard line energies. The values in Table 1 are recommended for clean Au, Ag and Cu:

Table 1. Reference Binding Energies (eV)

	Al K α	Mg K α
Cu 3p	75.14	75.13
Au 4f _{7/2}	83.98	84.00
Ag 3d _{5/2}	368.26	368.27
Cu L ₃ MM	567.96	334.94
Cu 2p _{3/2}	932.67	932.66
Ag M ₄ NN	1128.78	895.75

from M. P. Seah *Surf. Interface Anal.* **14**, 488 (1989)

Because the 2p_{3/2} and 3p_{3/2} photoelectron peak energies of Cu are widely separated in energy, measurement of these peak binding energies provides a quick and simple means of checking the accuracy of the binding energy scale. Utilizing all of the above standard energies establishes the linearity of the energy scale and its position, i.e., the location of the Fermi level.

3. Programming Scans for an Unknown Sample

For a typical XPS investigation where the surface composition is unknown, a broad scan survey spectrum should be obtained first to identify the elements present. Once the elemental composition has been determined, narrower detailed scans of selected peaks can be used for a more comprehensive picture of the chemical composition. This is the procedure that has been followed in compiling data for this handbook, even though specimen composition was known prior to analysis.

a. **Survey Scans.** Most elements have major photoelectron peaks below 1100 eV, and a scan range from 1100-0 eV binding energy is usually sufficient to

E. Data Interpretation

identify all detectable elements. The spectra in this handbook were recorded with a scan range of 1400-0 eV (Al excitation) or 1200-0 eV (Mg excitation) binding energy. In an unknown sample, if specific elements are suspected at low concentrations, their standard spectra should be consulted before programming the survey scan. If the strongest line occurs above 1100 eV binding energy, the scan range can be modified accordingly.

An analyzer pass energy of 187 eV, in conjunction with the appropriate aperture, is recommended for survey scans with the PHI Model 5600 MultiTechnique system. These settings result in adequate resolution for elemental identification and produce very high signal intensities, minimizing data acquisition time and maximizing elemental detectability.

b. Detail Scans. For purposes of chemical state identification, for quantitative analysis of minor components and for peak deconvolution or other mathematical manipulations of the data, detail scans must be obtained for precise peak location and for accurate registration of line shapes. There are some logical rules for this programming.

- (1) Scans should be wide enough to encompass the background on both sides of the region of in-

terest, yet with small enough step sizes to permit determination of the exact peak position. Sufficient scanning must be done within the time limits of the analysis in order to obtain good counting statistics.

- (2) Peaks from any species thought to be radiation-sensitive or transient should be run first. Otherwise, any convenient order may be chosen.

- (3) No clear guidelines can be given on the maximum duration of data gathering on any one sample. It should be recognized, however, that chemical states have vastly varying degrees of radiation sensitivity and that for any one set of irradiation conditions, there exists for many samples a condition beyond which it is impractical to attempt gathering data.

- (4) With the PHI Model 5600 MultiTechnique system, an analyzer pass energy of 23 eV is normally used for routine detail scans. Where higher energy resolution is needed, lower pass energies can be utilized. For example, the sputter-cleaned Si 2p on p. 56, taken at 23 eV pass energy, can be compared to the chemically etched Si 2p shown in Figure 2 (p. 11).

E. Data Interpretation

1. The Nature of the Spectrum

a. General Features. The spectrum is displayed as a plot of the number of electrons versus electron binding energy in a fixed, small energy interval. The position on the kinetic energy scale equal to the photon excitation energy minus the spectrometer work function cor-

responds to a binding energy of 0 eV with reference to the Fermi level (Equation 1, p. 10). Therefore, a binding energy scale with 0 at that point and increasing to the left is customarily used.

The spectra in this handbook are typical for the various elements. The well-defined peaks are due to electrons

which have not suffered an inelastic energy loss emerging from the sample. Electrons that have lost energy increase the level of the background at binding energies higher than the peak energy. The background is continuous because the energy loss processes are random and multiple. The background in the Mg $K\alpha$ induced spectra is larger than the background in the monochromated Al $K\alpha$ induced spectra because of excitation by Bremsstrahlung radiation of the non-monochromated light.

The "noise" in the spectrum is not instrumental in origin but is the consequence of the collection of single electrons as counts randomly spaced in time. The standard deviation for counts collected in any channel is equal to the square root of the counts so that the percent standard deviation is $100/(\text{counts})^{1/2}$. The signal-to-noise ratio is then proportional to the square root of the counting time. The background level upon which the peak is superimposed is a characteristic of the specimen, the excitation source and the transmission characteristics of the instrument.

b. Types of Lines. Several types of peaks are observed in XPS spectra. Some are fundamental to the technique and are always observed. Others are dependent upon the exact physical and chemical nature of the sample. A third type is the result of instrumental effects. The following describes the various spectral features that are likely to be encountered:

(1) *Photoelectron Lines.* The most intense photoelectron lines are relatively symmetrical and are typically the narrowest lines observed in the spectra. Photoelectron lines of pure metals can, however, exhibit considerable asymmetry due to coupling with conduction electrons. Peak width is a convolution of the natural line width (the lifetime of the "hole" resulting from the photoionization process), the width of the x-ray line which created the photoelectron line and the in-

strumental contribution to the observed line width. Less intense photoelectron lines at higher binding energies are usually wider by 1-4 eV than the lines at lower binding energies. All of the photoelectron lines of insulating solids are of the order of 0.5 eV wider than photoelectron lines of conductors. The approximate binding energies of all photoelectron lines detectable by Al or Mg radiation are cataloged in Appendices G and H.

(2) *Auger Lines.* These are groups of lines in rather complex patterns. There are four main Auger series observable in XPS. They are the KLL, LMM, MNN and NOO series, identified by specifying the initial and final vacancies in the Auger transition. The KLL series, for example, includes those processes with an initial vacancy in the K shell and final double vacancy in the L shell. The symbol V (e.g., KVV) indicates that the final vacancies are in valence levels. The KLL series has, theoretically, nine lines, and others have still more. Because Auger lines have kinetic energies which are independent of the ionizing radiation, they appear on a binding energy plot to be in different positions when ionizing photons of different energies (i.e., different x-ray sources) are used. Core-type Auger lines (with final vacancies deeper than the valence levels) usually have at least one component of intensity similar to the most intense photoelectron line. Positions of the more prominent Auger components are cataloged along with the photoelectron peaks in Appendices G and H.

(3) *X-ray Satellites.* The x-ray emission spectrum from a nonmonochromatic source used for irradiation exhibits not only the characteristic x-ray but also some minor x-ray components at higher photon energies. For each photoelectron peak that results from the routinely used Mg and Al $K\alpha$ x-

ray photons, there is a family of minor peaks at lower binding energies, with intensity and spacing characteristic of the x-ray anode material. The pattern of such satellites for Mg and Al is shown in Table 2. A resultant spectrum using Mg x-rays is shown in Figure 6.

Table 2. X-ray Satellite Energies and Intensities

	$\alpha_{1,2}$	α_3	α_4	α_5	α_6	β
Mg displacement, eV	0	8.4	10.1	17.6	20.6	48.7
relative height	100	8.0	4.1	0.6	0.5	0.5
Al displacement, eV	0	9.8	11.8	20.1	23.4	69.7
relative height	100	6.4	3.2	0.4	0.3	0.6

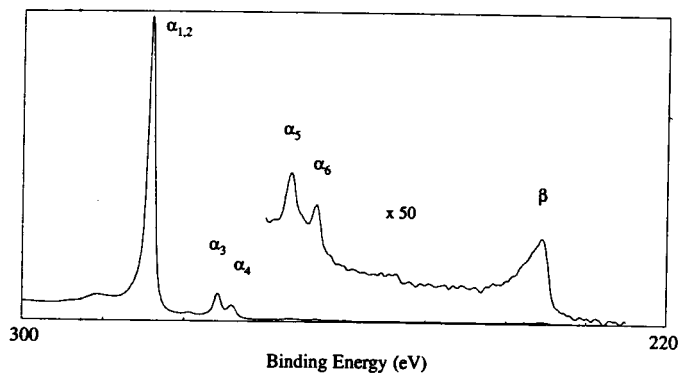


Figure 6. Mg x-ray satellites observed in the C 1s spectrum of graphite.

(4) *X-ray Ghost Lines.* Occasionally, x-radiation from an element other than the x-ray source anode material impinges upon the sample, resulting in small peaks corresponding to the most intense spectral peaks but displaced by a characteristic energy interval. These lines may result from Mg impurity in the Al anode or vice versa, Cu from the anode base structure, oxidation of the anode, or generation of x-ray photons in the Al foil x-ray window. On occasion, such lines can originate via

generation of x-rays within the sample itself. This last possibility is rare because the probability of x-ray emission is low relative to Auger electron emission. Nevertheless, such minor lines can be puzzling. Table 3 indicates where such peaks are most likely to occur relative to the most intense photoelectron lines. Because such ghost lines rarely appear with nonmonochromatic x-ray sources and are not possible with monochromatic x-ray sources, they should not be considered in line identification until all other possibilities are excluded.

Table 3. Displacement of X-ray Ghost Lines (eV)

Contaminating Radiation	Anode Material	
	Mg	Al
O ($K\alpha$)	728.7	961.7
Cu ($L\alpha$)	323.9	556.9
Mg ($K\alpha$)	—	233.0
Al ($K\alpha$)	-233.0	—

(5) *Shake-Up Lines.* Not all photoelectric processes are simple ones which lead to the formation of ions in the ground state, but there is a finite probability that the ion will be left in an excited state a few electron volts above the ground state. In this event, the kinetic energy of the emitted photoelectron is reduced, with the difference corresponding to the energy difference between the ground state and the excited state. This results in the formation of a satellite peak a few electron volts lower in kinetic energy (higher in binding energy) than the main peak. For example, the characteristic shake-up line for carbon in aromatic compounds, a shake-up process involving the energy of the $\pi \rightarrow \pi^*$ transition, is shown in Figure 7.

In some cases, most often with paramagnetic compounds, the intensity of the shake-up satellite may

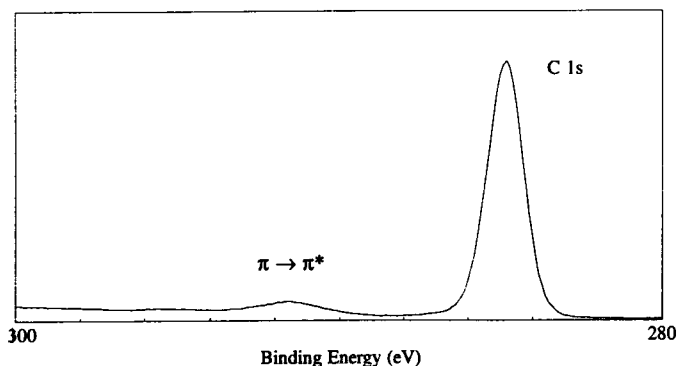


Figure 7. The π bond shake-up satellite for C 1s in polystyrene. The peak is about 6.7 eV higher than the main photopeak.

approach that of the main line. More than one satellite of a principal photoelectron line can also be observed, as shown in Figure 8. The occurrence of such lines is sometimes also apparent in Auger spectral contours (Figure 9). The displacements and relative intensities of shake-up satellites can sometimes be useful in identifying the chemical state of an element, as discussed in Section E.3.d. (p. 24).

(6) *Multiplet Splitting.* Emission of an electron from a core level of an atom that itself has a spin (unpaired electrons in valence levels) can create a vacancy in two or more ways. The coupling of the new unpaired electron left after photoemission from an s-type orbital with other unpaired electrons in the atom can create an ion with several possible final state configurations and as many energies. This results in a photoelectron line which is split asymmetrically into several components similar to the one shown in Figure 10.

Multiplet splitting also occurs in the ionization of p levels, but the result is more complex and subtle. In favorable cases, it results in an apparent slight

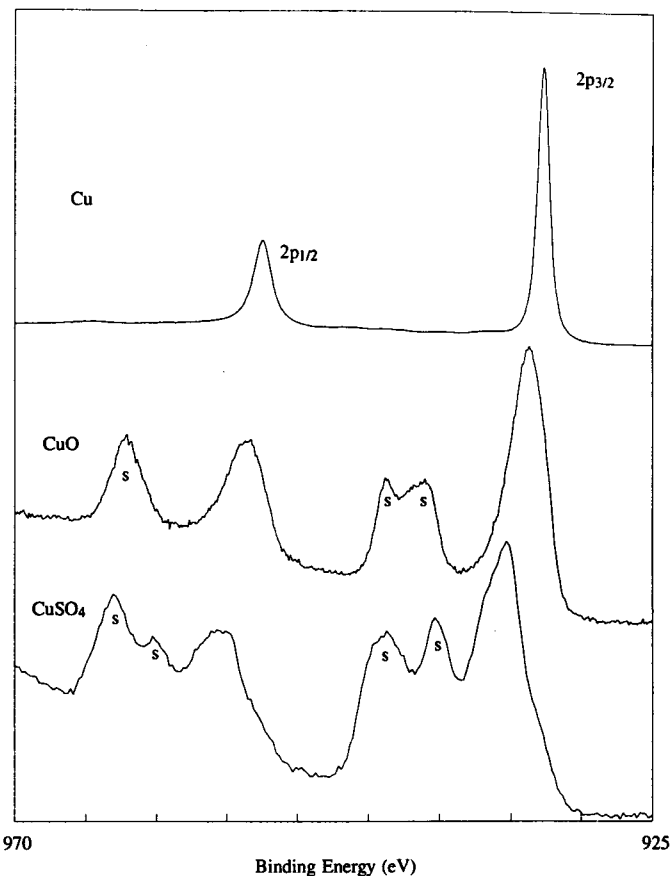


Figure 8. Examples of shake-up lines (s) of the copper 2p observed in copper compounds.

increase in the spin doublet separation, evidenced in the separation of the $2p_{1/2}$ and $2p_{3/2}$ lines in first-row transition metals, and in the generation of a less easily noticed asymmetry in the line shape of the components. Often such effects on the p doublet are obscured by shake-up lines.

(7) *Energy Loss Lines.* With some materials, there is an enhanced probability for loss of a specific

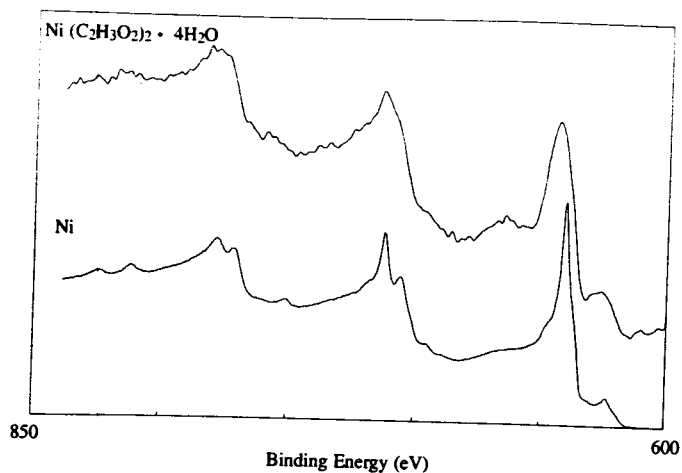


Figure 9. Examples of the effects of chemical states on Auger line shapes in nickel compounds.

amount of energy due to interaction between the photoelectron and other electrons in the surface region of the sample (Figure 11). The energy loss phenomenon produces a distinct and rather sharp hump 20-25 eV above the binding energy of the parent line. Under certain conditions of spectral display, energy loss lines can cause confusion. Such phenomena in insulators are rarely sharper than that shown in Figure 11 and are usually much more muted. They are different in each solid medium.

With metals, the effect is often much more dramatic, as indicated by the loss lines for aluminum shown in Figure 12. Energy loss to the conduction electrons occurs in well-defined quanta characteristic of each metal. These plasmons arise from group oscillations of the conduction electrons. The photoelectron line, or the Auger line, is successively mirrored at intervals of higher binding energy with reduced intensity. The energy

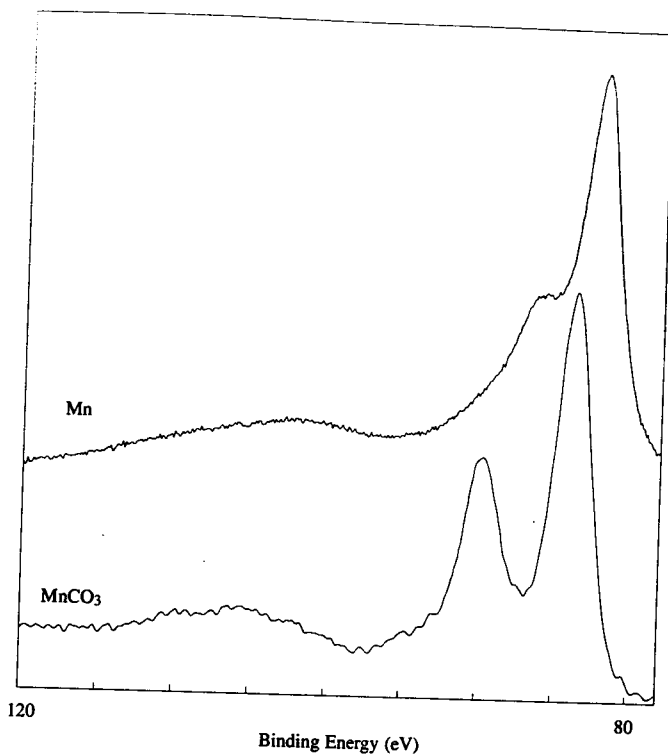


Figure 10. Multiplet splitting of the Mn 3s.

interval between the primary peak and the loss peak is called the plasmon energy. The so-called bulk plasmons are the more prominent of these lines. A second series, the surface plasmons, exists at energy intervals determined approximately by dividing the bulk plasmon energy by the square root of two. The effect is not easily observed in nonconductors, nor is it prominent in all conductors. Plasmon lines are especially prominent in the Groups Ia and IIa metal spectra in this handbook.

(8) *Valence Lines and Bands.* Lines of low intensity occur in the low binding energy region of the

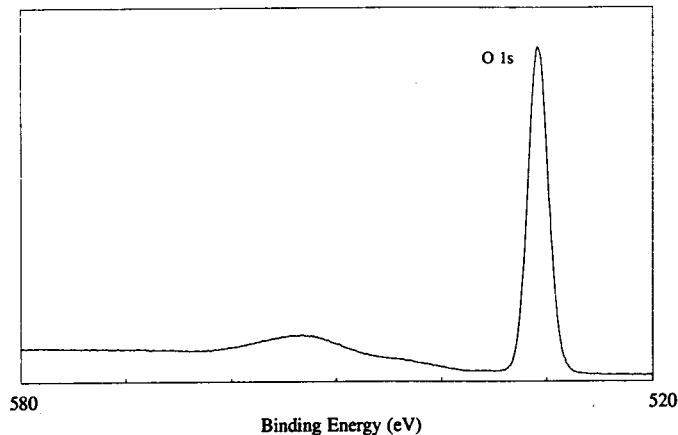


Figure 11. Energy loss envelope from the O 1s line in Al_2O_3 (sapphire).

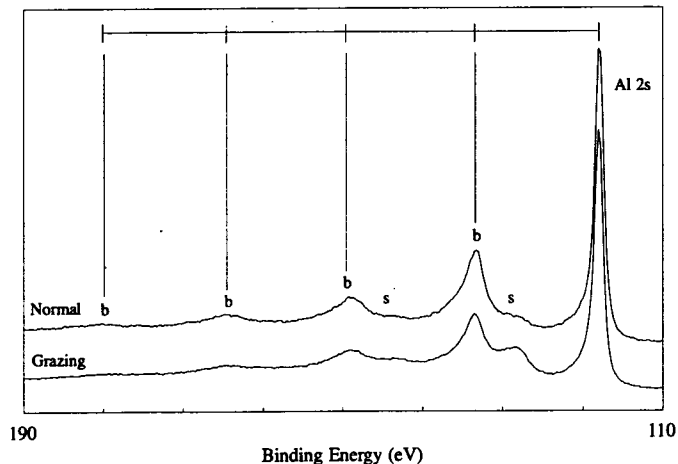


Figure 12. Surface (s) and bulk (b) plasmon lines associated with the Al 2s at normal and grazing take-off angles.

spectrum between the Fermi level and 10-20 eV binding energy. These lines are produced by photoelectron emission from molecular orbitals and from solid state energy bands. Differences be-

tween insulators and conductors are especially noted by the absence or presence of electrons from conduction bands at the Fermi level. Valence bands may also be used to distinguish between materials where the core level XPS photoelectron lines are quite similar in shape and position. Appendix D contains valence band spectra of several materials.

2. Line Identification

In general, interpretation of the XPS spectrum is most readily accomplished first by identifying the lines that are almost always present (specifically those of C and O), then by identifying major lines and associated weaker lines, and lastly by identifying the remaining weak lines. Most modern, commercially available spectrometers have peak identification algorithms within their data reduction packages. Poor signal-to-noise of the data or database limitations may require manual identification of some peaks. The following step-by-step procedure simplifies the data interpretation task and minimizes data ambiguities.

Step 1. The C 1s, O 1s, C (KLL) and O (KLL) lines are usually prominent in any spectrum. Identify these lines first along with all derived x-ray satellites and energy loss envelopes.

Step 2. Identify other intense lines (Appendix J) present in the spectrum, then label any related satellites and other less intense spectral lines associated with those elements. The energy positions of the less intense lines are noted in the line position table with the spectra. Keep in mind that some lines may be interfered with by more intense, overlapping lines from other elements. The most serious interferences by the C and O lines, for example, are Ru 3d by C 1s, V 2p and Sb 3d by O 1s, I (MNN) and Cr (LMM) by O (KLL), and Ru (MNN) by C (KLL).

Step 3. Identify any remaining minor lines. In doing this, assume they are the most intense lines of an unknown element. If not, they should already have been identified in the previous steps. Again, keep in mind possible line interferences. Small lines that seem unidentifiable can be ghost lines. Use Table 3 (p. 18) to check for the more intense parent photoelectron lines.

Step 4. Check the conclusions by noting the spin doublets for p, d and f lines. They should have the right separation (cf. spin orbit splitting for individual elements and Appendices G and H) and should be in the correct intensity ratio. The ratio for p lines should be about 1:2, d lines 2:3 and f lines 3:4. P lines, especially 4p lines, may be less than 1:2.

3. Chemical State Identification

The identification of chemical states primarily depends on the accurate determination of line energies. To determine line energies accurately, the voltage scale of the instrument must be precisely calibrated (cf. Section D.2., p. 15), a line with a narrow sweep range must be recorded with good statistics (of the order of several thousand counts-per-channel above background), and accurate correction must be made for static charge if the sample is an insulator.

a. Determining Static Charge on Insulators. During analysis, insulating samples tend to acquire a steady-state charge of as much as several volts. This steady-state charge is a balance between electron loss from the surface by emission and electron gain by conduction or by acquisition of slow or thermal electrons from the vacuum. The steady-state charge, usually positive, can be minimized with an adjacent neutralizer or flood gun. It is often advantageous to do this to reduce differential charging and sharpen the spectral lines.

A serious problem is exactly determining the extent of charging. Any positive charging retards outgoing

electrons and tends to make the peaks appear at higher binding energies, whereas excessive charge compensation can make the peaks shift to lower binding energies. The following are four methods which are usually valid for charge correction on insulating samples:

(1) Measurement of the position of the C 1s line from adventitious hydrocarbon nearly always present on samples introduced from the laboratory environment or from the glove box. This line, on unsputtered inert metals such as Au or Cu, appears at 284.8 eV, so any shift from this value can be taken as a measure of the static charge. At this time, it is not known whether a reproducible line position exists for C remaining on the surface after ion beam etching.

(2) The use of an internal standard, such as a hydrocarbon moiety of a polymer sample. For the study of supported catalysts or similar materials, one can adopt a suitable value for a constituent of the support and use that to interrelate binding energies of different samples. One must be certain that treatments of the various samples are not so different that the inherent binding energies of support constituents are changed.

(3) The use of a normally insulating sample so thin that it effectively does not insulate. This can be assumed if the spectrum of the underlying conductor appears in good intensity and if line positions are not affected by changes in electron flux from the charge neutralizer.

(4) For the study of insulating polymer films, binding energies of the C functional groups may also be determined by applying a small amount of poly(dimethyl siloxane) solution (10^{-6} M) to the sample surface and charge reference to the Si 2p of the silicone (at about 102.1 eV).

Some precautions should be kept in mind. If the sample is heterogeneous on even a micrometer scale, particles of different materials can be charged to different extents, and interpretation of the spectrum is complicated accordingly. One cannot physically mix a conducting standard like Au or graphite of micron dimensions with a powder and validly use the Au or graphite line in order to correct for static charge. Differential charging can be minimized to a great extent by using a flood source of low-energy electrons.

b. Photoelectron Line Chemical Shifts and Separations. An important advantage of XPS is its ability to obtain information on chemical states from the variations in binding energies, or chemical shifts, of the photoelectron lines. While many attempts have been made to calculate chemical shifts and absolute binding energies, the factors involved (especially in the solid state) are imperfectly understood, and one must rely on experimental data from standard materials. The tables accompanying the spectra in this handbook record considerable data from the literature as well as data obtained specifically for this handbook. All literature data have been carefully evaluated to the instrumental calibration and static charge reference values given above and are, therefore, directly comparable.

Because occasional line interferences do occur, it is sometimes necessary to use a line other than the most intense one in the spectrum. Chemical shifts of a minor line are within 0.2 eV of the chemical shift of the primary line. However, exceptional separations can occur in paramagnetic materials because of multiplet splitting. Separations of photoelectron lines can be determined approximately from the line position tables in Appendices G and H.

c. Auger Line Chemical Shifts and the Auger Parameter. Core-type Auger lines (transitions ending with double vacancies below the valence levels) usually have at least one component that is narrow and intense,

often nearly as intense as the strongest photoelectron line (cf. spectra for F, Na, As, In, Te and Pb). There are four core Auger groups that can be generated by Mg or Al x-rays: the KLL (Na, Mg); the LMM (Cu, Zn, Ga, Ge, As, Se); the MNN (Ag, Cd, In, Sn, Sb, Te, I, Xe, Cs, Ba); and NOO (Th, U). The MNN lines in the rare earths, while accessible, are very broad because of multiplet splitting and shake-up phenomena with most of the compounds. Valence-type Auger lines (final states with vacancies in valence levels) — such as those for O and F (KLL); Mn, Fe, Co and Ni (LMM); and Ru, Rh and Pd (MNN) — can be intense and are, therefore, also useful. Chemical shifts occur with Auger lines as well as with photoelectron lines. The chemical shifts are different from those of the photoelectron lines, but they are often more pronounced. This can be very useful for identifying chemical states, especially in combination with photoelectron chemical shift data. If data for the various chemical states of an element are plotted with the binding energy of the photoelectron line on the abscissa and the kinetic energy of the Auger line on the ordinate, a two-dimensional chemical state plot can be obtained. Such plots are in Appendix A for F, Na, Al, Si, S, Cu, Zn, As, Se, Ag, Cd, In, Sn and Te.

With chemical states displayed in two dimensions, the Auger parameter method becomes more powerful as a tool for identifying the chemical components than using photoelectron chemical shifts alone. In the format adopted for this handbook, the kinetic energy of the Auger line is plotted against the binding energy of the photoelectron line, with the latter plotted in the -x direction (kinetic energy is still, implicitly, +x). The kinetic energy of the Auger electron, referred to the Fermi level, is easily calculated by subtracting from the photon energy the position of the Auger line on the binding energy scale.

With this arrangement, each diagonal line represents all values of equal sums of Auger kinetic energy and

photoelectron binding energy. The Auger parameter, α , is defined as,

$$\alpha = KE_A - KE_P = BE_P - BE_A \quad (2)$$

or as the difference in binding energy between the photoelectron and Auger lines. This difference can be accurately determined because static charge corrections cancel. With all kinetic and binding energies referenced to the Fermi level, and recalling that:

$$KE = h\nu - BE \quad (3)$$

then...

$$KE_A + BE_P = h\nu + \alpha \quad (4)$$

or the sum of the kinetic energy of the Auger line and the binding energy of the photoelectric line equals the Auger parameter plus the photon energy. A plot showing Auger kinetic energy versus photoelectron binding energy then becomes independent of the photon energy.

In general, polarizable materials, especially conductive materials, have a high Auger parameter, while insulating compounds have a lower Auger parameter.

d. Chemical Information from Satellite Lines and Peak Shapes

(1) *Shake-up Lines.* These satellite lines have intensities and separations from the parent photoelectron line that are unique to each chemical state (Figure 8, p. 19). Some Auger lines also exhibit radical changes with chemical state that reflect these processes (Figure 9, p. 20). With transition elements and rare earths, the absence of shake-up satellites is usually characteristic of the elemental or diamagnetic states. Prominent shake-up patterns typically occur with paramagnetic states. Table 4 is a guide to some expected paramagnetic states.

Table 4. General Guide to Paramagnetic Species

Multiplet splitting and shake-up lines are generally expected in the paramagnetic states below:

Atomic No.	Paramagnetic States	Diamagnetic States
22	Ti(II) Ti(III)	Ti(IV)
23	V(II), V(III), V(IV)	V(V)
24	Cr(II), Cr(III), Cr(IV), Cr(V)	Cr(VI)
25	Mn(II), Mn(III), Mn(IV), Mn(V)	Mn(VII)
26	Fe(II), Fe(III)	K ₄ Fe(CN) ₆ , Fe(CO) ₄ Br ₂
27	Co(II), Co(III)	CoB, Co(NO ₂) ₃ NH ₃ , K ₃ Co(CN) ₆ , Co(NH ₃) ₆ Cl ₃
28	Ni(II)	K ₂ Ni(CN) ₄ , square planar complexes
29	Cu(II)	Cu(I)
42	Mo(IV), Mo(V)	Mo(VI), MoS ₂ , K ₄ Mo(CN) ₈
44	Ru(III), Ru(IV), Ru(V)	Ru(II)
47	Ag(II)	Ag(I)
58	Ce(III)	Ce(IV)
59-70	Pr, Nd, Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Yb compounds	
74	W(IV), W(V)	W(VI), WO ₂ , WCl ₄ , WC, K ₄ W(CN) ₈
75	Re(II), Re(III), Re(IV), Re(V), Re(VI)	Re(VII), ReO ₃
76	Os(III), Os(IV), Os(V)	Os(II), Os(VI), Os(VIII)
77	Ir(IV)	Ir(III)
92	U(III), U(IV)	U(V)

(2) *Multiplet Splitting.* On occasion, the multiplet splitting phenomenon can also be helpful in identifying chemical states. The 3s lines in the first series of transition metals, for example, exhibit separations characteristic of each paramagnetic chemical state. The 3s line, however, is weak and therefore is not often useful analytically. The 2p doublet separation is also affected by multiplet splitting, and the lines are more intense. The effect becomes very evident with Co compounds where the separation varies up to 1 eV. When first-row transition metal compounds are under study, it is

useful to accurately record these line separations and make comparisons with model compounds.

(3) *Auger Line Shape.* Valence-type Auger transitions form final-state ions with vacancies in molecular orbitals. The distribution of the group of lines is strongly affected, therefore, by the nature of the molecular orbitals in the different chemical states. Although little has yet been tabulated on this subject, the spectroscopist should bear in mind the possible utility of Auger line shapes.

4. Quantitative Analysis

For many XPS investigations, it is important to determine the relative concentrations of the various constituents. Methods have been developed for quantifying the XPS measurement utilizing peak area and peak height sensitivity factors. The method which utilizes peak area sensitivity factors typically is the more accurate and is discussed below. This approach is satisfactory for quantitative work. For transition metal spectra with prominent shake-up lines, it is best to include the entire 2p region when measuring peak area.

For a sample that is homogeneous in the analysis volume, the number of photoelectrons per second in a specific spectra peak is given by:

$$I = n f \sigma \theta y \lambda A T \quad (5)$$

where n is the number of atoms of the element per cm^3 of the sample, f is the x-ray flux in photons/ $\text{cm}^2\text{-sec}$, σ is the photoelectric cross-section for the atomic orbital of interest in cm^2 , θ is an angular efficiency factor for the instrumental arrangement based on the angle between the photon path and detected electron, y is the efficiency in the photoelectric process for formation of photoelectrons of the normal photoelectron energy, λ is the mean free path of the photoelectrons in the sample, A is the area of the sample from which photoelectrons

are detected, and T is the detection efficiency for electrons emitted from the sample. From Equation 5:

$$n = I / f \sigma \theta y \lambda A T \quad (6)$$

The denominator in Equation 6 can be defined as the atomic sensitivity factor, S . If we consider a strong line from each of two elements, then:

$$\frac{n_1}{n_2} = \frac{I_1/S_1}{I_2/S_2} \quad (7)$$

This expression may be used for all homogeneous samples if the ratio S_1/S_2 is matrix-independent for all materials. It is certainly true that such quantities as σ and λ vary somewhat from material to material (especially λ), but the ratio of each of the two quantities σ_1/σ_2 and λ_1/λ_2 remains nearly constant. Thus, for any spectrometer, it is possible to develop a set of relative values of S for all of the elements. Multiple sets of values may be necessary for instruments with multiple x-ray sources at different angles relative to the analyzer.

A general expression for determining the atom fraction of any constituent in a sample, C_x , can be written as an extension of Equation 7:

$$C_x = \frac{n_x}{\sum n_i} = \frac{I_x/S_x}{\sum I_i/S_i} \quad (8)$$

Values of S based on peak area measurements are indicated in Appendices E and F. The values of S in the appendices are based on empirical data (C.D. Wagner et al. *Surf. Interface Anal.* 3, 211 (1981)) which have been corrected for the transmission function of the spectrometer. The values in the appendix are only valid for and should only be applied when the electron energy analyzer used has the transmission characteristics of the SCA supplied by Physical Electronics. An example of the application of Equation 8 to analysis of a

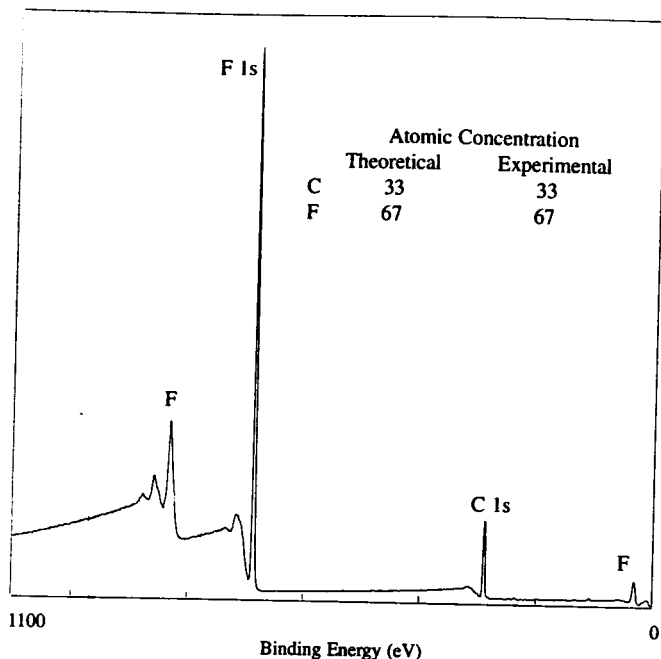


Figure 13. Quantitative analysis of poly(tetrafluoroethylene).

sample of known composition, poly(tetrafluoroethylene), is shown in Figure 13.

The use of atomic sensitivity factors in the manner described will normally furnish semiquantitative results (within 10-20%), except in the following situations:

a. The technique cannot be applied rigorously to heterogeneous samples. It can be useful with heterogeneous samples in measuring the relative number of atoms detected, but one must be conscious that the microscopic character of the heterogeneous system influences the quantitative results. Moreover, an overlying contamination layer has the effect of diminishing the intensity of high binding energy peaks more than that of low binding energy peaks.

b. Transition metals, especially of the first series, have widely varying and low values of γ , whereas γ for the other elements is rather uniform at about 0.8 eV. Thus, a value of S determined on one chemical state for a transition metal may not be valid for another chemical state. This effect can be minimized by including shake-up peaks in the area measurement.

c. When peak interferences occur, alternative lines must sometimes be used. The ratios of spin doublets (except 4p) are rather uniform, and the weaker of the pair can often be substituted. The spectra of the elements should be consulted, but caution must be exercised because the spectra of the elements themselves can be different from the spectra of their compounds.

d. Occasionally, an x-ray satellite from an intense photoelectron line interferes with measurement of a weak component. A mathematical approach can then be used to subtract the x-ray satellite before the measurement.

For quantitative work, check the spectrometer operation frequently to ensure that analyzer response is constant and optimum. A useful test is the recording of the three widely spaced spectral lines from Cu. Measurement of the peak height in counts-per-second should be made on 20-volt-wide scans of the $2p_{3/2}$, LMM Auger and $3p$ lines. Maintenance of such records makes it easy to notice if an instrument change occurs that would affect quantitative analysis.

5. Determining Element Location

a. **Depth.** There are four methods of obtaining information on the depth of an element in the sample. The first two methods described below utilize the characteristics of the spectrum itself but provide limited information. The third provides more detailed information but is attended by certain problems. The fourth utilizes measurements at two or more electron escape angles.

(1) The presence or absence of an energy loss peak or envelope indicates whether the emitting atoms are in the bulk or at the surface. Because electrons from surface atoms do not traverse the bulk, peaks from the surface atoms are symmetrical above level baselines on both sides, and the energy loss peak is absent. For a homogeneous sample, peaks from all elements will have similar inelastic loss structures.

(2) Elements whose spectra exhibit photoelectron lines widely spaced in kinetic energy can be approximately located by noting the intensity ratio of the lines. In the energy range above approximately 100 eV, electrons moving through a solid with lower kinetic energy are attenuated more strongly than those with higher kinetic energy. Thus, for a surface species, the low kinetic energy component will be relatively stronger than the high kinetic energy component, compared to that observed in the pure material. The data for homogeneous bulk solids can be compared with intensity ratios observed on unknowns to determine qualitatively the distribution of the element in the sample. Suitable elements include Na and Mg (1s and 2s); Zn, Ga, Ge and As ($2p_{3/2}$ and 3d); and Cd, In, Sn, Sb, Te, I, Cs and Ba ($3p_{3/2}$ and 4d or $3d_{5/2}$ and 4d).

When the element is in a bulk homogeneous layer beneath a thin contaminating layer, the characteristic intensity ratio is modified in the opposite direction. Thus, for a pair of lines from subsurface species, the low kinetic energy line will be attenuated more than the high kinetic energy line, distorting the characteristic intensity ratio. By observing such intensity ratios and comparing them with the pure bulk elements, it is possible to deduce whether the observed lines are from predominantly surface-, subsurface- or homogeneously distributed material.

(3) Depth profiling can be accomplished using controlled erosion of the surface by ion sputtering. Table 5 lists some data on sputter rates as a general guide. One can use this technique on organic materials, but few data are available for calibration. Chemical states are often changed by the sputter technique, but useful information on elemental distribution can still be obtained.

Table 5. Relative Sputter Rates at 4 kV.

Target	Sputter Rate
Ta ₂ O ₅	1.00
Si	0.90
SiO ₂	0.85
Pt	2.20
Cr	1.40
Al	0.95
Au	4.10

Another useful method of controlled erosion, especially of organic materials, is reaction with oxygen atoms from a plasma. This technique may also change the chemical states in the affected surface. Further, because the elements differ in their rates of reaction with oxygen atoms, the rate of removal of surface materials will be sample dependent.

(4) In XPS studies, the sample-mounting angle is not usually critical, though it does have some effect on the spectra. Very shallow electron take-off angles accentuate the spectrum of any component segregated on the surface, whereas a sample mounted at an angle normal to the analyzer axis minimizes the contribution from such a component. This effect can be used to estimate the depth of layers on or in the surface. This effect is not limited to flat surfaces, because angular dependence is even observed with powders, though the effects are muted. The spectrometer used to obtain the spectra presented in this handbook in-

tegrates the signal over only a narrow range of take-off angles.

It is possible to change the angle between the plane of the sample surface and the angle of entrance to the analyzer. At 90° with respect to the surface plane, the signal from the bulk is maximized relative to that from the surface layer. At small angles, the signal from the surface becomes greatly enhanced, relative to that from the bulk. The location of an element can thus be deduced by noting how the magnitude of its spectral peaks changes with sample orientation in relation to those from other elements. The analysis depth may be estimated by $d = \lambda \sin \theta$, where d is the analysis depth of the overlayer, λ is the inelastic mean free path, and θ is the take-off angle of the analyzed electrons.

Physical Electronics SCAs permit angle-dependent studies by simply varying the angle of the sample surface with respect to the input lens of the analyzer. The magnification of the lens determines the half-angle acceptance of the analyzer. An example of the information that can be gained through the use of this capability is shown in Figure 14. Data were obtained at normal (near 90°) and grazing (near 15°) take-off angles from a silicon sample with a thin silicon oxide overlayer. The observed intensity ratio of oxidized to elemental Si is much greater at the low take-off angle.

b. Surface Distribution. Many XPS systems have the capability to obtain data from areas as small as $30 \mu\text{m}$ in diameter using lens defined areas. Alternately, analysis areas of $< 10 \mu\text{m}$ can be achieved with a scanning focused photo beam. These relatively high lateral resolutions allow for the acquisition of XPS maps which show both elemental and chemical state information.

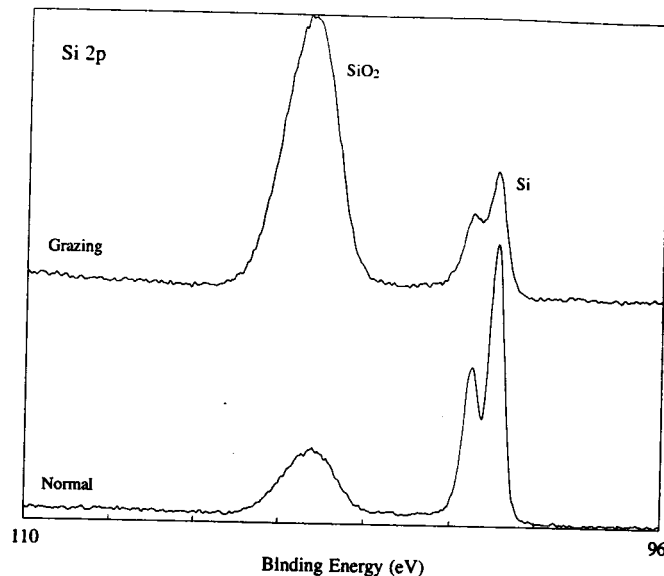


Figure 14. An example of the enhanced surface sensitivity achieved by varying the electron take-off angle. A thin oxide on silicon is enhanced at the low take-off angle.

c. Insulating Domains on a Conductor. The occurrence of steady-state charging of an insulator during analysis sometimes has useful consequences. Microscopic insulating domains on a conductor reach their own steady-state charge, while the conductor remains at spectrometer potential. Thus, an element in the same chemical state in both phases will exhibit two peaks. If a change is made in the supply of low-energy electrons which stabilize the charge (as from the neutralizer filament) or if a bias is applied to the conductor, the spectral peaks from the insulating phase will move relative to those from the conducting phase. For such heterogeneous systems, this can be an extremely useful technique. It makes it possible to determine whether the elements that contribute to the overall spectrum are in the conducting phase, the insulating phase or both.

F. How to Use this Handbook

1. Qualitative Analysis

Elemental and chemical identification of sample constituents can be performed by combining the information in the survey spectra with the binding energy tables of Appendices G, H and J.

a. Identify all major photoelectron peaks by using the line position tables in Appendix J.

b. Compare the elemental identifications with the elemental survey spectra to see that line positions and relative intensities are consistent. Also note the positions of the Auger electron peaks.

c. Review Section E (pp. 16-28) to account for fine structures such as energy loss lines, shake-up peaks, satellite lines, etc., not identified in the handbook spectra or energy tables.

d. Identify any remaining peaks assuming they are intense photoelectron or Auger lines using Appendices G or H.

e. Chemical state identification can be determined from high resolution spectra of the strongest photoelectron and sharpest Auger lines.

(1) Correct binding energies for static charging of insulators. When applicable, charge reference the binding energy scale to the C 1s photoelectron peak at 284.8 eV.

(2) Determine the chemical state from the measured shifts in the photoelectron binding ener-

gies by comparing the binding energy to the charts with the standard spectra and with the tabulated data in Appendix B.

(3) As suggested above, much about the chemical state can be learned from the magnitude and position of shake-up lines as well as from the energy and shape of valence Auger lines.

(4) For the elements F, Na, Al, Si, S, Cu, Zn, As, Se, Ag, Cd, In, Sn and Te, the Auger parameter tables in Appendix A may prove useful. The Auger line positions may be converted to kinetic energy by subtracting from the photon energy (Al = 1486.6 eV, Mg = 1253.6 eV). Note the location of the points for Auger kinetic energy and photoelectron binding energy on the respective elemental plot. Proximity of the experimental points to those of recorded chemical states should be considered probable identification. Note that experimental error is much greater along the Auger parameter grid than normal to the grid lines.

2. Quantification

The atomic sensitivity factors presented in Appendices E and F are applicable to the Physical Electronics Model 10-360 SCA and the Omni Focus III lens. A simplified expression to determine the atomic concentration of any element is given by Equation 8 (p. 25). However, the accuracy is limited by the assumptions made in Section E.4. (p. 25).

II. Standard XPS Spectra of the Elements

Standard Spectra of the Elements

This section of the handbook contains survey spectra of 81 elements, high resolution spectra of the most useful photoelectron lines, a chart of binding energies for each of the observed photoelectron and major Auger electron peaks, and a photoelectron chemical state binding energy chart for each of the elements. Used in combination with the appendices, the survey spectra aid in elemental identification, while the high-resolution spectra and binding energy data aid in the identification of chemical states.

Survey Spectra

The survey data include all of the lines which are normally useful. For most elements, the survey data were acquired with both a monochromatic Al x-ray source and a nonmonochromatic Mg x-ray source. When survey spectra for two compounds are presented, the monochromatic source is used for both. The photon source for each survey is noted on the survey. The photoelectron and Auger lines for the element of interest are identified. Lines which occur due to other

elements are only designated by the elemental symbol, and x-ray satellites and energy loss lines are not noted. For many elements, the Auger peaks are presented in expanded form.

The ordinate is left undesignated, but the general contours and intensity ratios of the spectra are typical of measurements made using a Physical Electronics Model 10-360 SCA with an Omni Focus lens.

High-Resolution Spectra

The high-resolution spectra of the most useful photoelectron peaks are presented. Unless otherwise noted, the high-resolution data were acquired using the same photon source as the survey on the same page. The binding energy of the main line is noted and when appropriate, the spin orbit separation (Δ) is given. The lines from insulators were charge-corrected to adventitious hydrocarbon at 284.8 eV.

The spectra of the inert gas atoms implanted in graphite or silicon deserve special mention. The high-resolution data often show an asymmetric peak shape or a second resolvable peak when a single symmetric peak is expected. The intensity of the second, high binding energy peak is dependent on the implantation energy and is diminished at lower energies. The spectra are of inert gas atoms implanted at 4 kV.

Photoelectron and Auger Electron Line Position Tables

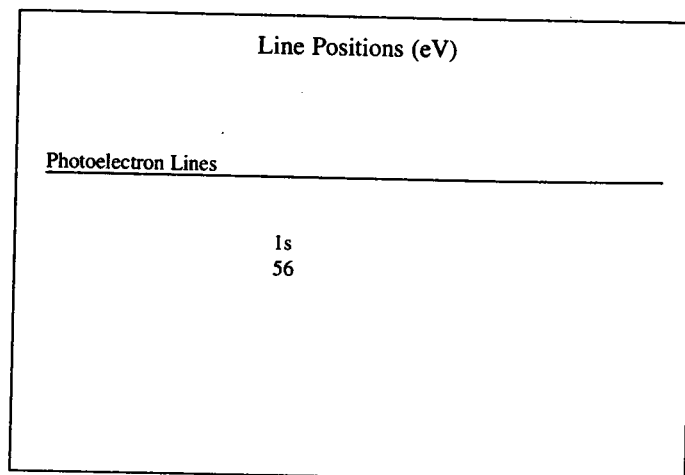
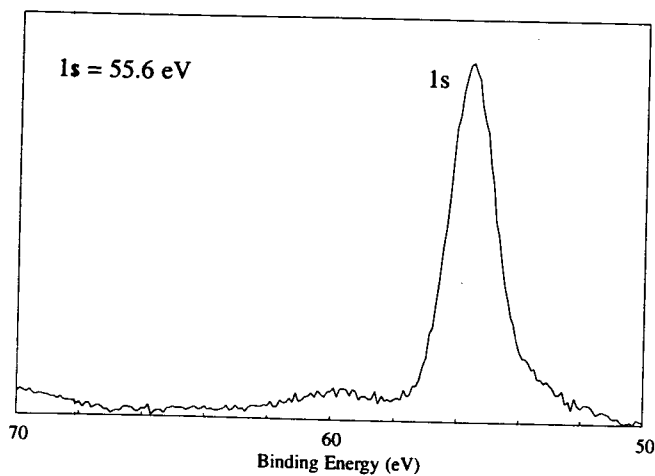
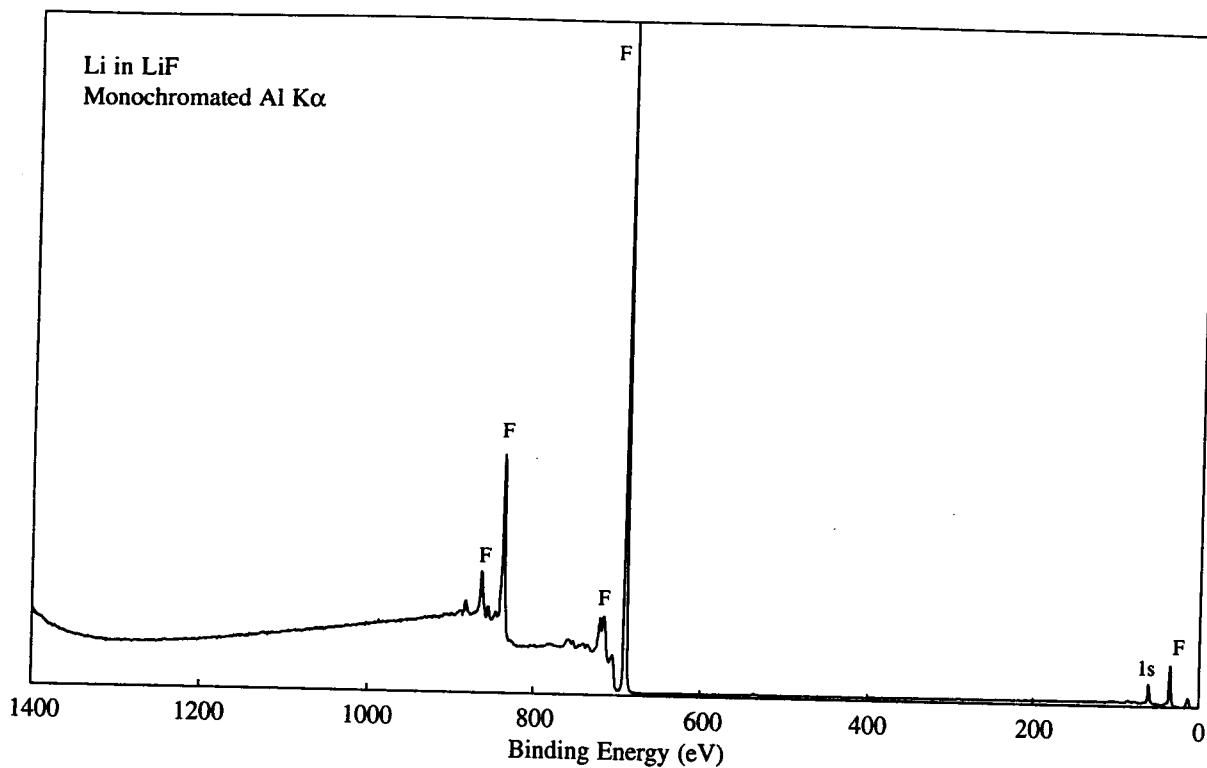
The photoelectron and Auger line position tables reflect the energies of the elemental peaks observed in this handbook. For oxidized or

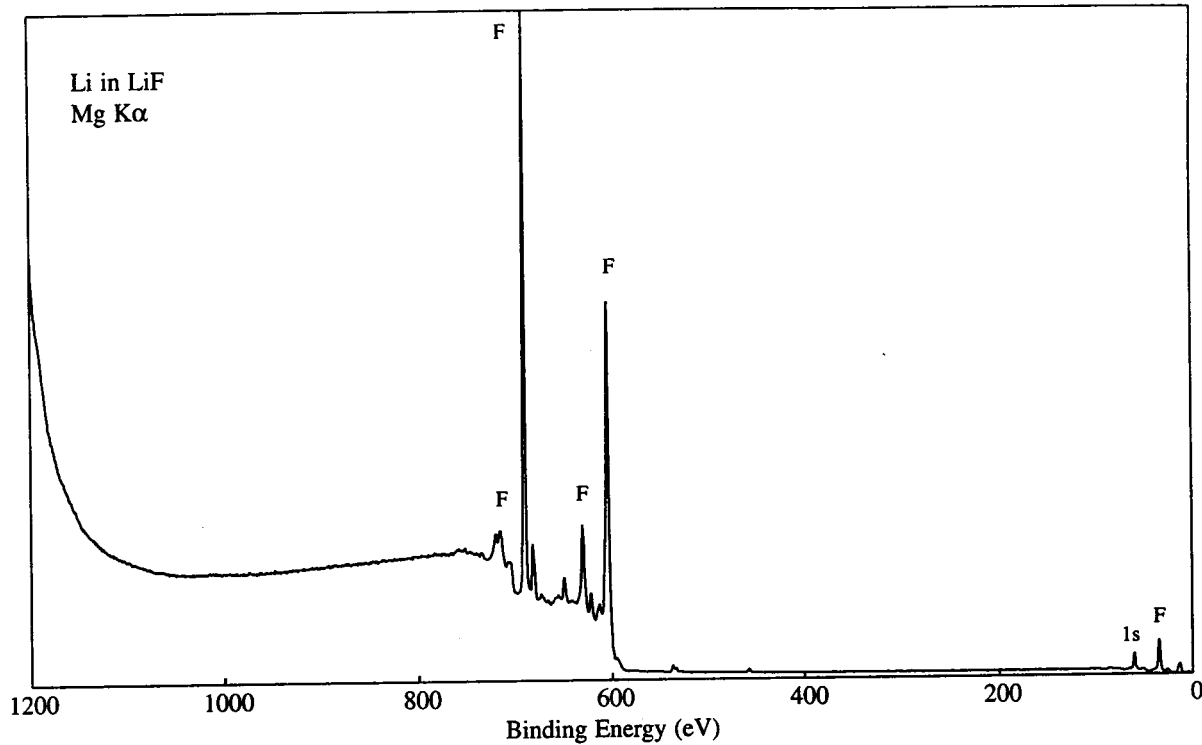
reduced species, the measured values may differ by a few electron volts.

Chemical State Binding Energy Tables

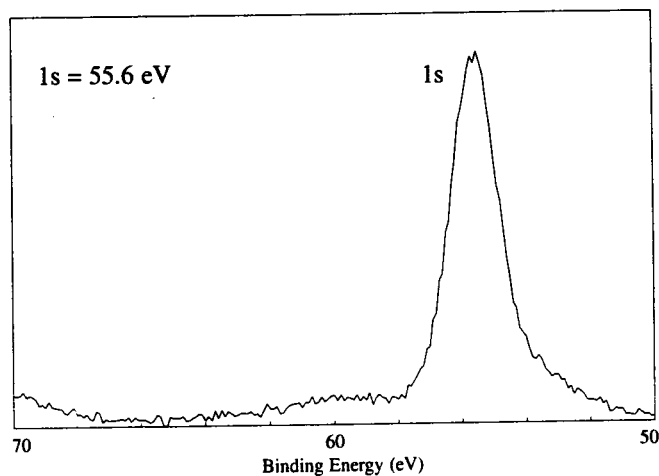
The binding energy tables have been constructed to reflect the general changes in binding energy with change in oxidation state or chemical environment. A more extensive listing with specific binding energy values for more than 1500 compounds is presented in Appendix B.

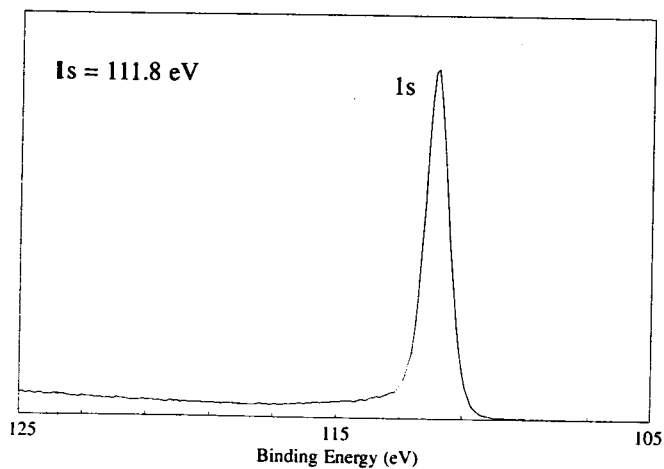
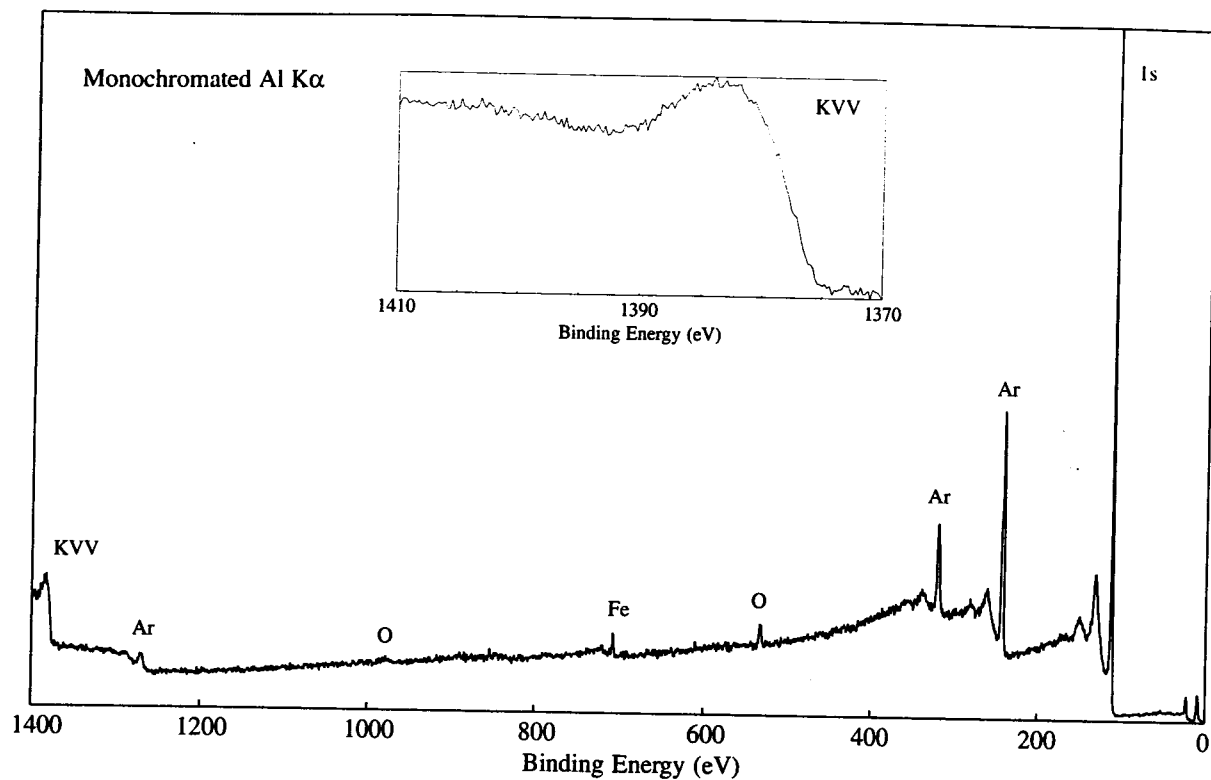
Abbreviations in the chemical state database are as follows: acac = acetyl acetate; metallocene = metal (C_5H_5)₂; Bu = butyl; Et = ethyl; Me = methyl; Ph = phenyl; OAc = acetate.



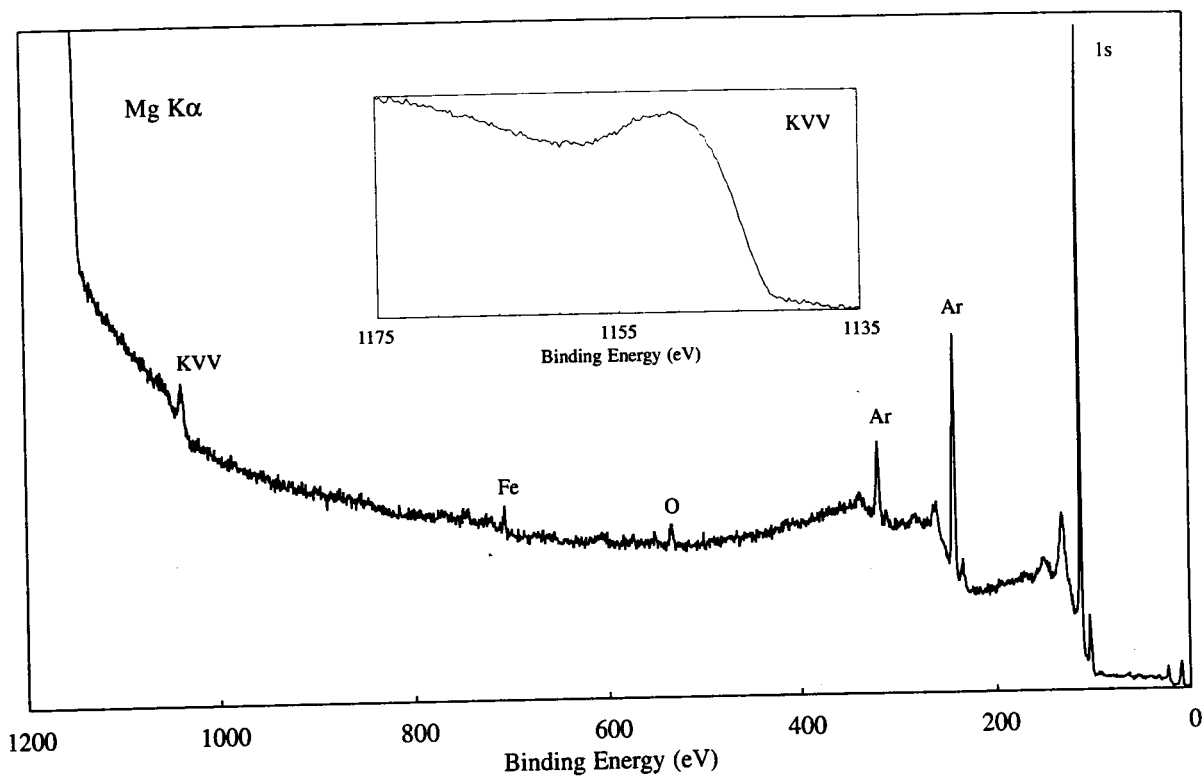


Compound Type	1s Binding Energy (eV)			
	54	55	56	57
Li				
LiBr				
LiCl				
LiF				
Li ₂ O				
LiOH				
Li ₂ CO ₃				
Li ₃ PO ₄				
Li ₄ P ₂ O ₇				
LiNbO ₃				

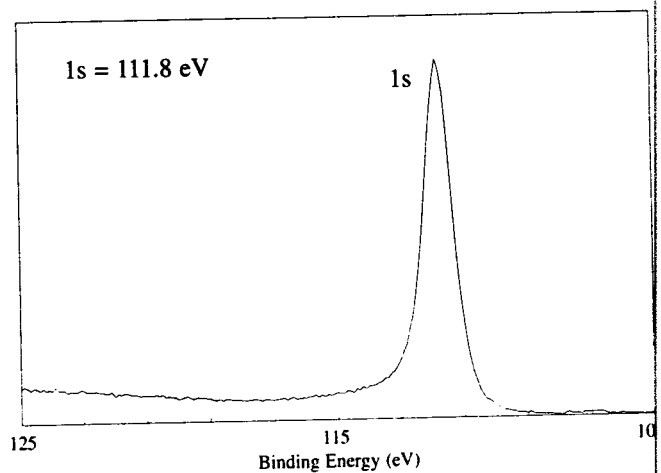


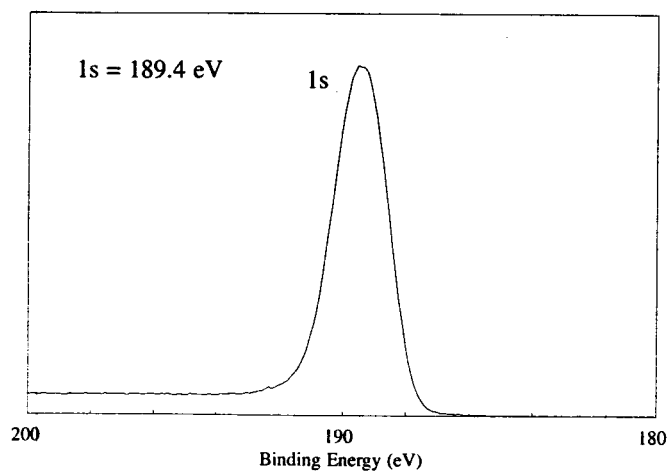
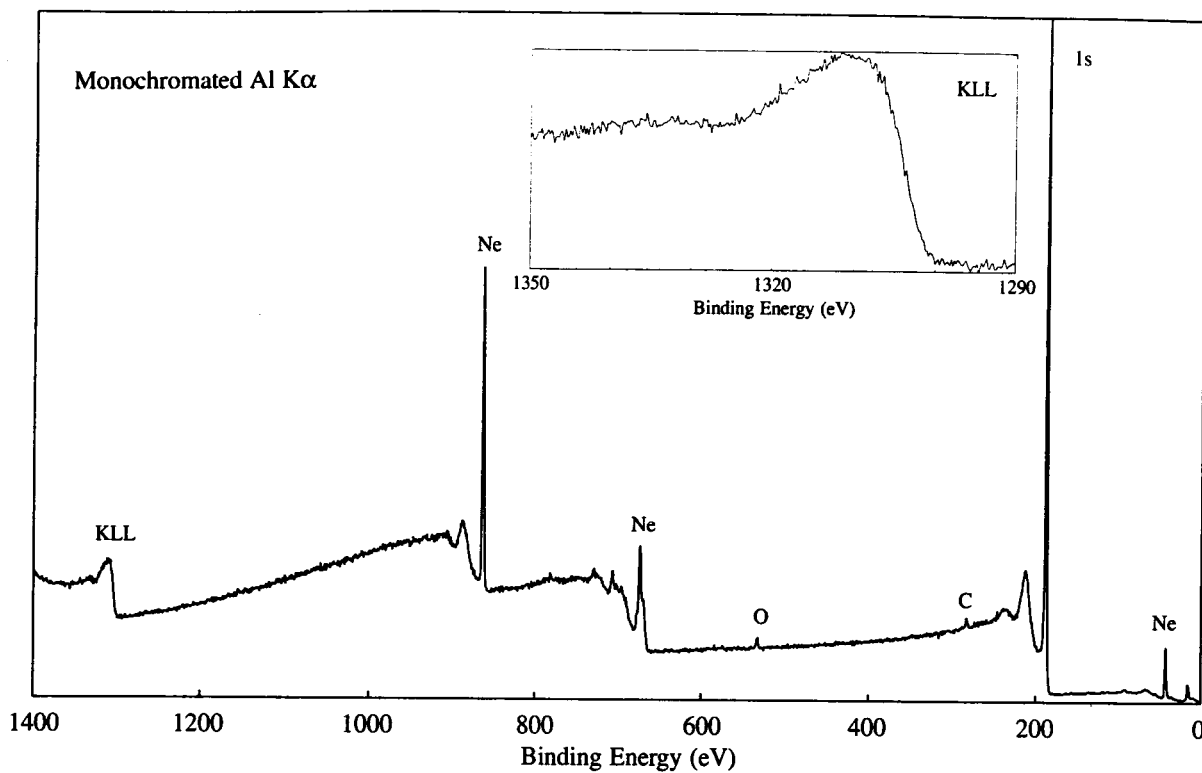


Line Positions (eV)	
<u>Photoelectron Lines</u>	
Is	112
<u>Auger Lines</u>	
KVV	
1384	(Al)
1151	(Mg)

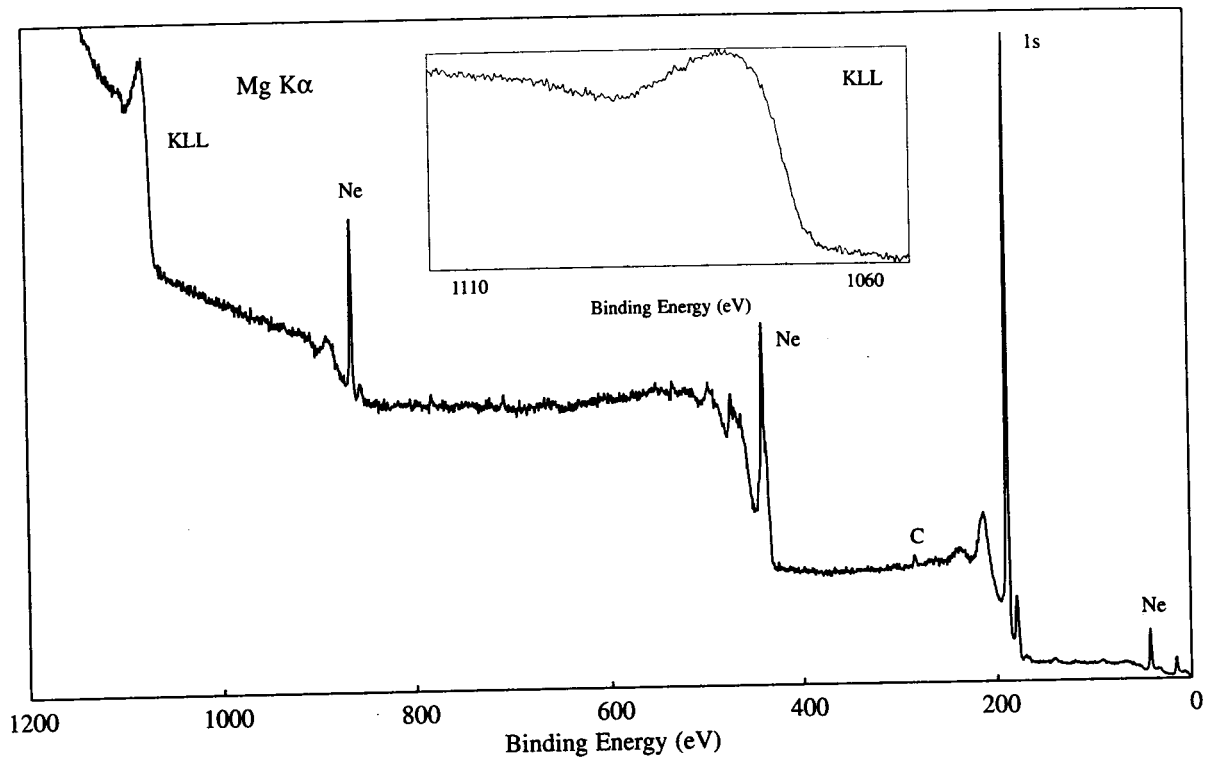


Compound Type	1s Binding Energy (eV)						
	111	112	113	114	115	116	117
Be		■					
BeO				■			
BeMoO ₄				■			
BeRh ₂ O ₄				■			
BeF ₂						■	
NaBeF ₃						■	
Na ₂ BeF ₄					■		

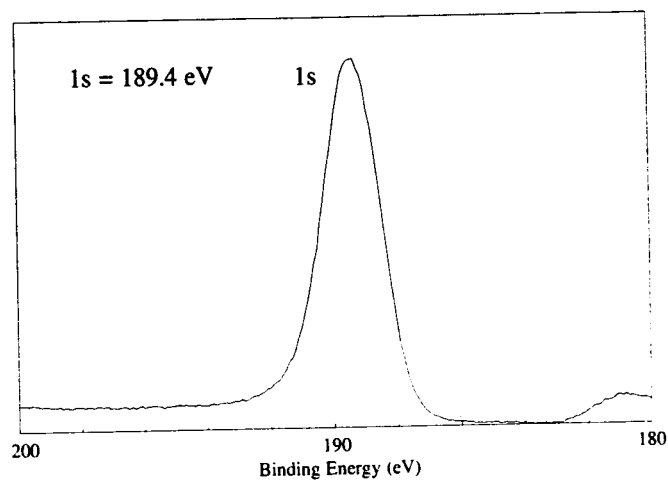


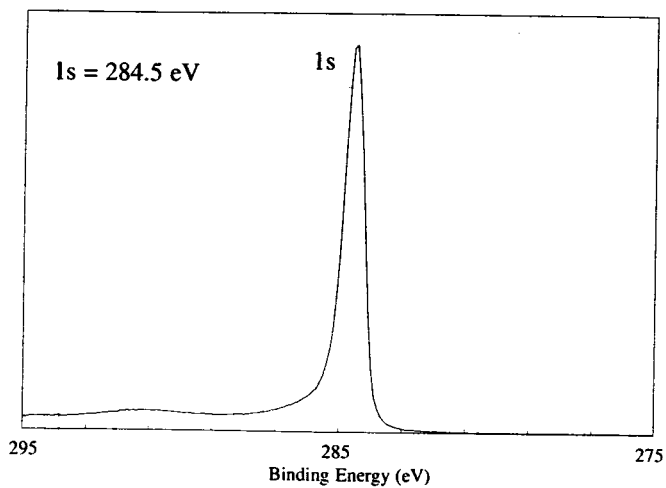
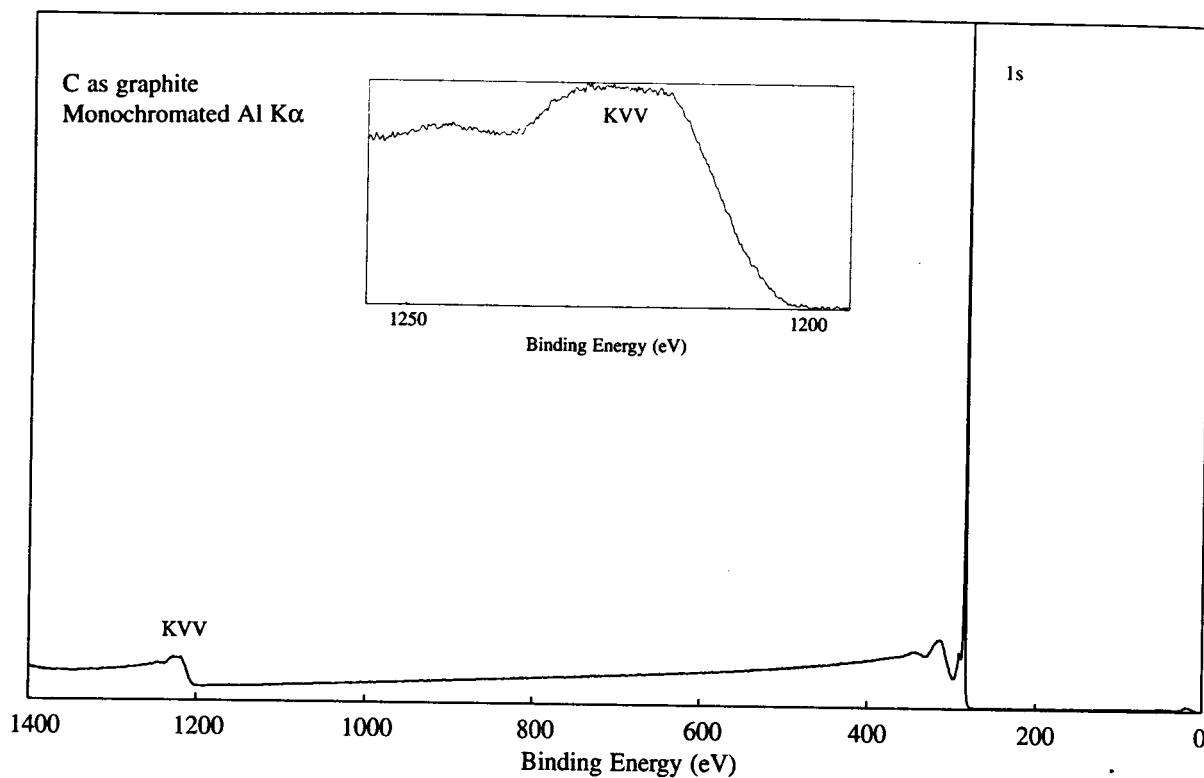


Line Positions (eV)	
<u>Photoelectron Lines</u>	
1s	189
<u>Auger Lines</u>	
KLL	
1310	(Al)
1077	(Mg)

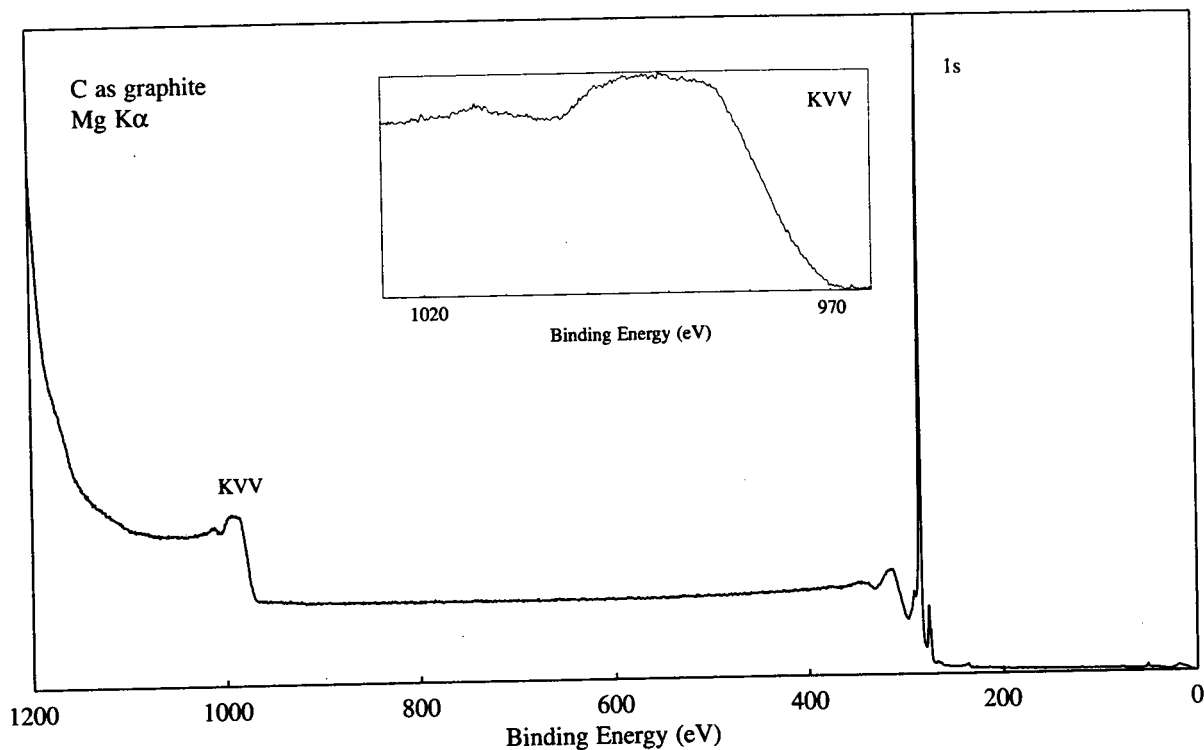


Compound Type	1s Binding Energy (eV)					
	186	188	190	192	194	196
B						
Boride						
BN						
B ₂ O ₃						
NaBF ₄						
NaBH ₄						
H ₃ BO ₃						
Na ₂ B ₄ O ₇ · 10H ₂ O						
B ₁₀ H ₁₄						

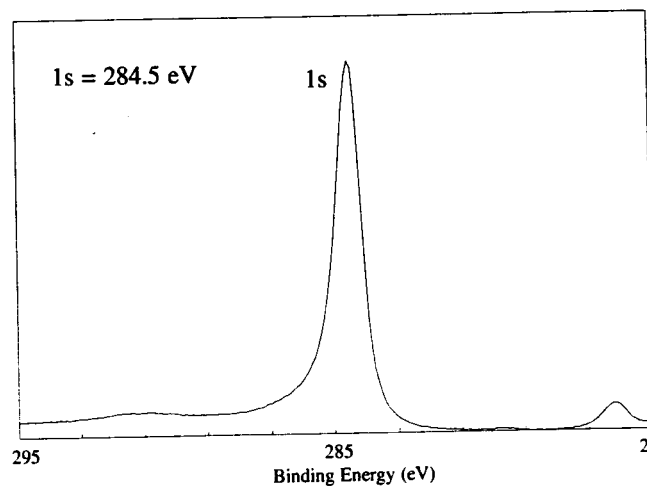


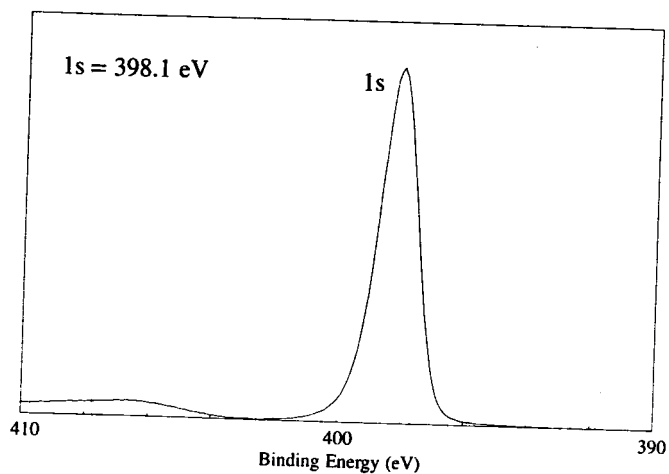
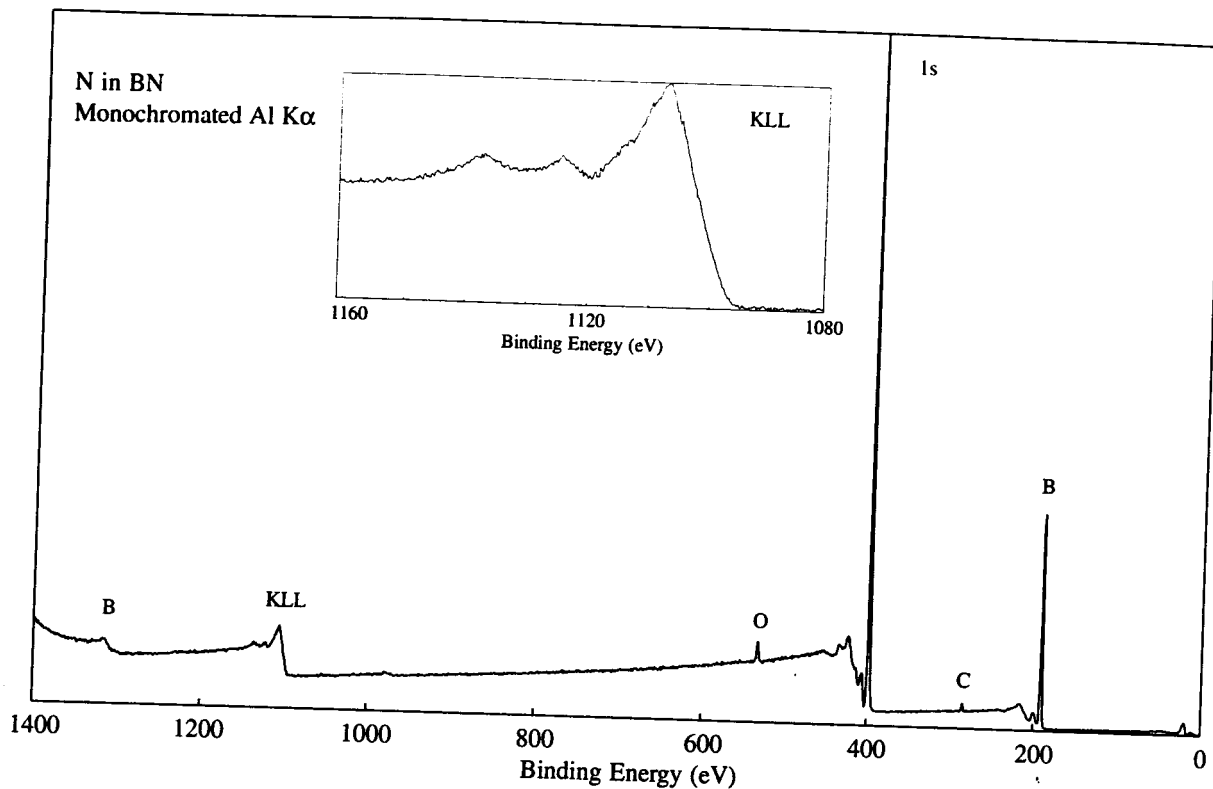


Line Positions (eV)	
<u>Photoelectron Lines</u>	
1s	285
<u>Auger Lines</u>	
KVV	
1223	(Al)
990	(Mg)

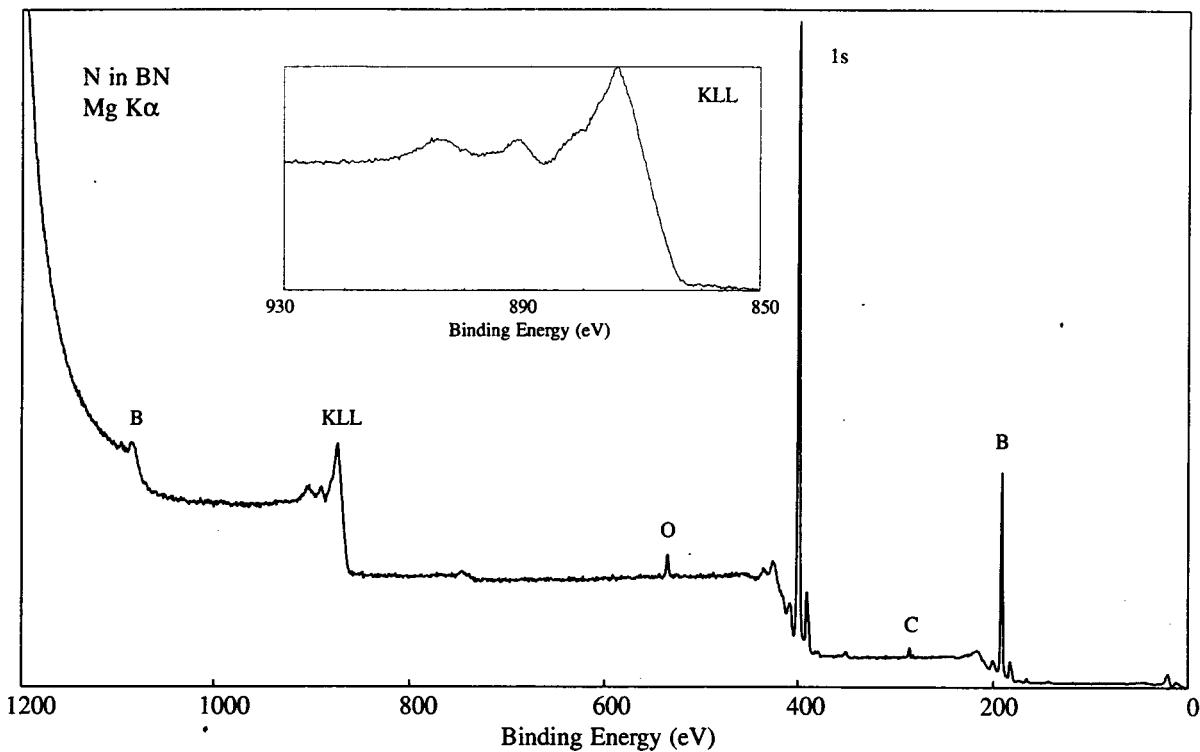


1s Binding Energy (eV)	
Compound Type	280 282 284 286 288 290 292 294
Carbide	281-283
Carbon	284-285
C with N	285-289
C with S	286-288
C with O	286-287
Alcohols	286-287
Ethers	286-287
Ketones/Aldehydes	286-287
Carboxyls	288-290
Carbonates	289-291
C with Cl	289-291
C with F	291-293
CHF	292-293
CF ₂	293-294
CF ₃	294-295

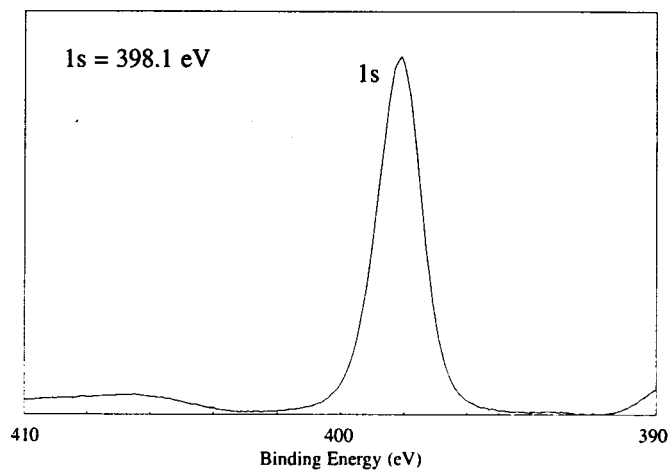


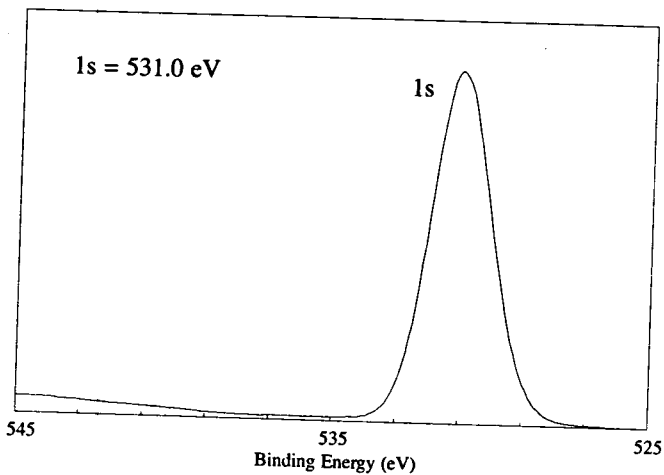
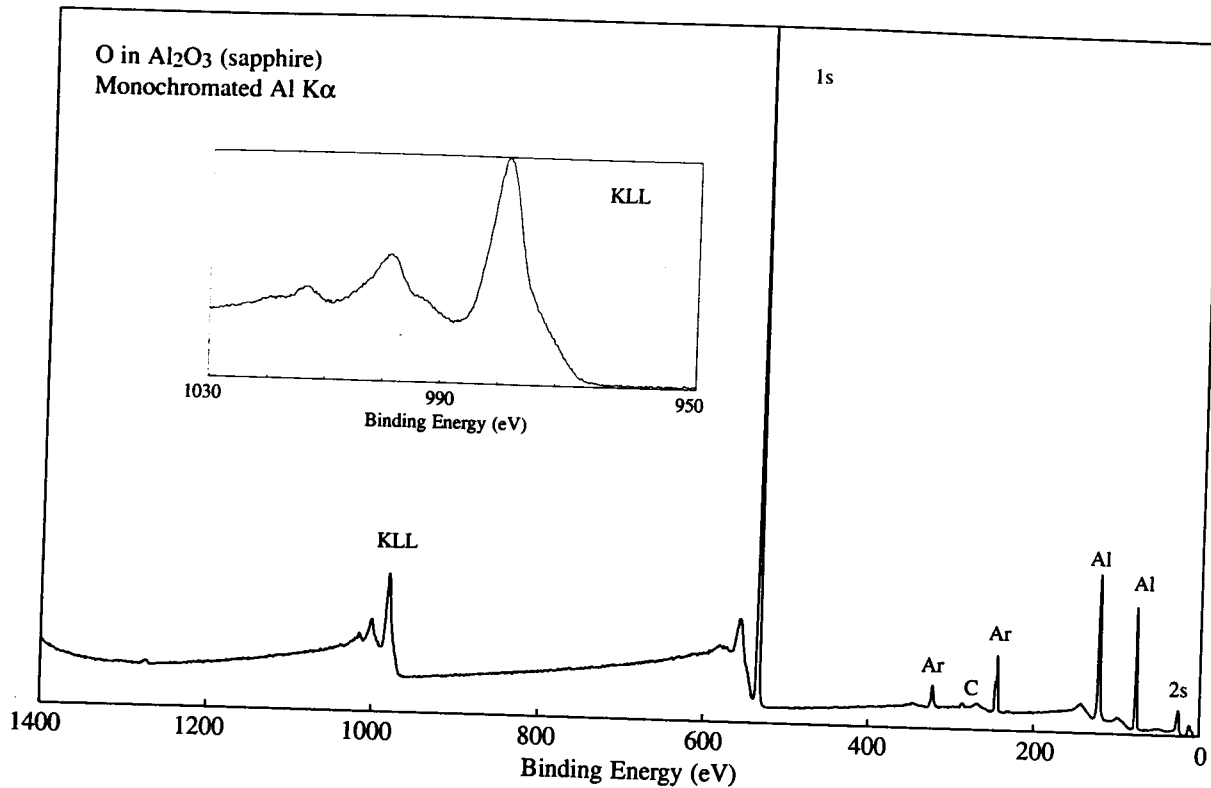


Line Positions (eV)	
<u>Photoelectron Lines</u>	
1s	398
<u>Auger Lines</u>	
KLL	
1107	(Al)
874	(Mg)

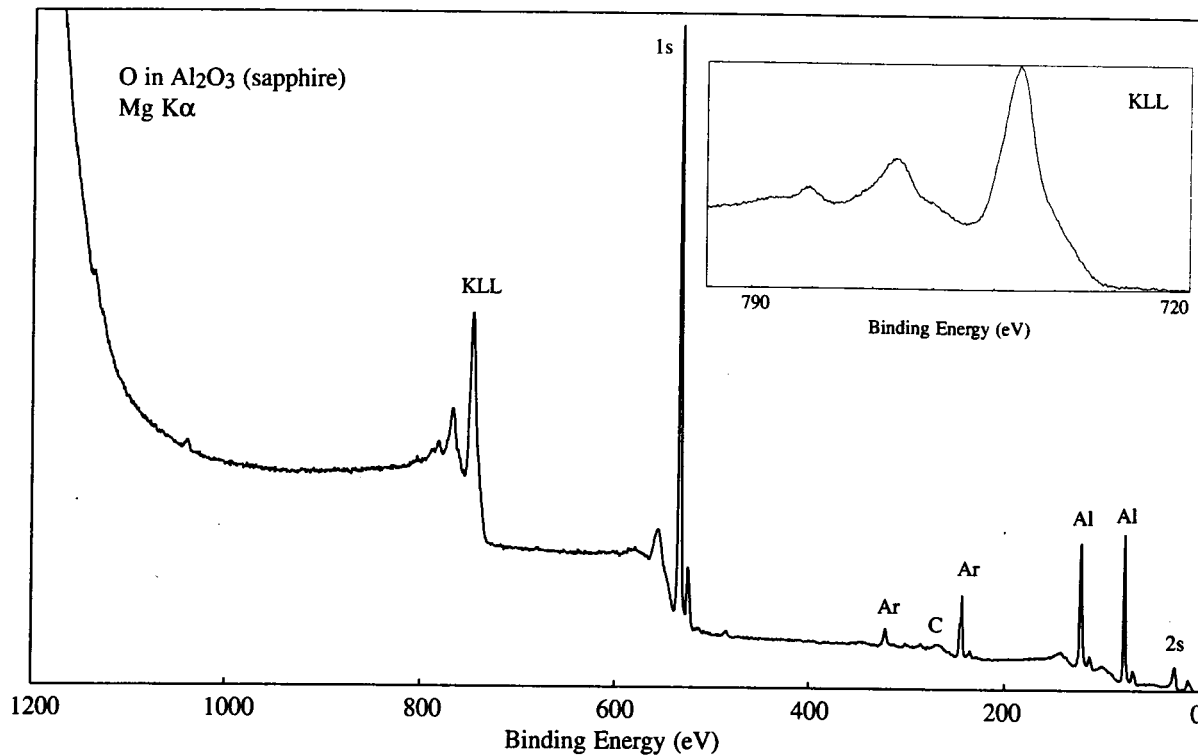


Compound Type	1s Binding Energy (eV)								
	396	398	400	402	404	406	408	410	
NH ₃			■						
Nitride	■	■							
BN		■							
Si ₃ N ₄		■							
Cyanides		■	■						
Nitrites					■				
Ammonium Salt				■	■				
Azide(N*NN*)		■							
Azide (NN*N)					■				
Nitrates							■		
Organic Matrix		■	■						

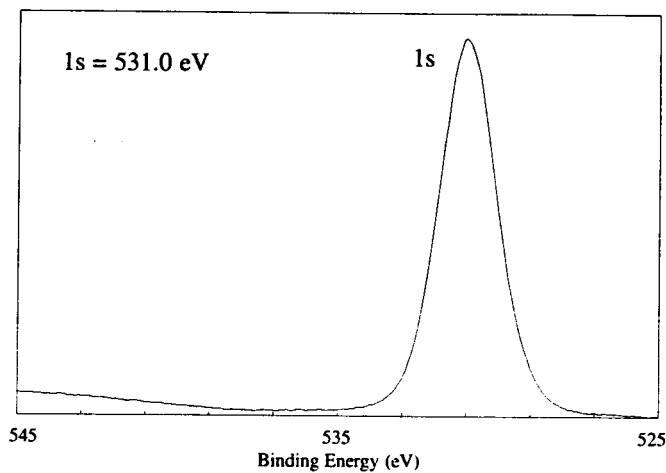


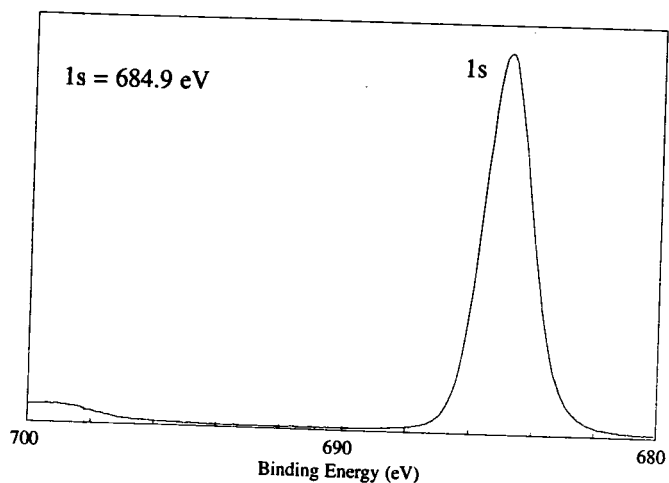
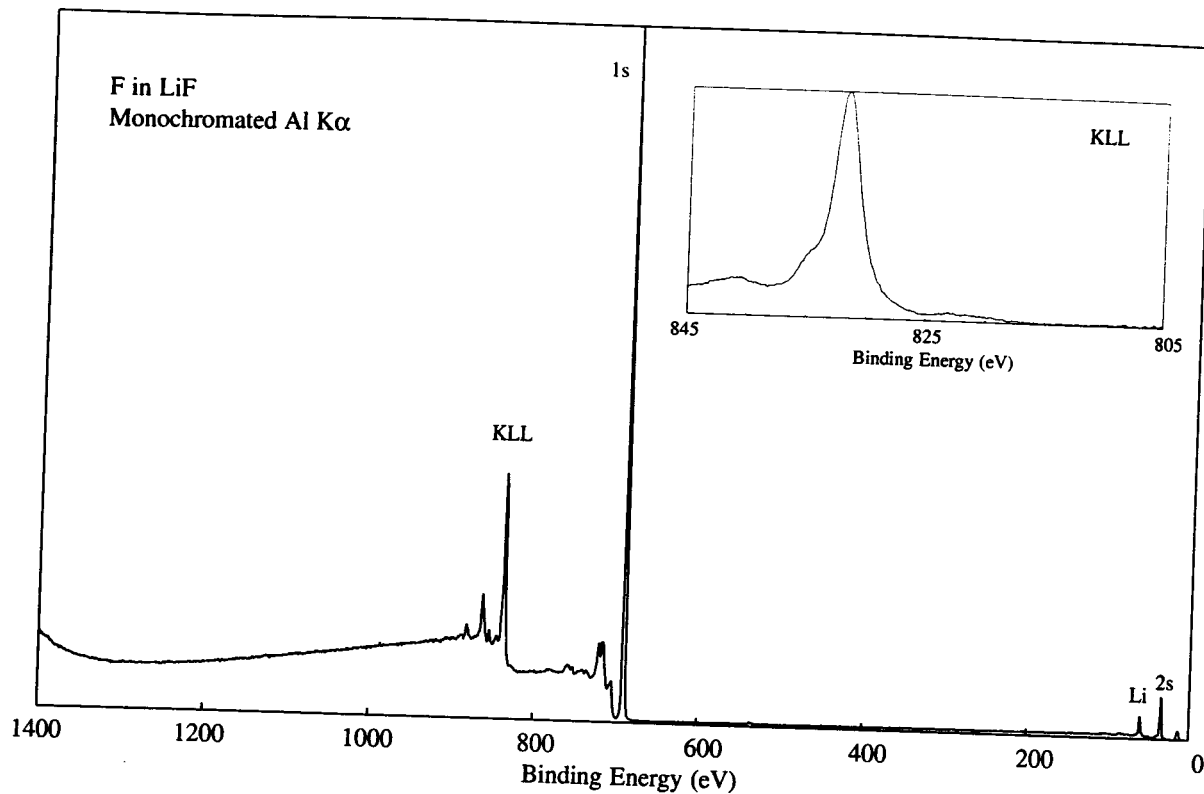


Line Positions (eV)			
<u>Photoelectron Lines</u>			
1s	2s		
531.	23		
<u>Auger Lines</u>			
KL ₁ L ₁	KL ₁ L ₂₃	KL ₂₃ L ₂₃	
1013	999	978	(Al)
780	766	745	(Mg)

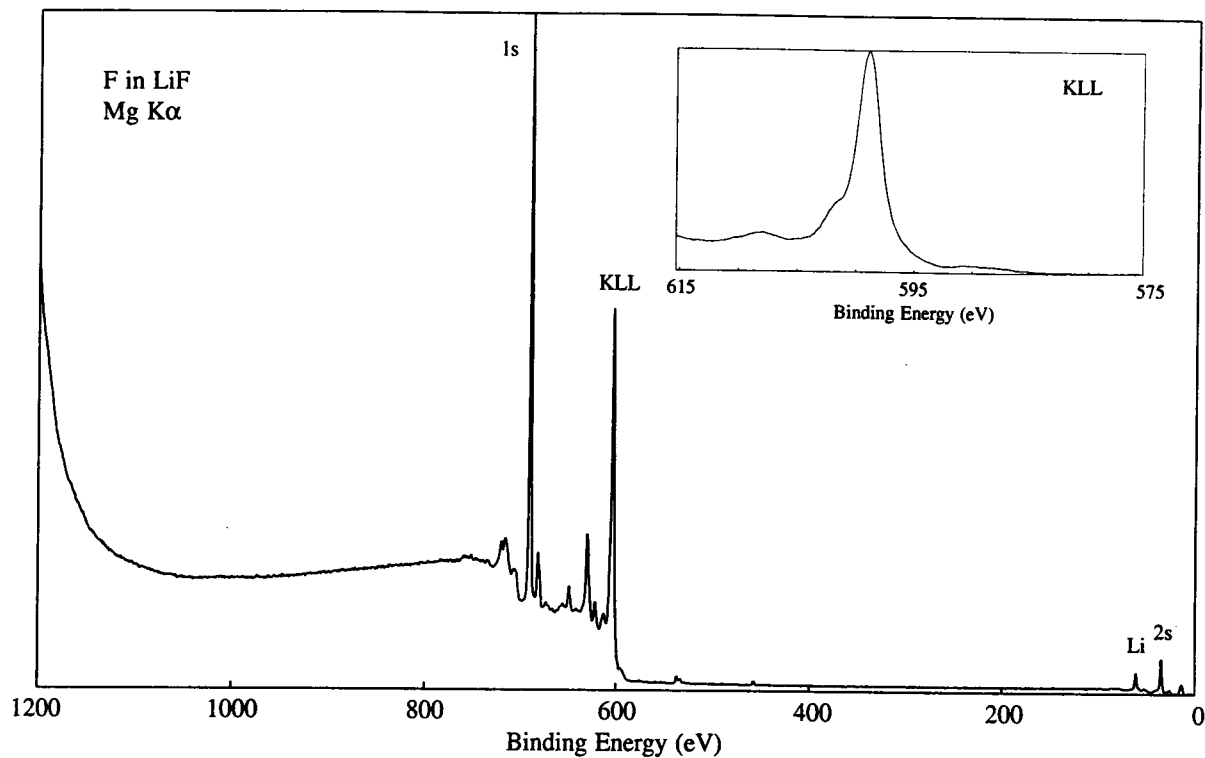


Compound Type	1s Binding Energy (eV)						
	528	529	530	531	532	533	534
Metal Oxides	[Bar spanning 528-531]						
Fe ₂ O ₃	[Bar spanning 528-531]						
SiO ₂	[Bar spanning 529-531]						
Hydroxides	[Bar spanning 530-532]						
Phosphates	[Bar spanning 530-533]						
Nitrates	[Bar spanning 530-533]						
Sulfates	[Bar spanning 531-533]						
Carbonates	[Bar spanning 530-532]						
Chlorates	[Bar spanning 531-532]						
Al ₂ O ₃	[Bar spanning 530-532]						
Silicones	[Bar spanning 531-532]						

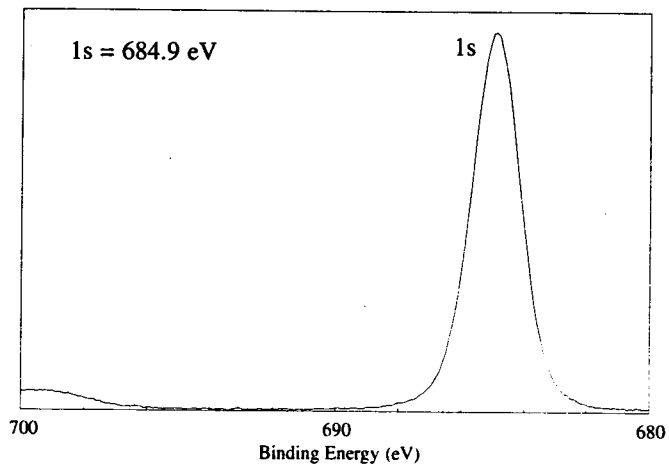


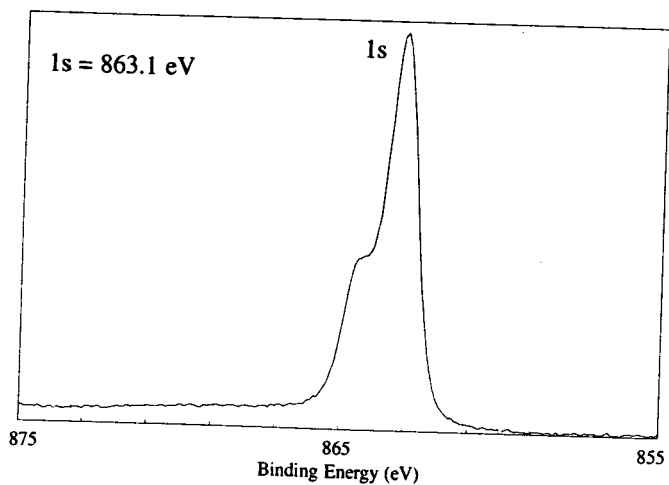
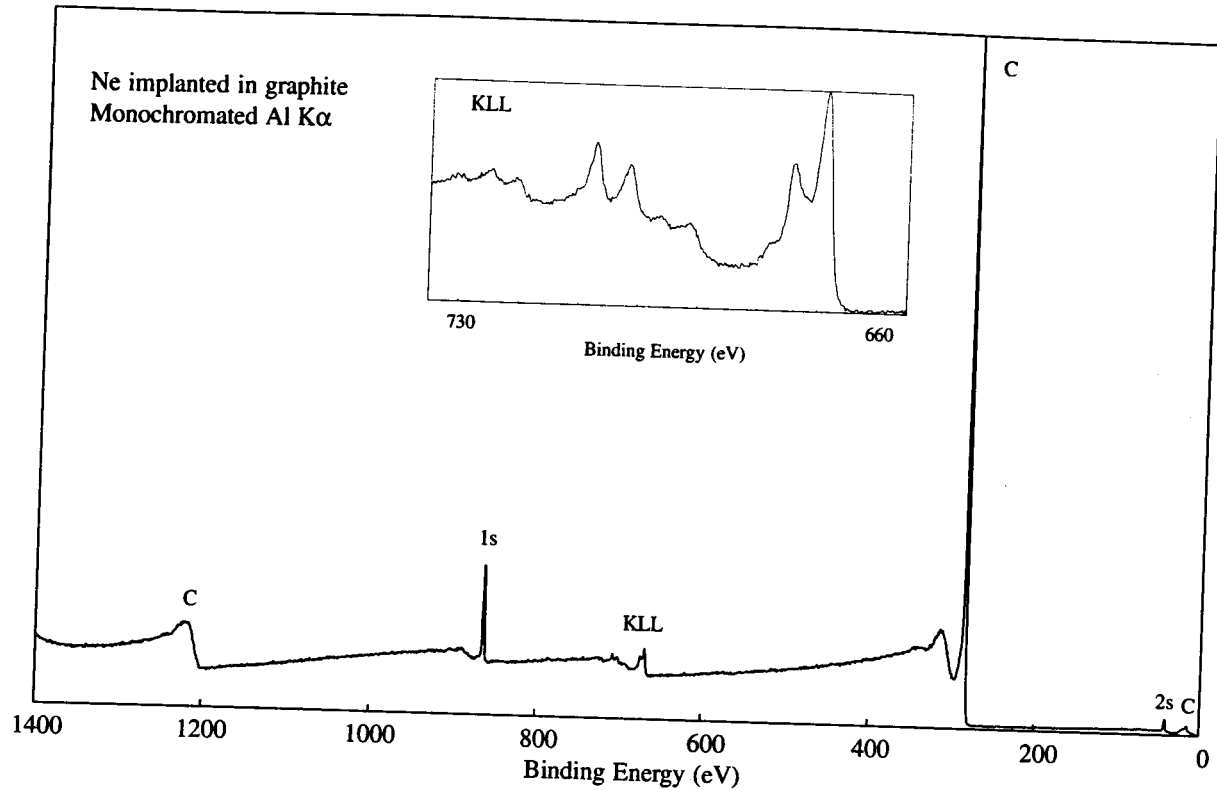


Line Positions (eV)		
<u>Photoelectron Lines</u>		
1s	2s	
685	30	
<u>Auger Lines</u>		
KL ₁ L ₁	KL ₁ L ₂₃	KL ₂₃ L ₂₃
877	858	832 (Al)
644	625	599 (Mg)

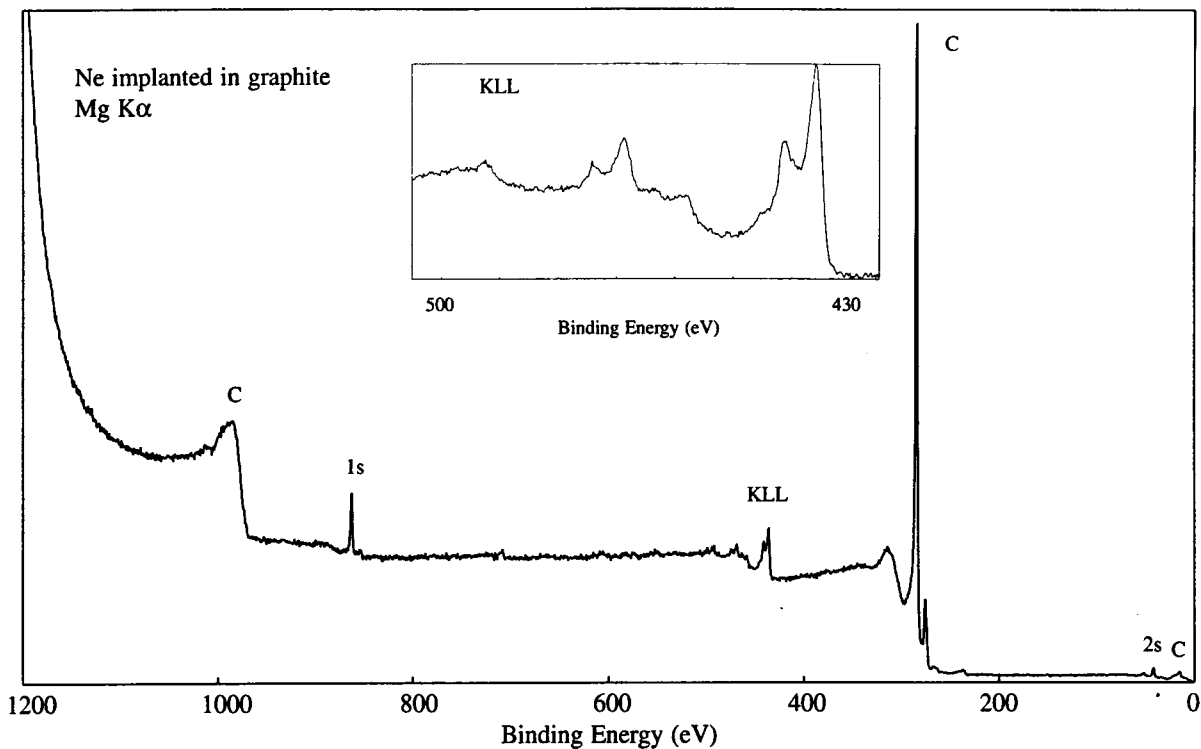


Compound Type	1s Binding Energy (eV)						
	683	684	685	686	687	688	689
KF		■					
LiF			■				
NaF		■					
BaF ₂	■	■					
MgF ₂				■			
AlF ₃ · 3H ₂ O				■			
NaBF ₄					■		
Na ₂ SiF ₆					■		
p-(CF ₂ =CF ₂)							■
EtNH ₂ BF ₃				■			
Ph ₃ PBF ₃				■			

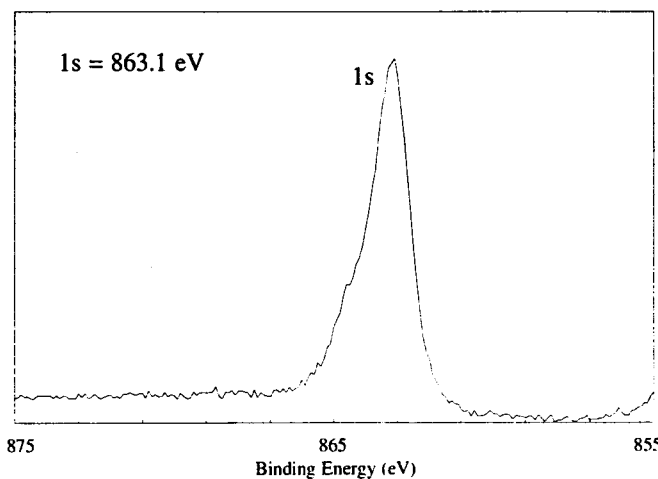


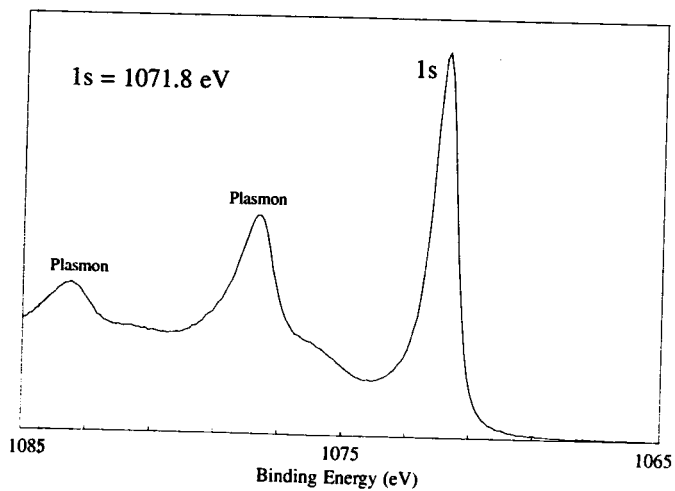
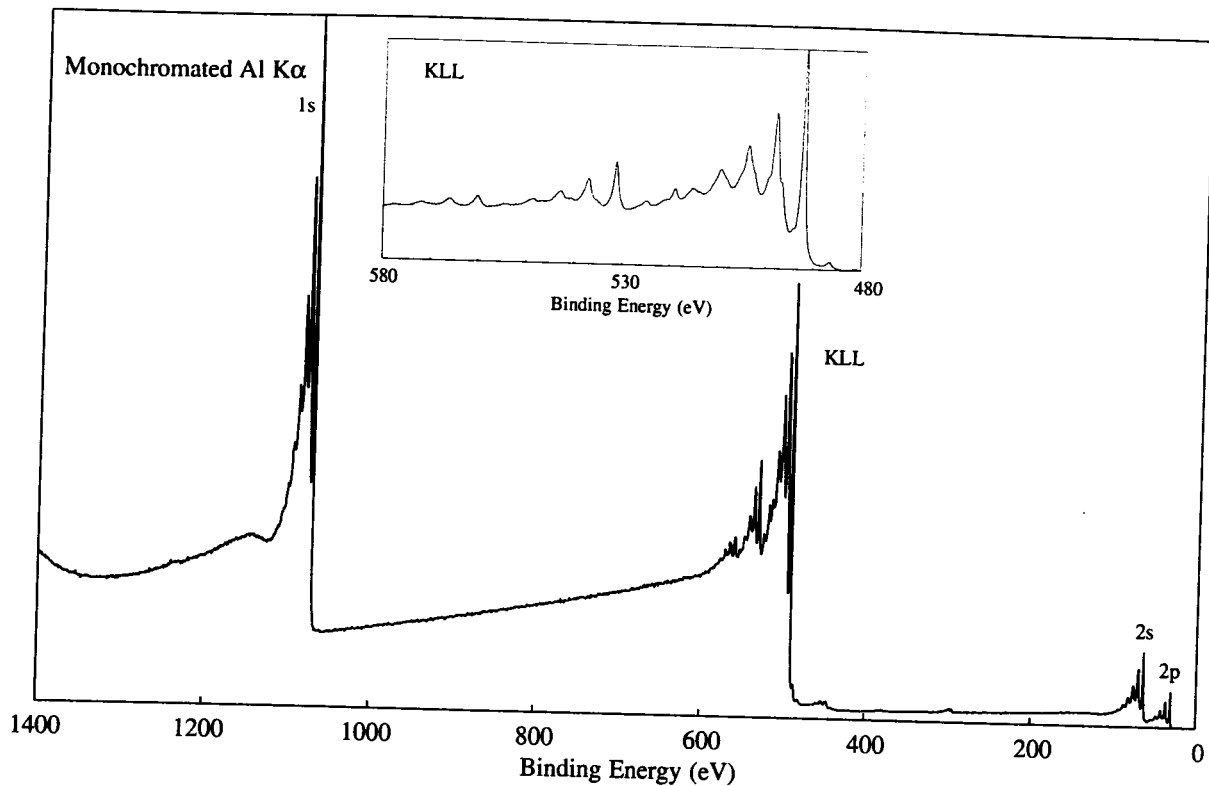


Line Positions (eV)			
<u>Photoelectron Lines</u>			
1s	2s	2p	
863	41	14	
<u>Auger Lines</u>			
KL ₁ L ₁	KL ₁ L ₂₃	KL ₂₃ L ₂₃	
725	702	669	(Al)
492	469	436	(Mg)

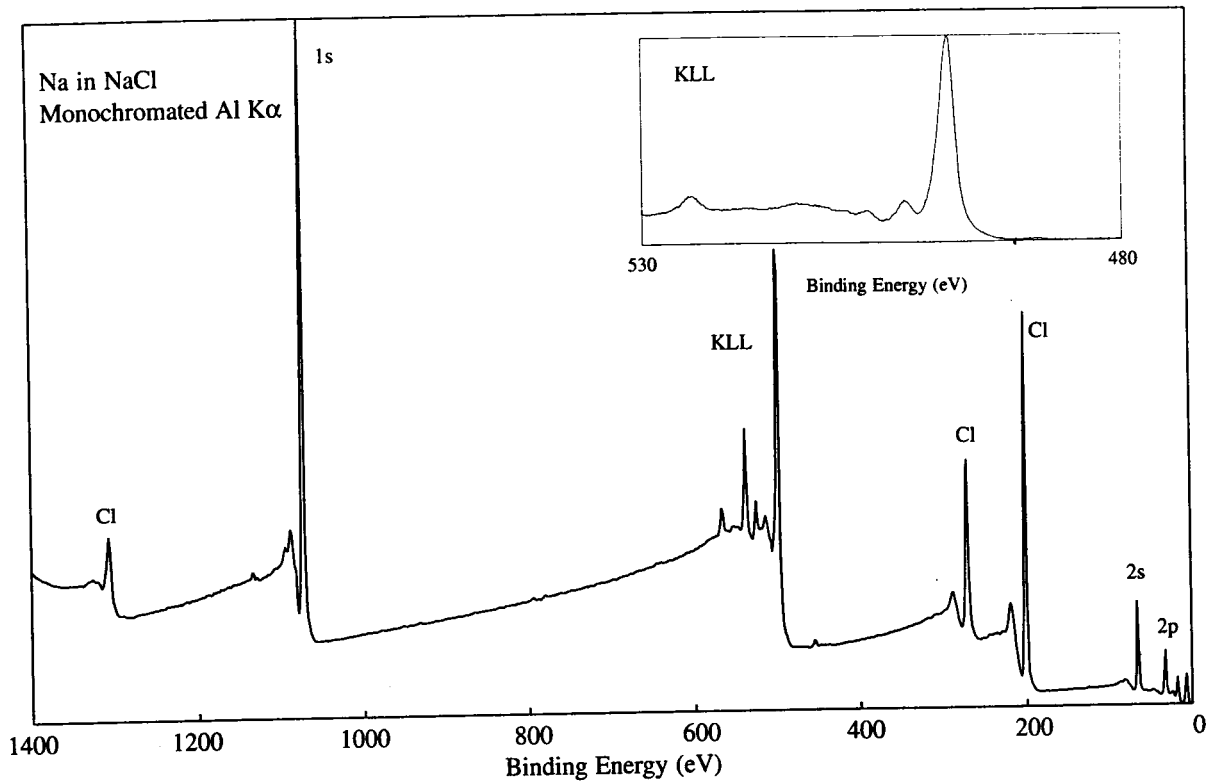


Compound Type	1s Binding Energy (eV)			
	861	862	863	864
Ne in Ag			■	
Ne in Au	■			
Ne in Cu		■		
Ne in Fe				■
Ne in graphite			■	

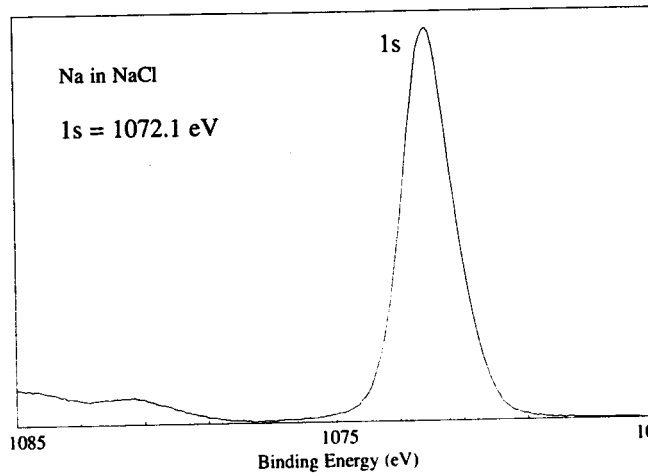


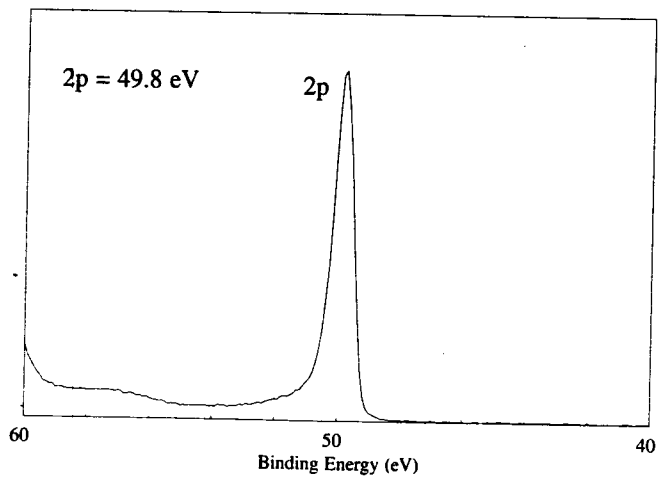
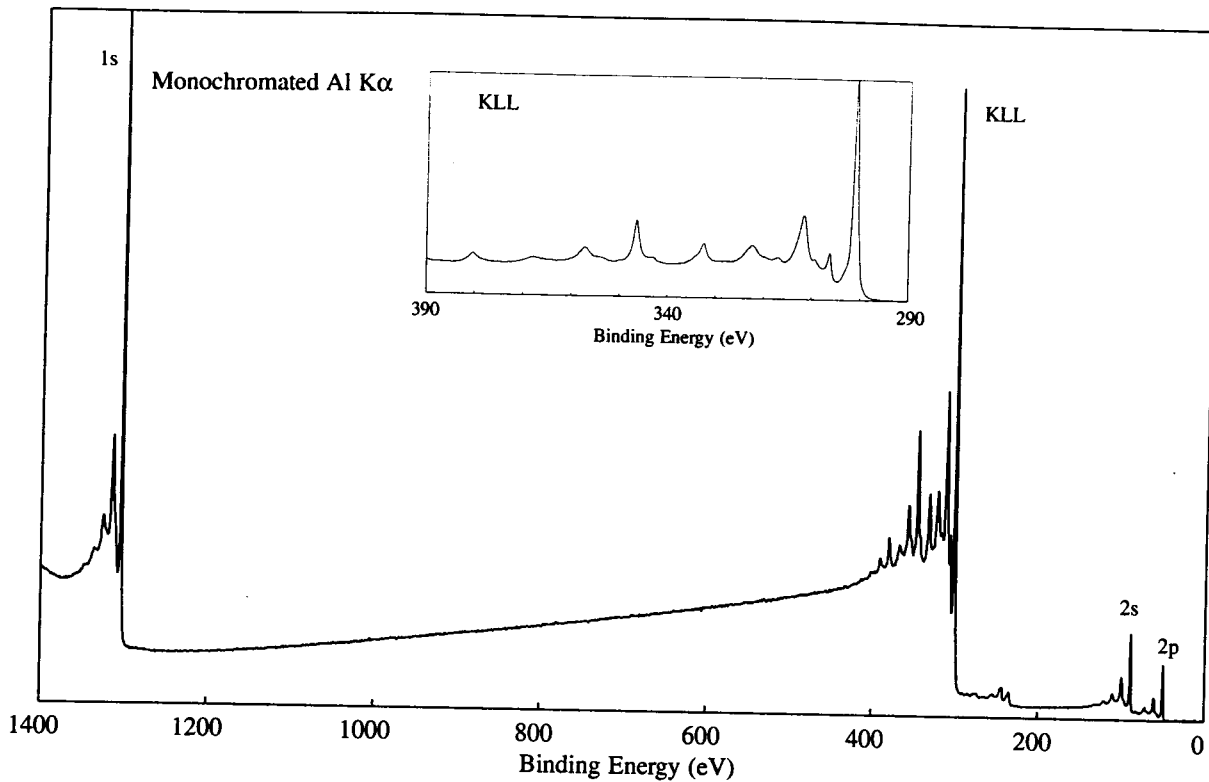


Line Positions (eV)			
Photoelectron Lines			
1s	2s	2p	
1072	64	31	
Auger Lines			
KL ₁ L ₁	KL ₁ L ₂₃	KL ₂₃ L ₂₃	
561	532	493	(Al)
328	299	260	(Mg)

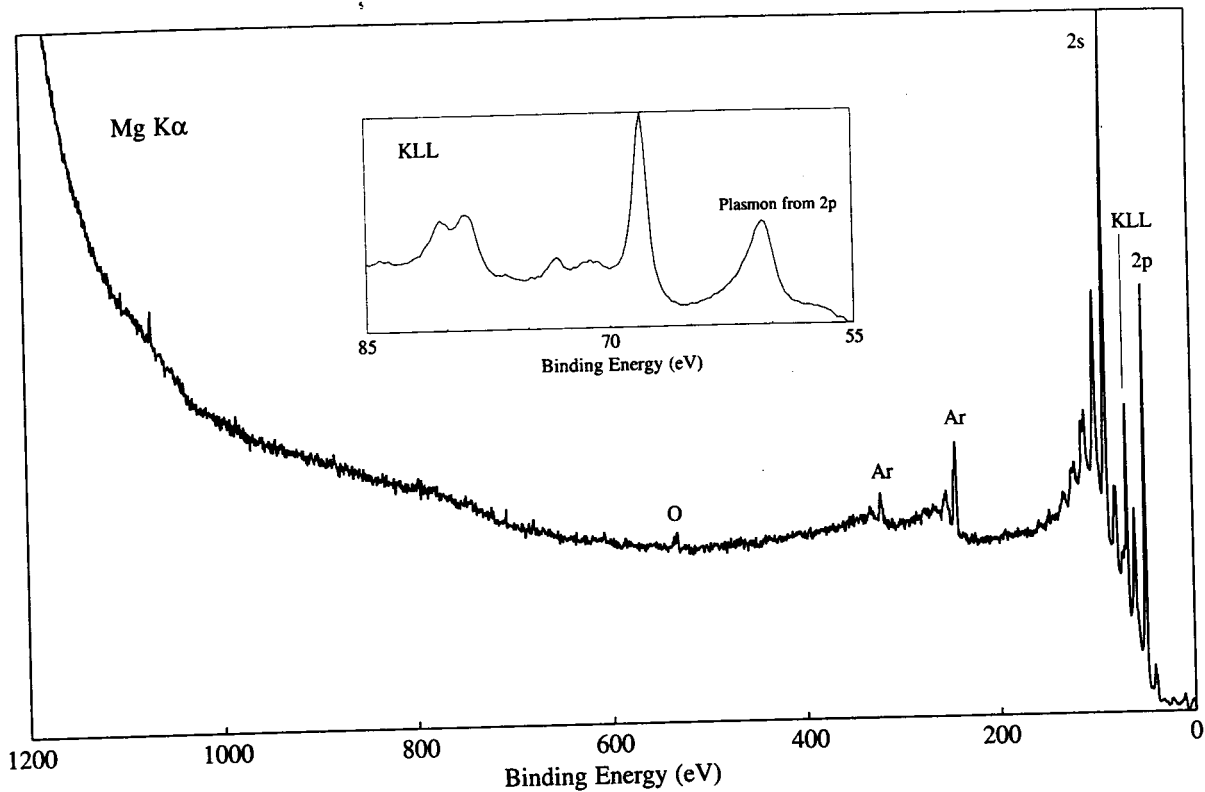


Compound Type	1s Binding Energy (eV)			
	1070	1071	1072	1073
Na			█	
NaI			█	
NaBr			█	
NaCl			█	
NaF		█		
Na ₂ CO ₃		█		
Na ₂ S ₂ O ₃		█		
Na ₂ SO ₄		█		
Na ₄ P ₂ O ₇	█	█		
NaH ₂ PO ₄			█	
Mol Sieve			█	

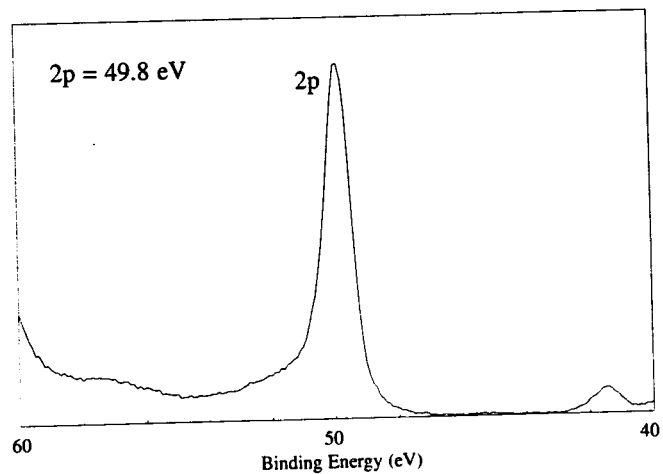


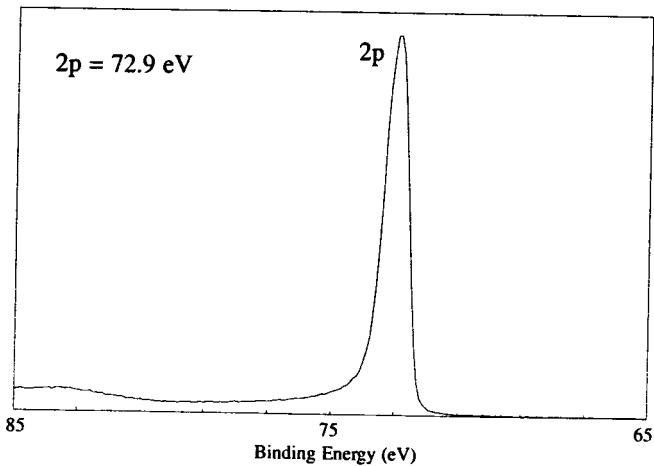
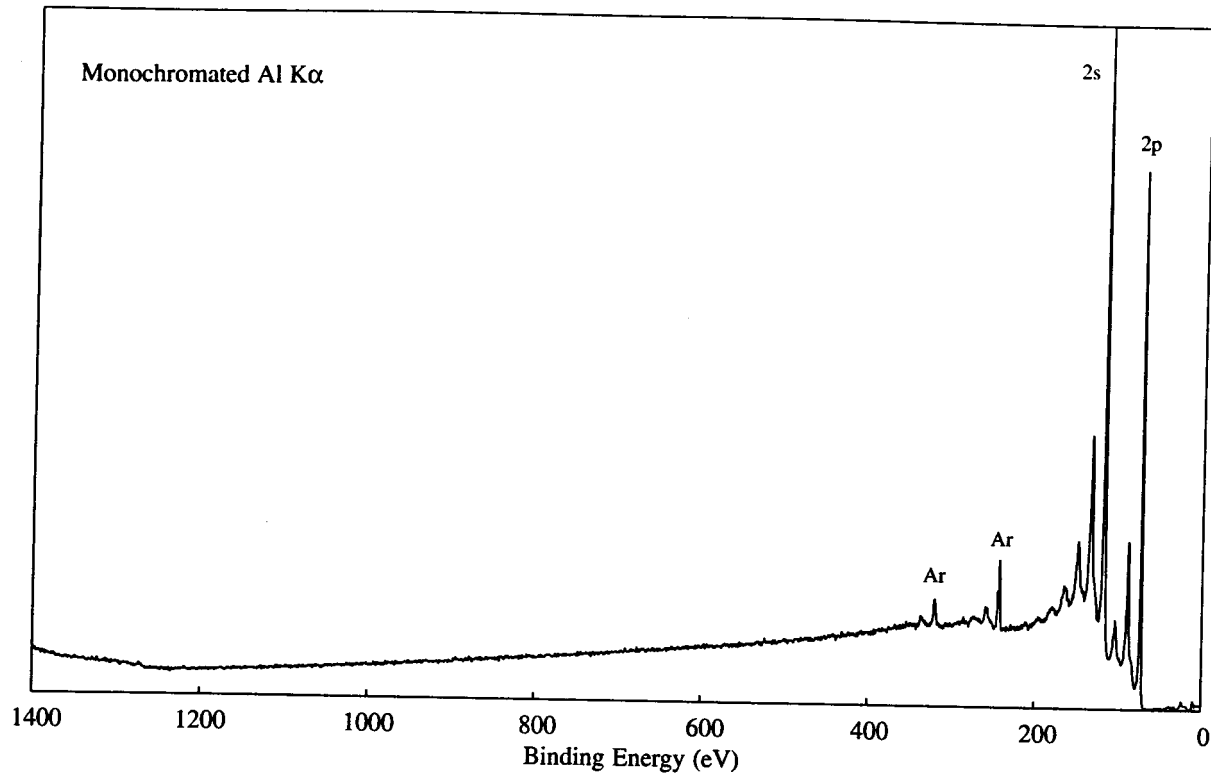


Line Positions (eV)			
<u>Photoelectron Lines</u>			
1s	2s	2p	
1303	89	50	
<u>Auger Lines</u>			
KL ₁ L ₁	KL ₁ L ₂₃	KL ₂₃ L ₂₃	
381	347	301	(Al)
148	114	68	(Mg)

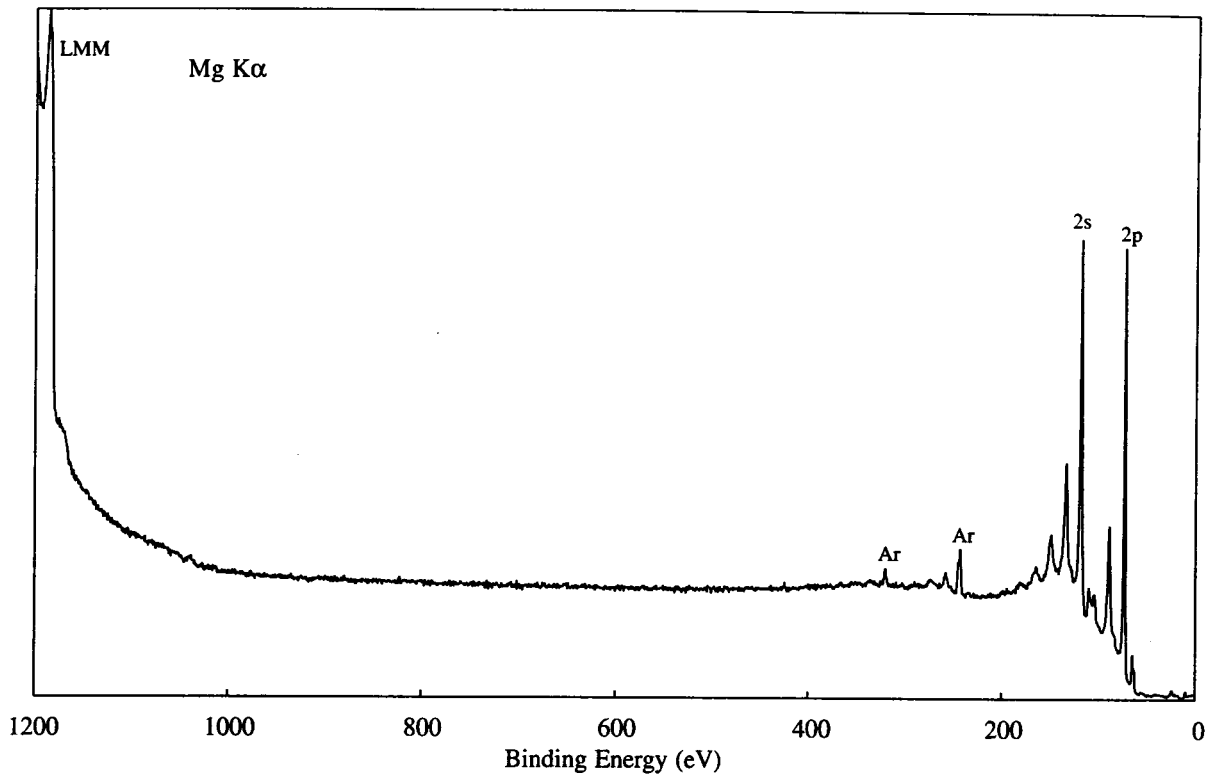


Compound Type	2p Binding Energy (eV)			
	48	49	50	51
Mg			■	
Mg ₂ Cu			■	
Mg ₃ Bi ₂				■
MgF ₂				■
Mg(OH) ₂		■		
MgAl ₂ O ₄			■	

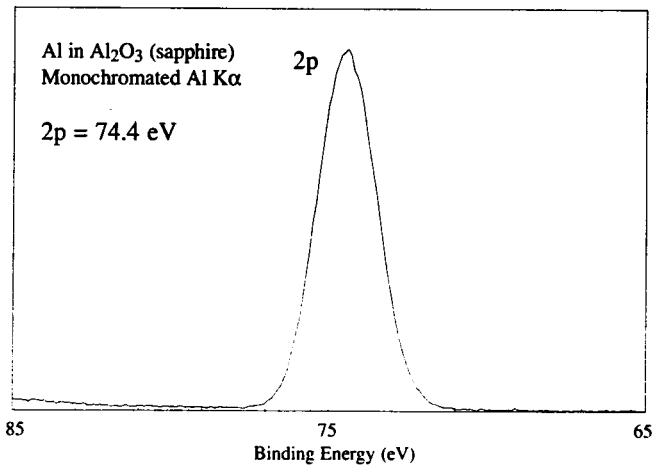


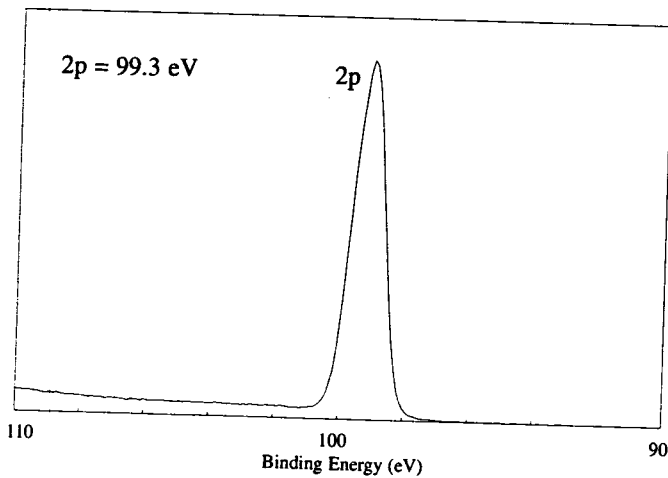
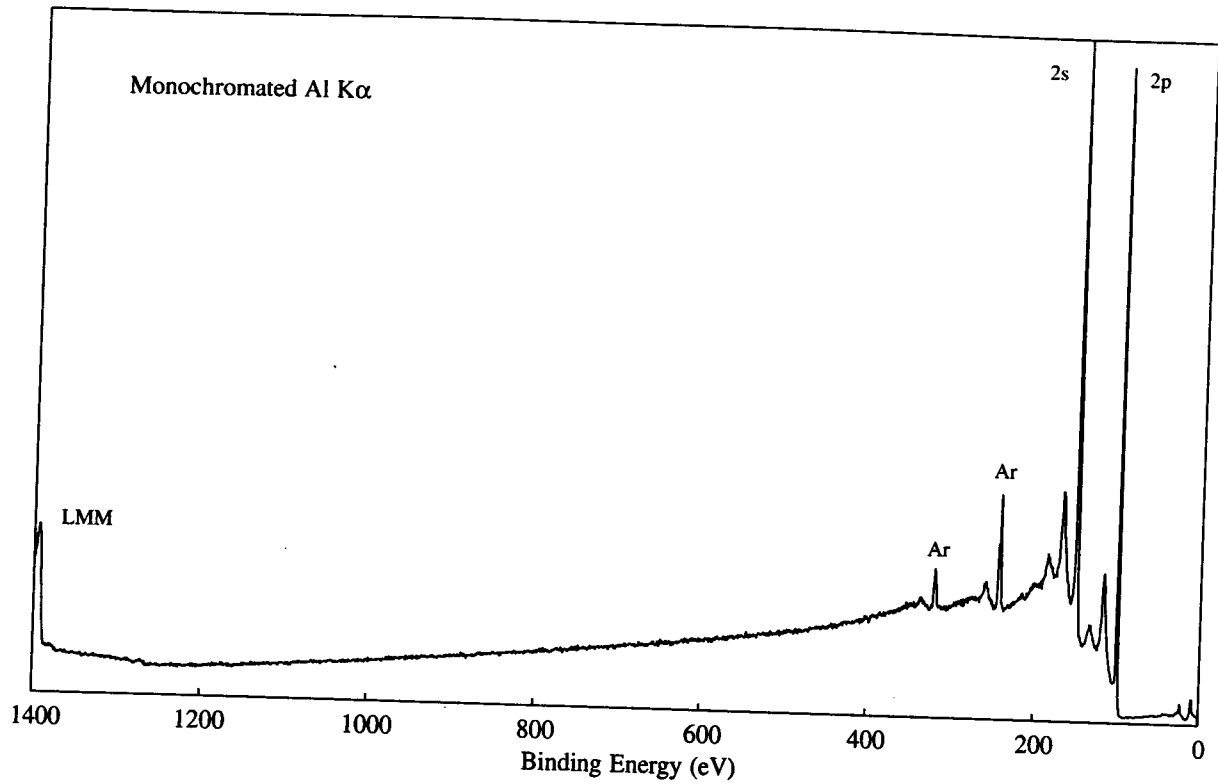


Line Positions (eV)	
<u>Photoelectron Lines</u>	
2s	2p
118	73
<u>Auger Lines</u>	
L ₂₃ M ₁ M ₂₃	
1419	(Al)
1186	(Mg)

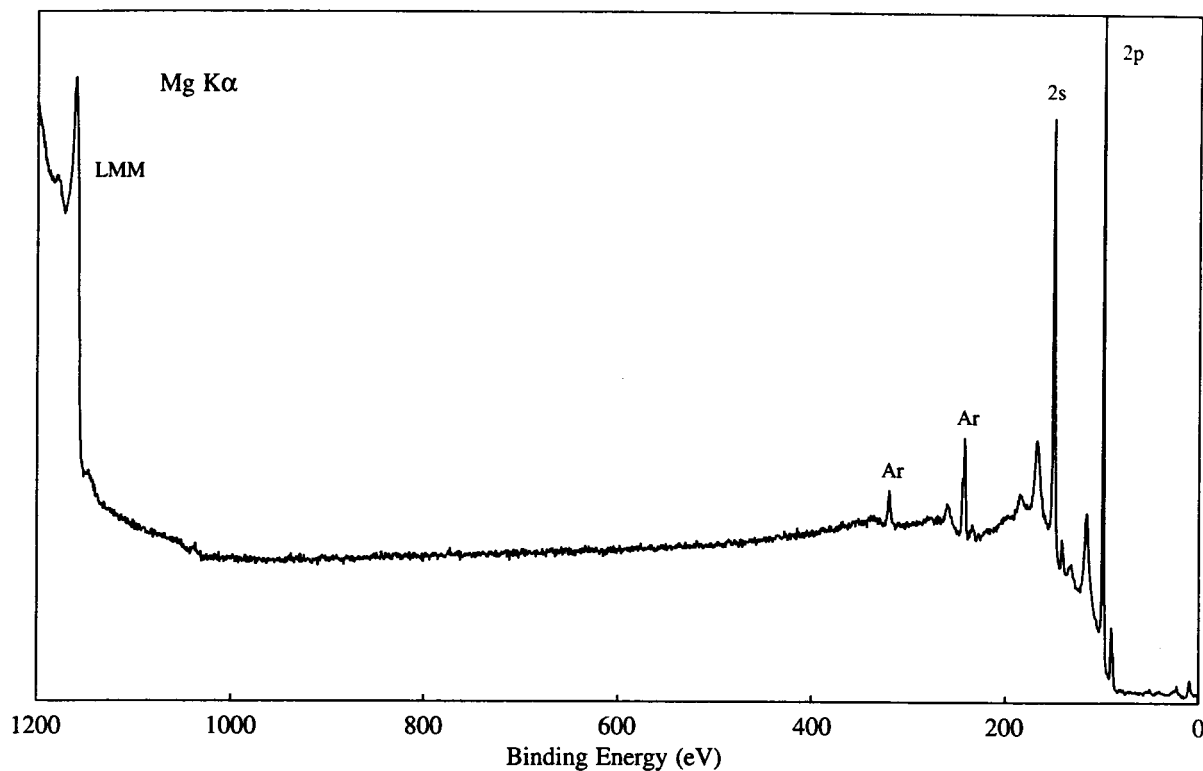


Compound Type	2p Binding Energy (eV)					
	72	73	74	75	76	77
Al		■				
AlAs			■			
AlGaAs			■			
LiAlH ₄					■	
Halides				■	■	
AlF ₃						■
Oxides				■		
Al ₂ O ₃ , sapphire			■	■		
Al ₂ O ₃ , alpha			■	■		
Al ₂ O ₃ , gamma			■	■		
AlOOH, boehmite			■	■		

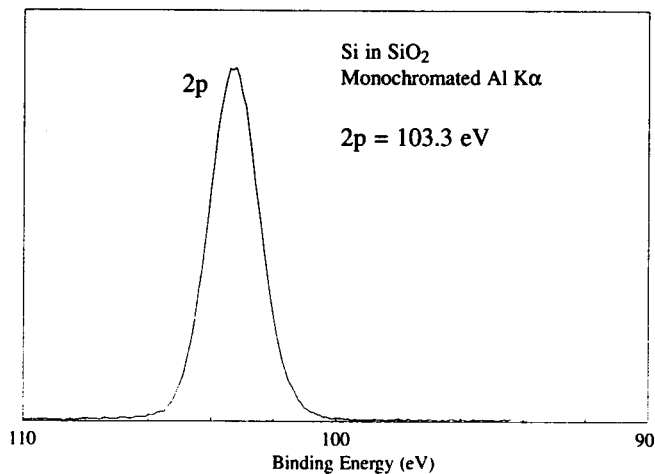


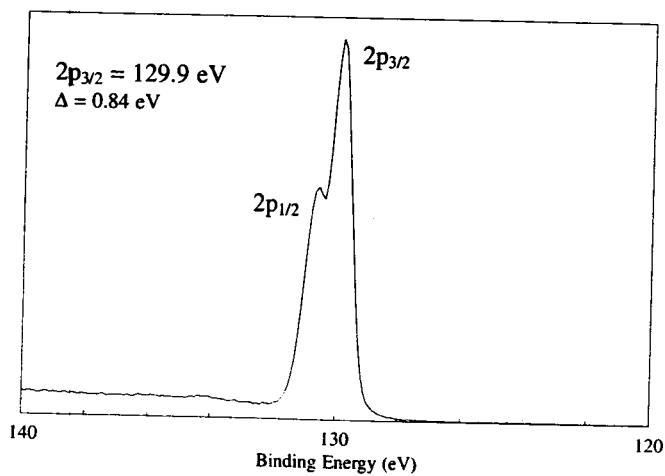
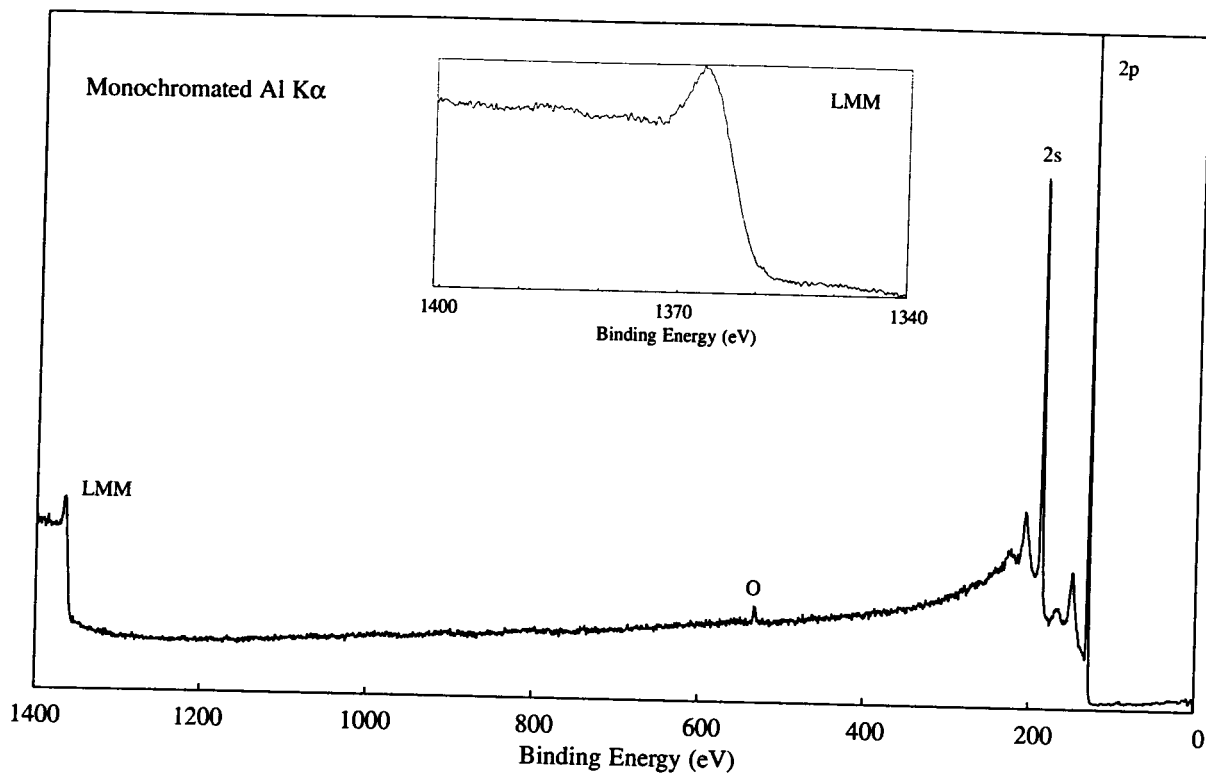


Line Positions (eV)	
<u>Photoelectron Lines</u>	
2s	2p
151	99
<u>Auger Lines</u>	
L ₂₃ M ₂₃ M ₂₃	
1394	(Al)
1161	(Mg)

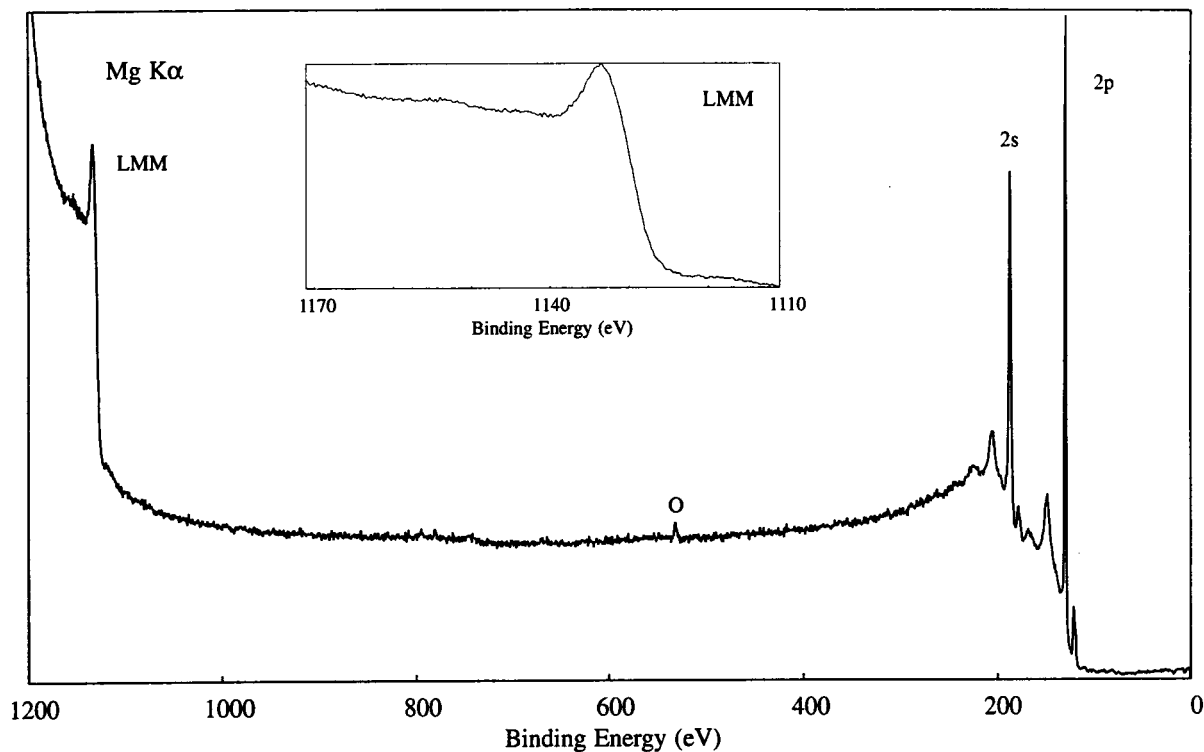


Compound Type	2p Binding Energy (eV)			
	98		101	104
Silicides		■		
Silicon	■			
Carbides		■		
Nitrides			■	
Silicones (Silanes)			■	
Silicates			■	
Silica <chem>SiO2</chem>				■

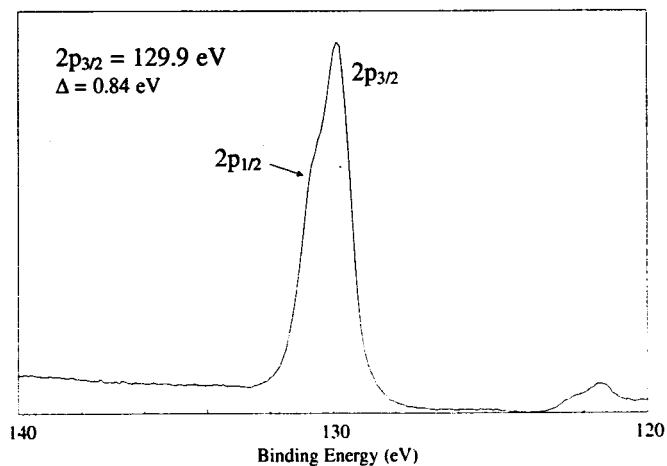


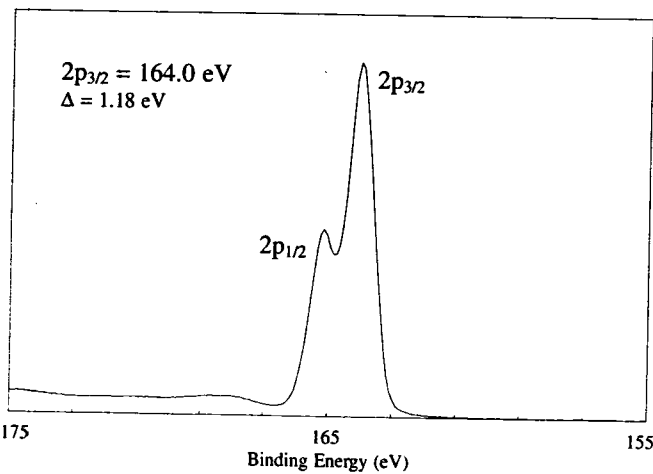
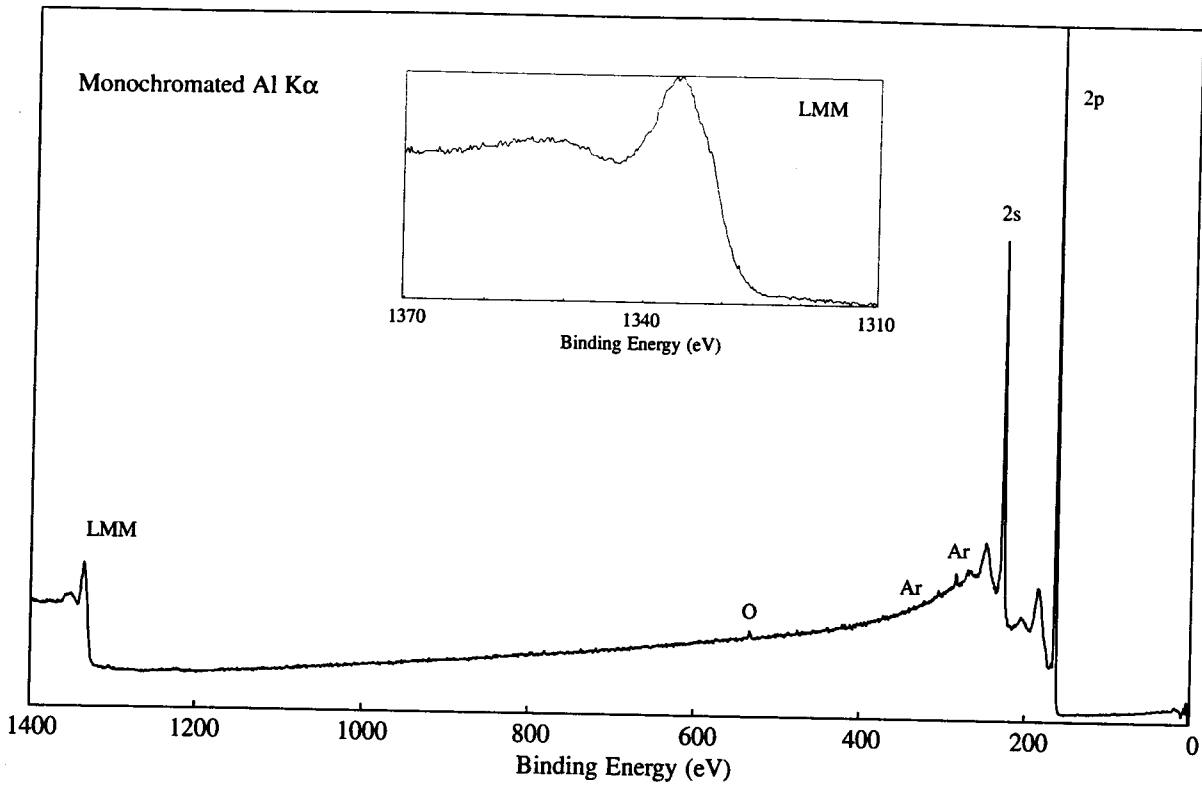


Line Positions (eV)			
<u>Photoelectron Lines</u>			
2s	2p _{1/2}	2p _{3/2}	3s
188	131	130	14
<u>Auger Lines</u>			
L ₂₃ M ₂₃ M ₂₃			
1367		(Al)	
1134		(Mg)	

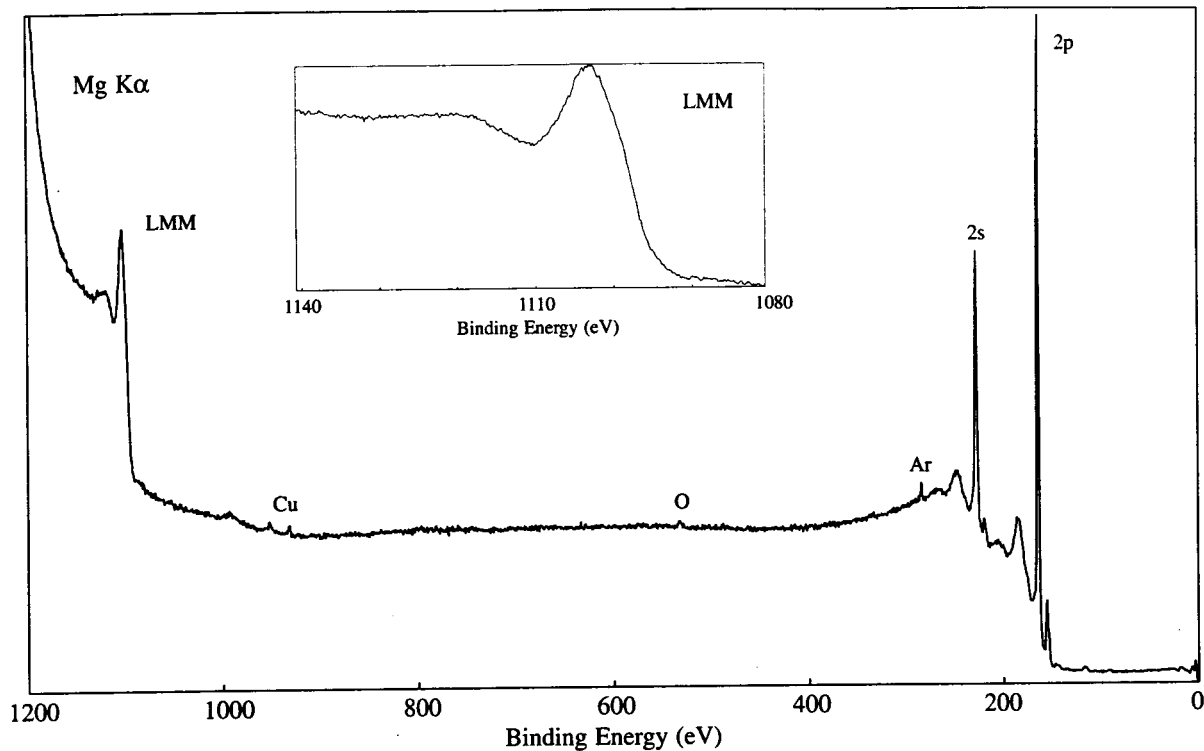


Compound Type	2p Binding Energy (eV)							
	128	129	130	131	132	133	134	135
P			■					
P (red)			■					
GaP		■	■					
InP		■	■					
Phosphate					■	■		
Pyrophosphate					■	■		
Metaphosphate							■	
P ₄ O ₁₀								■
Ph ₃ P				■				
Ph ₂ PSH					■			
(PhO) ₃ PO							■	■

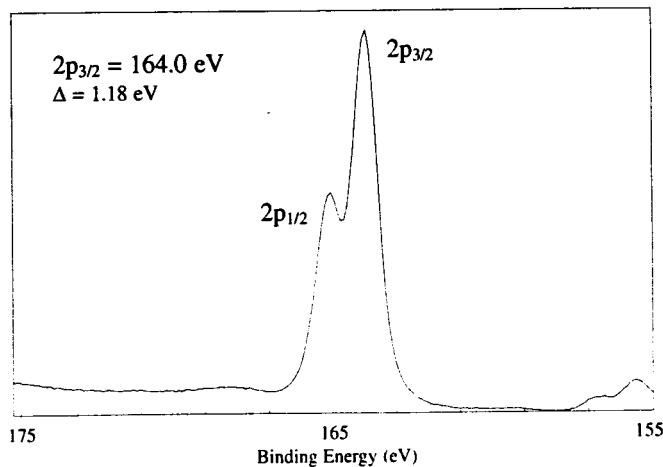


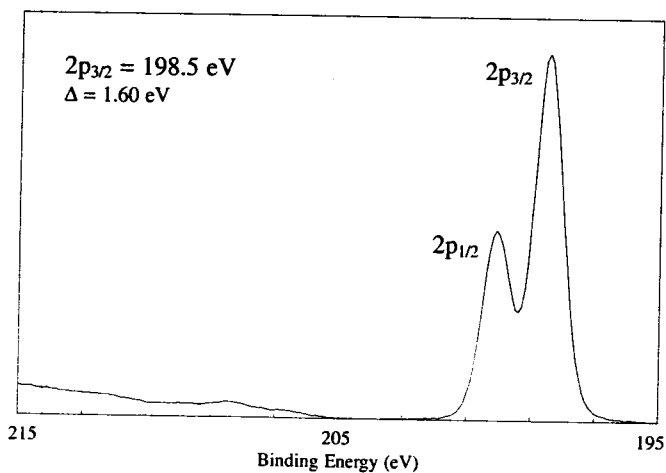
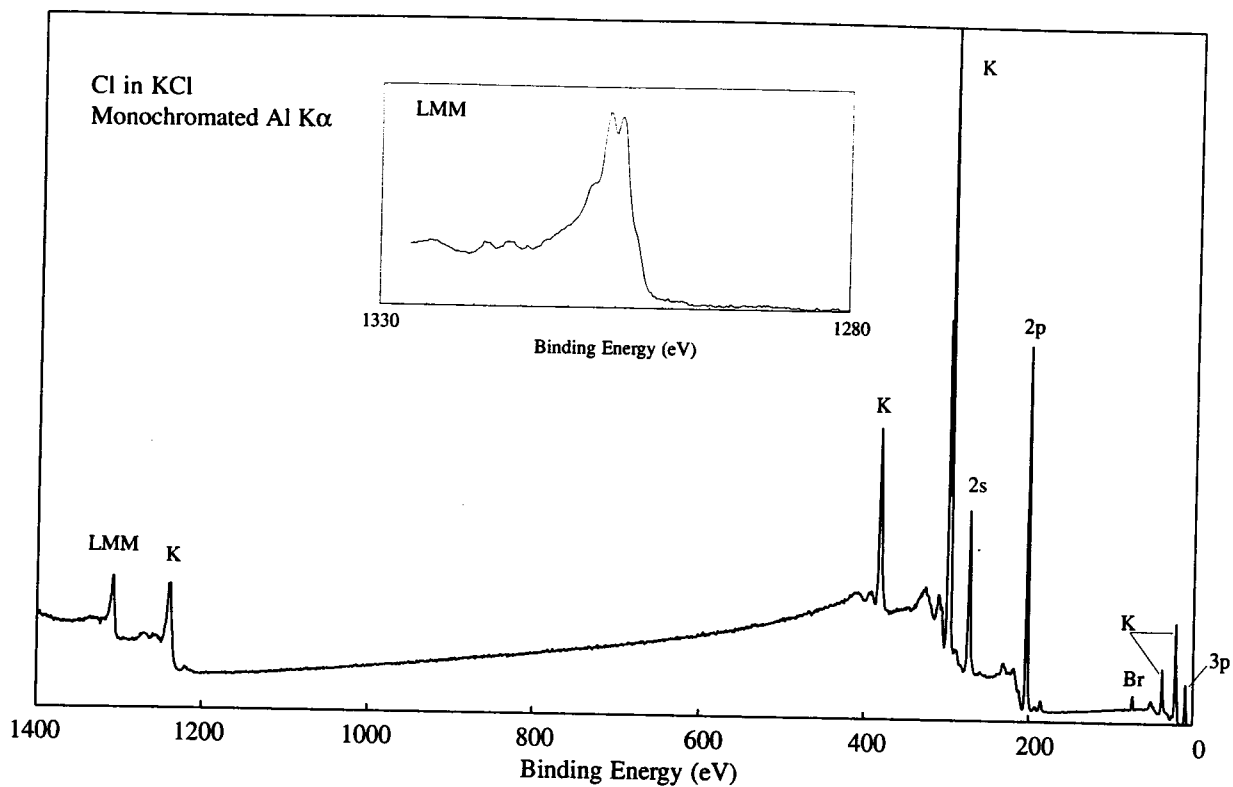


Line Positions (eV)			
<u>Photoelectron Lines</u>			
2s	2p _{1/2}	2p _{3/2}	3s
228	165	164	18
<u>Auger Lines</u>			
L ₂₃ M ₂₃ M ₂₃			
	1336	(Al)	
	1103	(Mg)	



Compound Type	2p _{3/2} Binding Energy (eV)						
	160	163	166	169	172	175	178
S							
Sulfide	█	█					
Sulfite			█				
Sulfate				█			
SF ₆						█	
SO ₂				█			
Thiophene		█					
Mercaptan		█					
Cysteine		█					
Sulfone			█	█			

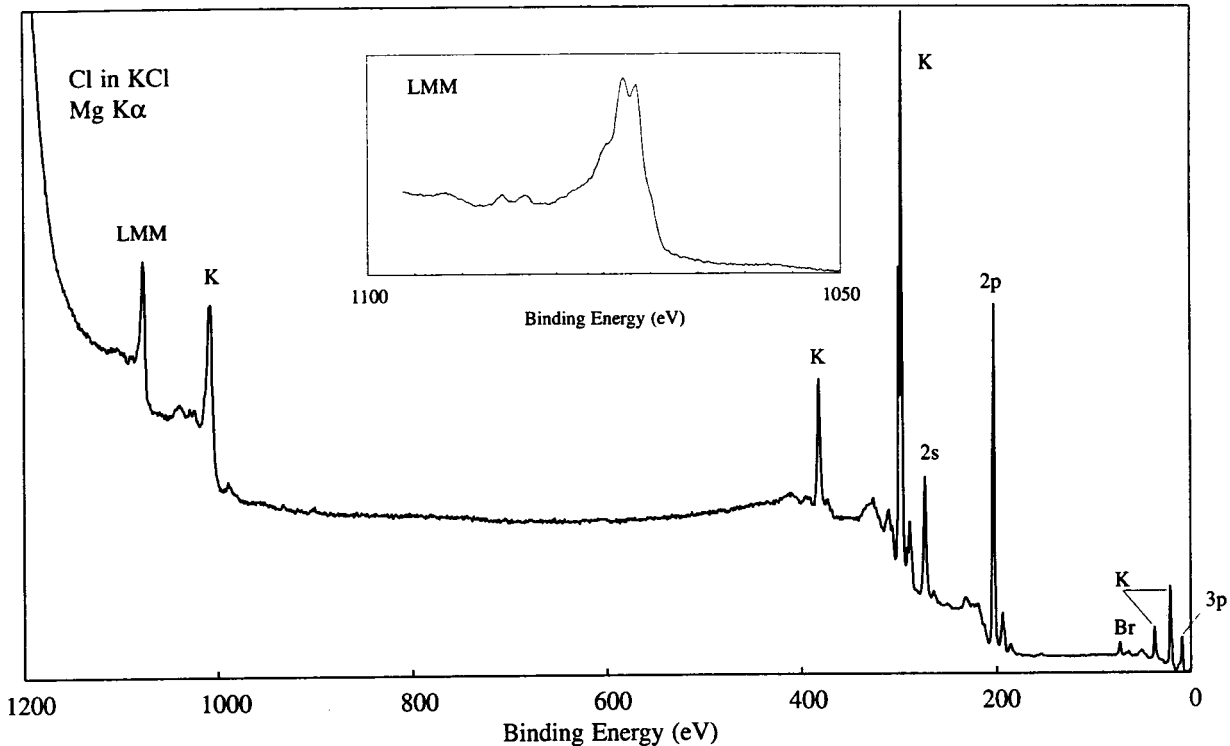




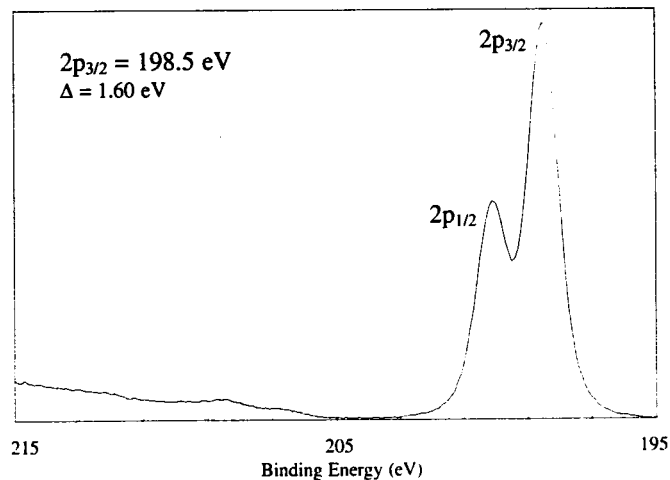
Line Positions (eV)

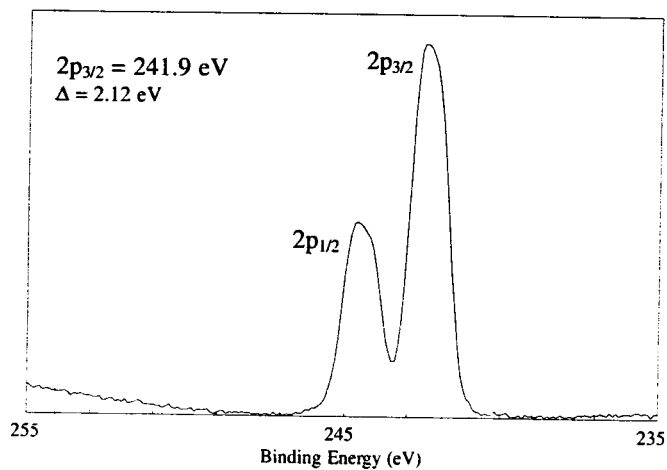
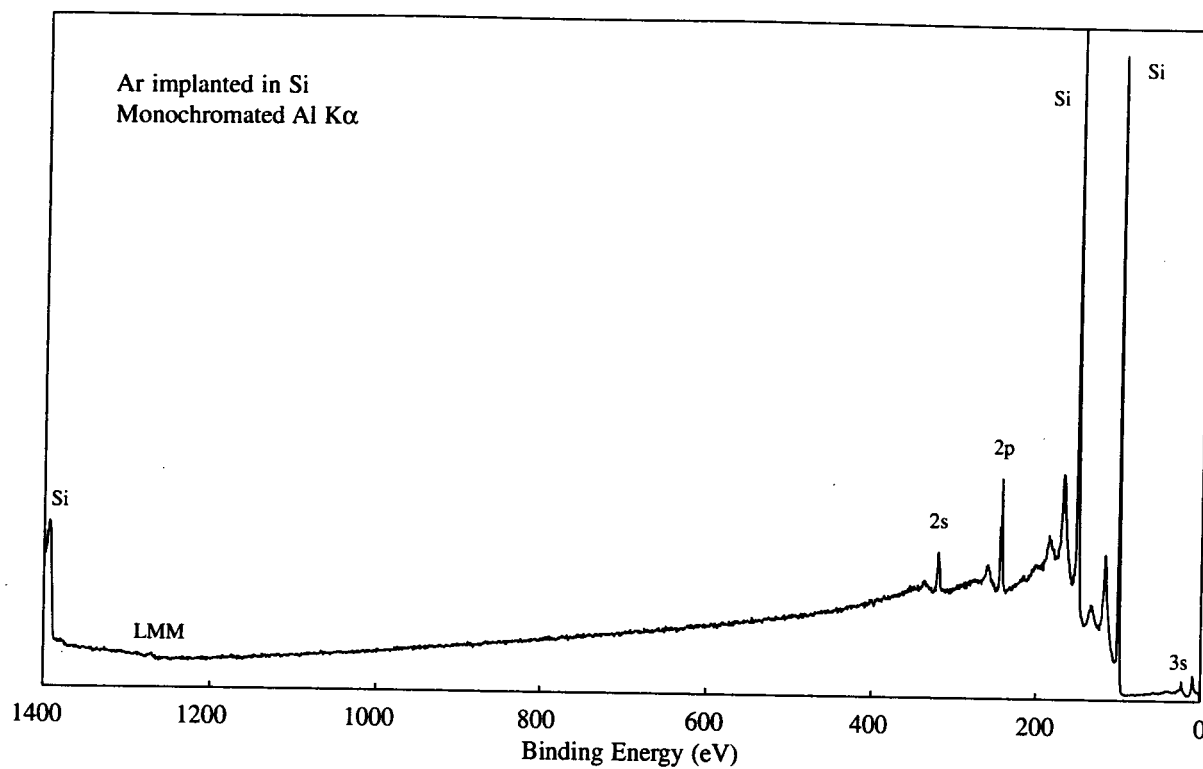
Photoelectron Lines				
2s	2p _{1/2}	2p _{3/2}	3s	3p
271	201	199	17	6

Auger Lines	
L ₂₃ M ₂₃ M ₂₃	
1304	(Al)
1071	(Mg)

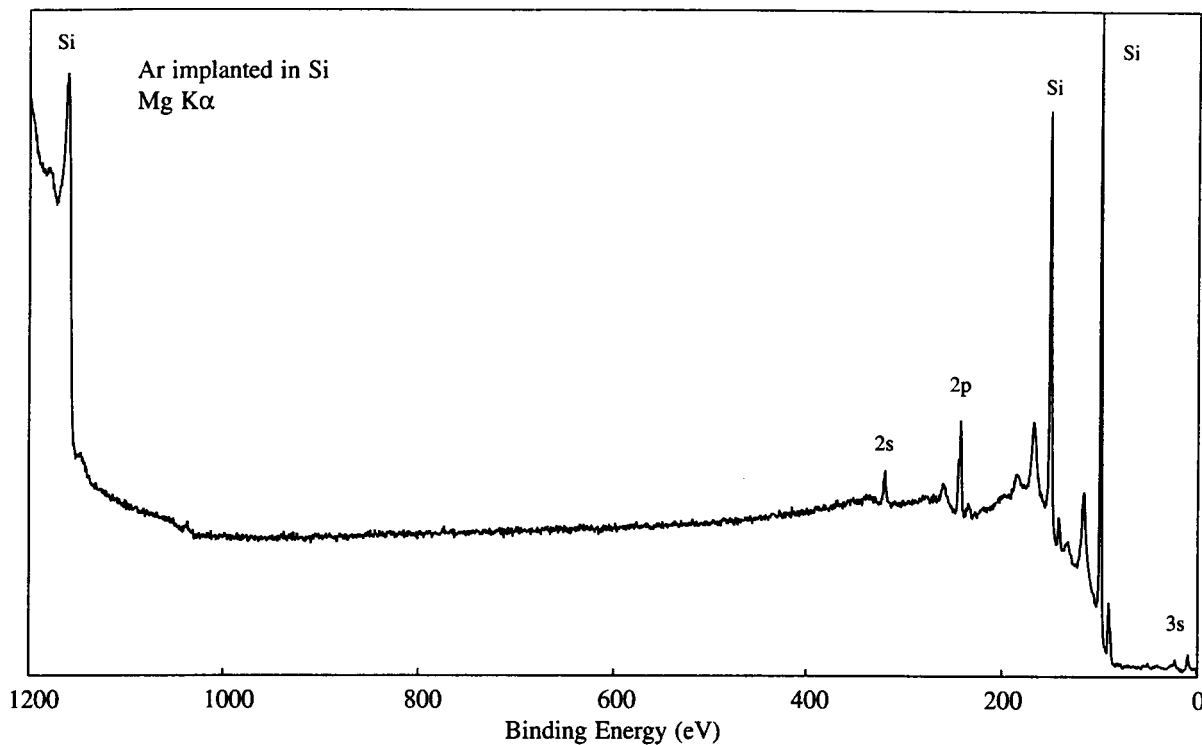


Compound Type	2p _{3/2} Binding Energy (eV)						
	198	200	202	204	206	208	210
Alkali Chloride	■						
CuCl ₂		■					
NiCl ₂		■					
PdCl ₂	■						
K ₂ IrCl ₆	■						
Pt(NH ₃) ₂ Cl ₂	■						
Perchlorate						■	■
KClO ₃					■		
NaClO ₄						■	
C ₆ H ₅ Cl		■	■				
p(CH ₂ =CHCl)		■					

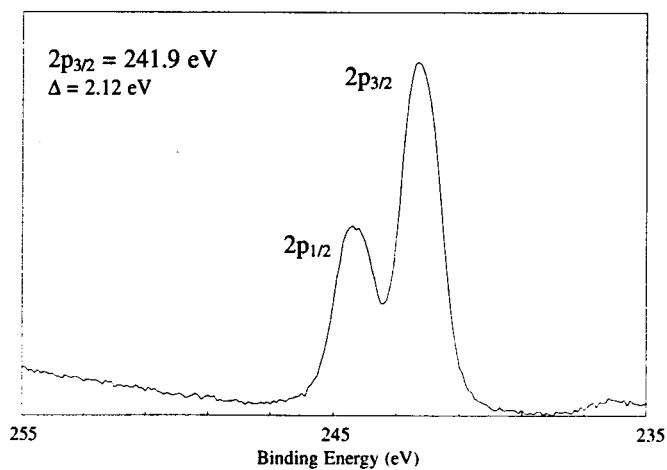


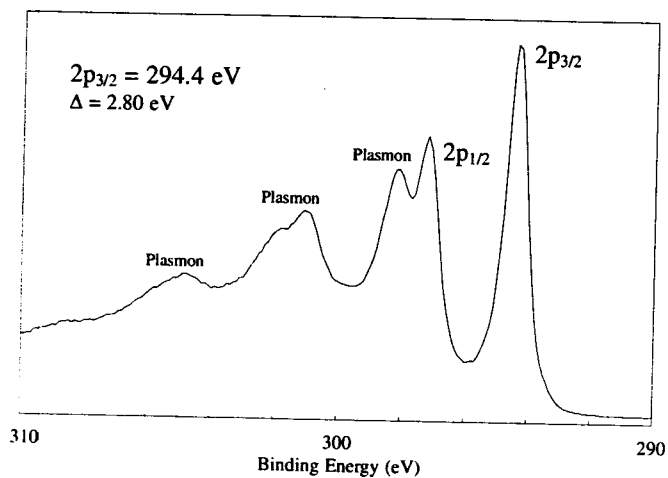
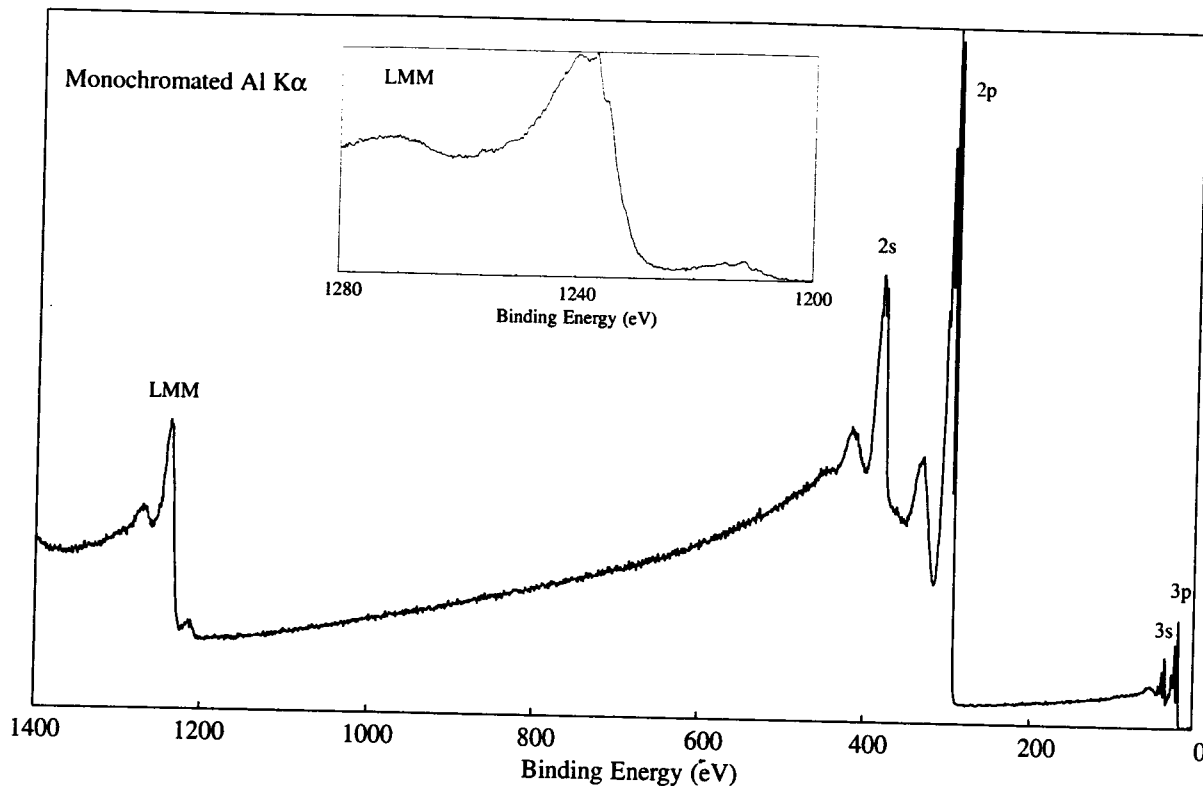


Line Positions (eV)			
<u>Photoelectron Lines</u>			
2s	2p _{1/2}	2p _{3/2}	3s
320	244	242	24
<u>Auger Lines</u>			
L ₂₃ M ₂₃ M ₂₃			
	1272	(Al)	
	1039	(Mg)	

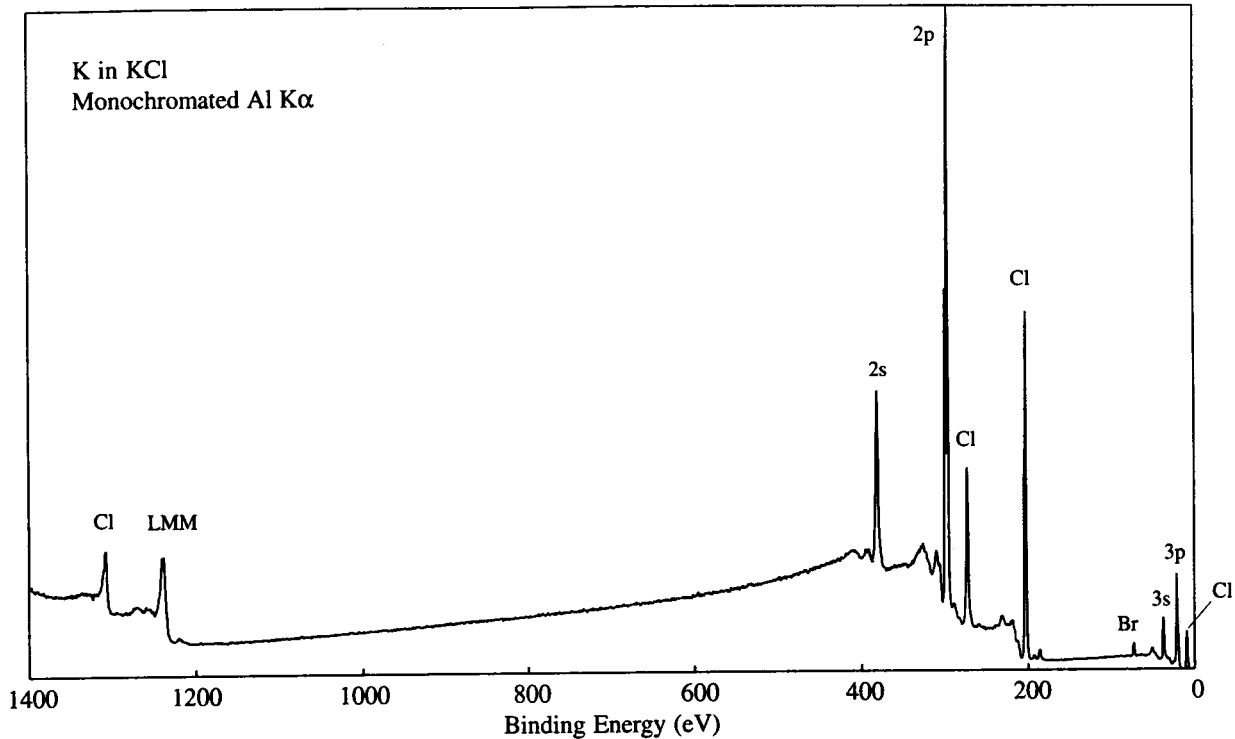


Compound Type	$2p_{3/2}$ Binding Energy (eV)		
	240	241	242
Ar in Ag		█	
Ar in Au	█		
Ar in Cu		█	
Ar in Pt	█		
Ar in graphite		█	█
Ar in Si			█

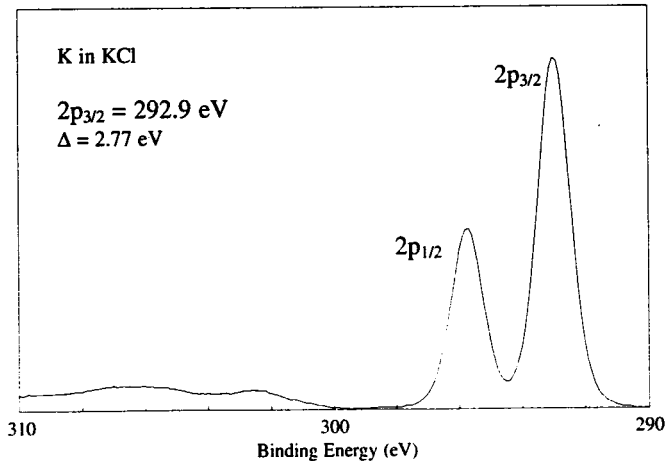


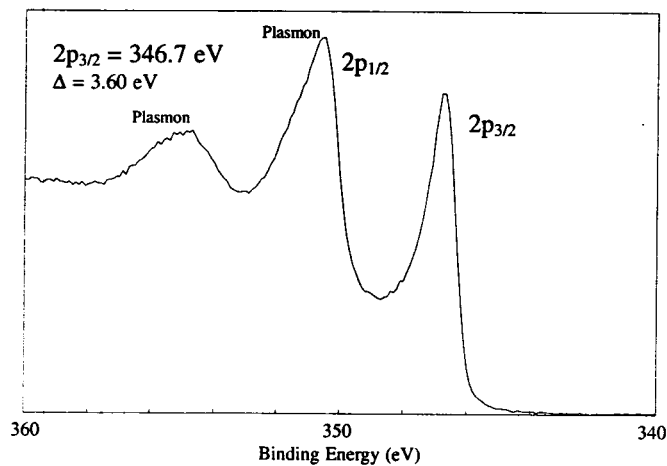
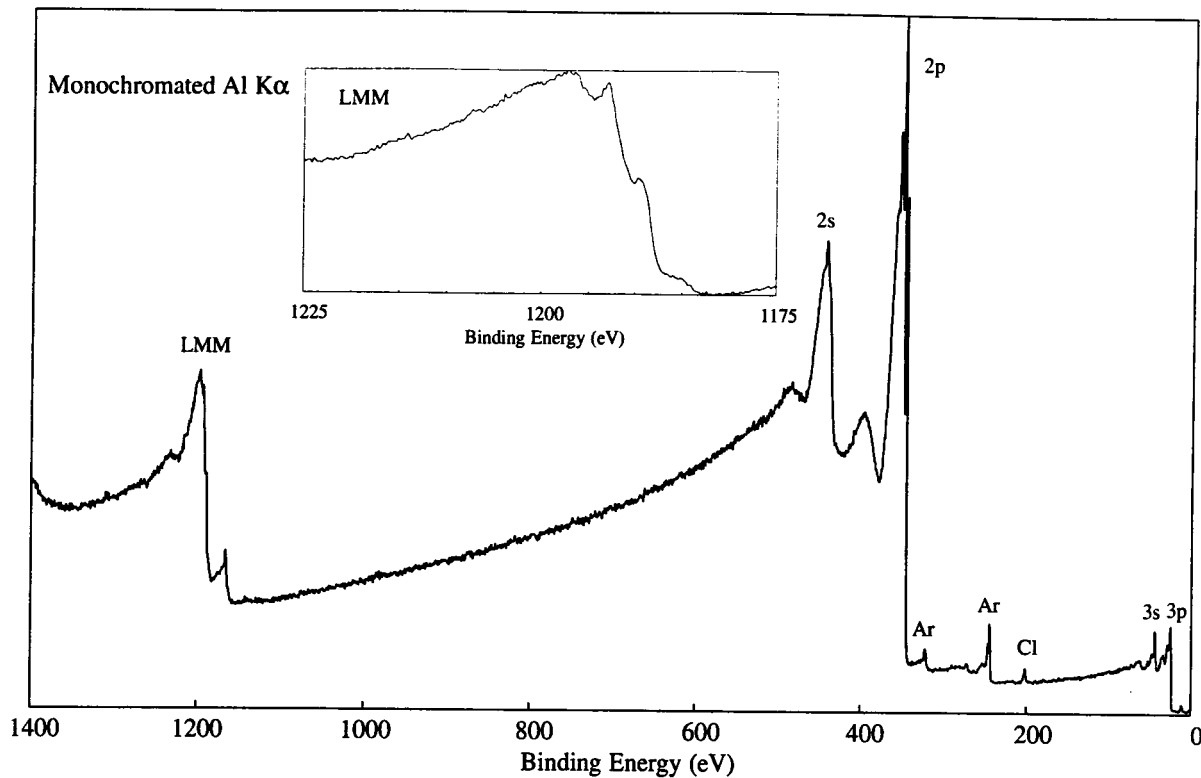


Line Positions (eV)				
Photoelectron Lines				
2s	2p $_{1/2}$	2p $_{3/2}$	3s	3p
380	297	294	35	19
Auger Lines				
L $_{23}$ M $_{23}$ M $_{23}$				
		1239	(Al)	
		1006	(Mg)	

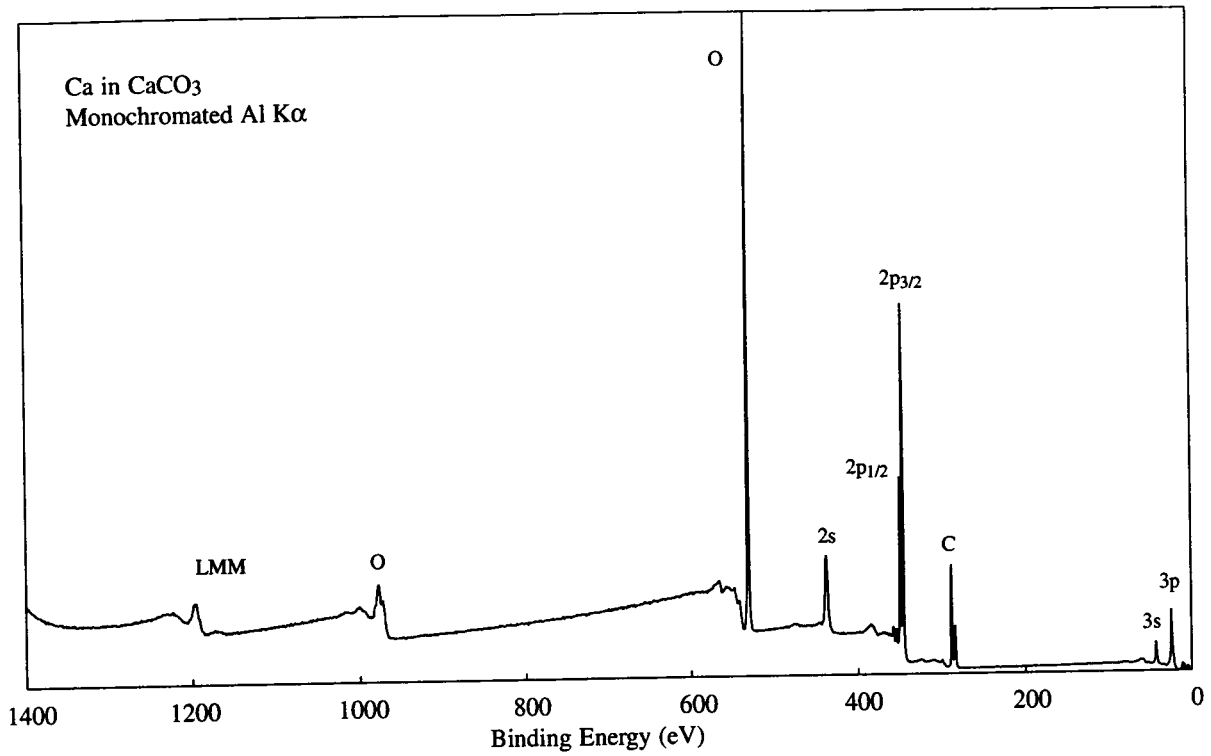


Compound Type	2p _{3/2} Binding Energy (eV)				
	291	292	293	294	295
K					■
Halides			■		
KCN				■	
KNO ₃			■		
KClO ₃		■			
KClO ₄			■		
K ₃ PO ₄				■	
K ₄ P ₂ O ₇		■			
K ₂ CrO ₄			■		
K ₂ Cr ₂ O ₇		■			

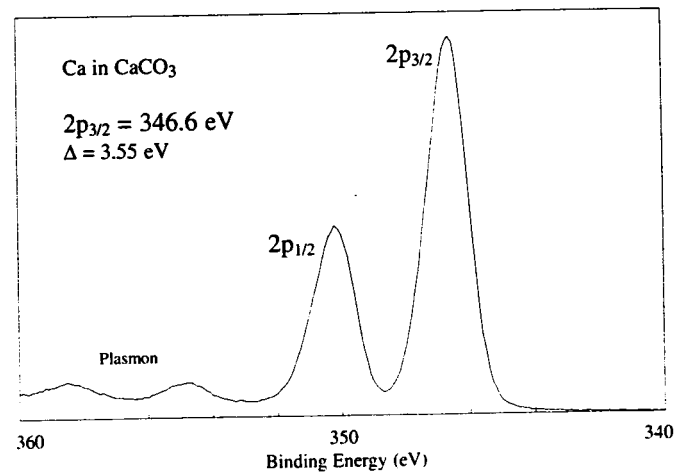


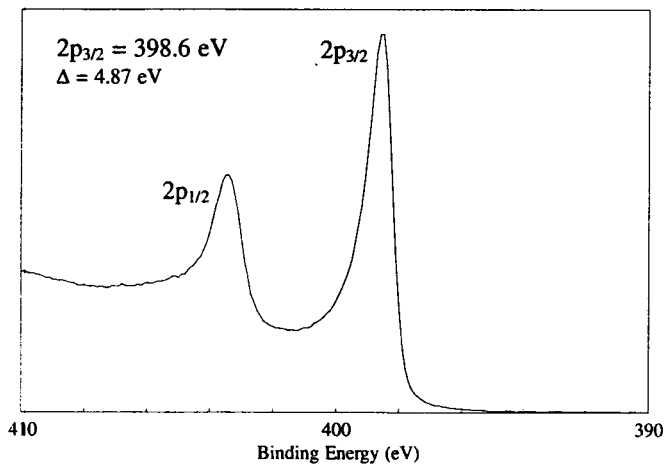
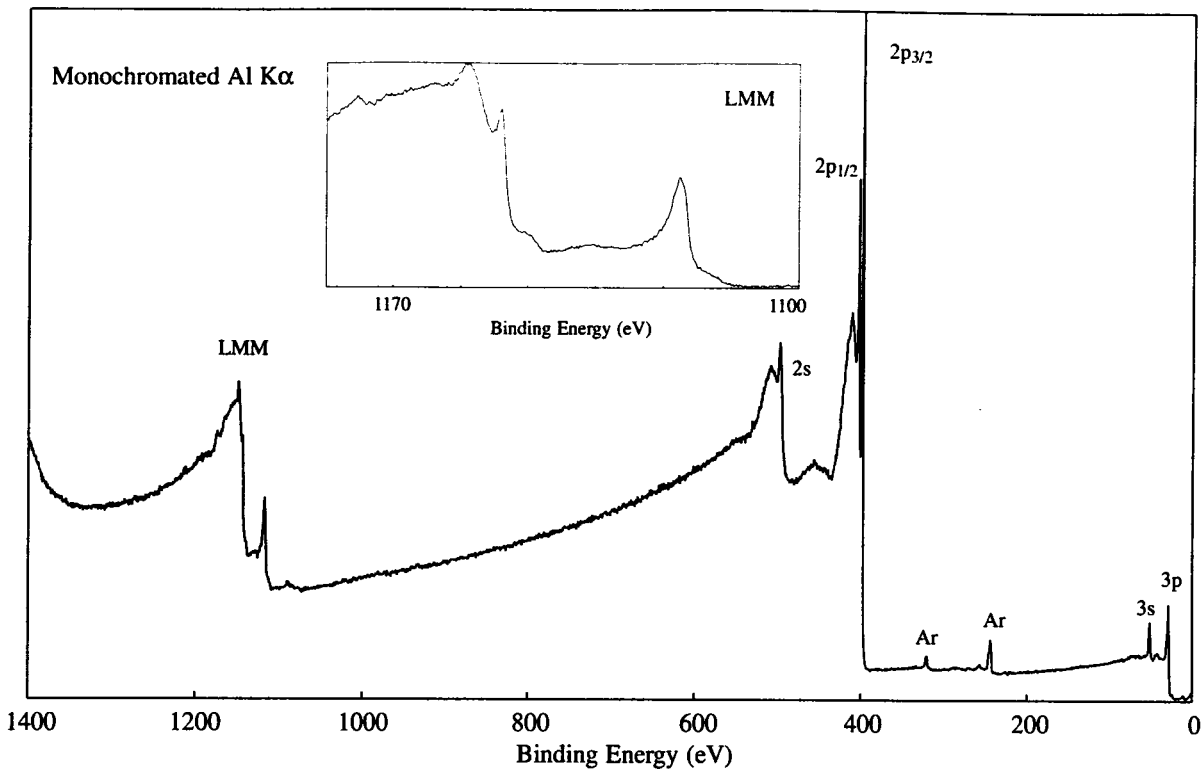


Line Positions (eV)				
<u>Photoelectron Lines</u>				
2s	2p $_{1/2}$	2p $_{3/2}$	3s	3p
440	351	347	45	26
<u>Auger Lines</u>				
L $_{23}$ M $_{23}$ M $_{23}$				
1197		(Al)		
964		(Mg)		

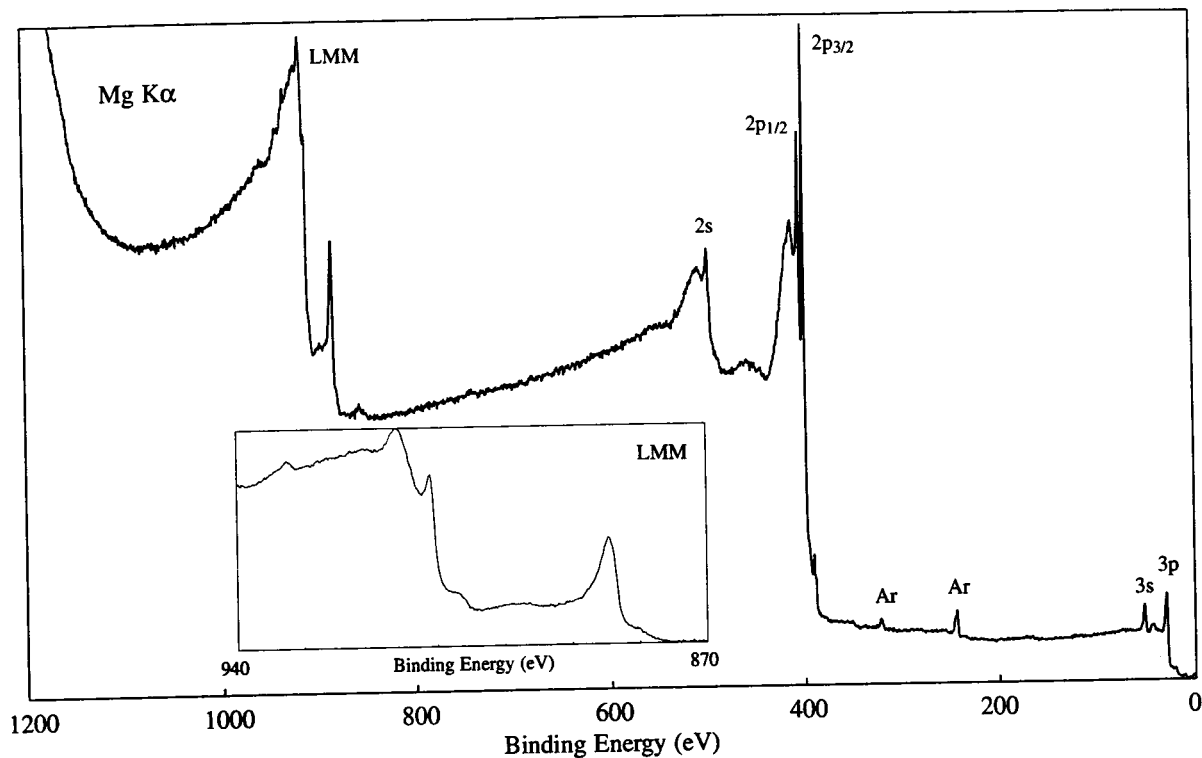


Compound Type	2p _{3/2} Binding Energy (eV)				
	345	346	347	348	349
Ca		■	■		
CaS		■			
CaCl ₂				■	
CaF ₂				■	
CaO		■			
CaCO ₃			■	■	
Ca(NO ₃) ₂					■
CaCrO ₄		■			
CaMoO ₄			■		
CaSO ₄				■	
Ca ₃ Si ₃ O ₉			■		

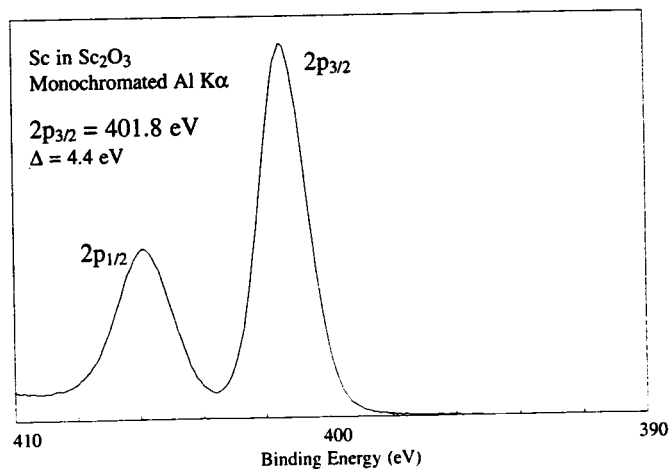


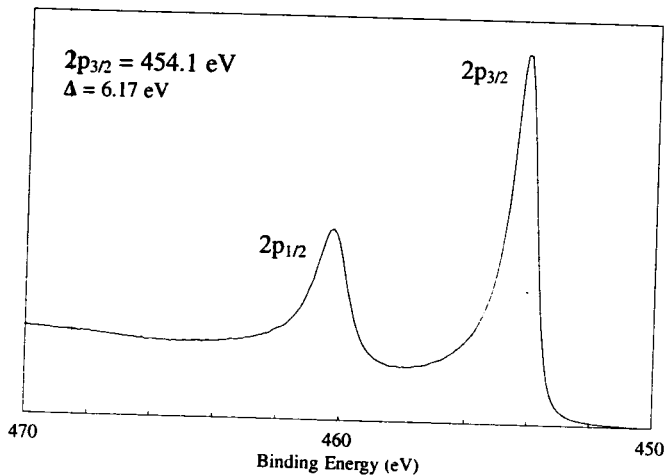
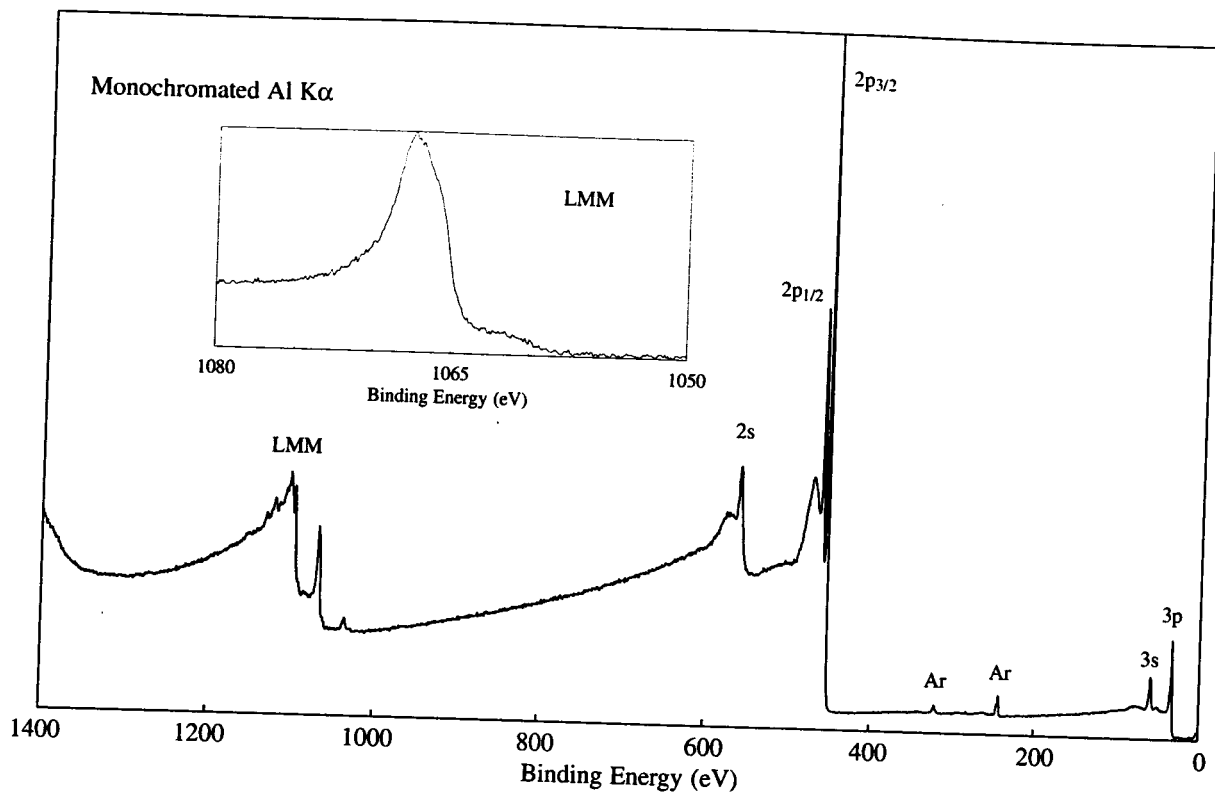


Line Positions (eV)				
<u>Photoelectron Lines</u>				
2s	2p _{1/2}	2p _{3/2}	3s	3p
499	404	399	51	29
<u>Auger Lines</u>				
LM ₂₃ M ₂₃	L ₃ M ₂₃ M ₄₅ (¹ P)			
1149	1118	(Al)		
916	885	(Mg)		

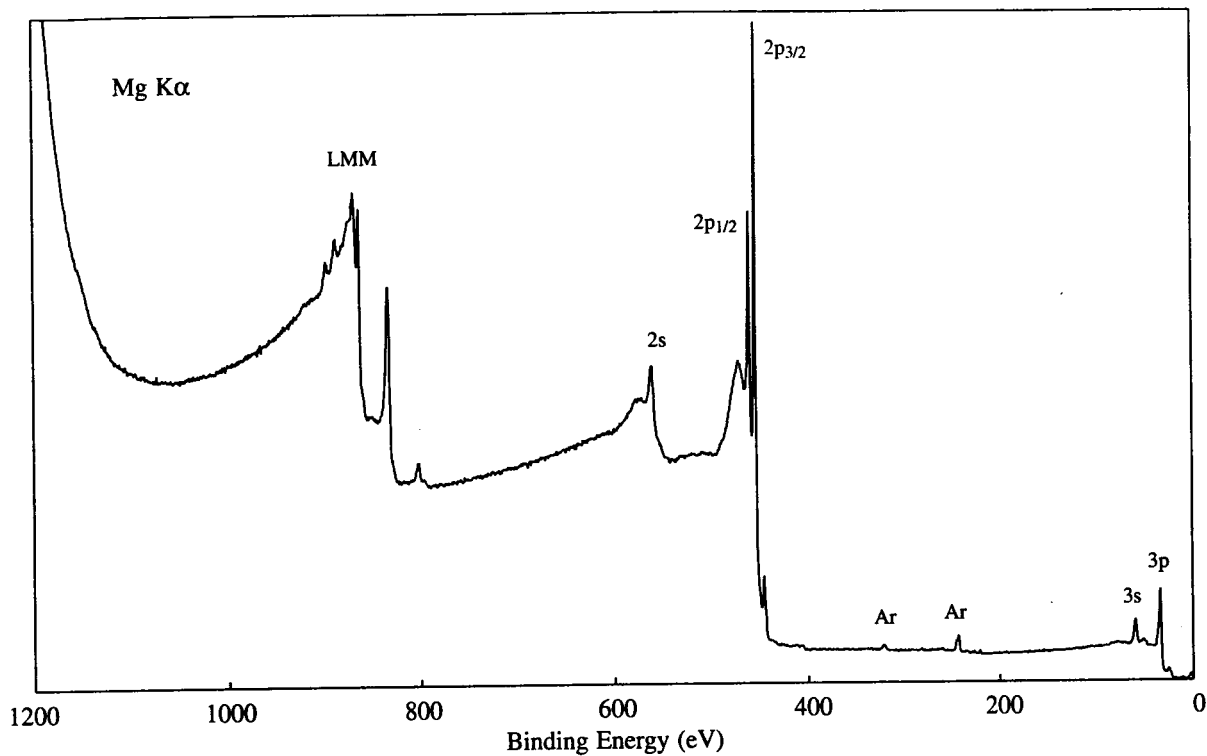


Compound Type	2p _{3/2} Binding Energy (eV)				
	398	399	400	401	402
Sc		■			
ScN			■		
Sc ₂ O ₃				■	■
ClSc(C ₅ H ₅) ₂				■	
Sc(C ₅ H ₅)(C ₈ H ₈)			■		

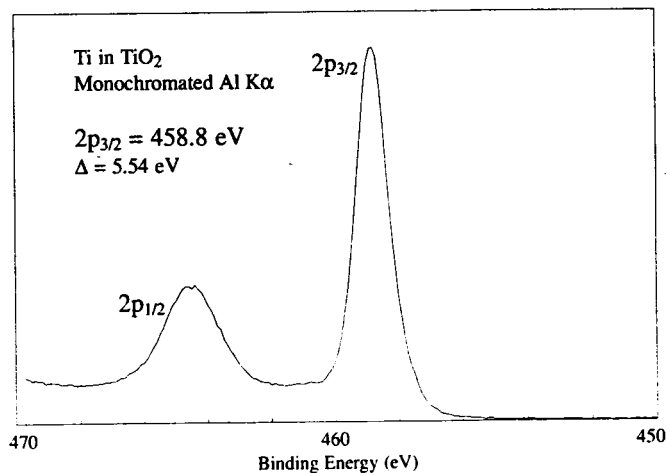


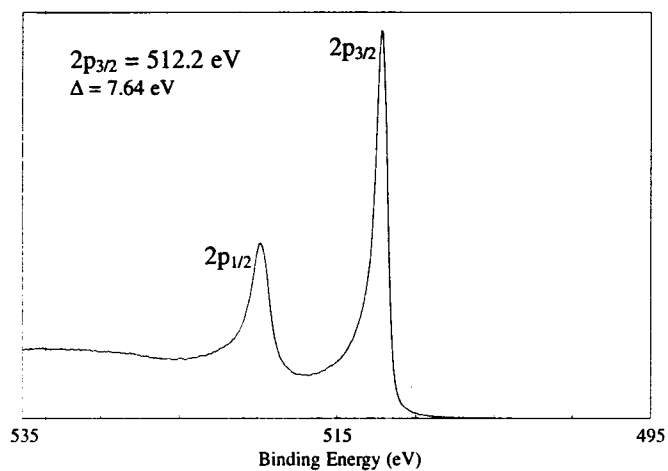
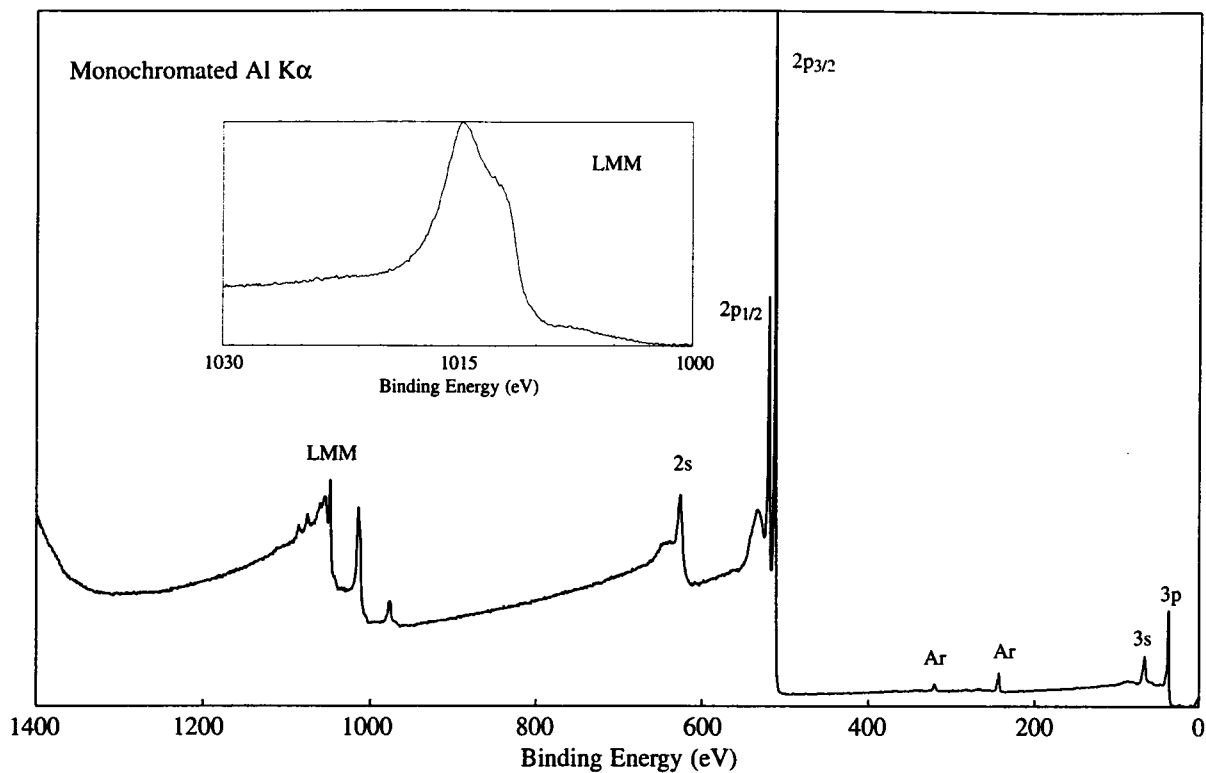


Line Positions (eV)				
Photoelectron Lines				
2s	2p _{1/2}	2p _{3/2}	3s	3p
561	460	454	59	33
Auger Lines				
LM ₂₃ M ₂₃	L ₃ M ₂₃ M ₄₅ (¹ P)			
1098	1068	(Al)		
865	835	(Mg)		

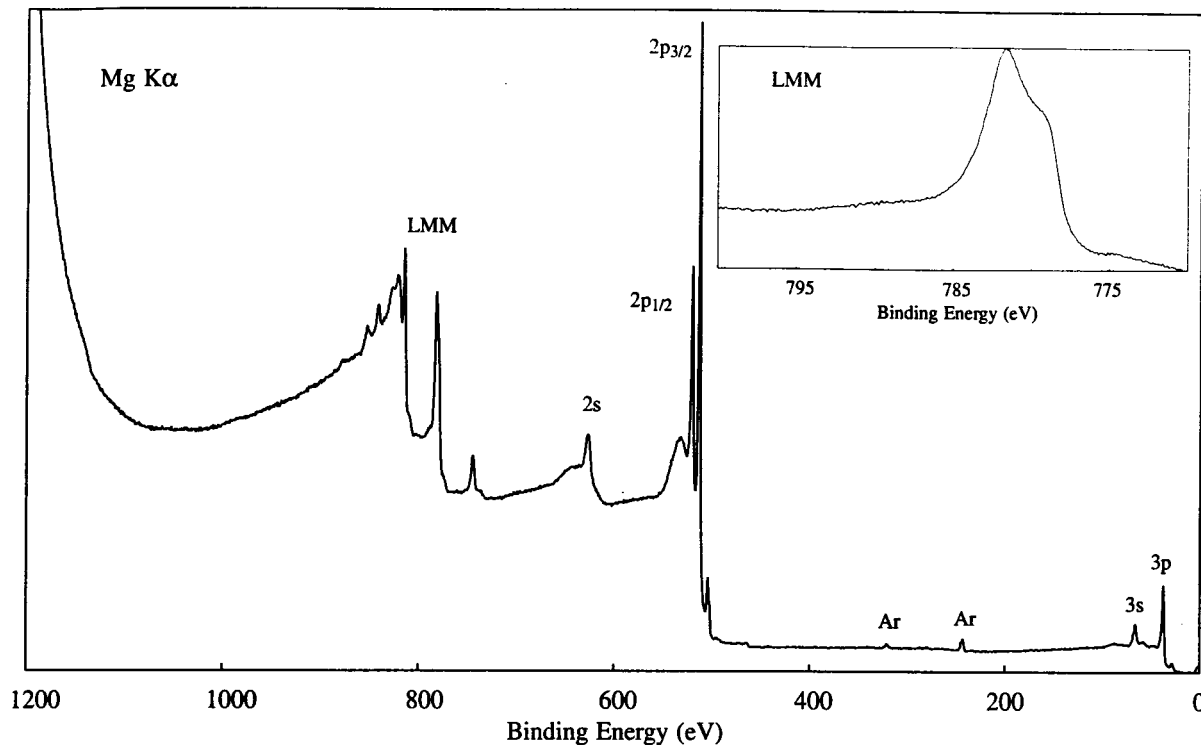


Compound Type	2p _{3/2} Binding Energy (eV)							
	453	454	455	456	457	458	459	460
Ti		■						
TiB ₂		■						
TiN				■				
TiCl ₄							■	
TiO			■					
TiO ₂							■	■
BaTiO ₃ (cubic, tetra.)							■	■
CaTiO ₃							■	■
PbTiO ₃							■	■
SrTiO ₃							■	■
Metallocene			■					

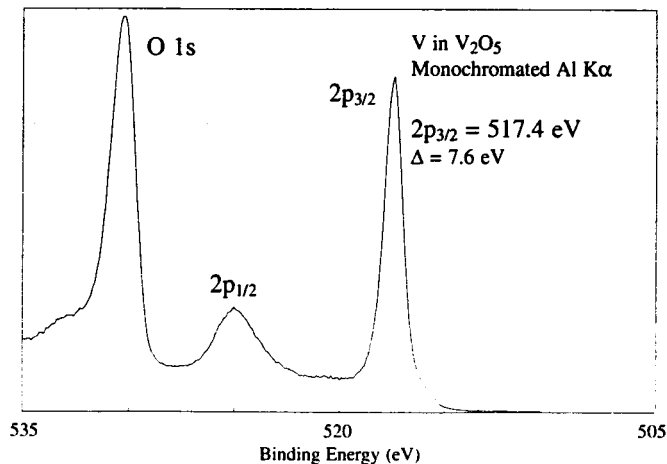


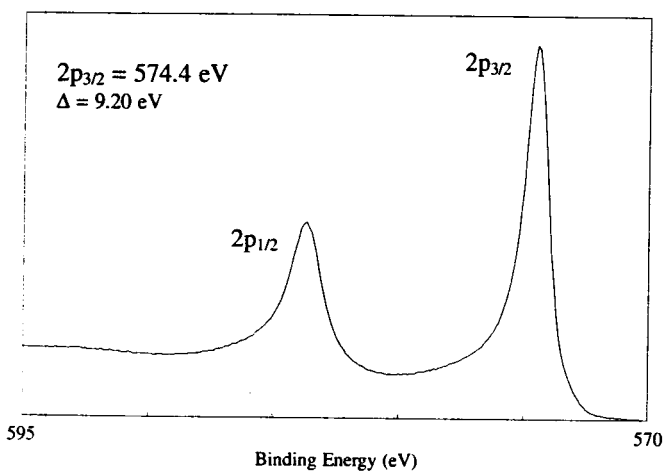
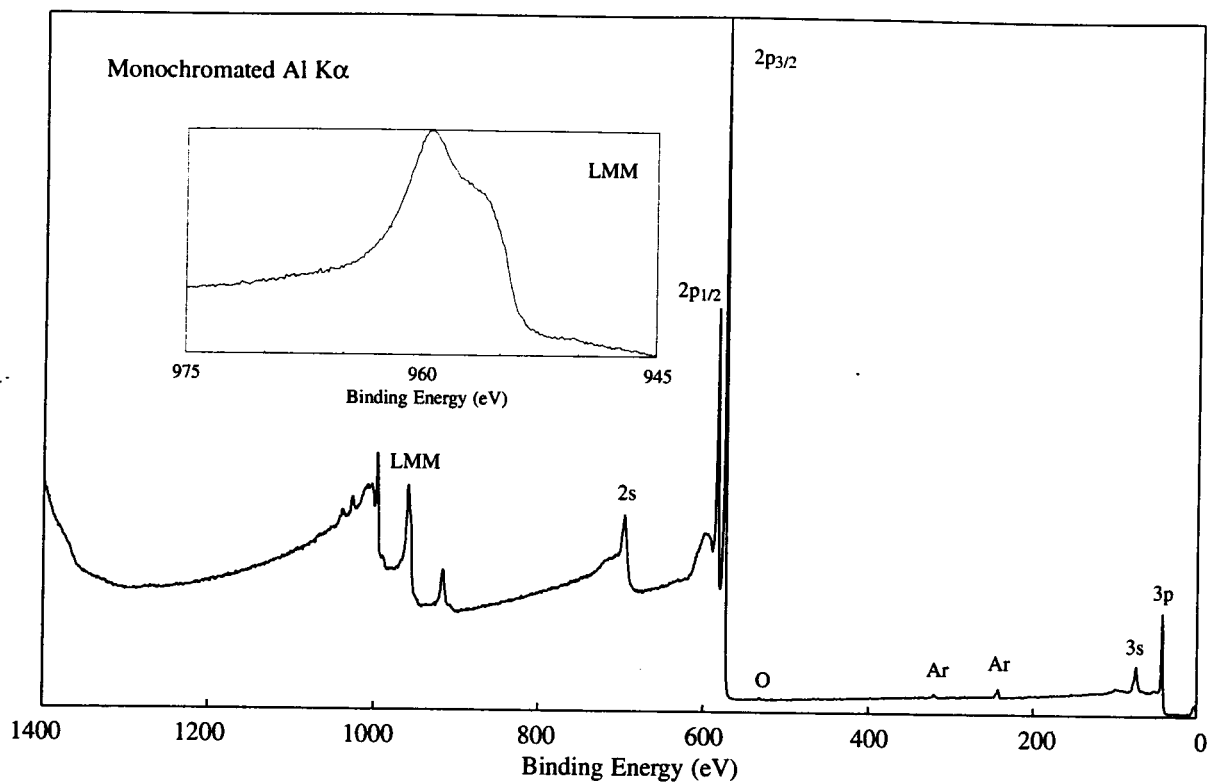


Line Positions (eV)				
Photoelectron Lines				
2s	2p _{1/2}	2p _{3/2}	3s	3p
627	520	512	66	37
Auger Lines				
L ₂₃ M ₂₃ M ₂₃	L ₃ M ₂₃ M ₄₅ (¹ P)	L ₃ M ₄₅ M ₄₅		
1048	1014	977	(Al)	
815	781	744	(Mg)	



Compound Type	2p _{3/2} Binding Energy (eV)						
	512	513	514	515	516	517	518
V	■						
VB ₂		■					
VN			■				
Oxide				■			
VOCl ₂					■		
VOSO ₄					■		
Vanadate						■	
K ₄ V(CN) ₆		■					
V(acac) ₃			■				
VO(acac) ₂				■			
Metallocene		■					

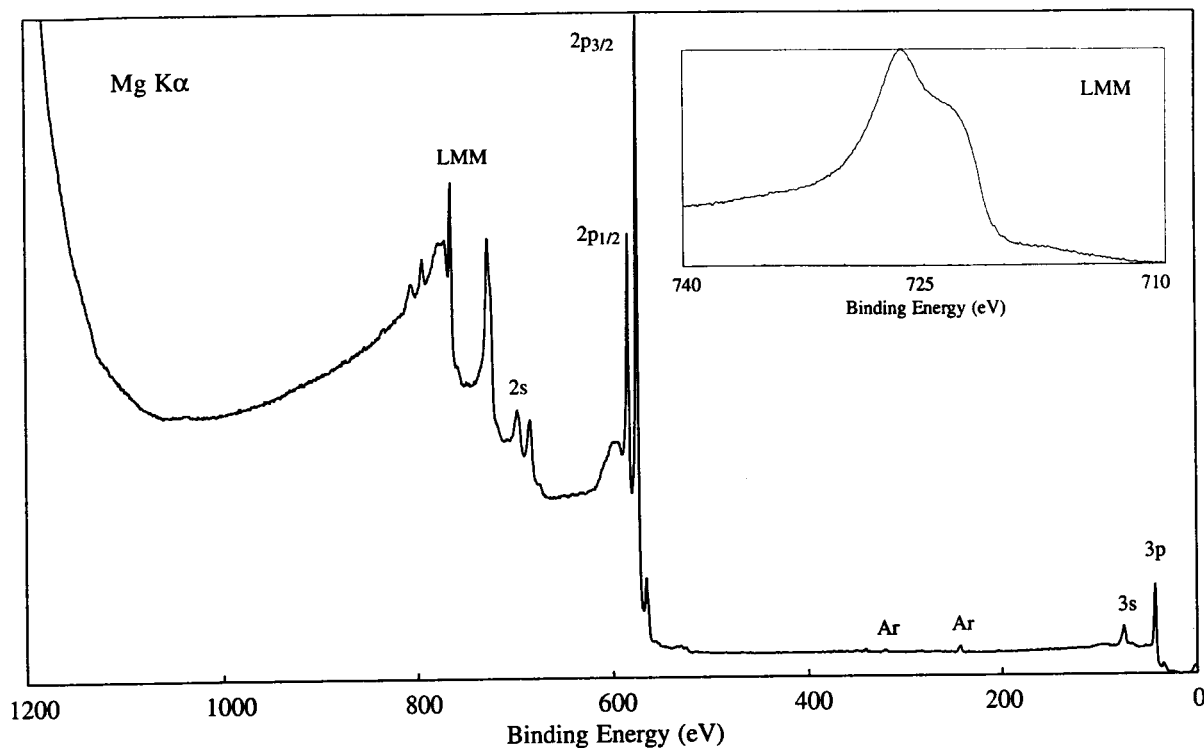




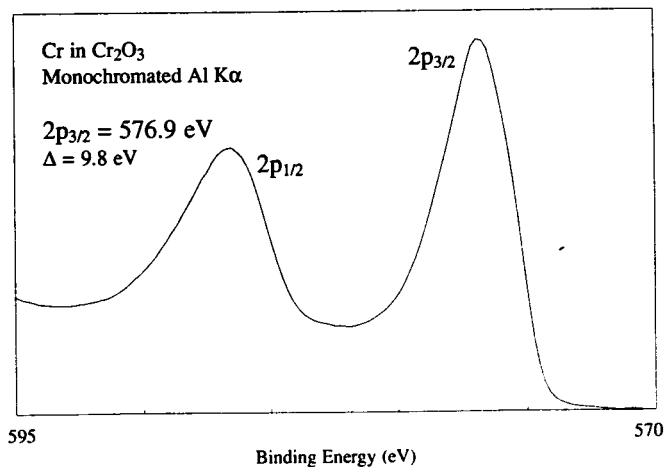
Line Positions (eV)

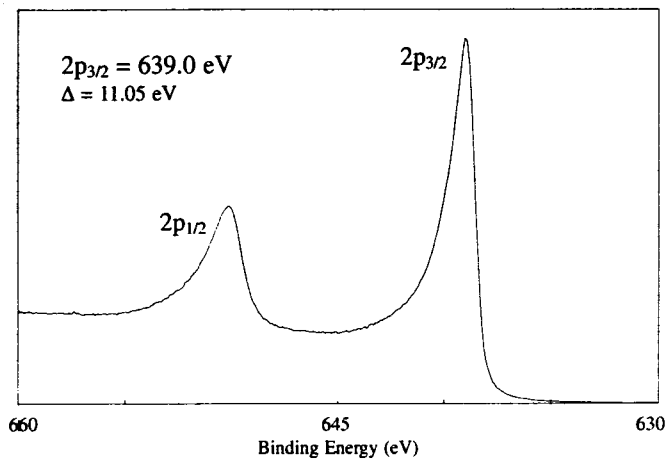
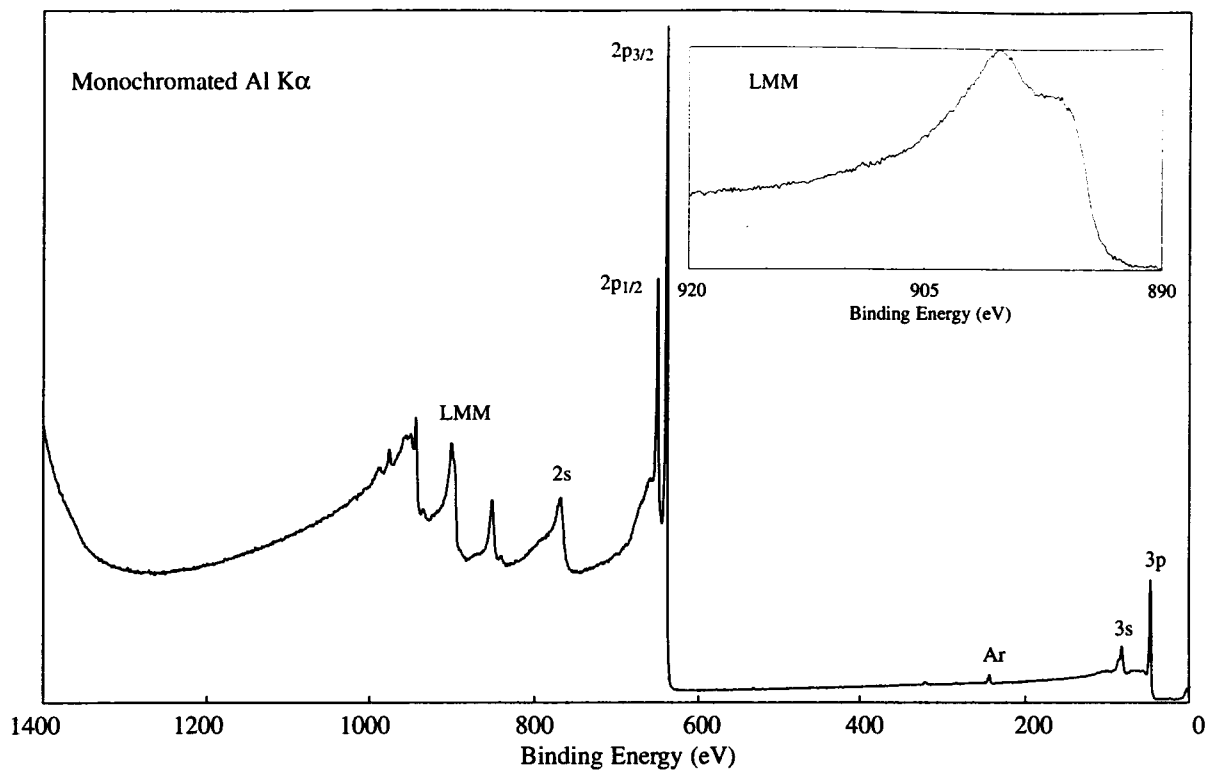
Photoelectron Lines				
2s	2p _{1/2}	2p _{3/2}	3s	3p
696	583	574	75	43

Auger Lines			
L ₂₃ M ₂₃ M ₂₃	L ₃ M ₂₃ M ₄₅ (¹ P)	L ₃ M ₄₅ M ₄₅	
997	959	917	(Al)
764	726	684	(Mg)

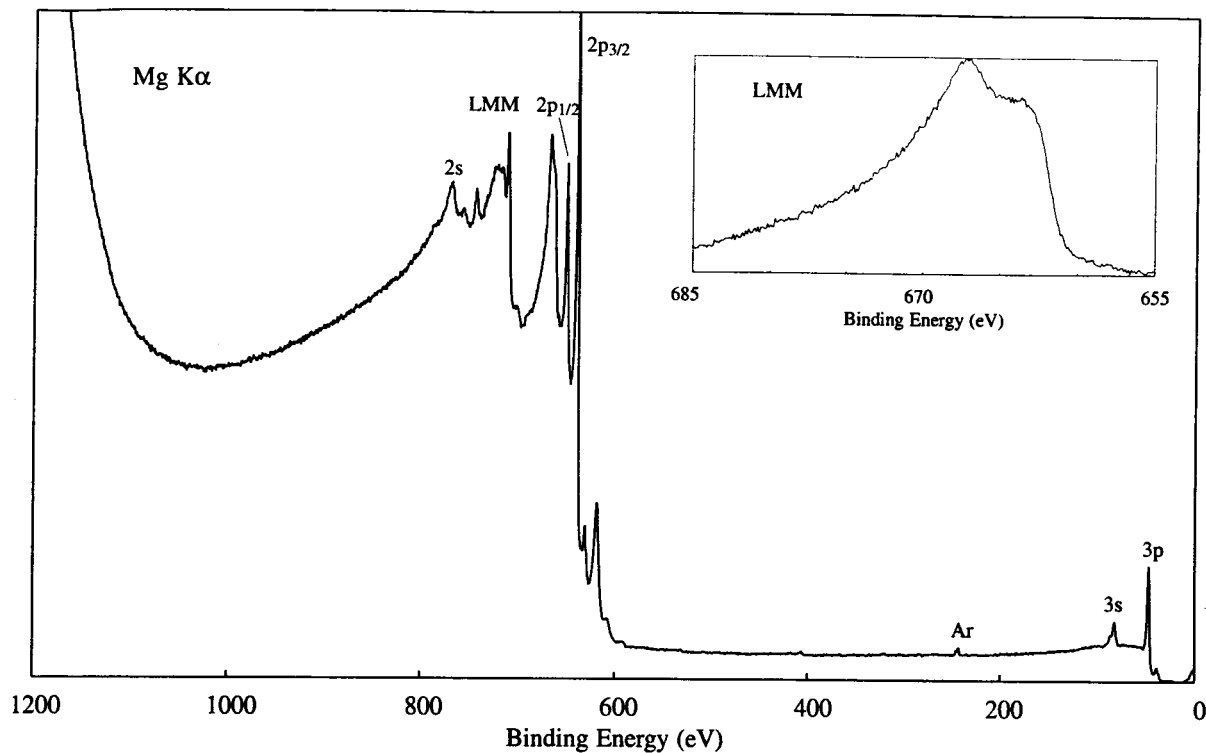


Compound Type	2p _{3/2} Binding Energy (eV)				
	574	576	578	580	582
Cr					
Cr Nitride					
CrBr ₃					
CrCl ₃					
Oxide					
CrF ₃					
Cr(OH) ₃					
CrOOH					
K ₂ Cr ₂ O ₇					
K ₃ Cr(CN) ₆					
Cr(acac) ₃					

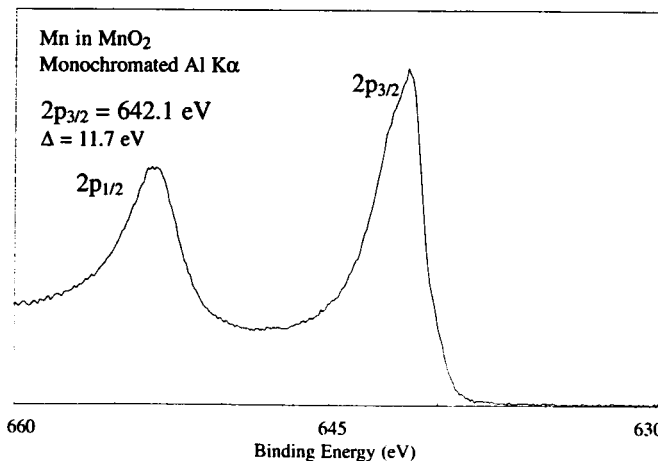


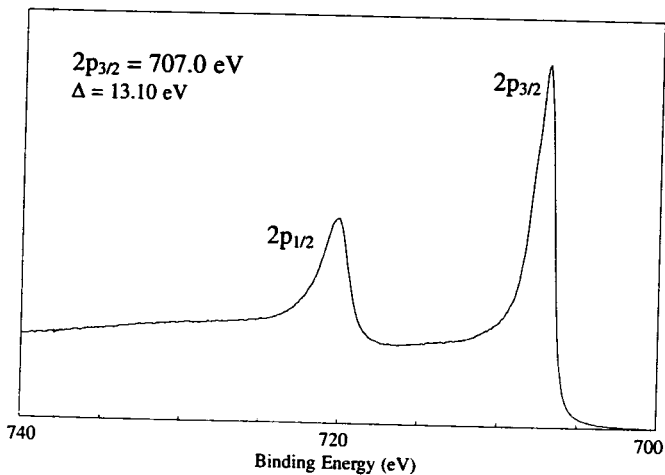
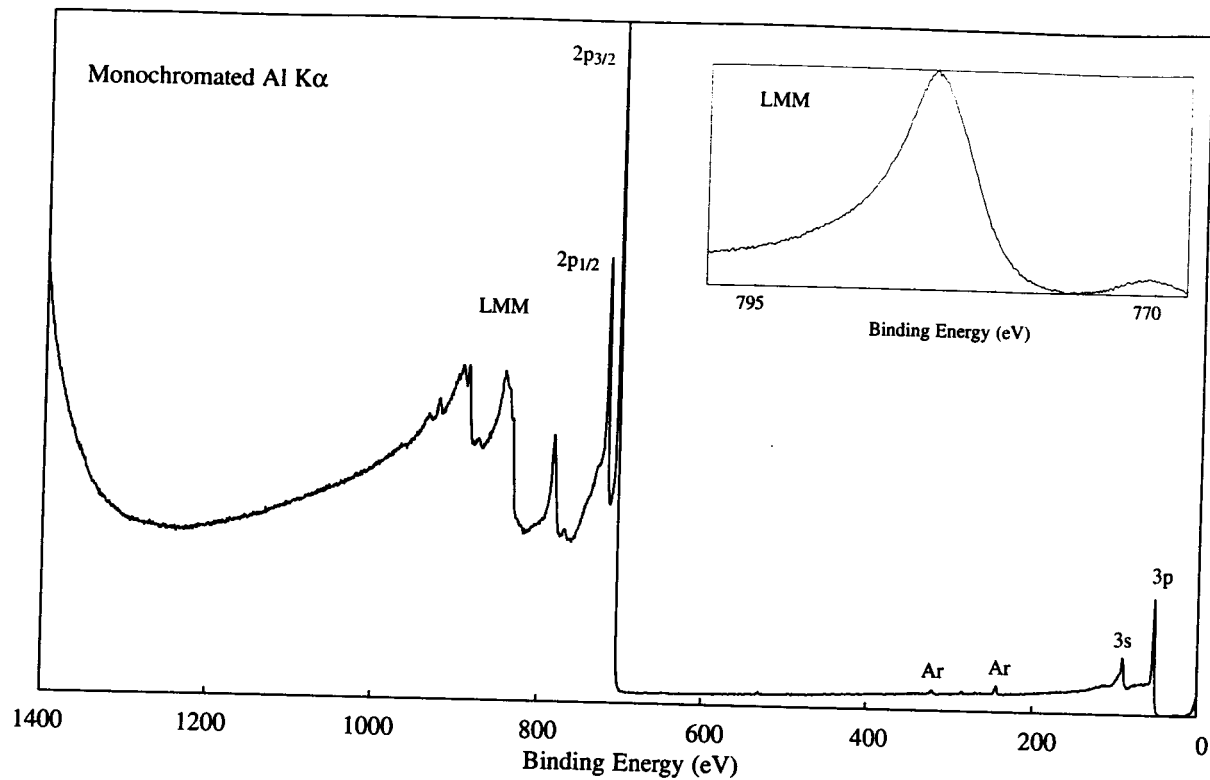


Line Positions (eV)				
<u>Photoelectron Lines</u>				
2s	2p _{1/2}	2p _{3/2}	3s	3p
769	650	639	83	48
<u>Auger Lines</u>				
L ₂₃ M ₂₃ M ₂₃	L ₃ M ₂₃ M ₄₅	L ₃ M ₄₅ M ₄₅		
944	900	852	(Al)	
711	667	619	(Mg)	

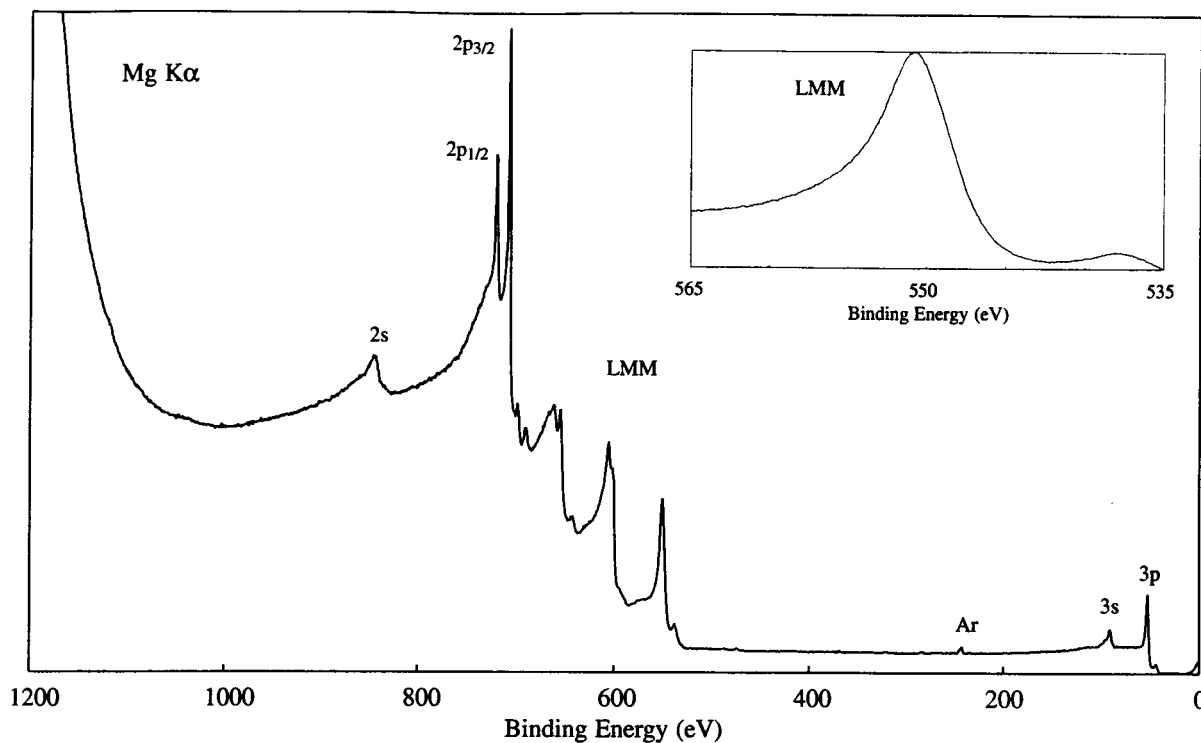


Compound Type	$2p_{3/2}$ Binding Energy (eV)								
	638	639	640	641	642	643	644	645	
Mn		■							
MnS				■	■	■			
MnCl ₂					■				
MnF ₃						■			
MnO			■	■	■				
Mn ₂ O ₃				■	■				
Mn ₃ O ₄				■	■				
MnO ₂				■	■	■			
MnOOH					■				
MnSO ₄								■	
Mn(C ₅ H ₅) ₂	■								

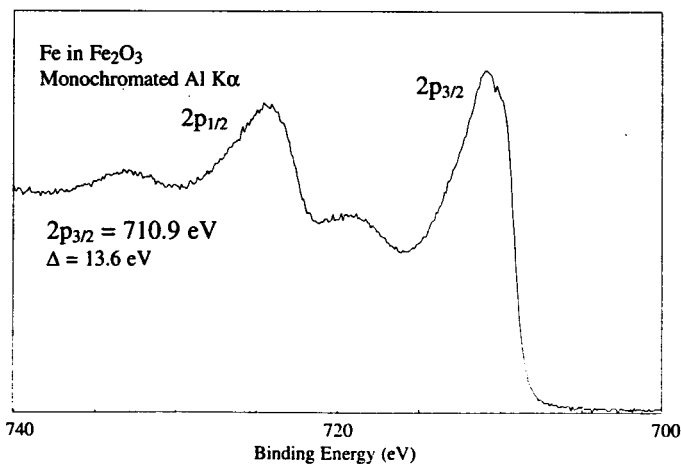


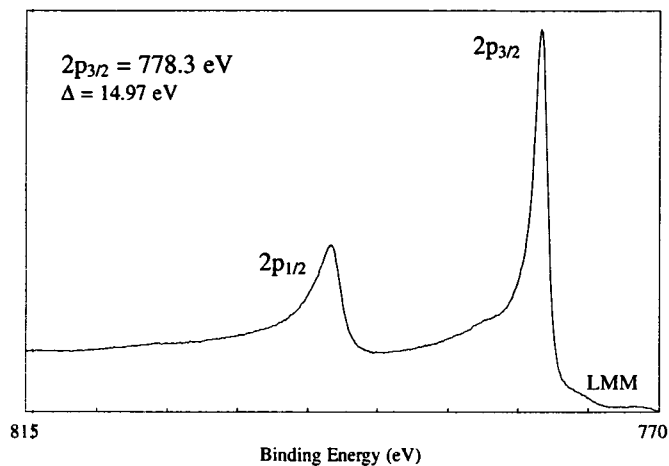
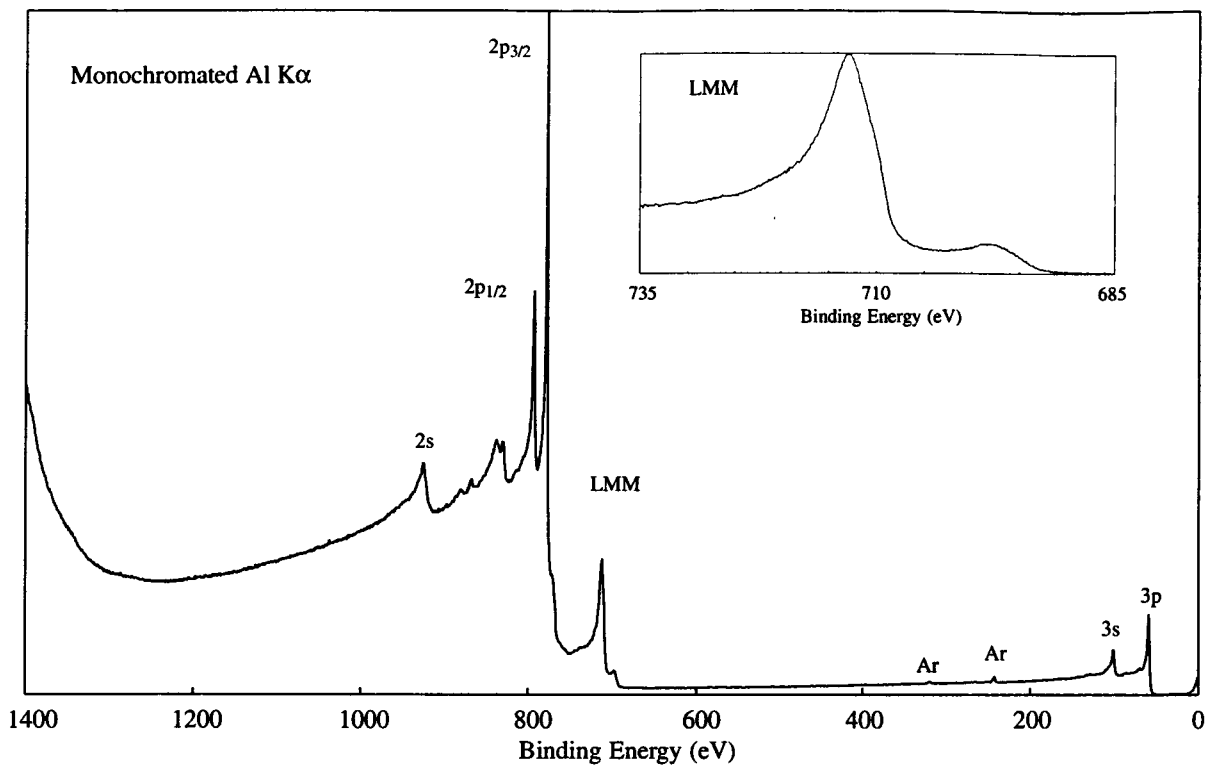


Line Positions (eV)				
<u>Photoelectron Lines</u>				
2s	2p _{1/2}	2p _{3/2}	3s	3p
845	720	707	92	53
<u>Auger Lines</u>				
LM ₂₃ M ₂₃	L ₃ M ₂₃ M ₄₅ (¹ P)	L ₃ M ₄₅ M ₄₅		
888	839	784	(Al)	
655	606	551	(Mg)	

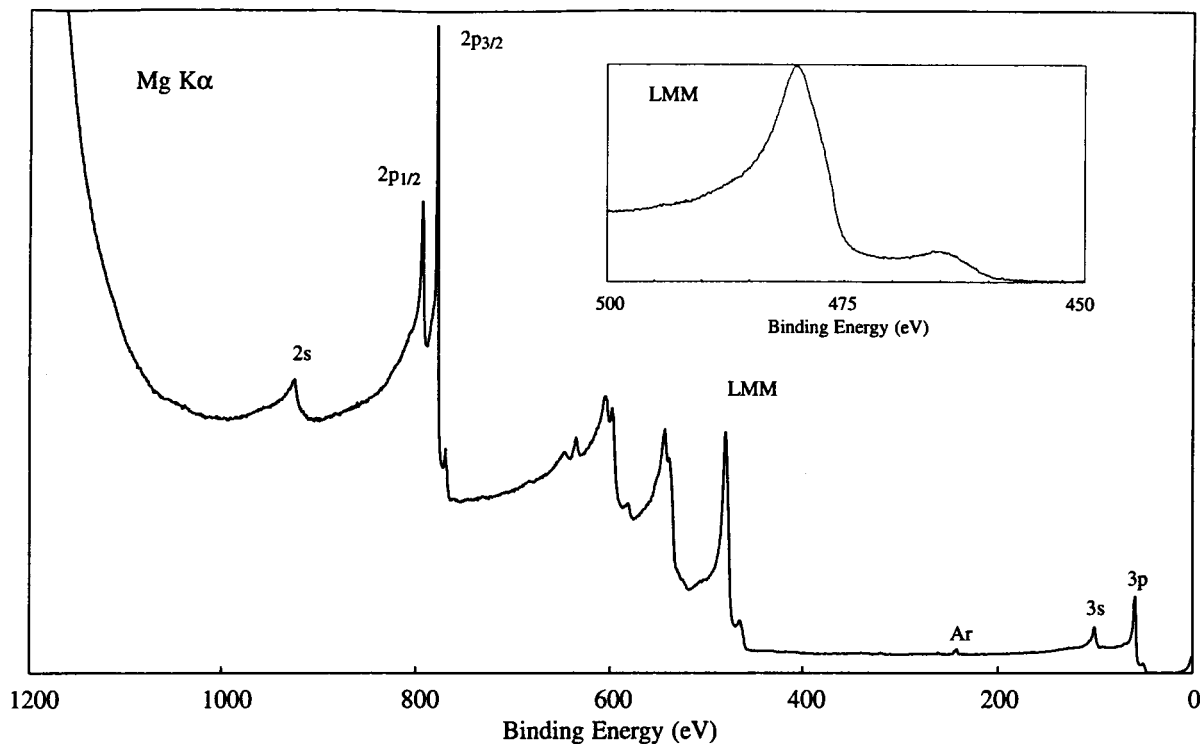


Compound Type	2p _{3/2} Binding Energy (eV)							
	706	707	708	709	710	711	712	713
Fe		■						
FeS							■	
FeS ₂ (markasite, pyr)	■							
FeCl ₂						■		
FeCl ₃						■		
FeO				■				
Fe ₂ O ₃					■			
FeOOH							■	
FeSO ₄							■	
K ₃ Fe(CN) ₆				■				
K ₄ Fe(CN) ₆		■	■	■				

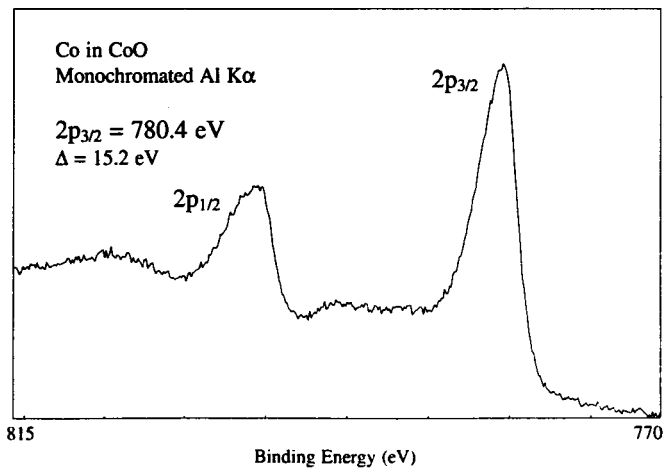


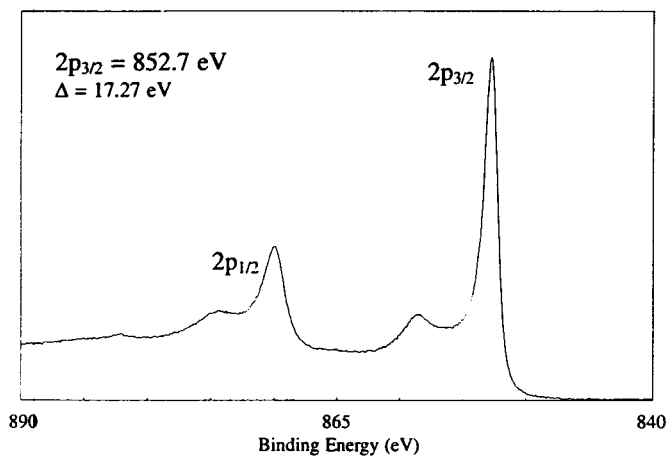
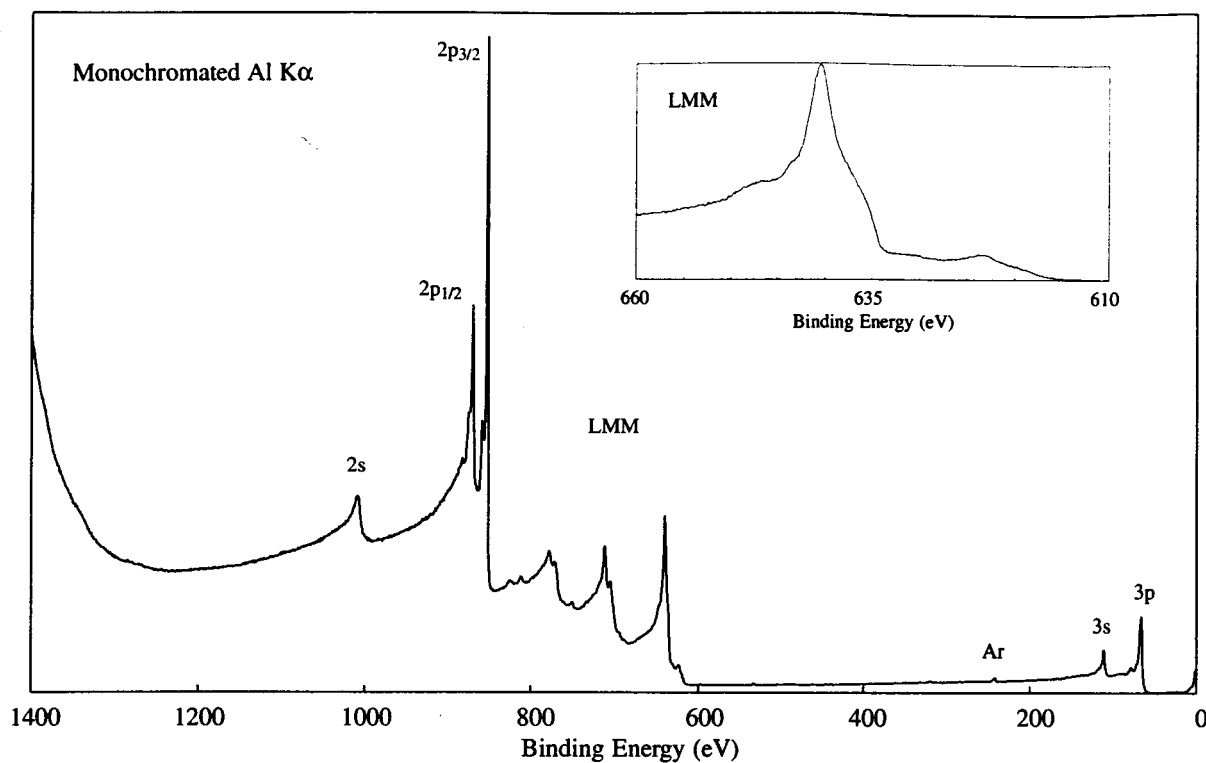


Line Positions (eV)				
Photoelectron Lines				
2s	2p _{1/2}	2p _{3/2}	3s	3p
925	793	778	101	60
Auger Lines				
L ₃ M ₂₃ M ₂₃	L ₂ M ₂₃ M ₂₃	L ₃ M ₂₃ M ₄₅ (¹ P)		
838	831	777	(Al)	
605	598	544	(Mg)	
L ₃ M ₂₃ M ₄₅ (³ P)	L ₂ M ₂₃ M ₄₅ (¹ P)	L ₃ M ₄₅ M ₄₅		
771	713	698	(Al)	
538	480	465	(Mg)	

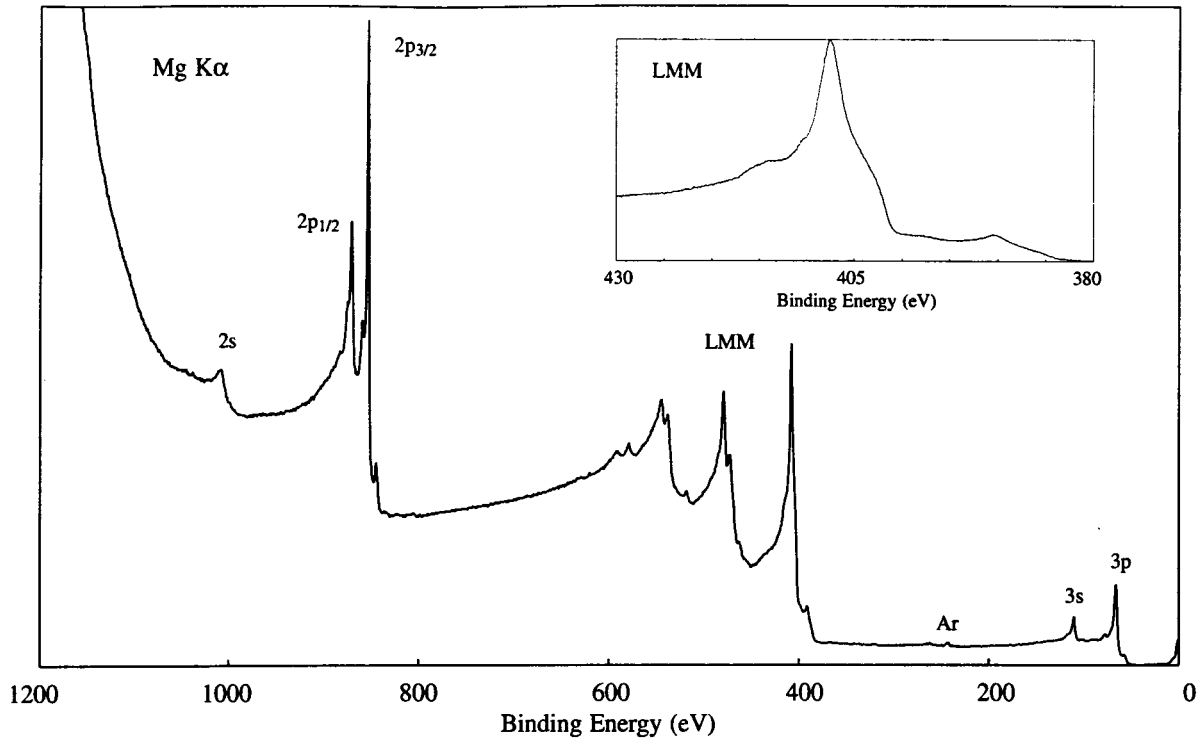


Compound Type	$2p_{3/2}$ Binding Energy (eV)						
	778	779	780	781	782	783	784
Co	■						
CoF ₂						■	■
CoF ₃					■	■	
CoO			■	■			
Co ₃ O ₄		■	■	■			
Co ₂ O ₃		■	■				
CoOOH		■	■				
Co(OH) ₂				■	■		
CoSO ₄							■
Co(NH ₃) ₃ Cl ₃				■	■		

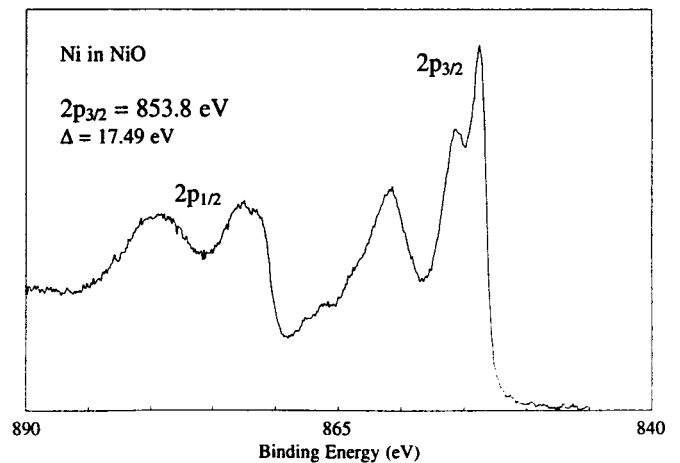


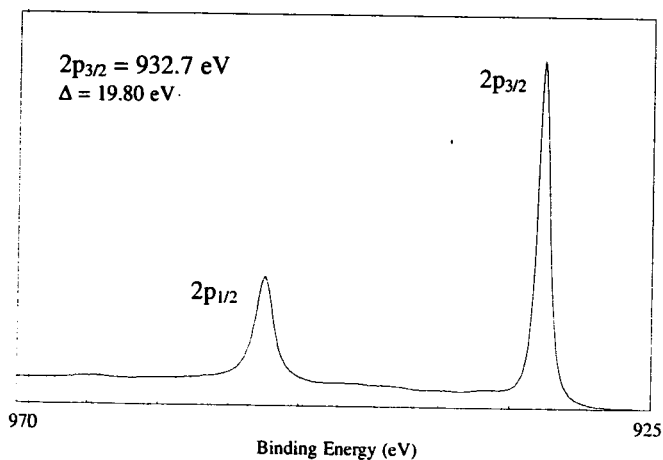
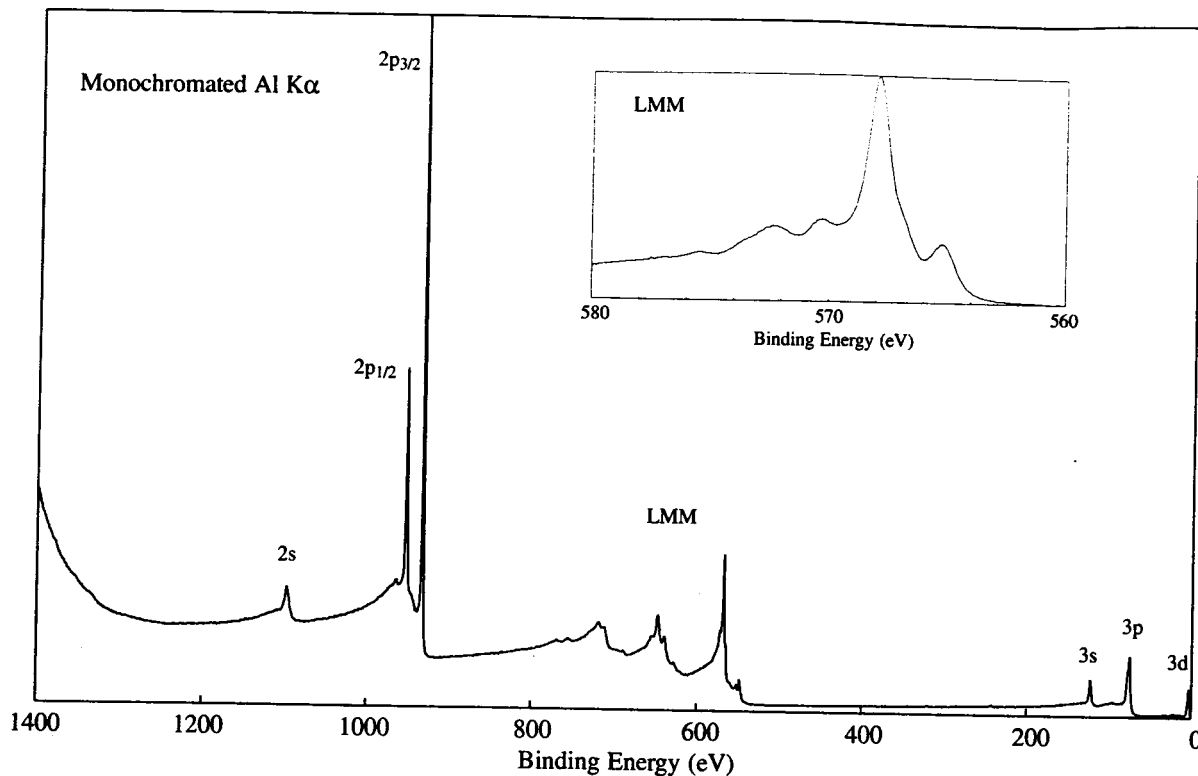


Line Positions (eV)					
<u>Photoelectron Lines</u>					
2s	2p _{1/2}	2p _{3/2}	3s	3p	
1009	870	853	111	67	
<u>Auger Lines</u>					
L ₃ M ₂₃ M ₂₃	L ₂ M ₂₃ M ₂₃	L ₃ M ₂₃ M ₄₅ (¹ P)			
778	772	712			
545	539	479			
L ₃ M ₂₃ M ₄₅ (³ P)	L ₂ M ₂₃ M ₄₅ (¹ P)	L ₃ M ₄₅ M ₄₅			
706	641	624 (Al)			
473	408	391 (Mg)			

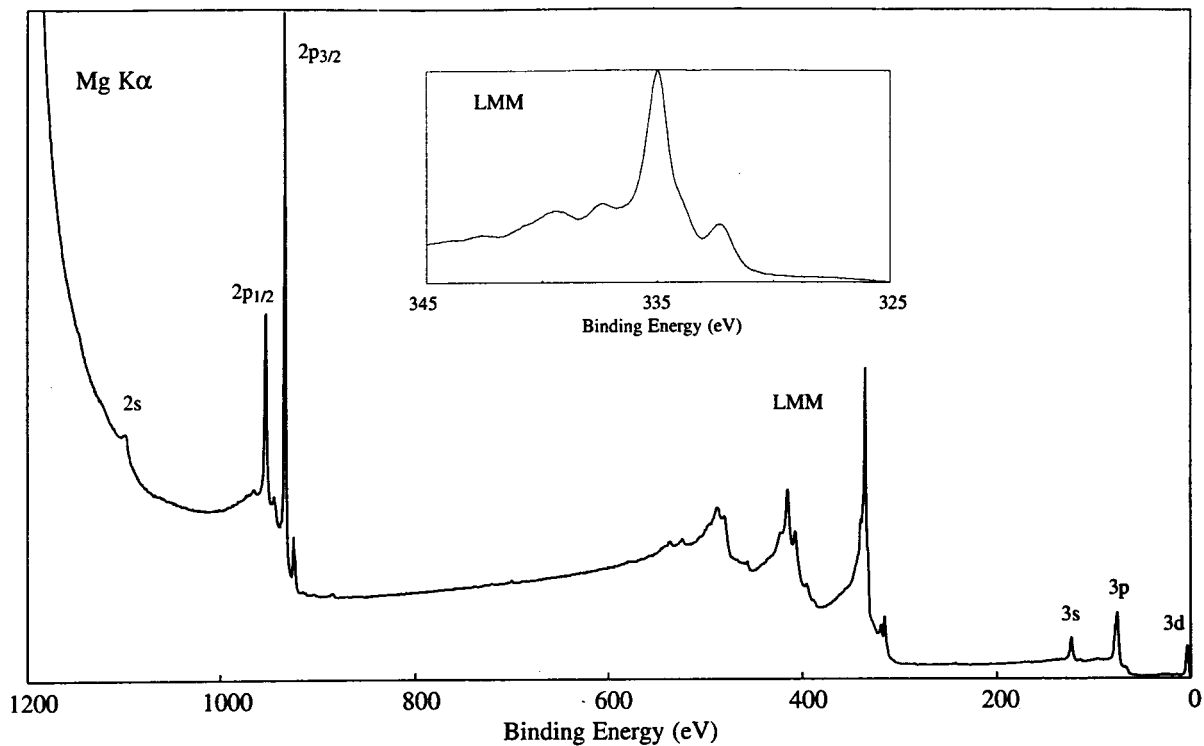


Compound Type	2p _{3/2} Binding Energy (eV)						
	852	853	854	855	856	857	858
Ni		■					
Silicides		■	■				
NiS		■	■				
Halides					■	■	■
NiO			■	■			
Ni ₂ O ₃					■	■	■
Ni(NO ₃) ₂					■	■	■
Ni(acac) ₂					■	■	■
Ni(OAc) ₂ · 4H ₂ O					■	■	■
Ni(dimethylglyoxim) ₂				■			

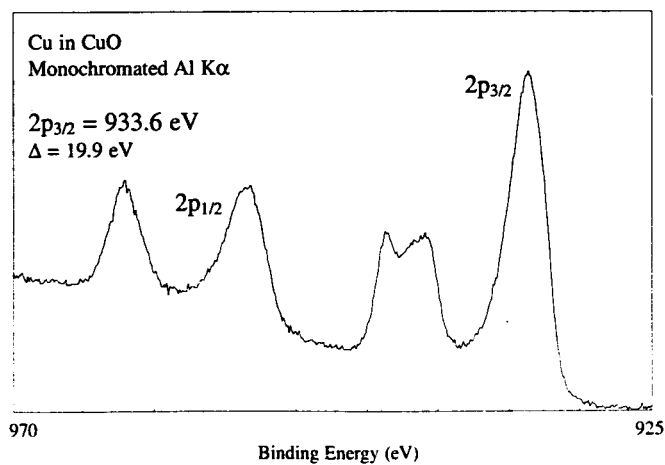


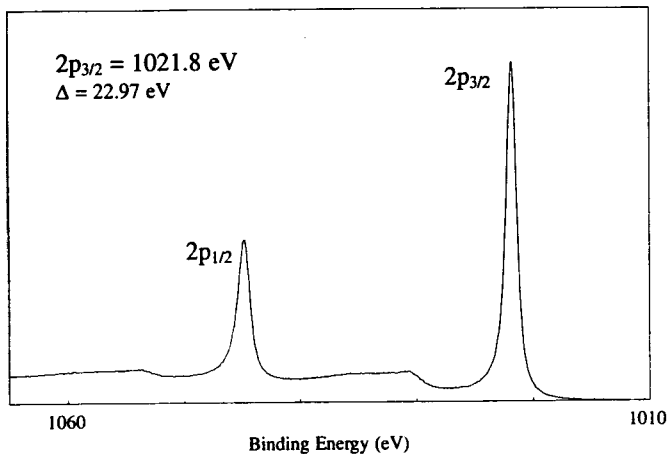
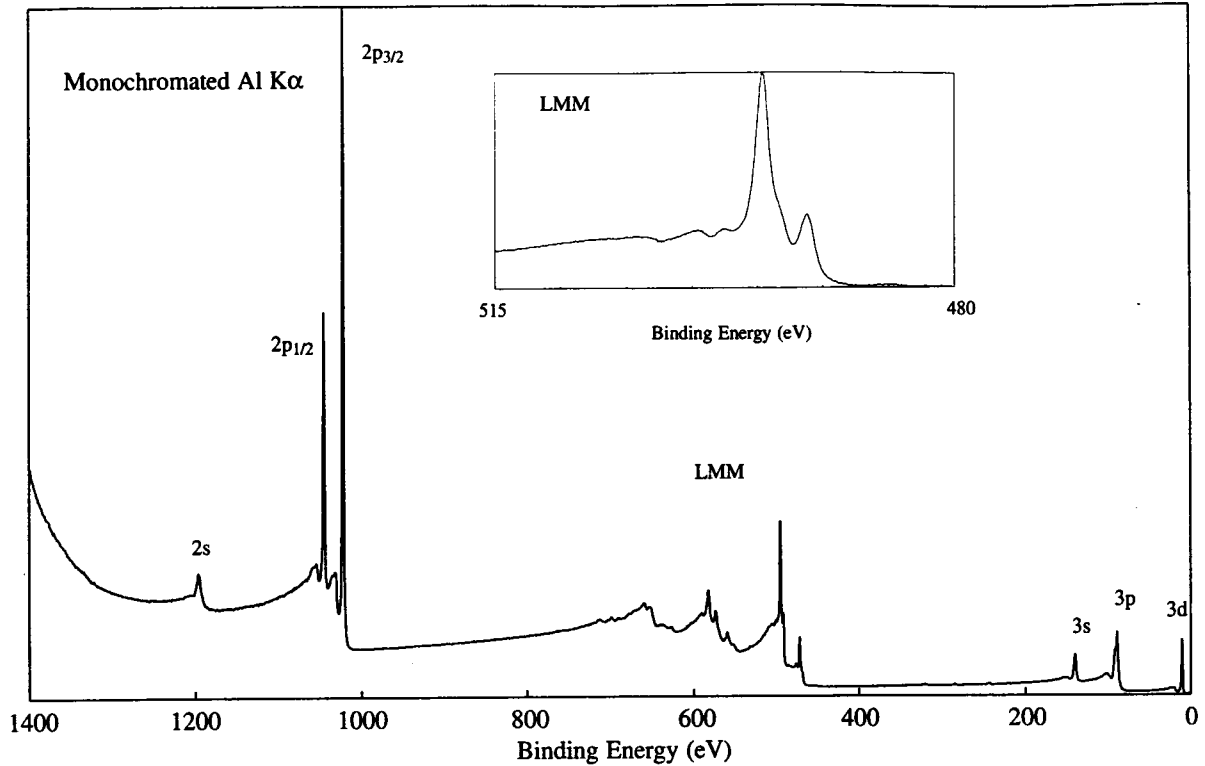


Line Positions (eV)					
<u>Photoelectron Lines</u>					
2s	2p _{1/2}	2p _{3/2}	3s	3p _{1/2}	3p _{3/2}
1097	953	933	123	77	75
<u>Auger Lines</u>					
	L ₃ M ₂₃ M ₂₃	L ₂ M ₂₃ M ₂₃	L ₃ M ₂₃ M ₄₅ (¹ P)		
	719	712	648 (Al)		
	486	479	415 (Mg)		
	L ₃ M ₂₃ M ₄₅ (³ P)	L ₂ M ₂₃ M ₄₅ (¹ P)	L ₃ M ₄₅ M ₄₅	L ₂ M ₄₅ M ₄₅	
	640	628	568	548 (Al)	
	407	395	335	315 (Mg)	

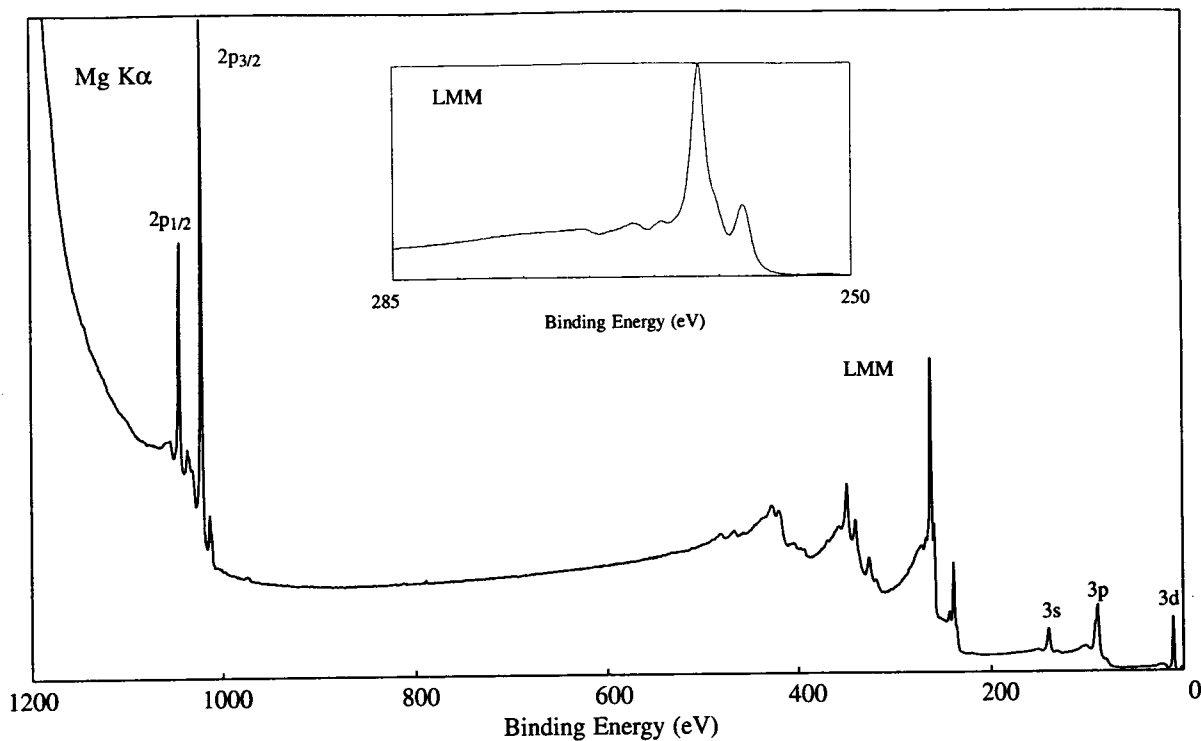


Compound Type	$2p_{3/2}$ Binding Energy (eV)					
	931	932	933	934	935	936
Cu			■			
Cu ₂ S		■	■			
CuS		■	■			
CuCl		■	■			
CuCl ₂					■	■
Cu ₂ O		■	■			
CuO				■	■	
Cu(OH) ₂					■	■
CuSO ₄					■	■
Cu(OAc) ₂		■	■	■	■	■
Cu(salicylaldoxime)				■		

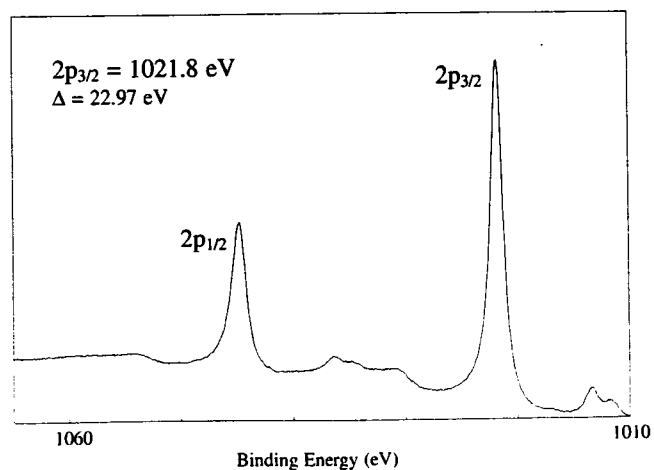


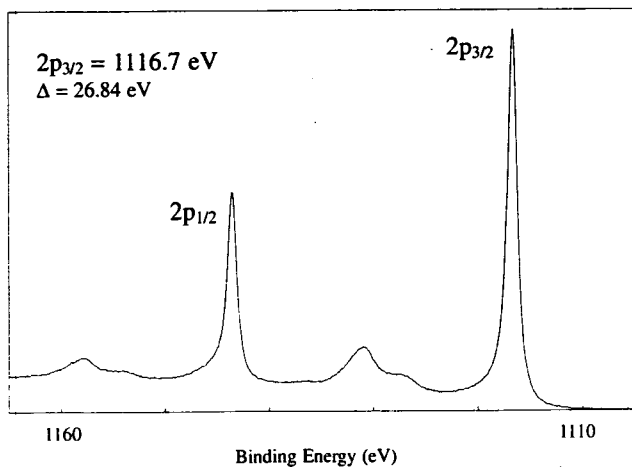
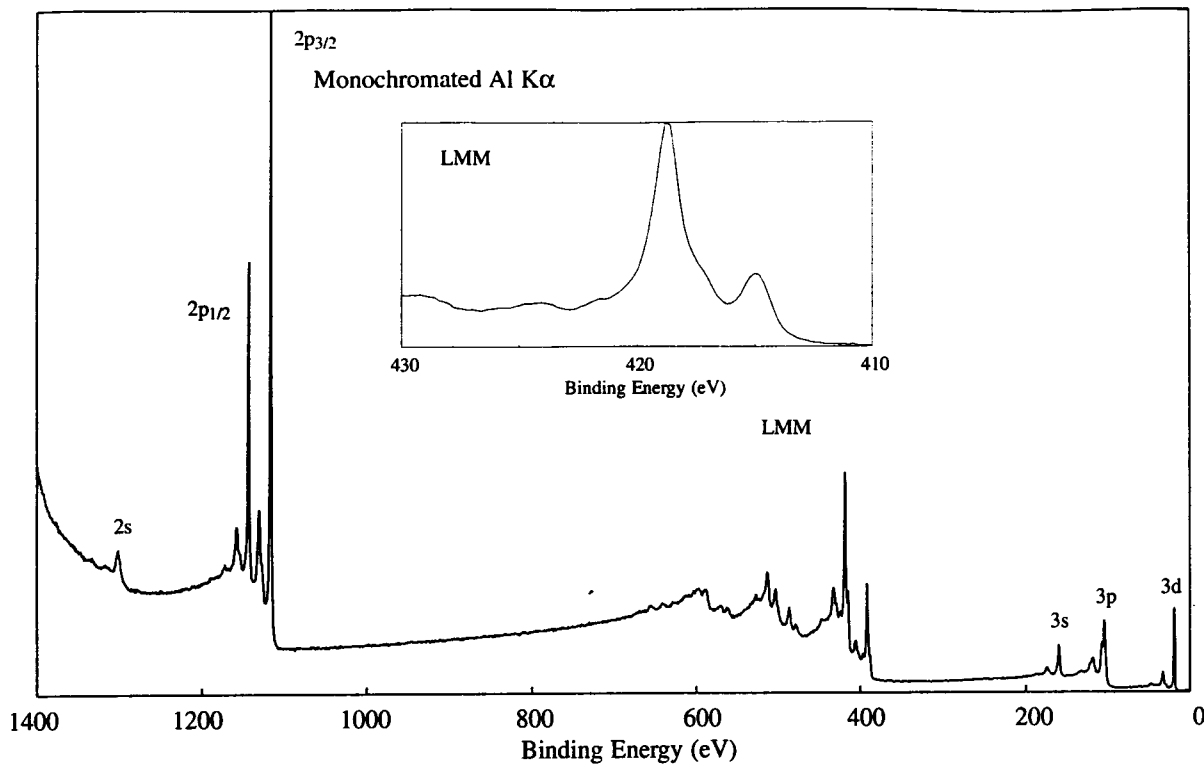


Line Positions (eV)						
Photoelectron Lines						
2s	2p _{1/2}	2p _{3/2}	3s	3p _{1/2}	3p _{3/2}	3d
1195	1045	1022	140	91	89	10
Auger Lines						
L ₃ M ₂₃ M ₂₃		L ₂ M ₂₃ M ₂₃		L ₃ M ₂₃ M ₄₅ (¹ P)		
660		652		582 (Al)		
427		419		349 (Mg)		
L ₃ M ₂₃ M ₄₅ (³ P)		L ₂ M ₂₃ M ₄₅ (¹ P)		L ₃ M ₄₅ M ₄₅		L ₂ M ₄₅ M ₄₅
573		559		495		472 (Al)
340		326		262		239 (Mg)

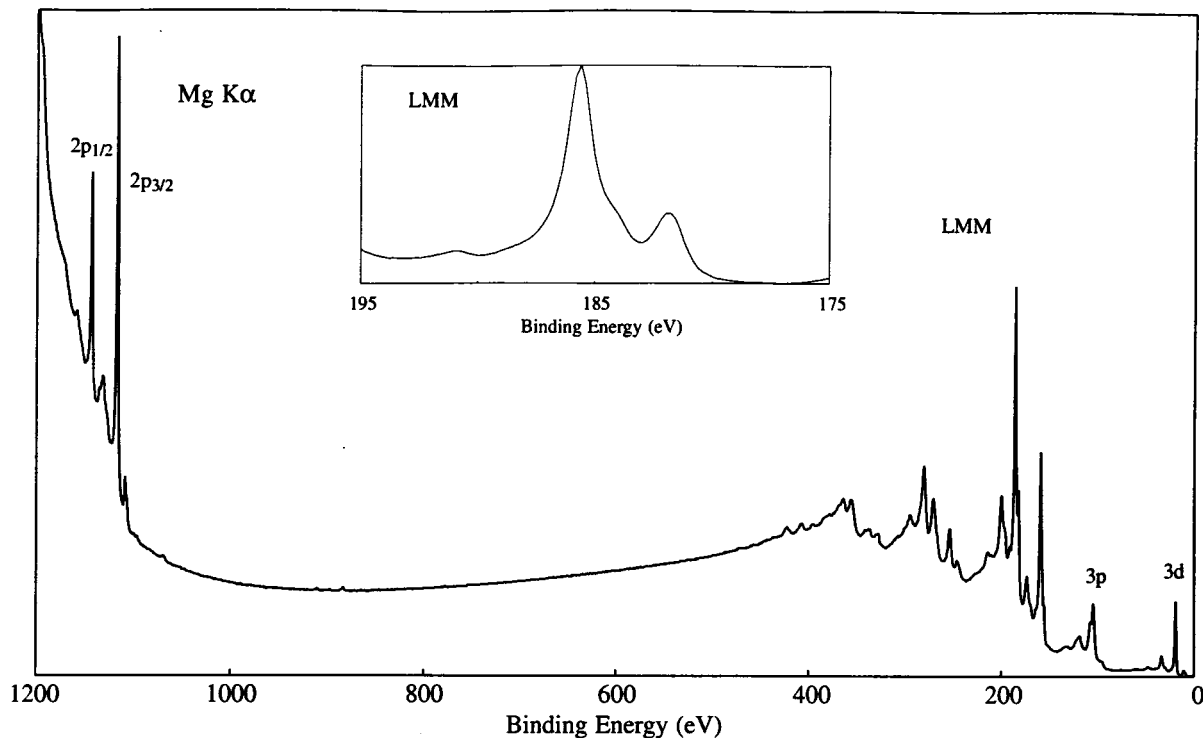


Compound Type	2p _{3/2} Binding Energy (eV)				
	1020	1021	1022	1023	1024
Zn					
ZnS					
Phosphide		■			
Halides					
ZnO				■	
Zn(acac) ₂			■		
(Me ₄ N) ₂ ZnBr ₄		■			
ZnSO ₄					■
Zn ₄ Si ₂ O ₇ (OH) ₂ · 2H ₂ O			■		
ZnCr ₂ O ₄			■		
ZnRh ₂ O ₄			■		



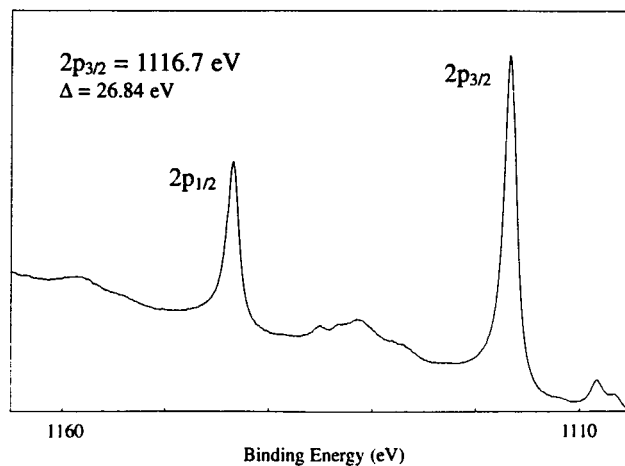


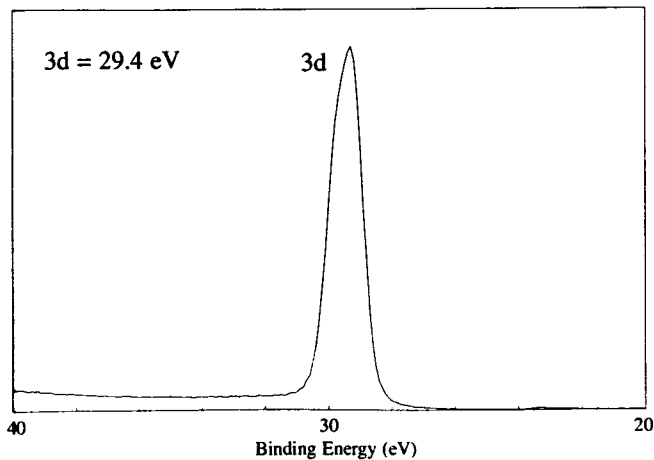
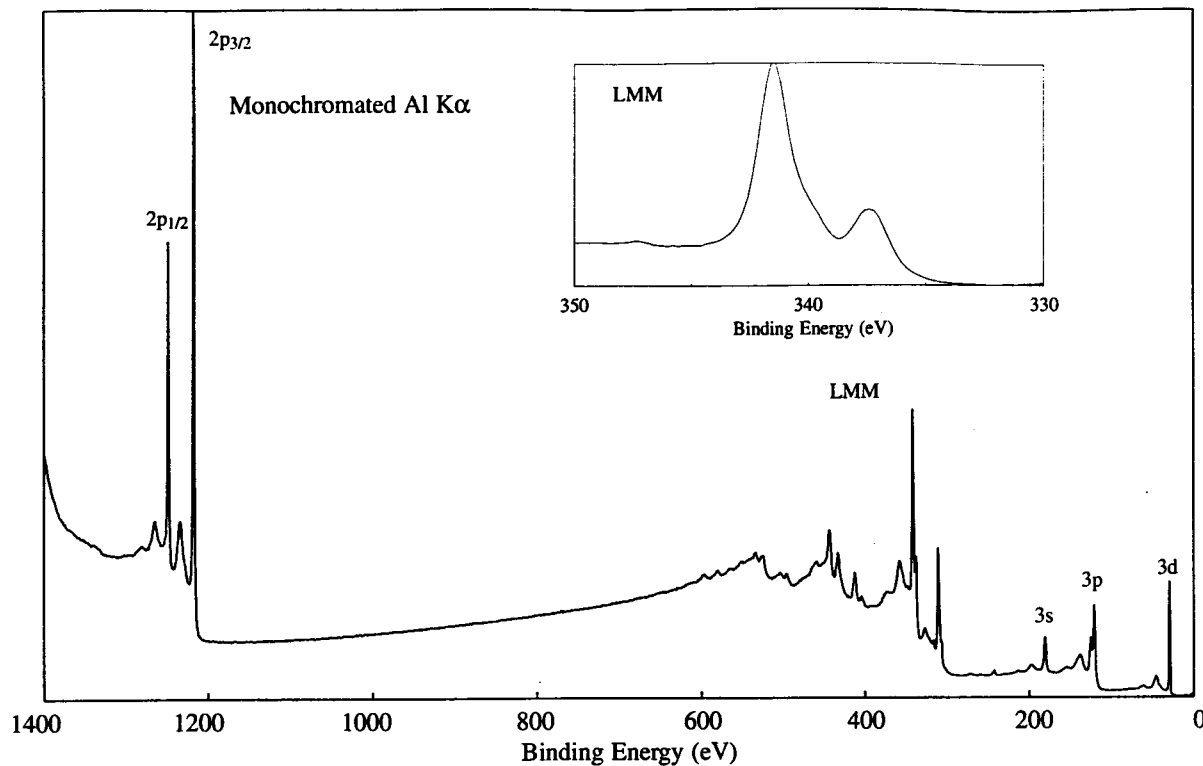
Line Positions (eV)						
Photoelectron Lines						
2s	2p _{1/2}	2p _{3/2}	3s	3p _{1/2}	3p _{3/2}	3d
1301	1144	1117	160	107	104	19
Auger Lines						
	L ₃ M ₂₃ M ₂₃	L ₂ M ₂₃ M ₂₃	L ₃ M ₂₃ M ₄₅ (¹ P)			
	597	589	514 (Al)			
	364	356	281 (Mg)			
	L ₃ M ₂₃ M ₄₅ (³ P)	L ₂ M ₂₃ M ₄₅ (¹ P)	L ₃ M ₄₅ M ₄₅	L ₂ M ₄₅ M ₄₅		
	504	487	419	392 (Al)		
	271	254	186	159 (Mg)		



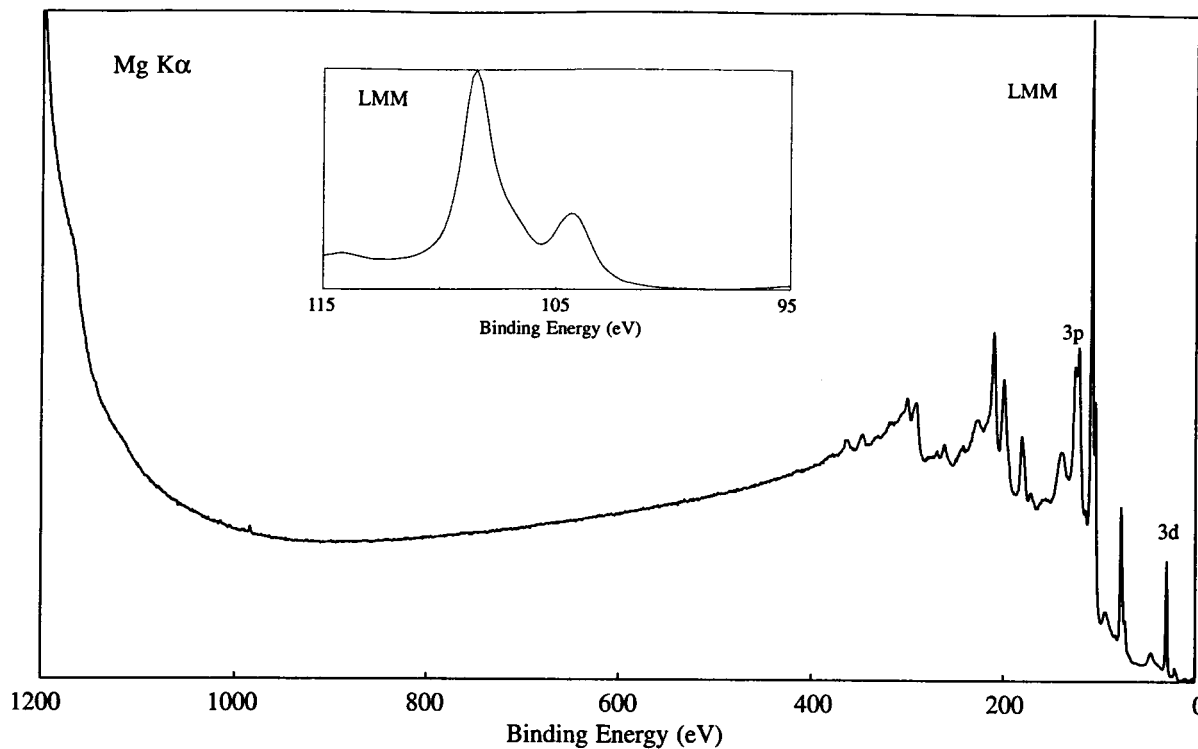
2p _{3/2} Binding Energy (eV)				
Compound Type	1116	1117	1118	
Ga		■		
GaP		■		
Ga ₂ O ₃		■	■	

3d Binding Energy (eV)				
Compound Type	18	19	20	21
Ga	■			
GaAs		■		
GaP		■	■	
AlGaAs		■		
Ga ₂ O ₃				■

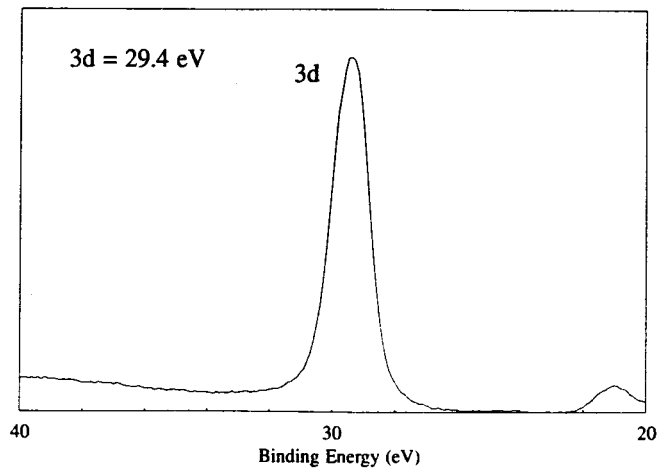


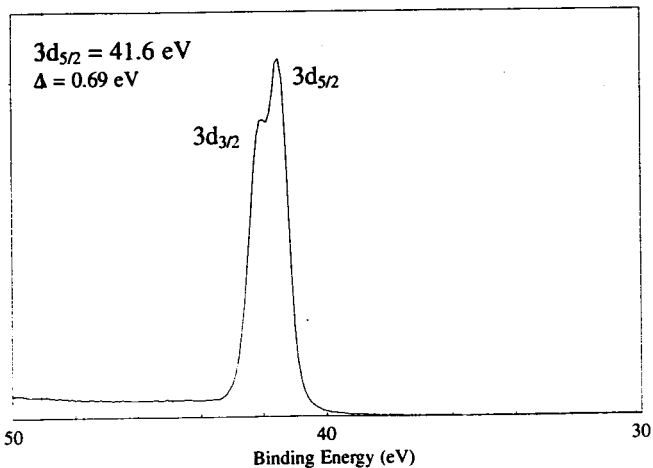
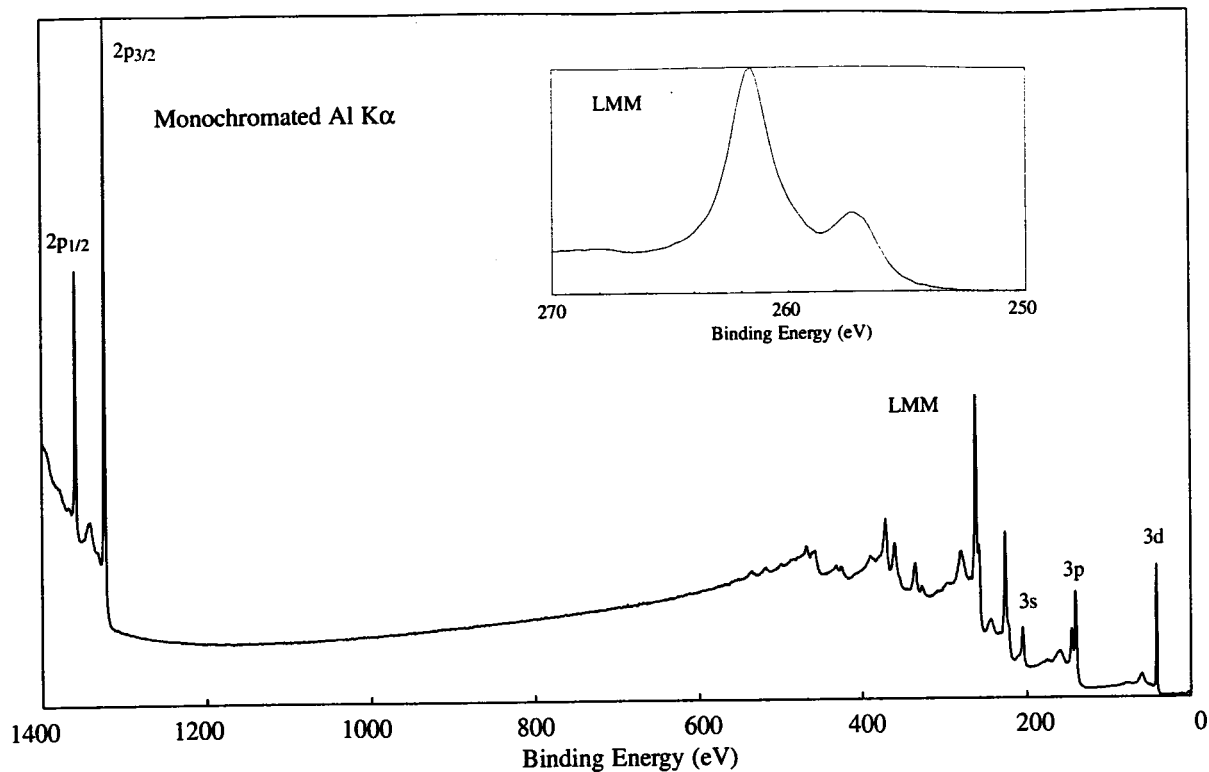


Line Positions (eV)					
Photoelectron Lines					
2p _{1/2}	2p _{3/2}	3s	3p _{1/2}	3p _{3/2}	3d
1248	1217	181	126	122	29
Auger Lines					
	L ₃ M ₂₃ M ₂₃	L ₂ M ₂₃ M ₂₃	L ₃ M ₂₃ M ₄₅ (¹ P)		
	534	525	444 (Al)		
	301	292	211 (Mg)		
L ₃ M ₂₃ M ₄₅ (³ P)	L ₂ M ₂₃ M ₄₅ (¹ P)	L ₃ M ₄₅ M ₄₅	L ₂ M ₄₅ M ₄₅		
433	412	342	310 (Al)		
200	179	109	77 (Mg)		

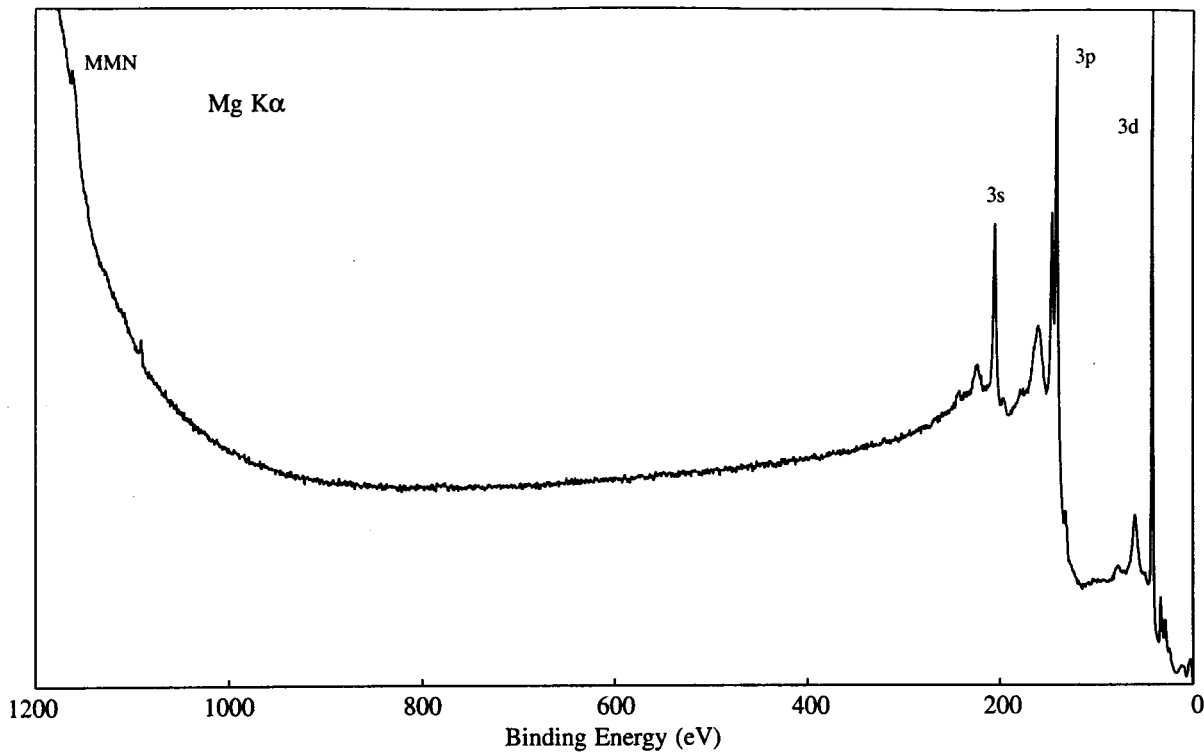


Compound Type	3d Binding Energy (eV)				
	29	30	31	32	33
Ge	■				
GeAs ₂	■	■			
GeTe ₃ As ₂		■	■		
GeS ₂ TeAs ₂		■	■		
GeS ₃ As		■	■		
GeTe ₂		■	■		
GeTe		■			
GeSe ₂			■	■	
GeSe			■	■	
Sulfides	■	■	■		
GeO ₂				■	

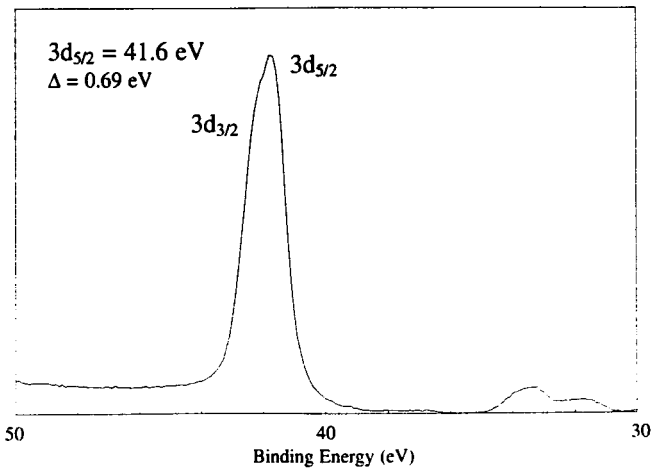


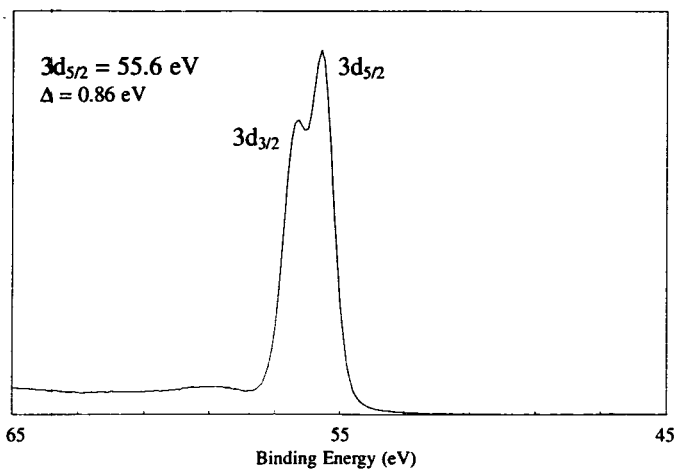
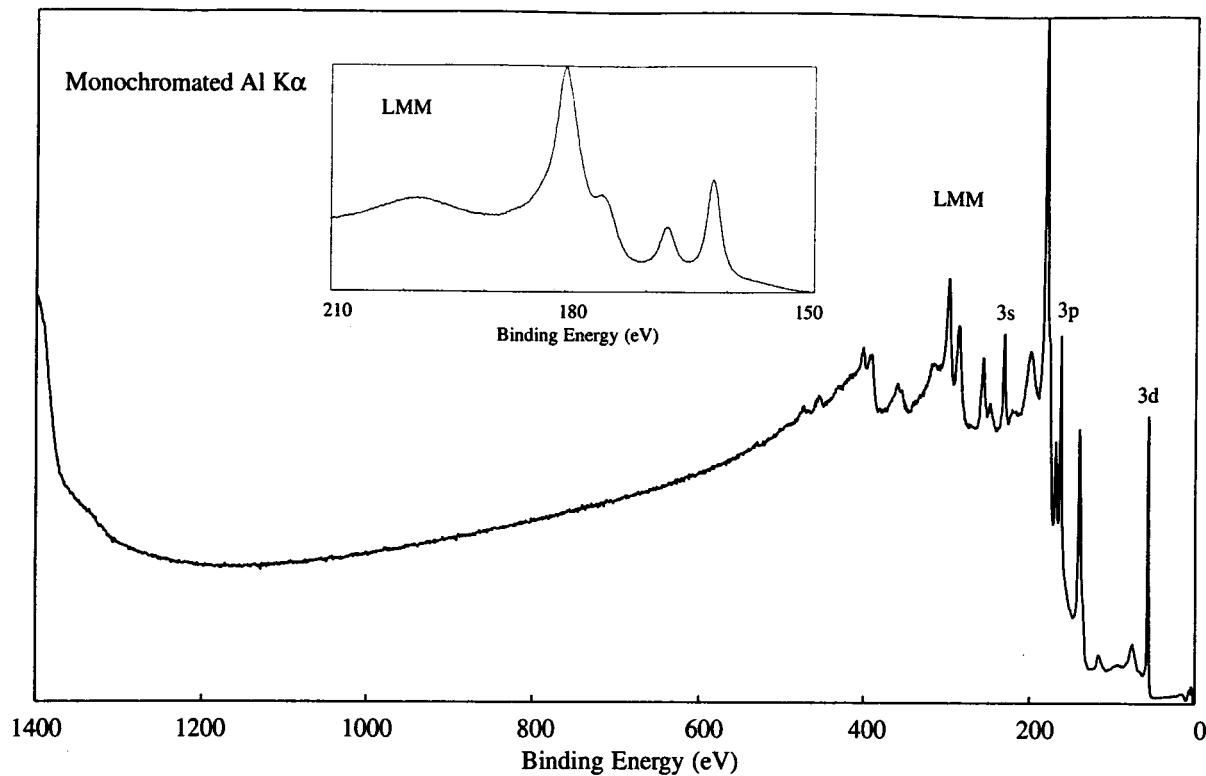


Line Positions (eV)						
Photoelectron Lines						
2p _{1/2}	2p _{3/2}	3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}
1359	1324	205	146	141	43	42
Auger Lines						
L ₃ M ₂₃ M ₄₅ (¹ P)		L ₃ M ₂₃ M ₄₅ (³ P)				
371		360 (Al)				
L ₂ M ₂₃ M ₄₅ (¹ P)		L ₃ M ₄₅ M ₄₅	L ₂ M ₄₅ M ₄₅			
336		262	226 (Al)			

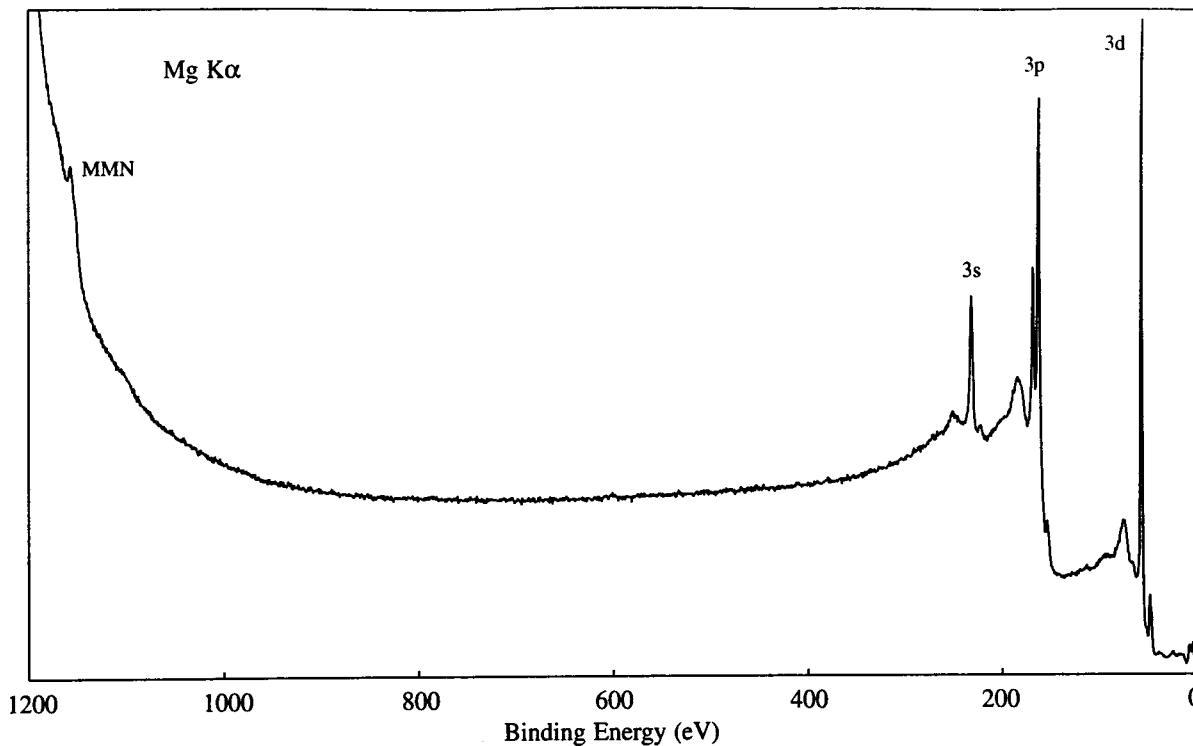


3d _{5/2} Binding Energy (eV)								
Compound Type	40	41	42	43	44	45	46	47
As			■					
AlAs		■						
AlGaAs		■						
GaAs		■						
InAs	■							
Sulfides				■	■			
AsI ₃				■				
AsBr ₃						■	■	
As ₂ O ₃						■		
As ₂ O ₅							■	

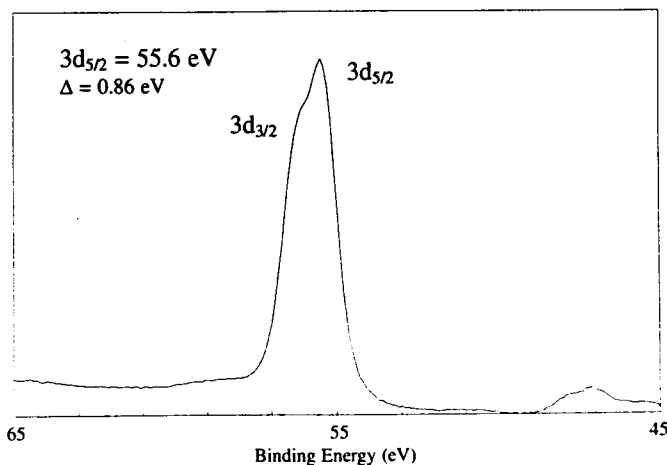


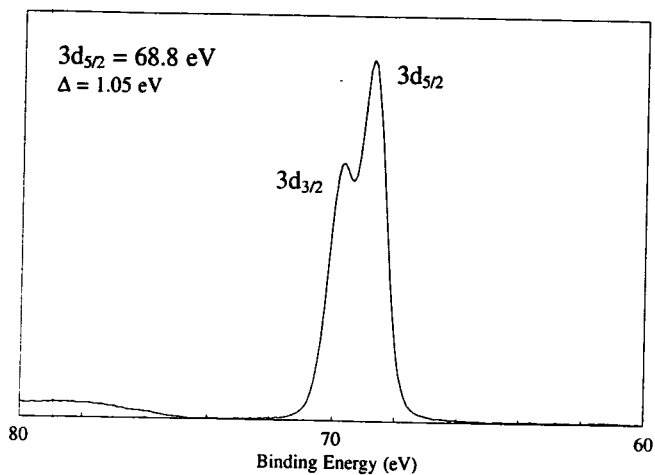
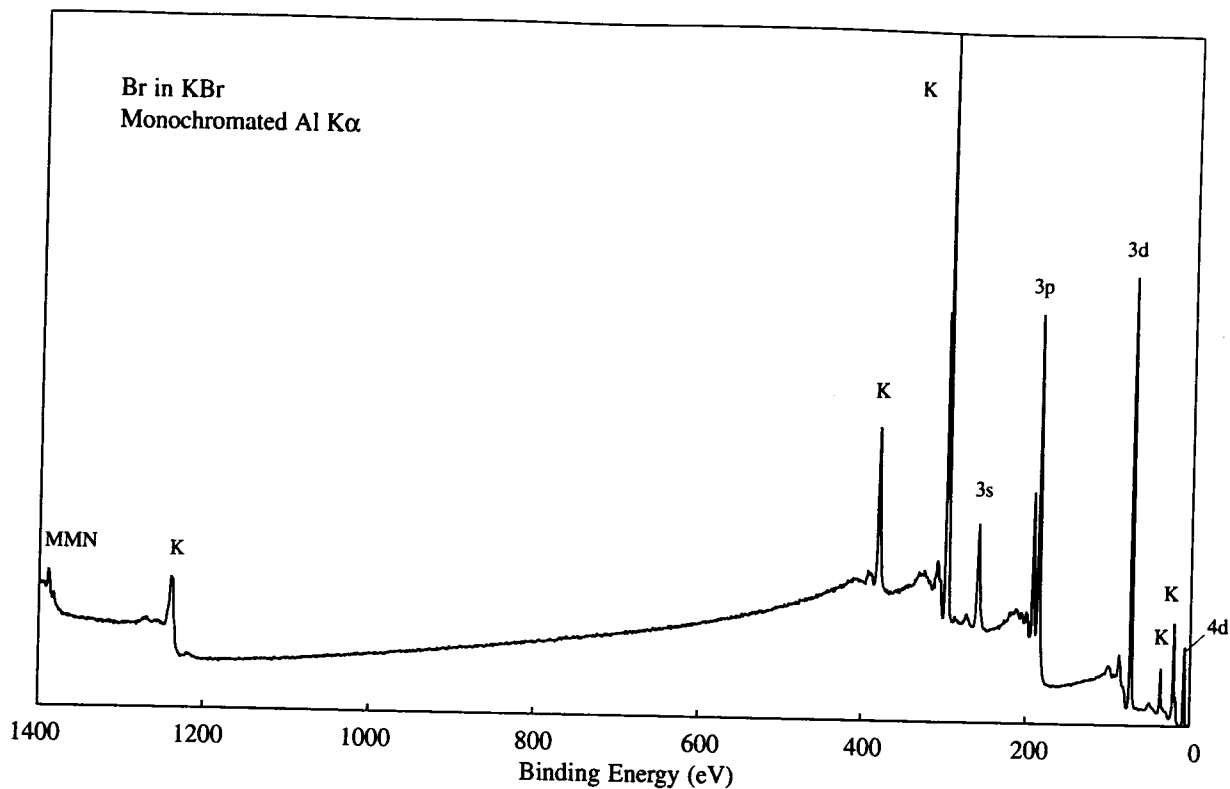


Line Positions (eV)				
<u>Photoelectron Lines</u>				
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}
232	169	163	57	56
<u>Auger Lines</u>				
$L_3M_{23}M_{45} (^1P)$		$L_3M_{23}M_{45} (^3P)$		
299		287 (Al)		
$L_2M_{23}M_{45} (^1P)$	$L_3M_{45}M_{45}$	$L_2M_{45}M_{45}$		
257	181	140 (Al)		

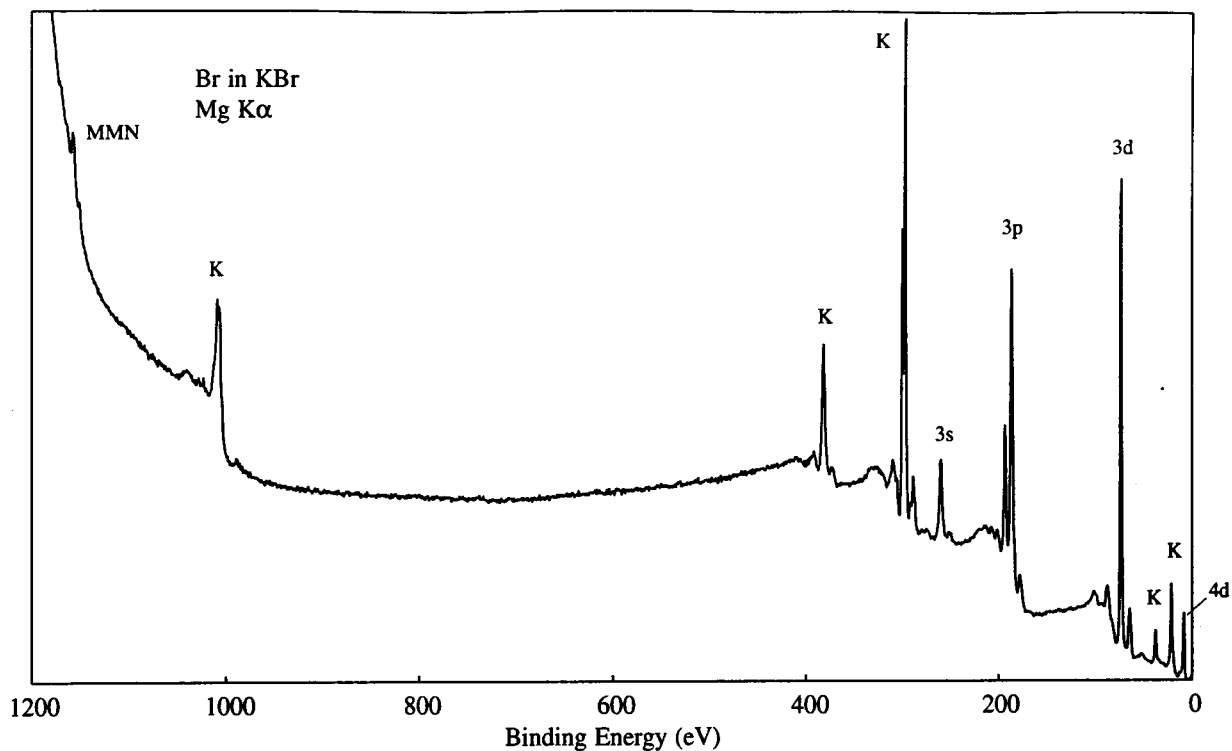


Compound Type	3d _{5/2} Binding Energy (eV)						
	54	55	56	57	58	59	60
Se							
As ₂ Se ₃							
Ga ₂ Se ₃							
GeSe							
GeSe ₂							
Selenides							
SeO ₂							
H ₂ SeO ₃							
(BrC ₆ H ₄) ₂ Se ₂							
(C ₁₄ H ₂₉ Se) ₂							
(C ₄ H ₈ COOH) ₂ SeO							

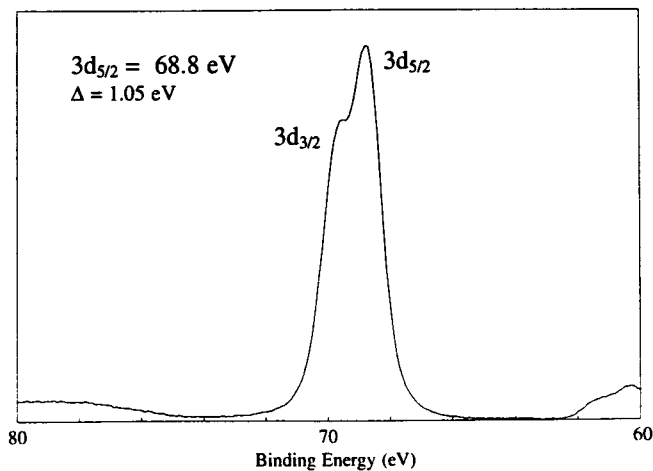


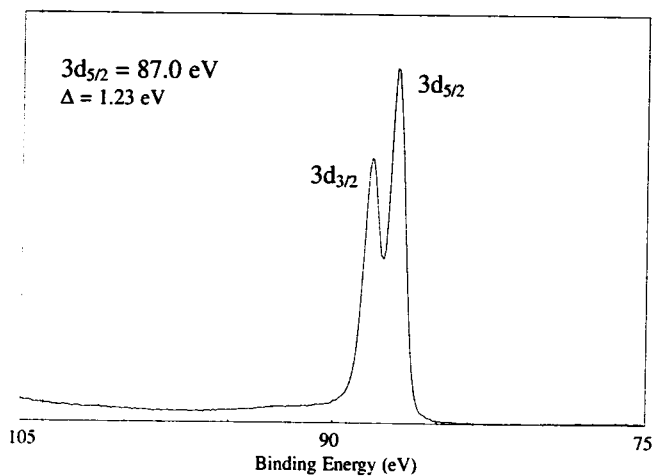
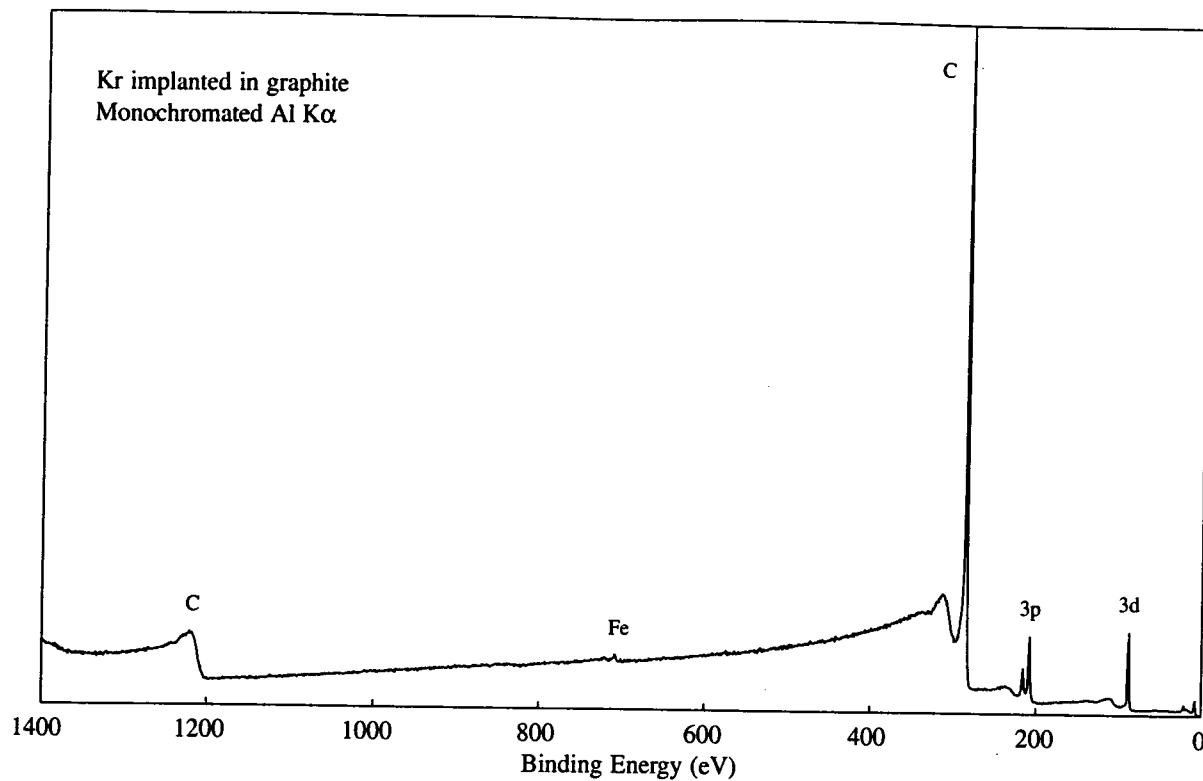


Line Positions (eV)						
<u>Photoelectron Lines</u>						
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4d
256	189	182	70	69	15	5
<u>Auger Lines</u>						
M ₂₃ M ₄₅ N ₂₃						
			1386	(Al)		
			1153	(Mg)		



Compound Type	$3d_{5/2}$ Binding Energy (eV)		
	68	69	70
CsBr	■		
RbBr	■	■	
KBr		■	
NaBr		■	
LiBr		■	■
CuBr ₂		■	■
PbBr ₂		■	■
Ni(NH ₃) ₆ Br ₂		■	■
Pt(NH ₃) ₄ Br ₂	■		
K ₂ PtBr ₄		■	■
K ₂ PtBr ₆		■	■



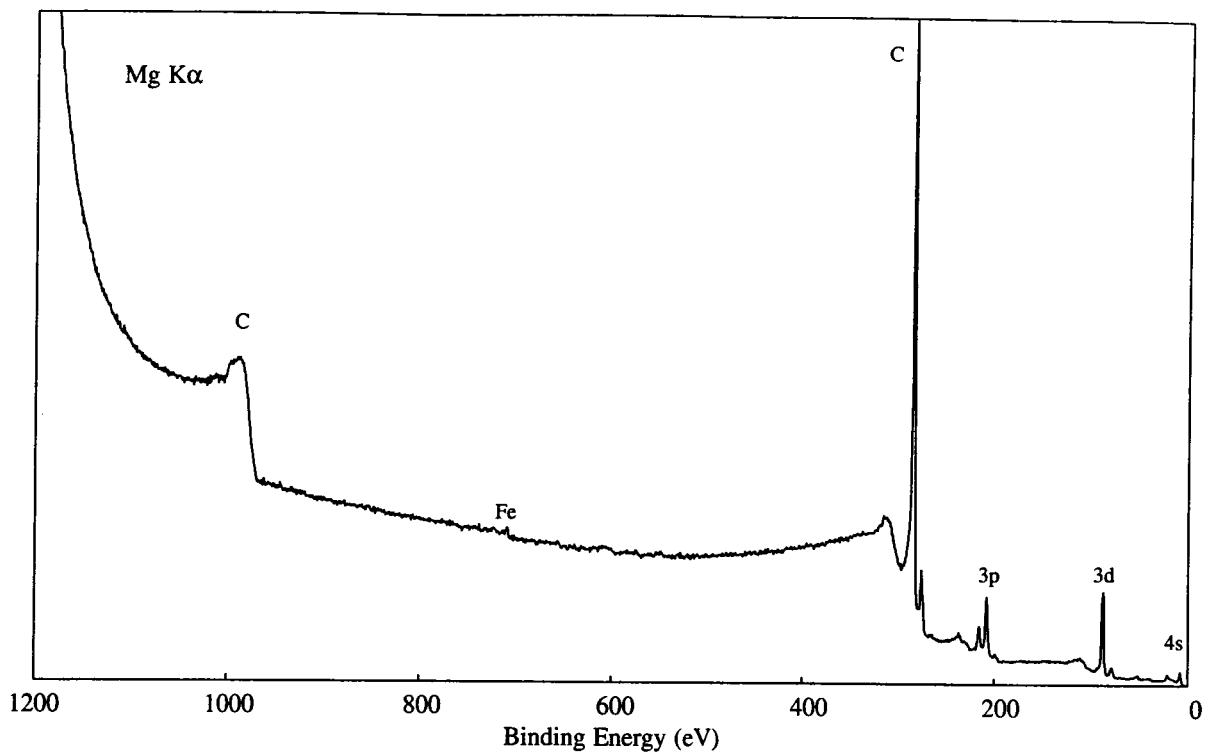


Line Positions (eV)

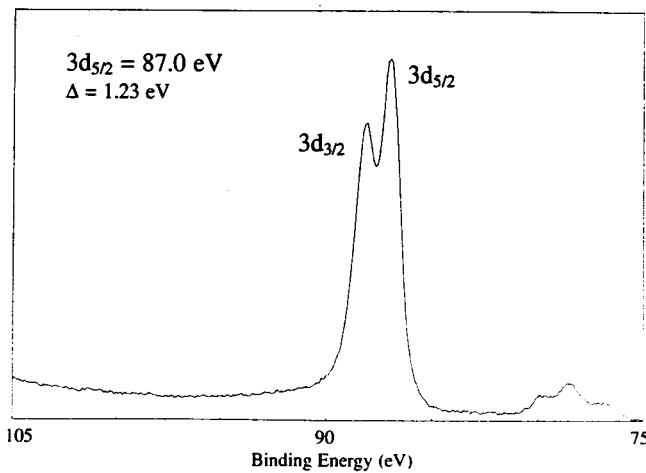
Photoelectron Lines

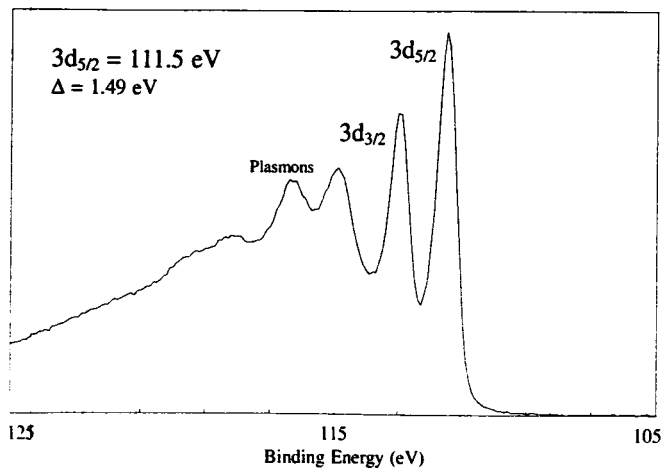
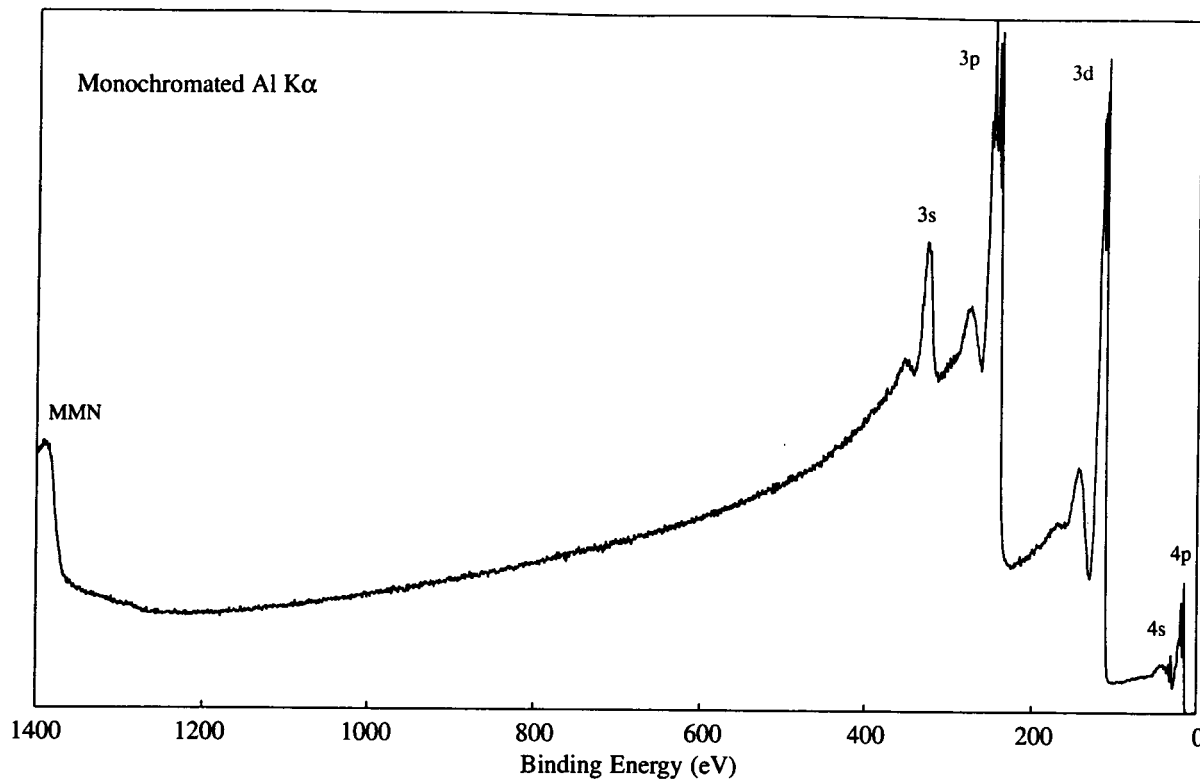
3s*	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p
287	216	208	88	87	21	8

*Estimate

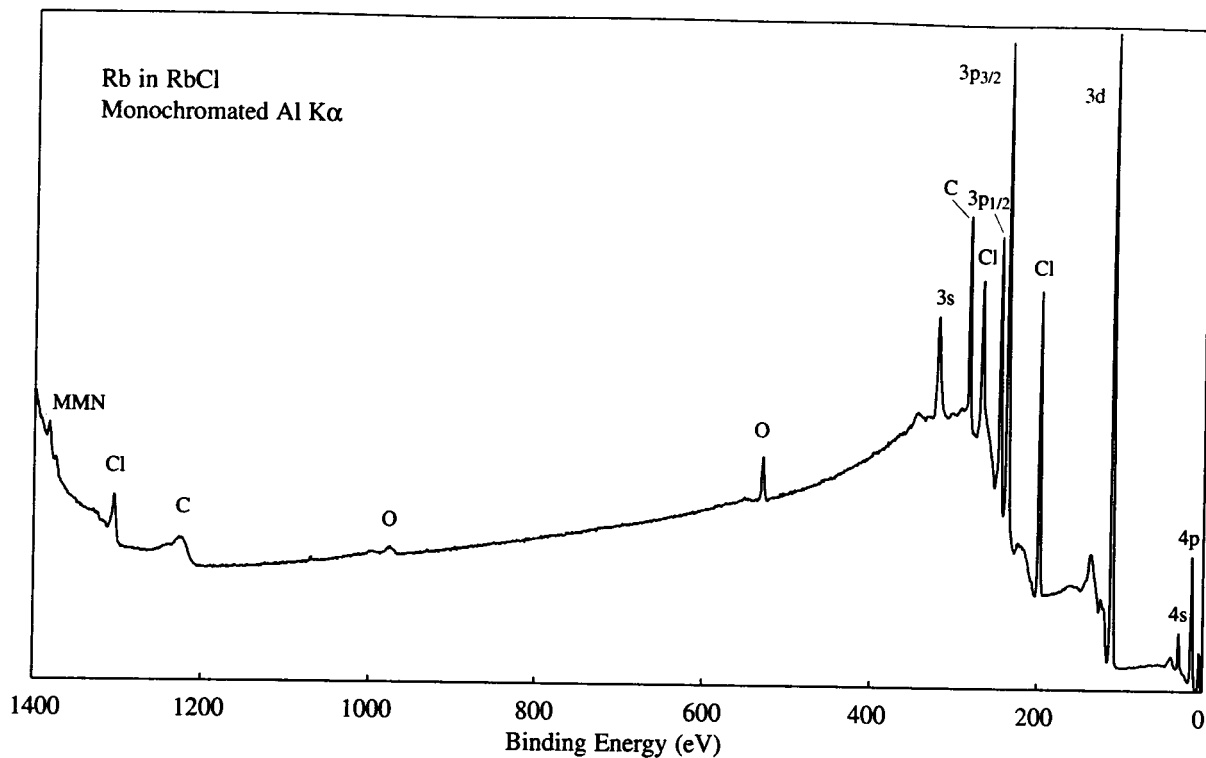


3d _{5/2} Binding Energy (eV)			
Compound Type	84	86	88
Kr in graphite		■	

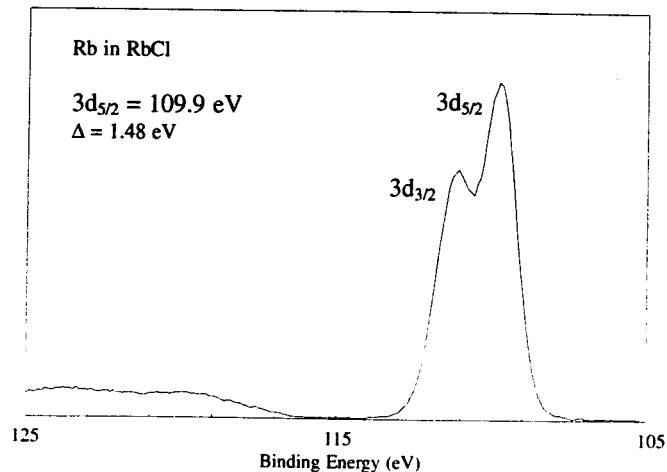


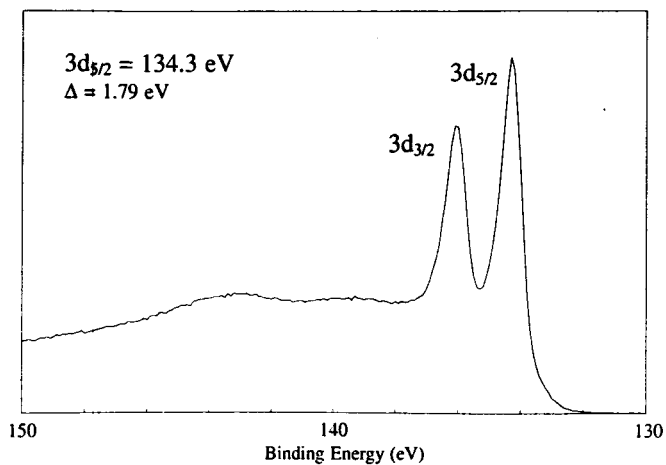
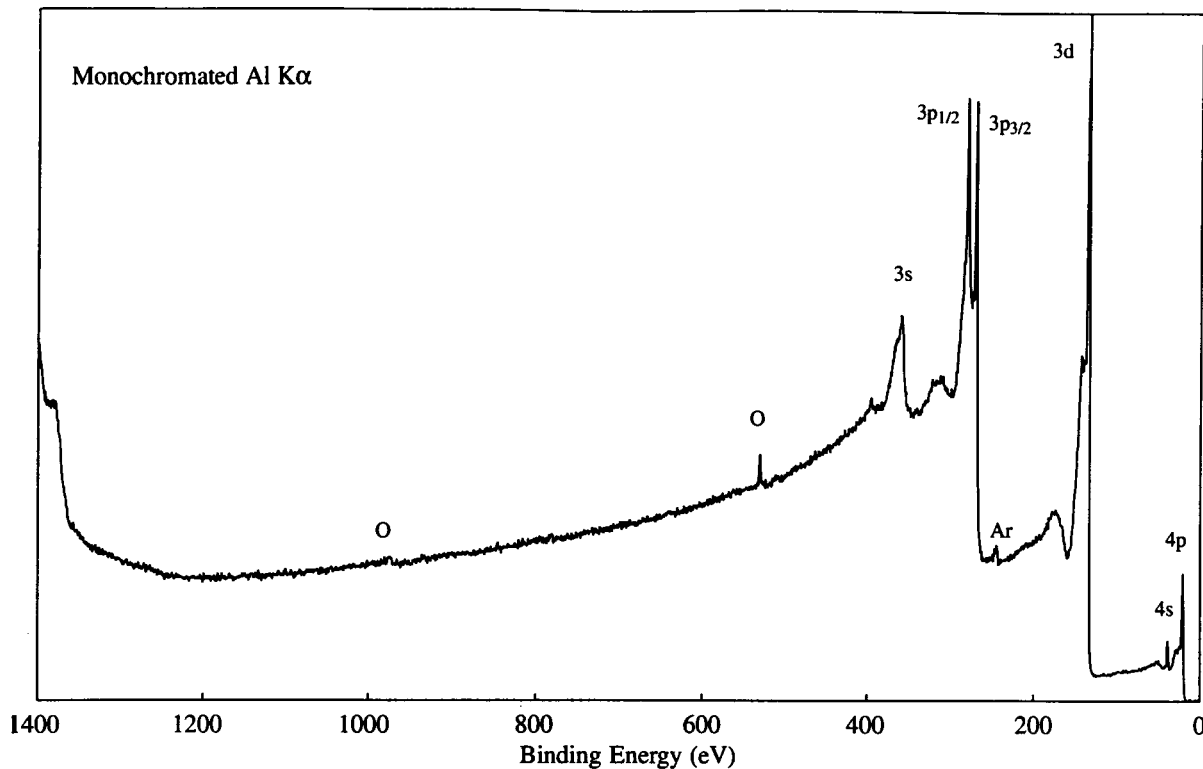


Line Positions (eV)						
Photoelectron Lines						
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p
325	249	240	113	111	31	16
Auger Lines						
M ₂₃ M ₄₅ N ₂₃						
1385						
1152						



Compound Type	3d _{5/2} Binding Energy		
	109	110	111
Rb			█
RbN ₃		█	
RbI			█
RbBr		█	
RbCl		█	
RbF		█	
Rb ₃ PO ₄		█	
Rb ₄ P ₂ O ₇		█	
RbClO ₄			█

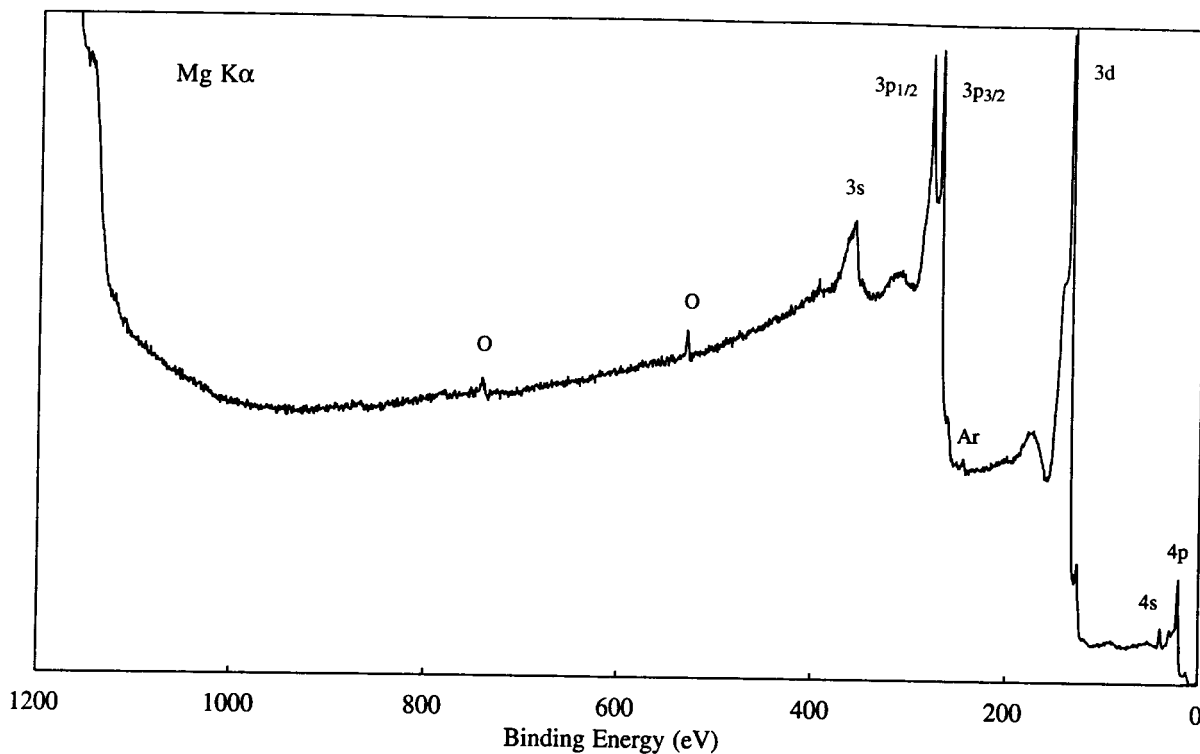




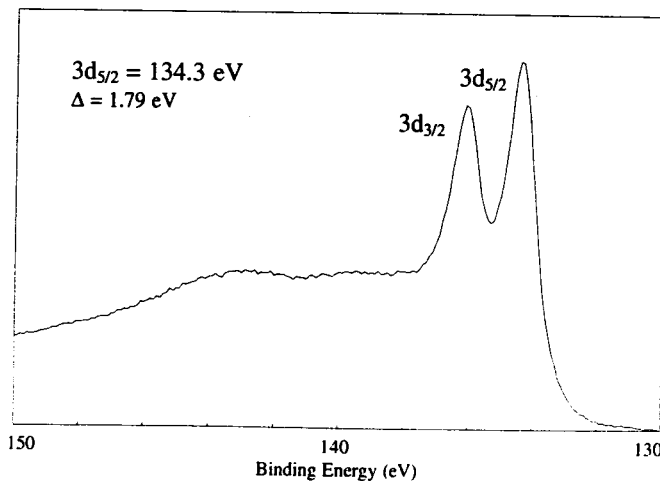
Line Positions (eV)

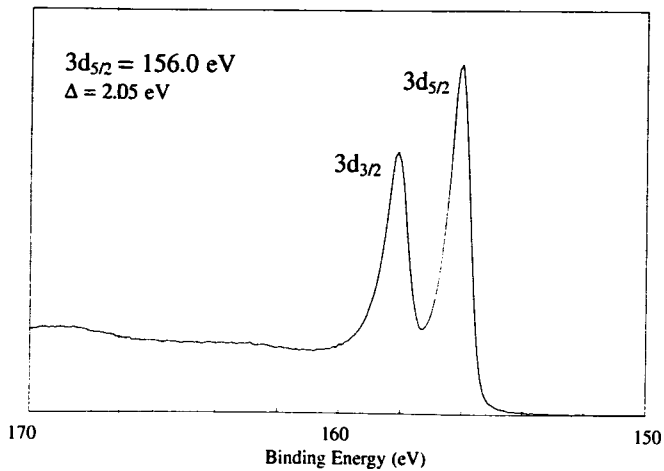
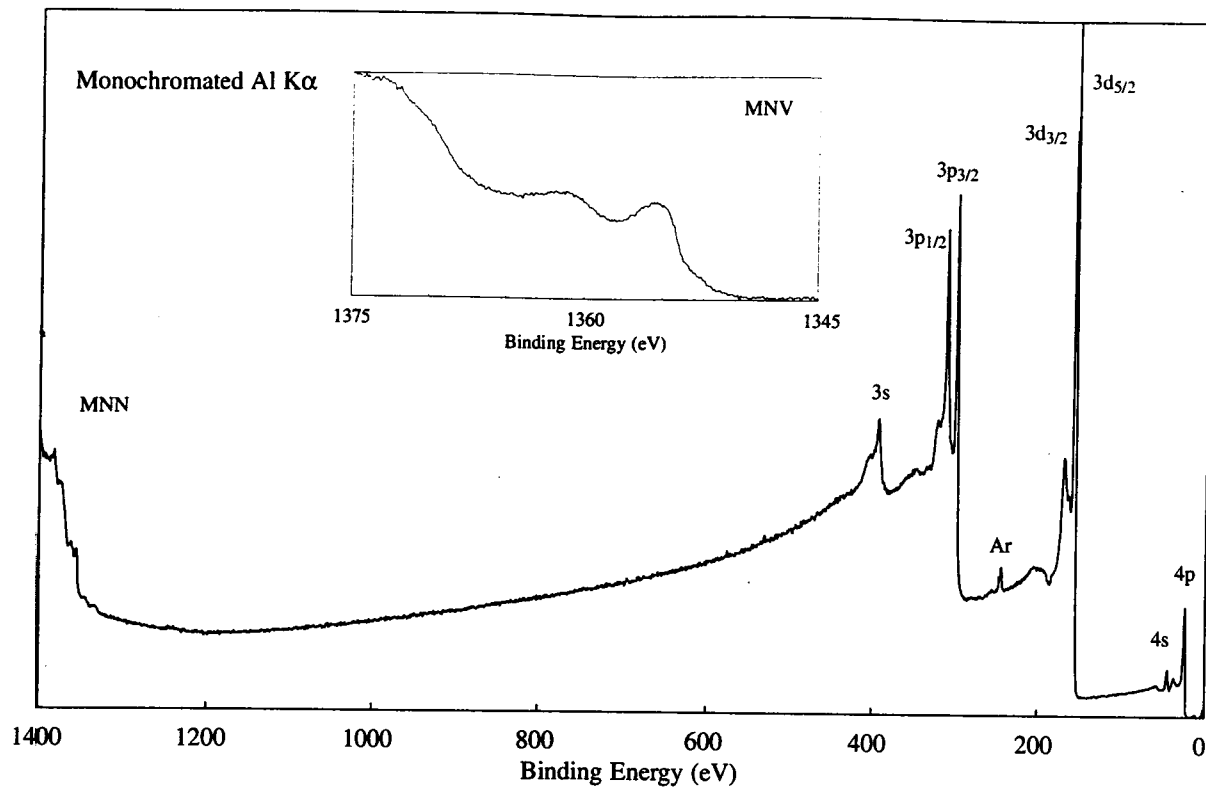
Photoelectron Lines

3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p
360	281	270	136	134	39	21

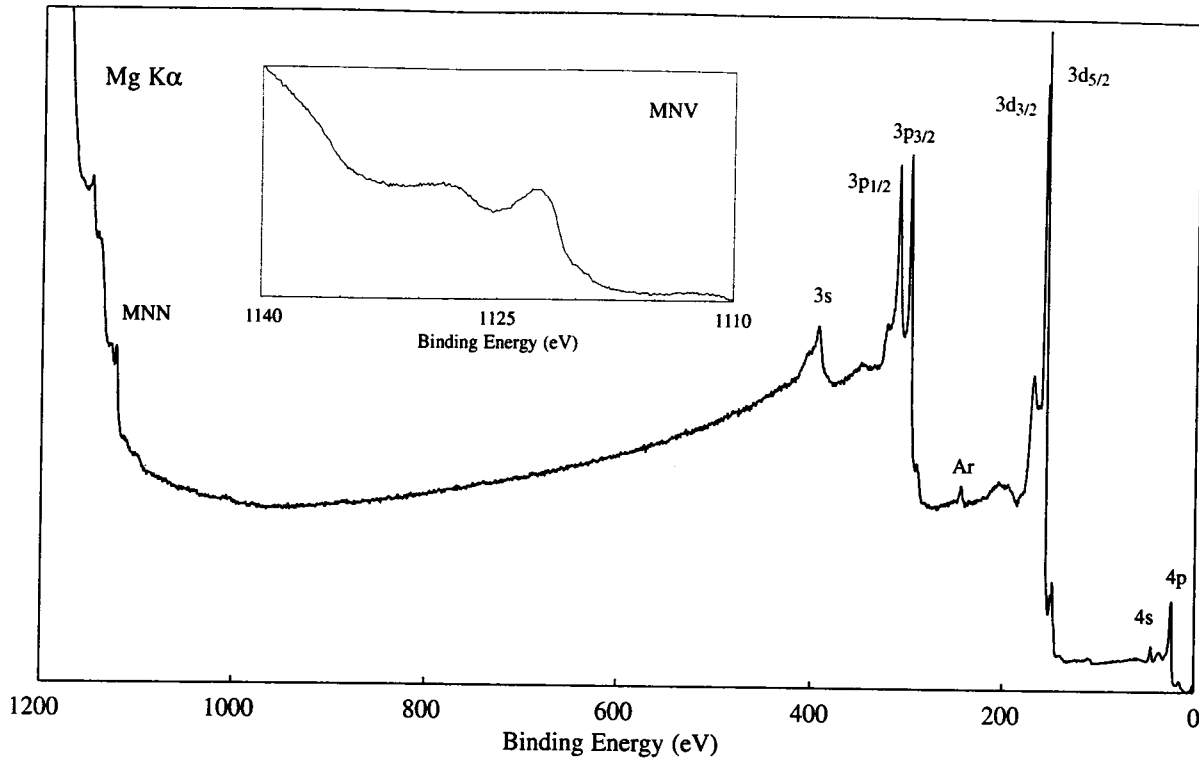


Compound Type	3d _{5/2} Binding Energy (eV)			
	133	134	135	136
Sr			■	
SrO				■
SrF ₂		■		
SrCO ₃	■			
SrSO ₄		■		
Sr(NO ₃) ₂			■	
SrMoO ₄		■		
SrRh ₂ O ₄	■			

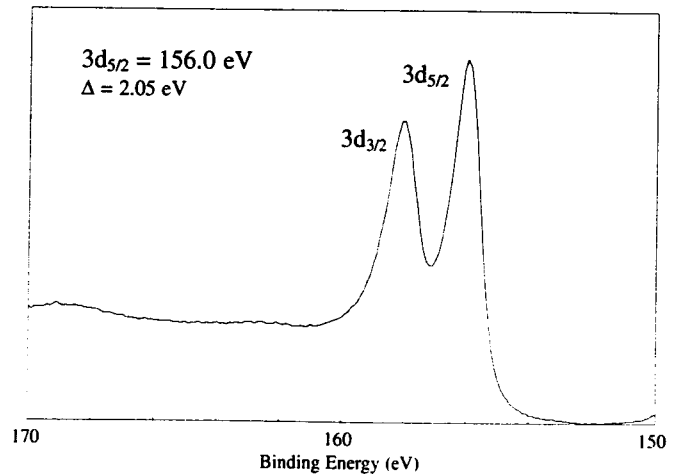


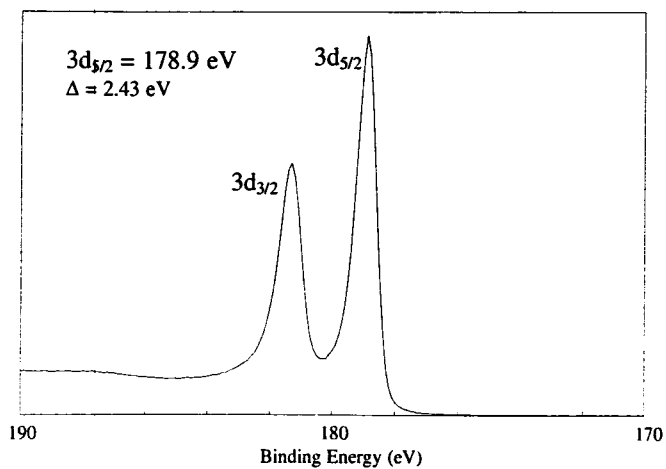
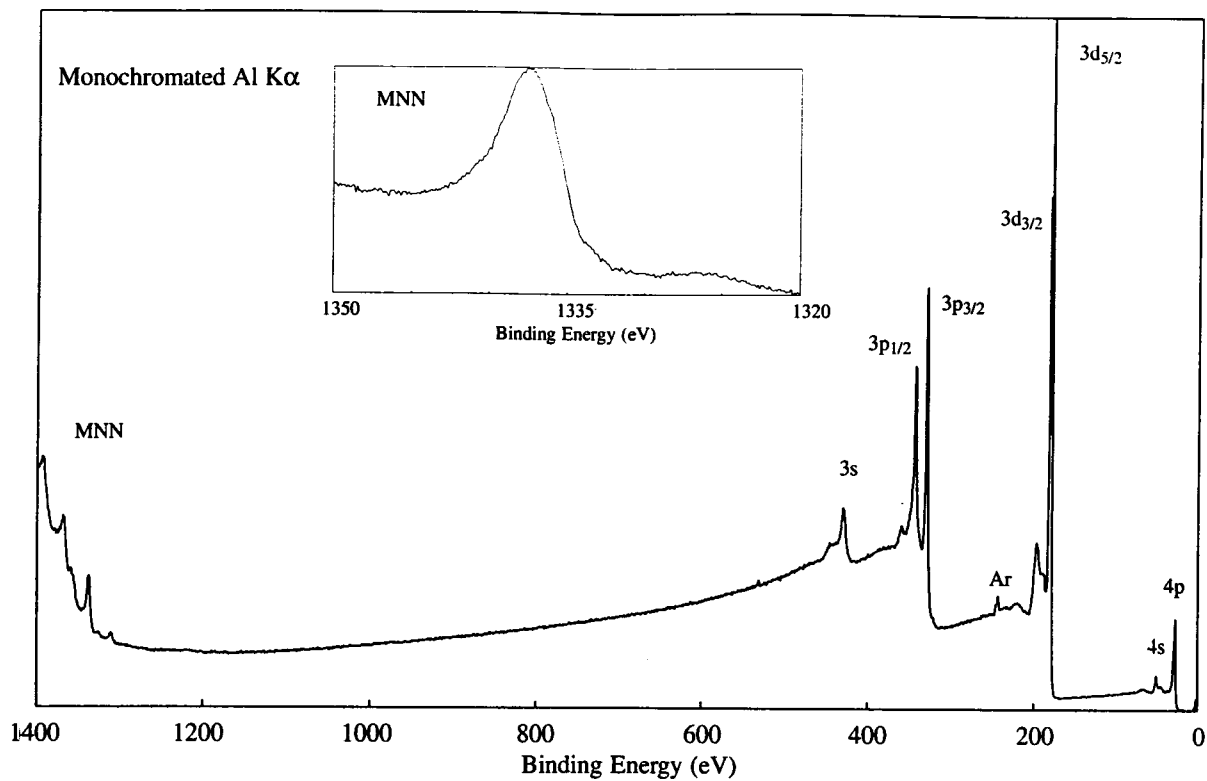


Line Positions (eV)						
Photoelectron Lines						
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p
394	311	299	158	156	45	24
Auger Lines						
M ₄₅ N ₂₃ V						
			1356	(Al)		
			1123	(Mg)		

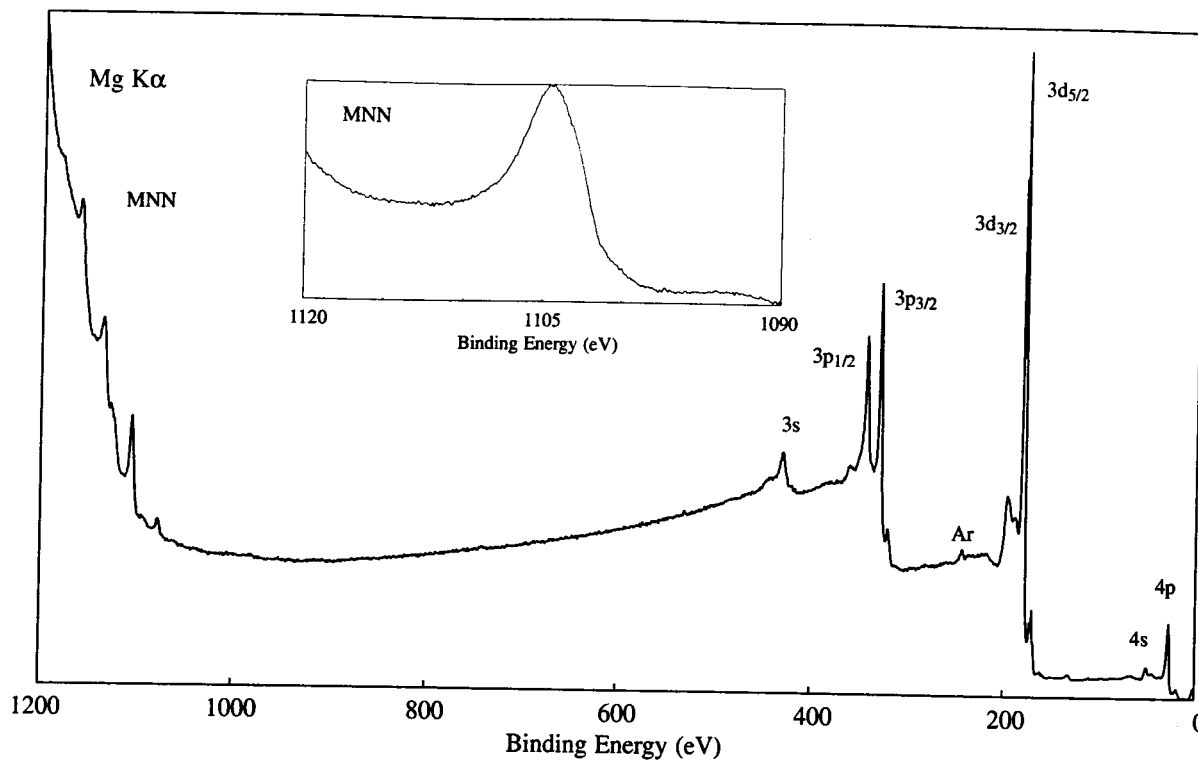


3d _{5/2} Binding Energy (eV)			
Compound Type	155	156	157
Y Y ₂ O ₃			

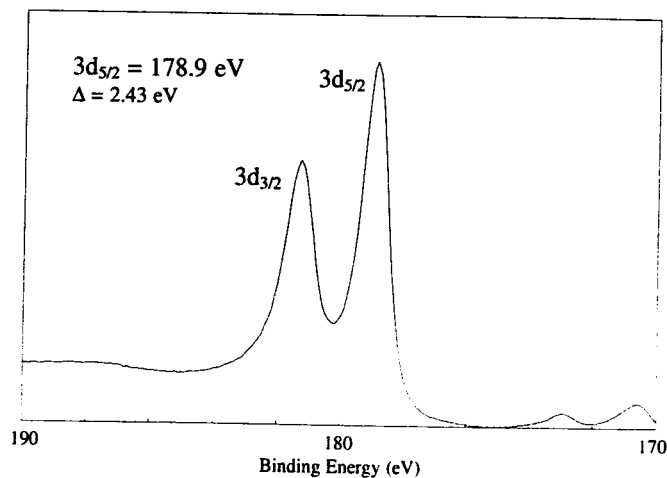


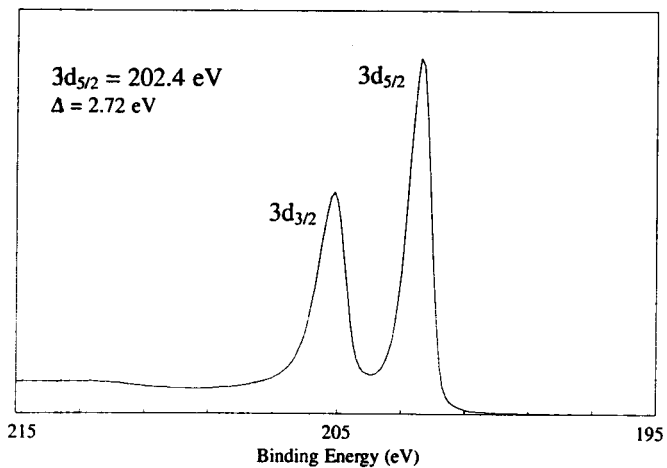
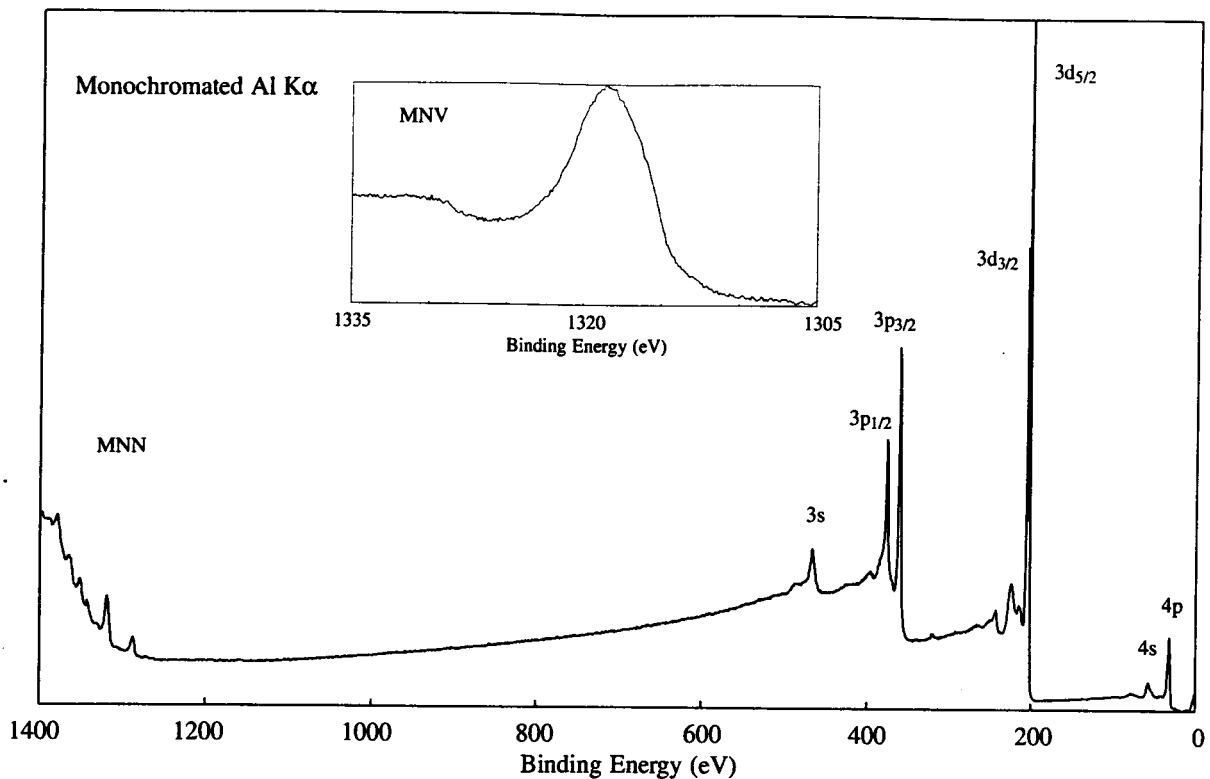


Line Positions (eV)						
Photoelectron Lines						
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p
430	343	330	181	179	51	28
Auger Lines						
M ₄₅ N ₂₃ N ₂₃	M ₄₅ N ₂₃ V	M ₄₅ N ₄₅ N ₄₅				
1393	1368	1337 (Al)				
1160	1135	1104 (Mg)				

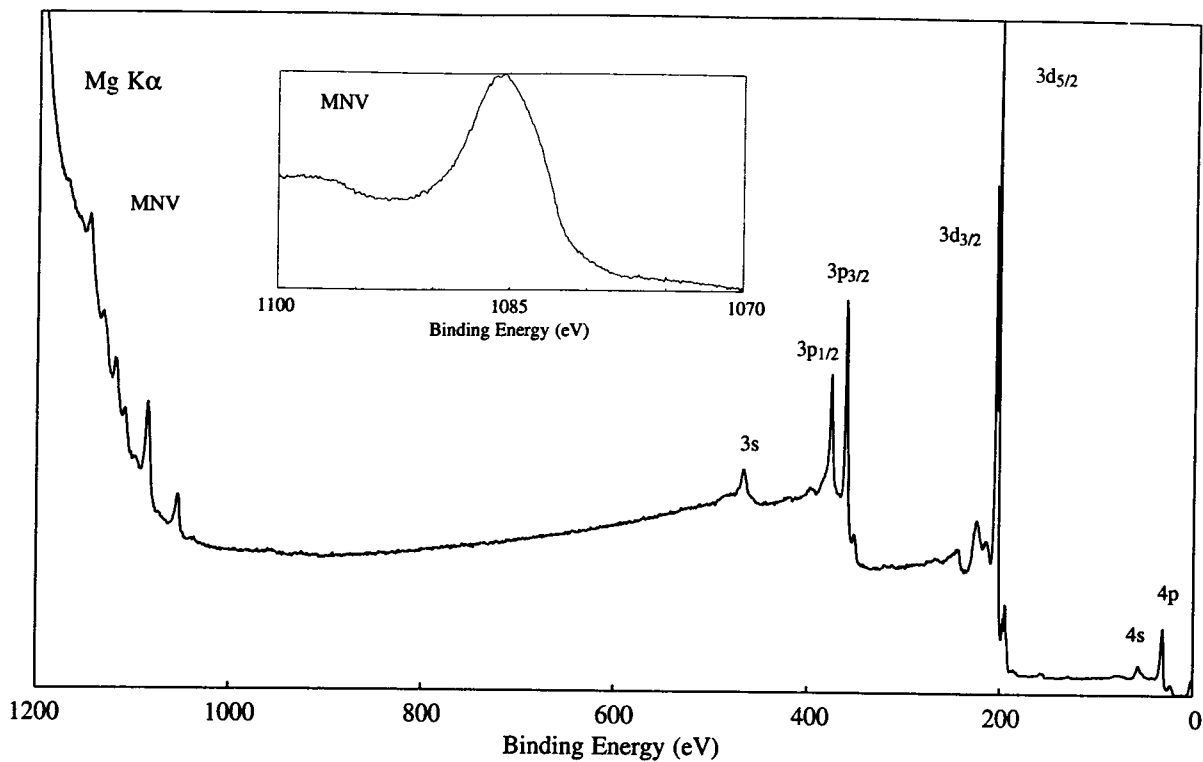


Compound Type	3d _{5/2} Binding Energy (eV)							
	178	179	180	181	182	183	184	185
Zr		■						
ZrO ₂					■			
ZrF ₅								■
K ₂ ZrF ₆							■	■
K ₃ ZrF ₇						■	■	■
KZrF ₅ · H ₂ O							■	■

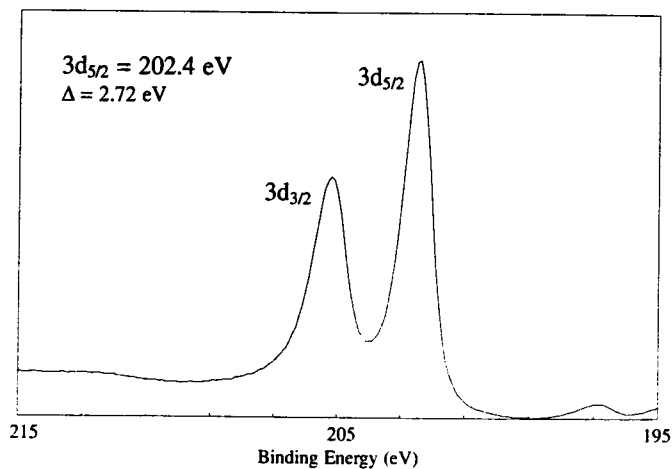


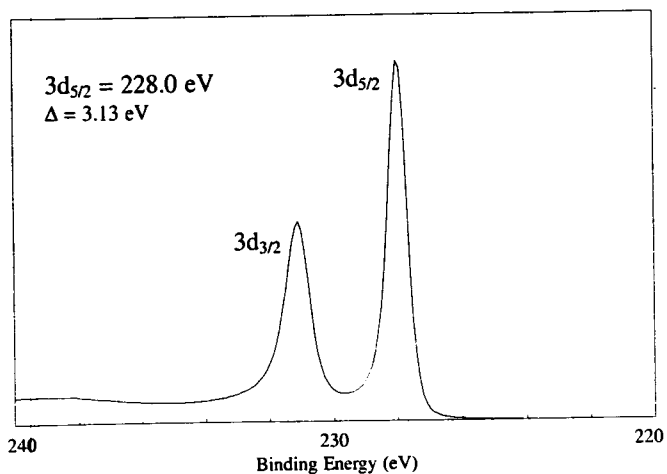
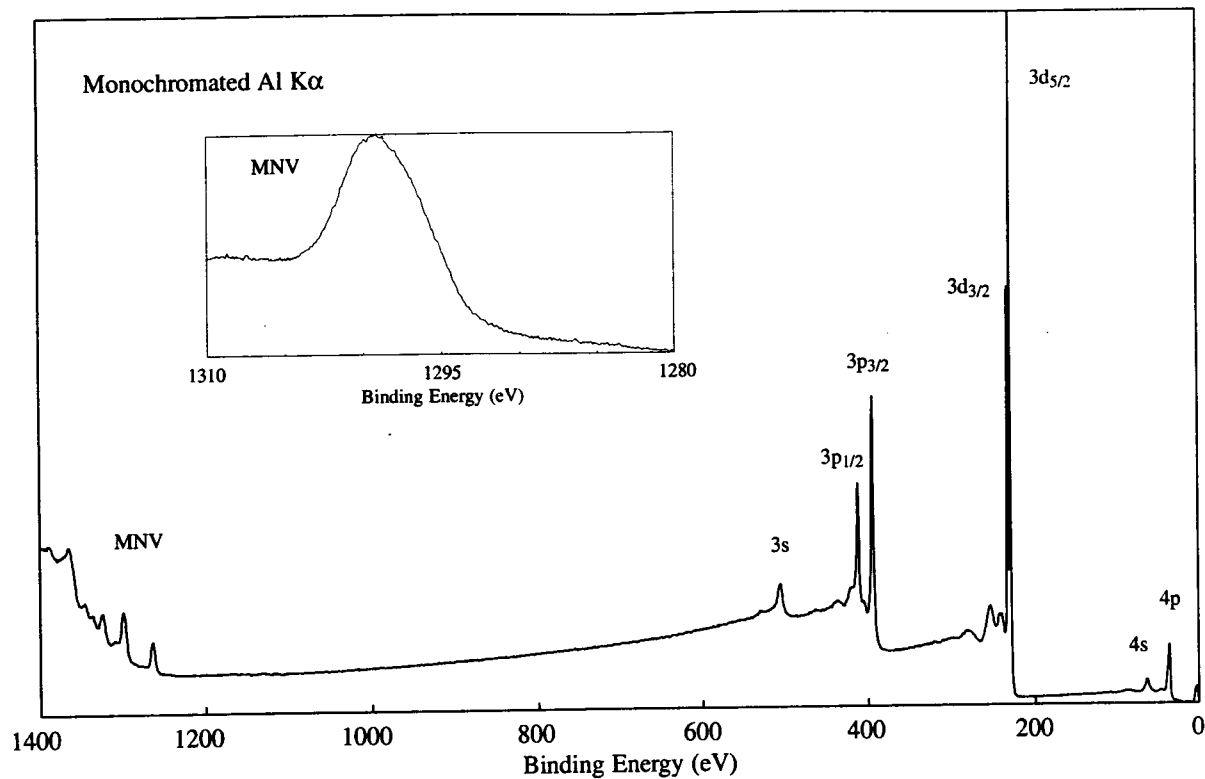


Line Positions (eV)						
<u>Photoelectron Lines</u>						
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p
467	376	361	205	202	56	31
<u>Auger Lines</u>						
M ₄₅ N ₂₃ V		M ₄₅ VV				
1319		1287 (Al)				
1086		1054 (Mg)				



Compound Type	3d _{5/2} Binding Energy (eV)							
	201	202	203	204	205	206	207	208
Nb		■						
NbN				■				
NbO			■	■	■			
Nb ₂ O ₅			■	■	■			
LiNbO ₃								
CaNb ₂ O ₆							■	■
Ca ₂ Nb ₂ O ₇							■	■
Br ₆ (Nb ₆ Cl ₁₂)(Bu ₄ N) ₂					■		■	
Cl ₂ (Nb ₆ Cl ₁₂)(Pr ₃ P) ₄					■		■	
Cl ₂ (Nb ₆ Cl ₁₂)(Me ₂ SO) ₄					■		■	

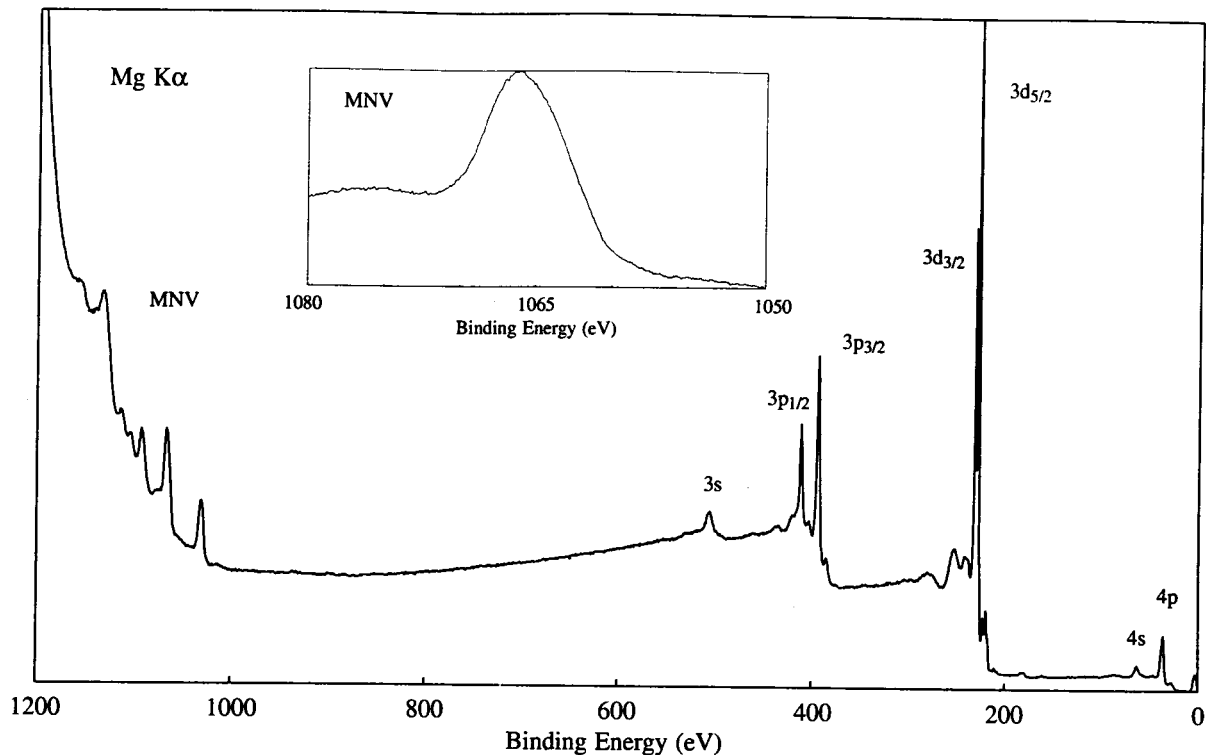




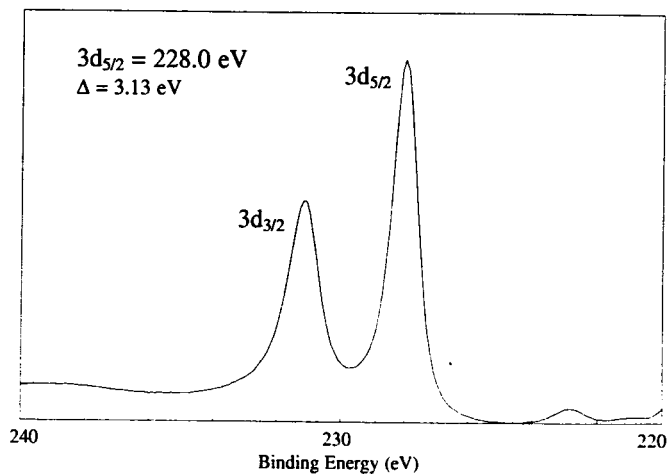
Line Positions (eV)

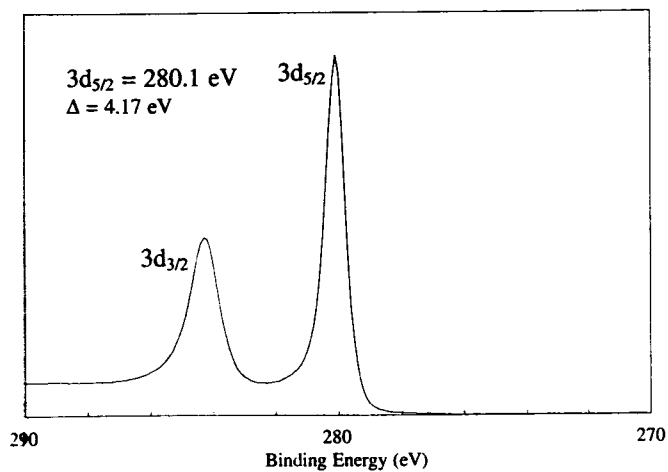
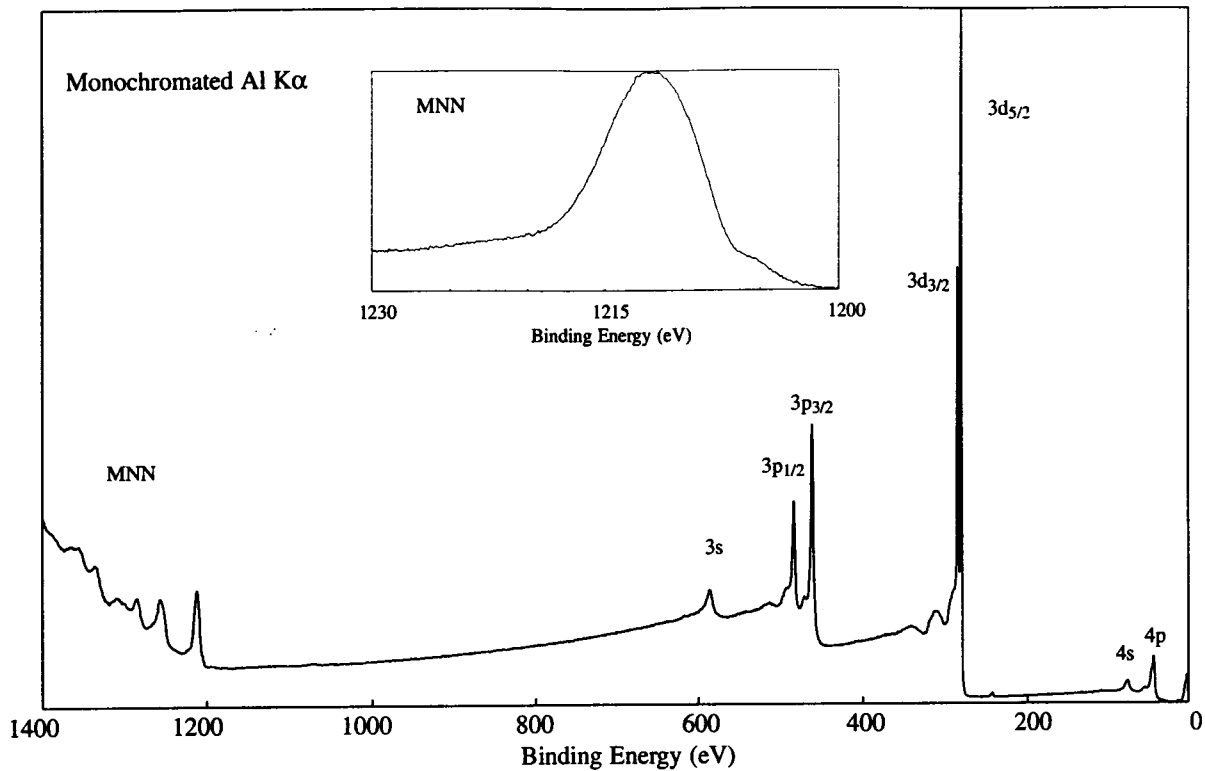
Photoelectron Lines						
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p
506	412	394	231	228	63	36

Auger Lines		
M ₄₅ N ₂₃ V	M ₄₅ VV	
1299	1264	(Al)
1066	1031	(Mg)

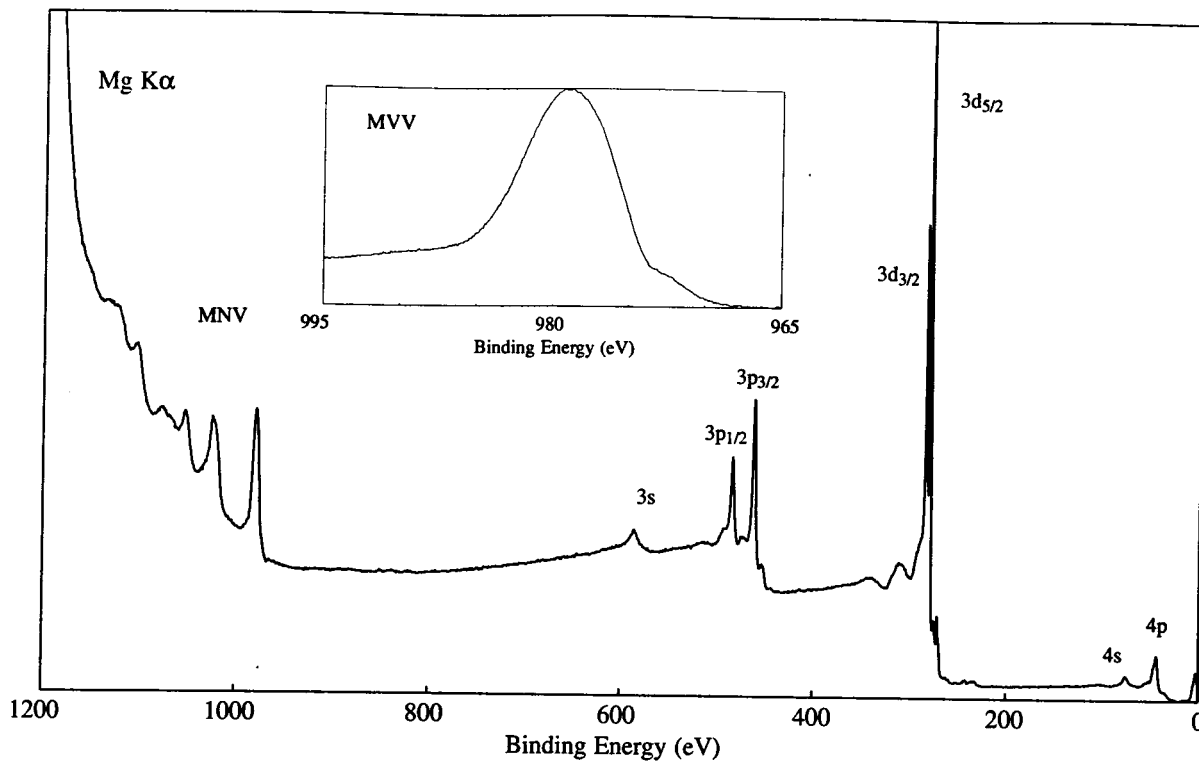


Compound Type	3d _{5/2} Binding Energy (eV)							
	226	227	228	229	230	231	232	233
Mo			■					
Boride		■	■					
Mo ₂ C		■	■					
MoS ₂				■	■			
MoCl ₃					■	■		
MoCl ₄						■	■	
MoCl ₅							■	■
MoO ₂				■				
MoO ₃							■	■
(NH ₄) ₂ MoO ₄							■	■
(CO) _k Mo(Ph ₃ P) _y		■	■					

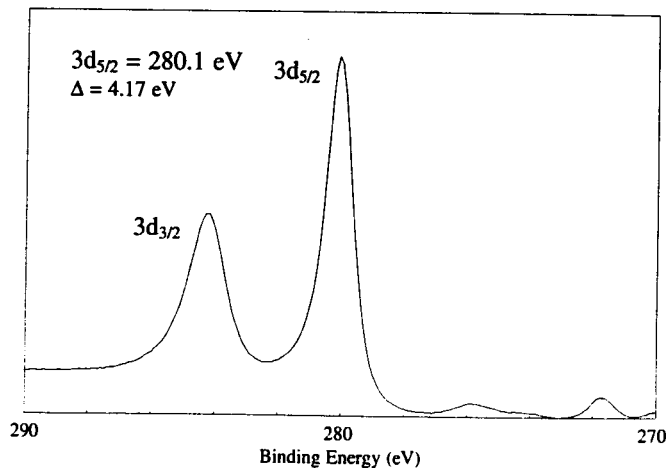


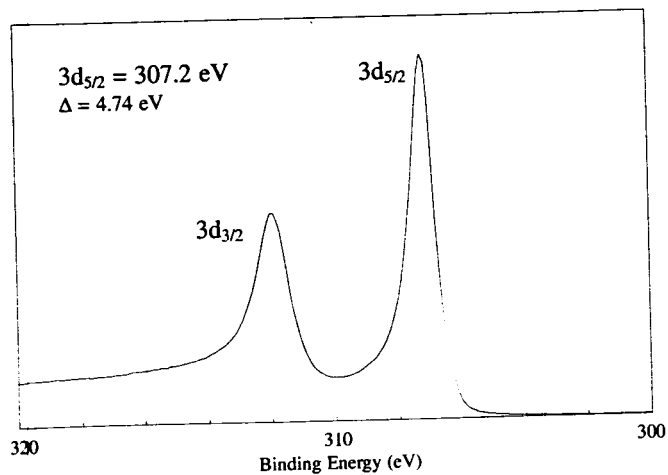
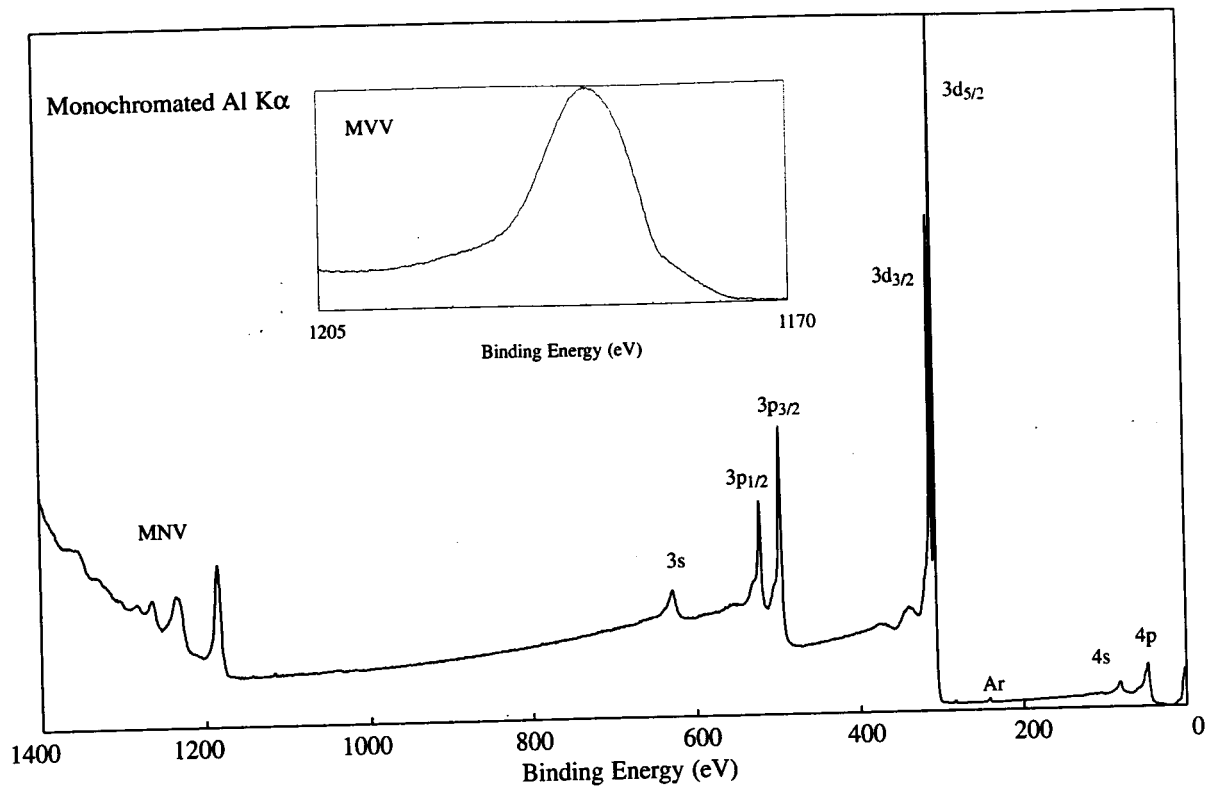


Line Positions (eV)						
Photoelectron Lines						
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p
586	484	462	284	280	75	43
Auger Lines						
M ₄₅ N ₂₃ V		M ₄₅ VV				
1256		1212		(Al)		
1023		979		(Mg)		



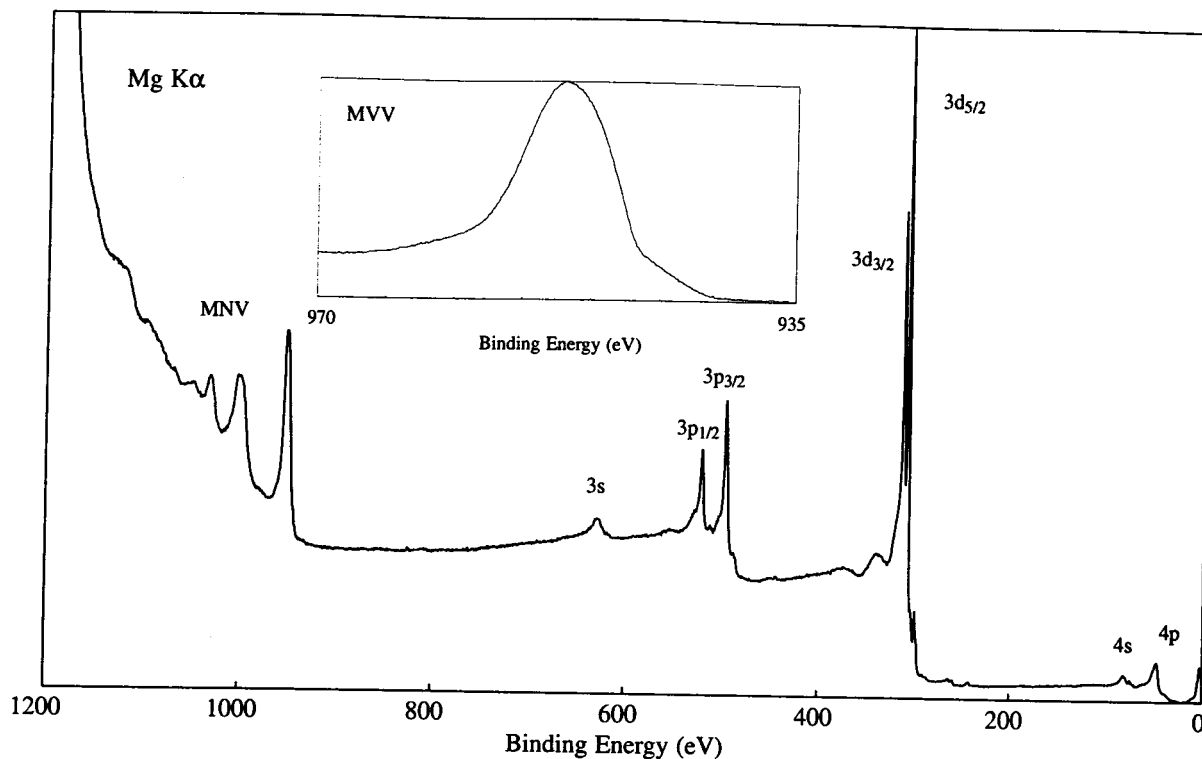
3d _{5/2} Binding Energy (eV)								
Compound Type	276	277	278	279	280	281	282	283
Ru					■			
RuCl ₃							■	
RuO ₂						■		
RuO ₃							■	
RuO ₄								■
Ru(NH ₃) ₅ N ₂ I ₂							■	■
Ru(NH ₃) ₅ N ₂ Br ₂					■			
Ru(NH ₃) ₅ N ₂ Cl ₂							■	■



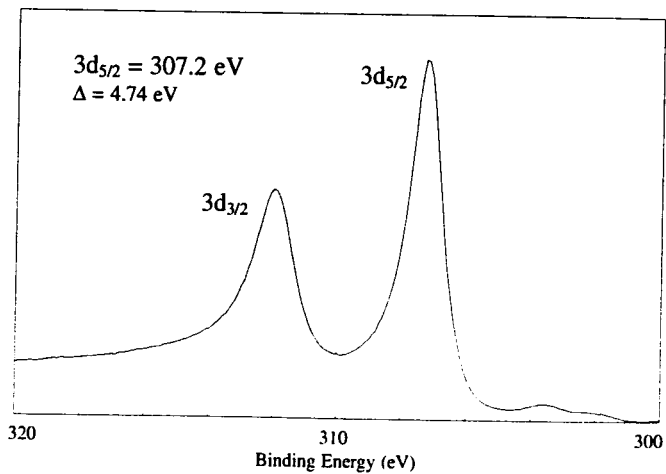


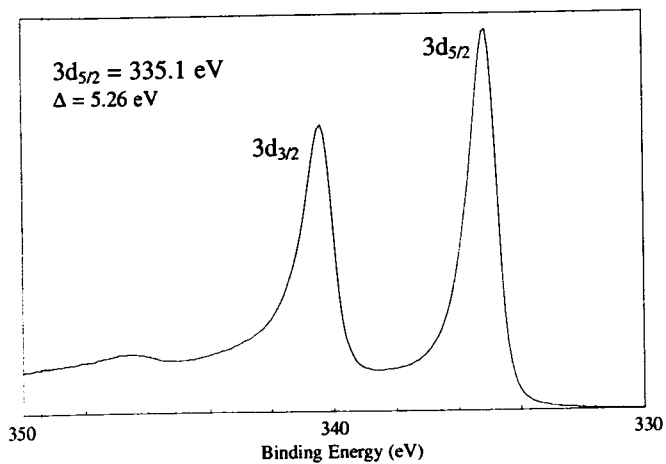
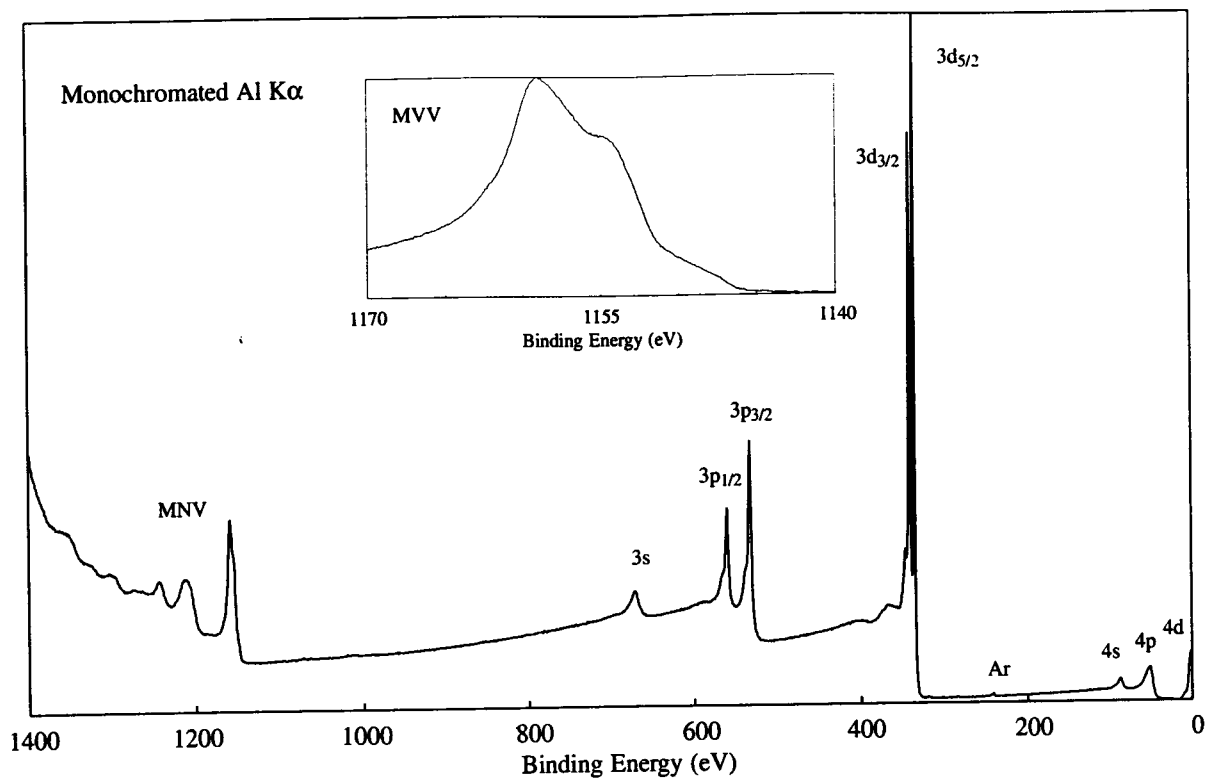
Line Positions (eV)

Photoelectron Lines						
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p
629	521	497	312	307	81	48
Auger Lines						
M ₄₅ N ₂₃ V		M ₄₅ VV				
1234		1185 (Al)				
1001		952 (Mg)				

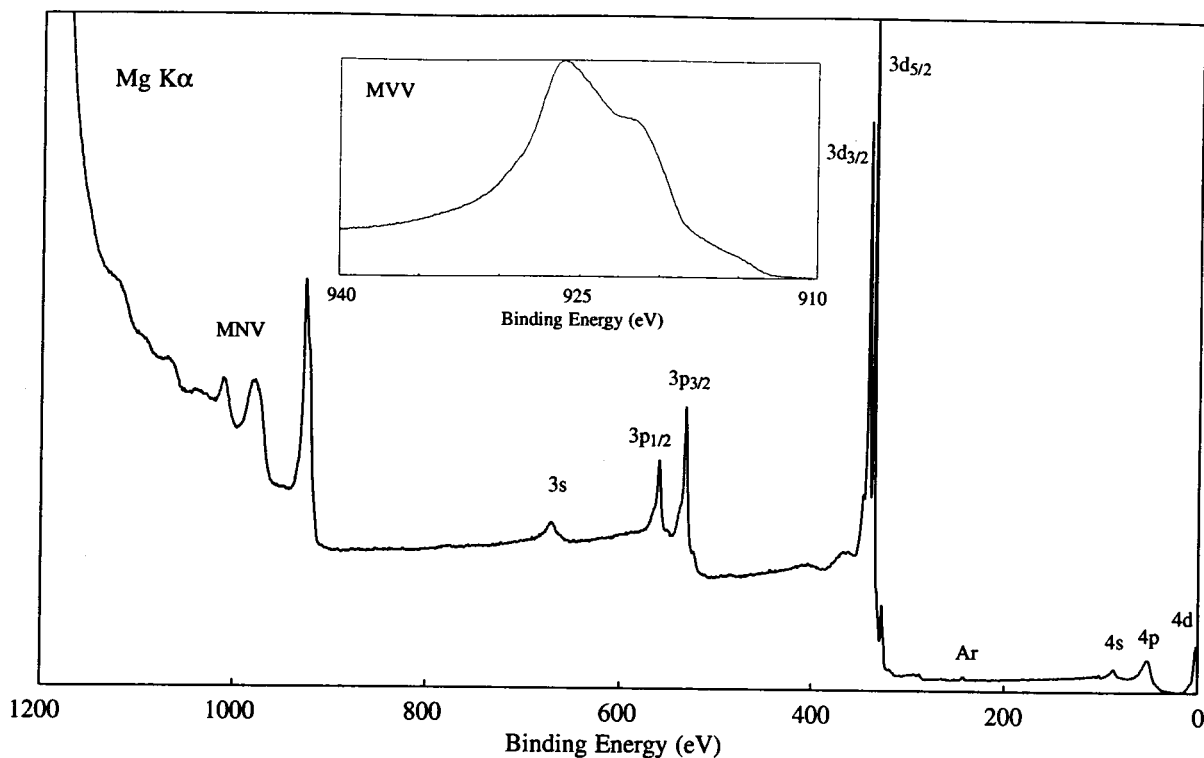


Compound Type	3d _{5/2} Binding Energy (eV)				
	307	308	309	310	311
Rh					
Halides					
Rh ₂ O ₃					
ClRh(Ph ₃ P) ₃					
Cl ₃ Rh(Ph ₃ P) ₃					
Cl ₆ Rh(Ph ₃ P) ₃					
Br ₆ Rh(Ph ₃ P) ₃					
Cl ₂ Rh ₂ (cyclooctadiene) ₂					
Rh ₂ (OAc) ₄ · 2H ₂ O					
Rh(NH ₂ CH ₂ COO) ₃ · H ₂ O					

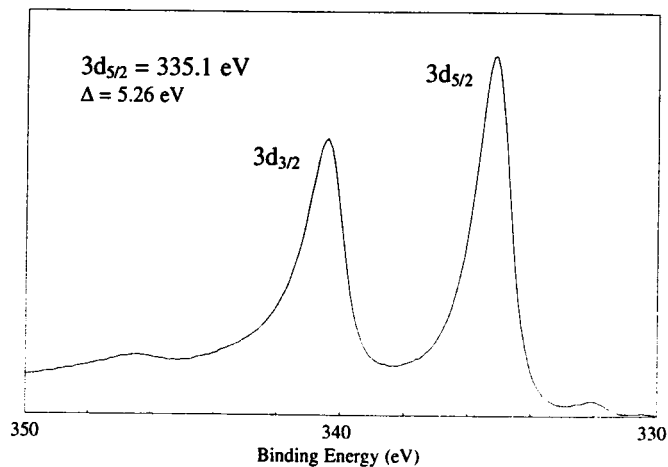


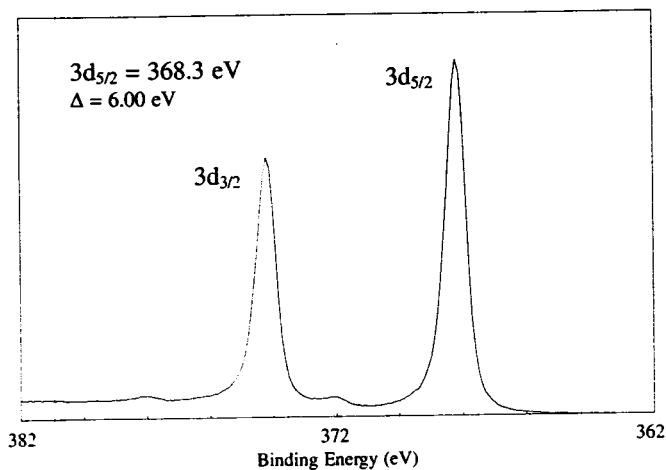
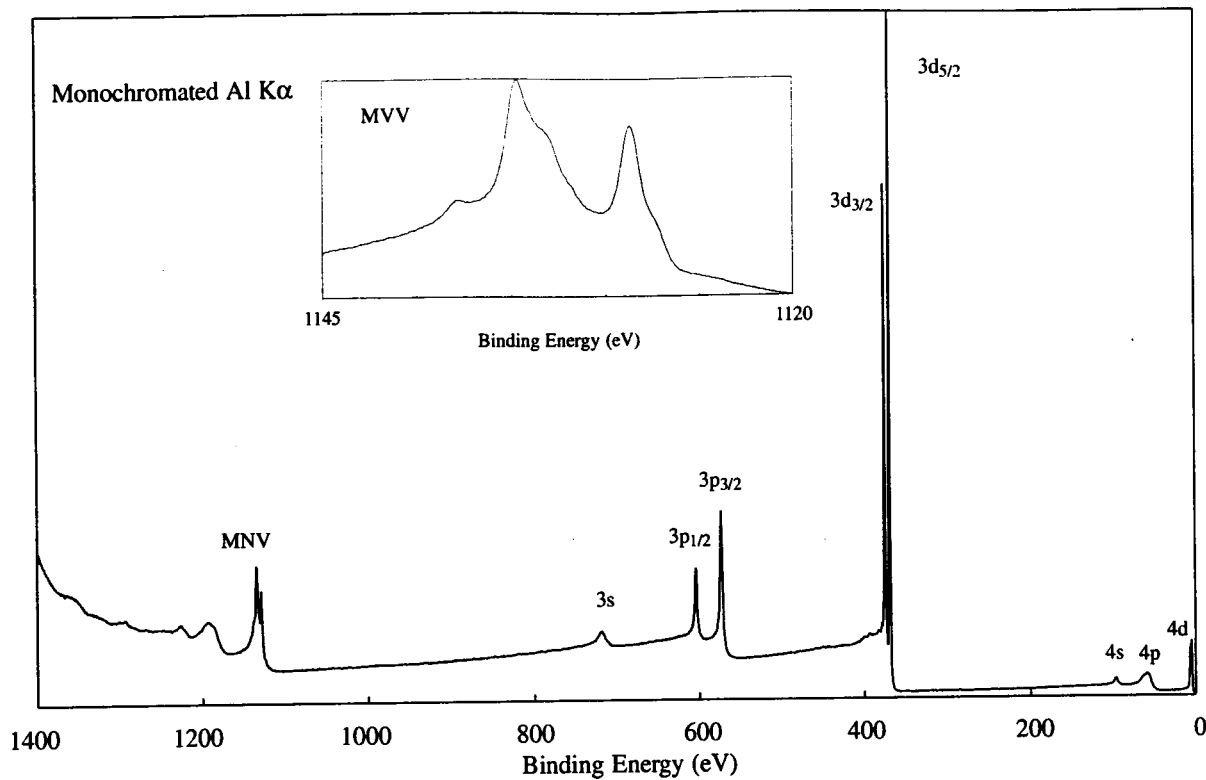


Line Positions (eV)						
<u>Photoelectron Lines</u>						
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p
671	560	533	340	335	88	52
<u>Auger Lines</u>						
M ₄₅ N ₂₃ V		M ₄₅ VV				
1211		1159		(Al)		
978		926		(Mg)		

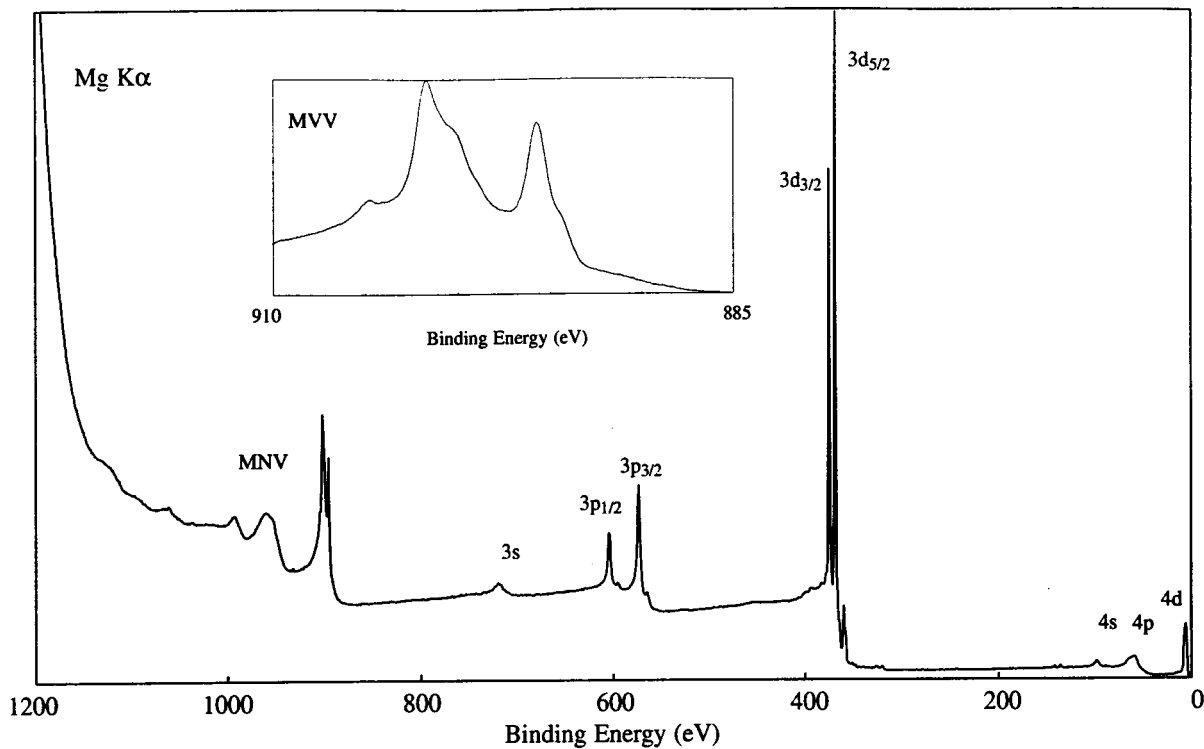


Compound Type	3d _{5/2} Binding Energy (eV)						
	335	336	337	338	339	340	341
Pd	■						
Pd ₂ Si		■	■				
Pd ₃ Si		■	■				
Halides		■	■	■			
PdO		■	■				
PdO ₂				■			
K ₂ PdCl ₄				■			
K ₂ PdBr ₄			■	■			
K ₂ PdCl ₆						■	
Pd(OAc) ₂					■		
Pd(SPh) ₂			■				

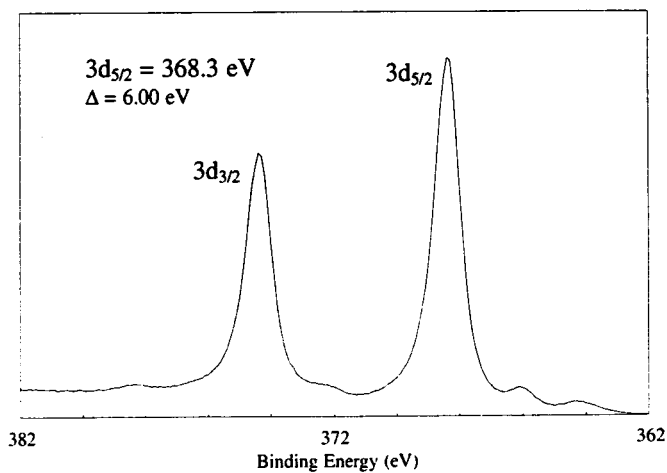


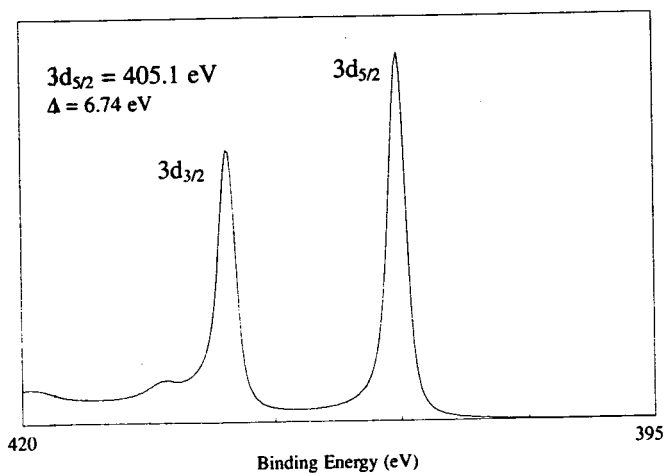
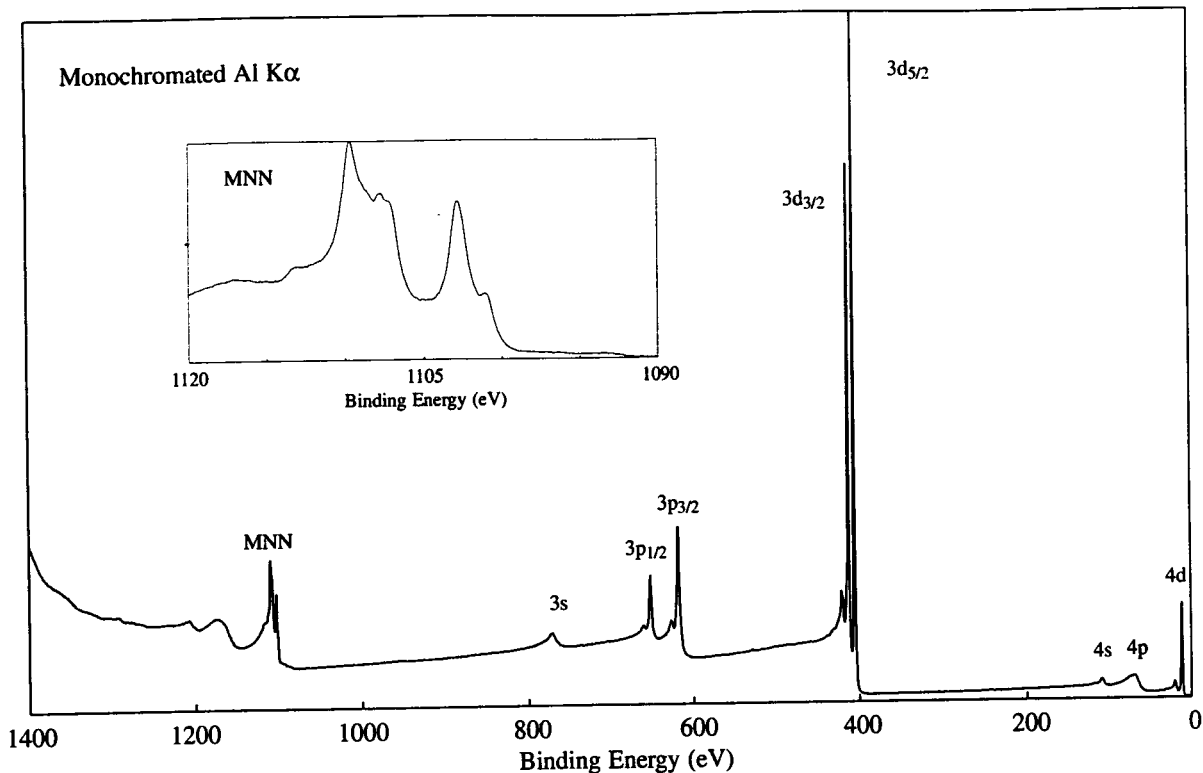


Line Positions (eV)						
<u>Photoelectron Lines</u>						
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p
719	604	573	374	368	98	60
<u>Auger Lines</u>						
M ₄₅ N ₂₃ V	M ₅ VV	M ₄ VV				
1191	1135	1129	(Al)			
958	902	896	(Mg)			



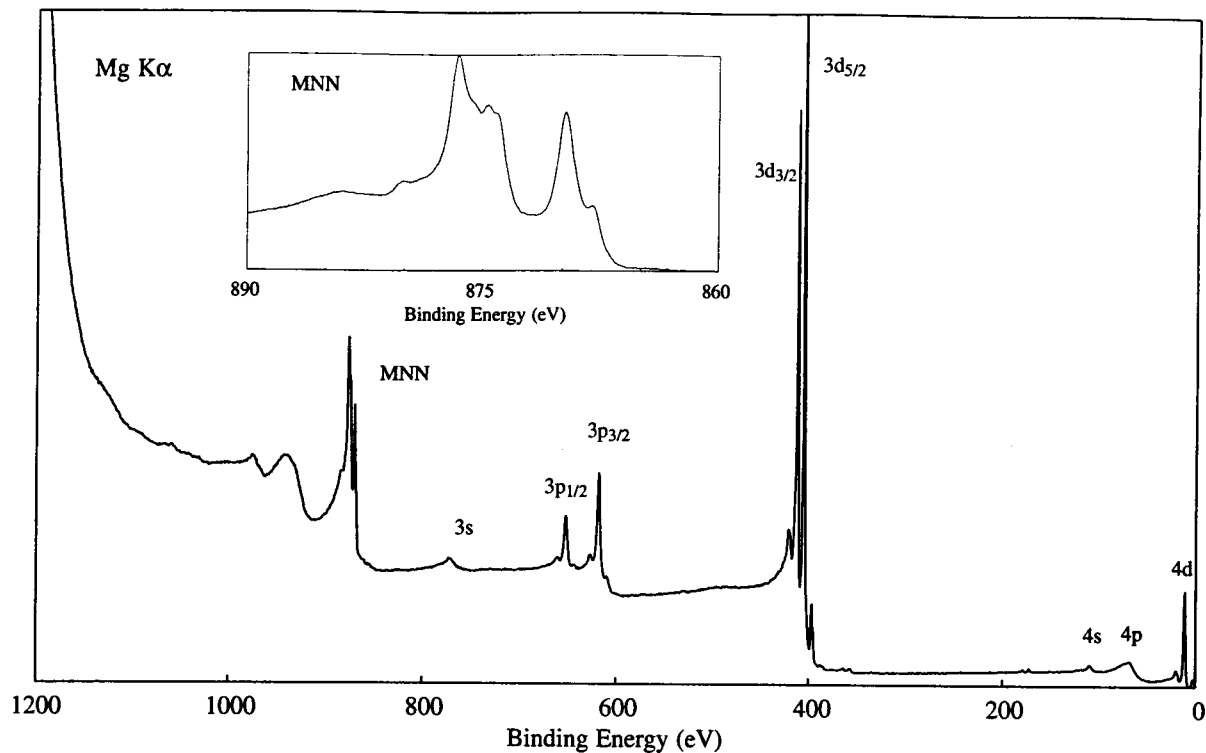
Compound Type	3d _{5/2} Binding Energy (eV)		
	367	368	369
Ag			
Alloys			
Ag ₂ S			
AgI			
AgF			
AgF ₂			
Oxides			
Ag ₂ CO ₃			
Sulfate			
AgOCCF ₃			
Ag(OAc)			



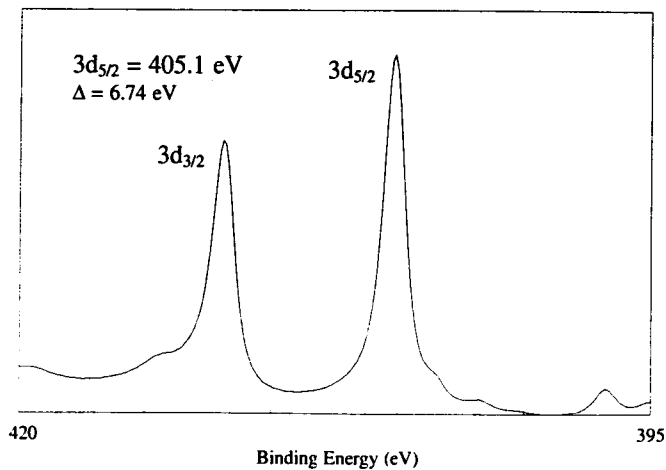


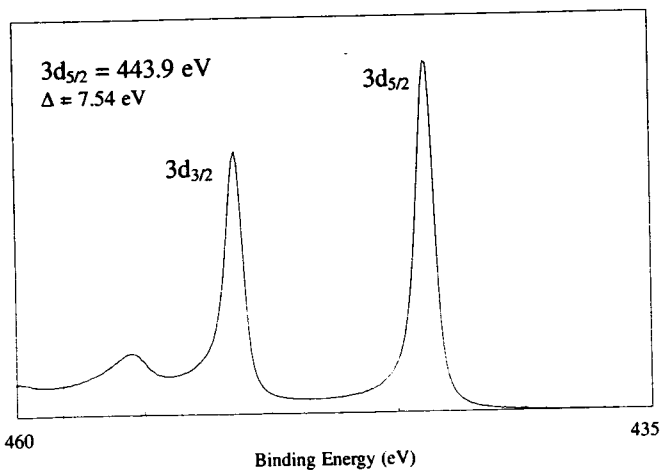
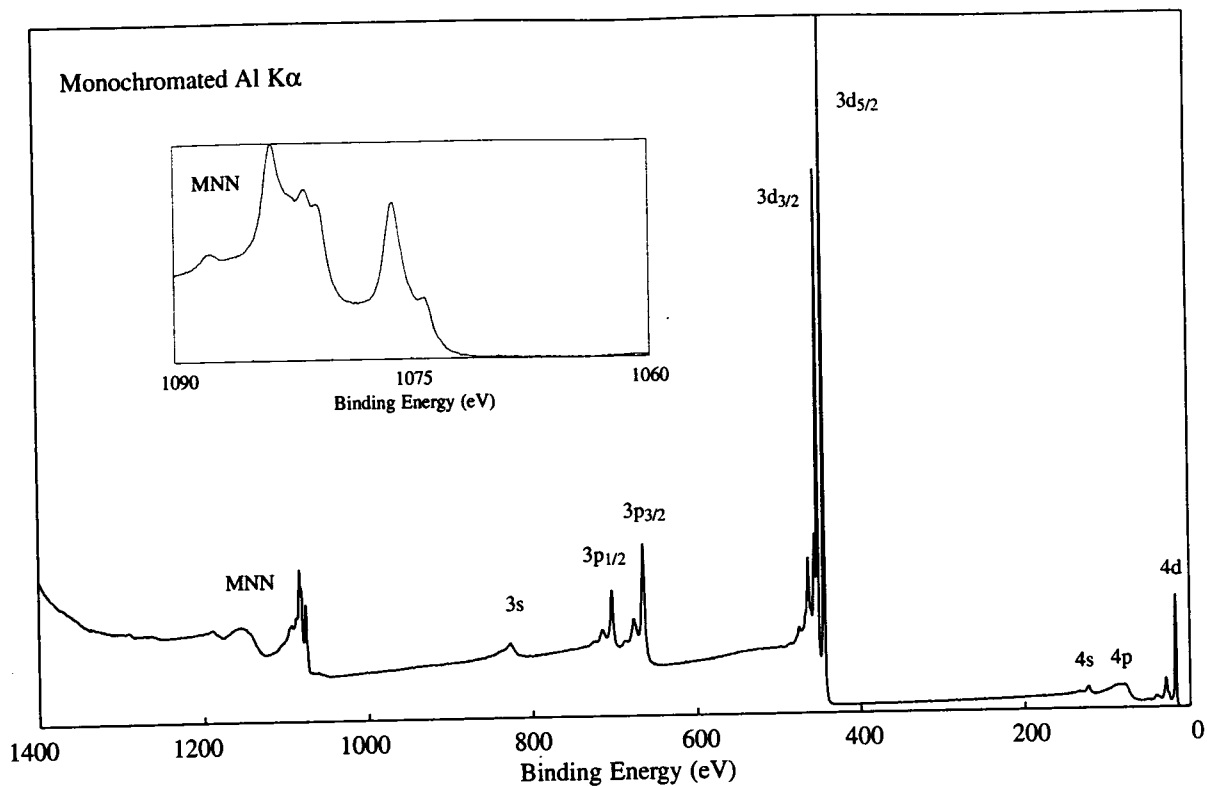
Line Positions (eV)

Photoelectron Lines							
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p	4d
772	652	618	412	405	110	69	11
Auger Lines							
M ₅ N ₄₅ N ₄₅		M ₄ N ₄₅ N ₄₅					
1110		1103 (Al)					
877		870 (Mg)					



Compound Type	3d _{5/2} Binding Energy (eV)			
	404	405	406	407
Cd		██████████		
Hg _{0.8} Cd _{0.2} Te		██████████		
CdTe		██████████		
CdSe		██████████		
CdS		██████████		
Halides			██████████	
CdO		██████████		
CdO ₂	██████████			
Cd(OH) ₂		██████████		
CdCO ₃		██████████		

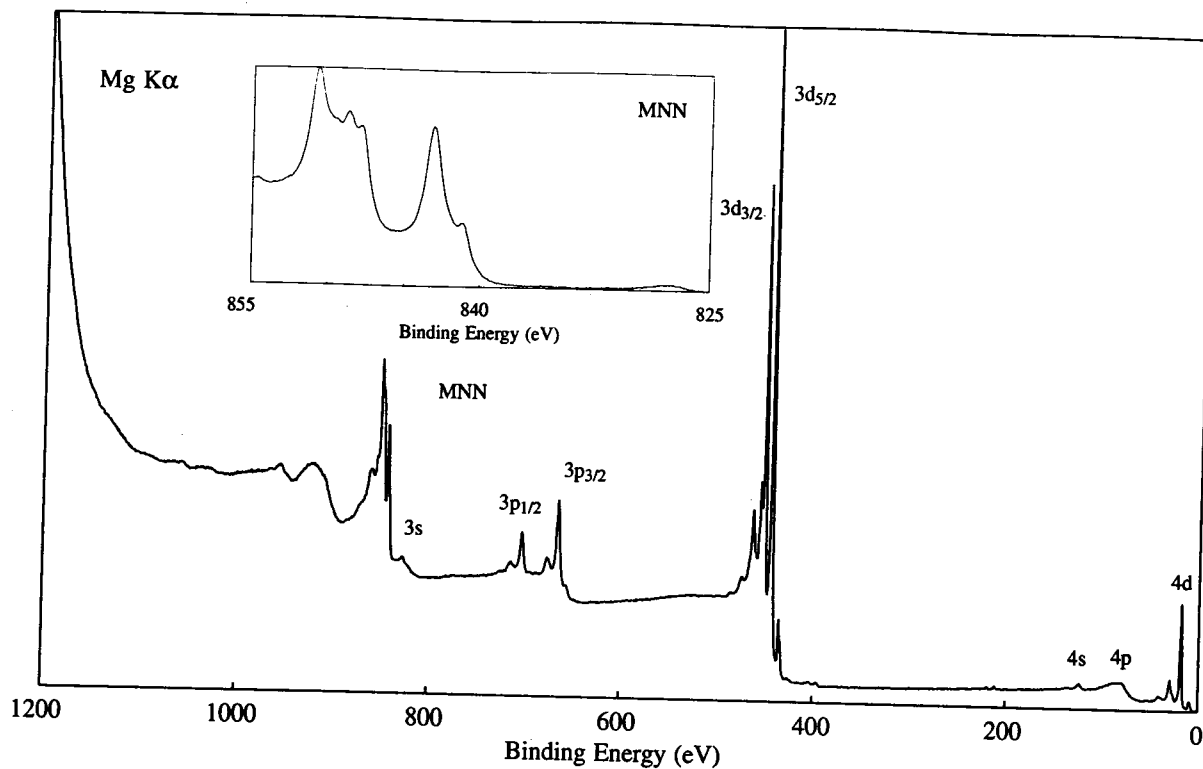




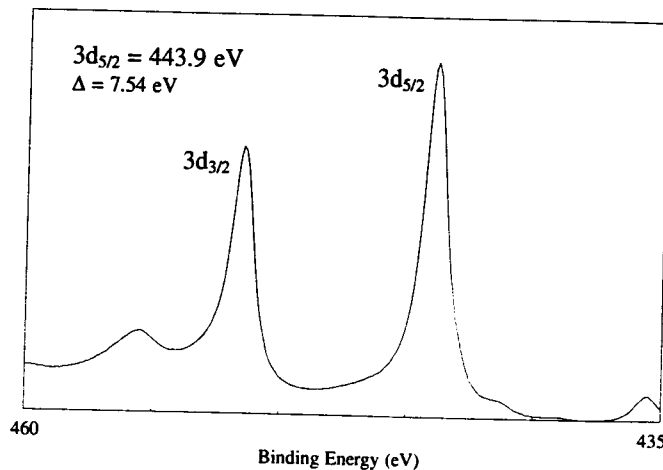
Line Positions (eV)

Photoelectron Lines							
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p	4d
828	703	665	452	444	123	78	17

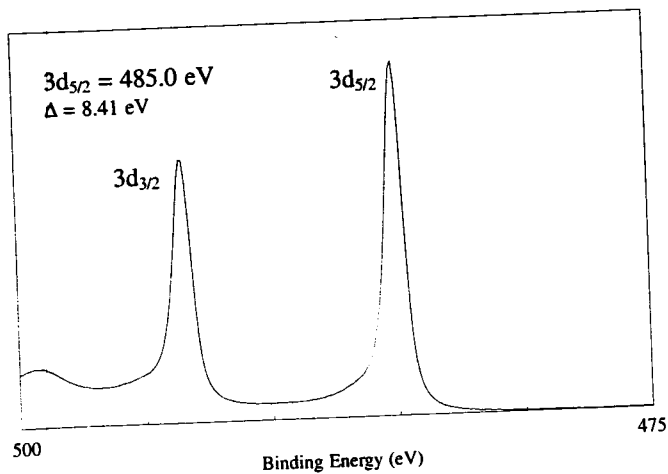
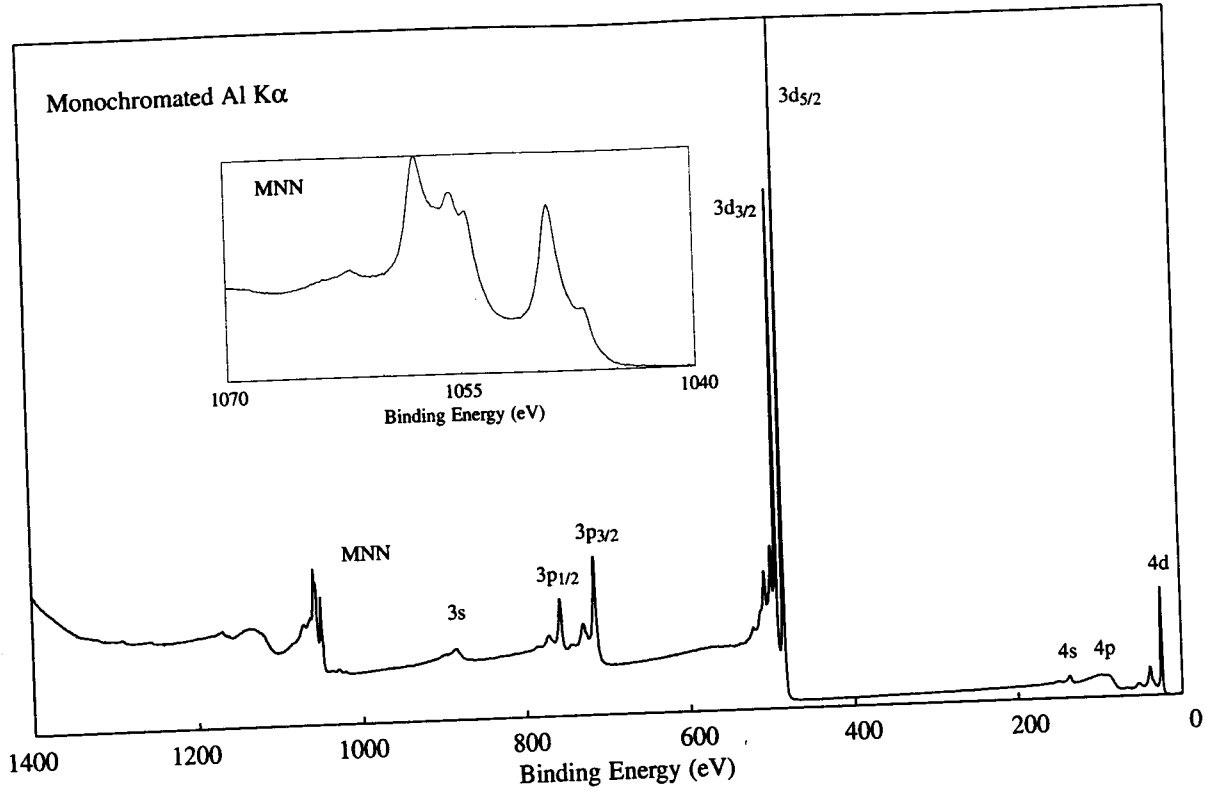
Auger Lines		
M ₅ N ₄₅ N ₄₅	M ₄ N ₄₅ N ₄₅	
1084	1076 (Al)	
851	843 (Mg)	



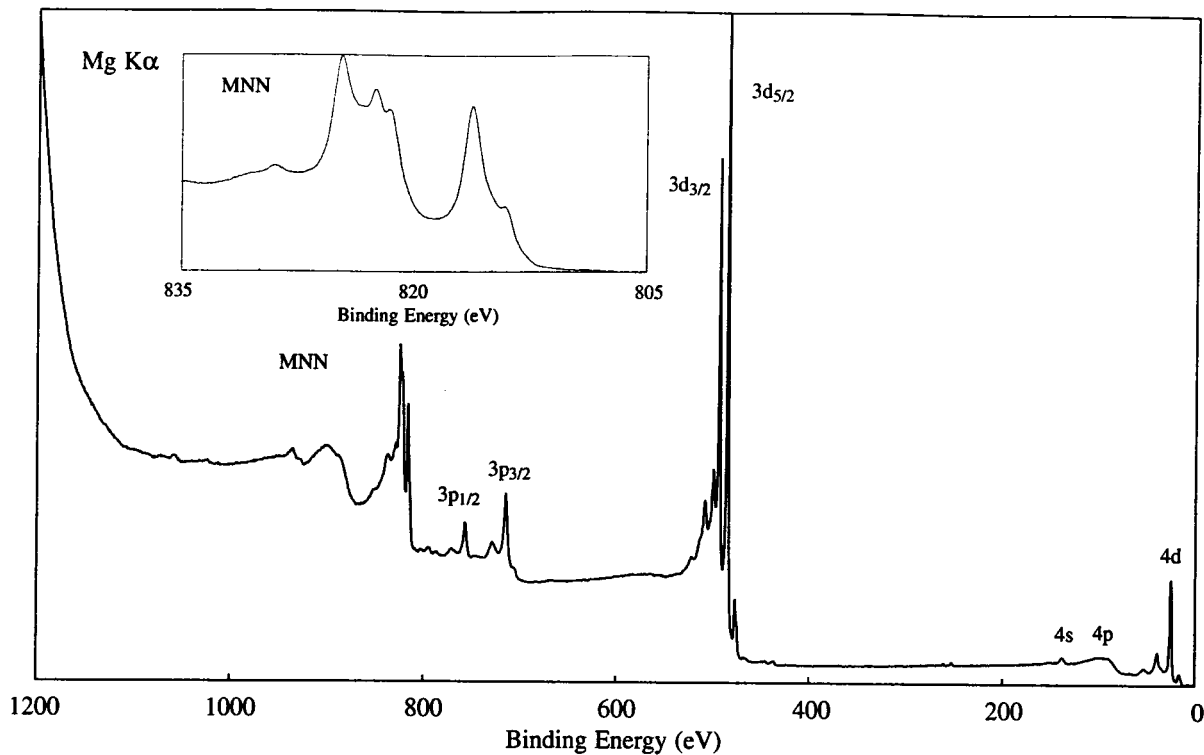
Compound Type	3d _{5/2} Binding Energy (eV)				
	443	444	445	446	447
In		■			
InSb		■			
InP			■		
In ₂ Te ₃			■		
InCl ₃				■	
InCl			■		
In ₂ O ₃		■			
In(OH) ₃			■		
In(acac) ₃			■		
Br ₂ InEt ₄ N				■	
Br ₂ InPr ₄ N				■	



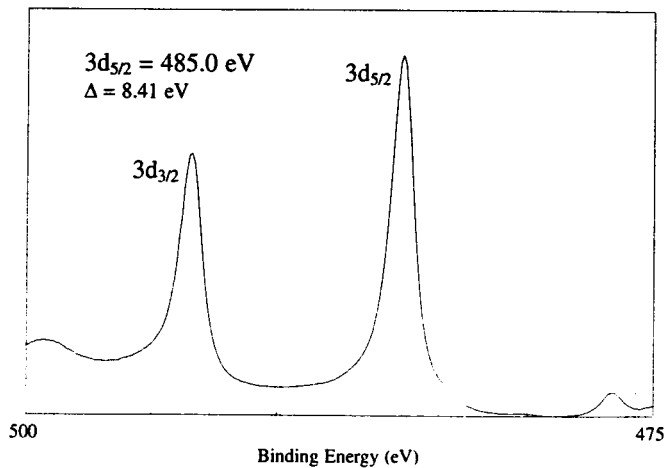
Tin **Sn**
 Atomic Number 50

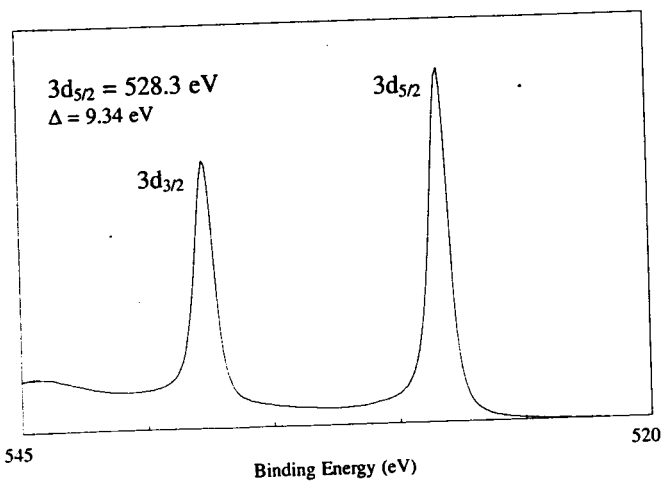
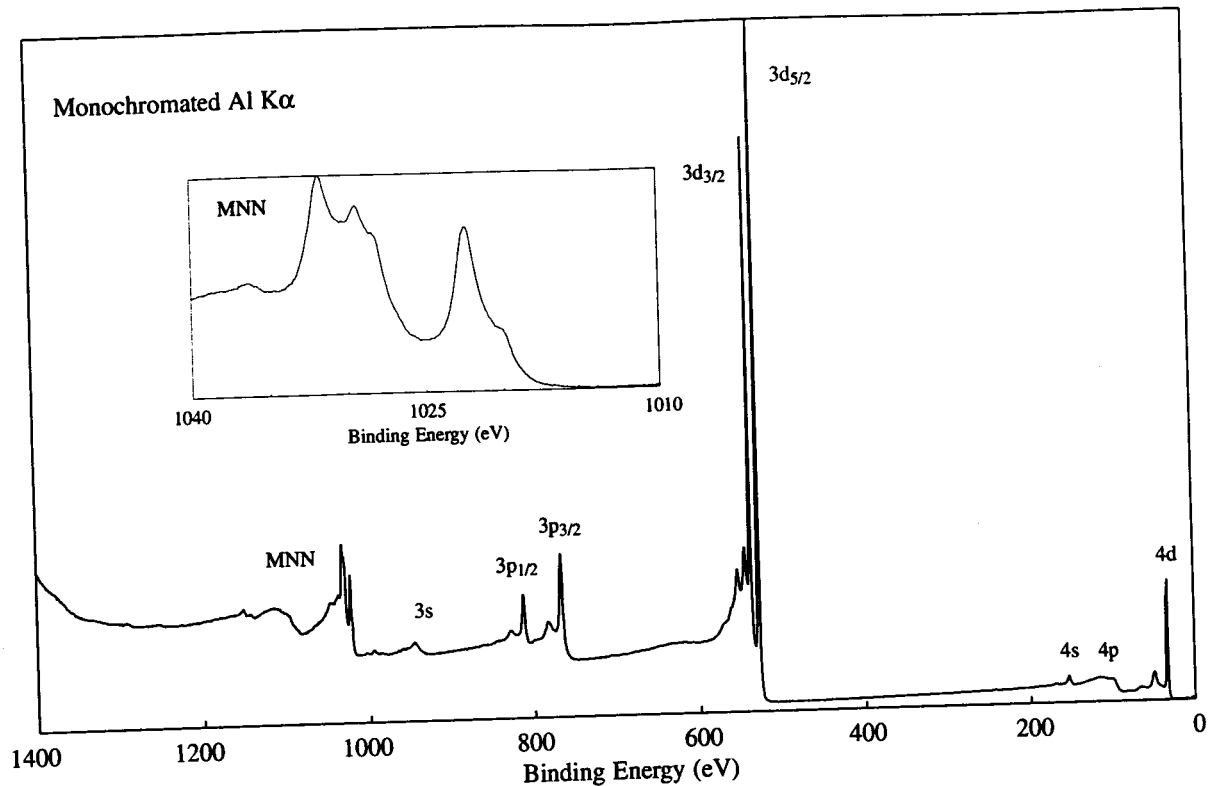


Line Positions (eV)							
<u>Photoelectron Lines</u>							
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p	4d
885	757	715	493	485	137	89	25
<u>Auger Lines</u>							
M ₅ N ₄₅ N ₄₅		M ₄ N ₄₅ N ₄₅					
1058		1049 (Al)					
825		816 (Mg)					

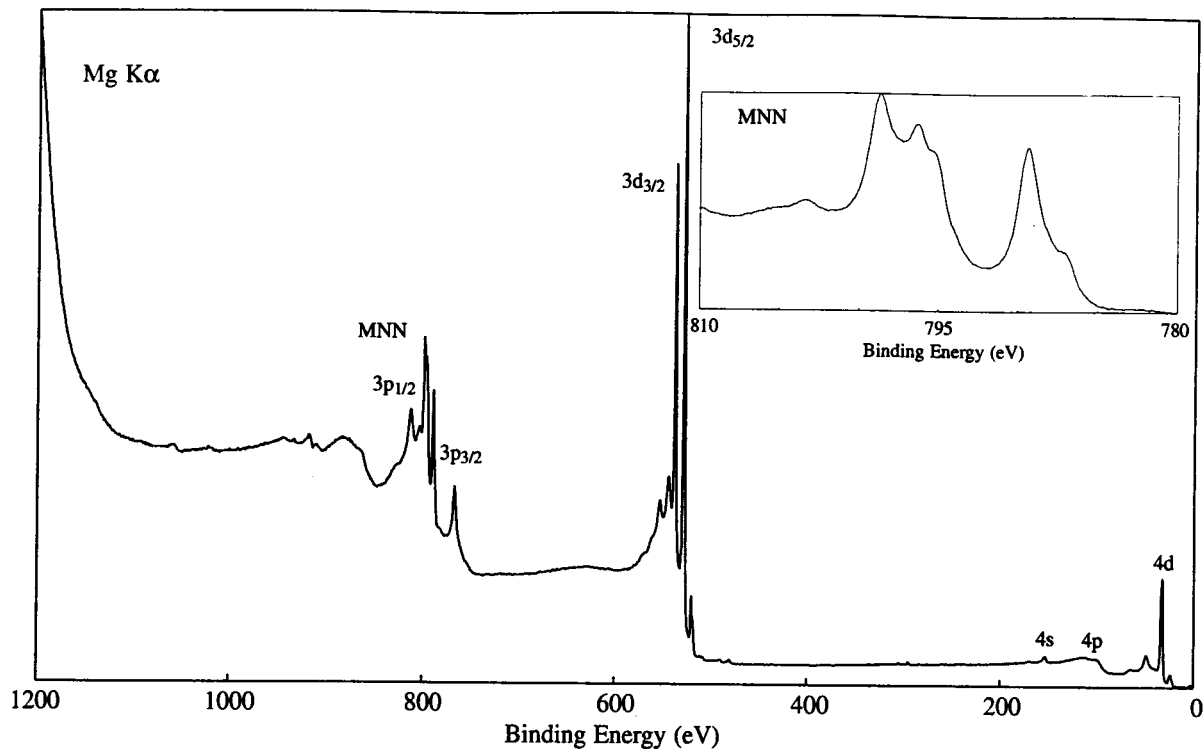


Compound Type	3d _{5/2} Binding Energy (eV)				
	484	485	486	487	488
Sn		■			
SnS			■		
Halides				■	
SnO			■	■	
SnO ₂				■	
Na ₂ SnO ₃				■	
Ph ₄ Sn		■	■	■	
Ph ₃ Sn (Halide)		■	■	■	
Me ₃ SnF				■	
Me ₂ SnF ₂				■	
Br ₆ Sn(Et ₄ N) ₂				■	

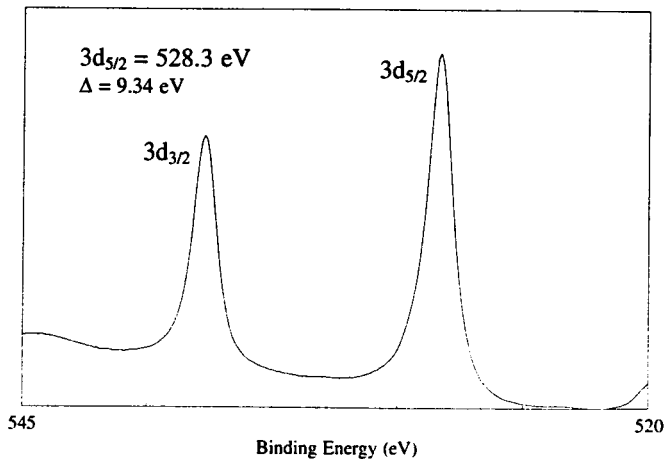


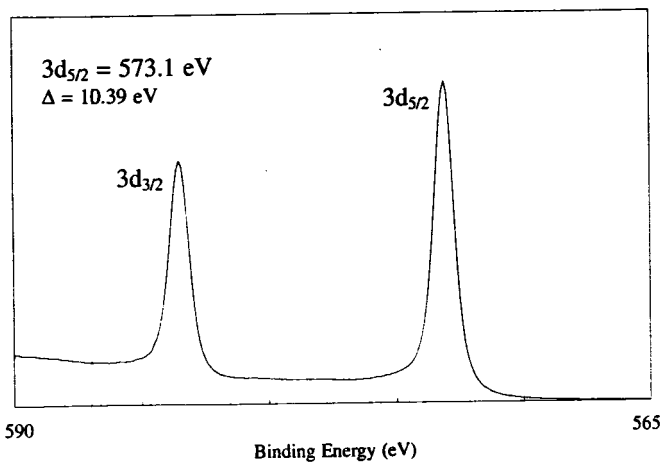
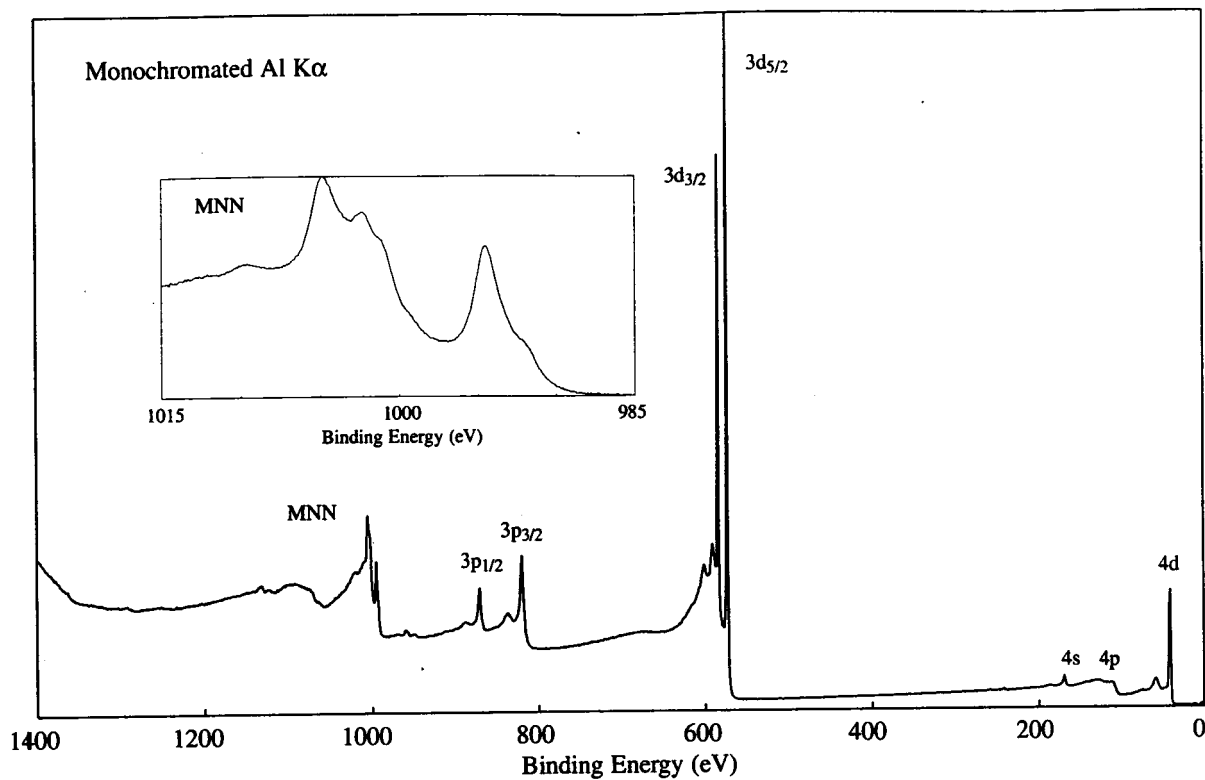


Line Positions (eV)							
<u>Photoelectron Lines</u>							
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	4s	4p	4d
944	813	767	537	528	153	99	33
<u>Auger Lines</u>							
M ₅ N ₄₅ N ₄₅		M ₄ N ₄₅ N ₄₅					
1032		1022 (Al)					
799		789 (Mg)					

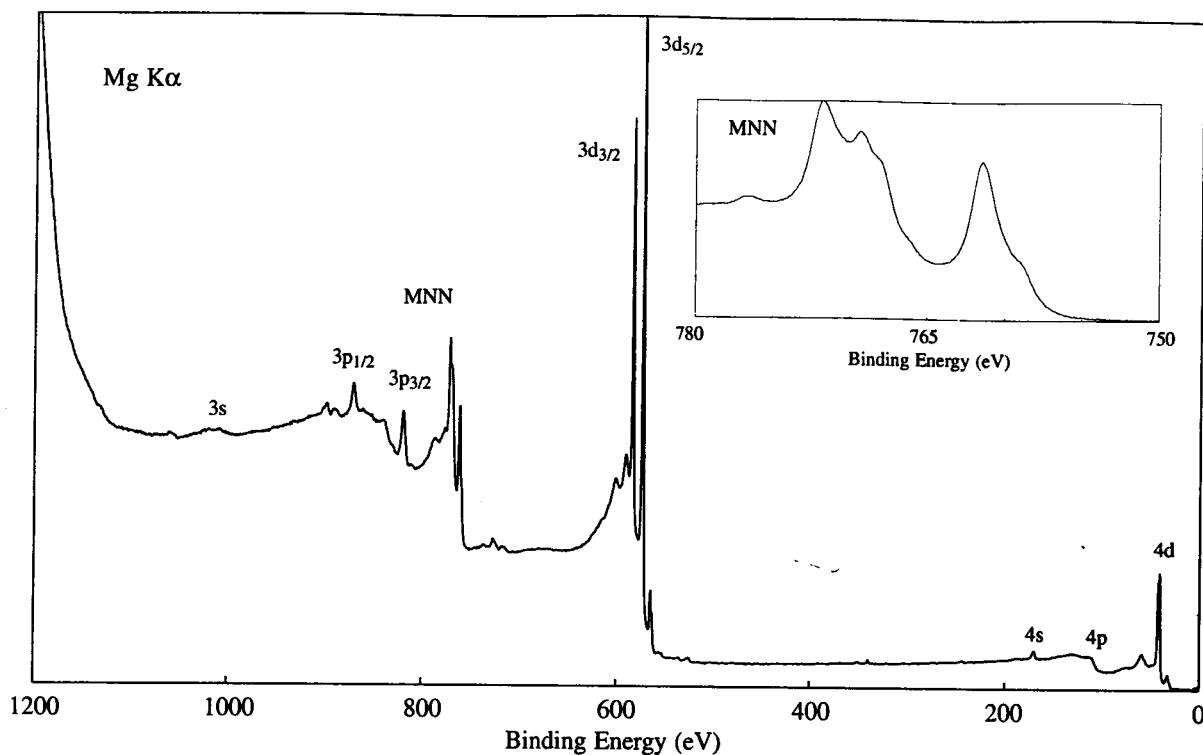


Compound Type	3d _{5/2} Binding Energy (eV)					
	528	529	530	531	532	533
Sb	■					
AlSb		■				
Sulfides			■			
Halides				■	■	
Sb ₂ O ₃			■			
Sb ₂ O ₅				■		
KSbF ₆						■
NaSbF ₆					■	
CsSbF ₄				■		
Ph ₃ Sb		■				
Bu ₃ Sb	■					

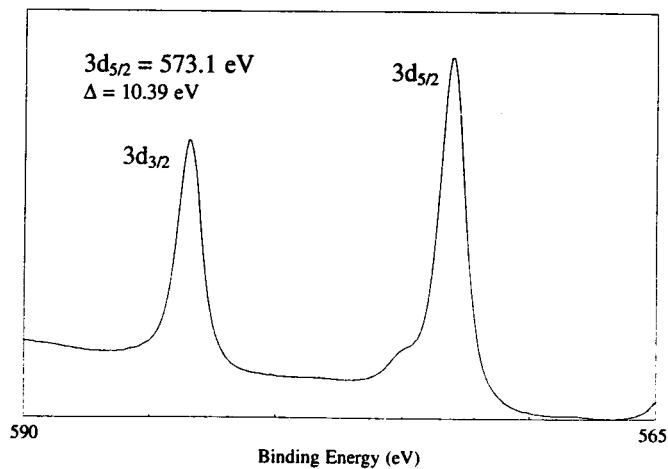


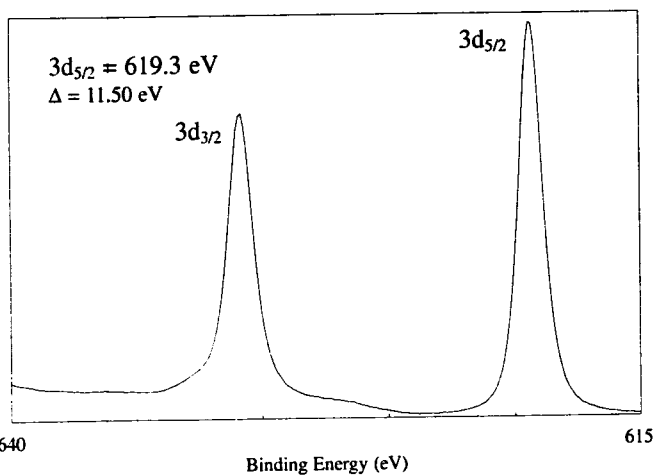
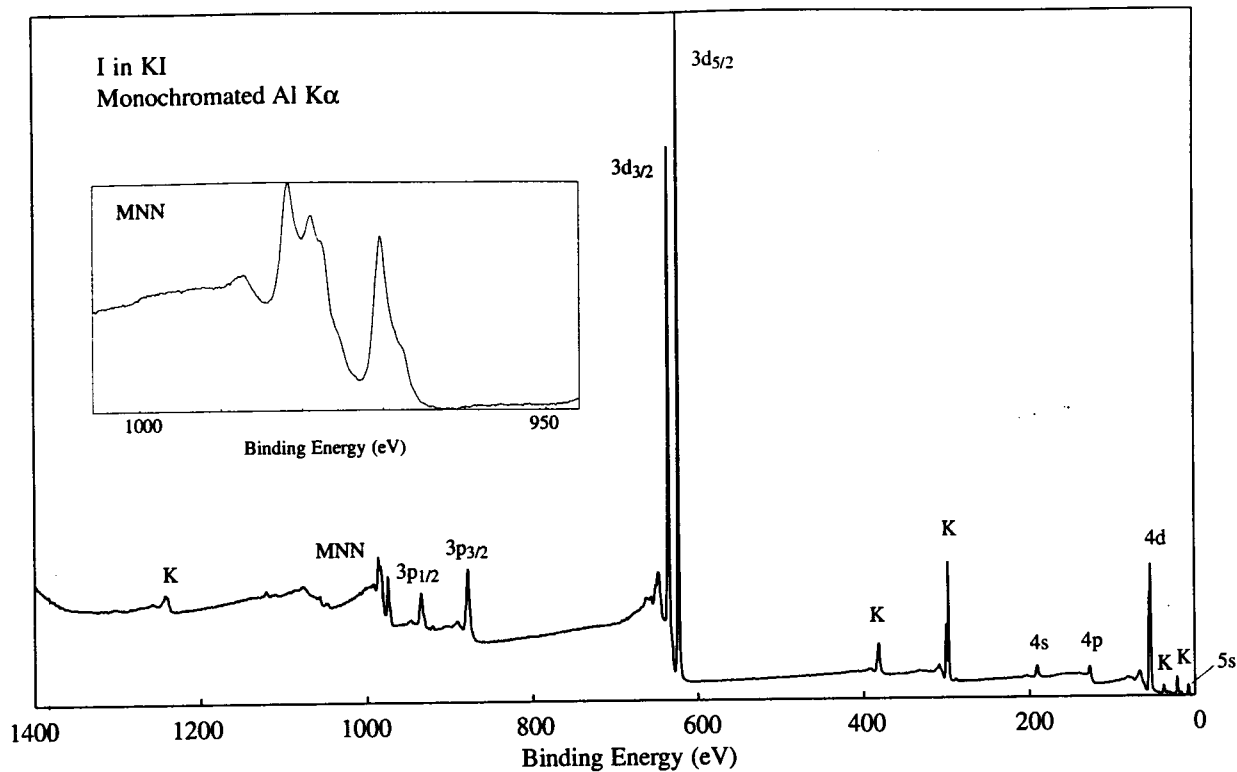


Line Positions (eV)				
<u>Photoelectron Lines</u>				
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}
1009	871	820	583	573
4s	4p	4d _{3/2}	4d _{5/2}	5s
170	111	42	41	12
<u>Auger Lines</u>				
M ₅ N ₄₅ N ₄₅		M ₄ N ₄₅ N ₄₅		
1005		995 (Al)		
772		762 (Mg)		



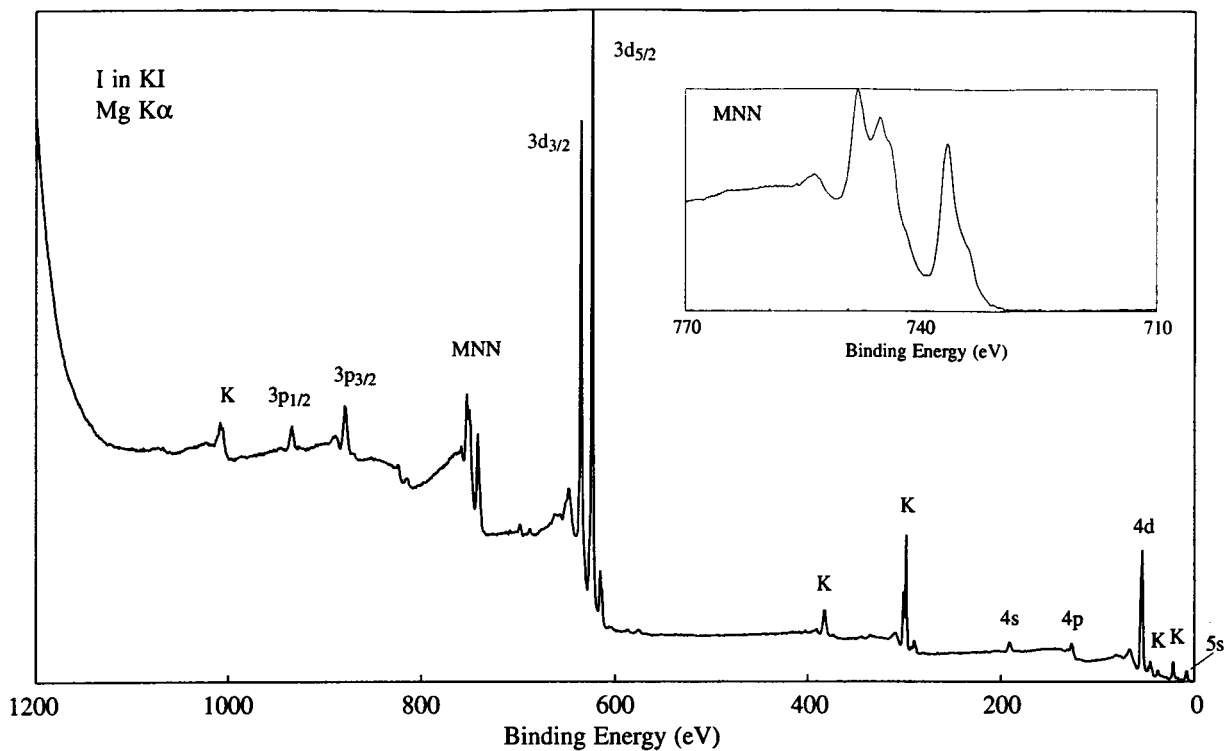
Compound Type	3d _{5/2} Binding Energy (eV)						
	572	573	574	575	576	577	578
Te		■					
CdTe	■	■					
GeTe	■	■					
Hg _{0.8} Cd _{0.2} Te	■	■					
Tellurides	■	■					
Halides					■	■	
TeO ₂					■	■	
TeO ₃						■	
Te(OH) ₆							■
Ph ₂ Te ₂			■				
Br ₃ TePh						■	



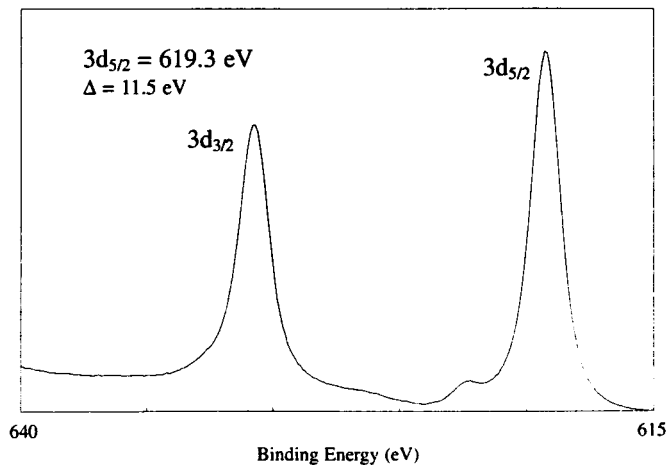


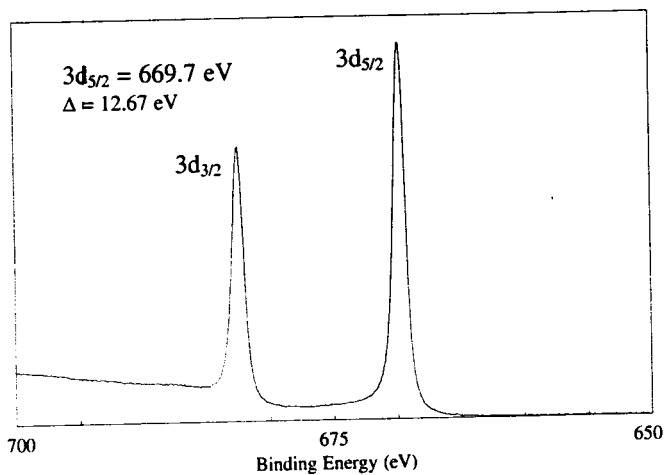
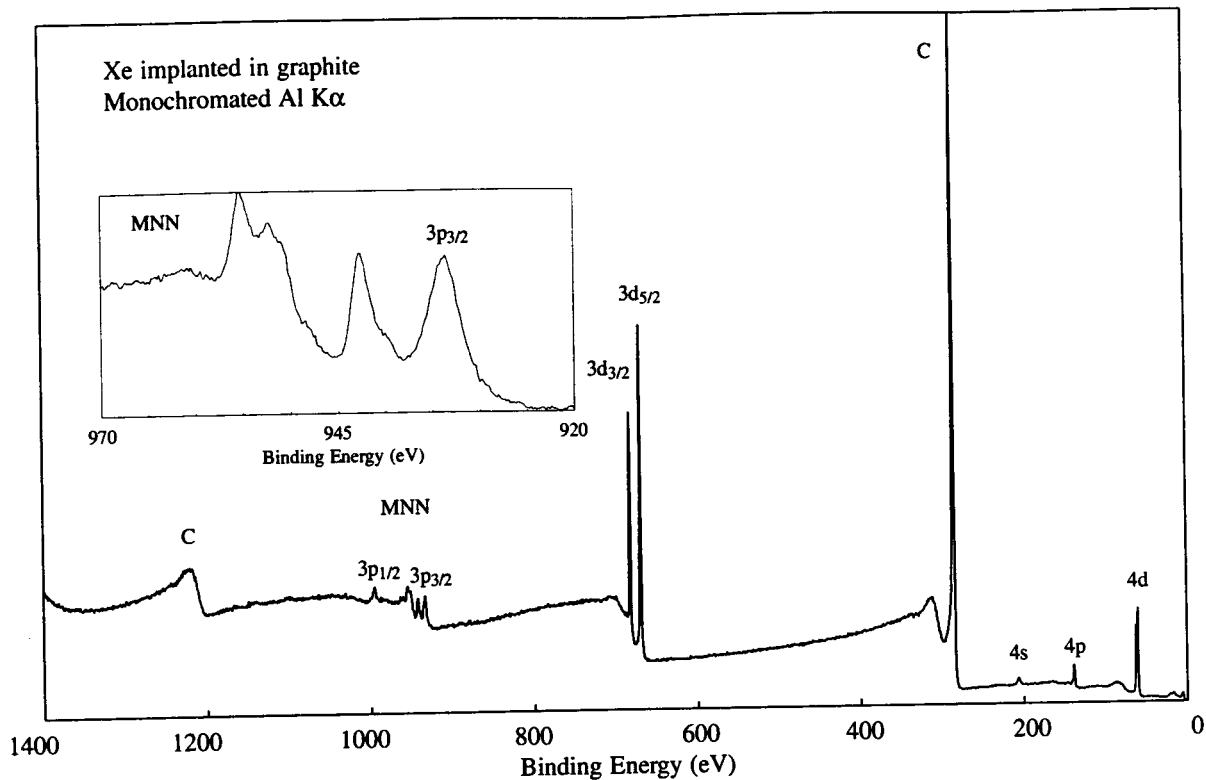
Line Positions (eV)

Photoelectron Lines				
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}
1071	930	875	630	619
4s	4p	4d _{3/2}	4d _{5/2}	5s
187	123	51	49	18
Auger Lines				
M ₅ N ₄₅ N ₄₅	M ₄ N ₄₅ N ₄₅			
982	971	(Al)		
749	738	(Mg)		

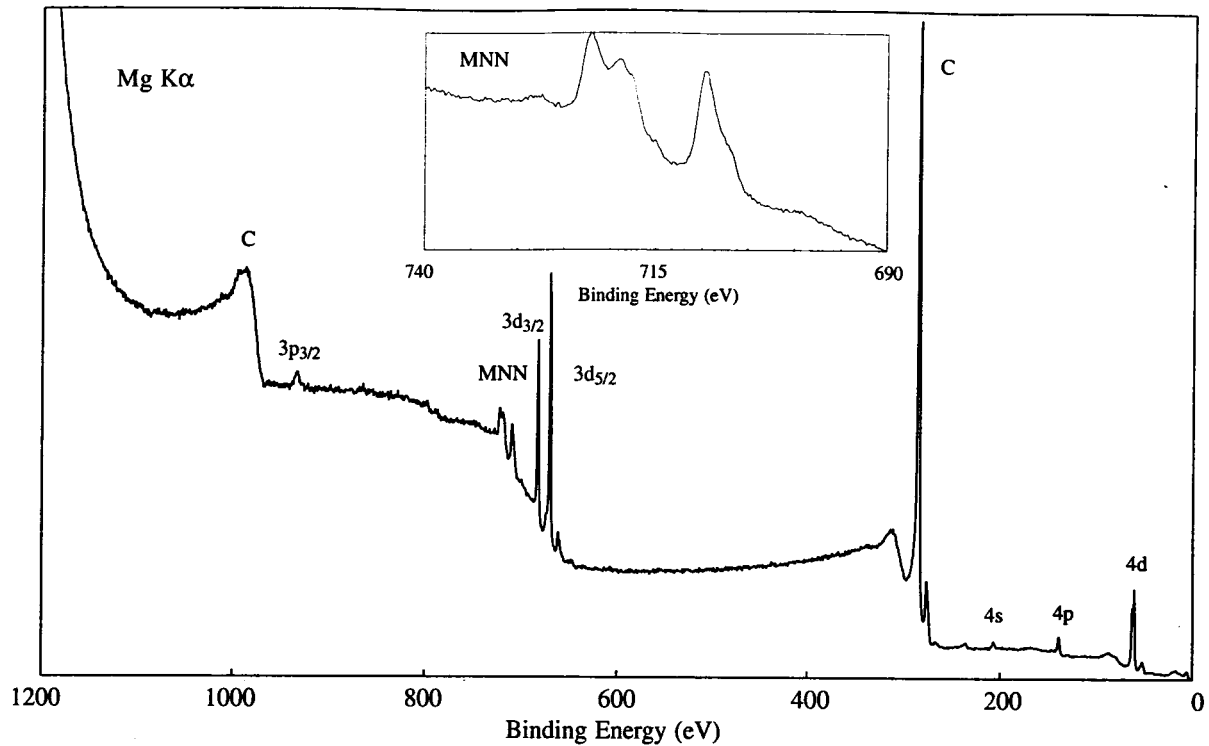


Compound Type	3d _{5/2} Binding Energy (eV)						
	618	619	620	621	622	623	624
I ₂			■				
Alkali iodides	■	■	■				
AgI		■	■				
NiI ₂	■	■					
NiI ₂ · 6H ₂ O		■	■				
NaIO ₃						■	
NaIO ₄							■
H ₅ I ₆						■	■
I ₂ O ₅						■	■
ICl				■			
ICl ₃					■		

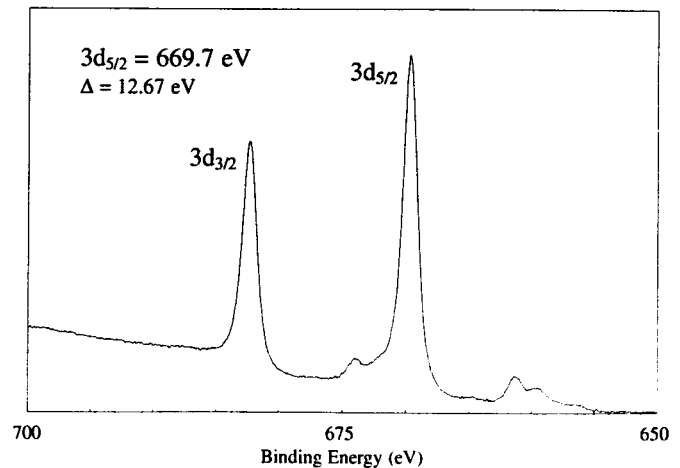


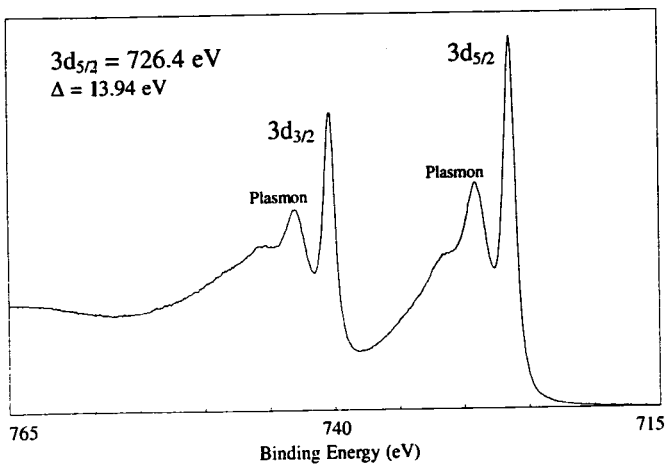
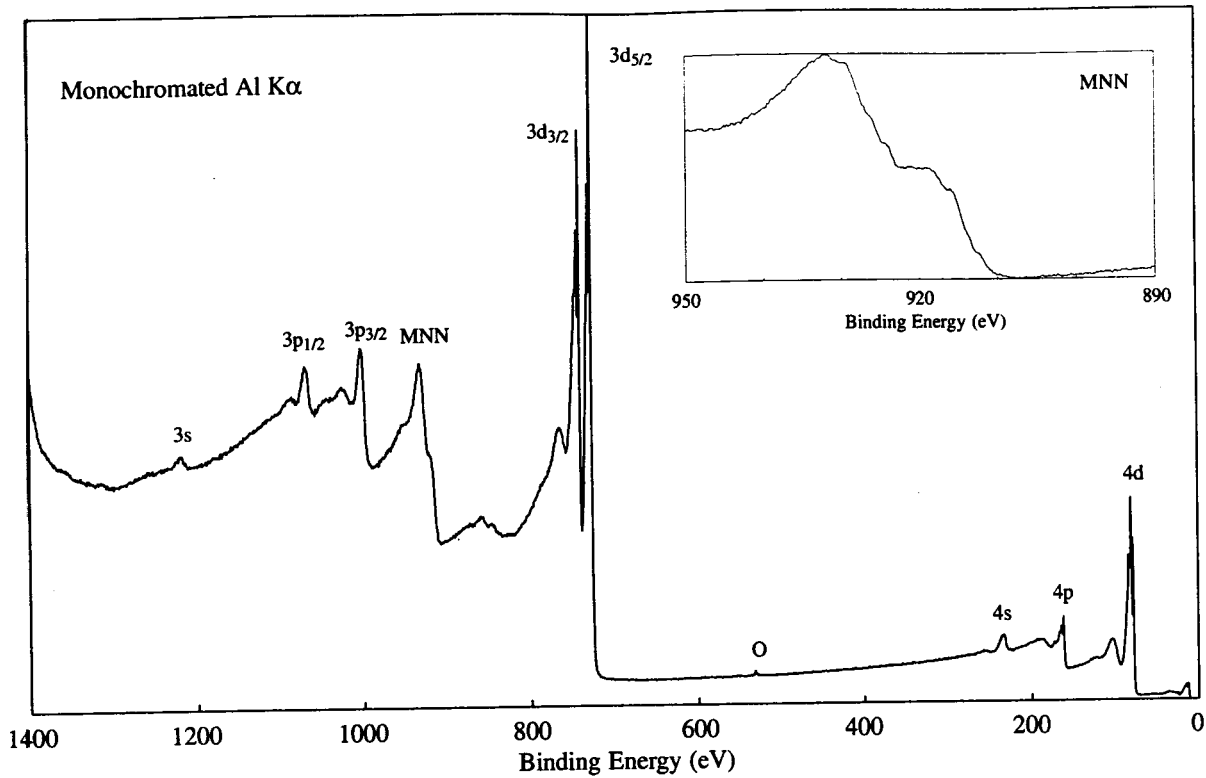


Line Positions (eV)				
<u>Photoelectron Lines</u>				
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}
1141	996	934	683	670
4s	4p	4d _{3/2}	4d _{5/2}	5s
207	139	63	61	17
<u>Auger Lines</u>				
M ₅ N ₄₅ N ₄₅		M ₄ N ₄₅ N ₄₅		
955		942 (Al)		
722		709 (Mg)		

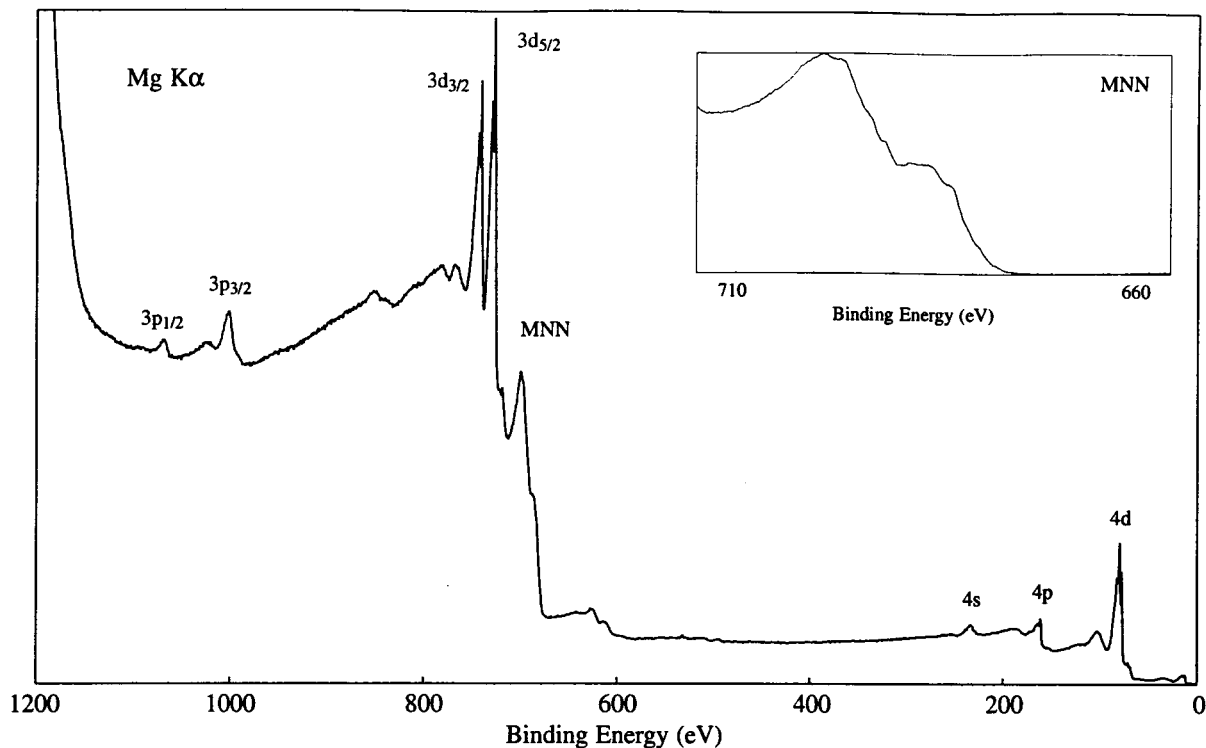


Compound Type	3d _{5/2} Binding Energy (eV)						
	668	669	670	671	672	673	674
Xe in Ag			■				
Xe in Au		■					
Xe in Cu			■				
Xe in Fe				■			
Xe in graphite		■					
Na ₄ XeO ₆							■

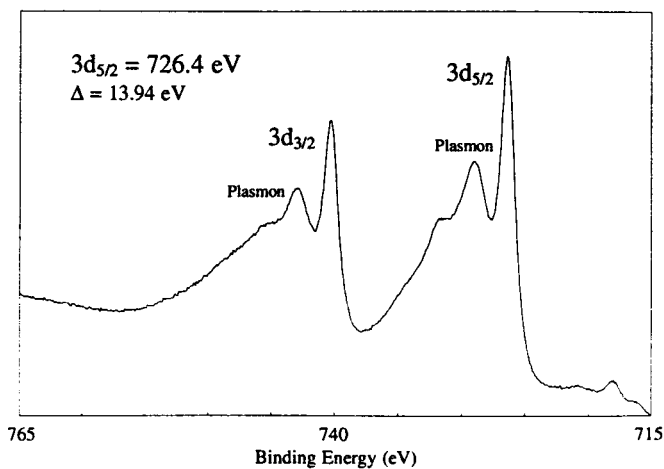




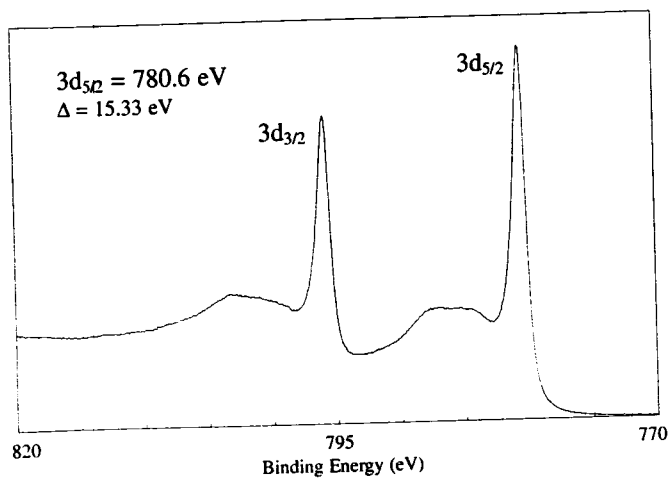
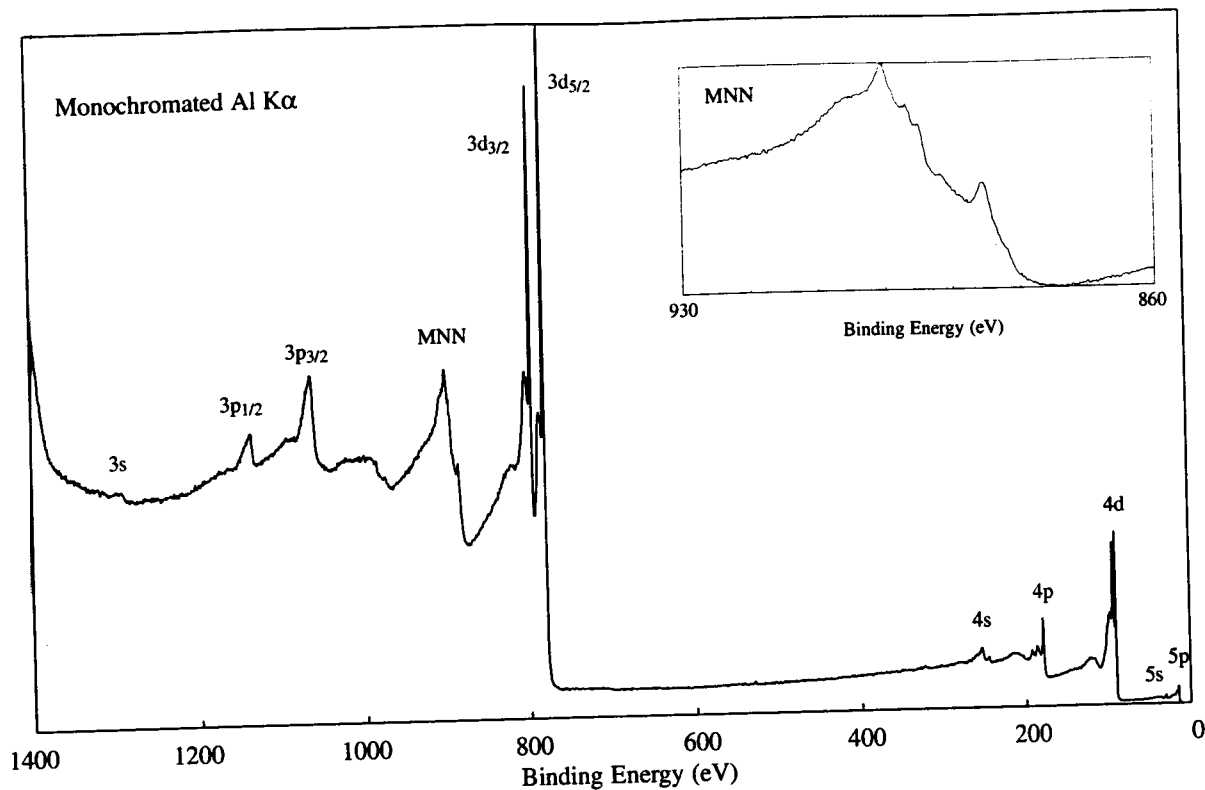
Line Positions (eV)					
Photoelectron Lines					
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}	
1219	1069	1002	740	726	
4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}	5s
234	173	161	80	77	25
Auger Lines					
M ₅ N ₄₅ N ₄₅		M ₄ N ₄₅ N ₄₅			
931		918		(Al)	
698		685		(Mg)	



3d _{5/2} Binding Energy (eV)				
Compound Type	723	724	725	726
Cs				■
Halides		■		
CsN ₃	■			
Cs ₂ SO ₄		■		
Cs ₃ PO ₄		■		
Cs ₄ P ₂ O ₇		■		
CsClO ₄		■		
Cs ₂ CrO ₄		■	■	
Cs ₂ Cr ₂ O ₇		■		
CsOH			■	



Barium Ba
Atomic Number 56



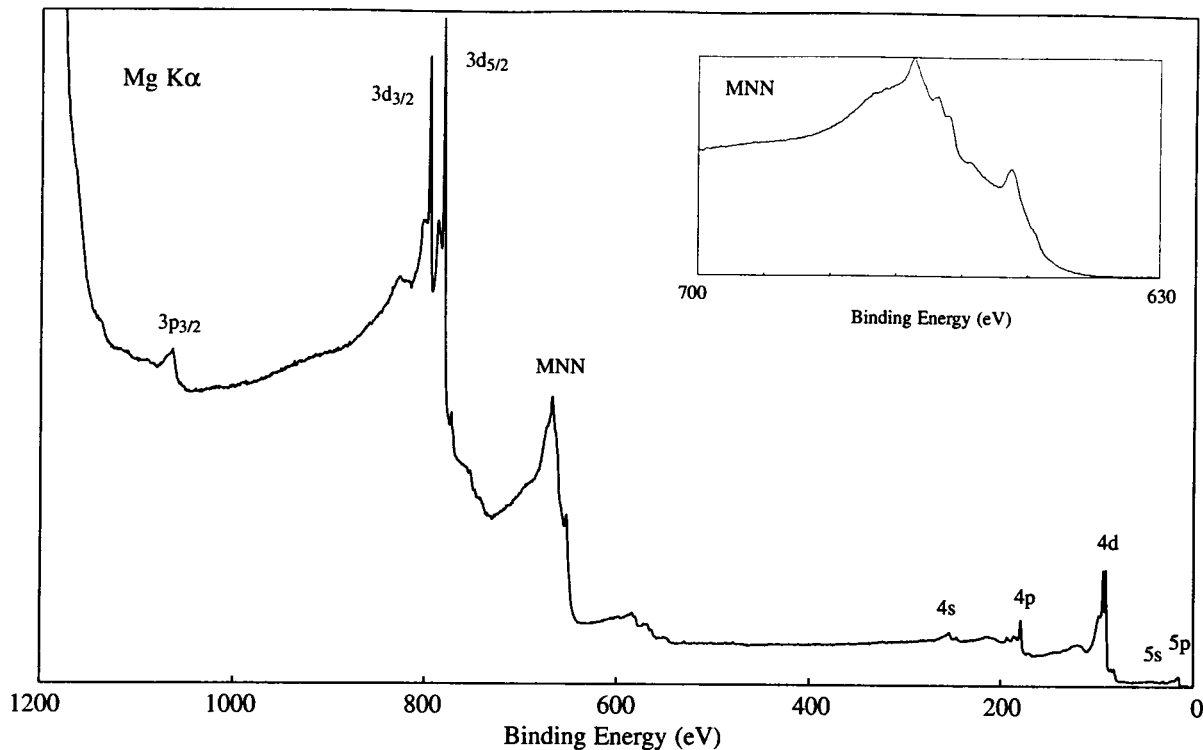
Line Positions (eV)

Photoelectron Lines

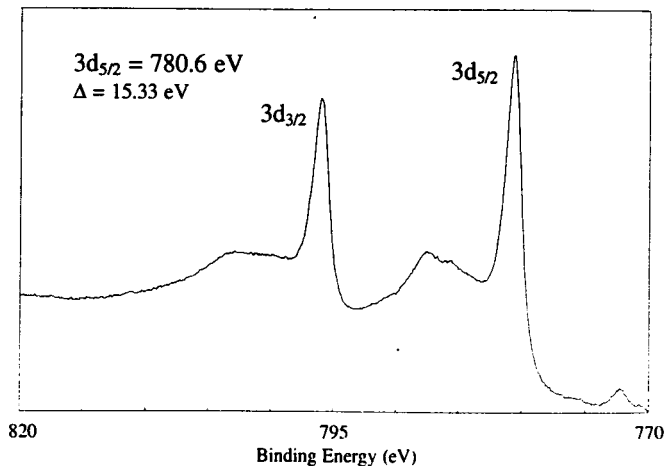
3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}		
1292	1138	1064	796	781		
4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}	5s	5p
254	193	179	93	90	31	15

Auger Lines

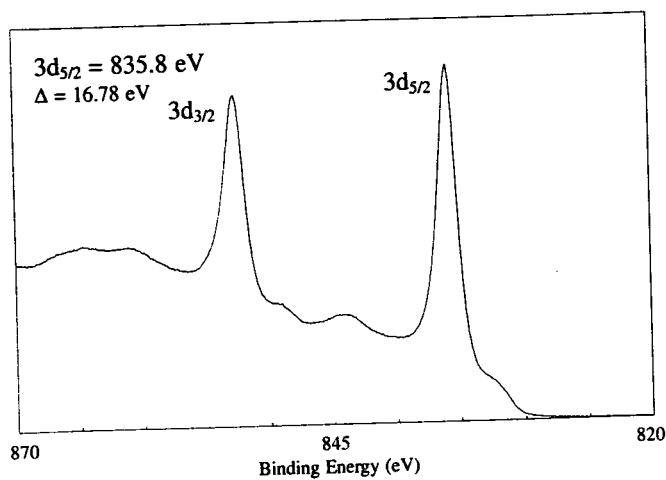
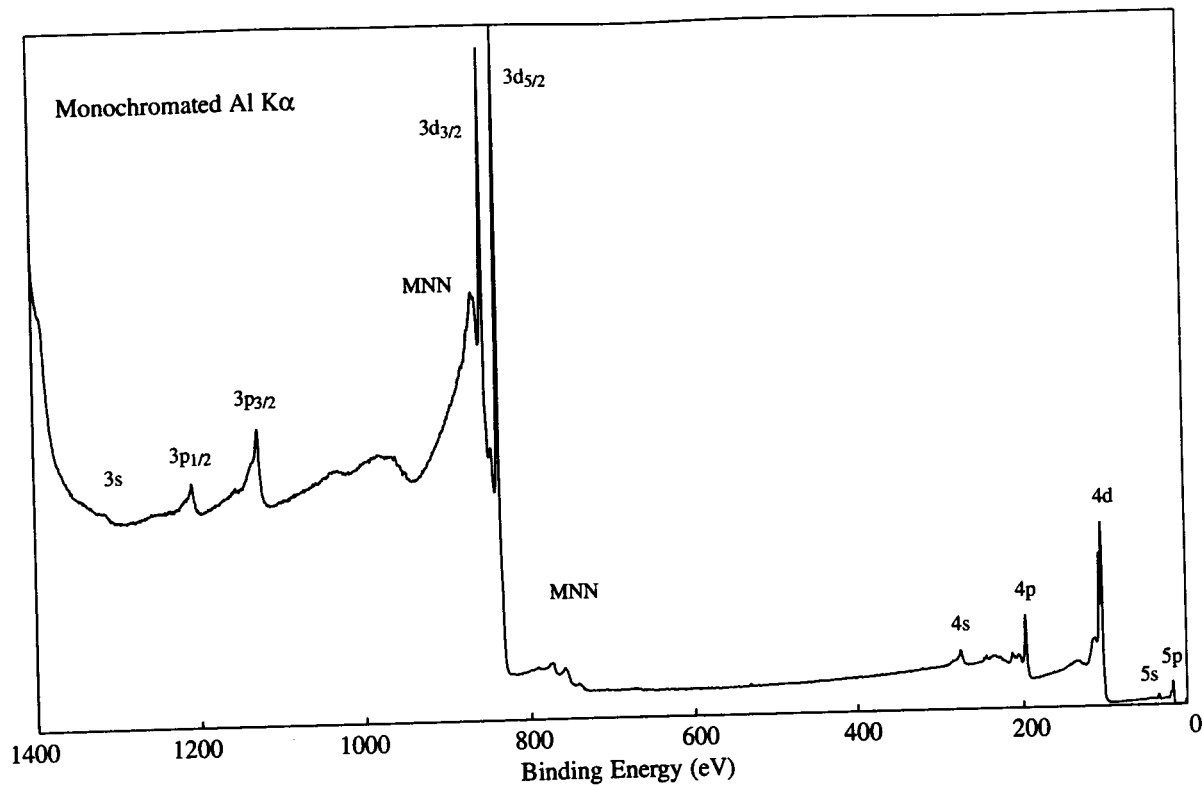
M ₅ N ₄₅ N ₄₅	M ₄ N ₄₅ N ₄₅	
900	886	(Al)
667	653	(Mg)



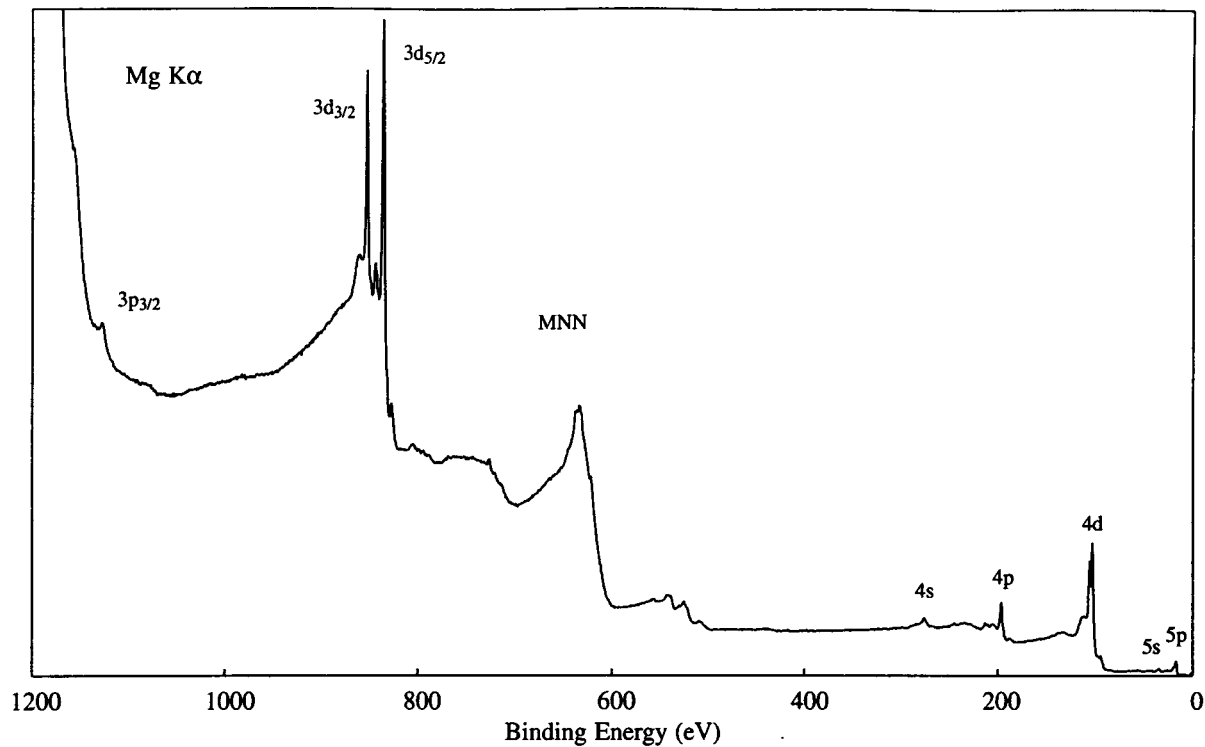
Compound Type	3d _{5/2} Binding Energy (eV)			
	778	779	780	781
Ba				■
BaS			■	
BaO		■		
Ba(NO ₃) ₂				■
BaCO ₃			■	
BaSO ₄			■	
BaCrO ₄	■			
BaMnO ₄	■			
BaRh ₂ O ₄		■		



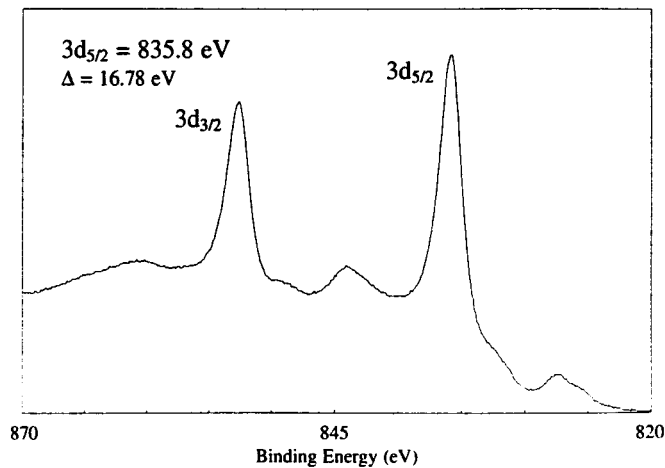
Lanthanum **La**
Atomic Number 57

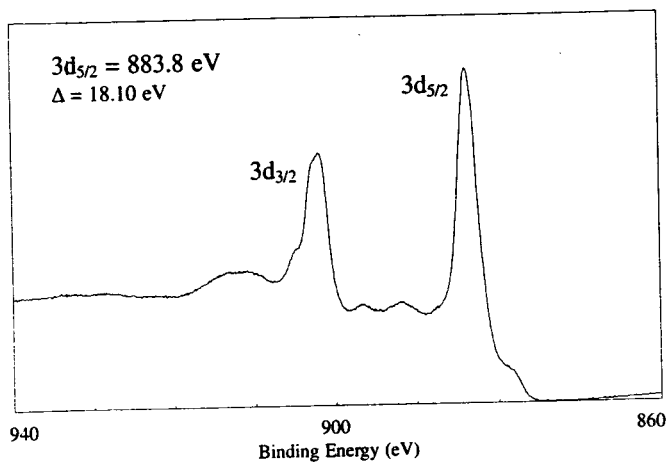
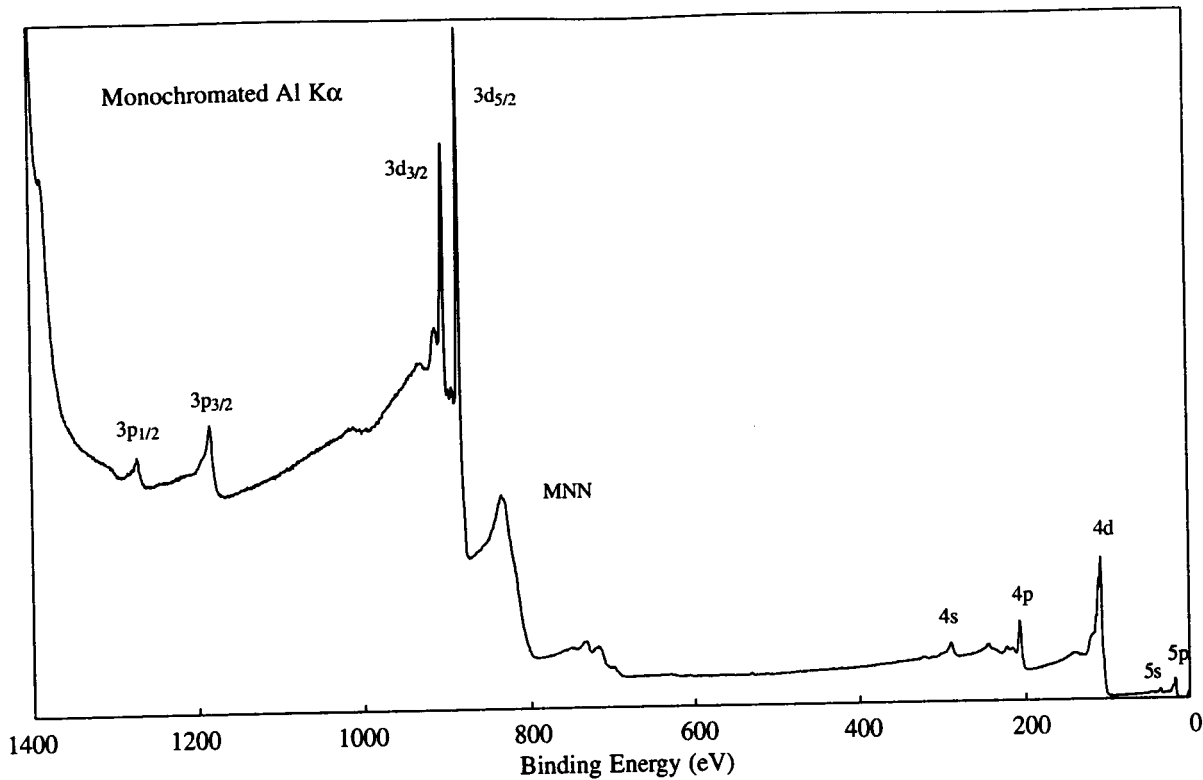


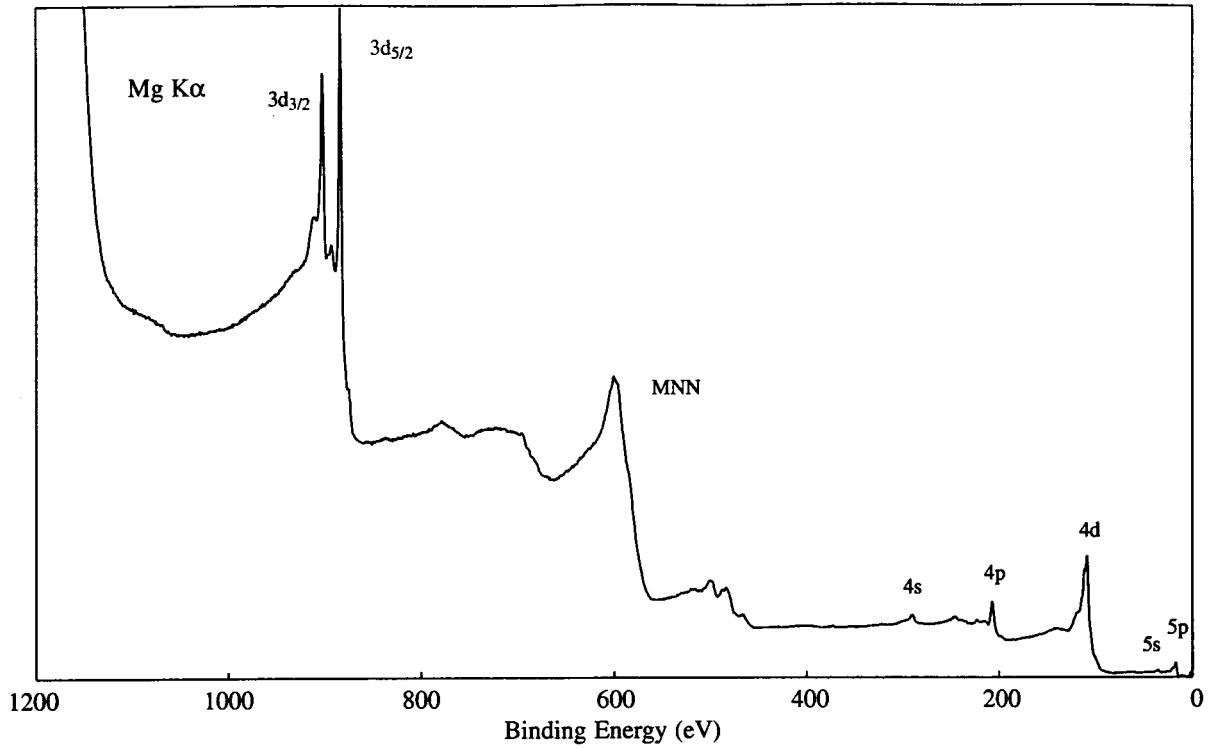
Line Positions (eV)						
Photoelectron Lines						
3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}			
1208	1128	853	836			
4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}	5s	5p
275	213	197	106	103	34	17
Auger Lines						
M ₅ N ₄₅ N ₄₅		M ₄ N ₄₅ N ₄₅				
867		854 (Al)				
634		621 (Mg)				



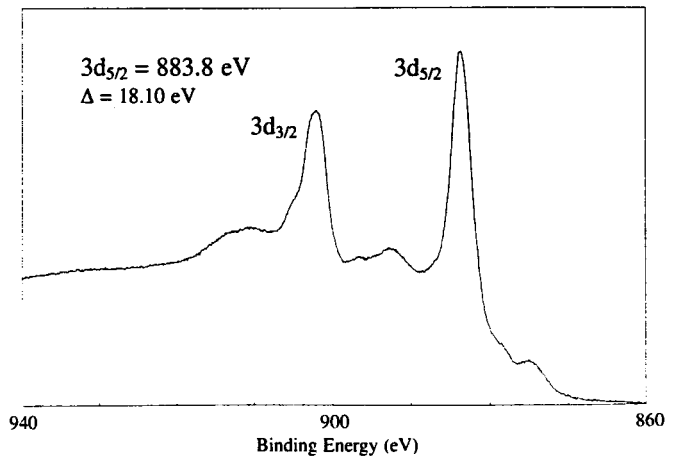
3d _{5/2} Binding Energy (eV)	
Compound Type	833 834 835 836 837 838 839
La	■
LaH ₂	■
La ₂ O ₃	■

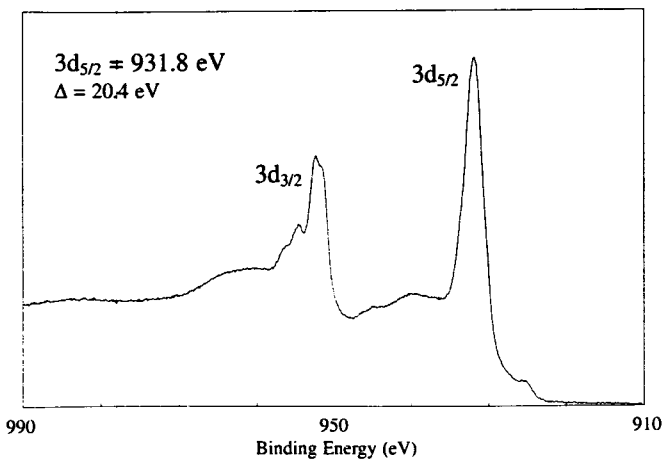
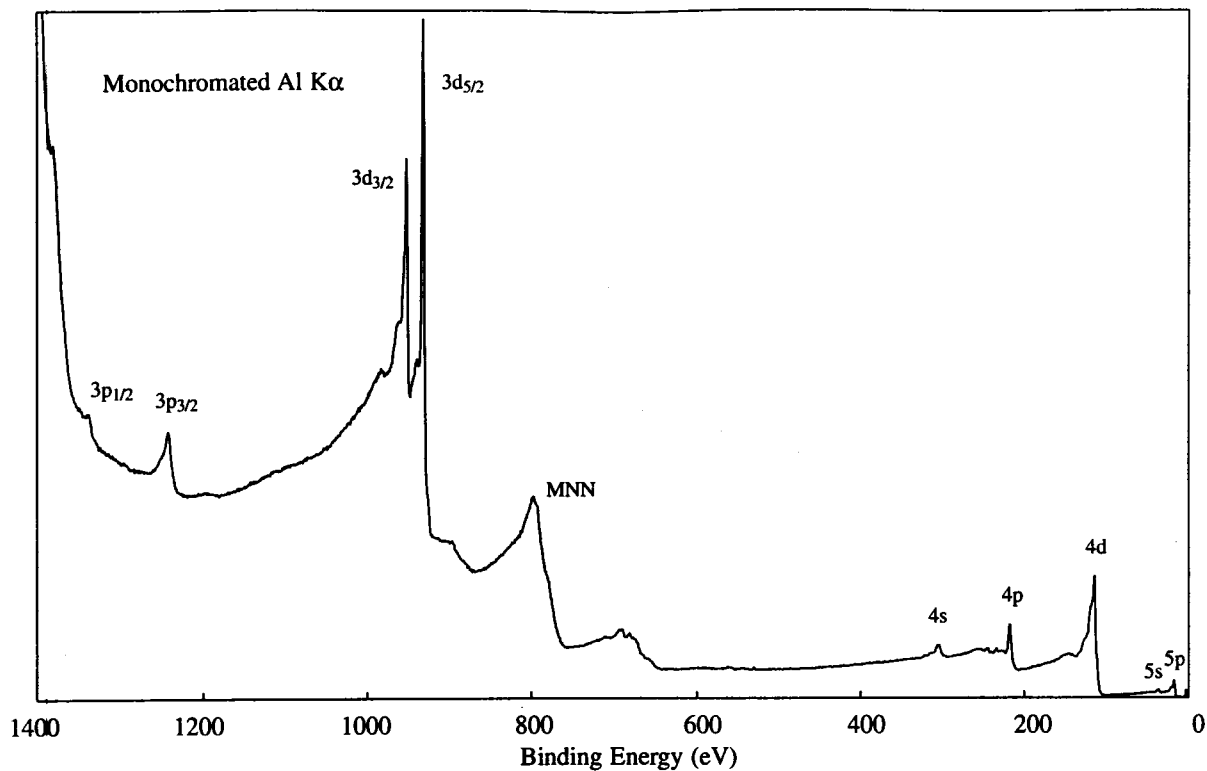






Compound Type	3d _{5/2} Binding Energy (eV)					
	881	882	883	884	885	886
Ce				■		
CeAl ₂			■	■		
CePd ₃				■	■	
CeSe				■	■	
CeCu ₂ Si ₂			■	■		
CeO ₂		■	■			
CeH ₃						■





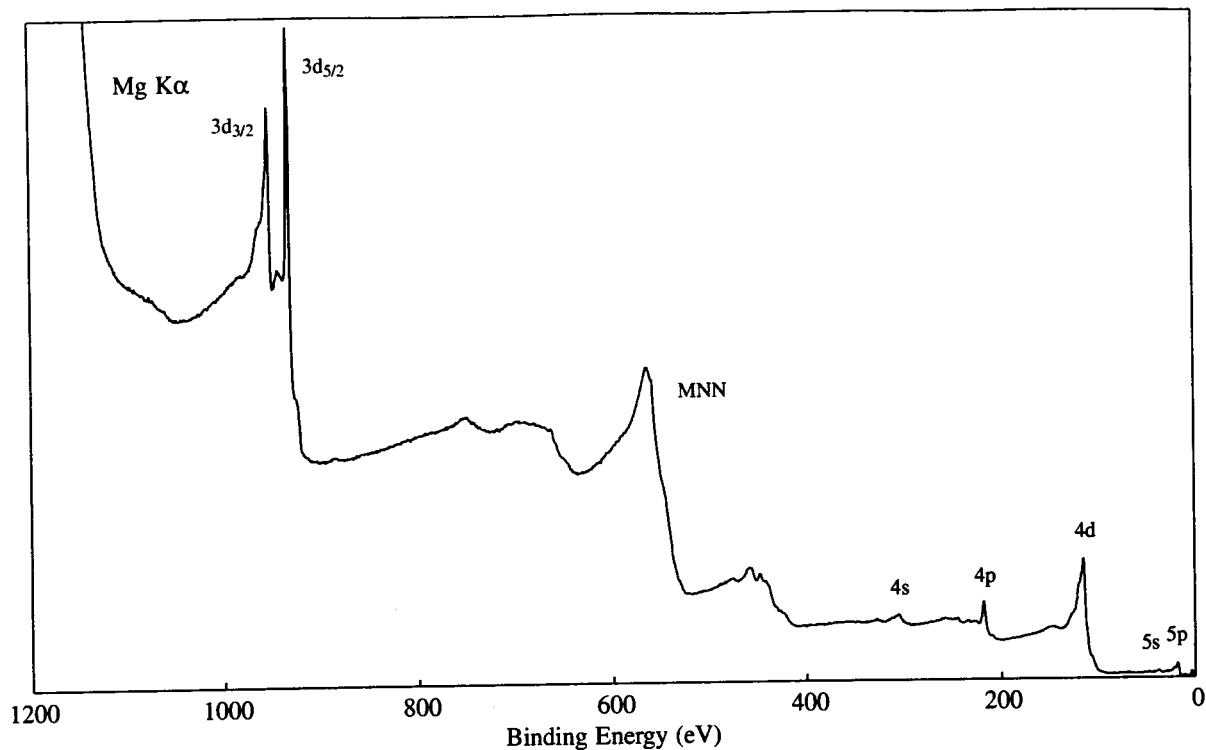
Line Positions (eV)

Photoelectron Lines

3p _{1/2}	3p _{3/2}	3d _{3/2}	3d _{5/2}		
1339	1242	952	932		
4s	4p _{1/2}	4p _{3/2}	4d	5s	5p
305	234	218	115	38	18

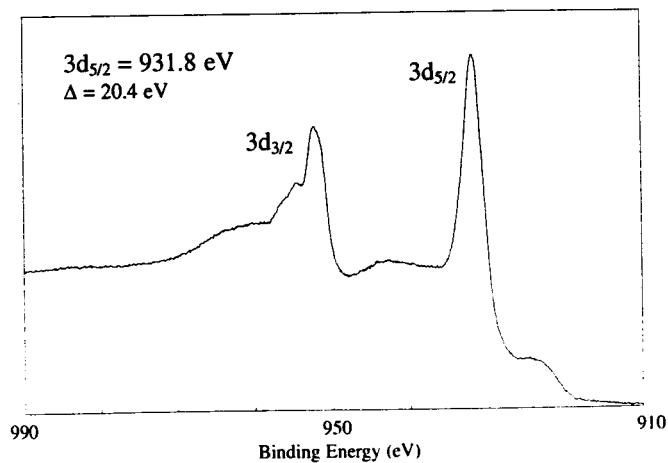
Auger Lines

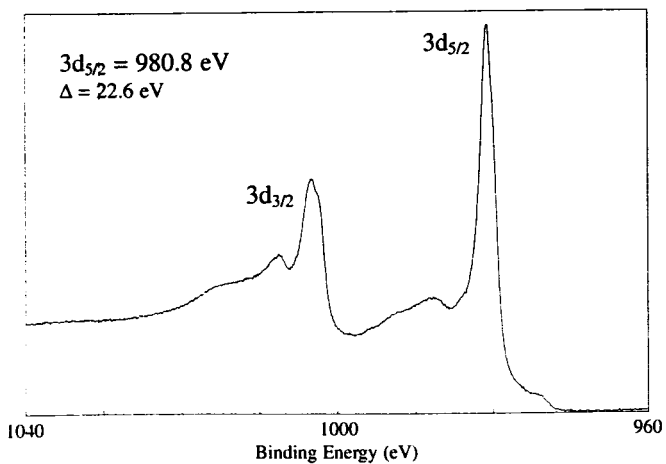
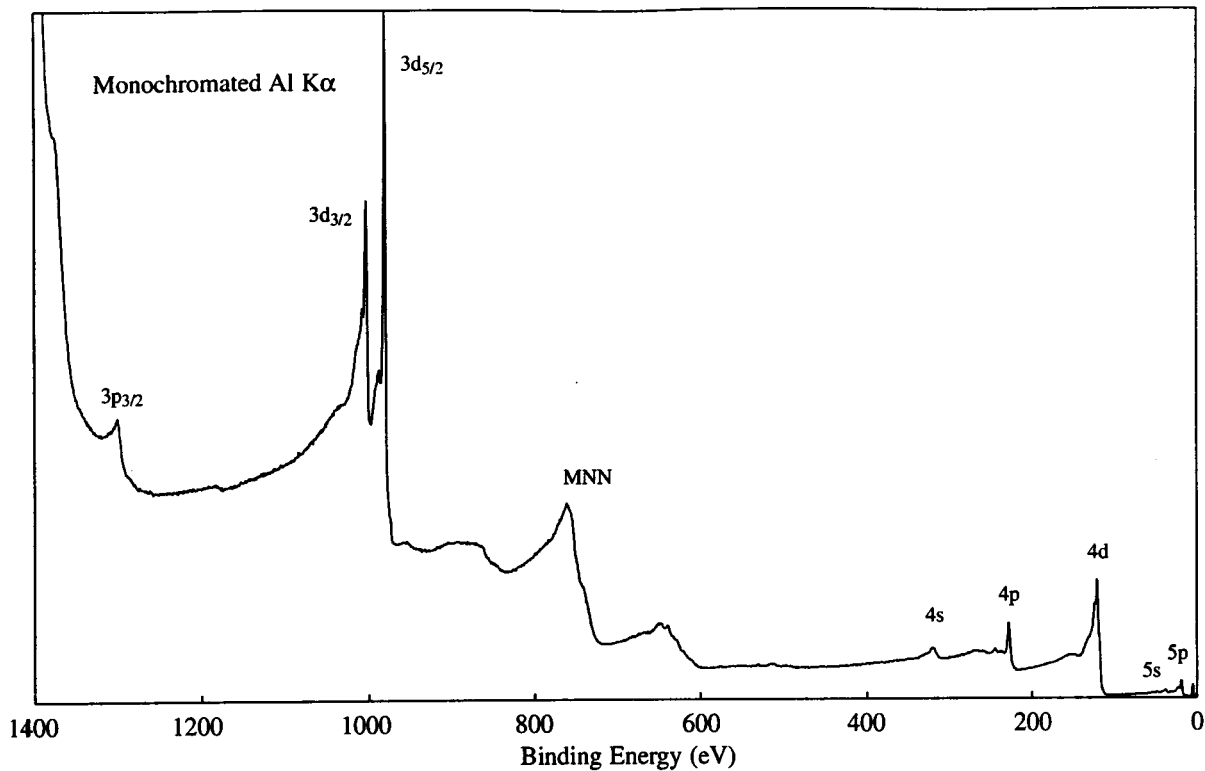
M ₄₅ N ₄₅ N ₄₅	
797	(Al)
564	(Mg)



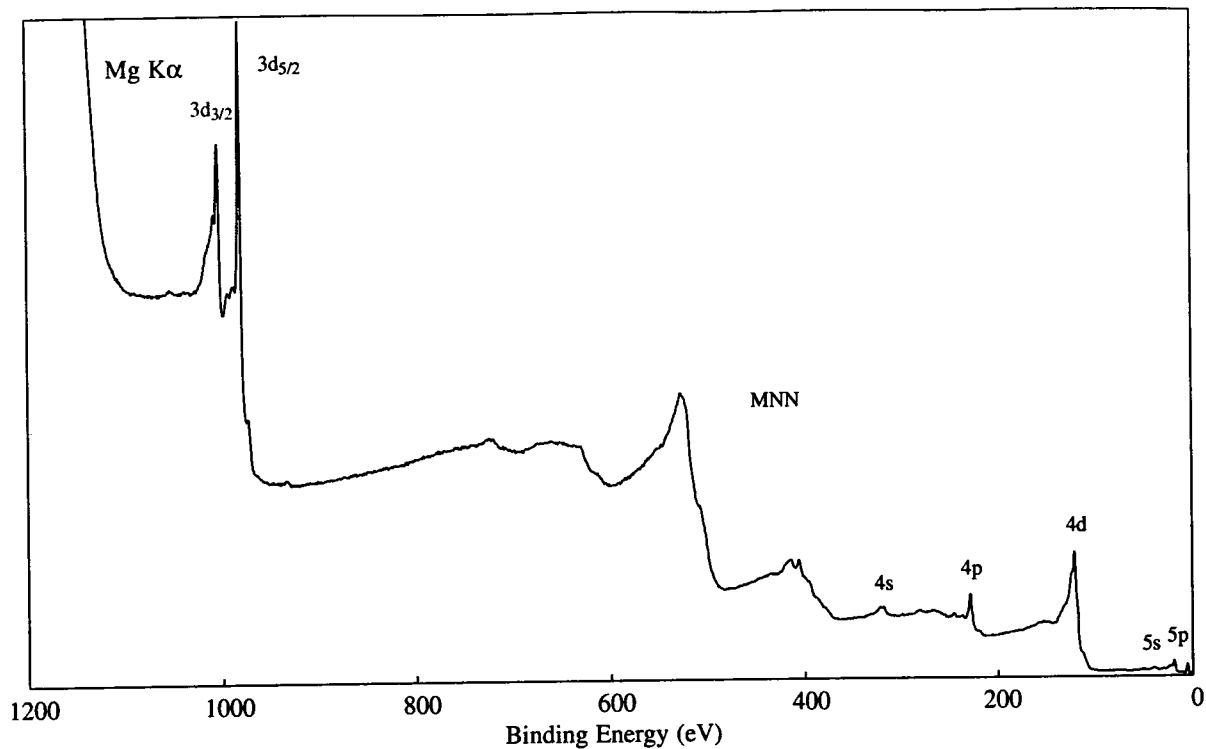
3d _{5/2} Binding Energy (eV)					
Compound Type	931	932	933	934	935
Pr		■			
Pr ₂ O ₃			■		
PrO ₂					■

4d Binding Energy (eV)			
Compound Type	115	116	117
Pr ₂ O ₃		■	
PrO ₂		■	



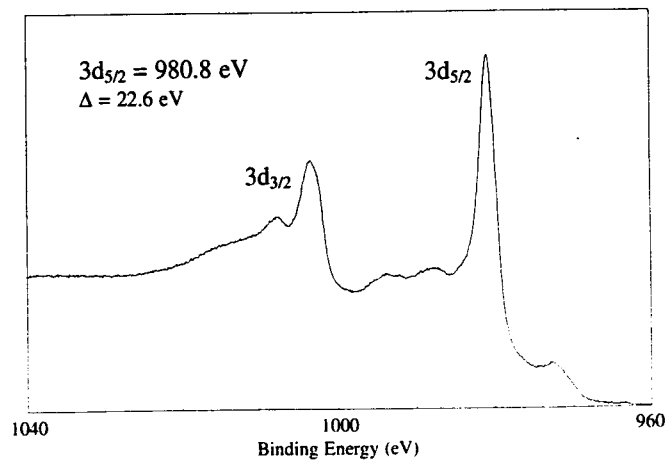


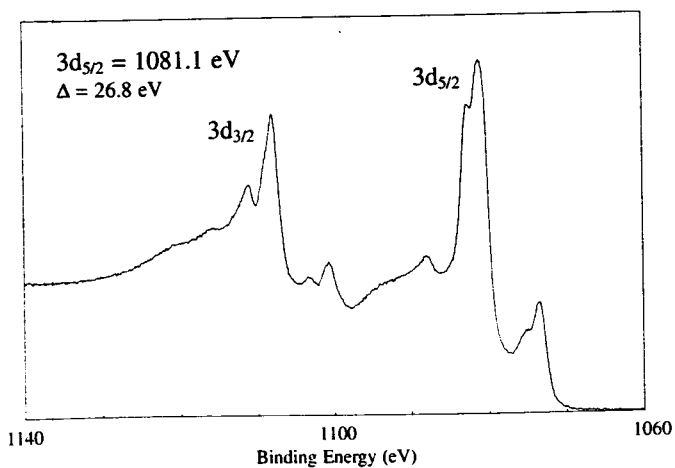
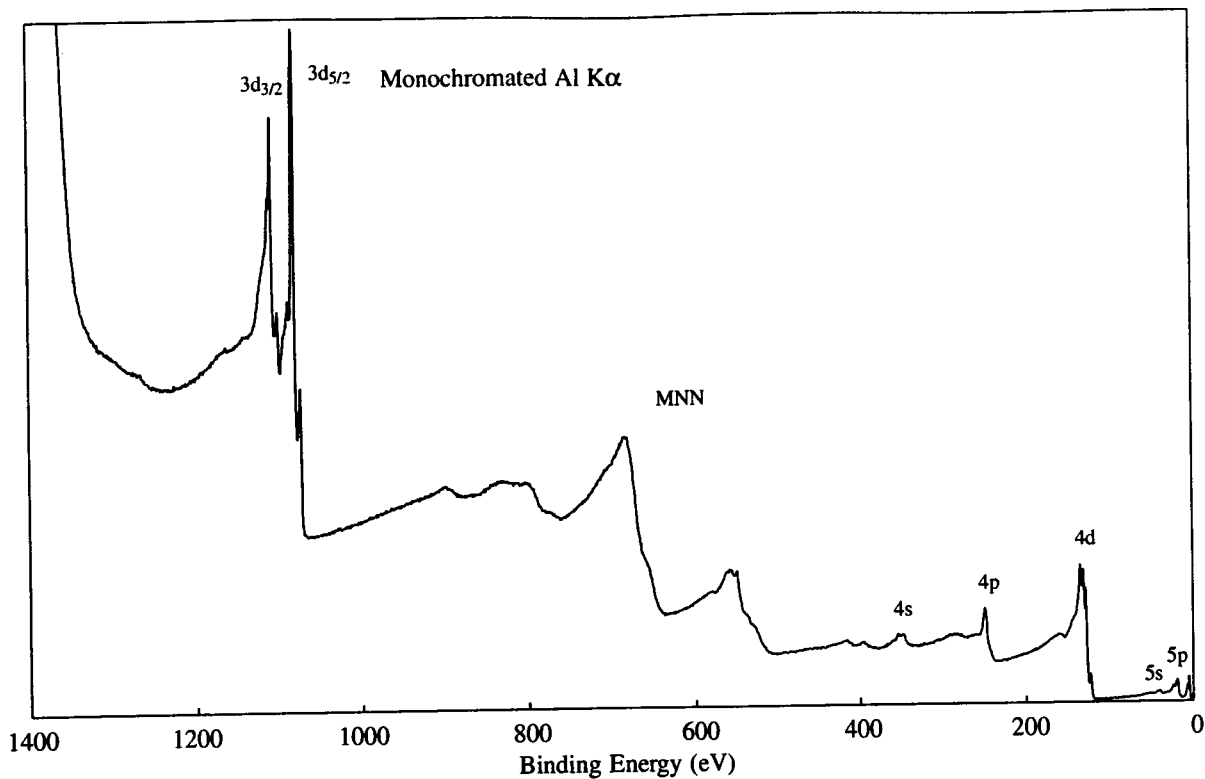
Line Positions (eV)					
Photoelectron Lines					
3p _{3/2}	3d _{3/2}	3d _{5/2}			
1301	1003	981			
4s	4p _{1/2}	4p _{3/2}	4d	5s	5p
320	245	228	121	39	19
Auger Lines					
M ₄₅ N ₄₅ N ₄₅					
		758	(Al)		
		525	(Mg)		



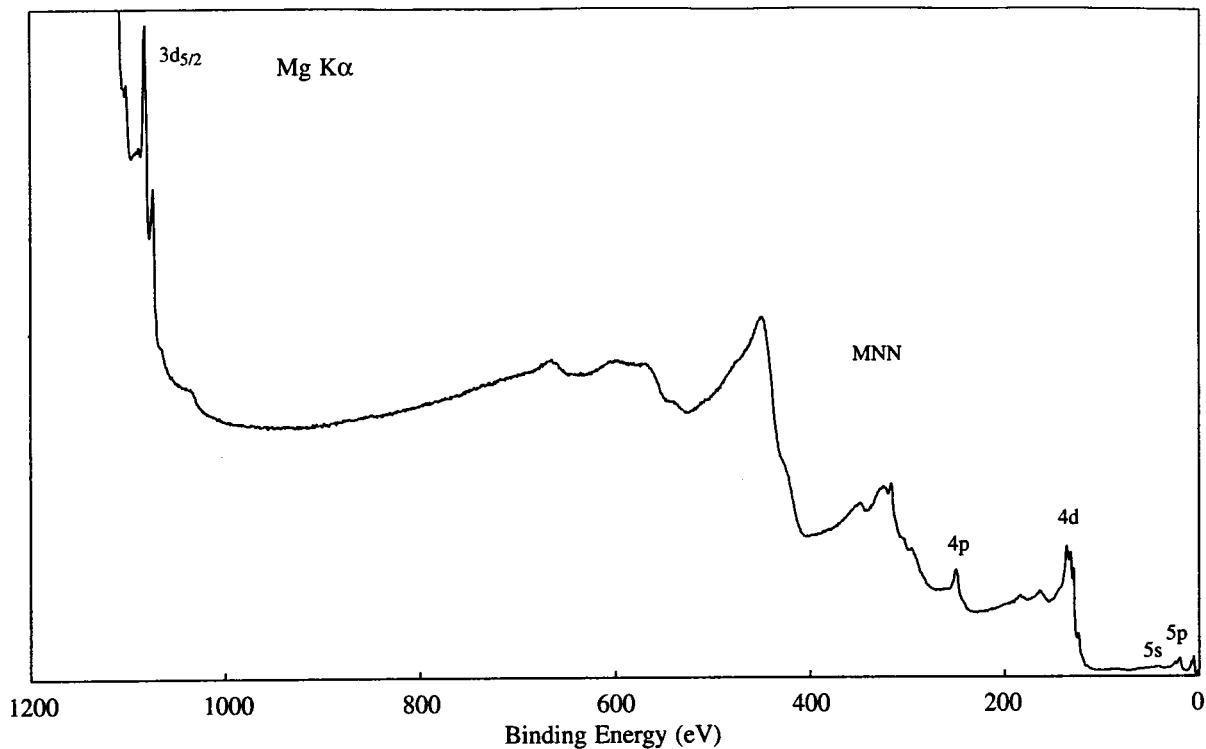
3d _{5/2} Binding Energy (eV)			
Compound Type	980	981	982
Nd		■	
Nd ₂ O ₃			■

4d Binding Energy (eV)			
Compound Type	119	120	121
Nd ₂ O ₃			■

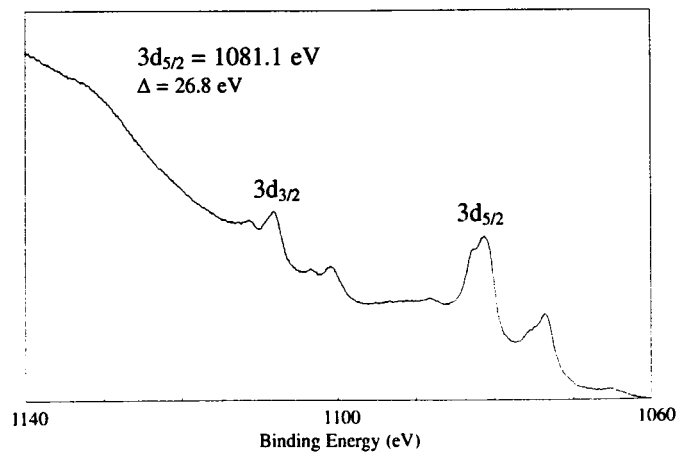


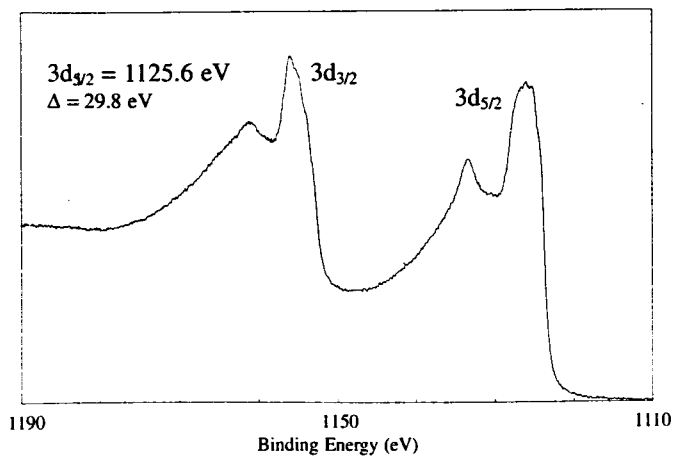
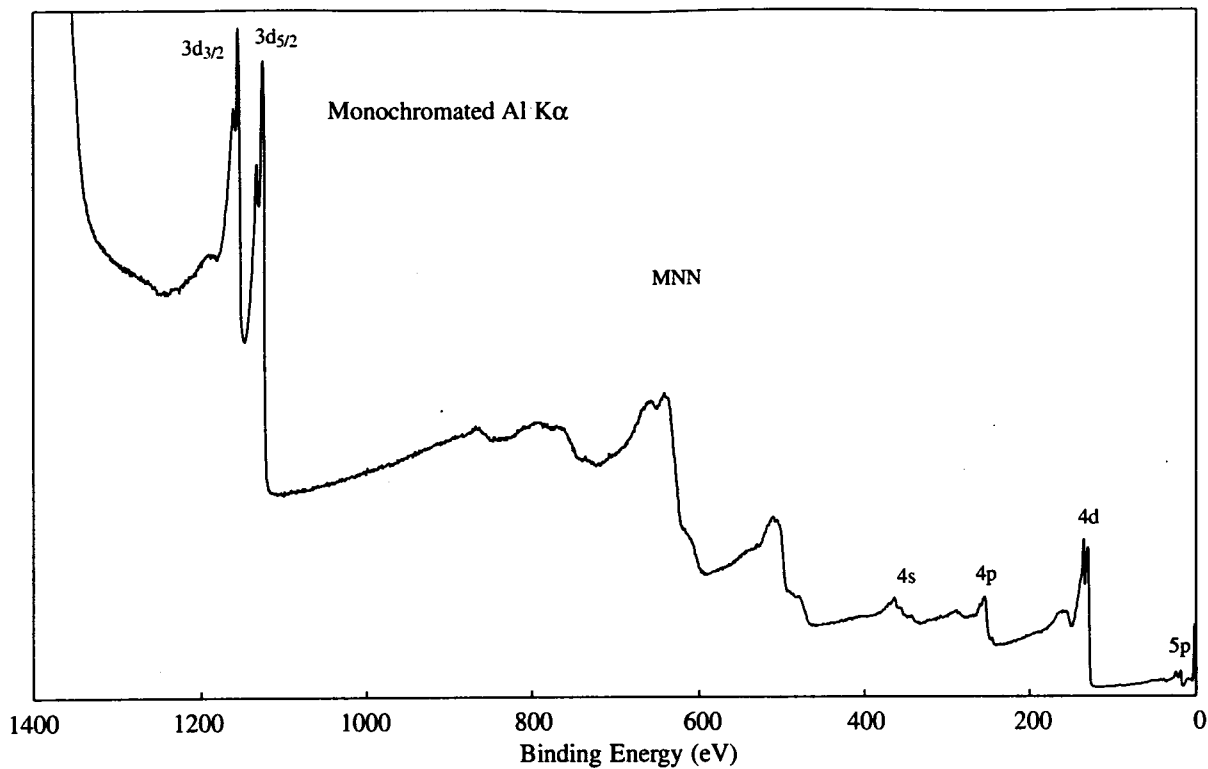


Line Positions (eV)							
<u>Photoelectron Lines</u>							
3d _{3/2}	3d _{5/2}	4s	4p _{1/2}	4p _{3/2}	4d	5s	5p
1108	1081	349	283	250	129	41	19
<u>Auger Lines</u>							
M ₄₅ N ₄₅ N ₄₅							
682		(Al)					
449		(Mg)					

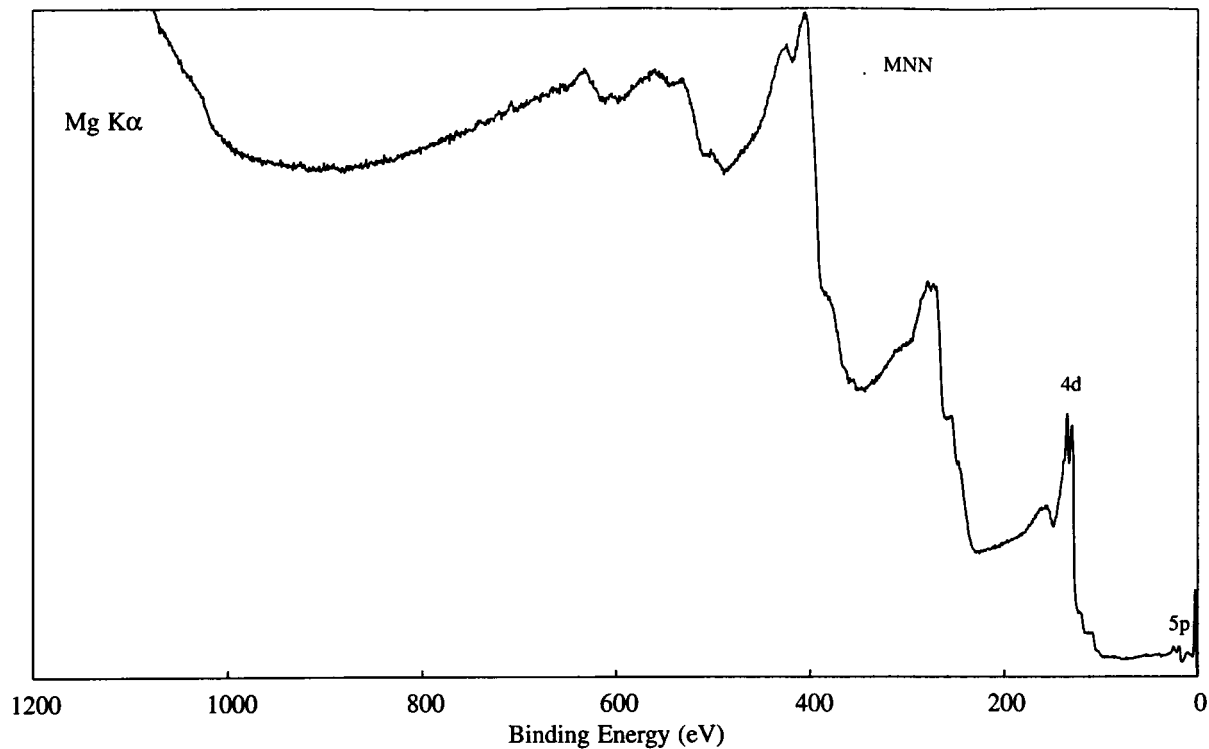


3d _{5/2} Binding Energy (eV)				
Compound Type	1081	1082	1083	1084
Sm				
Sm ₂ O ₃				



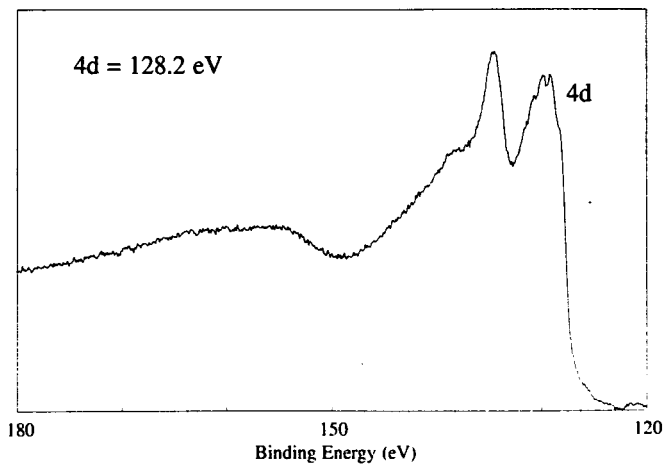


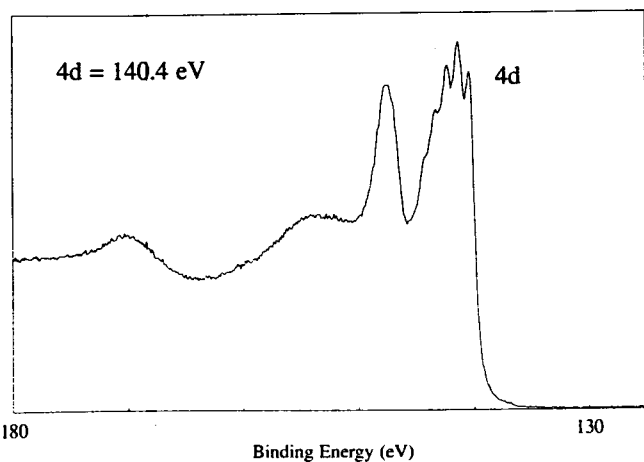
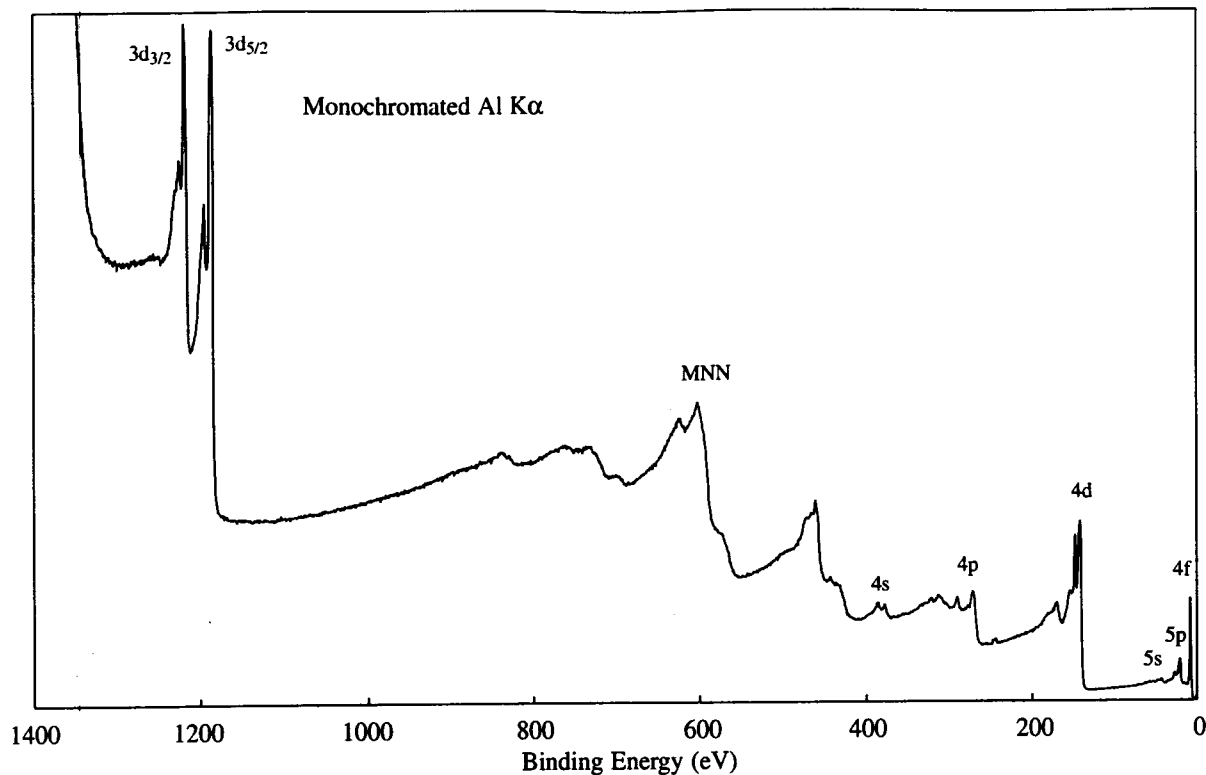
Line Positions (eV)							
<u>Photoelectron Lines</u>							
3d _{3/2}	3d _{5/2}	4s	4p _{1/2}	4p _{3/2}	4d	5s	5p
1155	1126	363	289	255	128	39	19
<u>Auger Lines</u>							
M ₄₅ N ₄₅ N ₄₅							
637		(Al)					
404		(Mg)					



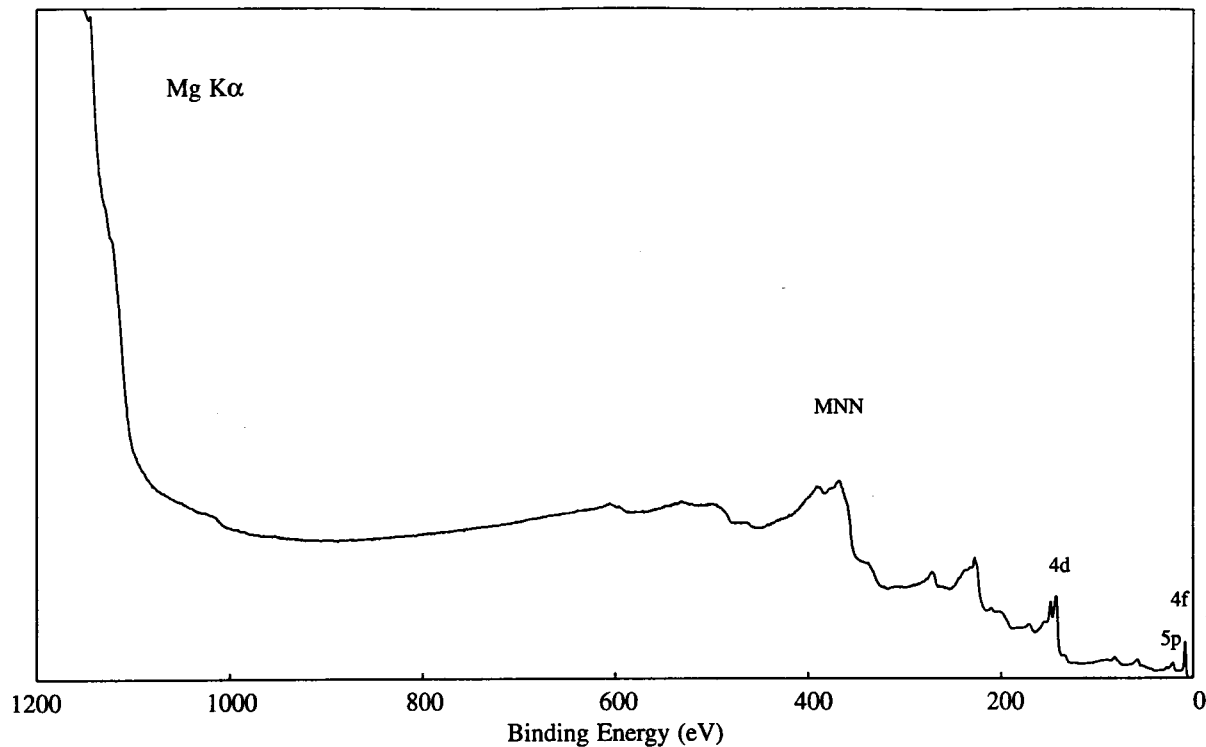
3d _{5/2} Binding Energy (eV)							
Compound Type	1123	1124	1125	1126	1127	1128	1129
Eu			■				

4d Binding Energy (eV)								
Compound Type	128	129	130	131	132	133	134	135
Eu	■							
Eu ₂ O ₃								■



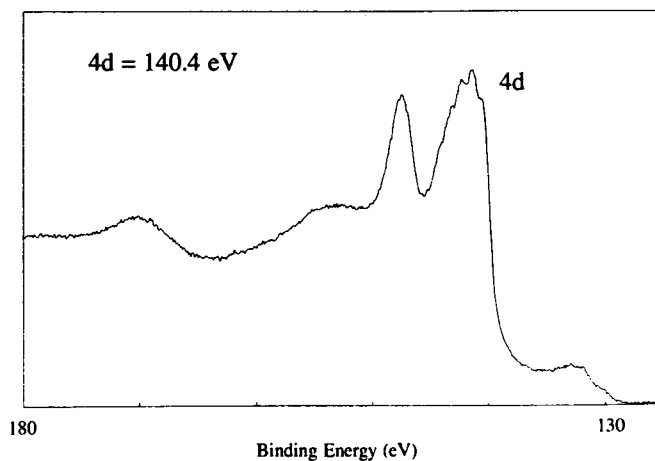


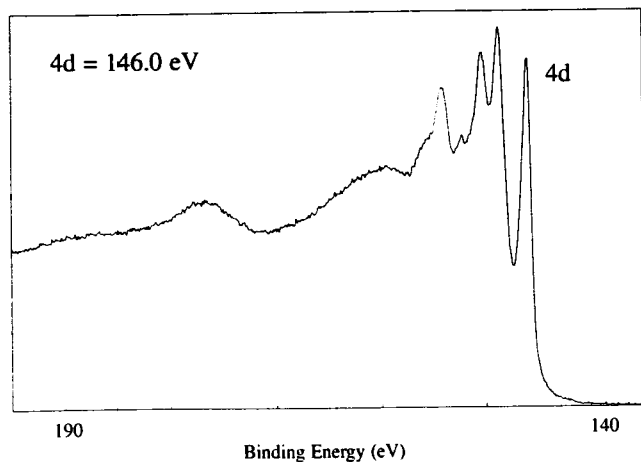
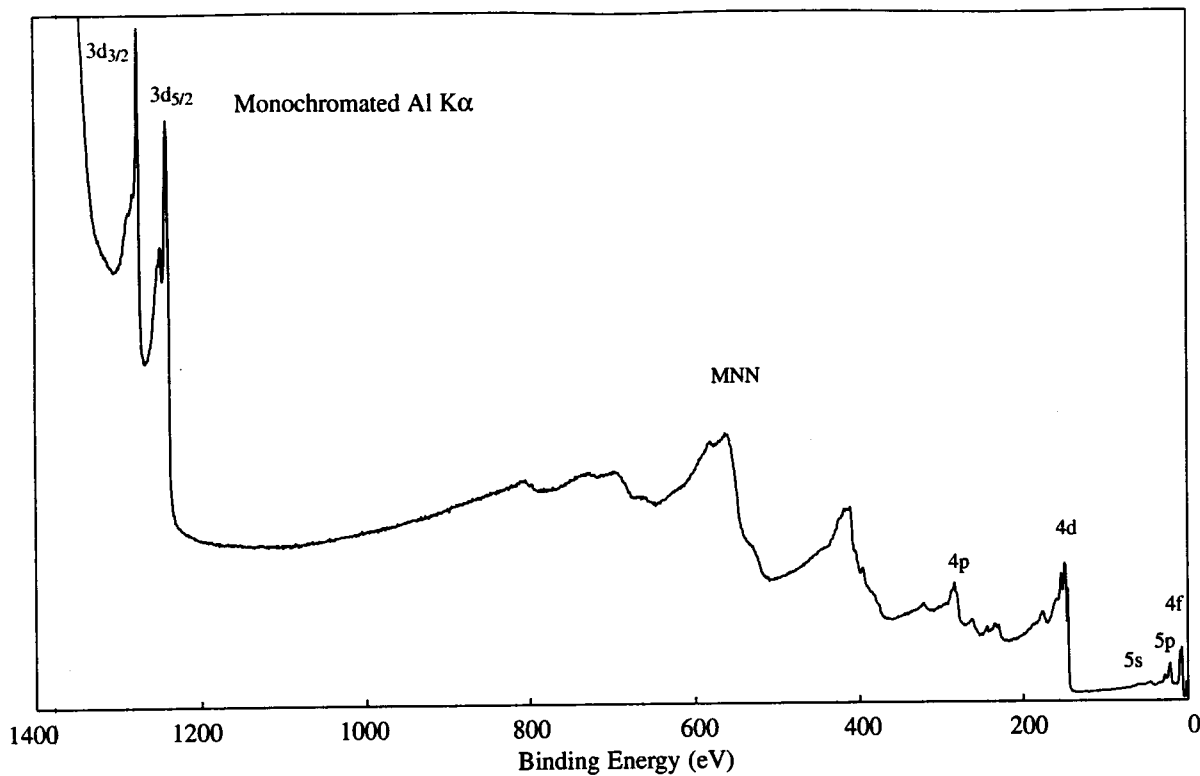
Line Positions (eV)						
<u>Photoelectron Lines</u>						
3d _{3/2}	3d _{5/2}					
1218	1186					
4s	4p _{1/2}	4p _{3/2}	4d	5s	5p	4f
378	291	272	140	43	21	8
<u>Auger Lines</u>						
M ₄₅ N ₄₅ N ₄₅						
602 (Al)						
369 (Mg)						



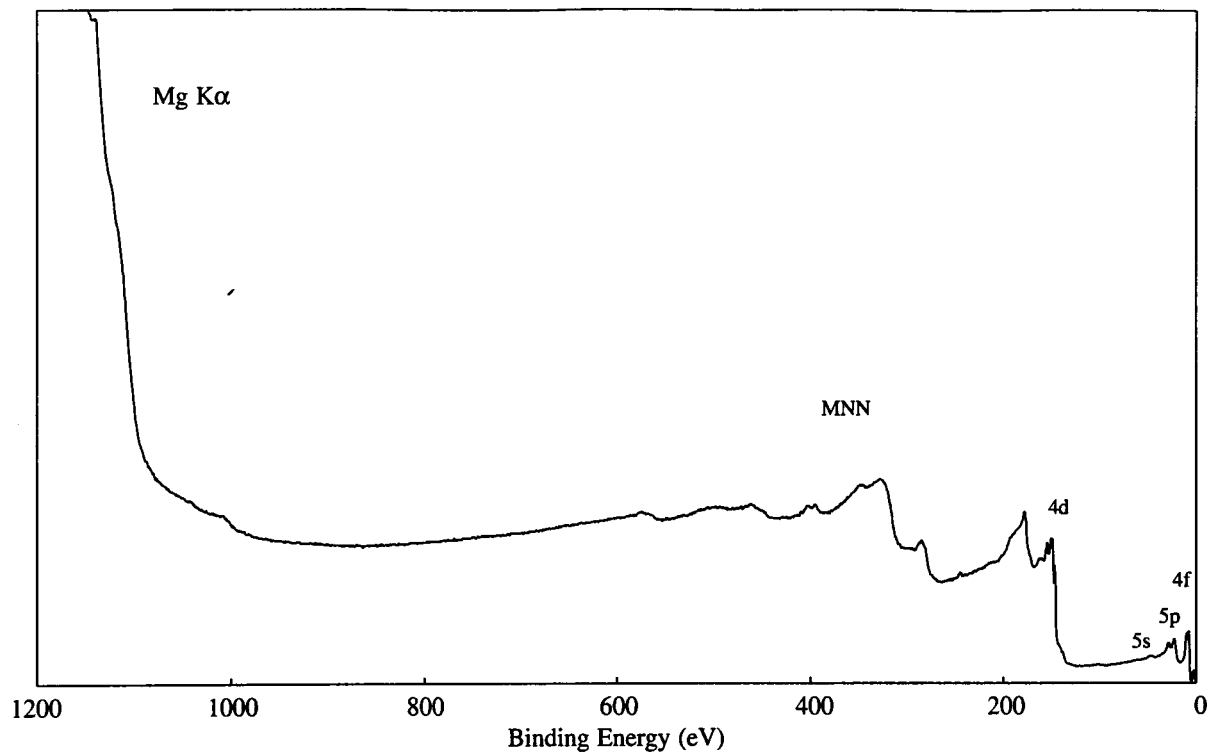
4d Binding Energy (eV)					
Compound Type	140	141	142	143	144
Gd	■				
Gd ₂ O ₃					■

3d _{5/2} Binding Energy (eV)			
Compound Type	1187	1188	1189
Gd	■		
Gd ₂ O ₃			■



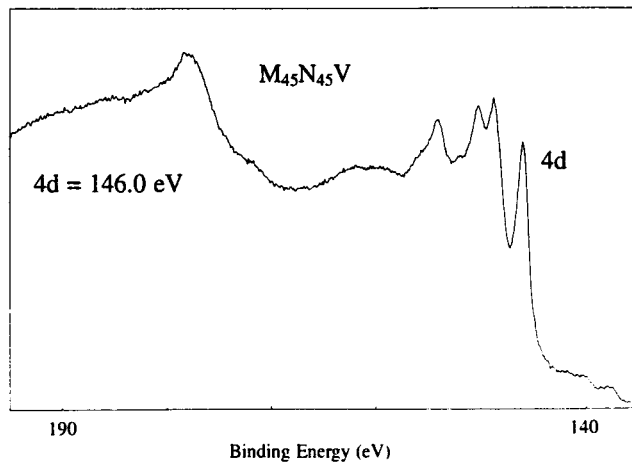


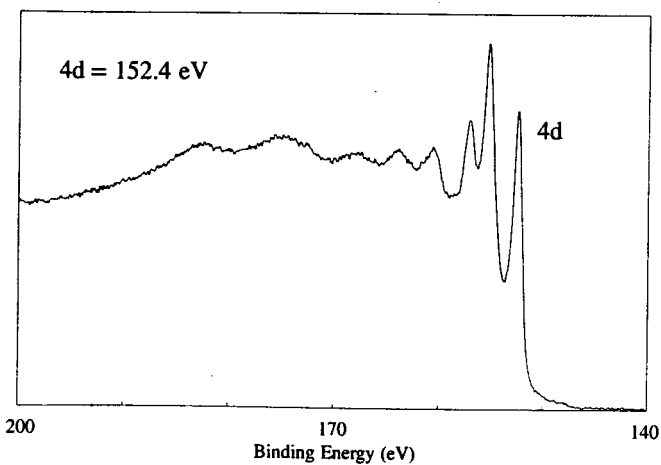
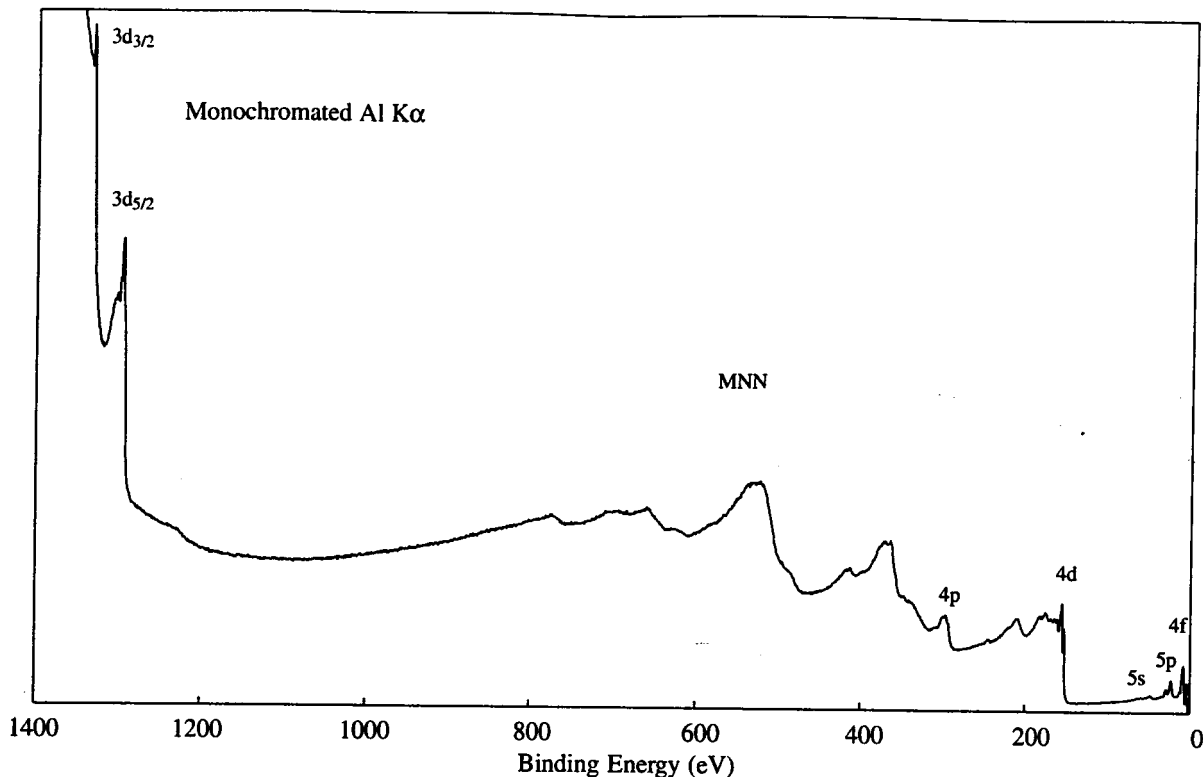
Line Positions (eV)						
<u>Photoelectron Lines</u>						
3d _{3/2}	3d _{5/2}					
1276	1241					
4s	4p _{1/2}	4p _{3/2}	4d	5s	5p	4f
396	322	285	146	45	22	8
<u>Auger Lines</u>						
M ₄₅ N ₄₅ N ₄₅	M ₄₅ N ₄₅ V	M ₅ VV	M ₄ VV			
559	411	260	230			(Al)
326	178					(Mg)



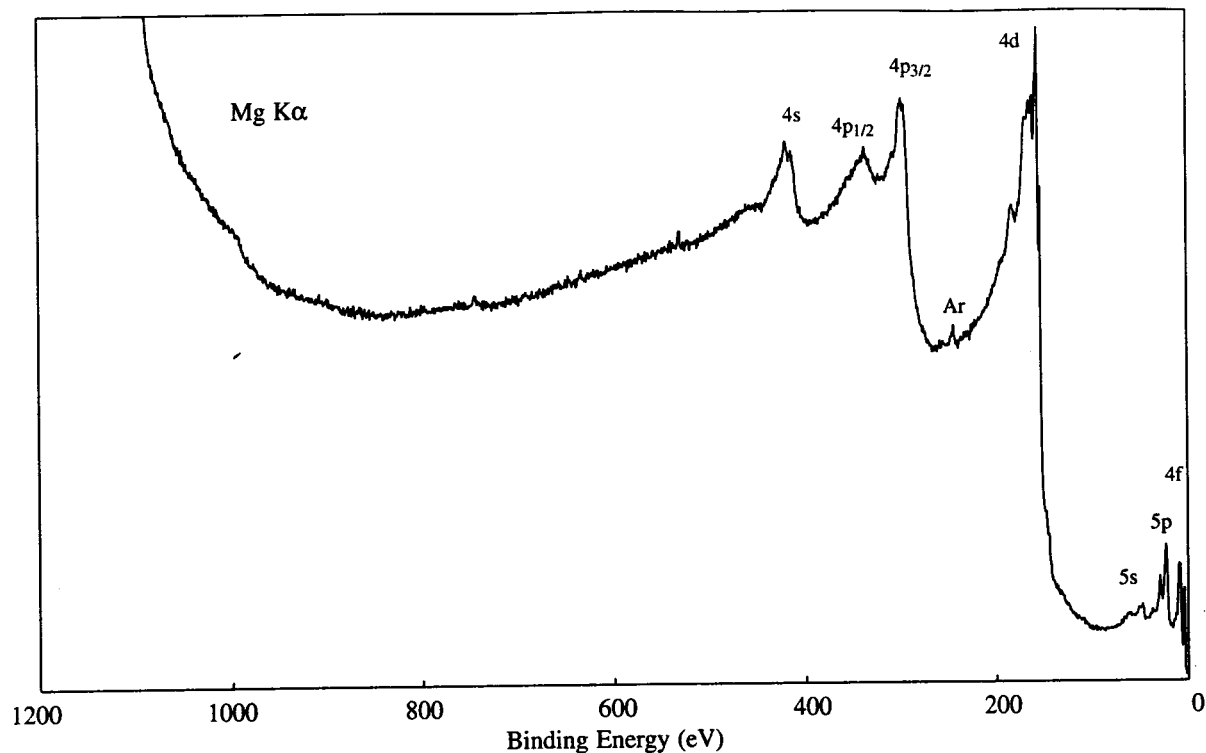
4d Binding Energy (eV)					
Compound Type	145	146	147	148	149
Tb		■			
Tb ₂ O ₃			■		
TbO ₂					■

3d _{5/2} Binding Energy (eV)			
Compound Type	1240	1241	1242
Tb			■
Tb ₂ O ₃		■	
TbO ₂		■	



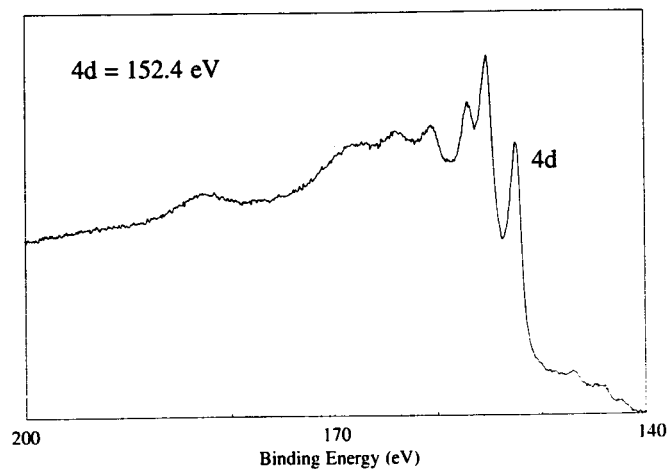


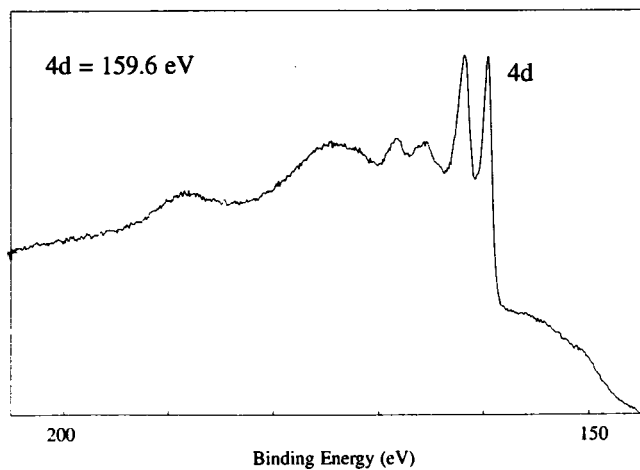
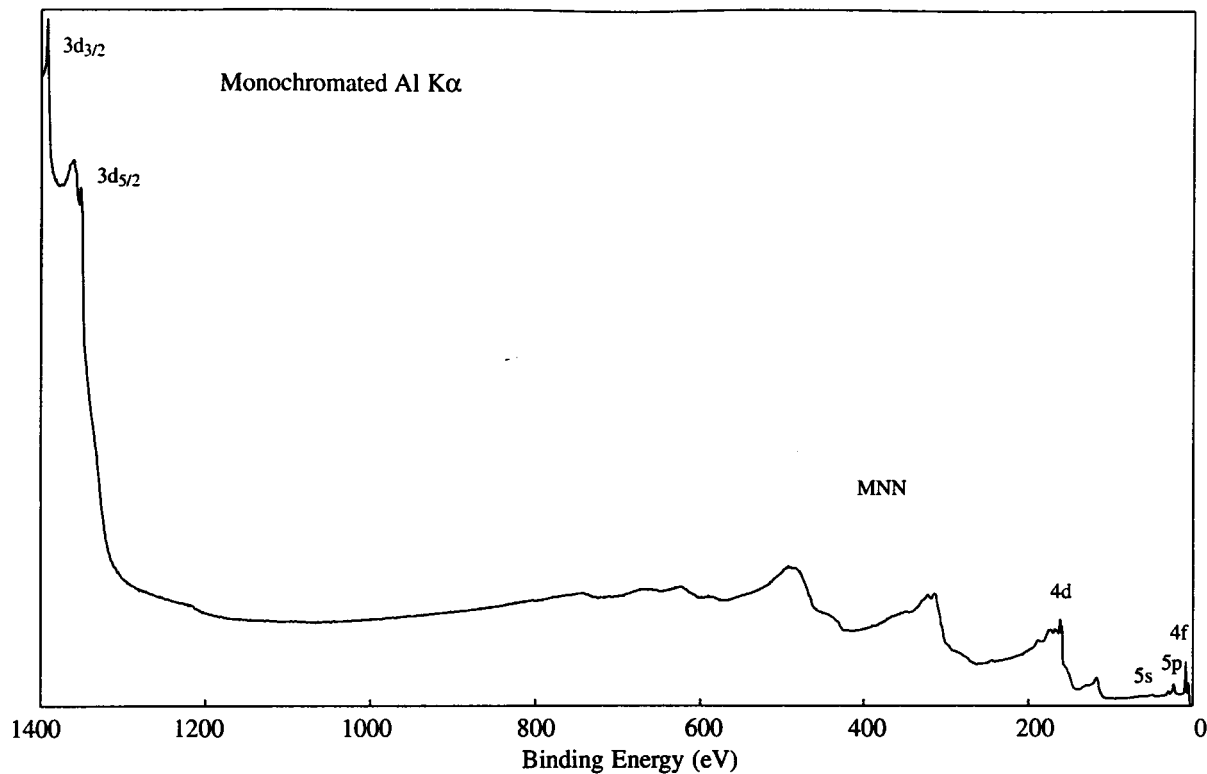
Line Positions (eV)						
<u>Photoelectron Lines</u>						
3d _{3/2}	3d _{5/2}					
1333	1296					
4s	4p _{1/2}	4p _{3/2}	4d	5s	5p	4f
417	337	297	152	48	23	8
<u>Auger Lines</u>						
M ₄₅ N ₄₅ N ₄₅	M ₄₅ N ₄₅ V					
526	368					(Al)



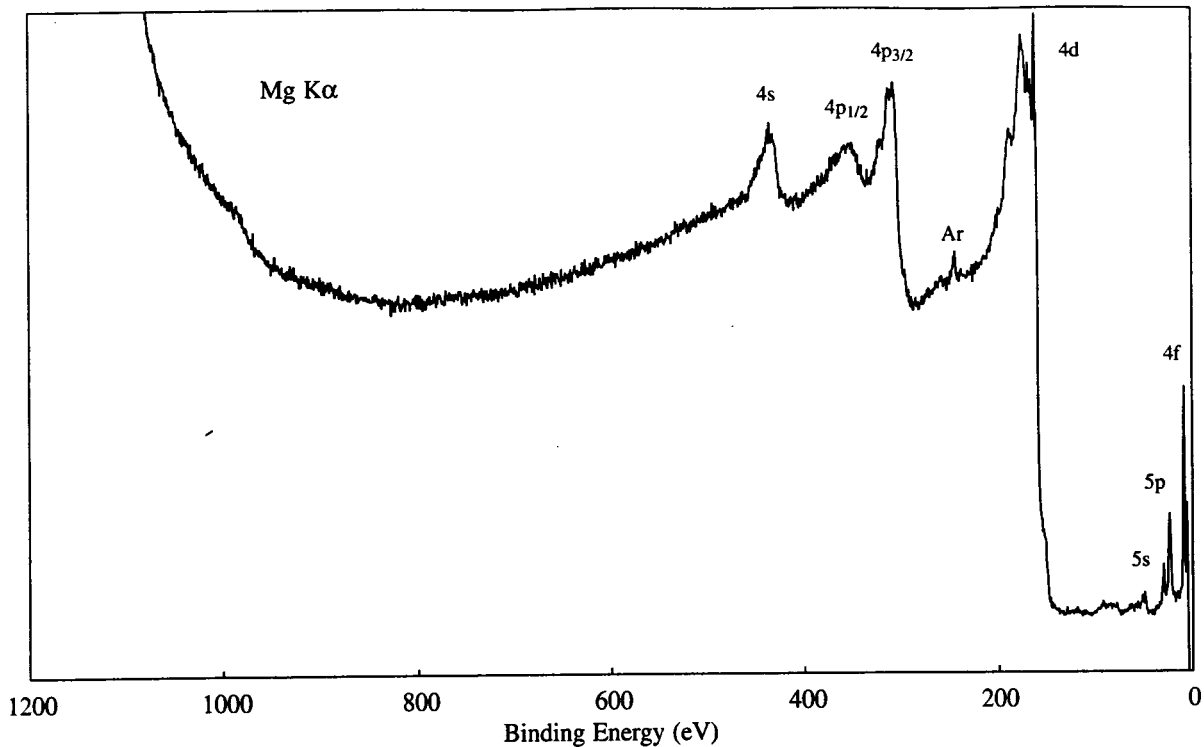
4d Binding Energy (eV)					
Compound Type	152	156	160	164	168
Dy Dy ₂ O ₃	■				■

3d _{5/2} Binding Energy (eV)					
Compound Type	1287	1289	1291	1293	1295
Dy Dy ₂ O ₃		■			■

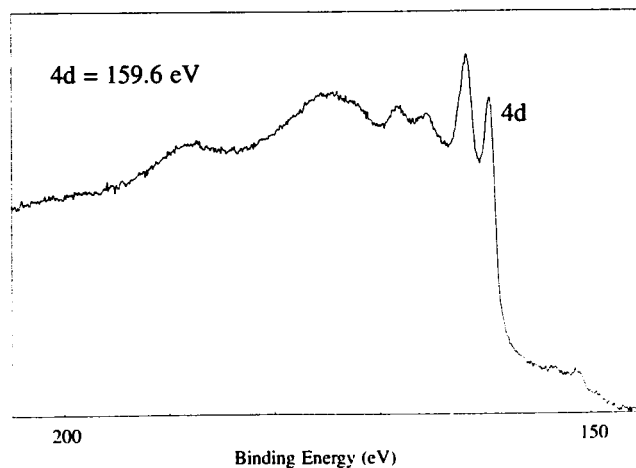


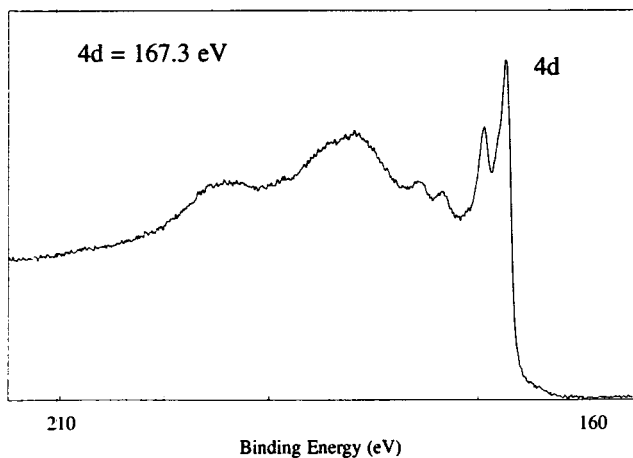
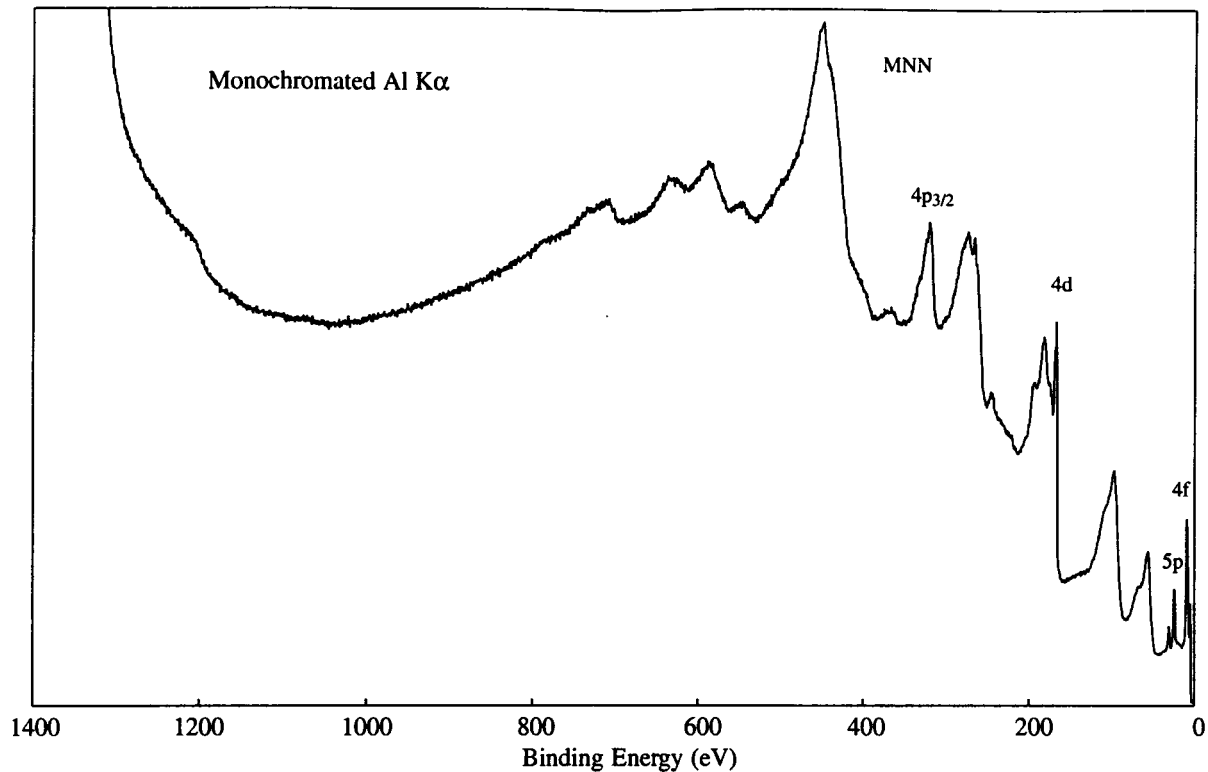


Line Positions (eV)					
Photoelectron Lines					
3d _{3/2}	3d _{5/2}	4s	4p _{1/2}	4p _{3/2}	4d
1393	1352	435	353	309	160
5s	5p _{1/2}	5p _{3/2}	4f		
49	30	24	9		
Auger Lines					
M ₄₅ N ₄₅ N ₄₅		M ₄₅ N ₄₅ V		M ₄ VV	
488		314		117 (Al)	

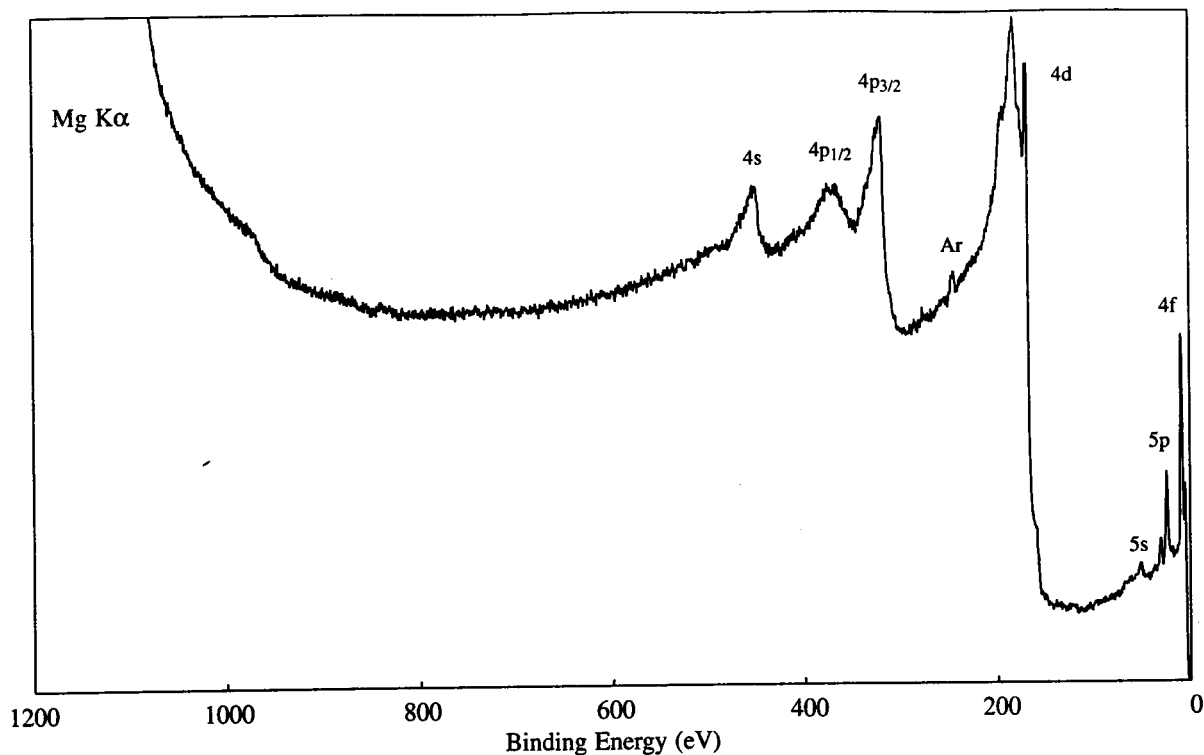


4d Binding Energy (eV)			
Compound Type	158	159	160
Ho		██████	

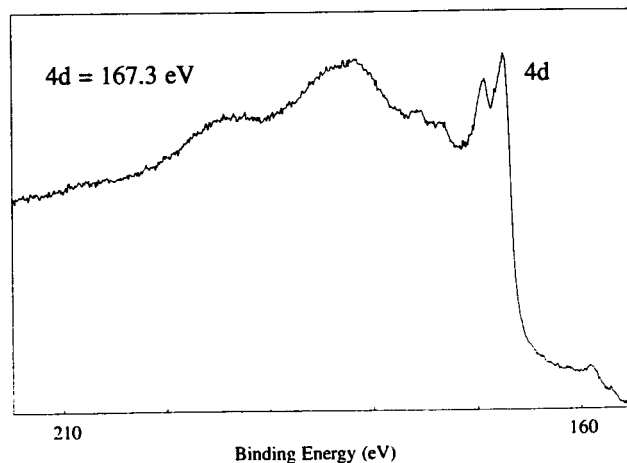


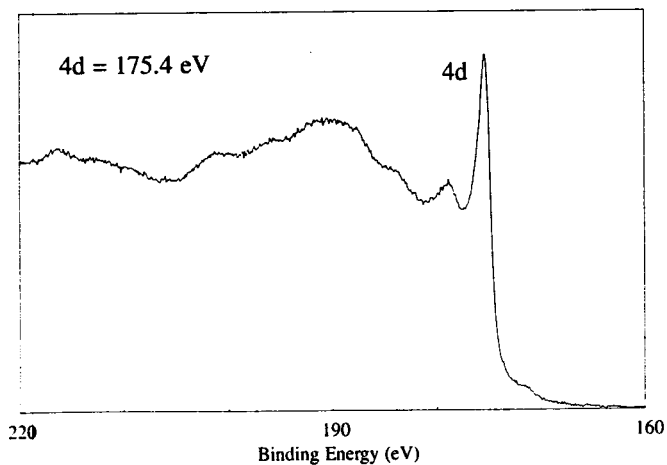
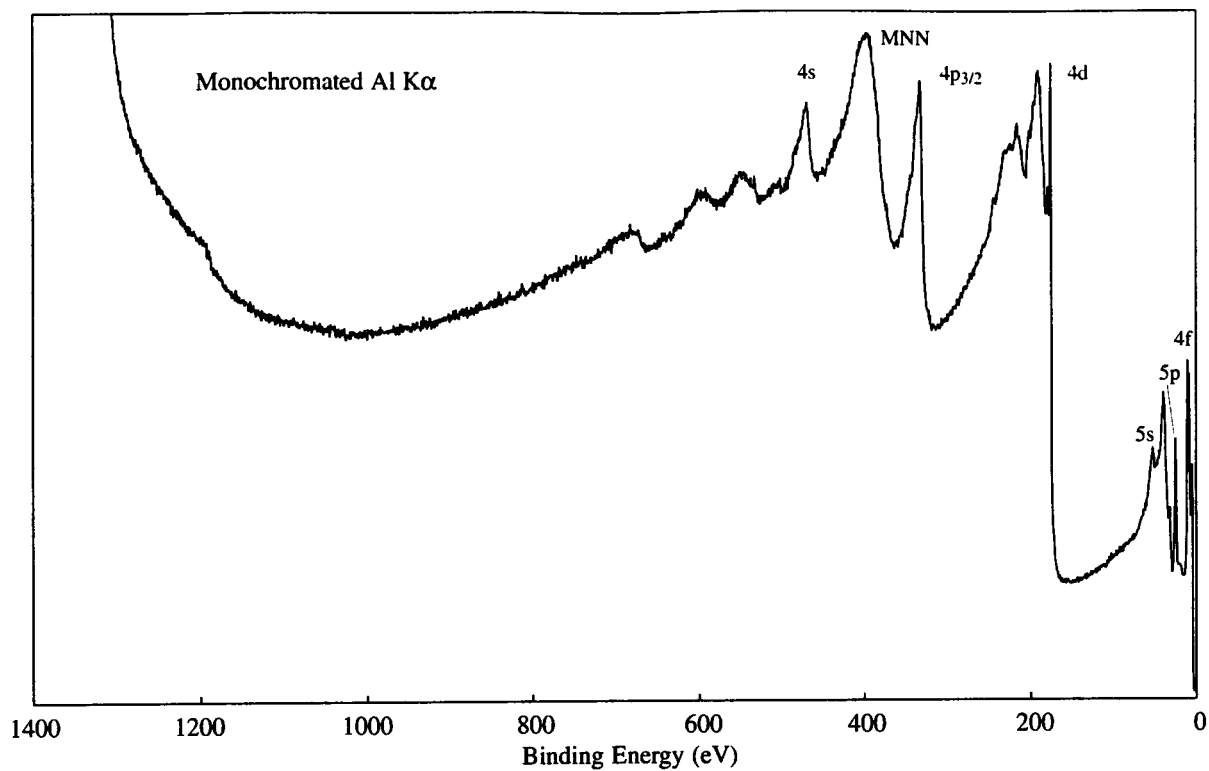


Line Positions (eV)							
<u>Photoelectron Lines</u>							
4s	4p _{1/2}	4p _{3/2}	4d	5s	5p _{1/2}	5p _{3/2}	4f
451	368	321	167	52	31	24	9
<u>Auger Lines</u>							
M ₄₅ N ₄₅ N ₄₅	M ₄₅ N ₄₅ V	M ₅ VV	M ₄ VV	(Al)			
440	273	98	56				

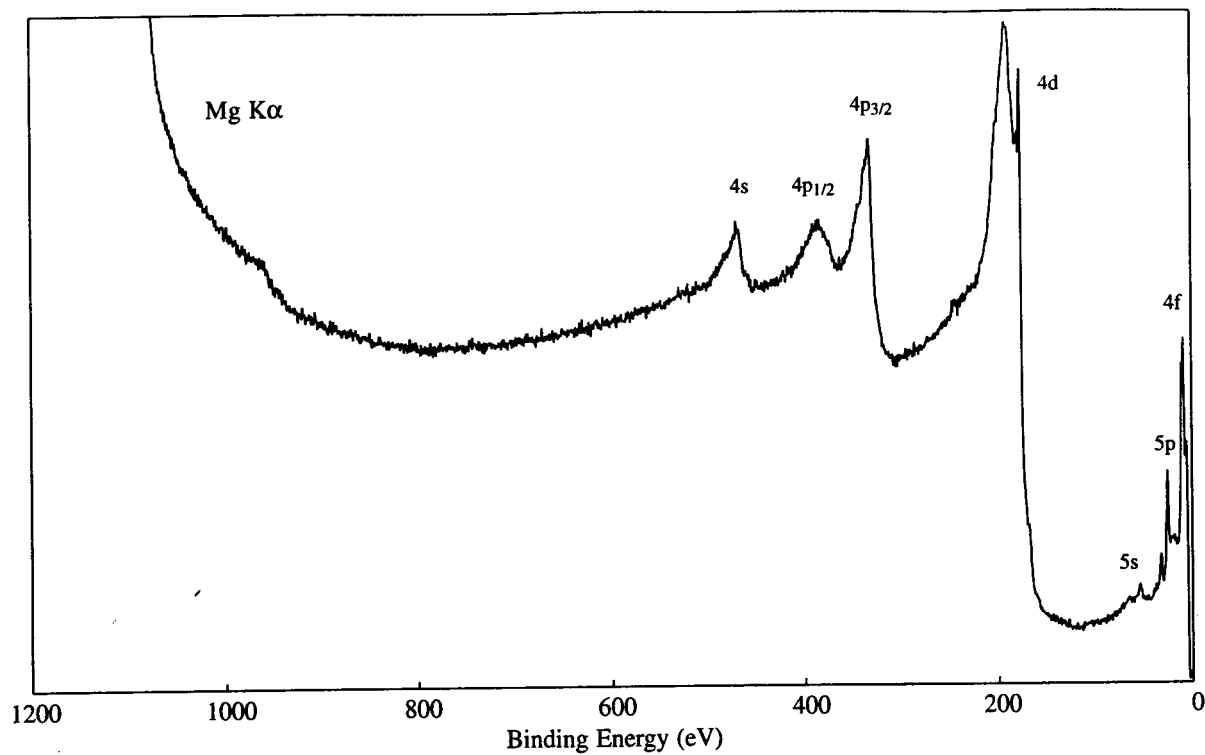


4d Binding Energy (eV)			
Compound Type	167	168	169
Er	■		
Er			■
Er ₂ O ₃		■	■

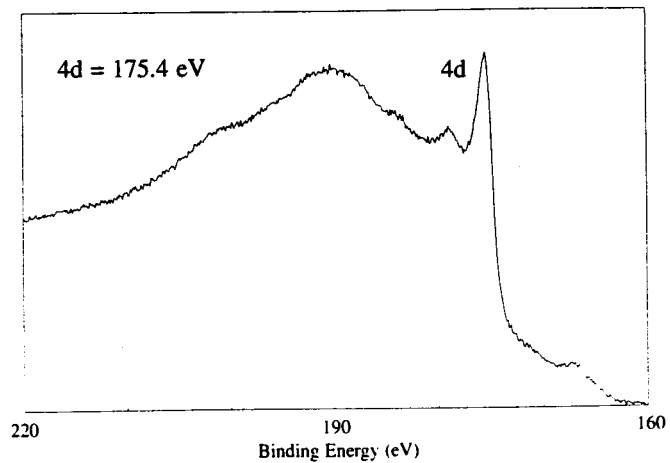


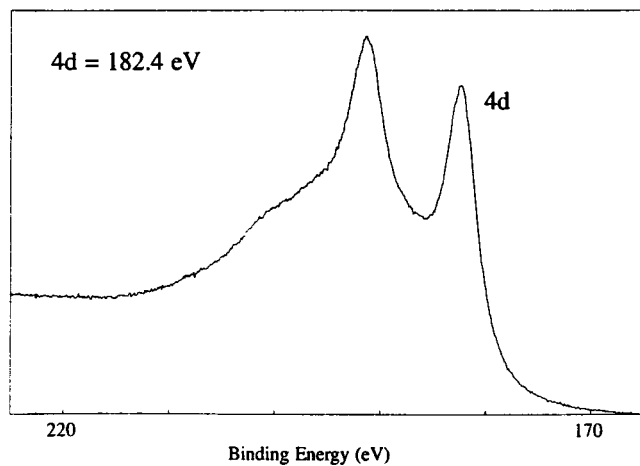
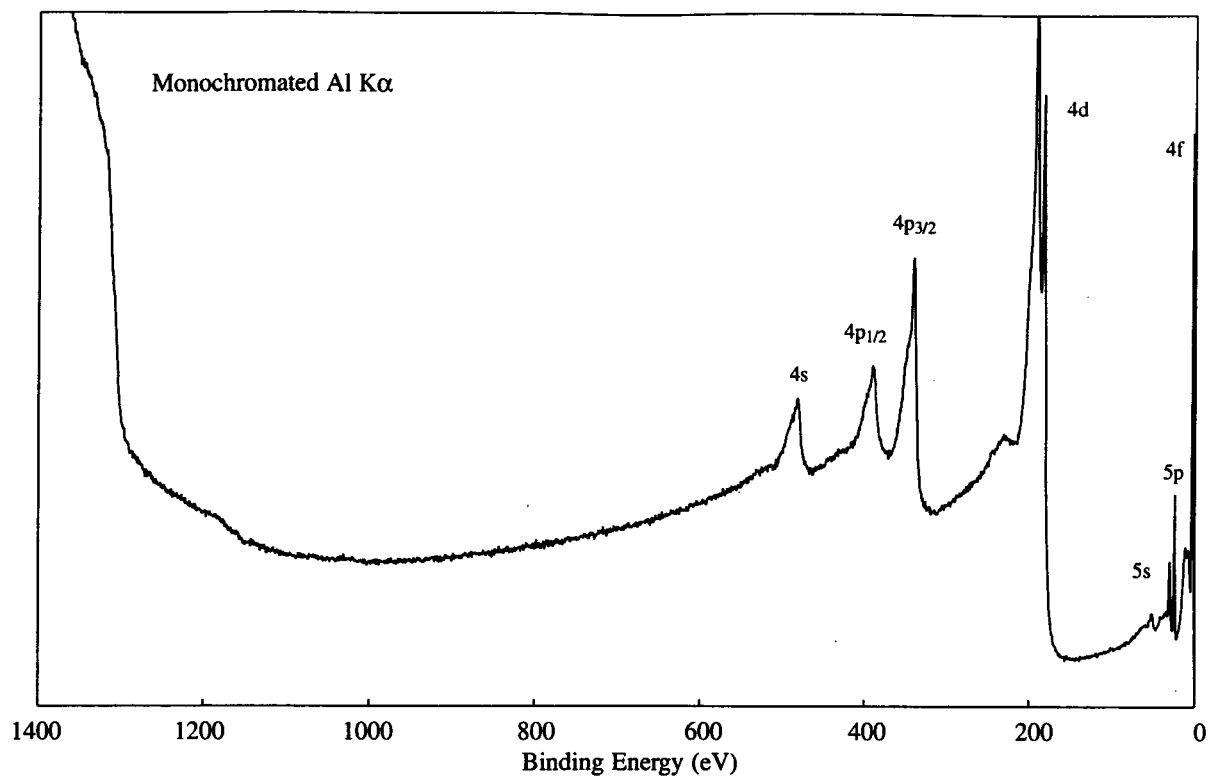


Line Positions (eV)							
<u>Photoelectron Lines</u>							
4s	4p _{1/2}	4p _{3/2}	4d	5s	5p _{1/2}	5p _{3/2}	4f
470	384	333	175	53	32	25	8
<u>Auger Lines</u>							
M ₄₅ N ₄₅ N ₄₅							
398 (Al)							

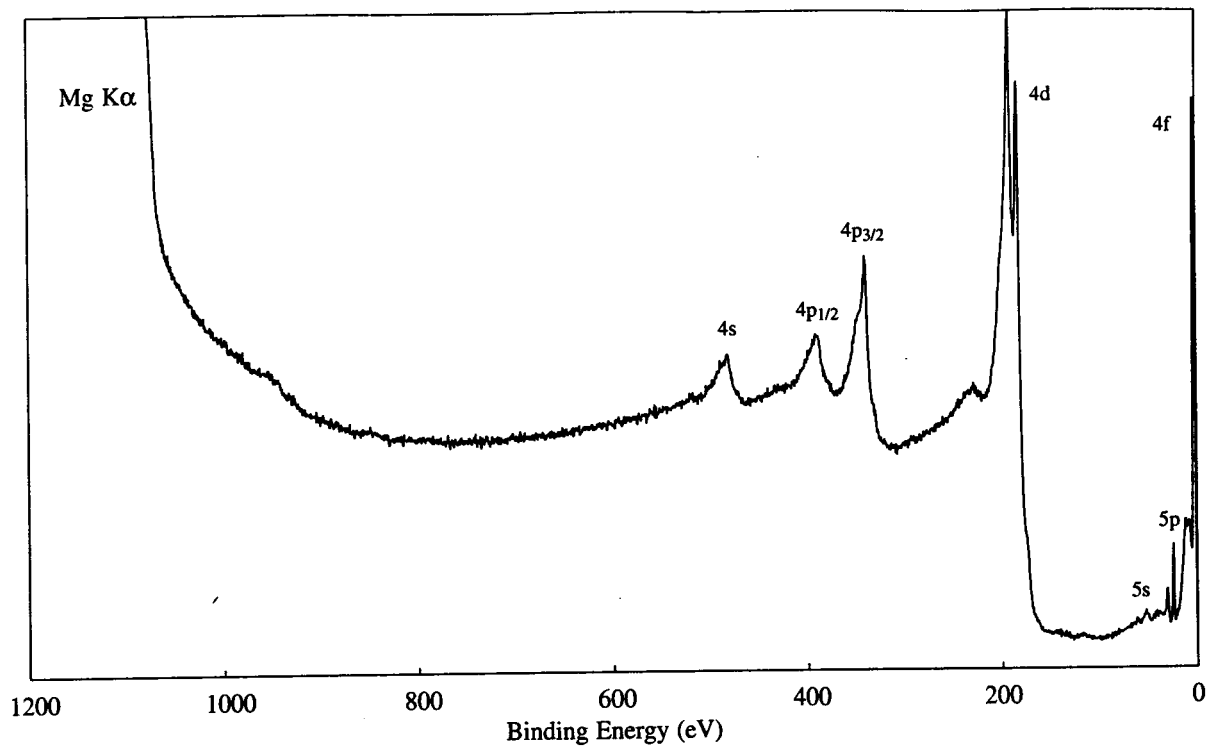


4d Binding Energy (eV)			
Compound Type	174	175	176
Tm			

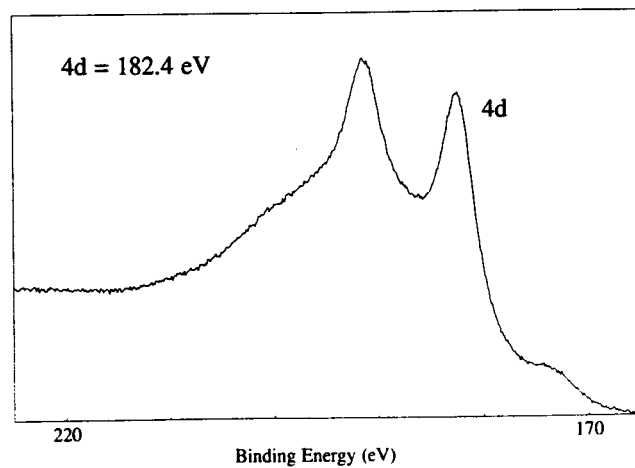


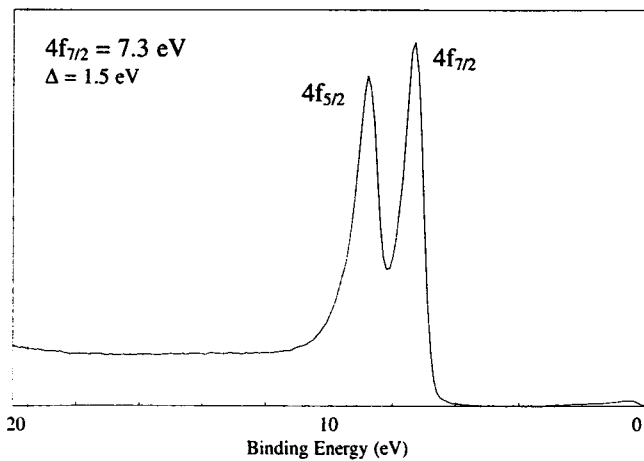
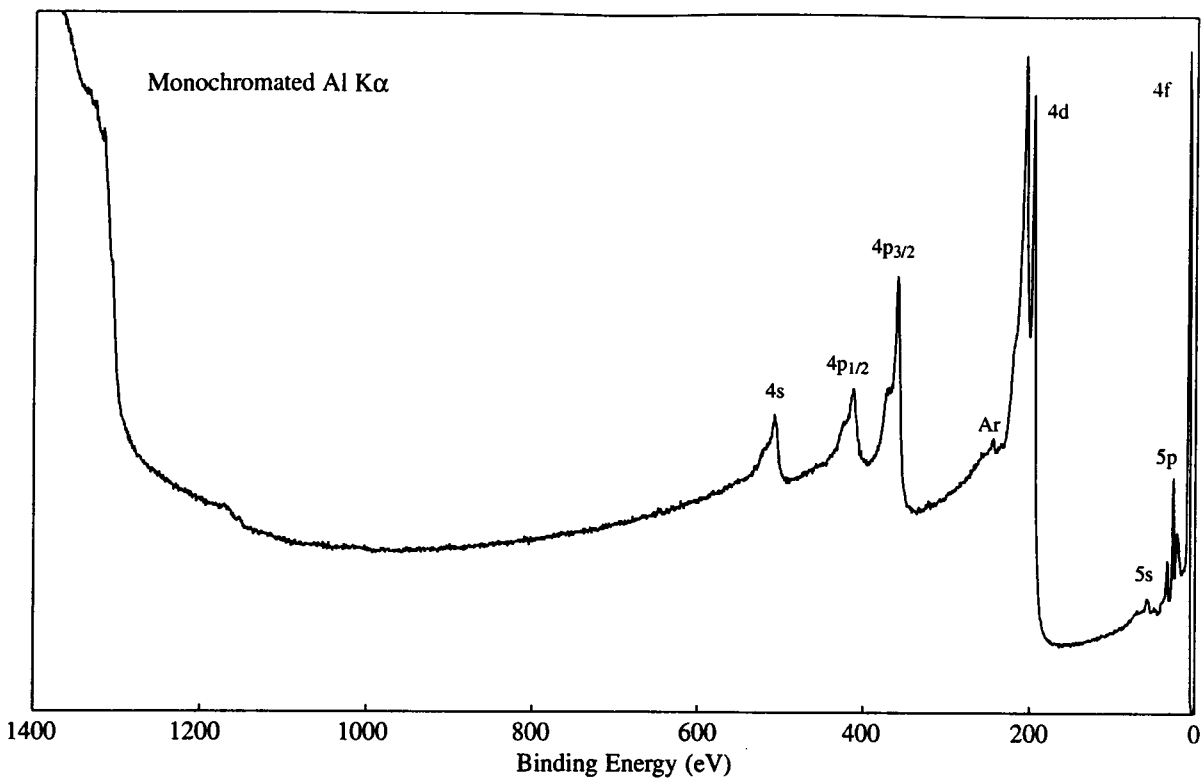


Line Positions (eV)							
Photoelectron Lines							
4s	4p _{1/2}	4p _{3/2}	4d	5s	5p _{1/2}	5p _{3/2}	4f
482	389	341	182	51	30	24	3

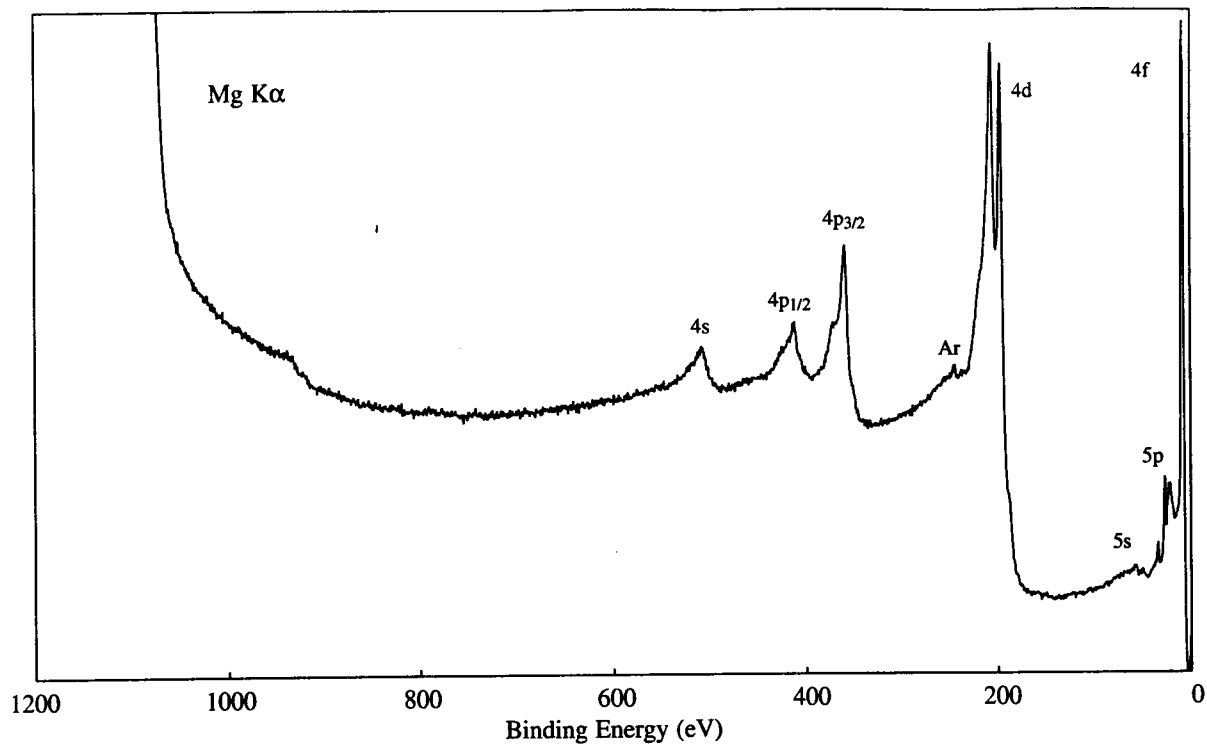


4d Binding Energy (eV)						
Compound Type	181	182	183	184	185	186
Yb		■				
Yb ₂ O ₃					■	

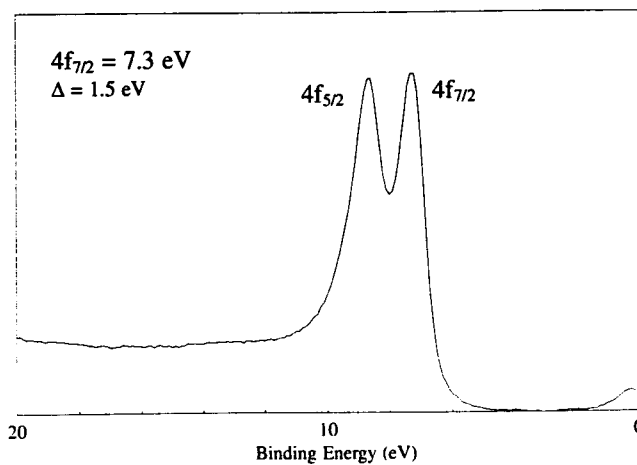


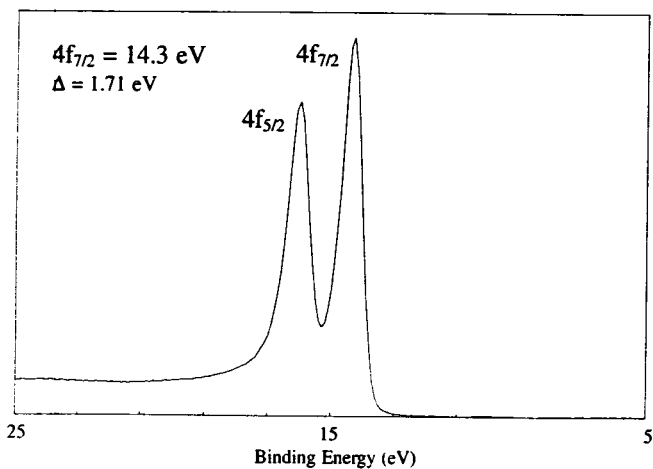
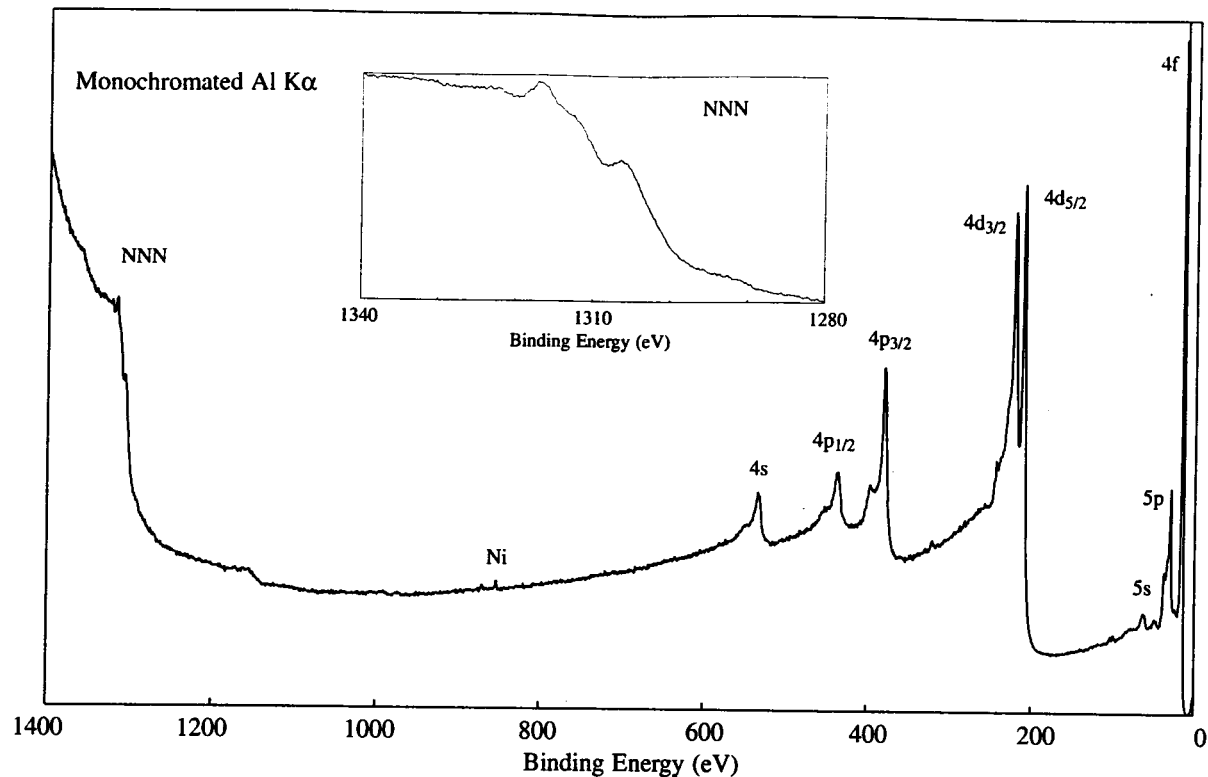


Line Positions (eV)				
Photoelectron Lines				
4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}
509	413	360	206	196
5s	5p _{1/2}	5p _{3/2}	4f _{5/2}	4f _{7/2}
57	34	27	9	7

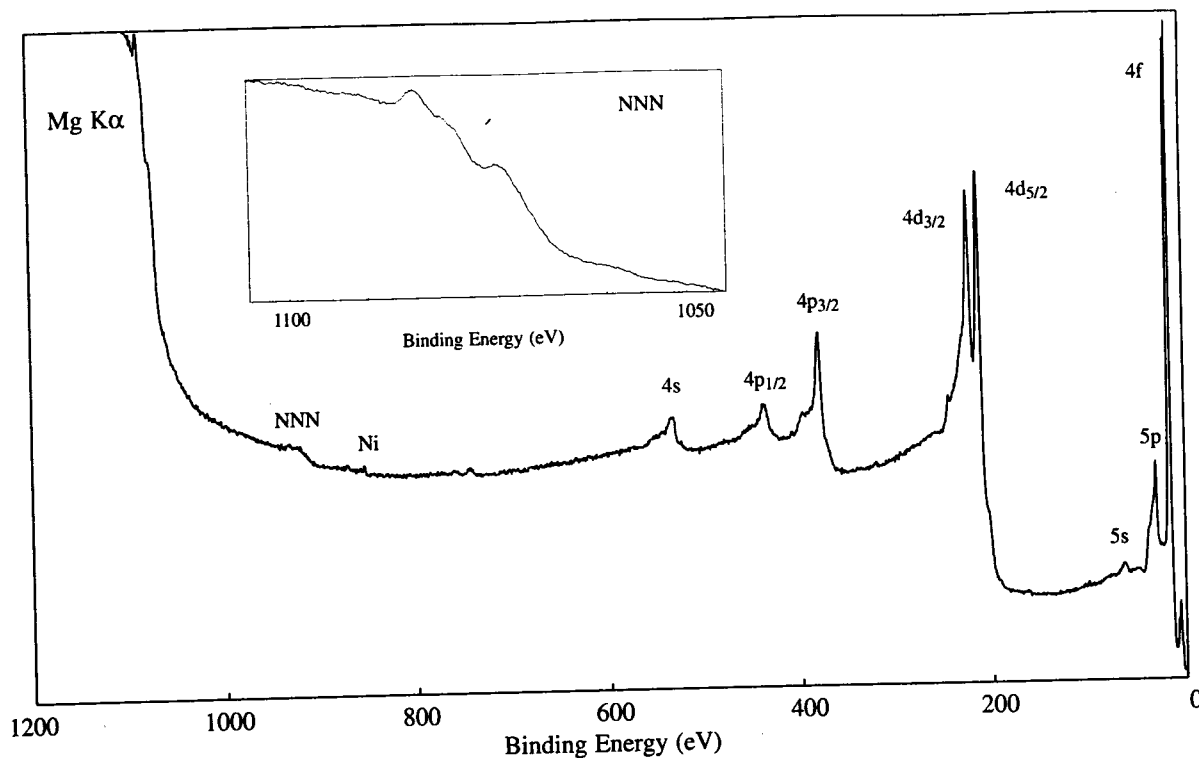


4f _{7/2} Binding Energy (eV)					
Compound Type	5	6	7	8	9
Lu					



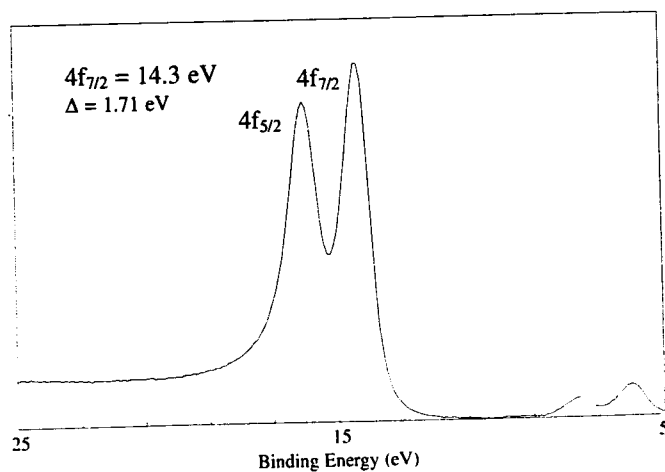


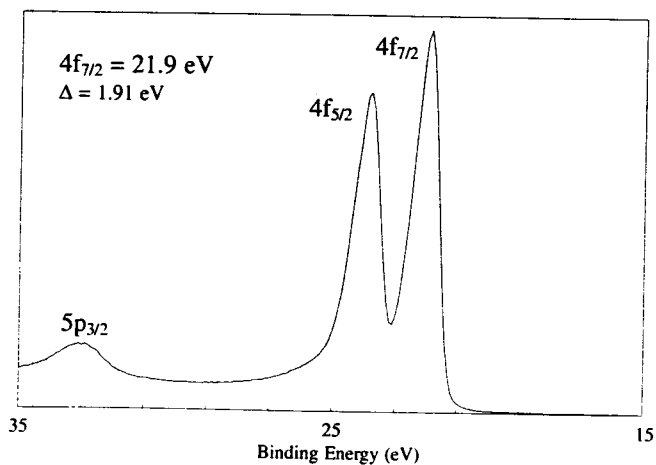
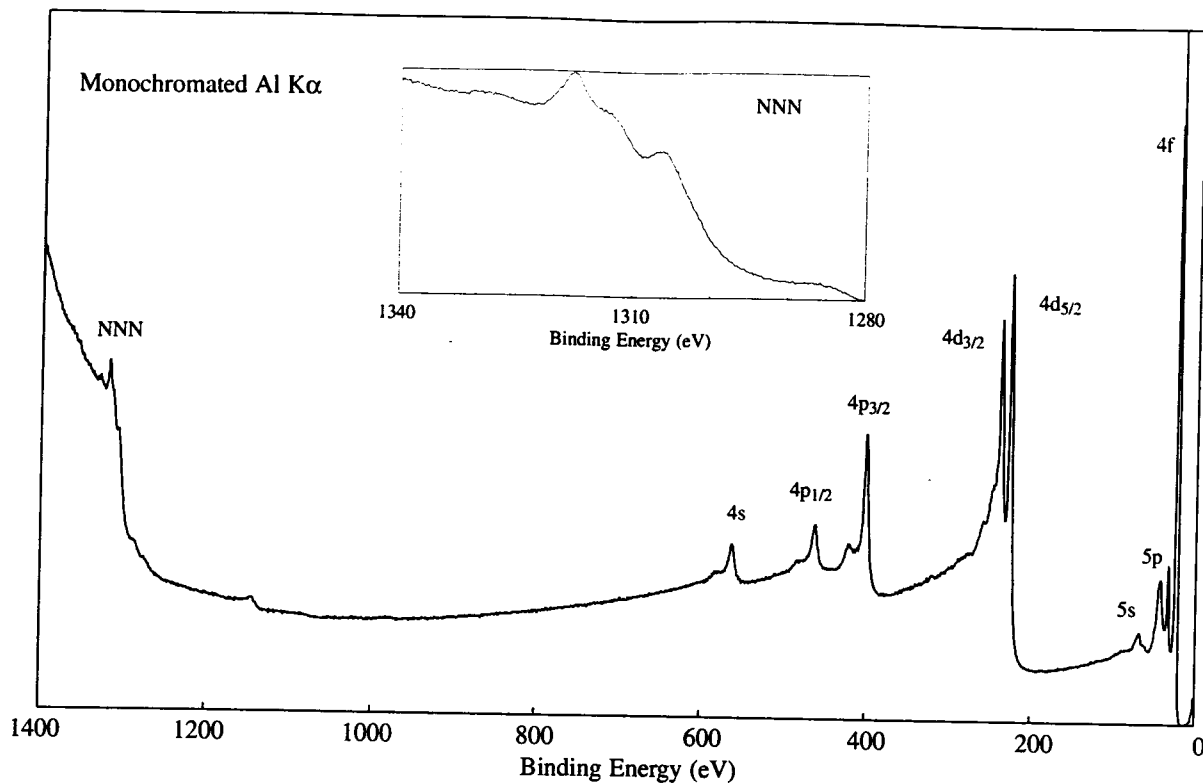
Line Positions (eV)				
Photoelectron Lines				
4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}
534	437	380	222	211
5s	5p _{1/2}	5p _{3/2}	4f _{5/2}	4f _{7/2}
63	38	30	16	14
Auger Lines				
N ₅ N ₆₇ N ₇		N ₄ N ₆₇ N ₇		
1317		1306		(Al)
1084		1073		(Mg)



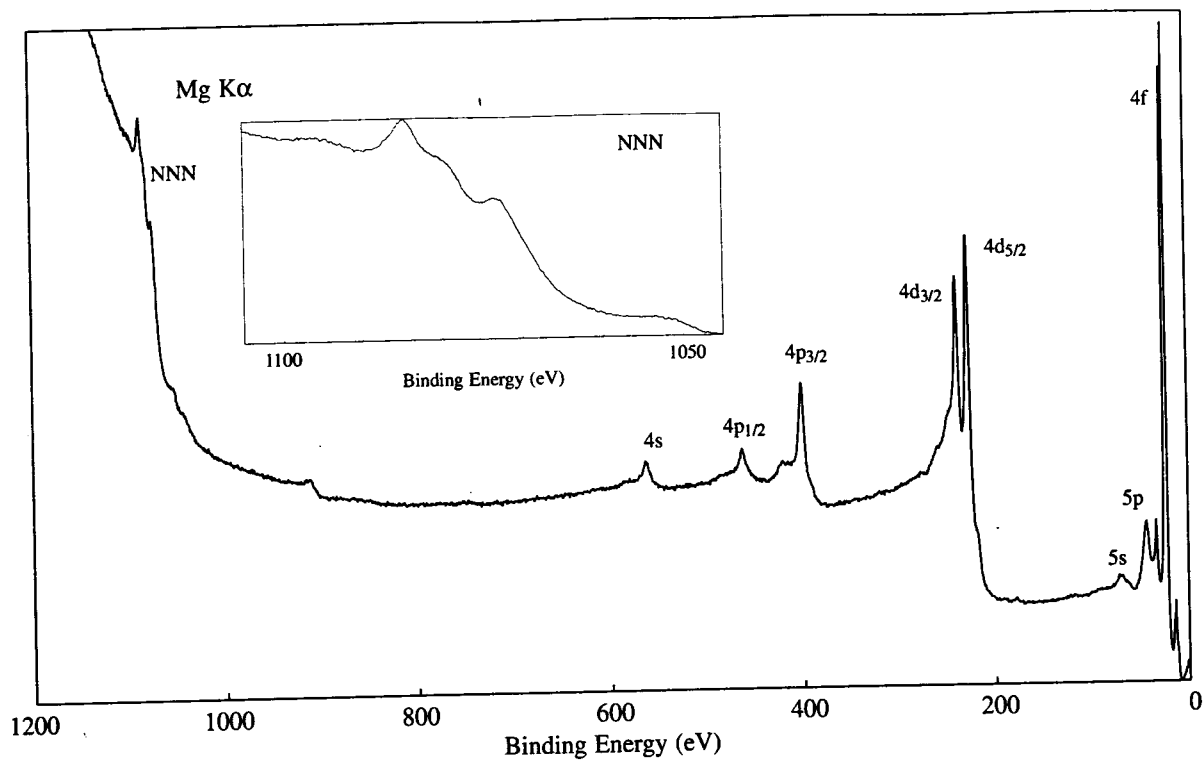
4f _{7/2} Binding Energy (eV)			
Compound Type	14	15	16
Hf	████████		
HfO ₂			████████

4d _{5/2} Binding Energy (eV)			
Compound Type	212	213	214
Hf		████████	
HfO ₂	████████		

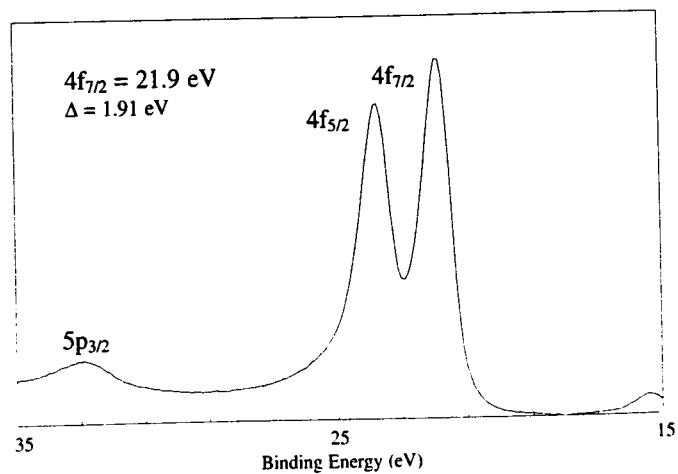


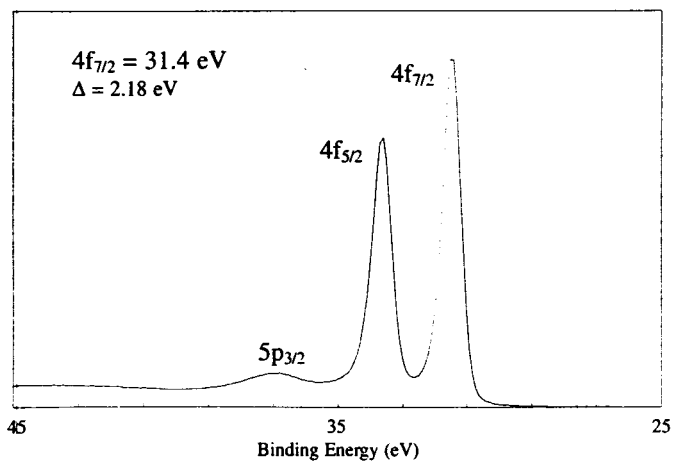
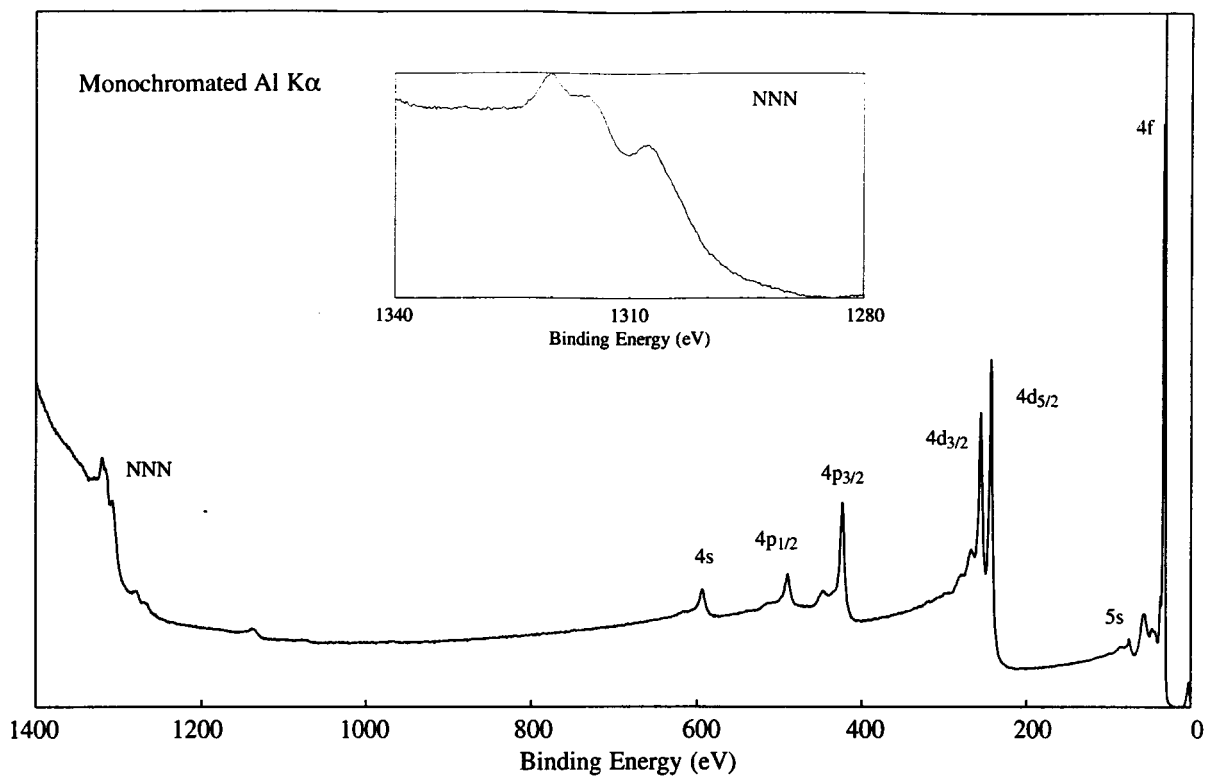


Line Positions (eV)				
Photoelectron Lines				
4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}
563	463	401	238	226
5s	5p _{1/2}	5p _{3/2}	4f _{5/2}	4f _{7/2}
69	43	33	24	22
Auger Lines				
N ₅ N ₆₇ N ₇		N ₄ N ₆₇ N ₇		
1318		1306 (Al)		
1085		1073 (Mg)		

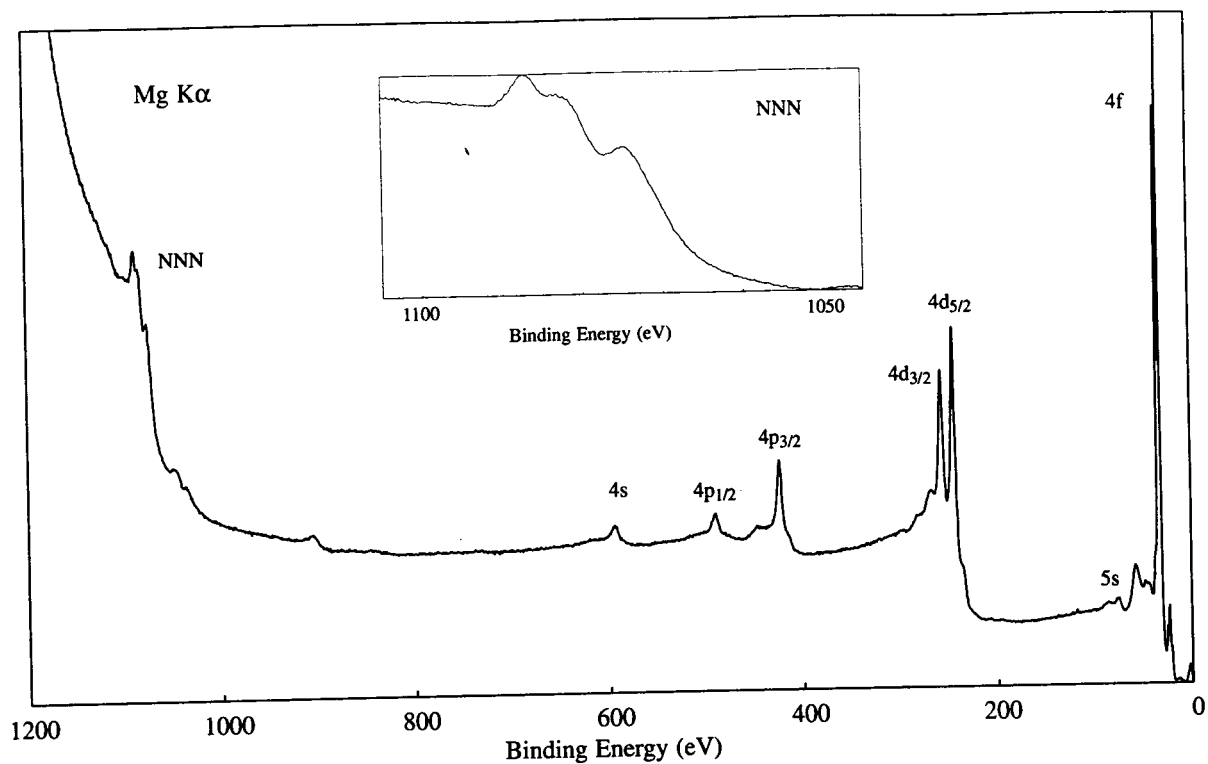


Compound Type	4f $_{7/2}$ Binding Energy (eV)							
	21	22	23	24	25	26	27	28
Ta		■						
TaS							■	
TaS $_2$							■	
Halides							■	■
Ta $_2$ O $_5$							■	■
Br $_6$ (Ta $_6$ Cl $_{12}$)(Bu $_4$ N) $_2$							■	■
Cl $_6$ (Ta $_6$ Cl $_{12}$)(Et $_4$ N) $_2$							■	■

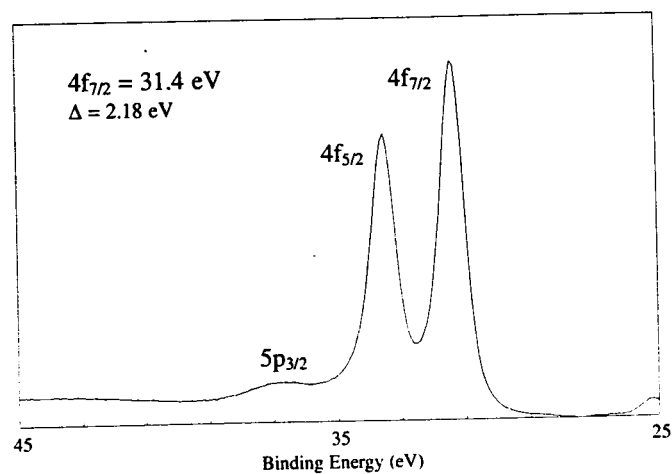


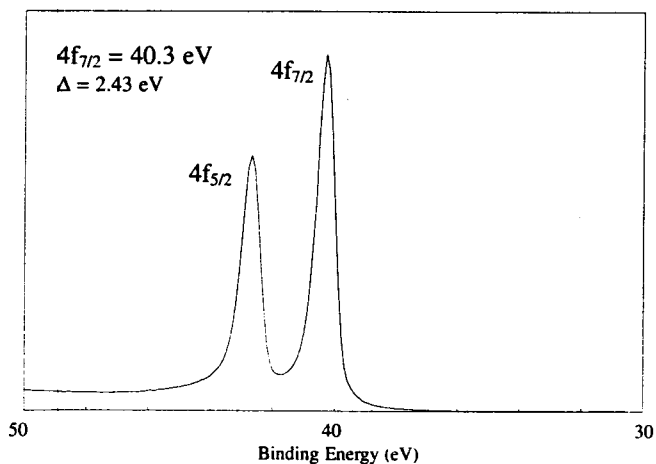
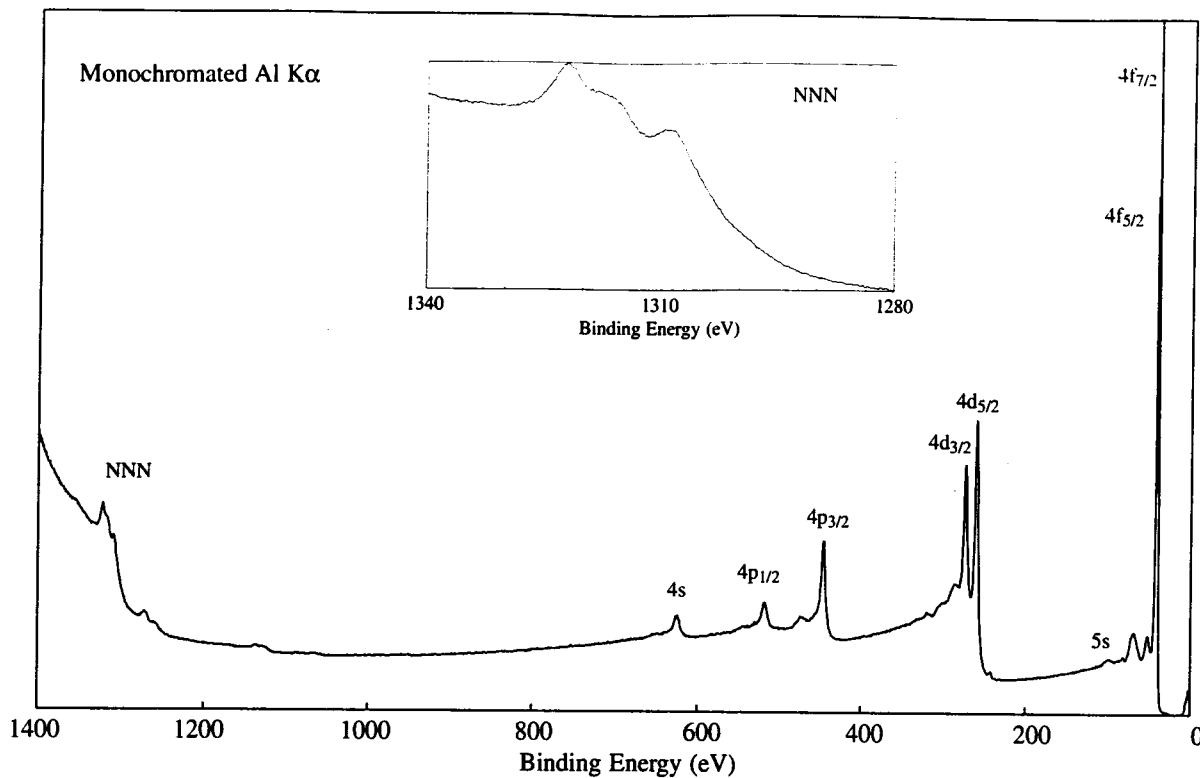


Line Positions (eV)				
Photoelectron Lines				
4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}
594	491	424	256	243
5s	5p _{1/2}	5p _{3/2}	4f _{5/2}	4f _{7/2}
75	47	37	33	31
Auger Lines				
N ₅ N ₆₇ N ₇		N ₄ N ₆₇ N ₇		
1320		1307 (Al)		
1087		1074 (Mg)		

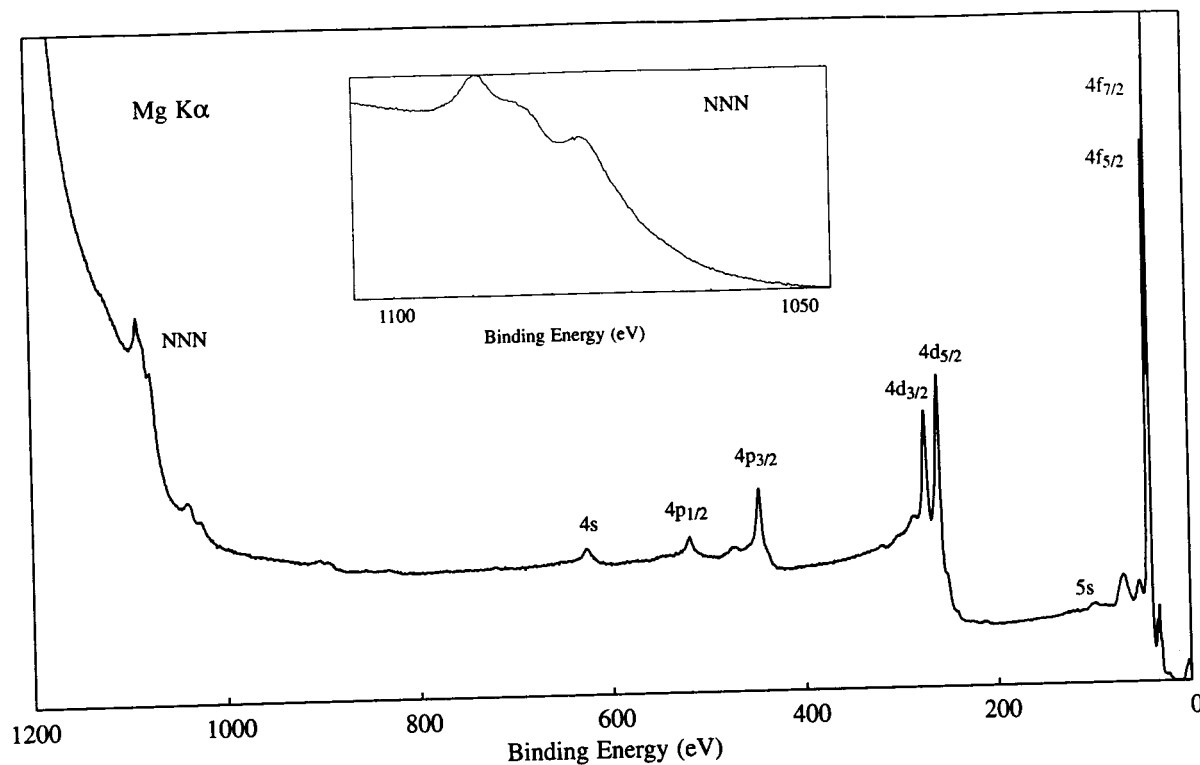


Compound Type	4f _{7/2} Binding Energy (eV)							
	31	32	33	34	35	36	37	38
W	■							
WC	■	■						
WS ₂			■					
Halides						■	■	
WOCl ₄								■
Oxides			■	■	■	■	■	
Tungstate					■	■	■	
Rh ₂ WO ₆						■		
Cl ₄ W(Et ₃ P) ₂					■			
Cl ₃ SnW(CO) ₃ (C ₅ H ₅)		■						
Ph ₃ PW(CO) ₅	■							

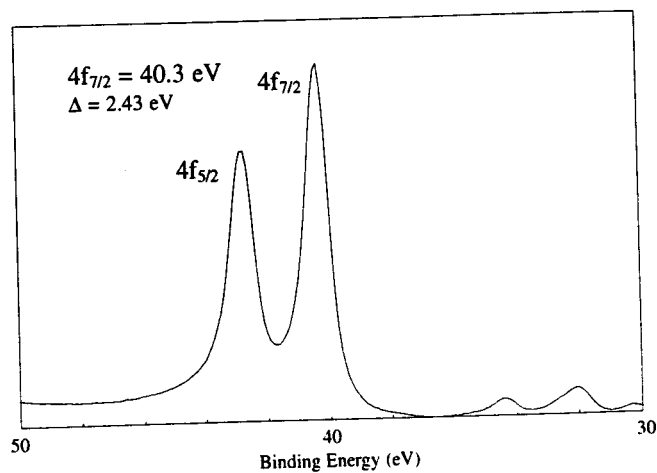


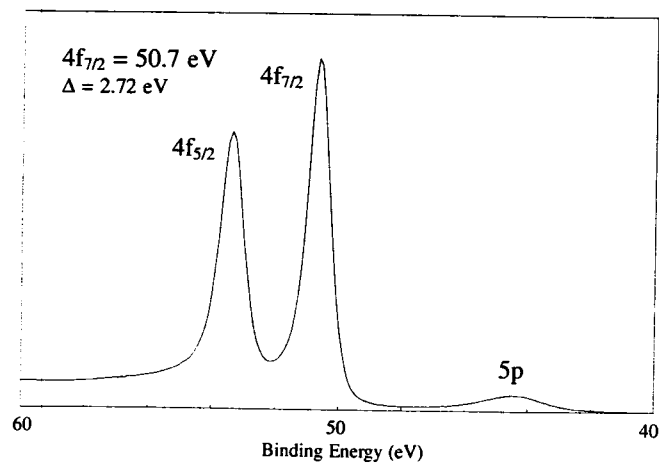
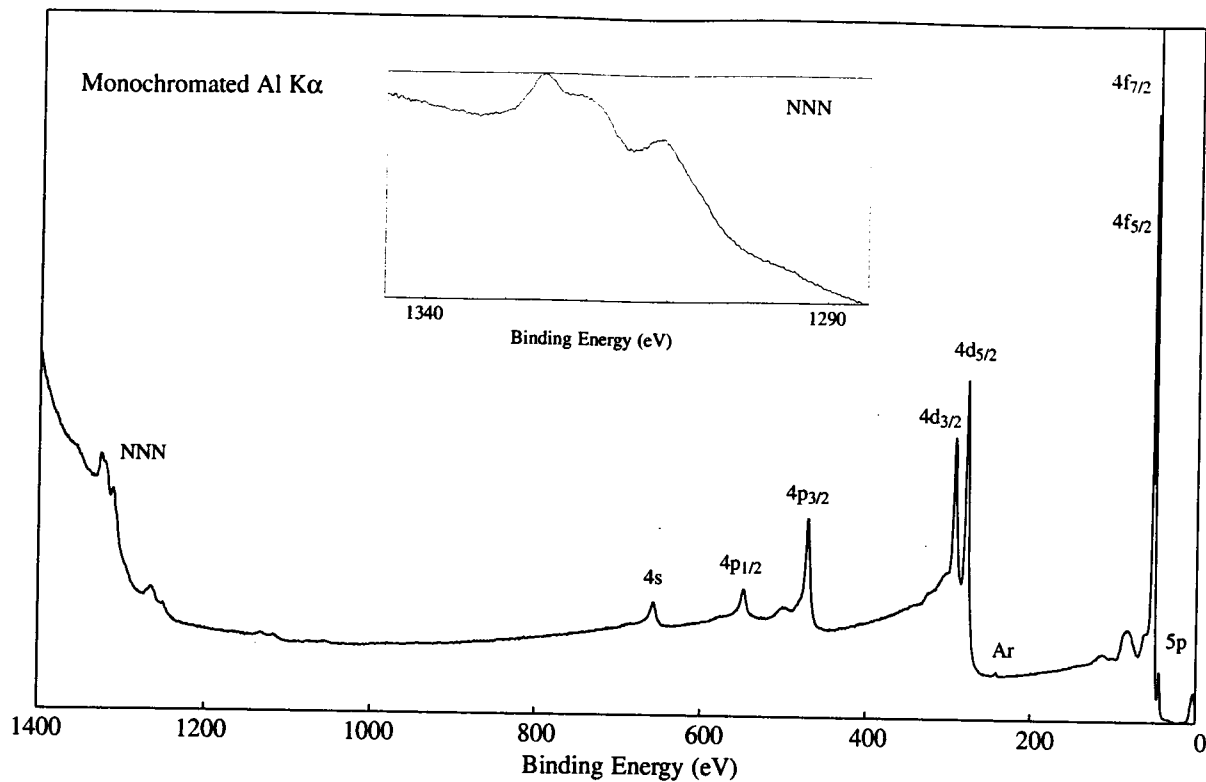


Line Positions (eV)							
<u>Photoelectron Lines</u>							
4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}	5s	4f _{5/2}	4f _{7/2}
625	518	446	274	260	99	42	40
<u>Auger Lines</u>							
N ₅ N ₆ N ₇		N ₄ N ₆ N ₇					
1322		1309 (Al)					
1089		1076 (Mg)					



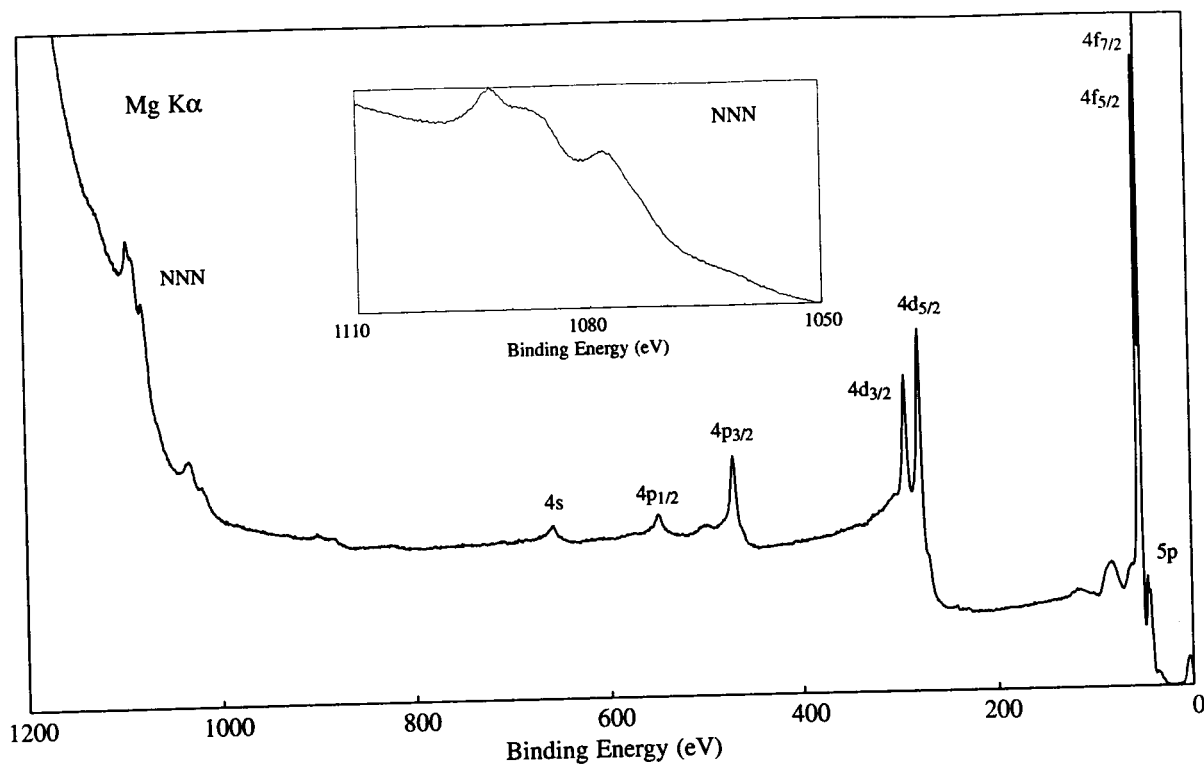
Compound Type	4f _{7/2} Binding Energy (eV)							
	40	41	42	43	44	45	46	47
Re	■							
ReO ₂					■			■
ReO ₃								
K ₂ ReCl ₆								
Cl ₃ ReO(Ph ₃ P) ₂								
Cl ₂ ReN(Ph ₃ P) ₂				■				
Cl ₄ Re(Et ₃ P) ₂					■			
Cl ₄ Re(PMe ₂ Ph) ₂				■				
Cl ₃ Re(PMe ₂ Ph) ₃ mer			■					
Cl ₂ Re(PMe ₂ Ph) ₄ trans		■						
ClReN ₂ (PMe ₂ Ph) ₄ trans	■							



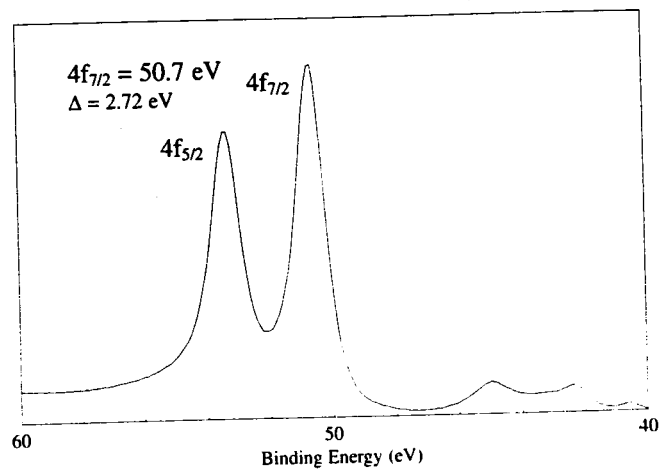


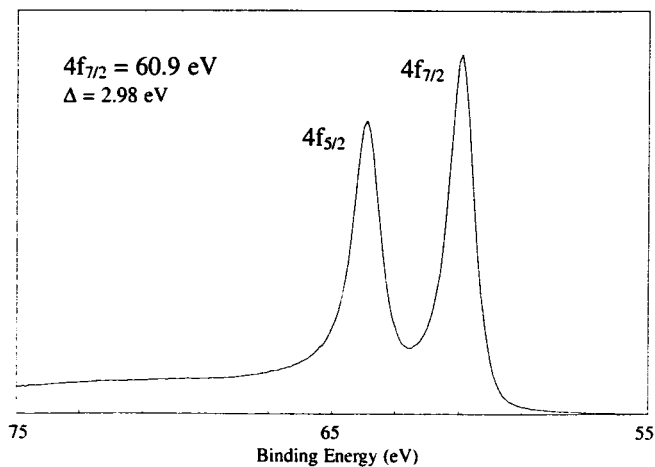
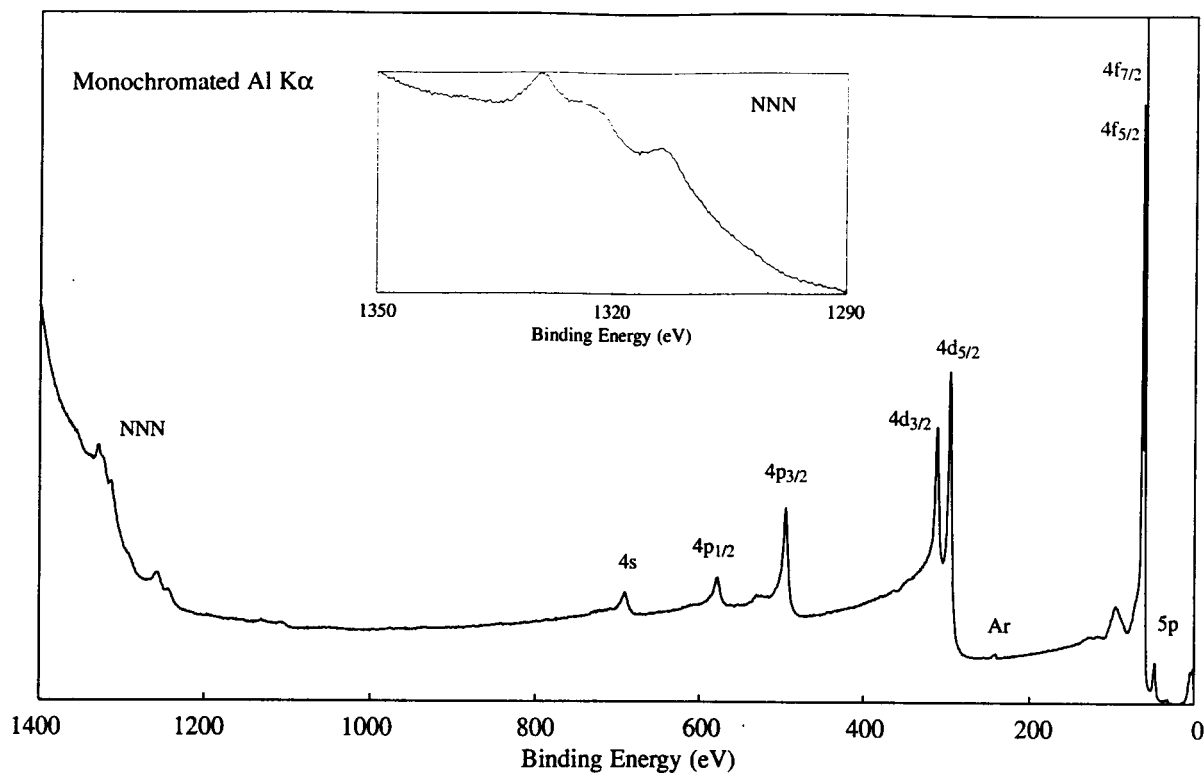
Line Positions (eV)				
Photoelectron Lines				
4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}
658	548	471	293	279
5s*	4f _{5/2}	4f _{7/2}	5p	
89	54	51	44	
Auger Lines				
N ₅ N ₆₇ N ₇		N ₄ N ₆₇ N ₇		
1326		1311		(Al)
1093		1078		(Mg)

*Estimate

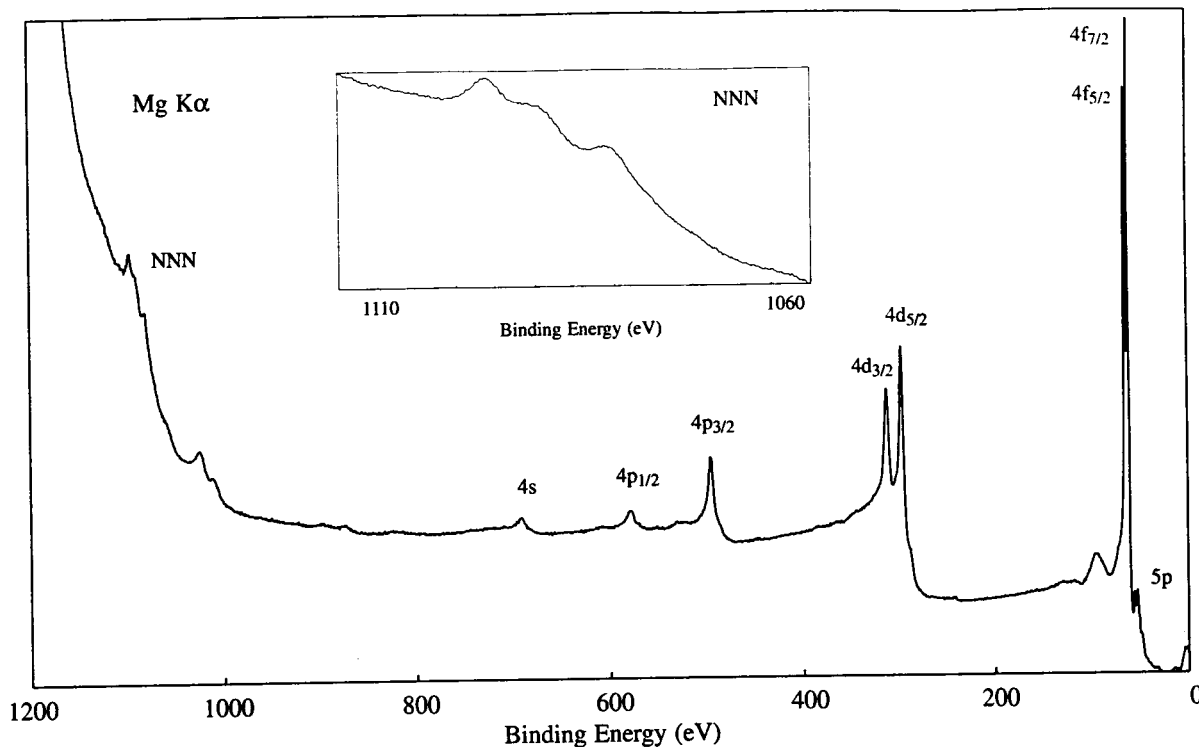


Compound Type	4f _{7/2} Binding Energy (eV)				
	50	51	52	53	54
Os	■				
OsO ₂			■	■	
K ₂ OsI ₆			■		
K ₂ OsBr ₆				■	
K ₂ OsCl ₆				■	■
OsCl ₄ (Et ₃ P) ₂				■	
OsCl ₄ (PhPMe ₂) ₂ trans				■	
OsCl ₃ (PhPMe ₂) ₃ mer			■		
OsCl ₂ (PhPMe ₂) ₄ trans	■				

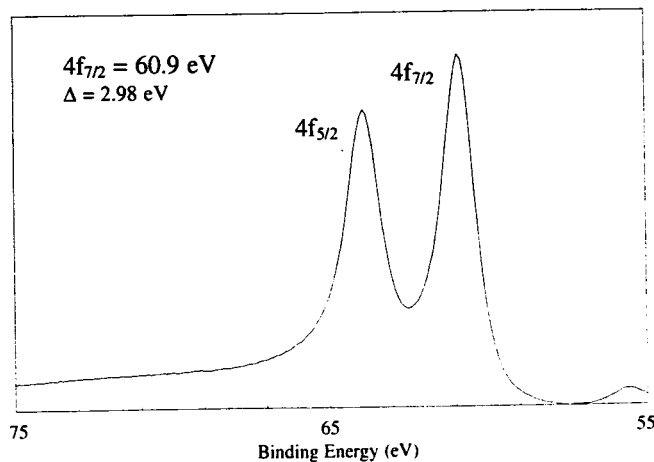


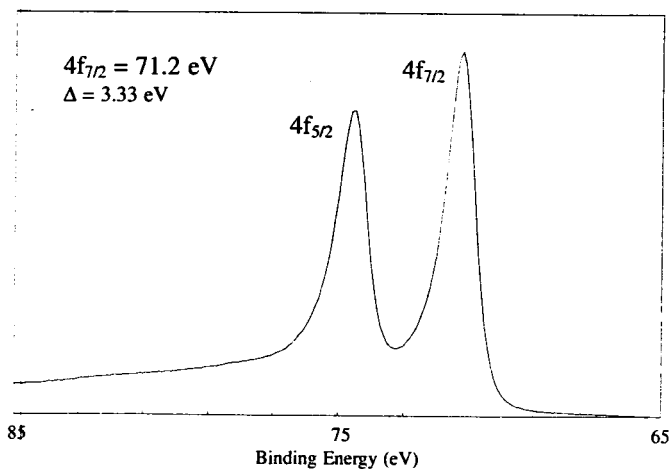
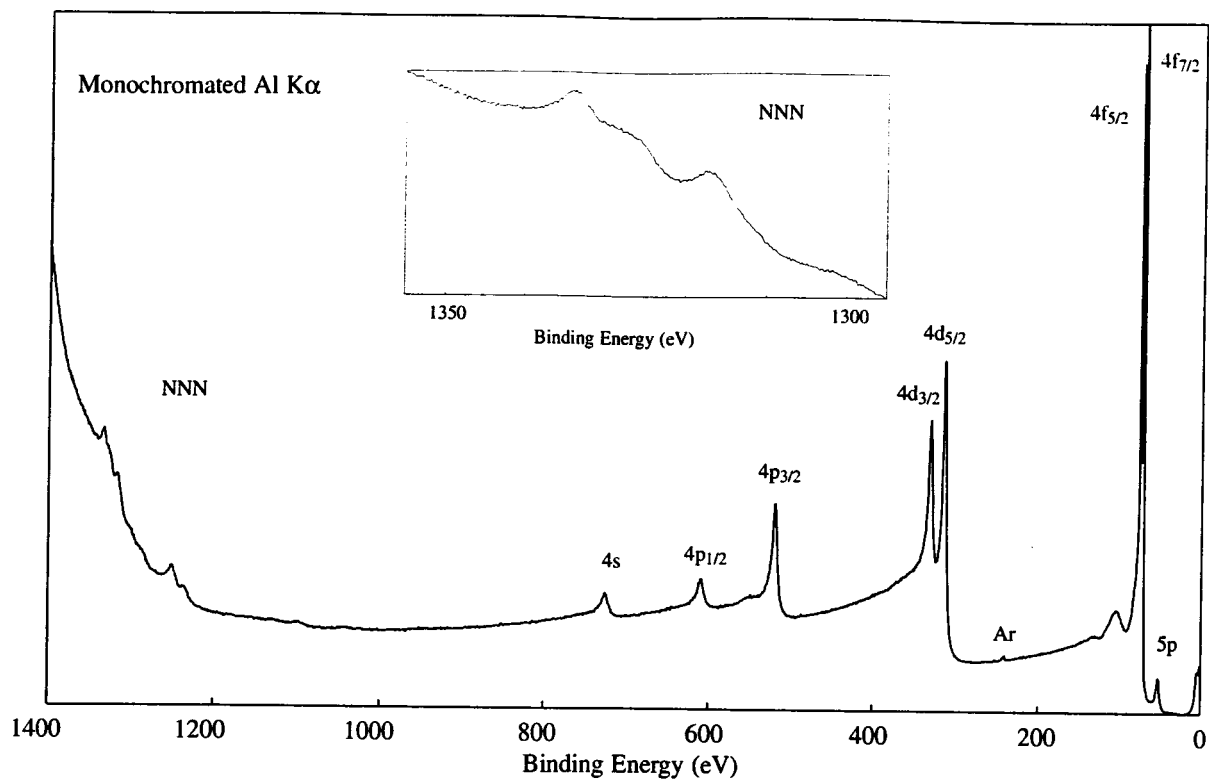


Line Positions (eV)				
Photoelectron Lines				
4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}
692	578	495	312	297
5s*	4f _{5/2}	4f _{7/2}	5p	
96	64	61	48	
Auger Lines				
N ₅ N ₆ N ₇		N ₄ N ₆ N ₇		
1329		1314 (Al)		
1096		1081 (Mg)		
*Estimate				



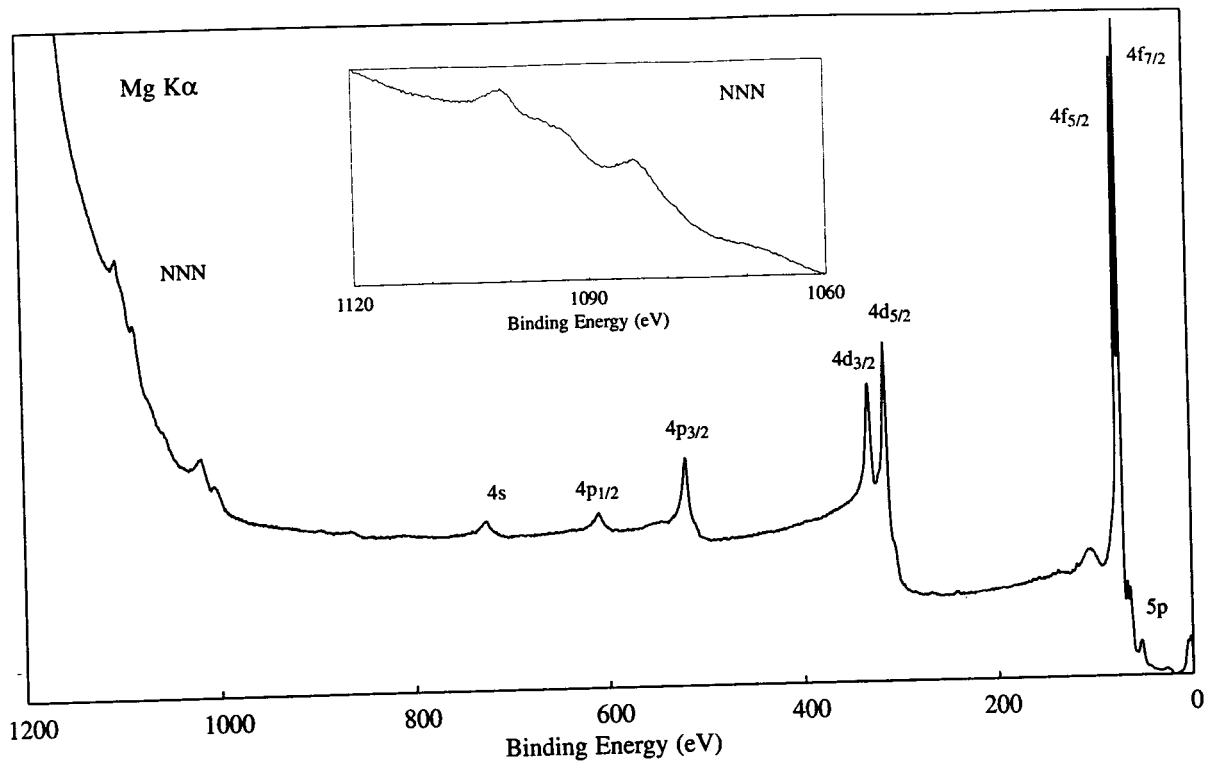
Compound Type	4f _{7/2} Binding Energy (eV)					
	60	61	62	63	64	65
Ir		■				
IrCl₃				■		
K₂IrBr₆			■	■		
K₃IrBr₆		■				
K₂IrCl₆				■	■	
K₃IrCl₆			■			
(NH₄)₂IrCl₆					■	
(NH₄)₃IrCl₆				■		
KIrCl₅NO						■
KIr₂(CO)₄Cl₄				■		
K₂Ir₂(CO)₄Cl₅				■		



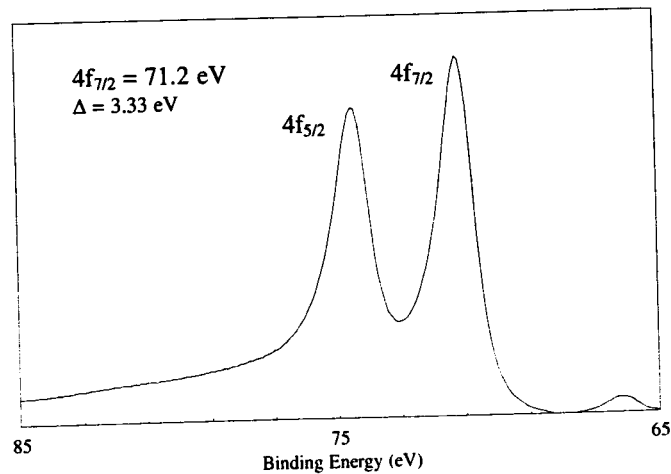


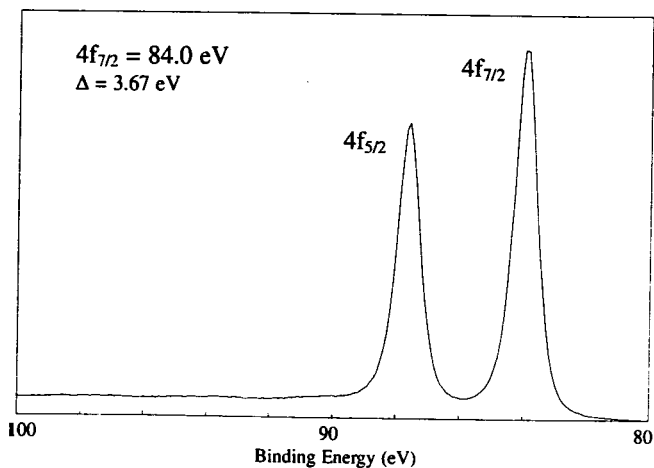
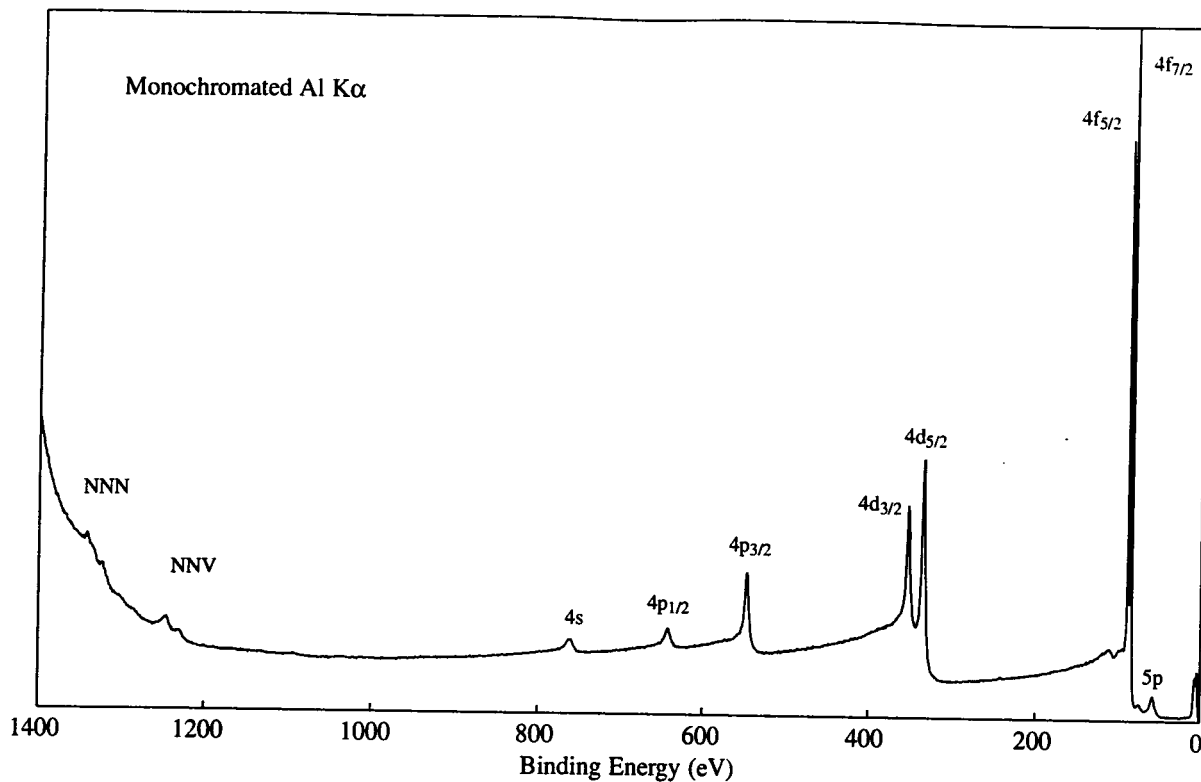
Line Positions (eV)				
<u>Photoelectron Lines</u>				
4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}
725	609	520	332	315
5s*	4f _{5/2}	4f _{7/2}	5p	
103	74	71	52	
<u>Auger Lines</u>				
N ₅ N ₆₇ N ₇		N ₄ N ₆₇ N ₇		
1334		1317 (Al)		
1101		1084 (Mg)		

*Estimate

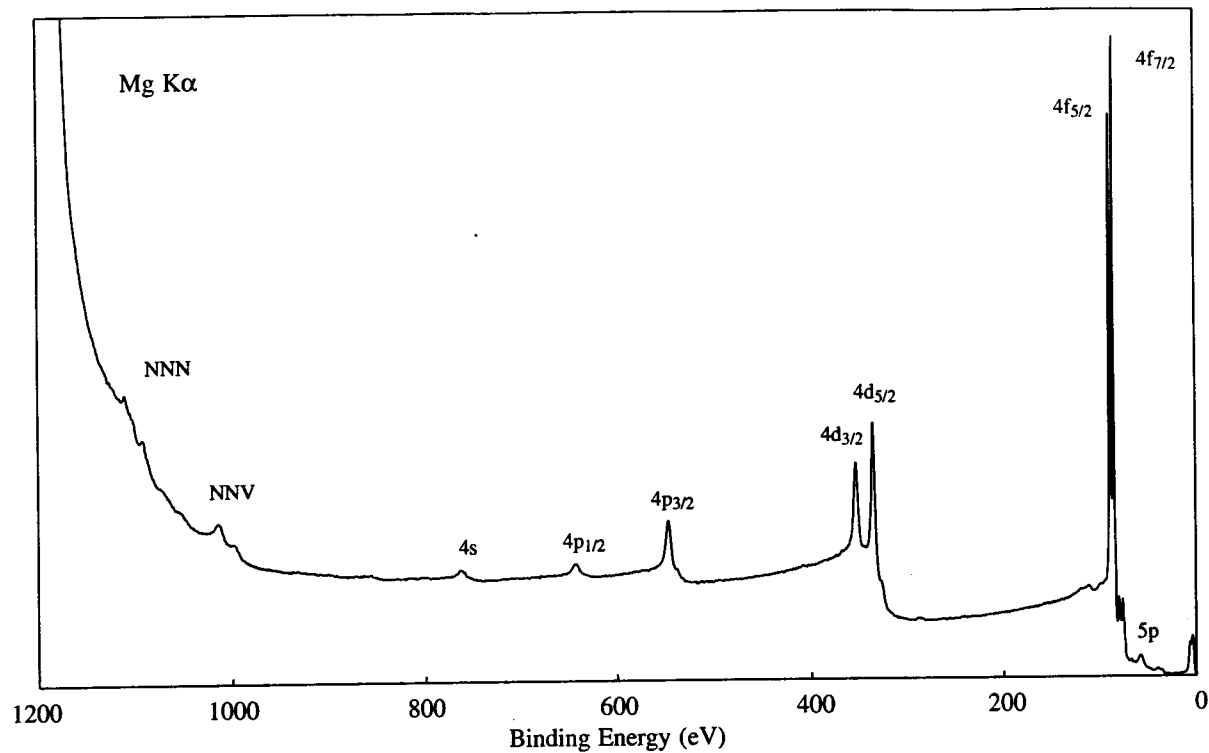


Compound Type	4f _{7/2} Binding Energy (eV)							
	71	72	73	74	75	76	77	78
Pt	■							
PtSi			■					
Pt ₂ Si		■						
PtCl ₂				■				
PtCl ₄						■		
Oxides					■			
P(OH) ₂		■						
(IV) Halides				■	■	■	■	■
Cl ₂ Pt(Ph ₃ P) ₂ cis		■	■					
I ₂ Pt(Me ₃ P) ₂ cis		■	■					
I ₂ Pt(Me ₃ P) ₂ trans			■					

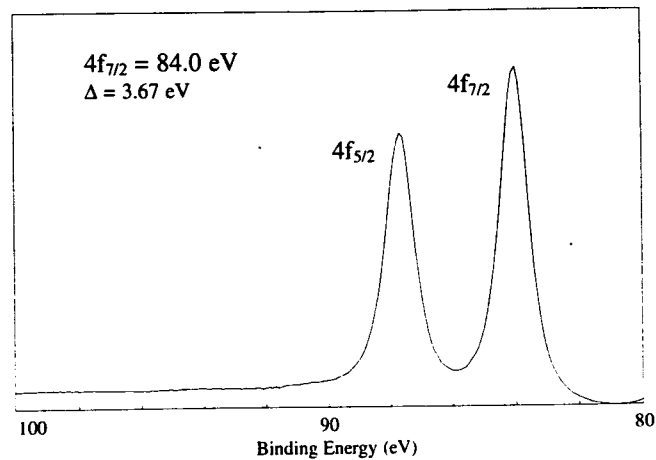


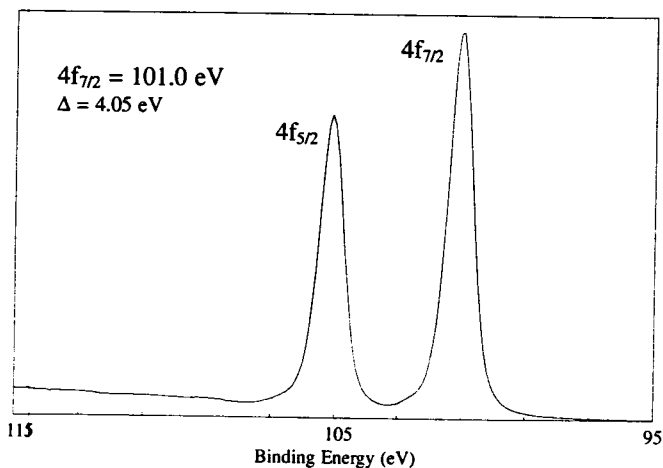
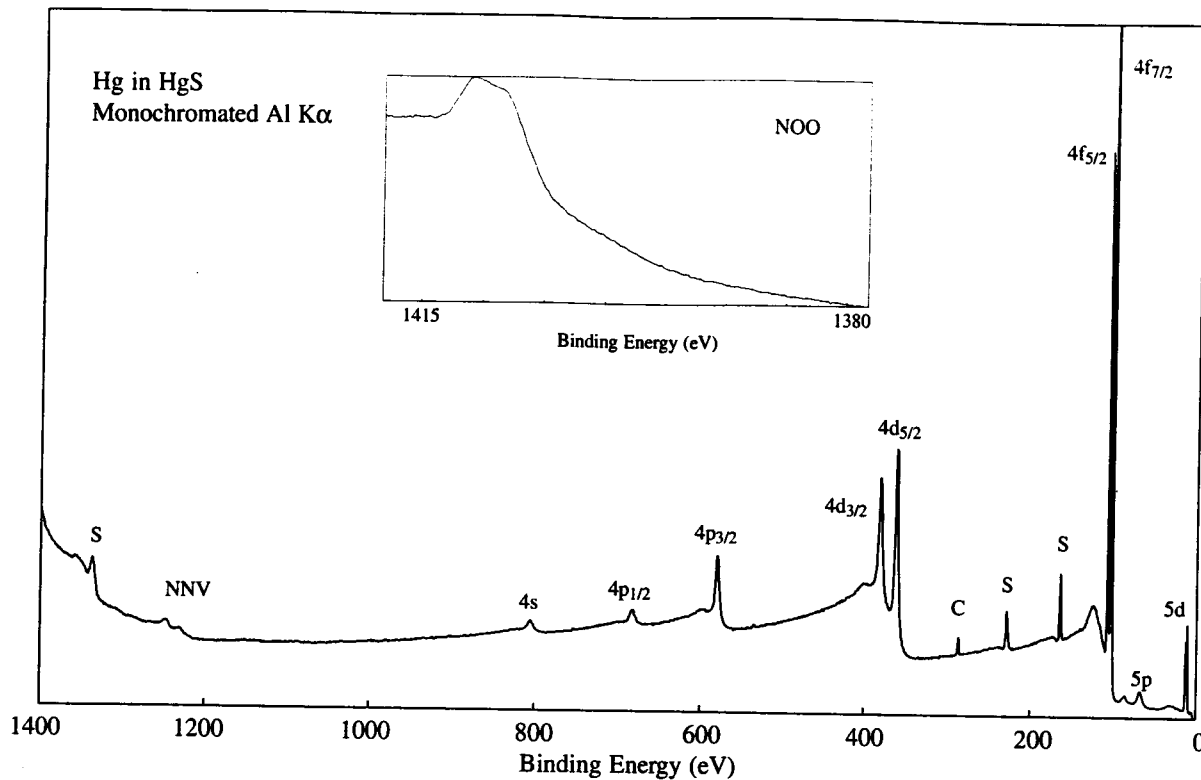


Line Positions (eV)				
<u>Photoelectron Lines</u>				
4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}
763	643	547	353	335
5s*	4f _{5/2}	4f _{7/2}	5p _{1/2}	5p _{3/2}
110	88	84	74	57
<u>Auger Lines</u>				
N ₆₇ O ₄₅ O ₄₅	N ₅ N ₆ N ₆₇	N ₄ N ₆ N ₆₇	N ₅ N ₆₇ V	
1416	1342	1324	1247	(Al)
1183	1109	1091	1014	(Mg)
*Estimate				



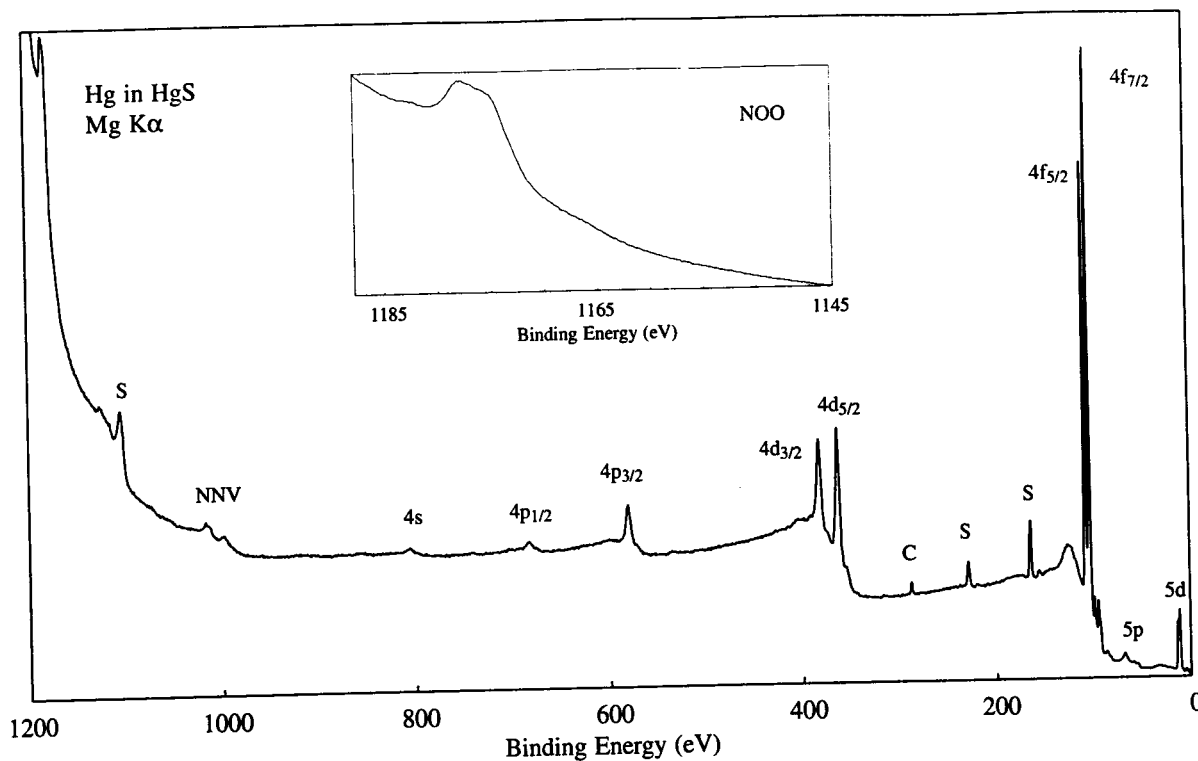
Compound Type	4f _{7/2} Binding Energy (eV)					
	83	84	85	86	87	88
Au		■				
AuSn			■			
AuSn ₄			■			
YbAu ₂		■				
ClAuPh ₃ P				■		
ClAu(Ph ₃ P) ₂				■		
Cl ₃ AuPh ₃ P					■	
(Ph ₃ P)AuNO ₃				■		
ClAu(Ph ₃ As)			■			
(-AuSPEt ₂ S-) ₂			■			
(-AuCH ₂ PEt ₂ CH ₂ -) ₂		■				



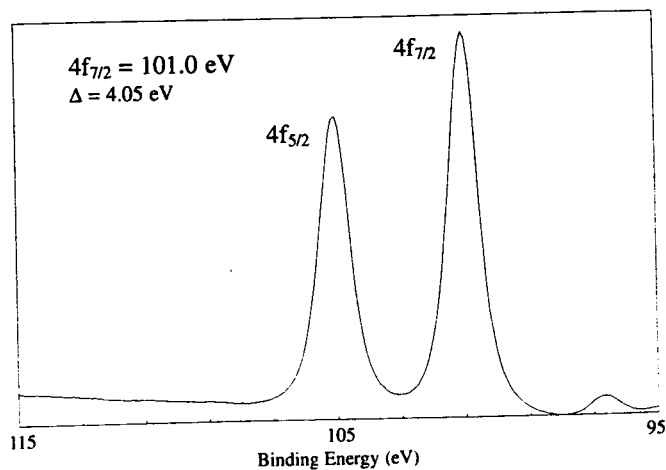


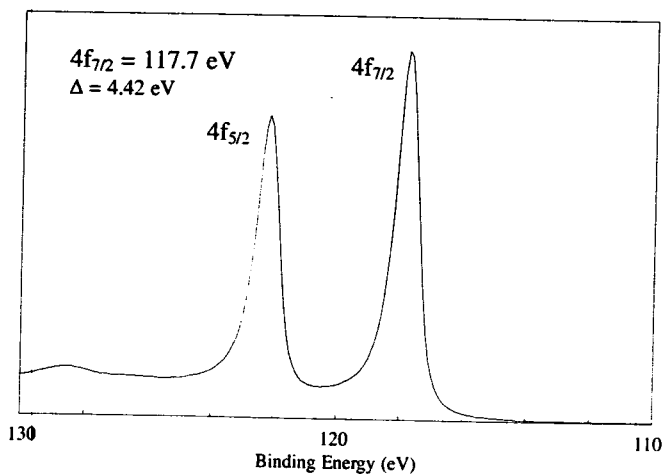
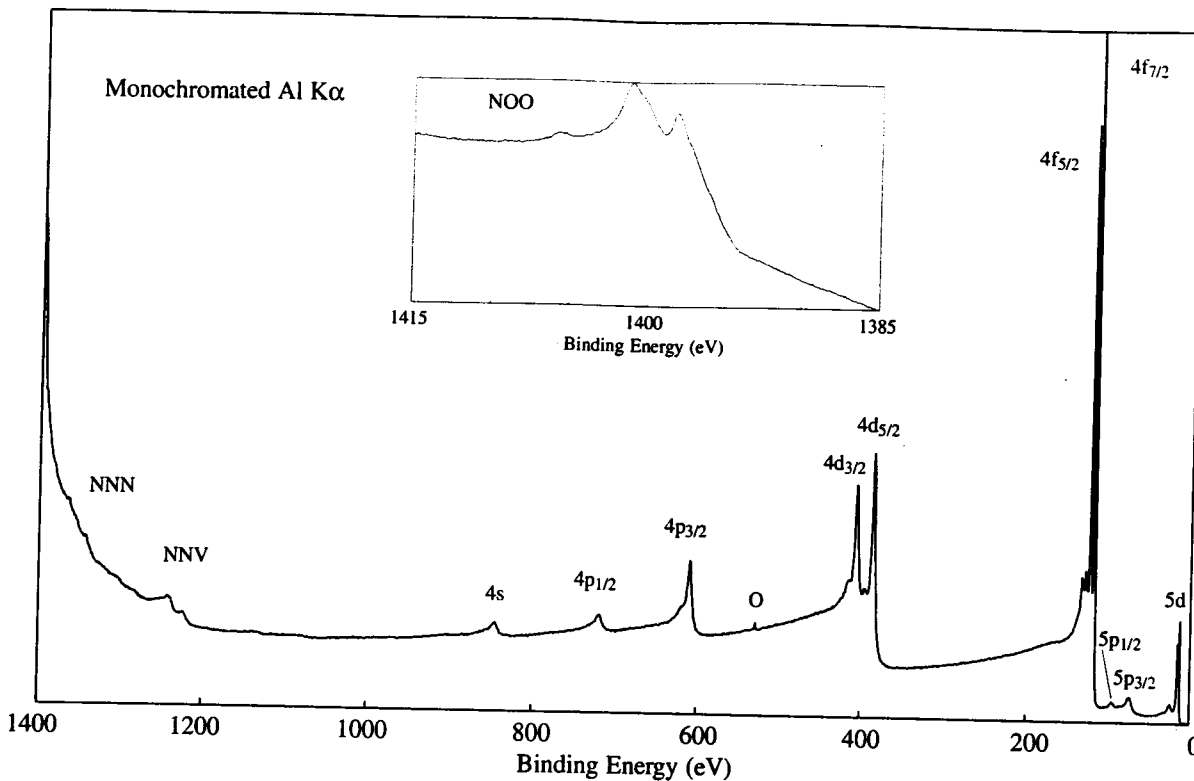
Line Positions (eV)					
<u>Photoelectron Lines</u>					
4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}	5s*
805	682	579	381	361	125
4f _{5/2}	4f _{7/2}	5p _{1/2}	5p _{3/2}	5d _{3/2}	5d _{5/2}
105	101	85	67	12	10
<u>Auger Lines</u>					
N ₇ O ₄₅ O ₄₅		N ₅ N ₇ O		N ₄ N ₆ O	
1412		1246		1230 (Al)	
1179		1013		997 (Mg)	

*Estimate

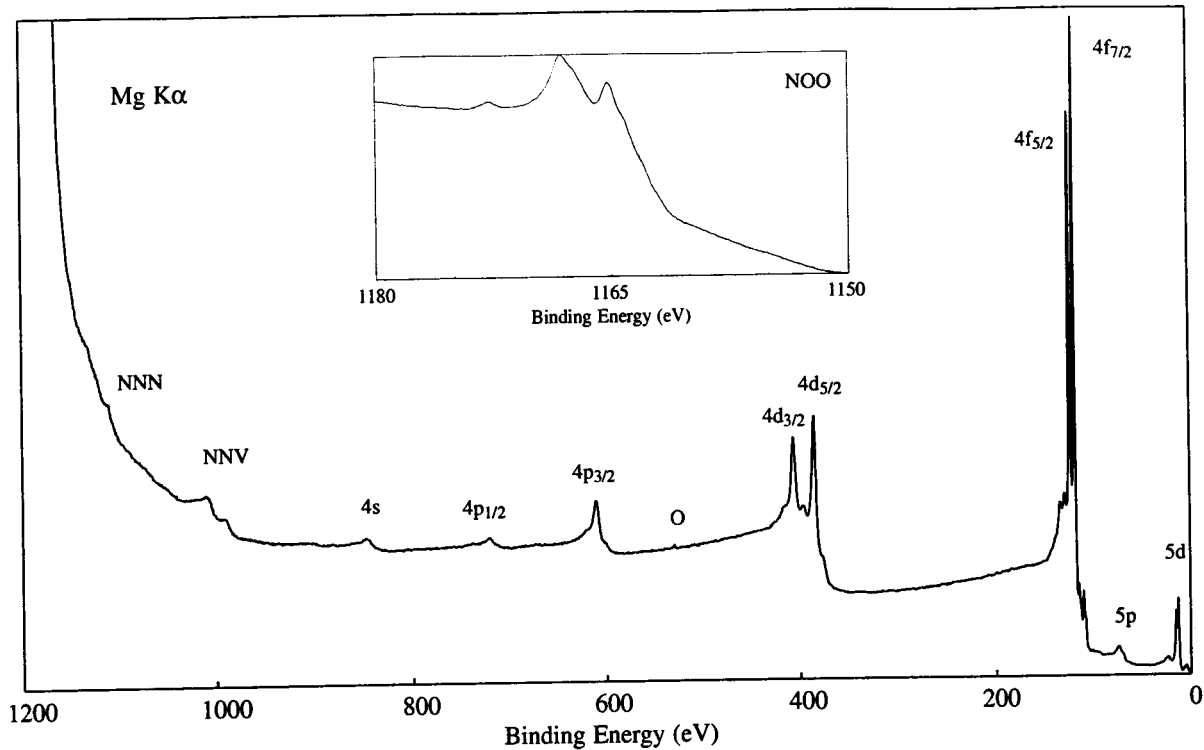


Compound Type	4f _{7/2} Binding Energy (eV)			
	99	100	101	102
Hg		■		
Hg _{0.8} Cd _{0.2} Te		■	■	
HgS		■	■	
HgI ₂			■	
HgBr ₂			■	
HgCl ₂				■
HgF ₂			■	■
HgO		■	■	
Et ₂ NC ₆ H ₄ HgOAc			■	■
Hg(thiodibenzoylme) ₂			■	■
(Ph ₄ P) ₂ Hg(SCN) ₄				■

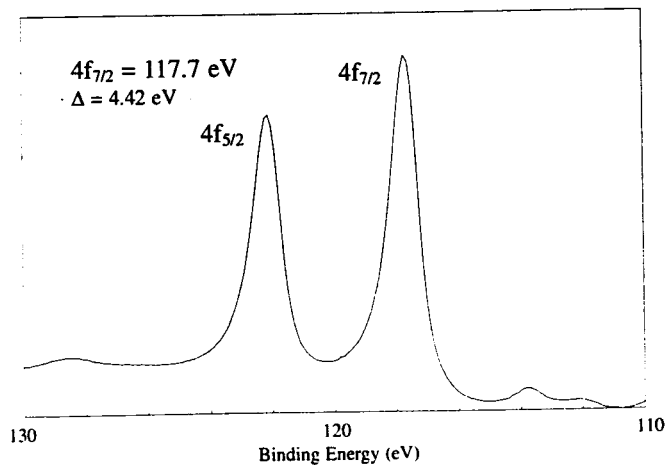


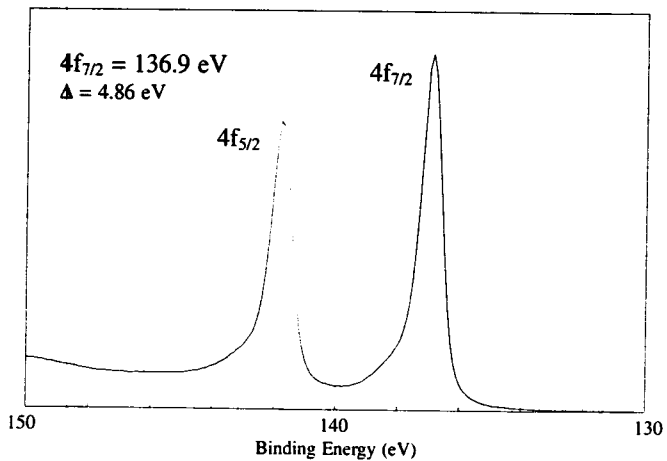
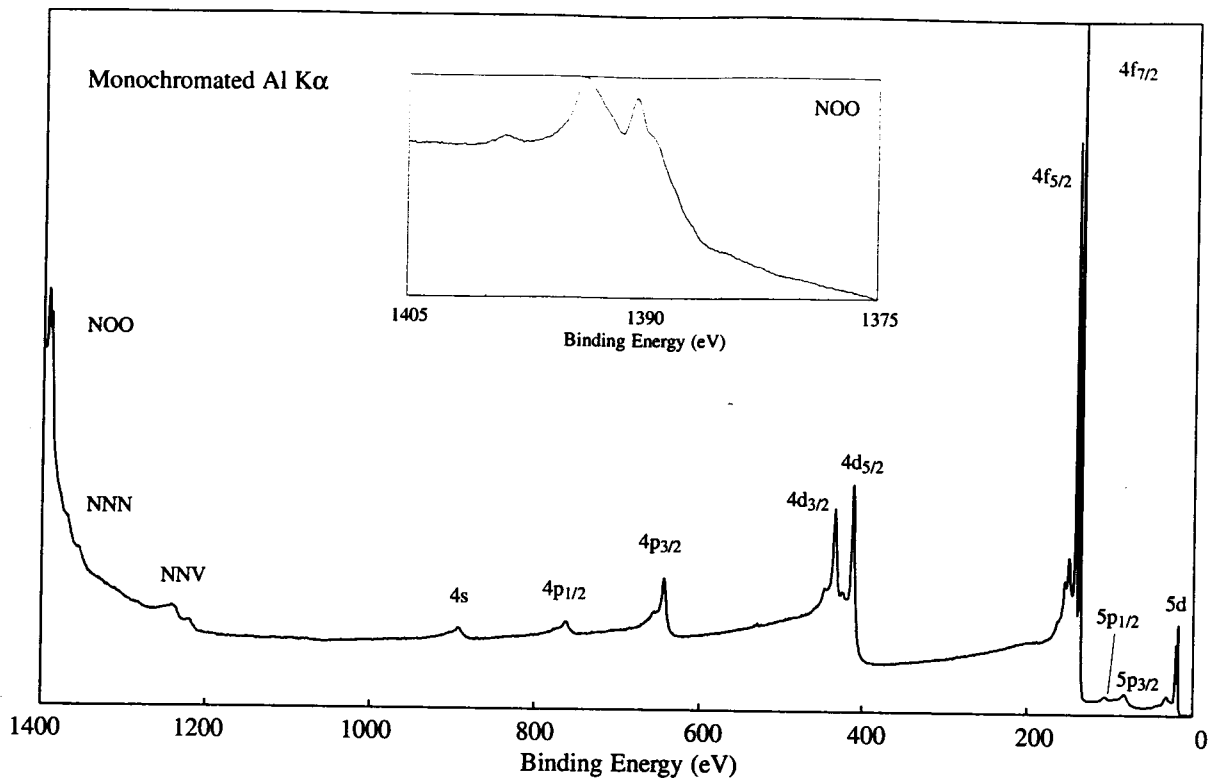


Line Positions (eV)					
<u>Photoelectron Lines</u>					
4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}	5s*
847	720	610	406	385	133
4f _{5/2}	4f _{7/2}	5p _{1/2}	5p _{3/2}	5d _{3/2}	5d _{5/2}
122	118	95	74	15	13
<u>Auger Lines</u>					
N ₇ O ₁₅ O ₄₅	N ₆ O ₄₅ O ₄₅	N ₅ N ₇ O ₅	N ₄ N ₆₇ O ₅		
1401	1399	1241	1222 (Al)		
1168	1166	1008	989 (Mg)		
*Estimate					

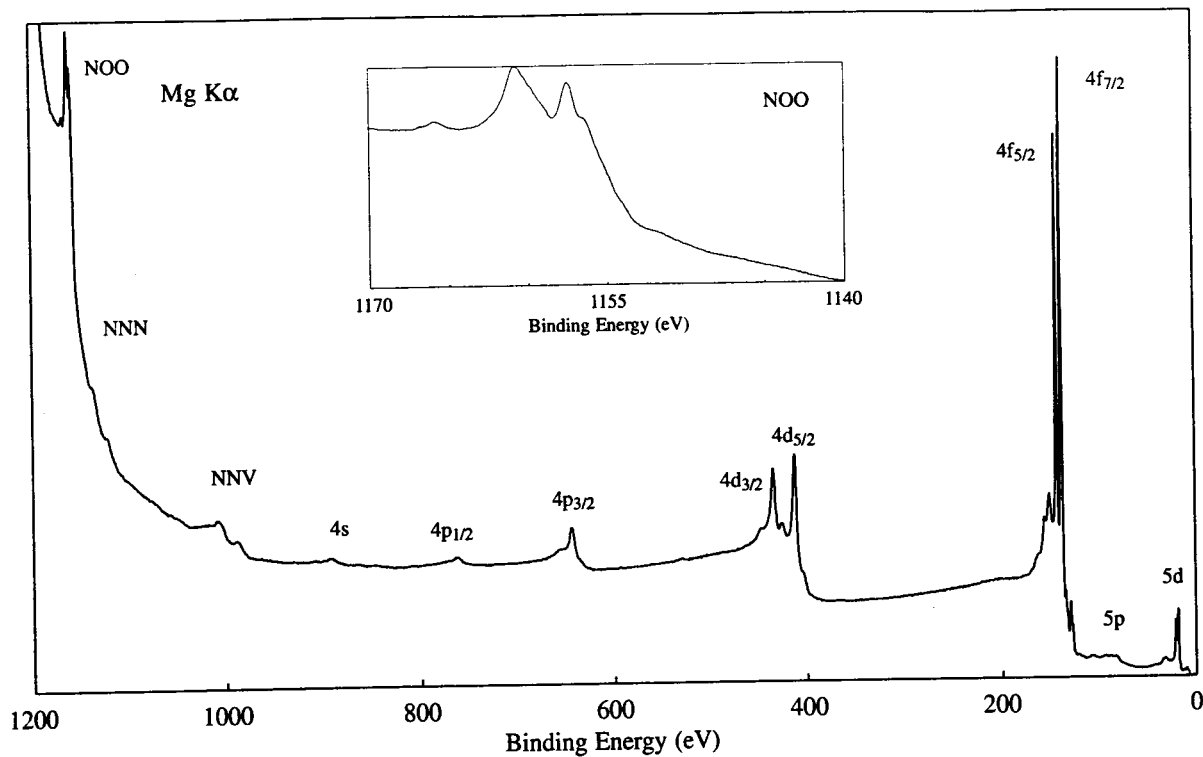


Compound Type	4f _{7/2} Binding Energy (eV)			
	117	118	119	120
Tl		█		
TlI			█	
TlBr			█	
TlCl			█	
TlF			█	
Tl ₂ S			█	
Tl ₂ S ₃			█	
Tl ₂ O ₃	█			
Cl ₃ Tl(pyridine) ₂	█		█	
Cl ₆ Tl ₂ (PhPEt ₂) ₅		█		

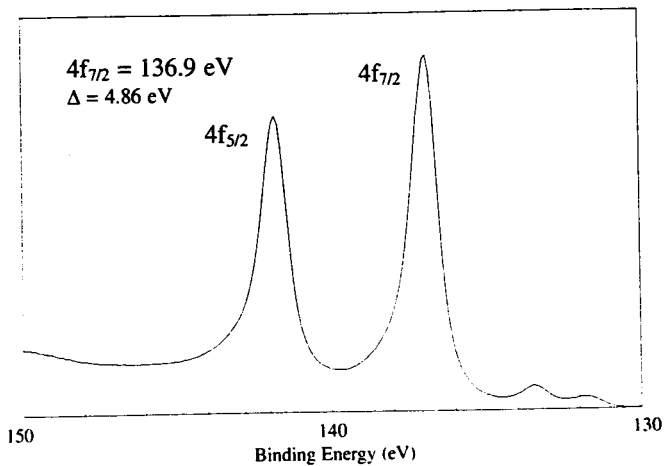


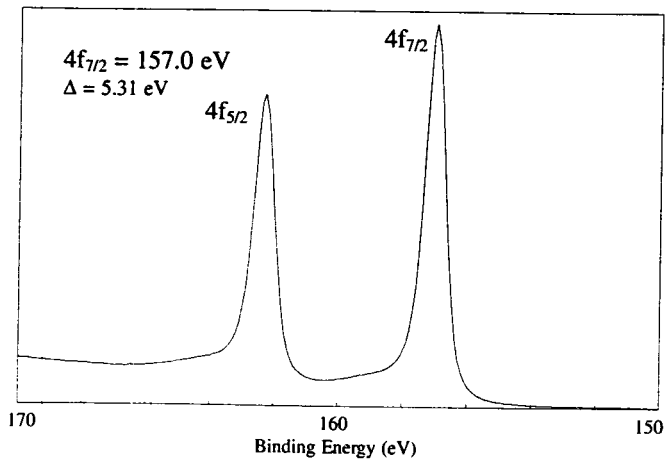
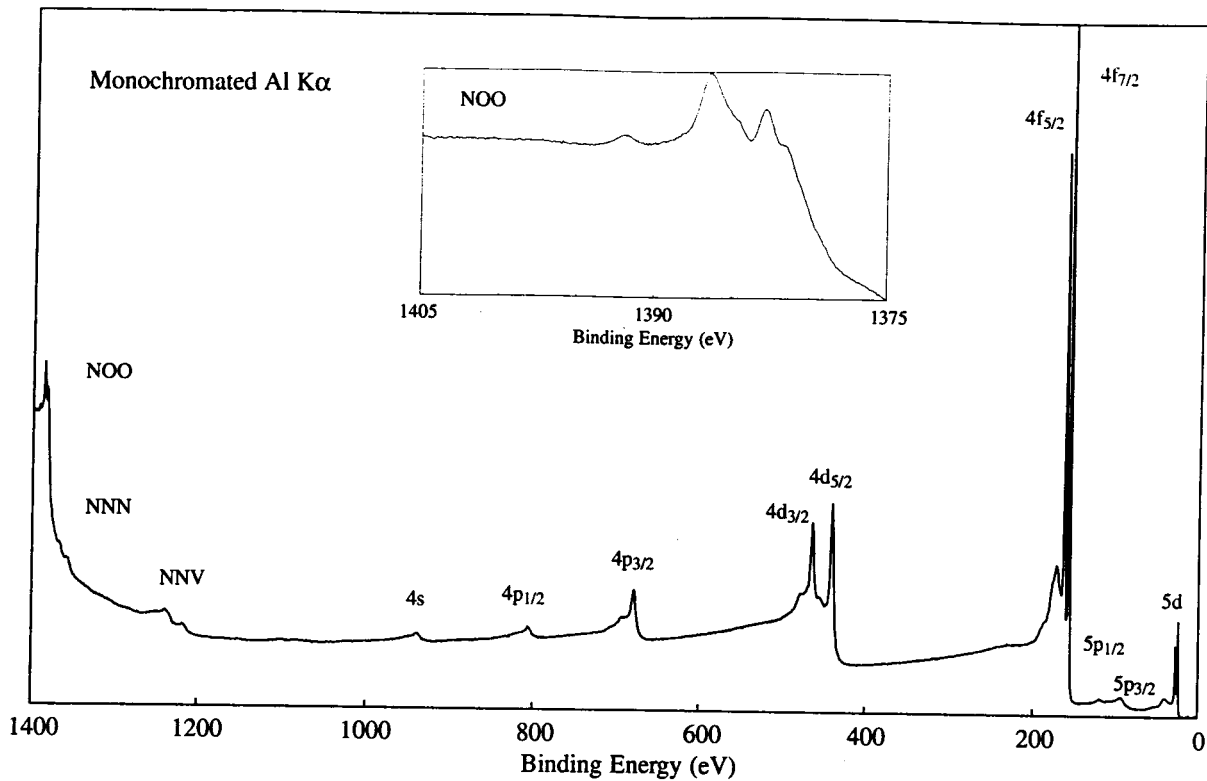


Line Positions (eV)					
Photoelectron Lines					
4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}	5s*
893	762	644	434	412	150
4f _{5/2}	4f _{7/2}	5p _{1/2}	5p _{3/2}	5d _{3/2}	5d _{5/2}
142	137	107	84	21	18
Auger Lines					
N ₇ O ₄₅ O ₄₅		N ₆ O ₄₅ O ₄₅			
1394		1391		(Al)	
1161		1158		(Mg)	
*Estimate					



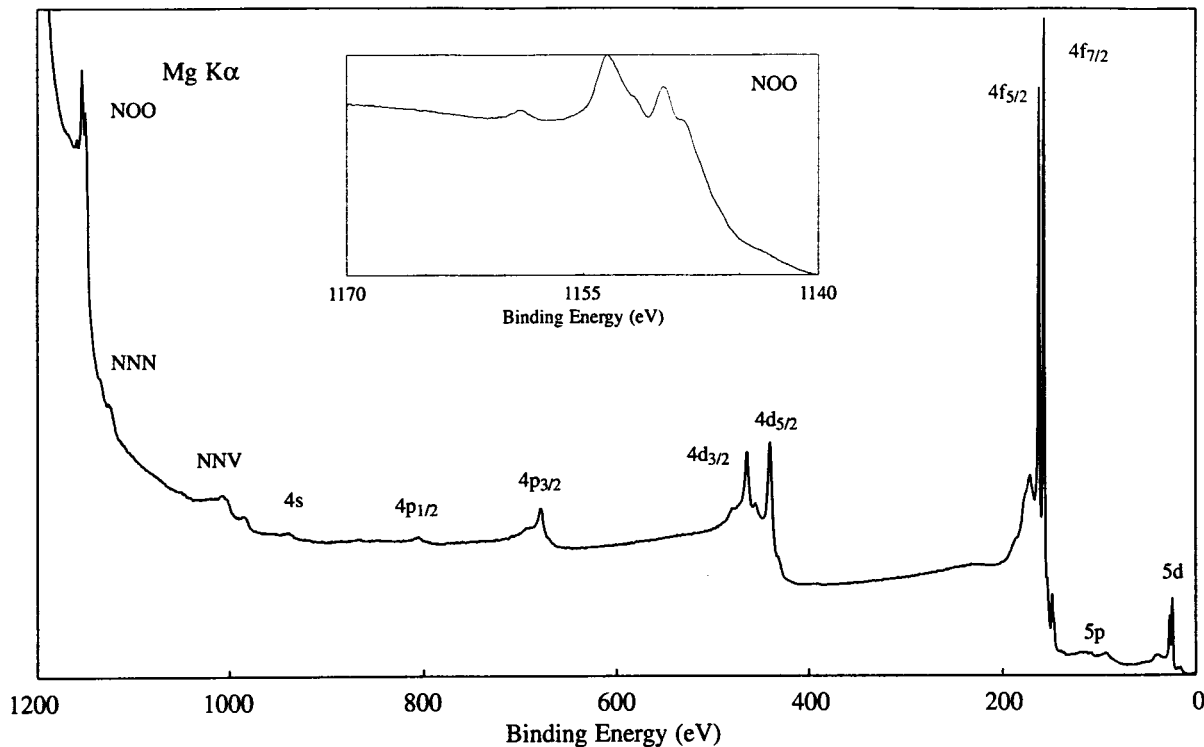
Compound Type	4f $_{7/2}$ Binding Energy (eV)				
	136	137	138	139	140
Pb		■			
PbTe			■		
PbSe			■		
Halides				■	
PbO				■	
Pb $_3$ O $_4$			■		
PbO $_2$		■			
Pb(OH) $_2$			■		
Pb(NO $_3$) $_2$				■	
PbSO $_3$				■	
PbSO $_4$					■



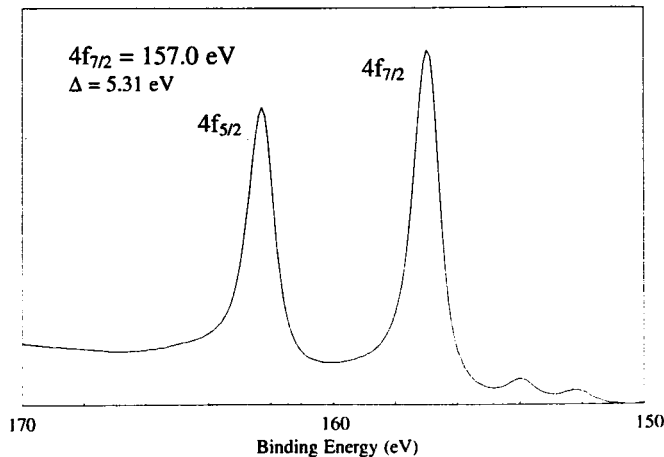


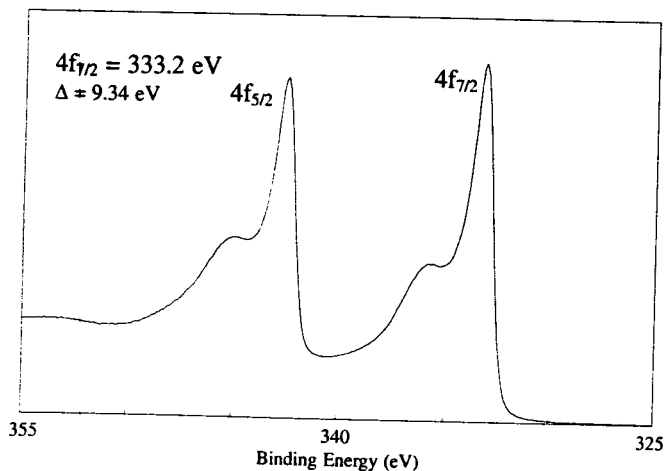
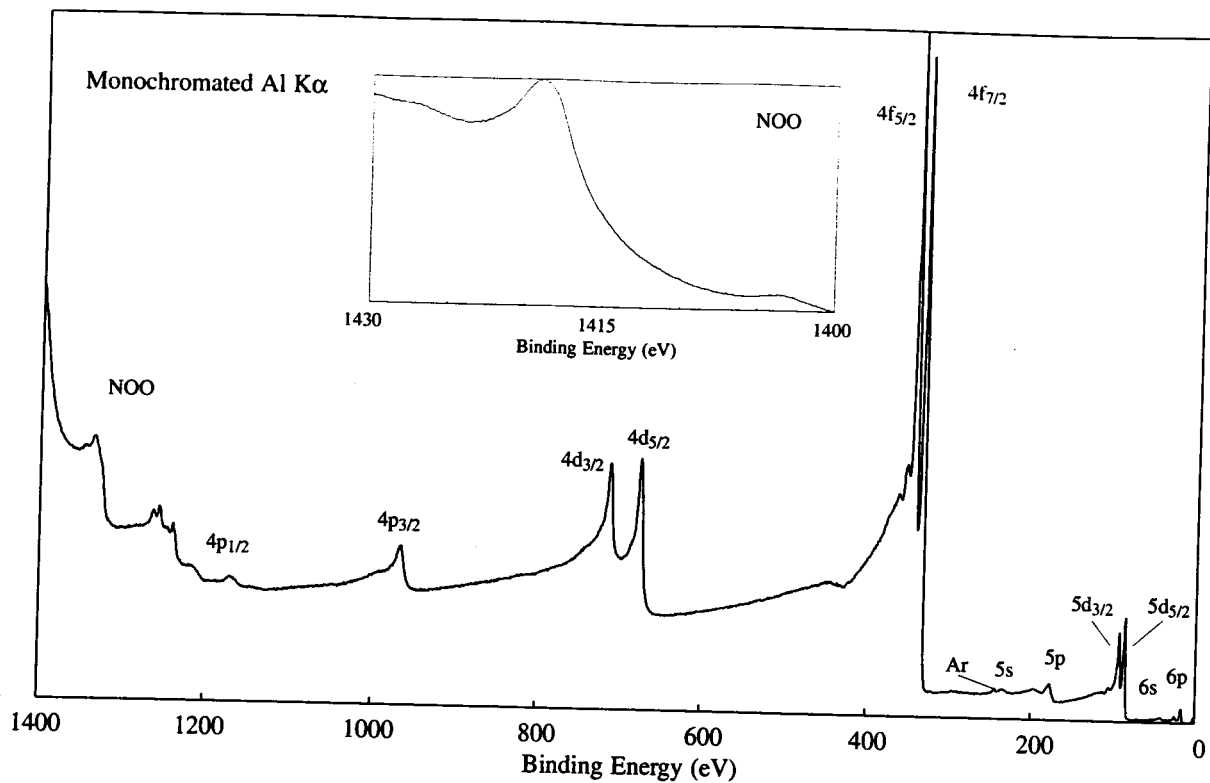
Line Positions (eV)					
<u>Photoelectron Lines</u>					
4s	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}	5s*
940	806	679	464	440	161
4f _{5/2}	4f _{7/2}	5p _{1/2}	5p _{3/2}	5d _{3/2}	5d _{5/2}
162	157	119	93	27	24
<u>Auger Lines</u>					
N ₇ O ₄₅ O ₄₅		N ₆ O ₄₅ O ₄₅			
1387		1383 (Al)			
1154		1150 (Mg)			

*Estimate

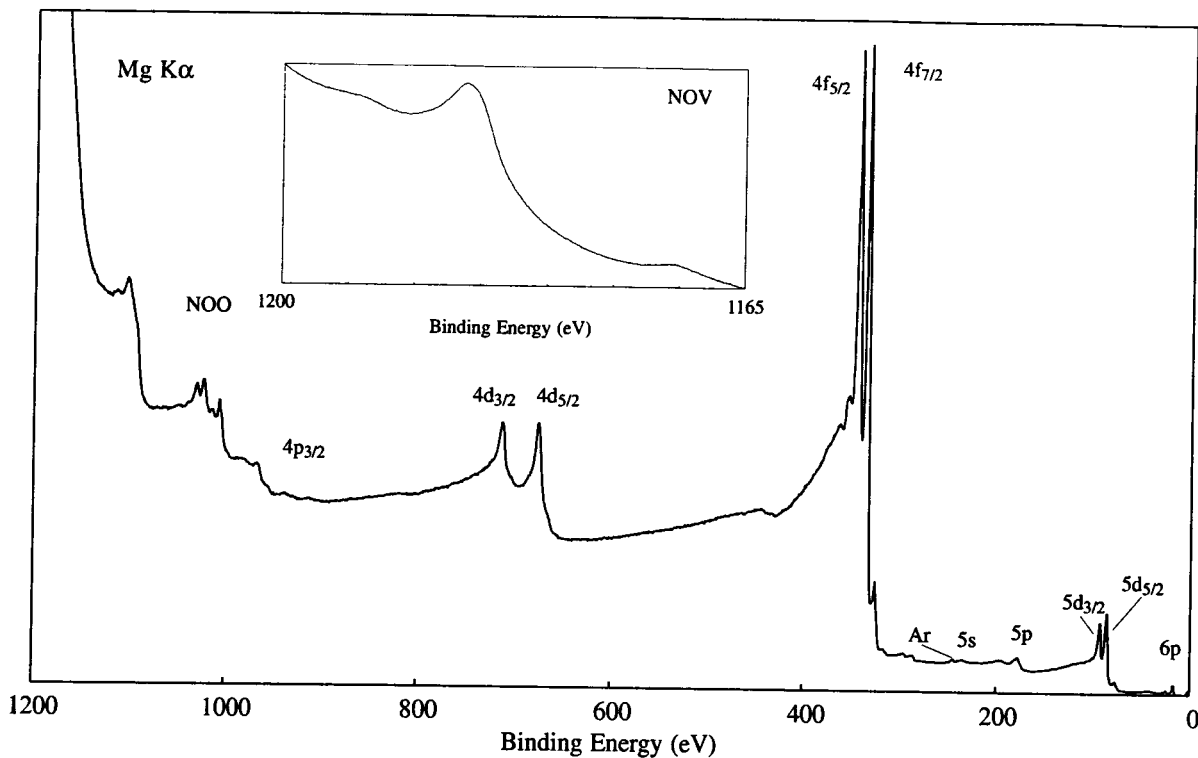


Compound Type	4f _{7/2} Binding Energy (eV)						
	156	157	158	159	160	161	162
Bi		■					
Bi ₂ S ₃				■			
BiI ₃				■			
BiF ₃				■		■	
Bi ₂ O ₃				■	■		
BiOCl				■	■		
NaBiO ₃				■			
Bi ₂ MoO ₆			■				
Bi ₂ Tl ₂ O ₇				■	■		
(BiO) ₂ Cr ₂ O ₇				■	■		
Bi ₂ (SO ₄) ₃ · H ₂ O						■	



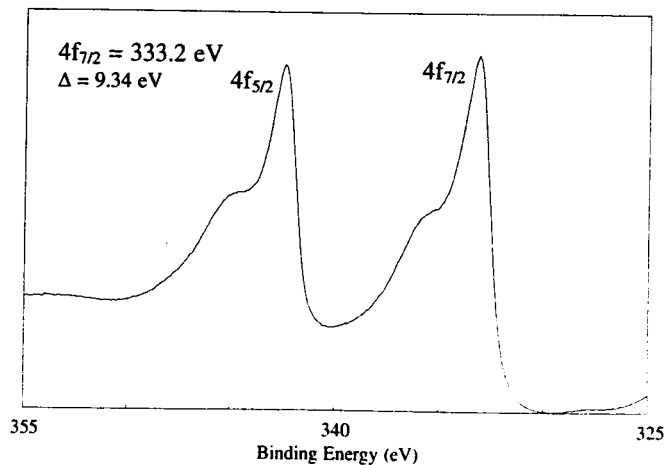


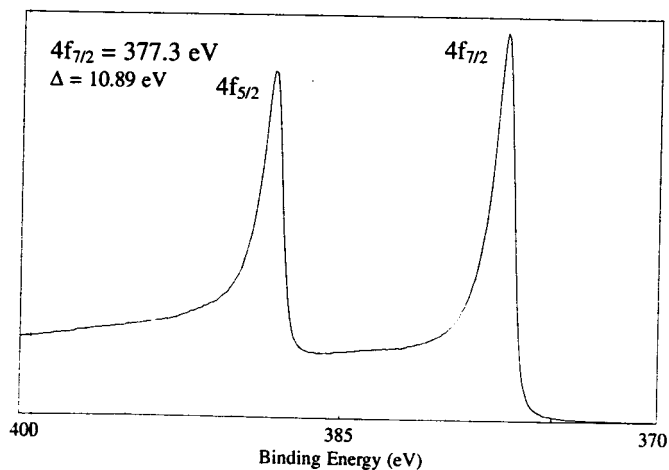
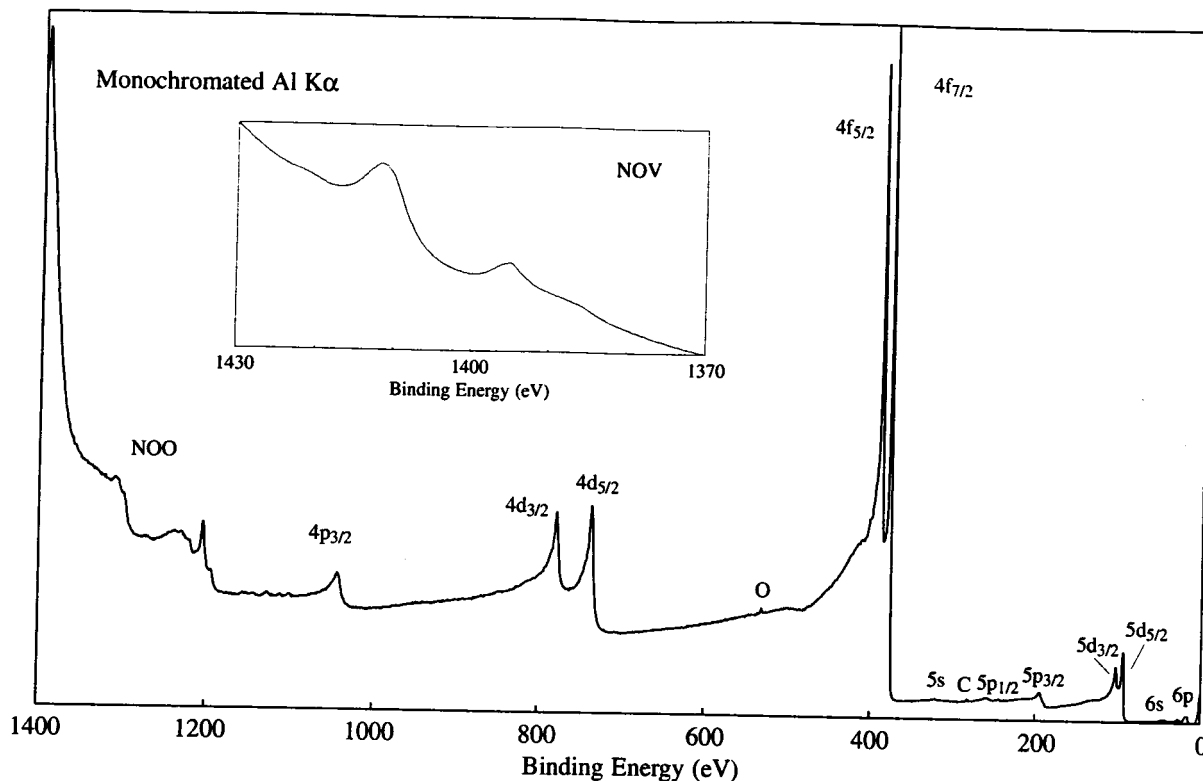
Line Positions (eV)								
Photoelectron Lines								
4s*	4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}	4f _{5/2}	4f _{7/2}		
1330	1170	965	713	676	342	333		
5s	5p _{1/2}	5p _{3/2}	5d _{3/2}	5d _{5/2}	6s	6p _{1/2}	6p _{3/2}	
294	234	177	93	85	42	25	17	
Auger Lines								
N ₆ O ₂₃ V	N ₆₇ O ₄₅ O ₄₅		N ₇ O ₄ O ₅		N ₆₇ O ₄₅ V			
1419	1404		1335		1239 (Al)			
1186	1171		1102		1006 (Mg)			
*Estimate								



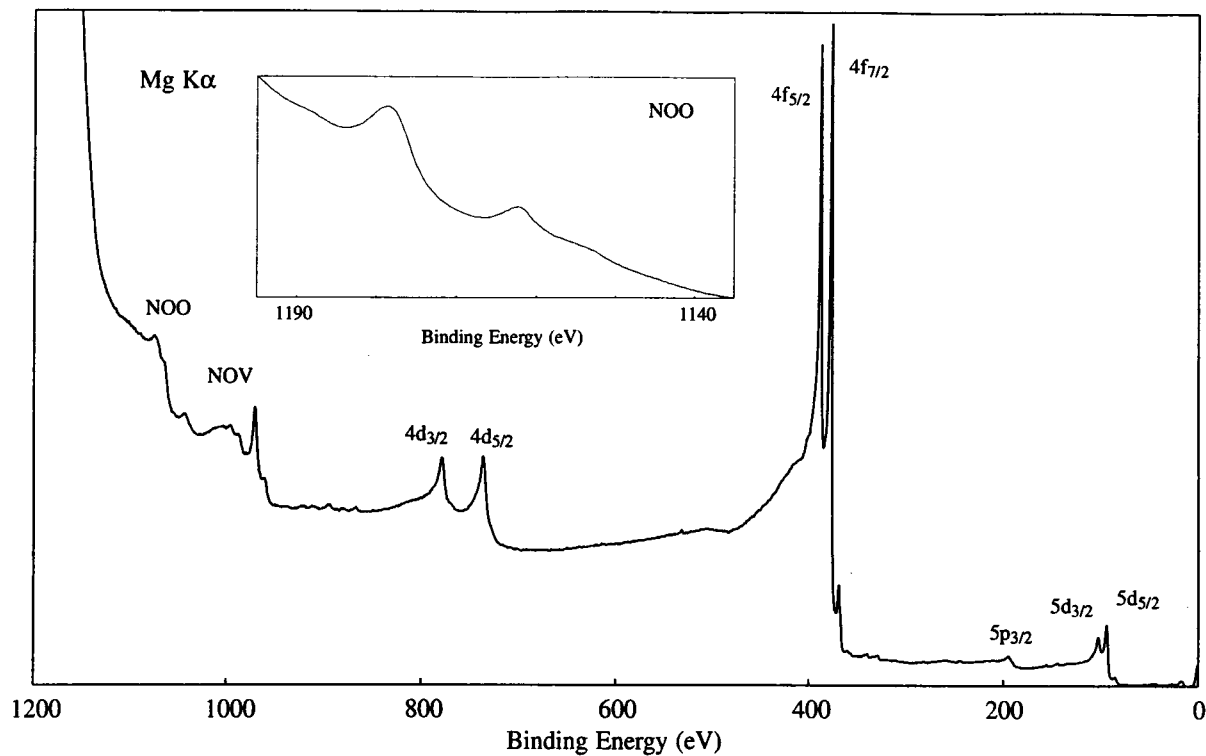
4f $_{7/2}$ Binding Energy (eV)					
Compound Type	333	334	335	336	337
Th	■				
ThO $_2$		■			
ThF $_4$				■	

4d $_{5/2}$ Binding Energy (eV)			
Compound Type	674	675	676
Th		■	
ThO $_2$		■	

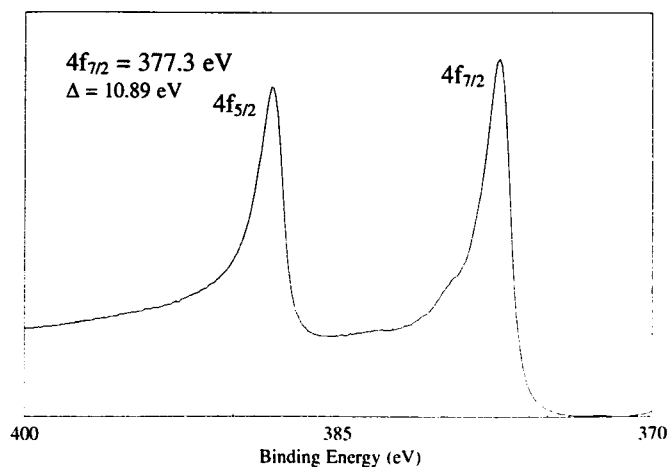




Line Positions (eV)								
Photoelectron Lines								
4p _{1/2}	4p _{3/2}	4d _{3/2}	4d _{5/2}	4f _{5/2}	4f _{7/2}			
1272	1043	779	736	388	377			
5s	5p _{1/2}	5p _{3/2}	5d _{3/2}	5d _{5/2}	6s	6p _{1/2}	6p _{3/2}	
322	260	195	103	94	44	26	17	
Auger Lines								
N ₆ O ₂₃ V	N ₇ O ₂₃ O ₅	N ₆ O ₄₅ O ₄₅	N ₆₇ O ₄₅ V					
1412	1396	1386	1204				(Al)	
1179	1163	1153	971				(Mg)	



Compound Type	4f _{7/2} Binding Energy (eV)						
	377	378	379	380	381	382	383
U	■						
Tellurides					■	■	
Selenides			■	■	■		
Sulfides			■	■			
Halides		■	■	■	■	■	■
Oxides		■	■	■	■	■	
Oxy Halides		■	■	■	■	■	■
U(SO ₄) ₂						■	
U(acac) ₄			■	■			
CaUO ₄				■	■		
K ₂ UF ₆							■



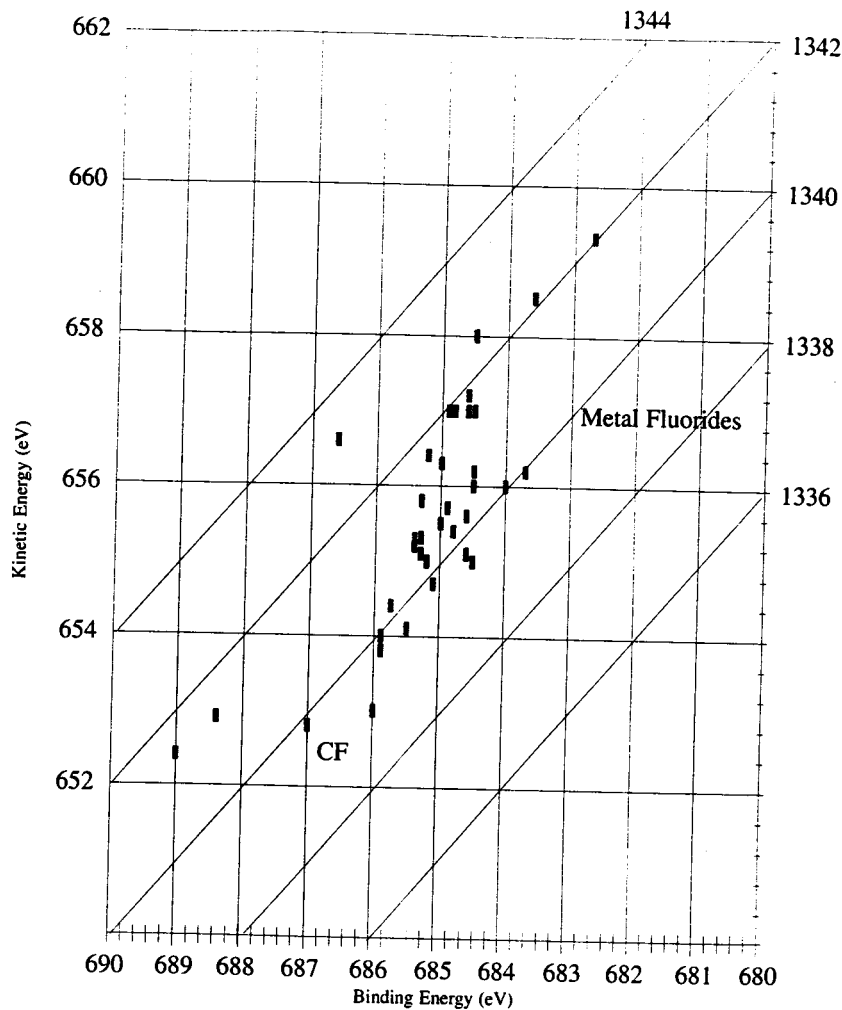
III. Appendix

Appendix A. Auger Parameters

The following tables plot the binding energy of the most intense photoelectron line versus the kinetic energy of the most intense Auger transition. The Auger parameter plots are useful for further separation of the chemical states.

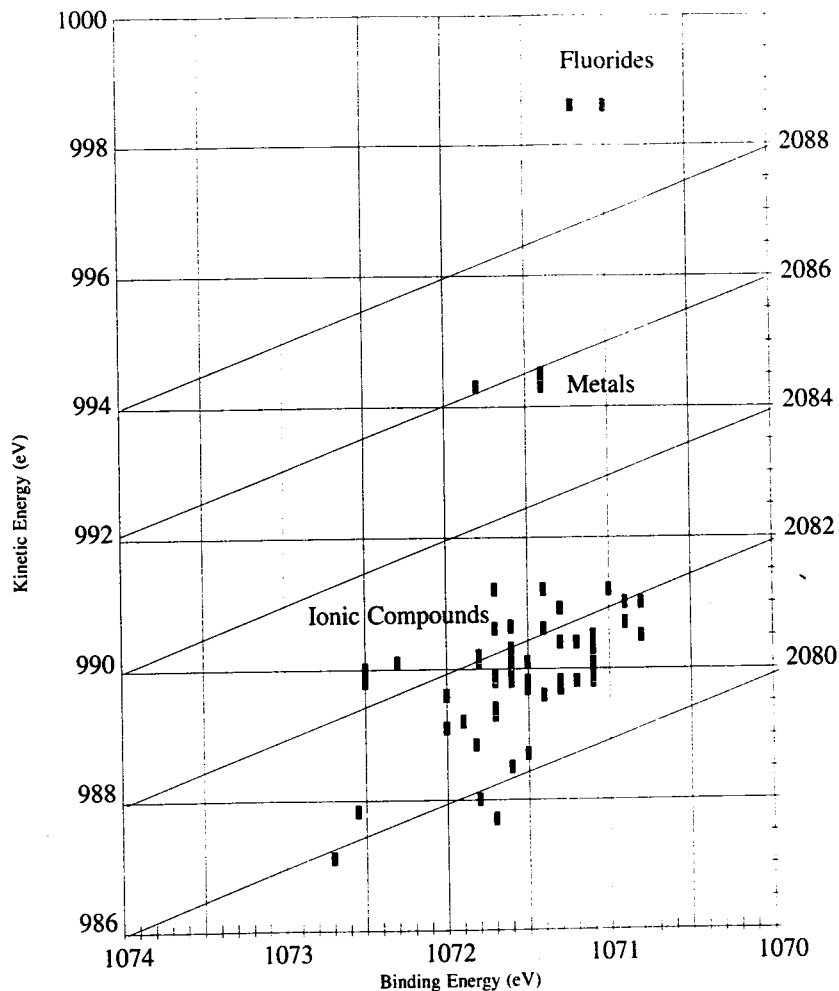
Fluorine

Compound	F 1s Binding Energy (eV)	F KLL Kinetic Energy (eV)
AgF	682.7	659.3
PbF ₂	683.6	658.5
BaF ₂	683.7	656.2
K ₃ FeF ₆	684.0	656.0
NaF	684.5	655.0
CdF ₂	684.5	656.0
CuF ₂	684.5	657.0
CuF ₂	684.5	656.2
CaF ₂	684.5	656.2
LaF ₃	684.5	658.0
ZnF ₂	684.6	655.6
PrF ₃	684.6	657.2
SmF ₃	684.6	657.0
K ₂ ZrF ₆	684.6	655.1
CaF ₂	684.8	655.4
NdF ₃	684.8	657.0
ThF ₄	684.9	657.0
K ₂ TiF ₆	684.9	655.7
SrF ₂	685.0	656.3
NiF ₂	685.0	655.5
LiF	685.1	654.7
InF ₃	685.2	656.4
K ₂ TaF ₇	685.2	655.0
YF ₃	685.3	655.8
Na ₂ TiF ₆	685.3	655.1
Na ₂ SnF ₃	685.3	655.3
HfF ₄	685.4	655.3
K ₂ NbF ₇	685.4	655.2
Na ₃ AlF ₆	685.5	654.1
MgF ₂	685.8	654.4
CsF	685.9	653.8
Na ₂ GeF ₆	685.9	654.0
Na ₂ SiF ₆	686.0	653.0
KSbF ₆	686.6	656.6
NaBF ₄	687.0	652.8
NiOCCF ₃	688.4	652.9
p-(CF ₂ =CF ₂)	689.0	652.4



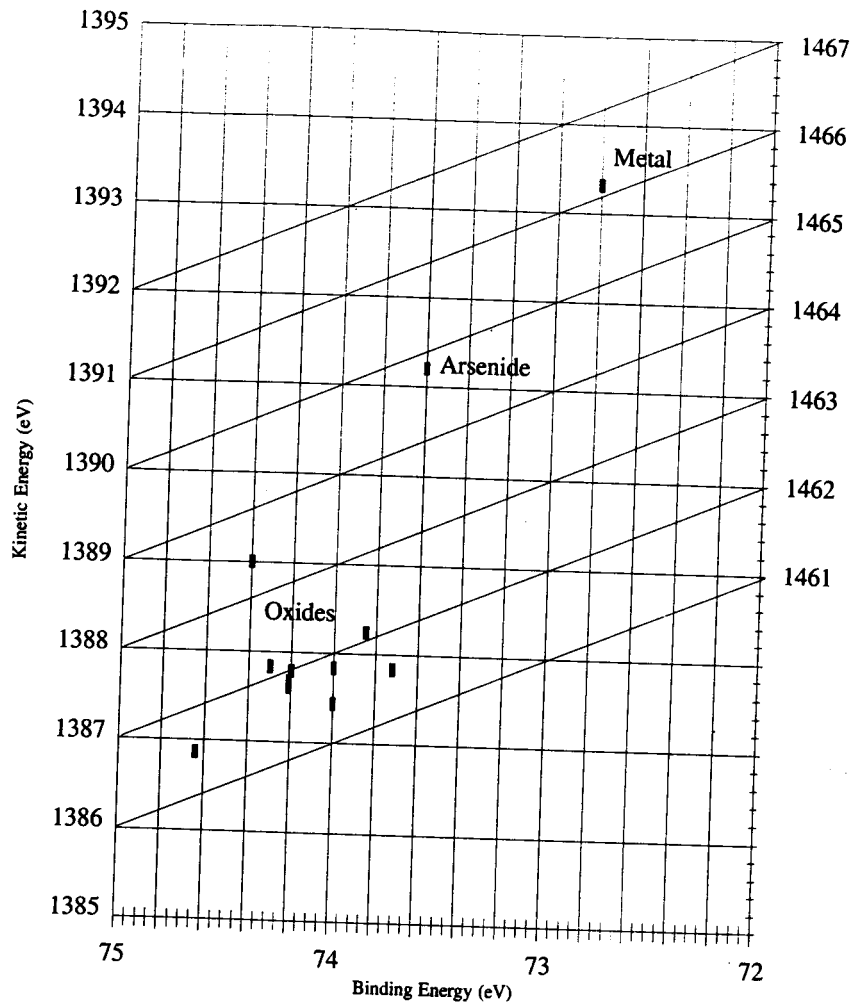
Sodium

Compound	Na 1s	Na KLL
	Binding Energy (eV)	Kinetic Energy (eV)
Na ₂ SeO ₃	1070.8	991.0
Na ₂ C ₂ O ₄	1070.8	990.5
Na ₂ MoO ₄	1070.9	991.0
NaAsO ₂	1070.9	990.7
NaF	1071.0	998.6
Na ₂ CrO ₄	1071.0	991.2
Na ₃ PO ₄	1071.1	990.1
NaH ₂ PO ₂	1071.1	989.8
Na ₂ SnO ₃ · 3H ₂ O	1071.1	990.3
NaOAc	1071.1	989.9
NaF	1071.2	998.6
Na ₂ SO ₄	1071.2	989.8
NaOOCCH ₂ SH	1071.2	990.4
Na ₂ SO ₃	1071.3	990.4
Na	1071.4	994.3
Na	1071.4	994.5
NaBr	1071.4	990.6
NaNO ₃	1071.4	989.6
Na ₂ CrO ₄	1071.4	991.2
NaCl	1071.5	990.1
Na ₂ CO ₃	1071.5	989.8
Na ₂ HPO ₄	1071.5	989.7
Na ₂ S ₂ O ₃	1071.6	990.1
NaNO ₂	1071.6	989.8
Na ₂ Cr ₂ O ₇	1071.6	990.6
NaI	1071.7	991.2
NaBr	1071.7	990.6
Na ₂ CO ₃	1071.7	989.8
NaOAc	1071.7	989.9
Na	1071.8	994.3
NaCl	1071.8	990.1
NaCl	1072.5	990.0
Na ₂ O	1072.5	989.8
Mol Sieve Y	1072.6	987.8
NaBF ₄	1072.7	987.1

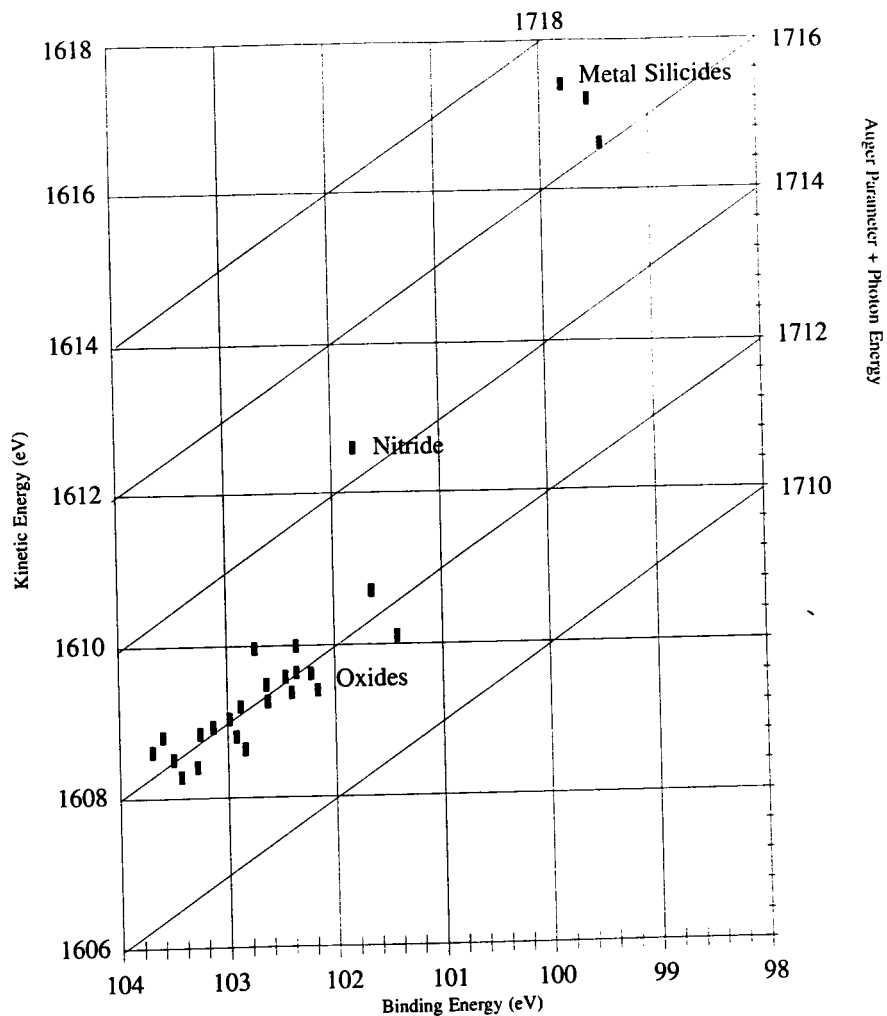


Aluminum

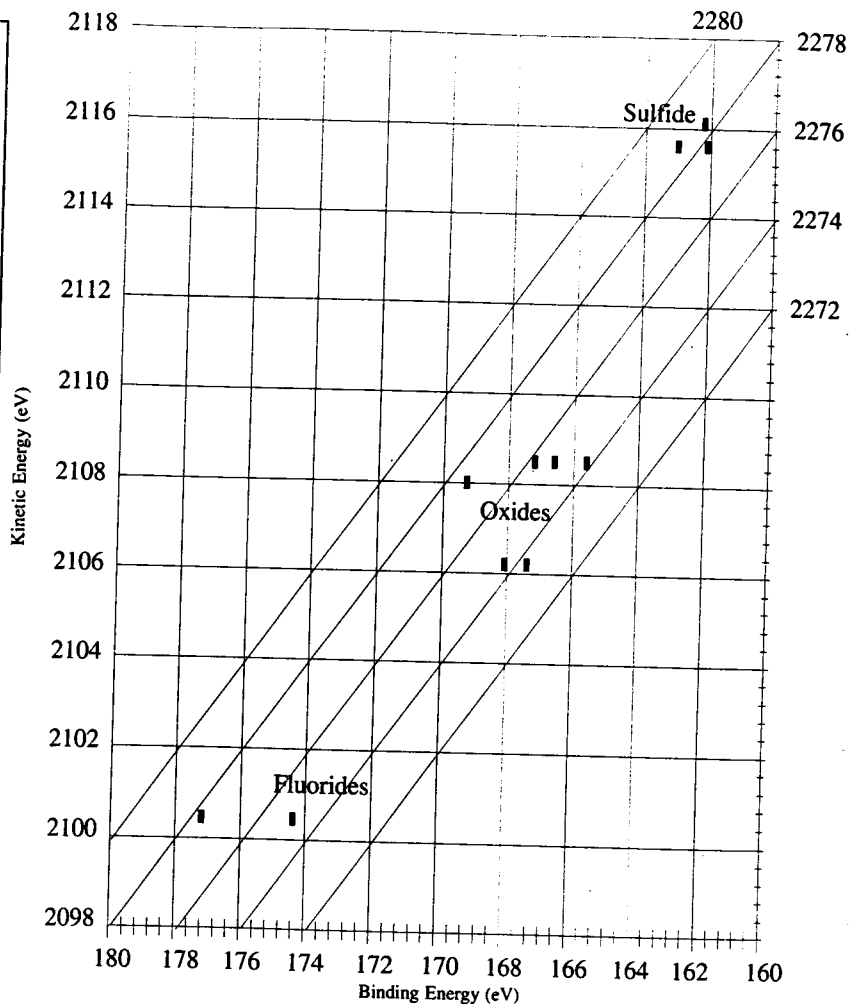
Compound	Al 2p	Al KLL
	Binding Energy (eV)	Kinetic Energy (eV)
Al	72.8	1393.3
AlAs	73.6	1391.2
Al ₂ O ₃ , gamma	73.7	1387.8
Al ₂ O ₃ , alpha	73.9	1388.2
Al ₂ O ₃ , gamma	74.0	1387.8
Al(OH) ₃ , gibbsite	74.0	1387.4
Al ₂ O ₃ , sapphire	74.2	1387.8
AlOOH, boehmite	74.2	1387.6
Al(OH) ₃ , bayerite	74.2	1387.7
Al ₂ O ₃ , gamma	74.3	1387.8
AlN	74.4	1389.0
Al ₂ SiO ₅ , sillimanite	74.6	1386.9



Silicon		
Compound	Si 2p Binding Energy (eV)	Si (KLL) Kinetic Energy (eV)
Si	99.5	1616.6
MoSi ₂	99.6	1617.2
PdSi	99.8	1617.4
Mol Sieve A	101.4	1610.1
Hydroxysodalite	101.7	1610.7
Si ₃ N ₄	101.8	1612.6
Mol Sieve X	102.2	1609.4
Natrolite	102.2	1609.6
Mica, muscovite	102.4	1609.6
Wollastonii, Ca ₃ Si ₃ O ₉	102.4	1610.0
p-Methylsil. (linear)	102.4	1609.4
LiAlSi ₂ O ₆ , spodumene	102.5	1609.6
NaAlSi ₃ O ₈ , albite	102.6	1609.2
AlSiO ₅ , sillimanite	102.6	1609.5
p-Phenylsil. (resin)	102.7	1610.0
Mol Sieve Y	102.8	1608.7
Pyrophyllite	102.9	1609.2
p-Methylsil. (resin)	102.9	1608.8
Kaolinite	103.0	1609.0
Talc, Mg ₃ Si ₄ O ₁₀ (OH) ₂	103.1	1608.9
SiO ₂ , alpha cristobal	103.3	1608.8
H Zeolon	103.3	1608.4
SiO ₂ , gel	103.4	1608.3
SiO ₂ , Vycor	103.5	1608.5
SiO ₂	103.6	1608.8
SiO ₂ , quartz	103.7	1608.6

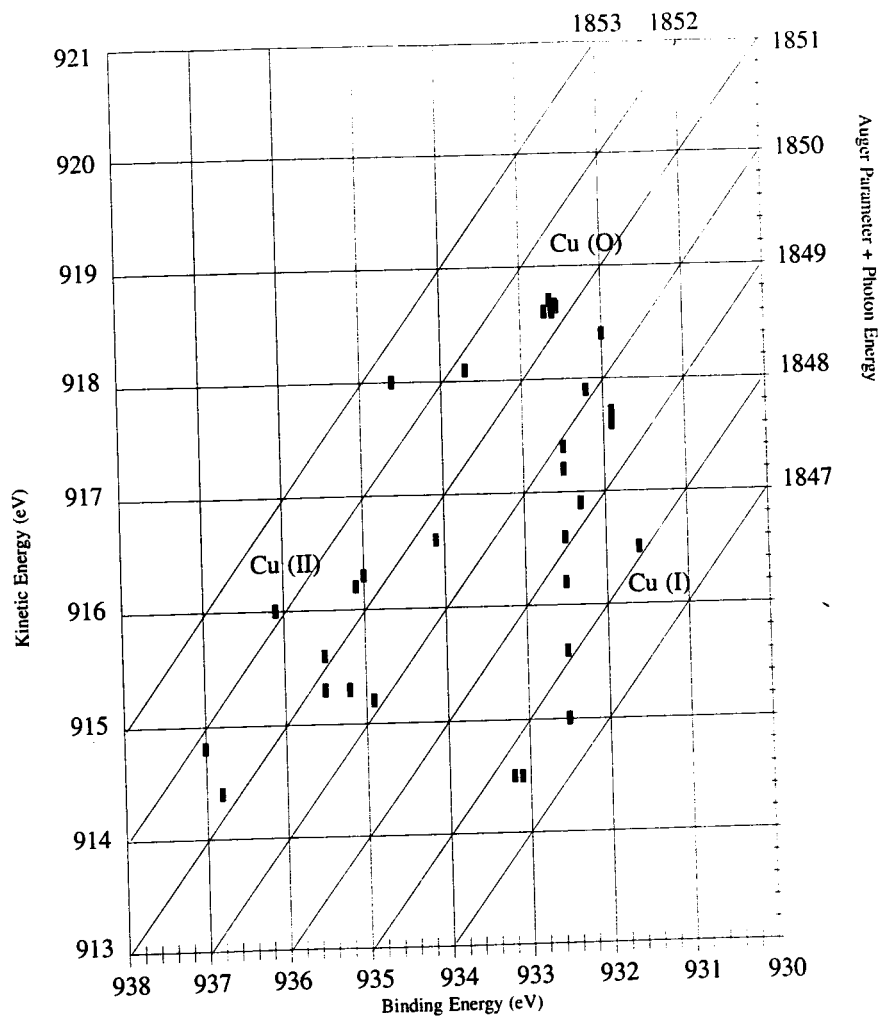


Sulfur		
Compound	S 2p	S KLL
	Binding Energy (eV)	Kinetic Energy (eV)
WS ₂	162.1	2115.6
NiS	162.2	2116.1
WS ₂	163.0	2115.6
Na ₂ SO ₃	165.6	2108.5
Na ₂ SO ₃	166.6	2108.5
Na ₂ SO ₃	167.2	2108.5
SO ₂	167.4	2106.2
SO ₂	168.1	2106.2
CuSO ₄	169.3	2108.0
SF ₆	174.4	2100.5
SF ₆	177.2	2100.5



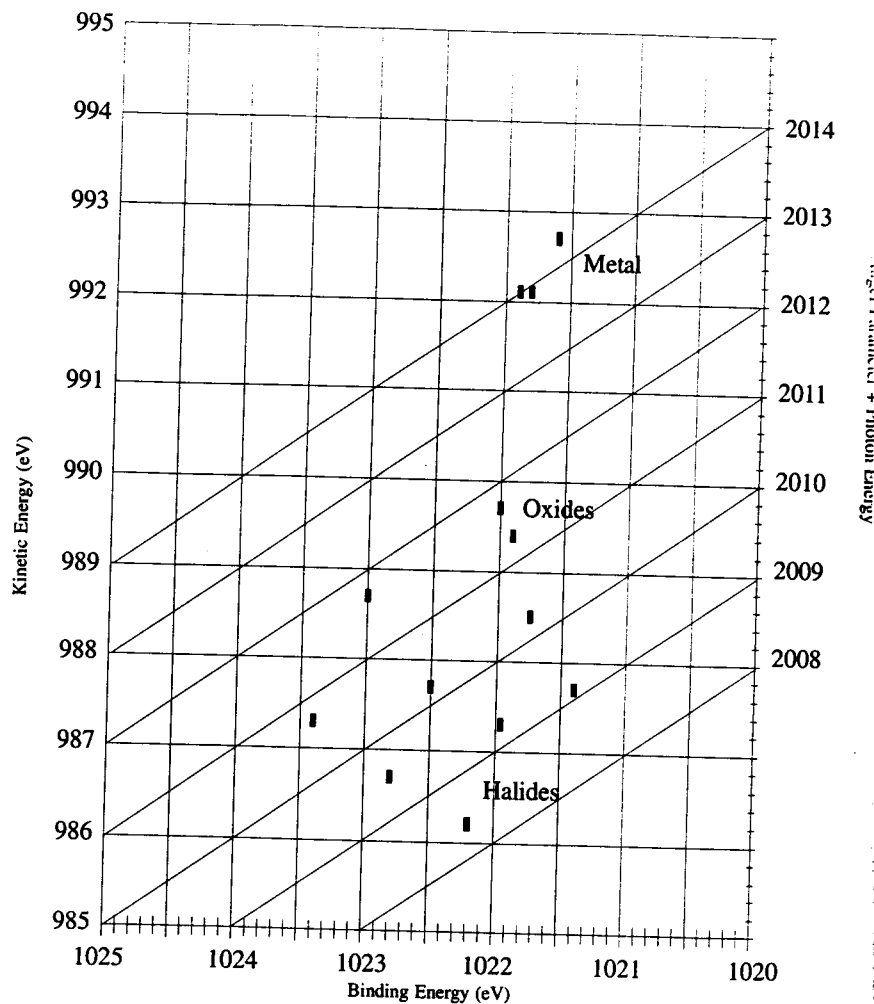
Copper

Compound	Cu 2p Binding Energy (eV)	Cu LMM Kinetic Energy (eV)
Cu ₂ Mo ₃ O ₁₀	931.6	916.5
Cu ₂ Se	931.9	917.6
Cu ₂ AgSe	931.9	917.7
CuSe	932.0	918.4
CuS	932.2	917.9
CuBr ₂	932.3	916.9
Cu ₂ S	932.5	917.4
CuCl	932.5	915.0
CuCl ₂	932.5	915.6
Cu ₂ O	932.5	916.2
Cu ₂ O	932.5	916.2
Cu ₂ O	932.5	916.6
Cu ₂ O	932.5	917.2
Cu	932.6	918.6
Cu	932.6	918.7
Cu ₆₄ Zn ₃₆	932.6	918.6
Cu	932.6	918.6
Cu	932.6	918.7
Cu	932.6	918.6
CuCN	933.1	914.5
CuC(CN) ₃	933.2	914.5
CuO	933.7	918.1
Cu ₃ Mo ₂ O ₉	934.1	916.6
CuMoO ₄	934.1	916.6
CuCr ₂ O ₄	934.6	918.0
CuSiO ₃	934.9	915.2
CuCO ₃	935.0	916.3
Cu(OH) ₂	935.1	916.2
CuCl ₂	935.2	915.3
Cu(NO ₃) ₂	935.5	915.3
CuSO ₄	935.5	915.6
CuF ₂	936.1	916.0
CuF ₂	936.8	914.4
CuF ₂	937.0	914.8

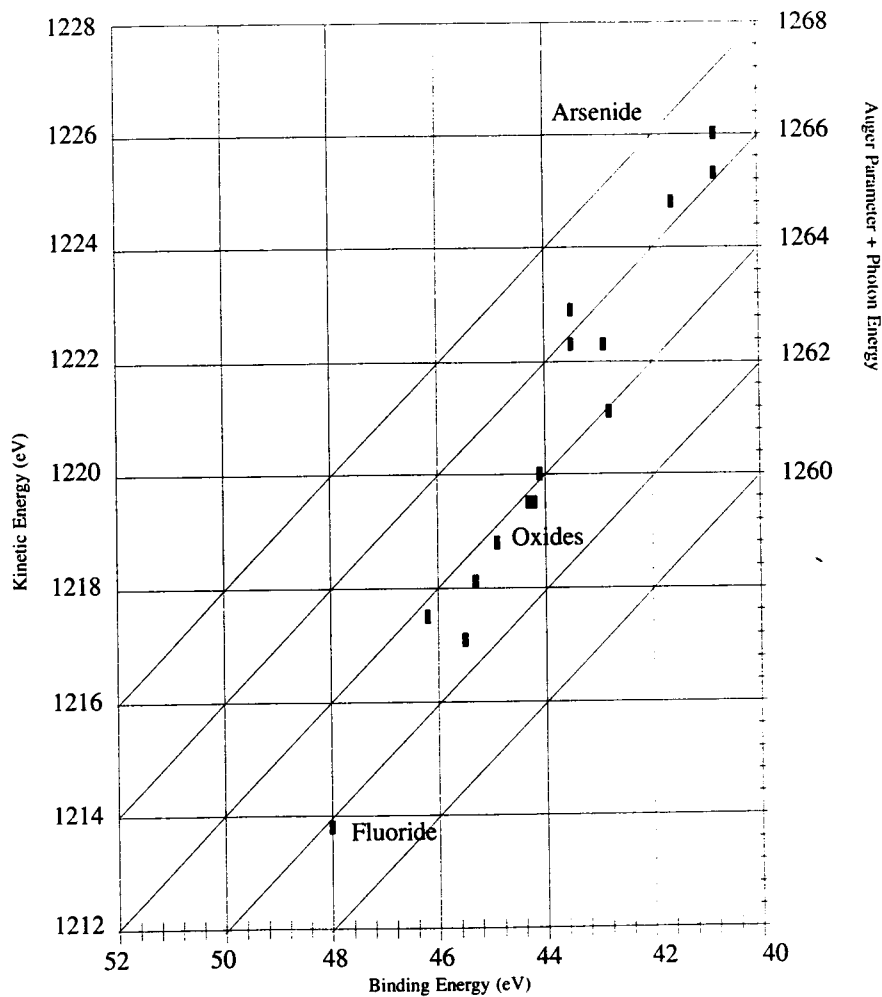


Zinc

Compound	Zn 2p _{3/2} Binding Energy (eV)	Zn LMM Kinetic Energy (eV)
Zn(acac) ₂	1021.4	987.7
Cu ₆₄ Zn ₃₆	1021.6	992.7
ZnO	1021.75	988.5
Zn	1021.8	992.1
Zn	1021.89	992.1
ZnCl ₂	1021.9	989.4
Zn ₄ Si ₂ O ₇ (OH) ₂ · 2H ₂ O	1021.96	987.3
ZnS	1022	989.7
ZnF ₂	1022.2	986.2
ZnO	1022.5	987.7
ZnF ₂	1022.8	986.7
ZnI ₂	1023	988.7
ZnBr ₂	1023.4	987.3

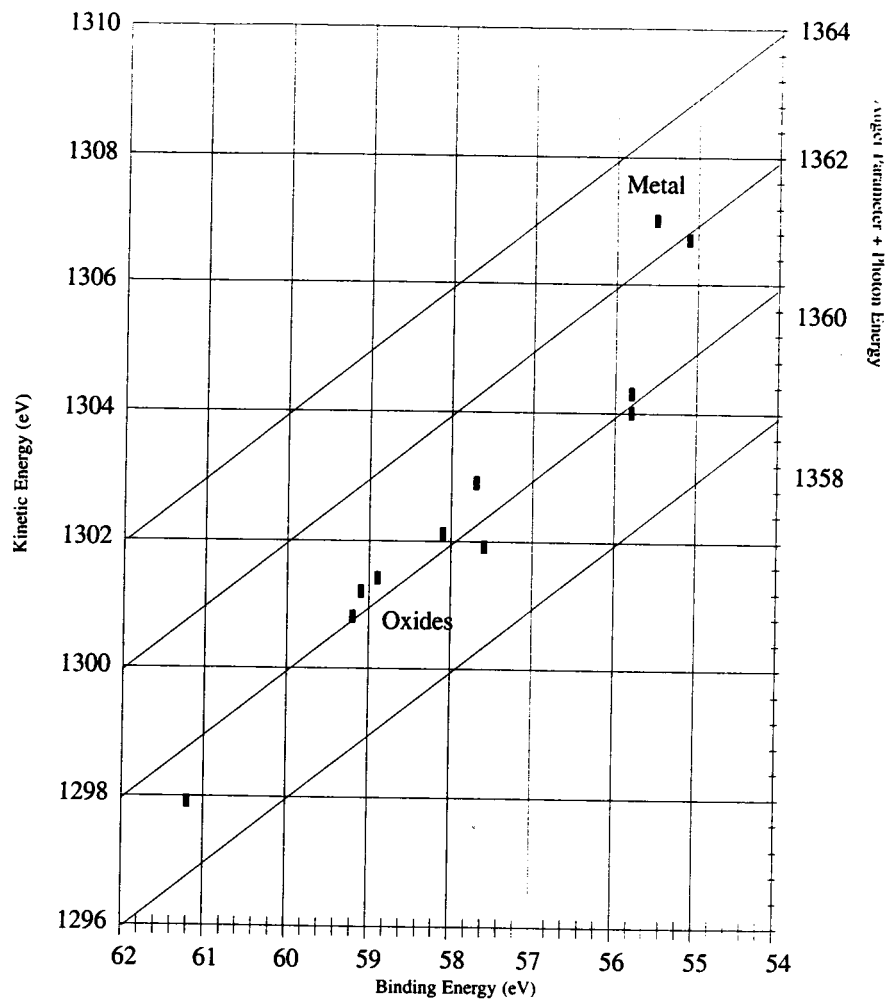


Arsenic		
Compound	As 3d Binding Energy (eV)	As LMM Kinetic Energy (eV)
NbAs	40.8	1226.0
GaAs	40.8	1225.3
As	41.6	1224.8
Ph ₃ As	42.8	1221.1
As ₂ Se ₃	42.9	1222.3
AsI ₃	43.5	1222.9
MeAsI ₂	43.5	1222.3
Ph ₃ AsS	44.1	1220.0
NaAsO ₂	44.2	1219.5
Ph ₃ AsO	44.3	1219.5
As ₂ O ₃	44.9	1218.8
AsBr ₃	45.3	1218.1
NaH ₂ AsO ₄	45.5	1217.1
As ₂ O ₅	46.2	1217.5
KAsF ₆	48.0	1213.8



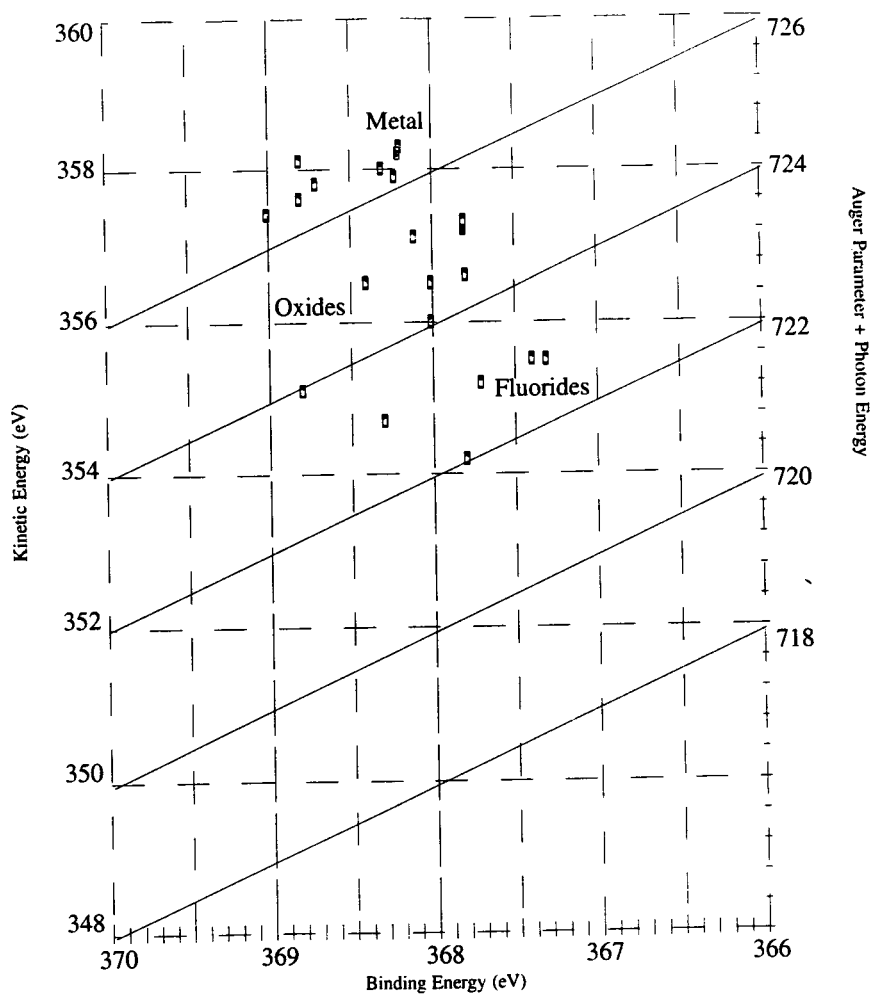
Selenium

Compound	Se 3d Binding Energy (eV)	Se LMM Kinetic Energy (eV)
Se	55.1	1306.7
Se	55.5	1307.0
Ph ₂ Se	55.8	1304.0
Ph ₂ Se ₂	55.8	1304.3
Ph ₂ SeO	57.6	1301.9
Cl ₂ SePh ₂	57.7	1302.9
I ₂ SePh ₂	58.1	1302.1
SeO ₂	58.9	1301.4
Na ₂ SeO ₃	59.1	1301.2
H ₂ SeO ₃	59.2	1300.8
H ₂ SeO ₄	61.2	1297.9



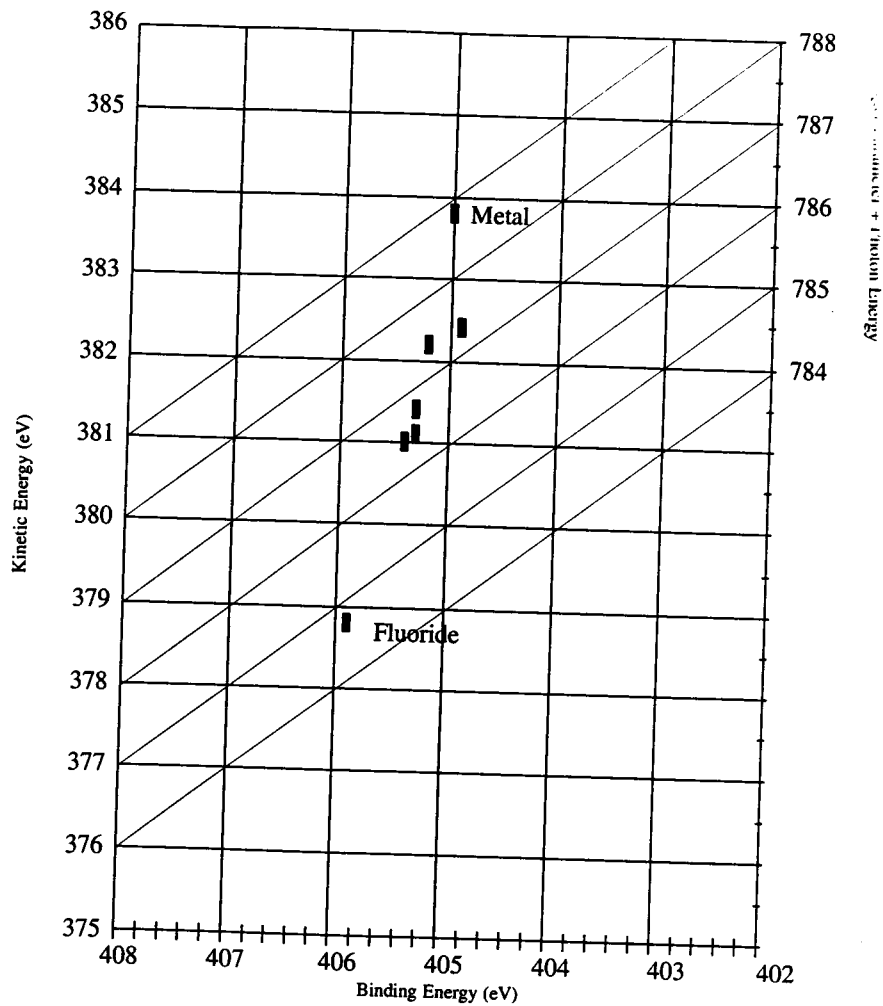
Silver		
Compound	Ag 3d Binding Energy (eV)	Ag M ₄ N ₅ N ₅ Kinetic Energy (eV)
AgF ₂	367.3	355.6*
AgO	367.4	355.5
AgF	367.7	355.3*
CuAgSe	367.8	357.3*
Ag ₂ Se	367.8	357.4*
Ag ₂ O	367.8	356.6
Ag ₂ SO ₄	367.8	354.2
AgI	368.0	356.1*
AgO	368.0	356.6*
Ag ₂ S	368.1	357.2*
Ag	368.2	358.2
Ag	368.2	357.9
Mg ₂₁ Ag ₇₉	368.3	358.1*
Ag ₂ SO ₄	368.3	354.7
Ag ₂ O	368.4	356.6*
Mg ₃₀ Ag ₅₀	368.7	357.9*
Al ₄₀ Ag ₆₀	368.8	357.7*
Mg ₉₇ Ag ₃	368.8	358.2*
AgOOCF ₃	368.8	355.1
Al ₉₅ Ag ₅	369.0	357.5*

* 6.0 eV added to the kinetic energy data on M₅N₅N₅ to obtain kinetic energy of M₄N₅N₅ line.



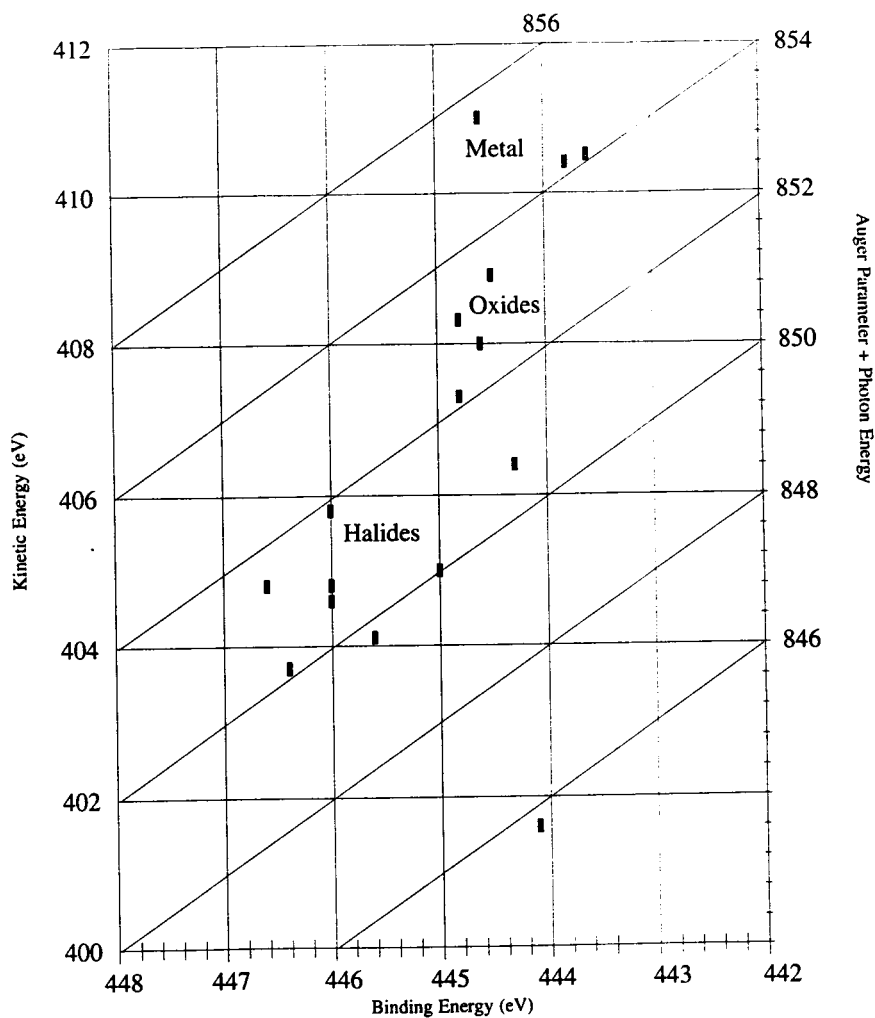
Cadmium

Compound	Cd 3d _{5/2}	Cd MNN
	Binding Energy (eV)	Kinetic Energy (eV)
CdTe	404.9	382.4
Cd	405.0	383.8
CdO	405.2	382.2
CdSe	405.3	381.4
CdS	405.3	381.1
CdI ₂	405.4	381.0
CdF ₂	405.9	378.8

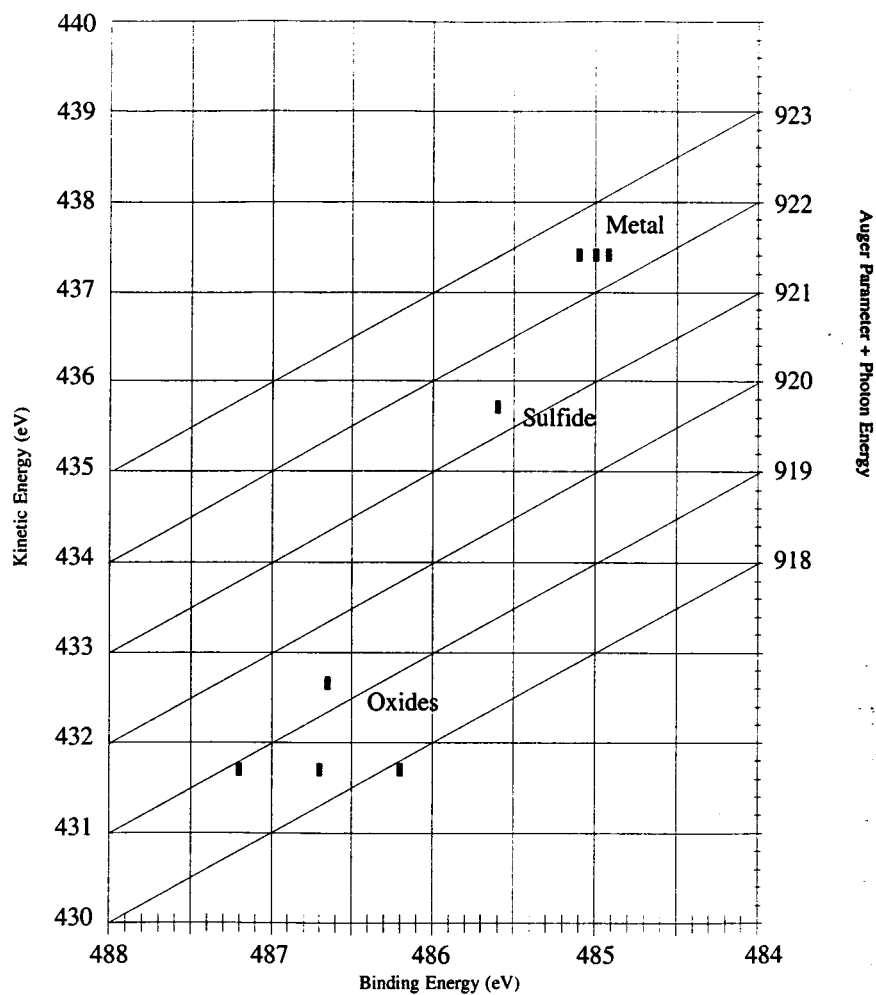


Indium

Compound	In 3d _{5/2}	In MNN
	Binding Energy (eV)	Kinetic Energy (eV)
In ₉₅ Sn ₅	443.6	410.5
In	443.8	410.4
InSb	444.1	401.6
In ₂ O ₃	444.3	406.4
In ₂ Te ₃	444.5	408.9
InP	444.6	408.0
InP	444.6	411.0
In ₂ Se ₃	444.8	408.3
In ₂ S ₃	444.8	407.3
In(OH) ₃	445.0	405.0
(NH ₄) ₃ InF ₆	445.6	404.1
InI ₃	446.0	405.8
InBr ₃	446.0	404.8
InCl ₃	446.0	404.6
InF ₃	446.4	403.7
InBr ₃	446.6	404.8

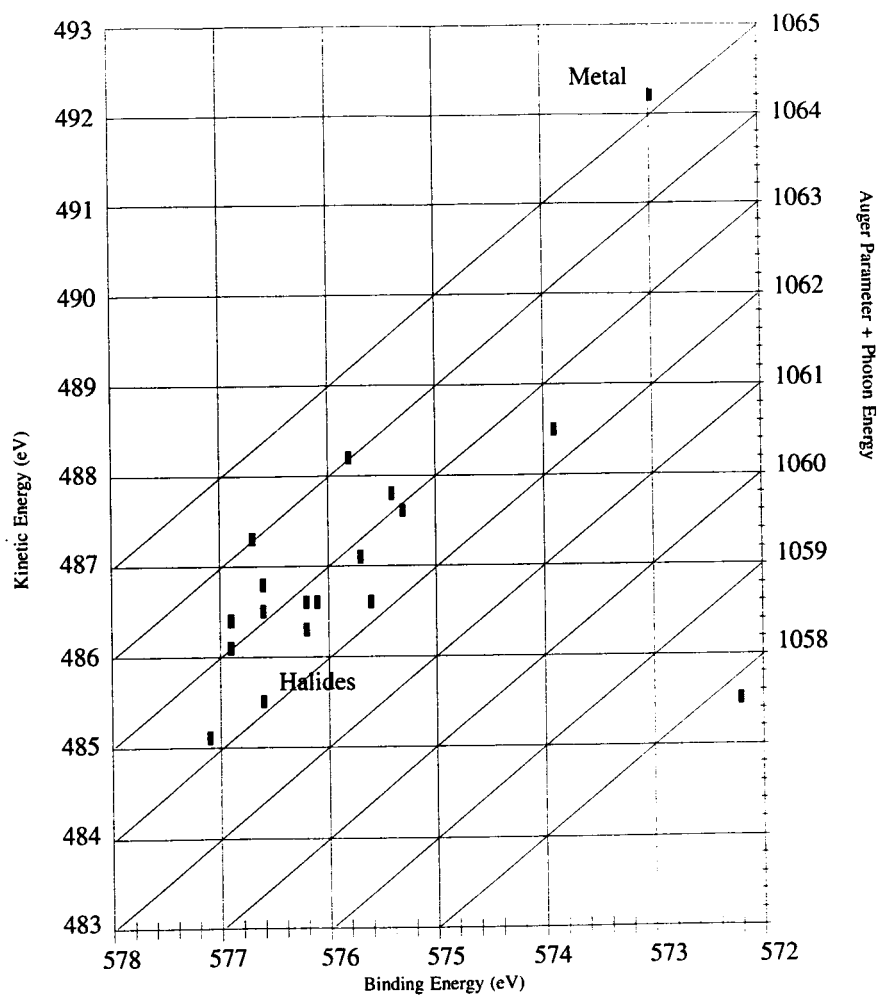


Tin		
Compound	Sn 3d _{5/2} Binding Energy (eV)	Sn MNN Kinetic Energy (eV)
Sn	484.9	437.4
Sn	485.0	437.4
Sn	485.1	437.4
SnS	485.6	435.7
Na ₂ SnO ₃	486.2	431.7
SnO ₂	486.7	432.7
Na ₂ SnO ₃	486.7	431.7
Na ₂ SnO ₃	487.2	431.7
NaSnF ₃	487.4	430.8



Tellurium

Compound	Te 3d _{5/2} Binding Energy (eV)	Te MNN Kinetic Energy (eV)
Na ₂ Te	572.2	485.5
Te	573.0	492.2
Ph ₂ Te ₂	573.9	488.5
I ₂ TeEt ₂	575.3	487.6
I ₂ TePh ₂	575.4	487.8
I ₂ TeMe ₂	575.6	486.6
TeO ₂	575.7	487.1
I ₃ TePh	575.8	488.2
p-tolylTeOOH	576.1	486.6
Cl ₂ TePh ₂	576.2	486.3
Br ₂ TePh ₂	576.2	486.6
TeO ₃	576.6	485.5
Br ₃ TePh	576.6	486.8
Br ₃ TeBu	576.6	486.5
TeBr ₂	576.7	487.3
TeCl ₄	576.9	486.1
(NH ₄) ₂ TeCl ₆	576.9	486.4
Te(OH) ₆	577.1	485.1



Appendix B. Chemical States Tables

This compilation of all the elements, listed alphabetically, provides specific binding energies of various compounds and pure elements, and a reference in abbreviated notation. When Auger lines are listed, they are in kinetic energy. For compounds with more than one chemical state, an asterisk denotes the atom whose binding energy is listed. The references are expanded in Appendix C. Any listing with a Φ refers to the work contained in this handbook.

This appendix, most of which was compiled by Dr. Charles Wagner for Physical Electronics, is part of the chemical state identification algorithm of the PHI software and is also the basis for the XPS database SRD-20 of the National Institute for Standards and Technology (NIST). Further references may also be found in the journal Surface Science Spectra published by the American Vacuum Society.

Ag 3d					
Ag	368.3	Φ	Ag ₂ Se(M ₅ N ₅ N ₅)	351.4	RRD78
Ag	368.2	Asam76	Ag ₂ S(M ₅ N ₅ N ₅)	351.2	RRD78
Ag	368.2	BiSw80	AgI(M ₅ N ₅ N ₅)	350.1	GaWi77
Ag	368.1	BiSw80	AgF(M ₅ N ₅ N ₅)	349.3	GaWi77
Ag	368.2	BiSw80	AgF ₂ (M ₅ N ₅ N ₅)	349.6	GaWi77
Ag	368.2	JHBK73	Ag ₂ O	356.6	Scho73
Ag	368.2	NyMa80	Ag ₂ O(M ₅ N ₅ N ₅)	350.6	RRD78, GaWi77
Ag	368.2	HGW75, Scho73, WRDM79,	AgO	355.5	WRDM79
Ag	368.2	GaWi77, SFS77, Wagn75	AgO(M ₅ N ₅ N ₅)	350.6	GaWi77
Ag	368.2	RRD78, Scho72	Ag ₂ SO ₄	354.2	Wagn75
Ag	368.2	HSBS81	Ag ₂ SO ₄	354.7	TMR80
Ag ₉₅ Sn ₅	368.0	WeAn80	AgOOCF ₃	355.1	Wagn75
Al ₄₀ Ag ₆₀	368.8	WeAn80			
Al ₉₅ Ag ₅	369.0	WeAn80	Al 2p		
Mg ₂₁ Ag ₇₉	368.3	WeAn80	Al	72.9	Φ
Mg ₃₀ Ag ₅₀	368.7	WeAn80	Al ₂ O ₃ , sapphire	74.4	Φ
Mg ₉₇ Ag ₃	368.8	WeAn80	Al	72.8	LMKJ75, Tayl82, WPHK82,
Ag ₂ Yb	368.8	WWC78			WRDM79, WaTa80
CuAgSe	367.8	RRD78	AlB ₂	71.9	MECC73
Ag ₂ Se	367.8	RRD78	AlAs	73.6	Tayl82
Ag ₂ S	368.1	RRD78	AJGaAs	73.6	Tayl82
AgI	368.0	GaWi77	Fe ₃ Al	73.4	ShTr75
AgF	367.7	GaWi77	LiAlH ₄	75.6	MSC73
AgF ₂	367.3	GaWi77	AlN	74.4	MSC73
Ag ₂ O	367.8	HGW75, GaWi77, Scho73	Al ₂ S ₃	74.6	MSC73
Ag ₂ O	368.4	RRD78	AlI ₃	74.6	MSC73
AgO	367.4	HGW75, GaWi77, Scho73	AlBr ₃	75.2	MSC73
AgO	368.0	WRDM79	AlCl ₃	74.7	MSC73
Ag ₂ CO ₃	367.5	HGW75	AlF ₃	76.3	MSC73
Ag ₂ SO ₄	367.8	TMR80	Al ₂ (MoO ₄) ₃	74.2	PCLH76
Ag ₂ SO ₄	368.3	Wagn75	Al ₂ (WO ₄) ₃	74.3	NgHe76
AgOOCF ₃	368.8	Wagn75	CoAl ₂ O ₄	73.6	PCLH76
Ag(OAc)	368.4	HHDD81	MgAl ₂ O ₄	74.7	HNUW78
Ag(3-Cl-pyridin) ₂ NO ₃	368.6	SmWa77	NiAl ₂ O ₄	74.2	LFWS79, NgHe76
			Al ₂ O ₃	74.3	Nefe82, MSC73, NSLS77
			Al ₂ O ₃	74.7	KIHe83, NGDS75
Ag M₄N₅N₅			Al ₂ O ₃ , sapphire	74.2	Tayl82, WPHK82
Ag	357.9	WRDM79	Al ₂ O ₃ , alpha	73.9	WPHK82
Ag	358.2	Wagn75	Al ₂ O ₃ , gamma	73.7	WPHK82
Ag (M ₅ N ₅ N ₅)	351.9	RRD 78, PWA 79	Al ₂ O ₃ , gamma	74.0	Barr83
Ag (M ₅ N ₅ N ₅)	351.6	GaWi77	Al ₂ O ₃ , gamma	74.3	NgHe76
Ag	358.3	Scho73, FKWF77	AlO ₂ H, boehmite	74.2	Tayl82, WPHK82
Ag	351.7	WeAn80	Al(OH) ₃ , bayerite	74.2	Tayl82, WPHK82
Al ₄ OAg ₆₀ (M ₅ N ₅ N ₅)	351.5	WeAn80	Al(OH) ₃ , gibbsite	74.0	WPHK82
Al ₉₅ Ag ₅ (M ₅ N ₅ N ₅)	351.5	WeAn80	Al ₂ SiO ₅ , kyanite	74.7	AnSw74
Mg ₂₁ Ag ₇₉ (M ₅ N ₅ N ₅)	352.1	WeAn80	Al ₂ SiO ₅ , mullite	74.8	AnSw74
Mg ₃₀ Ag ₅₀ (M ₅ N ₅ N ₅)	351.9	WeAn80	Al ₂ SiO ₅ , sillimanite	74.6	AnSw74, WPHK82
Mg ₉₇ Ag ₃ (M ₅ N ₅ N ₅)	352.2	WeAn80	Albite, NaAlSi ₃ O ₈	74.3	WPHK82
CuAgSe (M ₅ N ₅ N ₅)	351.3	RRD78			

Bentonite	75.0	Barr83	As ₄ S ₄	43.1	BWWI76
Kaolinite	74.6	Barr83, WPHK82	As ₂ S ₃	43.4	BWWI76
Mica, muscovite	74.3	WPHK82	As ₂ S ₅	44.4	SMAV72
Natrolite	74.3	WPHK82	AsI ₃	43.5	BWWI76
Pyrophyllite	74.7	WPHK82	AsBr ₃	45.3	BWWI76
Spodumene	74.3	WPHK82	As ₂ O ₃	44.9	LPGC77, MINN78, Tayl82, WRDM79
H Zeolon	74.8	WPHK82			Bert81, BWWI76, MINN78, SMAV72
Hydroxysodalite	75.0	WPHK82	As ₂ O ₅	46.2	SMAV72
Mol Sieve A	73.6	WPHK82, Barr83			WRDM79
Al(acac) ₃	72.9	MSC73	KH ₂ AsO ₄	46.7	Tayl82, WRDM79
Al KLL					
Al	1393.3	WPHK82, WaTa80	NaH ₂ AsO ₄	45.5	SMAV72
AlAs	1391.2	Tayl82	NaAsO ₂	44.2	Tayl82, WRDM79
AlN	1389.0	TaRa81	K ₃ AsO ₄	44.4	SMAV72
Al ₂ O ₃ , sapphire	1387.8	Tayl82, WPHK82	Na ₃ AsO ₄	44.9	SMAV72
Al ₂ O ₃ , alpha	1388.2	WPHK82	Na ₄ As ₂ O ₇	45.4	SMAV72
Al ₂ O ₃ , gamma	1387.8	WPHK82	KAsF ₆	48.0	SMAV72, WRDM79
AlOOH	1387.6	WPHK82, Tayl82	LiAsF ₆	49.4	SMAV72
Al(OH) ₃ , bayerite	1387.7	WPHK82, Tayl82	Ph ₃ As	42.8	HVV79, SMAV72
Al(OH) ₃ , gibbsite	1387.4	WPHK82	Ph ₃ AsS	44.1	BWWI76, HVV79
Al ₂ SiO ₅ , sillimanite	1386.9	WPHK82	Ph ₃ AsO	44.3	BWWI76, SMAV72, HVV79
Albite, NaAlSi ₃ O ₈	1386.5	WPHK82	Ph ₃ As(OH) ₂	44.5	SMAV72
Kaolinite	1386.7	WPHK82	MeAsI ₂	43.5	BWWI76
Mica, muscovite	1387.1	WPHK82	Ph ₄ AsI	44.6	HVV79
Natrolite	1386.5	WPHK82	Ph ₄ AsBr	44.6	HVV79, SMAV72
Pyrophyllite	1386.8	WPHK82	As LMM		
Spodumene	1387.1	WPHK82	As	1224.8	Wagn75, BWWI76
H Zeolon	1385.5	WPHK82	NbAs	1226.0	BWWI76
Hydroxysodalite	1386.4	WPHK82	GaAs	1225.3	Tayl82, WRDM79
Mol Sieve	1386.9	WPHK82	As ₂ Te ₃	1225.0	BWWI76
Ar 2p					
Ar in Si	241.9	Φ	As ₂ Se ₃	1223.3	BWWI76
Ar in Ag	241.2	CiHa74	As ₂ S ₃	1222.1	BWWI76
Ar in Ag	241.9	KiWi75	AsI ₃	1222.9	BWWI76
Ar in Au	240.3	CiHa74	AsBr ₃	1218.1	BWWI76
Ar in Au	240.7	KiWi75	As ₂ O ₃	1218.8	Tayl82, WRDM79, BWWI76
Ar in Cu	241.1	CiHa74	As ₂ O ₅	1217.5	BWWI76
Ar in Pt	240.4	KiWi75	NaH ₂ AsO ₄	1217.1	WRDM79
Ar in graphite	241.8	KiWi75	NaAsO ₂	1219.5	Tayl82, WRDM79
Ar in graphite	241.5	WRDM79	K ₂ AsF ₆	1213.8	WRDM79
As 3d					
As	41.6	Φ	Ph ₃ As	1221.1	BWWI76
As	41.6	Bert81, BWWI76, MINN78, SMAV72, UeOd81	Ph ₃ AsS	1220.0	BWWI76
NbAs	40.8	BWWI76	Ph ₃ AsO	1219.5	BWWI76
AlAs	41.0	Tayl82	MeAsI ₂	1222.3	BWWI76
AlGaAs	41.0	Tayl82	Au 4f		
GaAs	40.8	LPMK74	Au	84.0	Φ
GaAs	40.9	GGVL79, WRDM79, Tayl82, MINN78, IMNN79	Au	84.1	Asam76
InAs	40.6	LPMK74	Au	84.0	BiSw80
As ₂ Se ₃	42.9	BWWI76, UeOd82	Au	83.9	BiSw80
			Au	84.1	PEJ 82
			Au	84.2	ALMP82
			AuSn	84.5	FHPW73
			AuSn ₄	85.1	FHPW73
			YbAu ₂	84.6	WVC 78
			ClAuPh ₃ P	85.4	BMCK77, VVSW77

ClAu(Ph ₃ P) ₂	85.4	BMCK77			
Cl ₃ AuPh ₃ P	87.3	BMCK77			
(Ph ₃ P)AuNO ₃	85.4	BMCK77			
ClAu(Ph ₃ As)	85.2	VVSW77			
(-AuSPEt ₂ S-) ₂	84.8	VVSW77			
(-AuCH ₂ PEt ₂ CH ₂ -) ₂	84.0	VVSW77			
Au M₅N₇N₇					
Au	2015.8	PEJ82			
Au(M ₄ N ₇ N ₇)	2101.6	WaTa80			
Au	2015.7	WaTa80			
B 1s					
B	189.4	Φ			
B	187.3	HHJ70			
B ₂ C	186.5	HHJ70			
AlB ₂	188.5	MECC73			
Co ₂ B	189.1	MECC73			
CoB	188.1	MECC73			
Fe ₂ B	188.4	MECC73			
FeB	187.9	MECC73			
HfB ₂	188.3	MECC73			
MnB ₂	187.2	MECC73			
Mo ₂ B ₅	187.7	BrWh78			
MoB ₂	188.4	MECC73			
TiB ₂	187.5	MECC73			
VB ₂	188.3	MECC73			
W ₂ B ₅	187.9	MECC73			
CrB ₂	188.0	MECC73			
BN	190.5	HJGN70, KOK83, WRDM79			
Na ₃ BO ₆	192.0	HHJ70			
B ₂ O ₃	192.0	BrWh78			
B ₂ O ₃	193.3	NGDS75			
NaBF ₄	194.9	HHJ70, RNS73			
NF ₃ BF ₄	195.2	RNS73			
NaBH ₄	187.2	HHJ70			
H ₂ BO ₃	193.0	HHJ70			
Na ₂ B ₄ O ₇ · 10H ₂ O	192.6	HHJ70			
B ₁₀ H ₁₄	187.8	HHJ70			
Me ₃ NB ₃ H ₈	187.2	HHJ70			
NaBPh ₄	187.5	HHJ70			
NH ₃ BF ₃	194.9	BCGH73			
C ₂ H ₃ NBF ₃	194.3	BCGH73			
EtNH ₂ BF ₃	194.6	BCGH73			
Me ₃ NBF ₃	193.6	HHJ70			
NaBH(OMe) ₃	192.1	HHJ70			
Ph ₃ PBF ₃	193.3	HHJ70			
Ph ₃ POBF ₃	193.8	HHJ70			
Ph ₃ POBCl ₃	192.6	HHJ70			
Ph ₃ PBCl ₃	192.7	HHJ70			
CH ₃ CNBF ₃	195.5	BCGH73			
ClC ₆ H ₄ Bi(OH) ₂	191.7	HHJ70			
FC ₆ H ₄ Bi(OH) ₂	191.7	HHJ70			
(Et ₃ P) ₂ PtB ₁₀ H ₁₂	188.9	Rigg72			
(Ph ₃ P) ₂ PtB ₁₀ H ₁₂	188.5	Rigg72			
Ba 3d_{5/2}					
Ba	780.6			Φ	
Ba	779.3			VaVe80	
BaS	779.8			SiWo80	
BaO	779.9			WRDM79	
BaO	779.6			SiWo80	
BaO	779.1			VaVe80	
Ba(NO ₃) ₂	780.7			CLSW83	
BaCO ₃	779.9			CLSW83	
BaSO ₄	780.8			Wagn77	
BaSO ₄	780.4			CLSW83	
BaSO ₄	779.9			SiWo80	
BaSO ₄	778.9			ACHT73	
BaMoO ₄	779.1			NFS82	
BaRh ₂ O ₄	779.6			NFS82	
Ba MNN					
Ba	602.0			VaVe80	
BaO	597.5			WRDM79	
BaO	598.4			VaVe80	
BaSO ₄	596.1			Wagn77	
Be 1s					
Be	111.8			Φ	
Be	111.7			HJGN70, SMKM77, WRDM79	
BeO	113.8			HJGN70, KOK83, NFS82	
BeMoO ₄	113.7			NFS82	
BeRh ₂ O ₄	113.8			NFS82	
BeF ₂	115.3			NKBP73	
BeF ₂	116.1			HJGN70	
NaBeF ₃	115.3			NKBP73	
Na ₂ BeF ₄	114.7			NKBP73	
Bi 4f					
Bi	157.0			Φ	
Bi	156.9			SFS77	
Bi	157.0			LKMP73	
Bi	157.0			WRDM79, MSV73	
Bi ₂ S ₃	158.9			MSV73	
BiI ₃	159.3			MSV73	
BiF ₃	160.8			MSV73	
Bi ₂ O ₃	158.8			NGDS75	
Bi ₂ O ₃	159.3			MSV73	
Bi ₂ O ₃	159.8			DSBG82	
Bi ₂ O ₃	159.9			MSV73	
BiOCl	159.1			MSV73	
NaBiO ₃	159.1			MSV73	
Bi ₂ MoO ₆	158.3			MaWo75	
Bi ₂ Ti ₂ O ₇	159.7			MSV73	
(BiO) ₂ Cr ₂ O ₇	159.6			MSV73	
Bi ₂ (SO ₄) ₃ · H ₂ O	161.2			MSV73	
Br 3d					
KBr	68.8			Φ	
CsBr	68.1			MVS73	
CsBr	69.6			Shiq78	

RbBr	68.4	MVS73			
KBr	68.8	MVS73, WaTa80			
NaBr	68.8	MVS73, Shi78			
LiBr	69.2	MVS73			
CdBr ₂	69.2	SATD73			
CuBr ₂	68.9	VWHS81			
HgBr ₂	69.0	SATD73			
PbBr ₂	68.7	Nefe82			
ZnBr ₂	70.0	SATD73			
Co(NH ₃) ₆ SbBr ₆	68.9	Tric74			
Ni(NH ₃) ₆ Br ₂	68.7	NZB 78			
Pt(NH ₃) ₄ Br ₂	68.4	SNMK78			
K ₂ PtBr ₄	69.3	SNMK78			
K ₂ PtBr ₆	69.2	SNMK78			
Cs ₃ Sb ₂ Br ₉	70.8	Tric71			
Rb ₃ Sb ₂ Br ₉	70.1	Tric74			
Bromanil	70.1	OYK74			
Ph ₄ AsBr	66.7	HVV79			
Ph ₄ SbBr	68.0	HVV79			
(Me ₄ N) ₂ ZnBr ₄	67.8	EMGK74			
(Et ₄ N) ₂ MnBr ₄	67.9	EMGK74			
(Et ₄ N) ₂ NiBr ₄	68.9	EMGK74			
H ₃ POBBr ₃	69.3	HVV79			
H ₃ PBBBr ₃	69.6	HVV79			
Br ₂ Pt(CH ₃ CONH) ₄	68.7	NeSa78			
Br LMM					
LiBr	1389.2	Wagn78			
NaBr	1388.3	Wagn78			
KBr	1388.0	WaTa80			
KBrO ₃	1384.4	Wagn78			
Cl ₆ H ₈ Me ₃ NBr	1390.1	Wagn78			
C 1s					
Graphite	284.5	Φ			
Graphite	284.3	JHBK73			
Cr ₃ C ₂	282.8	RHJF69			
Fe ₃ C	283.9	ShTr75			
HfC	280.8	RHJF69			
Mo ₂ C	282.7	RHJF69			
NbC	281.9	RHJF69			
Ni ₃ C	283.9	SiLe78			
TaC	281.9	RHJF69			
TiC	281.6	RHJF69, IKIM73			
VC	282.2	RHJF69			
WC	282.8	RHJF69, CoRa76			
ZrC	281.1	RHJF69			
KCN	286.1	Vann76			
NaCN	286.2	Vann76			
K ₃ Co(CN) ₆	285.9	Vann76			
K ₃ Cr(CN) ₆	283.9	Vann76, ZeHa71			
K ₃ Fe(CN) ₆	283.9	Vann76, ZeHa71			
K ₄ Fe(CN) ₆	283.5	Vann76			
K ₃ Mn(CN) ₆	284.0	Vann76			
Na ₄ Mn(CN) ₆	284.0	Vann76			
K ₄ V(CN) ₆	285.5	Vann76			
			Cr(CO) ₆	287.9	BCGH72, BCHM72, KTWY76, PFD73
			Co(CO) ₃ NO	288.2	BCGH72
			Fe(CO) ₅	288.0	BCGH72
			Fe(CO) ₂ (NO) ₂	288.2	BCGH72
			Mn ₂ (CO) ₁₀	287.5	VWVB77
			Ni(CO) ₄	288.2	BCGH72
			(Mn(CO) ₄ Br) ₂	287.6	VWVB77
			BrMn(CO) ₅	288.0	VWVB77
			Ag ₂ CO ₃	288.4	HGW 75
			BaCO ₃	289.4	CLSW83
			CaCO ₃	289.6	CLSW83
			CdCO ₃	289.3	HGW 75
			Li ₂ CO ₃	289.8	CSFG79
			Na ₂ CO ₃	289.4	GHHL70, HHDD81
			NaHCO ₃	290.0	GHHL70
			SiCO ₃	289.5	CLSW83
			CS ₂	287.0	GHHL70
			CO ₂	291.9	GHHL70
			CCl ₄	292.4	GHHL70
			ClOF ₂	293.9	GHHL70
			CF ₄	296.7	GHHL70
			Cyclohexane	285.2	GHHL70
			Benzene	284.7	GHHL70, LaFo76, CKAM72
			C ₆ H ₅ C*H ₃	284.7	CKM71
			C ₆ H ₅ CH ₃ (C*CH ₃)	285.1	CKM71
			C ₆ H ₅ CH ₃ (C*-H)	285.0	CKM71
			Fe(C ₃ H ₅) ₂	284.5	BCDH73
			Cr(C ₆ H ₆) ₂	284.4	KTWY76
			CH ₃ C*H ₂ OH	286.3	GHHL70
			CH ₃ COOC*H ₂ CH ₃	286.9	GHHL70
			C ₆ F ₆	289.5	CKAM72
			Inositol	286.7	GHHL70
			Hydroquinone	286.4	GHHL70
			(C*HCOH) ₃	284.8	OYK74
			(CHC*OH) ₃	286.6	GHHL70
			(CH ₃ C*H ₂) ₂ O	286.5	GHHL70
			HCHO	287.7	GHHL70, CITH78
			(CH ₃ C*HO) ₃	287.6	GHHL70
			CH ₃ C*OCH ₃	287.9	GHHL70
			CF ₃ C*OCH ₃	288.5	GHHL70
			C*F ₃ COCH ₃	292.6	GHHL70
			(CO) ₆	288.3	GHHL70
			CH ₃ C*OOH	289.3	GHHL70
			CH ₃ C*OONa	288.2	HHDD81
			CH ₃ C*OONa	288.8	GHHL70
			CH ₃ C*OOAg	288.3	HHDD81
			HOCCCCOOH	289.9	GHHL70
			(COONa) ₂	289.0	GHHL70
			CF ₃ C*OOEt	290.4	GHHL70
			C*F ₃ COOEt	292.9	GHHL70
			Cl ₃ C*COONa	289.5	GHHL70
			Cl ₃ CC*OONa	288.3	GHHL70
			F ₃ C*COONa	292.1	GHHL70
			F ₃ CC*OONa	288.9	GHHL70
			p-Benzoquinone	287.4	OYK74

Cr(acac) ₃	286.0	ZeHa71	PVA (-CH ₂ C*HOH-)n	286.1	PRCV77
CH ₃ C*H ₂ OCOCI	287.1	GHHL70	Cellulose	286.2	Wagn81
EtOC*OCl	290.8	GHHL70	PEO (-CH ₂ C*H ₂ O-)n	286.1	Wagn81
(PhO) ₂ CO	290.7	ClTh78	poly (-CH ₂ CH ₂ C=O-)n	287.4	Wagn81
HC*(OCH ₃) ₃	289.7	GHHL70	C ₆ H ₄ (C*OOH) ₂	288.9	Wagn81
HCOONH ₄	238.4	GHHL70	HOOC*(CH ₂) _n C*OOH	288.9	Wagn81
OC*(OCH ₃) ₂	291.2	GHHL70	Sodium Stearate	288.3	Wagn81
O(C*H ₂ COOH) ₂	286.7	GHHL70	Mylar Polyester C*-H	284.85	Φ
O(CH ₂ C*OOH) ₂	289.5	GHHL70	Mylar Polyester C*-O	286.3	Wagn81
CH ₃ C*H ₂ Cl	286.1	GHHL70	Mylar Polyester C*O ₂	288.7	Wagn81
CH ₂ Br ₂	287.1	GHHL70	Polycarbonate-OC*O ₂ -	290.4	Wagn81
CH ₂ Cl ₂	287.8	GHHL70	Teflon (-CF ₂ CF ₂ -)n	292.2	CFK73
HCF ₃	294.7	GHHL70	(-C*FHCF ₂ -)n	289.3	CFK73
HCCl ₃	289.6	GHHL70	(-CFHC*F ₂ -)n	291.6	CFK73
C ₆ H ₅ Cl (C*Cl)	287.1	CKM71	(-CFHC*FH-)n	288.4	CFK73
C ₆ H ₅ Cl(C*H)	285.7	CKM71	(-C*H ₂ CF ₂ -)	286.3	CFK73
C ₆ H ₅ Br	285.1	LaFo76	(-CH ₂ C*F ₂ -)n	290.8	CFK73
C ₆ H ₅ F(C*F)	287.8	CKM71	(-C*H ₂ CFH-)n	285.9	CFK73
C ₆ H ₅ F(C*H)	285.6	CKM71	(-CH ₂ C*FH-)n	288.0	CFK73
C ₆ HCl ₅	286.1	CKAM75	PVC (-C*H ₂ CHCl-)	284.9	PRCV77
C ₆ HF ₅ (C*H)	286.9	CKAM72	PVC (-CH ₂ C*HCl-)	286.5	PRCV77
C ₆ HF ₅ (C*F)	289.2	CKAM72			
C ₆ F ₆	288.7	GHHL70			
Cl ₂ FCCFCI ₂	291.7	GHHL70	Ca 2p		
ClF ₂ C*CFCl ₂	292.9	GHHL70	Ca	346.3	Φ
C*H ₃ CN	286.3	BCGH73	CaCO ₃	346.6	Φ
CH ₃ C*N	287.2	BCGH73	Ca	345.9	VaVe80
CH ₃ CONH ₂	288.4	SNMK78	Ca	346.8	SMKM77
EtNH ₂	285.6	BCGH73, GHHL70	CaH ₂	346.7	FMUK77
EtNH ₂ BF ₃	286.8	BCGH73	CaSe	345.9	FMUK77
PhNH ₂	284.6	LaFo76	CaS	346.5	FMUK77
C(NH ₂) ₂ Cl	289.4	LeRa77	CaCl ₂	348.3	Wagn77
(CH ₂) ₆ N ₄	286.9	GHHL70	CaF ₂	347.8	Wagn77, NSLS77
C ₃ H ₃ N	285.5	BCGH73	CaO	346.1	InYa81
PhCN	285.4	LaFo76	CaO	346.7	FMUK77
C*H ₃ CNBF ₃	287.3	BCGH73	CaO	347.3	VaVe80
CH ₃ C*NBF ₃	289.1	BCGH73	CaCO ₃	346.9	Wagn77, CLSW83, WRDM79
Triazole	286.3	GHHL70	Ca(NO ₃) ₂	348.7	CLSW83
NC*N=C(NH ₂) ₂	286.4	LeRa77	CaCrO ₄	346.3	ACHT73
NCN=C*(NH ₂) ₂	288.2	LeRa77	CaMoO ₄	347.2	NFS82
H ₂ NCH ₂ C*OONa	287.9	GHHL70	CaRh ₂ O ₄	345.7	NFS82
H ₂ NCONH ₂	288.7	GHHL70, LeRa77	CaSO ₄	348.0	CLSW83
H ₂ NCSNH ₂	288.0	LeRa77, SrWa77	CaWO ₄	346.5	Nefe82
H ₂ NCONHCONH ₂	289.3	YY578	Ca ₃ Si ₃ O ₉	347.0	WPHK82
PhNO ₂	285.3	LaFo76			
Ph ₃ P	284.9	LMF80	Ca LMM		
Ph ₃ PO	284.6	LMF80	Ca	298.2	VaVe80
Ph ₃ PBr	285.4	LMF80, LaFo76	CaO	292.5	VaVe80
Ph ₃ Sn	284.6	BALS76	CaCO ₃	291.9	WRDM79, Wagn77
p(CH ₂ =CHCl)	286.3	PRCV77	CaCl ₂	291.9	Wagn77
p(CH ₂ =CHOH)	286.3	PRCV77	CaF ₂	289.1	Wagn77
p(HOCOCH=CH ₂)	289.0	HHDD81			
p(NaOCOCMe=CH ₂)	288.1	HHDD81	Cd 3d_{5/2}		
p(C*H ₂ OCOCH=CH ₂)	286.4	ClTh78	Cd	405.1	Φ
p(CH ₃ OC*OCH=CH ₂)	288.6	ClTh78	Cd	405.0	GaWi77, HSBS81, WRDM79, Wagn79
p(MeOCOCMe=CH ₂)	289.0	HHDD81	Cd _{99.9} Sn ₁	404.9	HSBS81

Hg _{0.8} Cd _{0.2} Te	404.6	SBB80	K ₂ ReCl ₆	198.4	CoHe72
CdTe	404.9	SBB80, GaWi77	K ₂ ReCl ₆	199.3	LeBr72
CdSe	405.3	GaWi77	K ₂ SnCl ₆	198.4	CoHe72
CdS	405.3	GaWi77	K ₂ WCl ₆	199.0	LeBr72
CdI ₂	405.4	GaWi77	K ₃ IrCl ₆	198.7	NSBN77
CdBr ₂	406.0	SATD73	K ₃ RhCl ₆	198.4	SNMK78
CdCl ₂	406.1	SATD73	K ₄ Mo ₂ Cl ₈	198.8	HUGH79
CdF ₂	405.9	GaWi77, SATD73, Wagn77	Na ₂ PdCl ₄	199.3	SeTs76
CdO	405.2	GaWi77, NGDS75, NFS82, SBB80	Co(NH ₃) ₆ SbCl ₆	198.9	Tric74
CdO ₂	403.6	HGW75	Pt(NH ₃) ₂ Cl ₂	198.8	CMHL77, Nefe78
Cd(OH) ₂	405.0	WRDM79, HGW75	Pt(NH ₃) ₄ Cl ₂	197.8	SNMK78
CdCO ₃	405.1	HGW75	Pt(NH ₃) ₆ Cl ₄	197.8	SNMK78
CdRh ₂ O ₄	404.7	NFS82	Rh(NH ₃) ₆ Cl ₃	198.1	Nefe78
			Cs ₃ Sb ₂ Cl ₉	198.0	BCH75, Tric74
Cd MNN			CsSbCl ₆	199.2	Tric74
Cd	383.8	WRDM79, Wagn75,	KIrCl ₃ NO	198.9	NSBN77
		GaWi77	ICI	200.1	Sher76
CdTe	382.4	GaWi77	CsClO ₄	208.2	MVS73
CdSe	381.4	GaWi77	KClO ₃	206.5	MVS73
CdS	381.1	GaWi77	KClO ₄	208.8	MVS73
CdI ₂	381.0	GaWi77	LiClO ₄	209.0	MVS73
CdF ₂	378.8	GaWi77	NaClO ₄	208.5	MVS73
CdO	382.2	GaWi77	Ni(NH ₃) ₆ (ClO ₄) ₂	208.2	NZB78
			NiClO ₄ · 6H ₂ O	208.6	NZB78
Ce 3d			RbClO ₄	208.4	MVS73
Ce	883.8	Φ	Me ₄ NCl	196.2	EMGK74
Ce	883.9	ScOs82	Et ₄ NCl	196.4	EMGK74
CeAl ₂	883.5	LFBC80	Ph ₄ NCl	196.1	HVV79
CePd ₃	884.3	LFBC80	NH ₄ Cl	197.9	EMGK74
CeSe	884.3	LFBC80	Chlorobenzene	200.1	CKAM75
CeCu ₂ Si ₂	883.6	LFBC80	Pentachlorobenzene	200.0	CKAM75
CeO ₂	881.8	WRDM79	ClRh(Ph ₃ P) ₃	198.0	Nefe78, OIIT79, MMRC72
CeO ₂	882.4	NGDS75, SaRa80	(Et ₃ P) ₂ PtHCl	198.0	Rigg72
CeH ₃	886.0	ScOs82	(Ph ₃ P) ₂ PtHCl, trans	197.1	CBA73
			(Et ₃ P) ₂ PtCl ₄	199.2	LeBr72, Nefe78, Rigg72
Cl 2p			(Et ₃ P) ₂ PtCl ₂	198.1	Rigg72
KCl	198.5	Φ	(Ph ₃ P) ₂ NiCl ₂	199.0	BNSA70, STHU76
CsCl	196.3	MVS73	(Ph ₃ P) ₂ NiCl ₂	198.3	NZB78
KCl	198.2	MVS73, NSLS77, YYS78	Ph ₃ PBCl ₃	199.4	HVV79
NaCl	198.4	MVS73, NSLS77, SGSO70	Ph ₃ POBCl ₃	198.9	HVV79
LiCl	198.5	MVS73, CSFG79	(Nb ₆ Cl [*] ₁₂)Cl ₆ (Et ₄ N) ₃	199.4	BeWa79
RbCl	197.9	MVS73	(Nb ₆ Cl ₁₂)Cl [*] ₆ (Et ₄ N) ₃	197.5	BeWa79
CuCl ₂	200.0	VWHS81	CdCl ₂	199.0	SATD73
NiCl ₂	199.4	KIHe83, TRLK73, YYS 78	CuCl ₂	199.2	YYS78
PdCl ₂	198.9	NKBP73	HgCl ₂	198.7	SATD73
RhCl ₃	199.3	OIIT79	InCl	198.4	FHT77
RhCl ₃ · 12H ₂ O	199.2	CMHL77	InCl ₃	199.0	FHT77
SbCl ₃	199.7	BCH 75	TiCl ₄	198.2	MRV83
ZnCl ₂	198.5	KIHe83	UCl ₃	198.1	TBVL82
K ₂ IrCl ₆	198.6	NSBN77, LeBr72, CoHe72	UCl ₄	197.7	TBVL82
K ₂ MbCl ₆	198.4	CoHe72	UCl ₅	197.7	TBVL82
K ₂ OsCl ₆	198.6	CoHe72, LeBr72	UOCl	198.5	TBVL82
K ₂ PdCl ₄	198.8	NKBP73	UOCl ₂	198.3	TBVL82
K ₂ PtCl ₄	198.8	CMHL77, SNMK78	ZnCl ₂	199.7	SATD73
K ₂ PtCl ₆	198.8	CoHe72, LeBr72, SNMK78	(NH ₄) ₂ PtCl ₄	198.2	KaEl79
			OPCl ₃	201.7	FIWe75

KClO ₃	206.5	NZK77	Br ₃ Co(Et ₄ N) ₂	780.1	EMGK74
KClO ₄	208.7	NZK77	Cl ₄ Co(Et ₄ N) ₂	780.6	EMGK74
HClPt(Ph ₃ P) ₂	197.9	AL77	Cl ₂ Co(thiourea) ₂	780.9	NBMO73
HClPt(Et ₃ P) ₂	198.0	AL77			
Cl ₂ Pt(Ph ₃ P) ₂	198.0	AL77	Cr 2p		
Ph ₄ PCuCl ₂	198.9	FSJL83	Cr	574.4	Φ
Ph ₄ PCuCl ₃	199.0	FSJL83	Cr ₂ O ₃	576.9	Φ
C ₆ H ₅ Cl	201.0	CKM71	Cr	574.3	LANM81
C ₆ H ₅ CCl ₃	201.0	CKM71	Cr	574.3	WRDM79
C(NH ₂) ₃ Cl	198.0	LeRa77	Cr ₂ N	576.1	RoRo76
p(CH ₂ =CHCl)	200.0	PRCV77, WRDM79	CrN	575.8	STAB76
			CrB ₂	574.3	MECC73
			Cr ₂ S ₃	574.8	CSC72
			CrI ₃	576.7	CSC72
			CrBr ₃	576.2	CSC72
			CrCl ₃	577.4	CSC72
			Cr ₂ O ₃	576.8	CSC72
					BDFP81, CDFM82, CSC72,
					WRDM79, NGDS75
					IHKK76
			CrO ₂	576.3	IIKK76
			CrO ₃	578.3	ACHT73
			CrF ₃	580.3	CSC72
			CrO ₃	579.8	CDFM82
			Cr(OH) ₃	577.3	CDFM82
			CrOOH	577.0	IHKK76
			Cr(CO) ₆	576.3	BCGH72, BCHM72
			Cr(CO) ₆	577.0	PFD73
			Cs ₂ CrO ₄	579.8	AT76
			Cs ₂ Cr ₂ O ₇	579.5	AT76
			CuCrO ₂	576.4	ACHT73
			CuCr ₂ O ₄	577.1	CDFM82
			K ₂ Cr ₂ O ₇	579.9	NSSP80
			LaCrO ₃	575.8	HoTh80
			Li ₂ CrO ₄	579.8	ACHT73
			LiCrO ₂	577.0	ACHT73
			Na ₂ CrO ₄	579.8	ACHT73
			Na ₂ Cr ₂ O ₇	580.5	LaKe76
			Na ₃ CrO ₄	579.4	ACHT73
			Na ₄ CrO ₄	577.9	LaKe76
			NaCrO ₂	577.1	LaKe76, ACHT73
			ZnCr ₂ O ₄	577.2	BDFP81
			BaCrO ₄	579.1	AITu76
			CaCrO ₄	578.9	ACHT73
			(NH ₄) ₃ CrF ₆	579.5	AITu76
			Cr(NH ₃) ₆ Cl ₃	578.5	AITu76
			K ₃ Cr(CN) ₆	576.3	Vann76, ZeHa71
			K ₃ CrF ₆	583.0	AITu76
			Cr(acac) ₃	577.7	AITu76
			Cr(acac) ₃	576.1	ZeHa71
			Cl ₃ Cr(urea) ₆	579.9	AITu76
			Cr(C ₂ H ₅) ₂	574.8	BCDH73, CDH 74, GSMJ74
			Cr(C ₂ H ₅) ₂	576.3	CIAd71
			Cr(C ₂ H ₅)(C-H)	574.4	CDH74, GSMJ74
			Cr(C ₆ H ₆) ₂	574.1	CDH74
			Cr(C ₆ H ₆) ₂	575.4	PFD73
			Cr(CO) ₃ PH ₃	575.3	BCGH72
Co 2p					
Co	778.3	Φ			
CoO	778.4	Φ			
Co	778.3	LANM81			
Co	778.1	WRDM79			
Co ₂ OSn ₈₀	777.9	ThSh78			
Co ₂ B	778.0	MECC73			
CoB	778.0	MECC73			
CoS	781.9	Limo81			
CoF ₂	783.0	CSC72			
CoF ₂ · 4H ₂ O	782.6	NBMO73			
CoF ₃	782.4	CSC72			
CoO	780.2	WRDM79			
CoO	780.4	Kim75, NGDS75,			
		NFS82, CBR76			
		NGDS75, OkHi76			
Co ₃ O ₄	780.2	GPDG79			
Co ₂ O ₄	779.5	McCo75			
Co ₂ O ₃	779.9	McCo75			
CoOOH	780.0	McCo75			
Co(OH) ₂	781.0	McCo75			
CoAl ₂ O ₄	780.8	OkHi76			
CoAl ₂ O ₄	781.9	PCLH76			
CoCr ₂ O ₄	780.2	OkHi76			
CoFe ₂ O ₄	779.7	OkHi76			
CoMn ₂ O ₄	780.0	OkHi76			
CoMoO ₄	780.9	GPDG79			
CoMoO ₄	782.8	PCLH76			
CoRh ₂ O ₄	781.2	NFS82			
CoSO ₄	784.0	Limo81			
ZnCo ₂ O ₄	780.4	OkHi76			
Cs ₂ CoI ₄	780.5	NBMO73			
Cs ₂ CoBr ₄	780.8	NBMO73			
Cs ₂ CoCl ₄	781.0	NBMO73			
K ₃ Co(C ₂ O ₄) ₃	780.9	CSC72			
K ₃ Co(NO ₂) ₆	781.8	NBMO73			
Co(CO) ₃ NO	780.7	BCGH72			
K ₃ Co(CN) ₆	781.2	OkHi76			
K ₃ Co(CN) ₆	782.1	Vann76			
Co(NH ₃) ₃ Cl ₃	781.4	NBMO73			
Co(NH ₃) ₃ Cl ₃	781.9	YNAB77			
Co(NH ₃) ₃ Cl ₃	781.1	CSC72			
Co(NH ₃) ₆ Cl ₃	781.8	NBMO73			
Co(C ₂ H ₅) ₂	779.1	BCDH73			
Co(C ₂ H ₅) ₂	781.3	CIAd71			

$\text{Cr}(\text{CO})_5\text{NH}_3$	575.5	BCGH72, BCHM72				
$\text{Cr}(\text{CO})_5\text{C}_6\text{H}_6$	575.7	CDH74		CuBr_2	932.3	VWHS81
$\text{Cr}(\text{CO})_3\text{C}_6\text{H}_6$	576.3	PFD73		CuCl	932.5	GaWi77, Wagn75
$\text{Cr}(\text{CO})_3(\text{Me}_3\text{P})$	575.2	BCGH72, BCHM72		CuCl_2	934.4	GaWi77
$\text{Cl}_3\text{Cr}(\text{C}_6\text{H}_5)$	576.1	GSMJ74		CuCl_2	935.2	WRDM79
$\text{ICr}(\text{C}_6\text{H}_6)$	576.4	CDH74		CuCl_2	934.8	VWHS81
				CuCl_2	935.6	YYS78
Cr LMM				CuF_2	936.1	GaWi77
Cr	527.2	WRDM79		CuF_2	937.0	WRDM79
				CuF_2	936.8	VWHS81
Cs 3d_{5/2}				Cu_2O	932.5	CDFM82, GaWi77, Wagn75, HMUZ78, MSSS81, Scho73b
Cs	726.4	Φ		CuO	933.7	HMUZ78, GaWi77, WRDM79, MSSS81
C	726.0	KDR77				MSSS81
CsI	723.9	MVS73		$\text{Cu}(\text{OH})_2$	935.1	NZK77
CsBr	724.0	MVS73		$\text{Cu}(\text{NO}_3)_2$	935.5	Wagn75
CsCl	723.7	MVS73		CuCN	933.1	NZK77
CsF	724.0	MVS73		$\text{CuC}(\text{CN})_3$	933.2	WRDM79
CsN_3	723.6	SGRS72		CuCO_3	935.0	Limo81
Cs_2SO_4	723.9	Wagn77		CuSO_4	934.9	NZK77
Cs_3PO_4	723.9	MVS73		Cu_2SO_4	935.5	WRDM79
$\text{Cs}_4\text{P}_2\text{O}_7$	723.8	MVS73		C SiO ₃	934.9	HMUZ78
CsClO_4	724.2	MVS73		$\text{Cu}_2\text{Mo}_3\text{O}_{10}$	931.6	HMUZ78
Cs_2CrO_4	724.5	ACHT73		$\text{Cu}_3\text{Mo}_2\text{O}_9$	934.1	HMUZ78
$\text{Cs}_2\text{Cr}_2\text{O}_7$	723.9	ACHT73		CuCr_2O_4	934.6	CDFM82
CsOH	724.5	WRDM79		CuCrO_2	932.3	ACHT73
				CuFe_2O_4	933.8	LDDDB80
Cs MNN				CuFeO_2	932.6	LDDDB80
Cs_2SO_4	568.4	Wagn77		CuMoO_4	934.1	HMUZ78
CsOH	586.7	WRDM79		CuRh_2O_4	934.4	NFS82
				$\text{Cu}(\text{OAc})_2$	931.8	BrFr74
Cu 2p				$\text{Cu}(\text{OAc})_2$	935.0	YYS79
Cu	932.7	Φ		$\text{Cu}(\text{acac})_2$	934.5	BrFr74
CuO	933.6	Φ		$\text{Cu}(\text{8-Hydroxyquinol.})$	935.0	BrFr74
Cu	932.6	ALMP82		$\text{Cu Salicylaldoxime}$	934.0	BuBu74
Cu	932.6	LANM81		$\text{Cu}_4\text{Cu}(\text{Et}_4\text{N})_2$	932.5	EMGK74
Cu	932.6	BiSw80		$\text{Cu}_2\text{Cu}(\text{H}_2\text{NCONHCONH}_2)_{20}$	935.8	YYS78
Cu	932.6	BiSw80				
Cu	932.7	BiSw80		Cu LMM		
Cu	932.7	PEJ82		Cu	918.6	BiSw80
Cu	932.6	Asam76, GaWi77, KPML73, WRDM79, Wagn75		Cu	918.7	BiSw80
				Cu	918.6	BiSw80
$\text{Cu}_{64}\text{Zn}_{36}$	932.6	VanO77		Cu	918.7	PEJ82
$\text{Cu}_{95}\text{Sn}_5$	932.5	Hegd82		Cu	918.6	KPML73, WRDM79, Wagn75, Asam76, GaWi77
Cu_3P	932.2	NSDU75		$\text{Cu}_{64}\text{Zn}_{36}$	918.6	VanO77
Cu_3P	932.2	NSDU75		Cu_2Se	917.6	RRD78
Cu_2Se	931.9	RRD78		CuSe	918.4	RRD78
CuSe	932.0	RRD78		CuAgSe	917.7	RRD78
CuAgSe	931.9	RRD78		Cu_2S	917.4	Wagn75
CuInSe_2	931.9	KJID81		CuS	917.9	RRD78
Cu_2S	932.5	Wagn75		CuS	916.9	VWHS81
CuS	932.2	RRD78		CuBr_2	915.0	Wagn75
CuS	933.2	Limo81		CuCl	915.6	GaWi77
CuS	931.9	BSRR81		CuCl_2	915.3	WRDM79, VWHS81, GaWi77
CuS	935.0	NSSP80		CuF_2	916.0	GaWi77
CuBr	932.1	BrFr74		CuF_2	914.8	WRDM79

CuF ₂	914.4	VWHS81	MgF ₂	685.8	Wagn80
Cu ₂ O	916.2	CDFM82, HMUZ78	MgF ₂	685.7	NBK74
Cu ₂ O	916.2	CDFM82, GaWi77, Wagn75, HMUZ78, MSSS81, Scho73b	SrF ₂	685.0	WRDM79
Cu ₂ O	916.6	MSSS81, Wagn75	SrF ₂	684.5	NBK74
Cu ₂ O	917.2	GaWi77	AgF	682.7	GaWi77
CuO	918.1	GaWi77, MSSS81, Scho73b	BeF ₂	685.8	NBK74, NKBP73
Cu(OH) ₂	916.2	MSSS81	CdF ₂	684.5	GaWi77, WRDM79
Cu(NO ₃) ₂	915.3	NZK77	CdF ₂	684.8	NBK74, SATD73
CuCN	914.5	Wagn75	CdF ₂	684.2	NSLS77
Cu(CN) ₂	914.5	NZK77	CuF ₂	684.5	GaWi77, WRDM79
CuCO ₃	916.3	WRDM79	CuF ₂	685.9	VWHS81
CuSO ₄	915.6	NZK77	HgF ₂	686.0	SATD73
C ₄ SiO ₃	915.2	WRDM79	MnF ₂	684.8	WRDM79
Cu ₂ Mo ₃ O ₁₀	916.5	HMUZ78	NiF ₂	685.0	GaWi77, WRDM79
Cu ₃ Mo ₂ O ₉	916.6	HMUZ78	NiF ₂ · 4H ₂ O	684.7	NSLS77
CuCr ₂ O ₄	918.0	CDFM82	PbF ₂	683.6	WRDM79
CuMoO ₄	916.6	HMUZ78	ZnF ₂	684.6	GaWi77, Wagn77
			ZnF ₂	685.1	NBK74
Dy 4d			AlF ₃ · 3H ₂ O	686.3	NBK74, NKBP73
Dy	152.4	Φ	GaF ₃ · 3H ₂ O	685.2	NBK74, NKBP73
Dy ₂ O ₃	167.7	SaRa80	GdF ₃	684.8	McTh76
			InF ₃	685.2	WRDM79
Dy 3d_{5/2}			InF ₃ · 3H ₂ O	685.3	NBK74, NKBP73
Dy	1295.5	Φ	LaF ₃	684.5	WRDM79
Dy ₂ O ₃	1298.9	SaRa80	NdF ₃	684.8	WRDM79
			PrF ₃	684.6	WRDM79
Er 4d			SmF ₃	684.6	WRDM79
Er	167.3	Φ	YF ₃	685.3	WRDM79
Er	169.4	WRDM79	UF ₃	685.3	TBVL82
Er ₂ O ₃	168.7	WRDM79	UF ₄	684.8	TBVL82, PMDS77
			UF ₅	684.8	TBVL82
Eu 3d_{5/2}			ThF ₄	684.9	WRDM79
Eu	1125.6	Φ	HfF ₄	685.4	WRDM79
			ZrF ₄	685.1	NKBP73
Eu 4d			NaBeF ₃	685.7	NKBP73
Eu	128.2	NNBF68	Na ₂ BeF ₄	685.2	NKBP73
Eu ₂ O ₃	135.9	NNBF68	NaBF ₄	687.0	WRDM79
			NF ₄ BF ₄	694.2	RNS73
F 1s			Na ₃ AlF ₆	685.5	WRDM79
LiF	684.9	Φ	Na ₂ SiF ₆	686.0	Wagn77
CsF	685.9	WRDM79	Na ₂ SiF ₆	686.4	NSLS77
KF	683.9	NBK74, MVS73	K ₂ SiF ₆	686.6	NBK74
KF	684.4	PMDS77	K ₂ TiF ₆	685.0	WRDM79
LiF	685.1	WRDM79	K ₂ TiF ₆	684.9	NBK74
LiF	685.0	MVS73, NBK74	Na ₂ TiF ₆	685.3	Wagn77
NaF	684.5	WRDM79	K ₃ FeF ₆	684.0	WRDM79
NaF	684.5	NBK74, NSLS77	K ₂ NiF ₆	687.6	TRLK73
NaF	683.7	MVS73	K ₂ GeF ₆	685.2	NBK74
RbF	683.6	MVS73	Na ₂ GeF ₆	685.9	WRDM79
RbF	682.9	NBK74	K ₂ ZrF ₆	684.6	NBK74, NKBP73
BaF ₂	683.7	WRDM79	Na ₂ ZrF ₆	685.0	WRDM79
BaF ₂	684.3	NBK74	KZrF ₅ · H ₂ O	684.8	NKBP73
CaF ₂	684.8	WRDM79	K ₃ ZrF ₇	684.3	NKBP73
CaF ₂	684.8	NBK74, NSLS77	NaSnF ₃	685.3	WRDM79
			K ₂ SnF ₆ · H ₂ O	685.1	NBK74
			CsSbF ₄	683.6	BCH75

K ₂ SbF ₅	683.9	Tric74	NaBF ₄	652.8	WRDM79
KSbF ₆	686.6	Wagn77	Na ₃ AlF ₆	654.1	WRDM79
KSb ₂ F ₇	684.3	Tric74	Na ₂ SiF ₆	653.0	Wagn77
Na ₂ SbF ₅	683.4	Tric74	K ₂ TiF ₆	655.7	WRDM79
NaSbF ₆	685.1	BCH75	Na ₂ TiF ₆	655.1	Wagn77
K ₃ RhF ₆	685.7	Nefe78	K ₃ FeF ₆	656.0	WRDM79
K ₂ NbF ₇	685.4	WRDM79	Na ₂ GeF ₆	654.0	WRDM79
K ₂ NbF ₇	685.2	NBK74	Na ₂ ZrF ₆	655.1	WRDM79
K ₂ TaF ₇	685.2	WRDM79	NaSnF ₃	655.3	WRDM79
K ₂ TaF ₇	685.1	NBK74	KSbF ₆	656.6	Wagn77
NaTaF ₆	685.2	NKBP73	K ₂ NbF ₇	655.2	WRDM79
Na ₂ TaF ₇	685.6	NKBP73	K ₂ TaF ₇	655.0	WRDM79
F ₃ TaF ₈	685.5	NKBP73	p-(CF ₂ =CF ₂)	652.4	Wagn77
K ₄ UF ₆	684.7	PMDS77	NiOCCF ₃	52.9	WRDM79
EuOF	685.3	PGBH80			
LaOF	685.2	RGBH80			
NdOF	685.1	RC ₃ '3'180	Fe 2p		
PrOF	685.0	RiBiH80	Fe	707.0	Φ
YOF	685.5	RGBH80	Fe ₂ O ₃	710.9	Φ
Cs ₂ MoO ₂ F ₄	684.7	NKBP73	Fe	706.7	LANM81
Cs ₂ WO ₂ F ₄	684.7	NKBP73	Fe	706.8	Asam76
UO ₂ F ₂	685.6	TBVL82	Fe	707.0	WRDM79, McZe77
p-(CF ₂ =CF ₂)	689.0	Wagn77	Fe ₃ Al	707.6	ShTr75
NiOCCF ₃	688.4	WRDM79	Fe ₃ Si	707.5	ShTr75
CH ₃ CNBF ₃	687.0	BCGH73	Fe ₂ B	706.9	MECC73
NH ₃ BF ₃	686.6	BCGH73	FeB	707.1	MECC73
C ₅ H ₉ NBF ₃	685.6	BCGH73	Fe ₃ C	708.1	ShTr75
EtNH ₂ BF ₃	686.6	BCGH73	FeS	710.3	CSC72
Et ₄ NSbF ₆	684.7	BCH 75	FeS ₂ (markasite, pyr)	712.2	Bind73, Limo81
Ph ₃ PBF ₃	685.7	HVV79	KFeS ₂	708.7	Bind73
Ph ₃ POBF ₃	685.8	HVV79	FeBr ₂	710.3	CSC72
			FeBr ₃	710.1	CSC72
F KLL			FeCl ₂	710.6	CSC72
CsF	653.8	WRDM79	FeCl ₃	711.3	CSC72
LiF	654.7	WRDM79	FeF ₂	711.3	CSC72
NaF	655.0	Wagn77	FeF ₃	714.2	CSC72
BaF ₂	656.2	WRDM79	FeO	709.4	McZe77
CaF ₂	655.4	WRDM79	Fe ₃ O ₄	708.2	McZe77
MgF ₂	654.4	Wagn77	Fe ₃ O ₄	710.4	OkHi76
SrF ₂	656.3	WRDM79	Fe ₂ O ₃	710.8	WRDM79, NGDS75
AgF	659.3	GaWi77	Fe ₂ O ₃ , alpha	710.9	McZe77
CdF ₂	656.0	GaWi77, WRDM79	Fe ₂ O ₃ , gamma	710.9	McZe77
CuF ₂	657.0	GaWi77	FeOOH, alpha	711.8	McZe77
CuF ₂	656.2	WRDM79	FeOOH, gamma	711.3	KoNa80
CuF ₂	656.2	WRDM79	CoFe ₂ O ₄	710.5	McZe77
NiF ₂	655.5	GaWi77, WRDM79	Fe(C ₂ O ₄) ₃ · 6H ₂ O	713.6	Kilk73
PbF ₂	658.5	WRDM79	FeSO ₄	712.1	Limo81
ZnF ₂	655.6	GaWi77, WRDM79	K ₃ FeF ₆	714.4	CSC72
InF ₃	656.4	WRDM79	NiFe ₂ O ₄	710.5	McZe77
LaF ₃	658.0	WRDM79	K ₃ Fe(CN) ₆	709.6	Vann76
NdF ₃	657.0	WRDM79	K ₄ Fe(CN) ₆	707.1	Vann76
PrF ₃	657.2	WRDM79	K ₄ Fe(CN) ₆	708.5	YNNA77
SmF ₃	657.0	WRDM79	Na ₂ Fe(CN) ₅ (NO)	709.7	YNNA77
YF ₃	655.8	WRDM79	Na ₃ Fe(CN) ₅ (N ₂ O)	707.4	YNNA77
ThF ₄	657.0	WRDM79	Na ₂ Fe(CN) ₅ (NO ₂)	706.8	YNNA77
HfF ₄	655.3	WRDM79	Na ₃ Fe(CN) ₅ NH ₃	707.6	YNNA77

$\text{Na}_3\text{Fe}(\text{CN})_5\text{N}_2\text{H}_4$	707.7	YNNA77	Gd_2O_3	143.8	SaRa80
$\text{Fe}(\text{CO})_5$	709.6	BCGH72	Gd 3d		
$\text{Fe}(\text{CO})_2(\text{NO})_2$	709.5	BCGH72	Gd	1187.0	Φ
$\text{KFe}_4(\text{NO})_7\text{S}_3 \cdot 2\text{H}_2\text{O}$	708.9	Nefe78	Gd_2O_3	1189.0	SaRa80
$\text{Fe}(\text{SMe})(\text{CO})_3$	708.6	BBFR77			
$\text{Fe}(\text{C}_5\text{H}_5)_2$	707.7	FWUM79, BCDH73, CDH74, Nefe78	Ge 2p_{3/2}		
$\text{I}_3\text{Fe}(\text{C}_5\text{H}_5)_2$	709.9	CDH74	Ge	1217.2	McWe76
$\text{Fe}(\text{C}_5\text{H}_4\text{COOH})_2$	708.4	FWUM79	Ge	1217.4	TLR78, MoVa73, Wagn75
Fe(phthalocyanine)	709.1	MSV79	GeS_2	1219.8	MoVa73
Fe LMM			GeS_2	1219.8	MoVa73
Fe	702.4	WRDM79	GeN_4	1218.8	TLR78
Ga 2p_{3/2}			GeI_2	1218.2	MoVa73
Ga	1116.7	Φ	GeF_2	1220.7	MoVa73
Ga	1116.5	Scho73a	GeO_2	1220.4	MoVa73, Wagn75
GaP	1116.8	Ni U75	Na_2GeO_3	1218.9	MoVa73
Ga_2O_3	1116.9	U75	Na-GeF_6	1221.3	Wagn75
Ga_2O_3	1117.8	Scho73a	K_2GeF_6	1220.7	MoVa73
Ga LMM			Ph ₄ Ge	1218.9	MoVa73
Ga	1068.2	WRDM79, MINN78, Scho73a	Ge LMM		
GaAs	1066.3	MINN78	Ge	1146.2	McWe76
GaAs	1067.1	MINN78	Ge	1145.4	SFS77
GaP	1065.6	MINN78, MIN81	Ge	1145.1	Wagn75, WRDM79
GaP	1066.8	MIN81	GeTe	1144.8	SFS77
GaN	1064.5	HeMa80	GeSe	1143.8	SFS77
Ga_2Se_3	1065.2	ITI82	GeS	1143.7	SFS77
Ga_2Se_3	1065.6	ITI82	GeO_2	1137.7	Wagn75
Ga_2O_3	1061.6	MINN78	Na_2GeF_6	1135.7	Wagn75
Ga_2O_3	1062.4	ITI82	Ge 3d		
Ga_2O_3	1062.9	Scho72a	Ge	29.4	Φ
Ga 3d			Ge	29.3	McWe76
Ga	18.6	MINN78, LBHK73, Scho73a, WRDM79	Ge	29.0	SFS77
GaSb	20.2	LBHK73	Ge	29.1	HKMP74, UeOd82, WRDM79
GaAs	18.8	LPMK74	GeAs_2	29.7	HKMP74
GaAs	19.2	IMNN79, MINN78, Tayl82,	GeTe_3As_2	29.9	HKMP74
GaP	18.8	MIN81	$\text{GeS}_2\text{TeAs}_2$	30.2	HKMP74
GaP	19.3	NIMN78, IMNN79	GeS_3As	30.4	HKMP74
GaP	19.9	LBHK73, MIN81	GeTe_2	30.1	HKMP74
GaP	18.7	LPMK74	GeTe	30.0	SFS77
GaN	19.5	HeMa80	GeTe	29.7	HKMP74
AlGaAs	19.0	Tayl82	GeSe ₂	31.0	UeOd82
Ga_2Se_3	19.7	ITI82	GeSe	30.9	SFS77
Ga_2Se_3	19.9	ITI82	GeS_2	30.4	HKMP74
Ga_2O_3	20.5	GGVL79	GeS	30.5	SFS77
Ga_2O_3	20.2	LBHK73, Scho73a	GeS	29.5	HKMP74
Ga_2O_3	20.5	ITI82	GeO_2	32.5	HKMP74
Ga_2O_3	21.0	MINN78	Ph ₄ Ge	31.2	HWVV74
			Ph ₃ GeI	31.8	HWVV74
			Ph ₃ GeBr	31.8	HWVV74
			Ph ₃ GeCl	31.8	HWVV74
Gd 4d			Hf 4f		
Gd	140.4	Φ	Hf	14.3	Φ

Hf	14.4	WRDM79	I ₂ Ni(Ph ₃ P) ₂	619.3	NZB78
HfO ₂	16.7	SaRa80	I ₂ Pt(Et ₃ P) ₂	619.2	Rigg72
Hf 4d			LiIn(Pr ₃ N)	619.6	FHT77
HfO ₂	213.2	SaRa80, NGDS75	I ₂ Pt(Me ₃ P) ₂ cis	621.1	CAB71
Hg 4f			I ₂ Pt(Me ₃ P) ₂ tran	621.9	CAB71
HgS (cinnabar)	101.0	Φ	I ₄ (Mo ₆ I ^{*8})	620.6	BeWa79
Hg	99.8	BrMc72, SATD73, SMBM76, WRDM79	I ^{*4} (Mo ₆ I ₈)	619.3	BeWa79
Hg _{0.8} Cd _{0.2} Te	100.2	SBB80	I MNN		
HgS	100.8	NSSP80	LiI	517.0	WRDM79
HgI ₂	100.7	SATD73	AgI	506.8	GaWi77
HgBr ₂	101.0	SATD73	CdI	507.0	GaWi77
HgCl ₂	101.4	SATD73	CuI	507.1	GaWi77
HgF ₂	101.2	SATD73	NiI ₂	507.3	GaWi77
HgO	100.8	NSSP80	ZnI ₂	506.0	GaWi77
Et ₂ NC ₄ H ₄ HgOAc	101.3	NSSP80	In 3d_{5/2}		
Cl ₂ Hg(H ₂ NCONHCONH ₂) ₂	101.3	YYS78	In	443.9	Φ
Hg(thiodibenzoylme) ₂	101.3	TBHH77	In	443.8	Bert81, Hegd82, WRDM79, PVVA79, LAK77
(Ph ₄ P) ₂ Hg(SCN) ₄	101.4	FoLa82	In ₉₅ Sn ₅	443.6	Hegd82
Ho 4d			InSb	444.1	IMNN79
Ho	159.6	Φ	InP	444.6	Bert81, CFRS80
I 3d_{5/2}			In ₂ Te ₃	444.5	WRDM79
KI	619.3	Φ	In ₂ Se ₃	444.8	WRDM79
I ₂	619.9	Sher76	In ₂ S ₃	444.8	Wagn77, MSC73
CsI	618.2	MVS73	InI ₃	446.0	Wagn77, MSC73
RbI	618.2	MVS73	InI	443.9	FHT77
KI	618.8	MVS73	InBr ₃	446.0	Wagn77
NaI	618.6	MVS73, Sher76	InBr ₃	446.6	MSC73
LiI	619.7	WRDM79	InBr	445.1	FHT77
LiI	618.9	MVS73	InCl ₃	446.0	Wagn77
AgI	619.4	GaWi77	InCl ₃	446.9	MSC73
CdI	619.2	GaWi77	InCl	444.9	MSC73
CdI	619.4	SATD73	InF ₃	446.4	Wagn75, MSC73
CuI	619.0	GaWi77	In ₂ O ₃	444.3	Wagn77, NGDS75, Bert81
HgI ₂	619.4	SATD73	In ₂ O ₃	444.6	CFRS80
InI	619.0	FHT77	In ₂ O ₃	444.9	LAK77, MSC73
InI ₃	619.1	FHT77	In(OH) ₃	445.0	WRDM79
NiI ₂	619.0	GaWi77	(NH ₄) ₂ InF ₆	445.6	Wagn77
NiI ₂ · 6H ₂ O	619.7	NZB78	CuInSe ₂	444.7	KJID81
ZnI ₂	619.8	GaWi77	In(acac) ₃	445.4	MSC73
ZnI ₂	619.7	SATD73	Br ₂ InEt ₄ N	445.7	FHT77
NaIO ₃	623.5	Sher76	Cl ₂ InEt ₄ N	445.2	FHT77
NaIO ₄	624.0	Sher76	Br ₄ InPr ₄ N	445.9	FHT77
HIO ₃	623.1	Sher76	I ₄ InPr ₄ N	445.4	FHT77
H ₂ IO ₆	623.0	Sher76	Cl ₄ InPr ₄ N	445.8	FHT77
I ₂ O ₅	623.3	Sher76	In MNN		
ICI	621.5	Sher76	In	410.4	WRDM79
ICl ₃	622.5	Sher76	In ₉₅ Sn ₅	410.5	PVVA79, KISC80, LAK77
Cs ₃ Sb ₂ I ₉	618.5	BCH75	InSb	401.6	IMNN79
Rb ₃ Sb ₂ I ₉	620.8	Tric74	InP	408.0	Bert81
Na(NiIO ₆) · H ₂ O	624.4	NZB78	InP	411.0	KISC80
			In ₂ Te ₃	408.9	WRDM79

In ₂ Se ₃	408.3	WRDM79			
In ₂ S ₃	407.3	Wagn77	K ₂ PtCl ₆	292.8	CoHe72, LeBr72
InI ₃	405.8	Wagn77	K ₂ ReCl ₆	292.8	CoHe72
InBr ₃	404.8	Wagn77	K ₂ ReCl ₆	293.7	LeBr72
InCl ₃	404.6	Wagn77	K ₂ SnCl ₆	292.8	CoHe72
InF ₃	403.7	Wagn75	K ₂ WCl ₆	293.3	LeBr72
In ₂ O ₃	406.4	Wagn77	K ₃ IrCl ₆	293.0	NSBN77
In(OH) ₃	405.0	WRDM79	K ₄ Mo ₂ Cl ₈	293.2	HUGH79
(NH ₄) ₂ InF ₆	404.1	Wagn77	KSbFF ₆	293.7	Wagn77
			KZrFF ₆ · H ₂ O	292.7	NKBP73
Ir 4f			K ₂ NiF ₆	294.2	TRLK73
Ir	60.9	Φ	K ₂ UF ₆	293.1	PMDS77
Ir	60.8	WRDM79, BHHK70, EPC75	K ₂ ZrF ₆	292.6	NKBP73
IrCl ₃	62.7	Folk73	K ₃ ZrF ₇	292.8	NKBP73
K ₂ IrBr ₆	62.6	Nefe78K ₃ IrBr ₆ 61.8Nefe78	K ₃ Co(CN) ₆	293.7	Vann76
K ₂ IrCl ₆	63.0	CoHe72, LeBr72	K ₃ Cr(CN) ₆	292.2	ZeHa7
K ₂ IrCl ₆	63.6	KSPB76, NSBN77	K ₃ Fe(CN) ₆	291.9	Vann76
K ₃ IrCl ₆	62.5	NSBN77	K ₃ Mn(CN) ₆	291.9	Vann76
(NH ₄) ₂ IrCl ₆	63.7	EPC75	K ₄ Fe(CN) ₆	291.9	Vann76
(NH ₄) ₂ IrCl ₆	63.0	EPC75	K ₄ V(CN) ₆	293.7	Vann76
Ir(CO) ₂ Cl	63.4	KSPB76	KIrCl ₃ NO	293.1	NSBN77
KIrCl ₃ NO	65.0	NSBN77	K ₂ Pt(CN) ₄ · 3H ₂ O	293.3	CaLe73
KIr ₂ (CO) ₄ Cl ₄	62.7	KSPB76	K ₂ Pt(CN) ₄ Cl ₂ · 3H ₂ O	292.9	CaLe73
K ₂ Ir ₂ (CO) ₄ Cl ₅	63.0	KSPB76	K ₃ Co(SCH ₂ CHNH ₂ COO) ₃	292.8	SSEW79
IrCl ₄ (EteP) ₂	63.6	LeBr72			
IrClN ₂ (Ph ₃ P) ₂	60.7	Folk73	K LMM		
IrI ₃ (H ₂ NCH ₂ CH ₂ NH ₂) ₃	63.1	NeBa72	KBr	250.7	WRDM79
IrCl ₃ (H ₂ NCH ₂ CH ₂ NH ₂) ₃	63.2	NeBa72	KF	250.1	Wagn77
IrCl ₄ (H ₂ NCH ₂ CH ₂ NH ₂) ₃	63.2	Nefe78	KSbF ₆	249.3	Wagn77
K 2p			Kr 3d		
K	294.4	Φ	Kr in graphite	87.0	Φ
KCl	292.9	Φ			
K	294.6	SMKM77, PeKa77	La 3d		
KI	292.8	MVS73	La	835.8	Φ
KBr	293.0	MVS73, WRDM79	La	835.9	ScSc82
KCl	292.8	MVS73, NSLS77	LaH ₂	838.8	ScSc82
KF	292.5	Wagn75	La ₂ O ₃	835.1	WRDM79
KF	292.8	PMDS77	La ₂ O ₃	833.7	SaRa80
KF	293.1	MVS73			
KCN	294.7	Vann76	La 4d		
KN ₃	292.5	SGRS72	La	103.9	NIS72, KEML74
KNO ₂	292.9	NSLS77	La ₂ O ₃	101.3	SaRa80, NGDS75, HoTh80
KClO ₃	293.2	MVS73	LaCrO ₃	101.7	HoTh80
KClO ₄	293.4	MVS73			
K ₃ PO ₄	293.5	MVS73	Li 1s		
K ₄ P ₂ O ₇	292.2	MVS73	LiF	55.6	Φ
K ₂ CrO ₄	292.6	ACHT73	Li	54.7	KLMP73, CSFG79
K ₂ Cr ₂ O ₇	292.1	ACHT73	LiN ₃	55.2	SGRS72
K ₂ Cr ₂ O ₇	292.8	NSSP80	LiBr	56.8	MVS73
K ₂ MoO ₄	292.6	NFS82	LiCl	56.0	CSFG79, MVS73
KRhO ₂	292.5	NFS82	LiF	55.7	MVS73, WRDM79
KAl ₂ (AlSi ₃ O ₁₀) ₂ (OH) ₂	293.0	WPHK82	Li ₂ O	55.6	CSFG79
K ₂ IrCl ₆	292.8	NSBN77, LeBr72, CoHe72	LiOH	54.9	CSFG79
K ₂ MoCl ₆	292.7	CoHe72	Li ₂ CO ₃	55.2	CSFG79
K ₂ O ₈ Cl ₆	293.0	CoHe72, LeBr72	Li ₃ PO ₄	55.4	MVS73

Li ₄ P ₂ O ₇	55.6	MVS73	MnF ₃	642.6	CSC72
LiClO ₄	57.2	MVS73	MnO	640.7	OHI75
Li ₂ CrO ₄	57.1	ACHT73	MnO	640.5	OkHi76
LiC ₈ O ₂	55.6	ACHT73	MnO	641.4	Aoki76, CSC72
LiNbO ₃	54.8	StHo79	Mn ₂ O ₃ , alpha	641.2	OHI75
Lu 4f			Mn ₂ O ₃	641.6	CSC72
Lu	7.3	Φ	Mn ₂ O ₃ , alpha	641.7	OkHi76
Lu 4d			Mn ₂ O ₃ , gamma	641.5	OkHi76
Lu	196.2	KEML74, LPWF75	Mn ₃ O ₄	641.4	OHI75
Lu ₂ O ₃	196.0	SaRa80, NGDS75	MnO ₂	642.4	WRDM79
Mg 2p			MnO ₂ , beta	641.1	OHI75
Mg	49.8	Φ	MnO ₂	642.3	Aoki76, CSC72, NGDS75
Mg	49.6	HAS75, LMKJ75, HFV 77, Fugg77, WRDM79	MnOOH	641.7	OHI75
Mg ₂ Cu	49.8	FWFA75	CoMn ₂ O ₄	641.5	OkHi76
Mg ₃ Bi ₂	50.6	FWFA75	CuMn ₂ O ₄	641.0	OkHi76
MgF ₂	51.0	Wagn80	MnCr ₂ O ₄	640.6	OkHi76
MgO	50.8	InYa81	MnSO ₄	644.9	Limo81
Mg(OH) ₂	49.5	HNUW78a	KMnO ₄	647.0	UmRe78
MgAl ₂ O ₄	50.4	HNUW78b	Mn ₂ (CO) ₁₀	641.6	VWVB77
Talc, Mg ₃ Si ₄ O ₁₀ (OH) ₂	50.5	WPHK82	BrMn(CO) ₅	641.9	VWVB77
Mg 1s			(BrMn(CO) ₄) ₂	641.7	VWVB77
Mg	1303.1	HAS75, LMKJ75, Fugg77	BrMn(CO) ₄ (Ph ₃ P)	641.5	VWVB77
Mg ₂ Cu	1303.0	FWFA75	BrMn(CO) ₃ (P(OMe) ₃) ₂	641.0	VWVB77
Mg ₃ Bi ₂	1304.0	FWFA75	Mn ₂ (CO) ₈ (Ph ₃ P) ₂	640.7	VWVB77
MgF ₂	1305.0	Wagn80	K ₃ Mn(CN) ₆	639.7	Vann76
Mg(OH) ₂	1302.7	HNUW78a	Na ₄ Mn(CN) ₆	638.3	Vann76
MgAl ₂ O ₄	1304.0	HNUW78b	Mn(C ₅ H ₅) ₂	638.5	BCDH73, CDH74
Mg KLL			Mn(CO) ₃ (C ₅ H ₅)	640.6	CDH74
Mg	1185.5	LMKJ75, SRHH78, WRDM79, Fugg77, HFV 77	Mn(CO) ₃ (C ₅ H ₅)	641.8	CIAD71
Mg ₂ Cu	1185.7	FWFA75	Mn LMM		
Mg ₃ Bi ₂	1184.6	FWFA75	Mn	617.6	Vayr81
MgF ₂	1178.2	Wagn80	Mo 3d		
Talc, Mg ₃ Si ₄ O ₁₀ (OH) ₂	1180.3	WPHK82	Mo	228.0	Φ
Mn 2p			Mo	227.9	NyMa80
Mn	639.0	Φ	Mo	228.0	CiDe75, WRDM79, CGR 78, GrMa75, KBAW74, WaTa80
MnO ₂	642.1	Φ	MoB ₂	227.9	MECC73
Mn	638.8	LANM81	Mo ₂ B ₅	227.3	BrWh78
Mn	639.0	WRDM79	Mo ₂ C	227.8	BrWh78
MnN	641.3	CSC72	MoSi ₂	227.7	WPHK82
MnS	640.3	CSC72	MoSe ₂	228.3	GrMa75
MnS, beta	640.8	Aoki76	MoS ₂	229.0	PCLH76, GrMa75
MnS, alpha	641.9	Aoki76	MoS ₂	229.6	SSOT81, StEd75
MnS	642.1	Limo81	MoCl ₃	230.0	GrMa75
MnI ₂	641.9	Aoki76, CSC72	MoCl ₄	230.6	GrMa75
MnBr ₂	642.0	Aoki76, CSC72	MoCl ₅	231.0	GrMa75, SwHe71
MnCl ₂	642.0	Aoki76, CSC72	MoO ₂	229.3	SaRa80, CGR78, CiDe75, KBAW74
MnF ₂	642.6	Aoki76, CSC72	MoO ₃	232.6	GPDG79, KBAW74, SaRa80, CiDe75, CGR78, GrMa75
			MoO ₃	232.6	WRDM79
			(NH) ₄ MoO ₄	232.1	SwHe71
			Al ₂ (MoO ₄) ₃	232.5	PCLH76
			Al ₂ (MoO ₄) ₃	233.3	NFS82

CaMoO ₄	232.8	NFS82	VN	397.4	STAB76
CoMoO ₄	232.4	GPDG79, CiDe75, AMFL74	BN	398.1	WRDM179, HJGN70
CrMoO ₄	232.2	TVG76	Si ₃ N ₄	397.4	TLR78
CuMoO ₄	232.7	HMUZ78	S ₂ N ₂	398.9	SDIO77
K ₂ MoO ₄	232.1	NFS82	SP(NH ₃) ₃	398.8	FIWe75
Na ₂ MoO ₄	232.1	CiDe75, NFS82, SwHe71, NLSL77	S ₄ N ₃ Cl	400.4	HHJ69
Na ₂ MoO ₄ · 2H ₂ O	232.5	GrMa75	(NPCI ₂) ₃	400.3	HHJ69
(NH ₄) ₂ Mo ₂ O ₇	232.5	AMFL74	Cs(N*NN*)	397.9	SGRS72
(NH ₄) ₂ Mo ₇ O ₂₄ · -H ₂ O	232.7	GrMa75	Cs(NN*N)	402.2	SGRS72
Cu ₃ Mo ₃ O ₁₀	232.4	HMUZ78	K(N*NN*)	398.5	SGRS72
Cu ₃ Mo ₂ O ₉	232.8	HMUZ78	K(NN*N)	402.8	SGRS72
Rh ₂ MoO ₆	231.8	NFS82	Li(N*NN*)	398.7	SGRS72
Cl ₂ Mo(NO) ₂	230.4	Nefe78	Li(NN*N)	403.1	SGRS72
K ₄ Mo ₂ Cl ₈	229.2	HUGH79	Na(N*NN*)	398.5	SGRS72
I ₄ (Mo ₆ I ₈)	228.8	BeWa79	Na(N*NN*)	400.1	HHJ69
Br ₄ (Mo ₆ Br ₈)	229.3	BeWa79	Na(NN*N)	402.9	SGRS72
Cl ₄ Mo(Ph ₃ P) ₂	231.9	HuBa74	Na(NN*N)	404.5	HHJ69
Cl ₄ Mo ₂ (Et ₃ P) ₄	228.7	Walt77	Rb(N*NN*)	398.1	SGRS72
Cl ₃ Mo(PhPMe ₂) ₃ mer	229.4	LeBr72	Rb(NN*N)	402.4	SGRS72
Cl ₄ Mo ₂ (PhPMe ₂) ₄	228.7	Walt77	K ₃ Co(CN) ₆	399.6	Vann76
(CO) ₅ Mo(Ph ₃ P)	228.3	HVV79	K ₃ Cr(CN) ₆	397.6	Vann76, ZeHa71
(CO) ₄ Mo(Ph ₃ P) ₂	227.8	HuBa74	K ₃ Fe(CN) ₆	398.1	Vann76
(CO) ₃ Mo(Ph ₃ P) ₃	227.4	HuBa74	K ₃ Mn(CN) ₆	398.3	Vann76
Cl ₂ Mo(CO) ₂ (Ph ₃ P) ₂	229.3	Nefe78	K ₄ Fe(CN) ₆	398.0	Vann76
Cl ₂ Mo(CO) ₃ (Ph ₃ P) ₂	228.8	HuBa74	K ₄ Fe(CN) ₆	397.8	YNNNA77
Cl ₂ Mo(NO) ₂ (Ph ₃ P) ₂	230.3	HuBa74	K ₄ V(CN) ₆	398.5	Vann76
Cl ₃ Mo(NO) ₂ (MeCN) ₂	231.5	Nefe78	Na ₂ Mn(CN) ₆	397.6	Vann76
Cl ₃ Mo(pyridyl) ₃	229.5	CELC76	Na ₂ Fe(CN) ₃ (N*O)	402.7	YNNNA77
Cl ₄ Mo(pyridyl) ₄	228.9	Walt77	Na ₂ Fe(CN*) ₃ (NO)	397.4	YNNNA77
Cl ₄ Mo(pyridyl) ₂	230.8	SwHe71	Na ₄ Fe(CN) ₃ N*O ₂	404.3	YNNNA77
Br ₄ (Mo ₆ Br ₈)(pyridyl) ₂	229.7	BeWa79	Na ₄ Fe(CN*) ₃ NO ₂	396.6	YNNNA77
Cl ₁₂ Mo ₆ (pyridyl)	229.6	HaWa74	KCN	399.8	HHJ69
Cl ₄ Mo(bipyridyl)	232.0	CELC76	KCN	398.3	YNNNA74
Cl ₃ MoO(bipyridyl)	231.9	CELC76	KCN	400.6	Vann76
Cl ₁ MoO ₂ (bipyridyl)	232.3	CELC76	NaCN	400.2	Vann76
(CO) ₄ Mo(bipyridyl)	226.3	GrMa75	(NH ₄) ₂ PtCl ₄	400.3	KaEl79
Cl ₁₂ Mo ₆ (Ph ₃ P) ₂	229.6	HaWa74	(NH ₄) ₂ SO ₄	401.3	SwAl74
Cl ₆ (Mo ₆ Br ₈)(Et ₄ N) ₂	229.2	BeWa79	N*H ₄ NO ₃	401.9	SwAl74, BCM78
Br ₆ (Mo ₆ Br ₈)(Et ₄ N) ₂	229.3	BeWa79	N*H ₄ NO ₃	402.3	BTE77
(Bu ₃ N) ₂ Mo(CO) ₄	227.4	GrMa75	N*H ₄ NO ₃	403.1	HHJ69
(Bu ₄ N) ₂ MoAl ₁₁	229.0	BeWa79	N ₂ H ₆ SO ₄	403.3	HHJ69
(Bu ₄ N) ₃ Mo ₂ Cl ₉	229.5	Walt77	N ₂ H ₆ SO ₄	401.7	Folk73
(C ₂ H ₅) ₃ Mo(CO) ₃	227.4	GrMa75	NH ₃ OHCl, ionic	402.9	HHJ69
MoO ₂ (acac) ₂	232.0	GrMa75	NH ₃ OHCl, ionic	401.4	Folk73
			NH ₃ SO ₃	402.6	HHJ69
			NaN ₂ O ₂	402.1	HHJ69
			KSCN	399.3	HHJ69
			KOCN	399.1	HHJ69
			KOCN	397.9	Folk73
			NF ₄ BF ₄	417.1	RNS73
			NaNO ₂	404.9	HHJ69, LiHe75
			NaNO ₂	403.9	BTE77
			Ba(NO ₃) ₂	407.5	CLSW83
			Ca(NO ₃) ₂	408.0	CLSW83
			KNO ₃	407.2	NLSL77
			NH ₄ N*O ₃	407.3	BTE77
N Is					
BN	398.1	Φ			
NH ₃	399.6	HHJ69			
NH ₃	398.7	LaLu79, RNS73			
Cr ₂ N	397.4	RoRo76			
CrN	396.7	STAB76			
GaN	397.0	HeMa80			
Ge ₃ N ₄	397.4	TLR78			
Si ₃ N ₄	396.2	STAB76			
TiN	396.9	STAB76			

NH ₄ N*O ₃	408.0	HHJ69	N(CH ₂ COOH) ₃	398.70	YoSa74
NH ₄ N*O ₃	405.8	BCM78	H ₂ NCH ₂ COOH	398.70	YoSa74
NaNO ₃	408.1	HHJ69, LiHe75	H ₃ NCH ₂ COO ionic	400.60	YoSa74
NaNO ₃	407.4	BTE77	EtCHNH ₂ COOH	400.60	YNAB77
Ni(NO ₃) ₂	407.0	TRLK73	H ₂ N(CH ₂) ₃ COOH	398.80	YoSa74
Ni(NO ₃) ₂ · 6H ₂ O	407.6	NZB78	CH ₃ CHNH ₂ COOH	401.00	YNAB77, KNPP74
Pb(NO ₃) ₂	407.2	TLR78	H ₂ NCONH ₂	399.50	LeRa77
Sr(NO ₃) ₂	408.1	CLSW83	H ₂ NCSNH ₂	399.80	SrWa77, NBM073
K ₂ Pt(NO ₂) ₄	404.7	SNMK78	H ₂ NCSNH ₂	399.20	LeRa77
K ₂ Pt(NO ₂) ₆	404.7	SNMK78	CH ₃ CONH ₂	399.60	SNMK78
K ₃ Co(NO ₂) ₆	404.2	NBM073	PhCONH ₂	399.50	LBNN78, HHJ 69
K ₃ Rh(NO ₂) ₆	404.1	SNMK78	PhN=NPh	399.60	BrFe76
K ₃ Rh(NO ₃) ₆	407.3	SNMK78	PhN=NPh	400.10	LiHe75
MoCl ₂ (NO) ₂	401.4	Nefe78	PhCH=NPh	399.10	SZNS77
K ₂ Os(NO)Cl ₅	402.8	Nefe78	1,1'-azonaphthalene	400.00	Yosh80
K ₂ Ru(NO)I ₅	402.5	Nefe78	NCN=C(N*H ₂) ₂	399.20	LeRa77
K ₂ Ru(NO)Br ₅	403.30	Nefe78	AmONO	404.5	LiHe75
Rh ₃ (NO) ₆ Cl ₃	401.90	Nefe78	PhC=NOHC=NOHPh	400.6	Yosh78
Co(CO) ₃ NO	402.20	BCGH72	MeC=NOHC=NOHMe	399.8	Yosh78
Fe(CO) ₂ (NO) ₂	401.80	BCGH72	Ni(dimethylglyoxime) ₂	400.4	NZB78
Co(NH ₃) ₅ Cl ₃	400.10	YNAB77	Cu Salicylaloxime	400.3	BuBu74
Ni(NH ₃) ₆ Br ₂	399.60	NZB 78	Cu(8-hydroxyquinol) ₂	399.5	YoSa74
Ni(NH ₃) ₆ (ClO ₄) ₂	399.90	NZB 78	8-Quinolinol	398.9	Yosh80
Pt(N*H ₃) ₂ (NO ₂) ₂	400.40	Nefe78, CMHL77	Cr(CO) ₅ NH ₃	399.5	BCGH72
Pt(NH ₃) ₂ (N*O ₂) ₂	404.40	Nefe78, CMHL77	N(EtO) ₃ SiCl	400.5	GrHe77
Pt(NH ₃) ₂ Cl ₂	400.20	Nefe78, CMHL77	N(EtO) ₃ SiH	399.8	GrHe77
Rh(NH ₃) ₆ Cl ₃	400.10	Nefe78	Morphine	398.5	SCKK75
Me ₄ NBr	401.40	SGCT74	Morphine H ₂ SO ₄	401.2	SCKK75
Me ₄ NCl	401.50	EMGK74			
Me ₄ NCl	402.30	LiHe75	Na 1s		
Et ₄ NCl	401.40	EMGK74	Na	1071.8	Φ
Et ₃ NHCl	401.20	LiHe75	NaCl	1072.1	Φ
Et ₃ NHHSO ₄	401.80	EvRe81	Na	1071.8	BaSr75
Bu ₃ N	398.90	LiHe75	Na	1071.4	KLMP73
BuNH ₃ HSO ₄	401.00	EvRe81	NaI	1071.7	WRDM79
Bu ₄ NHSO ₄	402.20	EvRe81	NaBr	1071.7	Wagn75
EtNH ₂	398.90	BCGH73	NaBr	1071.4	MVS73
EtNH ₂ BF ₃	401.40	BCGH73	NaCl	1071.6	Wagn75
NH ₄ Cl	400.80	SwAl74	NaCl	1072.5	SGSO70
NH ₄ Cl	401.50	EMGK74, BTE 77	NaCl	1071.5	KOK83
NH ₄ BF ₃	401.90	BCGH73	NaCl	1071.8	NSLS77
C ₃ H ₅ N	398.80	LiHe75	NaCl	1072.3	HHDD81
C ₃ H ₅ N	399.30	BCGH73	NaF	1071.2	Wagn75
C ₃ H ₅ NHCl	401.00	HHJ 69	NaF	1071.0	MVS73, NSLS77
C ₃ H ₅ NBF ₃	401.40	BCGH73	Na ₂ CO ₃	1071.5	WRDM79
Hexamethylenetetramm	399.40	LiHe75	Na ₂ CO ₃	1071.7	HHDD81
PhCN	399.20	LiHe75	Na ₂ HPO ₄	1071.6	WRDM79
C(NH ₂) ₃ Cl	400.10	LeRa77	Na ₂ HPO ₄	1071.5	Swif82
PhNH ₂	399.40	LiHe75	Na ₂ S ₂ O ₃	1071.6	Wagn75
Me ₃ NO	403.00	LiHe75	Na ₂ SO ₃	1071.3	Wagn75
OP(NMe ₃) ₃	399.10	FIWe75	Na ₂ SO ₄	1071.2	Wagn75
P(NMe ₂) ₃	398.30	GBMP79	Na ₂ SeO ₃	1070.8	Wagn75
Cysteine HCl Hydrate	401.20	SSEW79	Na ₂ TeO ₄	1071.1	Wagn75
Cysteine	400.00	LIMa79	Na ₃ PO ₄	1071.1	MVS73, Swif82, GMD79
H ₃ N(CH ₂) ₃ COOH ionic	400.80	YoSa74	Na ₄ P ₂ O ₇	1070.8	MVS73
HN(CH ₂ COOH) ₃ ionic	400.70	YoSa74	Na ₄ P ₂ O ₇	1071.6	GMD79

NaClO ₄	1071.8	MVS73	NaCl	990.1	KOK83
NaH ₂ PO ₂	1071.1	Swif82	NaF	998.6	Wagn75
NaH ₂ PO ₄	1072.0	Swif82	Na ₂ CO ₃	989.8	WRDM79
NaHCO ₃	1071.3	WRDM79	Na ₂ HPO ₄	989.9	WRDM79
NaN ₃	1070.8	SGRS72	Na ₂ HPO ₄	989.7	Swif82
NaNO ₂	1071.6	Wagn75	Na ₂ S ₂ O ₃	990.1	Wagn75
NaNO ₃	1071.4	Wagn75	Na ₂ SO ₃	990.4	Wagn75
NaPO ₃	1071.7	Wagn75	Na ₂ SO ₄	989.8	Wagn75
NaPO ₃	1071.7	Swif82, GMD 79	Na ₂ SeO ₃	991.0	Wagn75
Na ₂ Cr ₂ O ₇	1071.6	WRDM79	Na ₂ TeO ₄	990.5	Wagn75
Na ₂ CrO ₄	1071.4	Wagn75	Na ₃ PO ₄	990.1	Swif82
Na ₂ CrO ₄	1071.0	ACHT73	NaH ₂ PO ₂	989.8	Swif82
Na ₂ IrCl ₆	1071.9	Wagn75	NaH ₂ PO ₄	989.1	Swif82
Na ₂ MoO ₄	1070.9	Wagn75	NaHCO ₃	989.8	WRDM79
Na ₂ MoO ₄	1071.8	NLSL77	NaNO ₂	989.8	Wagn75
Na ₂ PdCl ₄	1071.8	Wagn75	NaNO ₃	989.6	Wagn75
Na ₂ SnO ₃ · 3H ₂ O	1071.1	WRDM79	NaPO ₃	989.3	Wagn75
Na ₂ WO ₄	1072.0	Wagn75	NaPO ₃	989.4	Swif82
NaAsO ₂	1070.9	Wagn75	Na ₂ Cr ₂ O ₇	990.6	WRDM79
NaBiO ₃	1071.3	WRDM79	Na ₂ CrO ₄	991.2	Wagn75
NaCrO ₂	1072.4	ACHT73	Na ₂ IrCl ₆	989.2	Wagn75
Na ₂ BeF ₄	1071.8	NKBP73	Na ₂ MoO ₄	991.0	Wagn75
Na ₂ GeF ₆	1071.7	Wagn75	Na ₂ PdCl ₄	990.2	Wagn75
Na ₂ SiF ₆	1071.7	Wagn75	Na ₂ SnO ₃ · 3H ₂ O	990.3	WRDM79
Na ₂ SiF ₆	1072.1	NLSL77	Na ₂ WO ₄	989.6	Wagn75
Na ₂ TaF ₇	1071.9	NKBP73	NaAsO ₂	990.7	Wagn75
Na ₂ TiF ₆	1071.6	Wagn75	NaBiO ₃	990.9	WRDM79
Na ₂ ZrF ₆	1071.5	Wagn75	Na ₂ GeF ₆	998.1	Wagn75
Na ₃ AlF ₆	1071.8	Wagn75	Na ₂ SiF ₆	987.7	Wagn75
Na ₃ TaF ₈	1071.8	NKBP73	Na ₂ TiF ₆	988.5	Wagn75
NaBF ₄	1072.7	Wagn75	Na ₂ ZrF ₆	988.7	Wagn75
NaBeF ₃	1071.9	NKBP73	Na ₃ AlF ₆	988.0	Wagn75
NaTaF ₆	1071.7	NKBP73	NaBF ₄	987.1	Wagn75
Na ₂ O	1072.5	BaSt75	Na ₂ O	989.8	BaSt75
NaOOCH	1071.1	WRDM79	NaOOCH	989.8	WRDM79
Na ₂ C ₂ O ₄	1070.8	WRDM79	Na ₂ C ₂ O ₄	990.5	WRDM79
NaAlSi ₃ O ₈ , albite	1072.2	WPHK82	Mol Sieve A	988.8	WPHK82
Hydroxysodalite	1070.5	WPHK82	Mol Sieve X	988.4	WPHK82
Natrolite	1072.4	WPHK82	Mol Sieve Y	987.8	WPHK82
Mol Sieve A	1071.8	WPHK82	NaOAc	989.9	Wagn75
Mol Sieve X	1072.3	WPHK82	NaOOCCH ₂ SH	990.4	WRDM79
Mol Sieve Y	1072.6	WPHK82	NaO ₃ SPh	989.7	WRDM79
NaOAc	1071.1	Wagn75			
NaOAc	1071.7	HHDD81			
NaOOCCH ₂ SH	1071.2	WRDM79	Nb 3d		
NaO ₃ SPh	1071.3	WRDM79	Nb	202.4	Φ
p-(NaOOCMe=CH ₂)	1072.2	HHDD81	Nb	202.3	NyMa80
			Nb	202.2	MSC73, NSCP74, WRDM79
			Nb	201.8	Bahl75
Na KLL			Nb ₃ Te ₄	202.8	Bahl75
Na	994.3	BaSt75	NbTe ₄	203.8	Bahl75
Na	994.3	KLMP73	Nb ₃ Se ₄	203.0	Bahl75
Na	994.5	SRHH78	NbSe ₂	203.4	Bahl75
NaI	991.2	WRDM79	NbS ₂	207.7	MSC73
NaBr	990.6	Wagn75	NbN	203.8	Bahl75
NaCl	990.3	Wagn75	NbBr ₅	207.1	MSC73
NaCl	990.0	SGSO70	NbCl ₅	208.0	MSC73

NbO	202.8	SPB76	Ni ₂ O ₃	855.8	KiWi74
NbO	203.7	Bahl75	Ni(OH) ₂	855.6	DPS77, LFWS79, McCo75
NbO	204.7	FCFG77	Ni(NO ₃) ₂	857.1	TRLK73
Nb ₂ O ₅	207.5	SPB76, MSC73, FCFG77, NFS82, NGDS75	Ni(NO ₃) ₂ · 6H ₂ O	856.9	NZB78
LiNbO ₃	207.1	StHo79	NiAl ₂ O ₄	855.8	SDR 80, LFWS79
KNbO ₃	206.5	MSC73	NiAl ₂ O ₄	857.4	NgHe76
CaNb ₂ O ₆	206.8	Bahl75	Ni ₂ SiO ₄	856.1	LFWS79
CdNb ₂ O ₆	207.0	Bahl75	NiClO ₄ · 6H ₂ O	857.2	NZB78
Ca ₂ Nb ₂ O ₇	206.7	Bahl75	NiFe ₂ O ₄	855.4	McCo75
RhNbO ₄	206.5	NFS82	NiRh ₂ O ₄	855.9	NFS82
Cl ₂ Nb ₄ Cl ₁₂ (H ₂ O) ₄ · 4H ₂ O	204.7	BeWa79	NiSO ₄	856.8	ShRe79
Cl ₆ (Nb ₆ Cl ₁₂)(Et ₄ N) ₃	204.7	BeWa79	NiSiO ₃	856.5	SRD79
Br ₆ (Nb ₆ Cl ₁₂)(Bu ₄ N) ₂	204.7	BeWa79	NiWO ₄	857.7	NgHe76
Cl ₂ (Nb ₆ Cl ₁₂)(Pr ₃ P) ₄	204.6	BeWa79	NaNiO ₆ · H ₂ O	856.4	NZB78
Cl ₂ (Nb ₆ Cl ₁₂)(Me ₂ SO) ₄	204.6	BeWa79	K ₂ NiF ₆	861.0	TRLK73
Nd 3d			Ni(CO) ₄	854.8	BCGH72
Nd	980.8	Φ	Br ₂ Ni(NH ₃) ₆	855.9	NZB78
Nd ₂ O ₃	982.0	SaRa80	Ni(NH ₃) ₆ (ClO ₄) ₂	856.5	NZB78
Nd 4d			Ni(acac) ₂	855.9	NZB78, TRLK73
Nd ₂ O ₃	120.8	SaRa80	Ni(OAc) ₂ · 4H ₂ O	856.5	NZB78
Ne 1s			Ni(C ₅ H ₅)	854.2	BCDH73
Ne in graphite	863.1	Φ	Ni(C ₅ H ₅)	856.8	CIAd71, TRLK73
Ne in Ag	862.4	CiHa74	Cl ₂ Ni(Ph ₃ P) ₂	855.0	BNSA70
Ne in Au	861.6	CiHa74	Cl ₂ Ni(Ph ₃ P) ₂	854.4	NZB78
Ne in Cu	862.2	CiHa74	Cl ₂ Ni(Ph ₃ P) ₂	857.0	STHU76
Ne in Fe	863.4	Wagn75	Ni(dimethylglyoxim) ₂	855.0	NZB78, YoYa81
Ne KLL			Cl ₂ Ni(bipyridyl)	855.7	NSWU77, NZB78
Ne in Fe	818.0	Wagn75	Ni(SPh) ₂	854.6	BBFR77
Ni 2p			Cl ₂ Ni(NH ₂ CONHCONH ₂) ₂	856.7	YYS78
Ni	852.7	Φ	Ni(2-aminobenzoate) ₂	855.9	YoYa81
NiO	853.8	Φ	Ni(P(OEt) ₃) ₄	853.8	TRLK73
Ni	852.7	LANM81	Cl ₂ Ni(Et ₃ P) ₂	854.7	FaBa79
Ni	852.7	ALMP82	Br ₄ Ni(Et ₄ N) ₂	855.2	EMGK74
Ni	852.8	PEJ82	Ni LMM		
Ni	852.7	WRDM79, ShRe79	Ni	846.1	PEJ82
Ni ₃ Yb	852.7	WWC78	Ni	846.2	WRDM79
Ni ₂ Si	853.0	GGM82	Ni	846.1	KiWi74, KGW76
NiSi	853.5	GGM82	O 1s		
NiS	852.8	ShRe79	Al ₂ O ₃ , sapphire	531.0	Φ
NiS	853.2	DPS77	Ag ₂ O	529.2	Scho73
NiS	855.1	NgHe76	AgO	528.6	Scho73, SRD80
NiI ₂ · 6H ₂ O	855.3	NZB78	Al ₂ O ₃	531.3	Nefe82, SDR80, BGD75, ZSOS79
NiCl ₂	856.7	TRLK73, KiHe83, YYS78	Al ₂ O	531.0	Tayl82, WPHK82
NiF ₂ · 4H ₂ O	857.5	NSLS77	Al ₂ O ₃ , alpha	531.8	WPHK82
NiO	853.5	WRDM79	Al ₂ O ₃ , gamma	530.9	Barr83, WPHK82
NiO	854.3	DPS77, KiHe83, LFWS79, NFS82, NZB78, SRD79	As ₂ O ₃	531.7	Tayl82, MINN78
NiO	854.3	KiWi74, McCo75	As ₂ O ₅	531.6	WZR80
Ni ₂ O ₃	857.3	NgHe76	B ₂ O ₃	533.0	NGDS75
			BaO	528.3	InYa81
			BeO	531.7	NGDS75, NFS75, HJGN70
			Bi ₂ O ₃	530.0	NGDS75, DSBG82
			CaO	529.4	InYa81

CaO	531.3	WZR80	Nb ₂ O ₅	530.6	NGDS75, NFS82
CdO	529.2	NFS75, NGDS75, SBB80	Nb ₂ O ₅	531.3	SaRa80
CdO ₂	530.3	HGW75	NbO ₂	530.7	SaRa80
Ce ₂ O ₃	530.3	PKHL80	Nd ₂ O ₃	530.6	SaRa80
CeO ₂	529.2	NGDS75	Ni ₂ O ₃	531.8	KiWi74, NgHe76
Co ₂ O ₃	529.9	McCo75	NiO	529.6	DPS77, LFWS79, NFS82, NGDS75, SRD79, WZR80
Co ₃ O ₄	530.2	NGDS75, WZR80	P ₂ O ₅ (bridging O)	532.2	NGDS75
Co ₃ O ₄	529.6	BGD75	P ₂ O ₅ (bridging O)	532.6	GMD79
Co ₃ O ₄	529.7	CBR76, GPDG79, HSU76	P ₂ O ₅ (nonbridging O)	533.6	NGDS75
CoO	530.1	BGD75, NFS82, NGDS75	P ₂ O ₅ (nonbridging O)	534.3	GMD79
Cr ₂ O ₃	531.0	HoTh80, DPS76, WZR80, BDFP81	PbO	528.9	NFS82
Cr ₂ O ₃	531.5	NGDS75	PbO	531.6	WZR80
CrO ₂	529.3	IICK76	PbO, rhombic	529.4	KOW73
CrO ₃	530.2	DPS76	PbO, rhombic	530.9	ZiHe78
Cs ₂ O	527.5	YaBa80	PbO, tetragonal	527.5	KOW73
Cs ₂ O ₄	530.5	YaBa80	PbO, tetragonal	528.9	ZiHe78
Cu ₂ O	530.3	HMUZ78, MSSS81, RBO72, Scho73b	PbO ₂	527.4	KOW73
CuO	529.6	MSSS81, McCo75, HMUZ78, RBO72, Scho73b	PbO ₂	529.0	TLR78
Fe ₂ O ₃	530.2	NGDS75, WZR80, KiIk73, Limo81	PdO	529.3	KGW74
Fe ₂ O ₃	529.6	HSU76, NSLS77	Pr ₂ O ₃	529.3	SaRa80
Fe ₂ O ₃ , alpha	529.6	McZe77	PrO ₂	528.6	SaRa80
Fe ₂ O ₃ , gamma	529.8	McZe77	PtO ₂	531.4	CMHL77
Fe ₃ O ₄	530.0	McZe77	ReO ₂	530.1	BHU81
FeO	529.8	McZe77	ReO ₃	531.9	BHU81
Ga ₂ O ₃	530.8	NGDS75, Scho73a, WZR80, ZSOS79	Rh ₂ O ₃	530.4	CMHL77, NFS82
GeO ₂	520.0	NGDS75, WZR80	RuO ₂	529.4	MWLF78
H ₂ O	533.2	NGDS75, WZR80	RuO ₂	529.4	KiWi74, McGi82, SaRa80
HfO ₂	530.4	NGDS75	RuO ₃	530.7	KiWi74
I ₂ O ₅	529.9	Sher76	Sb ₂ O ₃	530.0	WZR80
In ₂ O ₃	529.8	NGDS75	Sc ₂ O ₃	530.0	NGDS75, WZR80
In ₂ O ₃	530.3	CFRS80	SiO ₂	533.0	Barr83, KMH78, NGDS75
In ₂ O ₃	530.5	LAK77	SiO ₂	534.3	KiIk73
La ₂ O ₃	528.6	NGDS75	SiO ₂	532.5	NSLS77, SRD79
Li ₂ O	531.3	CSFG79	SiO ₂ , gel	532.8	WPHK82
Lu ₂ O ₃	529.5	NGDS75	SiO ₂ , Vycor	532.9	WPHK82
MgO	530.0	NFS82, NGDS75	SiO ₂ , alpha cristobal	532.5	WPHK82
MgO	531.2	InYa81	SiO ₂ , alpha quartz	532.7	WPHK82
MgO	532.1	WZR80	SiO ₂ , alpha quartz	533.2	TLR78
MnO	529.7	OHI75	SnO	530.1	ADPS77
Mn ₃ O ₄	529.6	OHI75	SnO ₂	530.6	ADPS77, LAK77, MWLF78, NGDS75, TLR78
Mn ₂ O ₃	529.6	OHI75	SrO	530.5	VaVe80
MnO ₂	530.0	NGDS75, WZR80	Tb ₂ O ₃	528.8	SaRa80
MnO ₂ , beta	529.6	OHI75	TbO ₂	528.8	SaRa80
MoO ₂	531.1	PCLH76	TeO ₂	530.2	GBP81, SBB80
MoO ₂	530.7	CGR78, KBAW74	ThO ₂	530.0	NGDS75
MoO ₂	529.9	SaRa80	TiO ₂	529.9	MWLF78, WZR80, NGDS75
MoO ₃	530.9	NGDS75, NFS82	UO ₂	530.4	MSSS81
MoO ₃	531.6	PCLH76	UO ₃	529.9	MSSS81
MoO ₃	530.4	SaRa80, KBAW74, HMUZ78, CGR78	V ₂ O ₃	530.5	CGR78
Na ₂ O	529.7	BaSi75	V ₂ O ₄	530.0	KKL83
Nb ₂ O ₅	529.6	GBP81	V ₂ O ₅	529.9	BCM78, KKL83
			WO ₂	530.5	NSLS77, NGDS75, NFS82
				530.4	CoRa76

WO ₃	530.6	CoRa76, KMH78, NFS82, NGDS75, NSLS77	Na ₂ CO ₃	531.6	HHDD81, WZR80
ZnO	530.4	NFS82, NGDS75, NSLS77, Scho73, WZR80, ZSOS79	PbCO ₃	531.2	WZR80
ZrO ₂	530.2	NGDS75	CsClO ₄	532.7	MVS73
ZrO ₂	530.9	WZR80	KClO ₄	532.2	MVS73
Al(OH) ₃ , bayerite	531.4	WPHK82	KClO ₃	532.3	MVS73
Al(OH) ₃ , gibbsite	531.5	WPHK80	LiClO ₄	533.4	MVS73
AlOOH, boehmite	531.5	Tayl82	NaClO ₄	533.0	MVS73
Co(OH) ₂	531.2	HSU76	RbClO ₄	532.8	MVS73
Cr(OH) ₃	531.2	DPS76	Al ₂ SiO ₅ , kyanite	531.3	AnSw74
Cu(OH) ₂	531.2	MSSS81	Al ₂ SiO ₅ , mullite	531.6	AnSw74
Fe(OH) ₂	531.3	HSU76	Al ₂ SiO ₅ , sillimanite	531.3	AnSw74
FeO*OH	530.1	McZe77	Al ₂ SiO ₅ , sillimanite	531.9	WPHK82
FeOO*H	531.2	McZe77	Ca ₃ (HSiO ₄) ₂	531.2	CIRi76
In(OH) ₃	531.8	WZR80	Co ₂ SiO ₄	531.6	WZR80
KOH	531.8	Kilk73	Na ₂ SiO ₃ · 5H ₂ O	530.6	CIRi76
LiOH	531.2	CSFG79, WZR80	Na ₂ SiO ₃ · 5H ₂ O*	532.5	CIRi76
Mg(OH) ₂	530.9	HNUW78	Ni ₂ SiO ₄	531.9	LFWS79
NaOH	532.8	BaSt75	NiSiO ₃	532.3	SRD79
Ni(OH) ₂	531.3	LFWS79	MgSiO ₃ · 2H ₂ O	532.0	CIRi76
AlPO ₄	532.8	CFRS80	MgSiO ₃ · 2H ₂ O*	532.8	CIRi76
Cs ₃ PO ₄	530.1	MVS73	Al ₂ (MoO ₄) ₃	531.0	PCLH76
Cs ₄ P ₂ O ₇	530.2	MVS73	Al ₂ (WO ₄) ₃	532.0	NgHe76
K ₃ PO ₄	530.4	MVS73	CaCrO ₄	529.5	ACHT73
K ₄ P ₂ O ₇	530.1	MVS73	CaMoO ₄	530.6	NFS82
Li ₃ PO ₄	531.5	MVS73	CaWO ₄	529.9	NFS82
Li ₄ P ₂ O ₇	531.7	MVS73	p-Benzoquinone	532.2	OYK74
Na ₃ PO ₄	530.4	MVS73, GMD79	Hydroquinone	533.5	OYK74
Na ₂ F ₂ O ₇ (bridging O)	531.1	GMD79	PhCOONa	531.4	LBNN78
Na ₄ F ₂ O ₇ (nonbridging O)	532.9	GMD79	p(Me ₂ Si(O))	532.5	WPHK82
NaPO ₃ (bridging O)	531.5	GMD79	Methylsilicone Resin	532.7	WPHK82
NaPO ₃ (nonbridging O)	533.4	GMD79	Phenylsilicone Resin	532.6	WPHK82
Ba(NO ₃) ₂	533.0	CLSW83	PhCONH ₂	532.2	LBNN78
Ca(NO ₃) ₂	533.6	CLSW83			
KNO ₃	532.7	NSLS77	Os 4f		
Pb(NO ₃) ₂	532.7	TLR78	Os	50.7	Φ
BaSO ₄	531.8	CLSW83	Os	50.6	Folk73, BNMN79
BaSO ₄	532.5	WZR80	Os	50.2	BHKK70
CaSO ₄	532.0	CLSW83, WZR80	OsCl ₃	53.1	Nefe78
Cr ₂ (SO ₄) ₃	532.1	DPS76	OsO ₂	52.0	SaRa80
FeSO ₄	532.4	Limo81	OsO ₂	52.7	Folk73
K ₂ SO ₄	531.2	WZR80	Os(HSO ₃) ₂	52.2	Nefe78
NiSO ₄	532.1	NSLS77, Nefe82	K ₂ OsI ₆	51.9	Nefe78
PbSO ₄	531.5	ZiHe78	K ₂ OsBr ₆	52.9	Nefe78
ZnSO ₄	532.5	Nefe82	K ₂ OsCl ₆	53.0	Folk73
Na ₂ SO ₃	531.2	WZR80	K ₂ OsCl ₆	53.2	CoHe72
Na ₂ S ₂ O ₃	531.8	WZR80	K ₂ OsCl ₆	53.5	LeBr72
PbSO ₃	530.8	ZiHe78	K ₂ OsCl ₆	53.9	Nefe78
PbS ₂ O ₃	531.1	ZiHe78	K ₂ OsO ₂ (OH) ₄	55.2	Nefe78
Ag ₂ CO ₃	530.6	HGW75	Os(NH ₃) ₅ N ₂ I ₂	50.9	Folk73
BaCO ₃	531.3	CLSW83	Os(NH ₃) ₅ N ₂ Br ₂	52.0	Folk73
CaCO ₃	531.4	CLSW83, WZR80	Os(NH ₃) ₄ (N ₂) ₂ Br ₂	51.6	Folk73
CdCO ₃	531.4	HGW75	Os(NH ₃) ₅ N ₂ Cl ₂	52.2	Folk73
CuCO ₃	531.5	WZR80	K ₂ Os(NO)Br ₅	53.3	Nefe78
Li ₂ CO ₃	531.5	CSFG79	K ₂ Os(NO)Cl ₅	53.4	Nefe78
			HOs(Ph ₃ P)Cl(CO)	51.1	Nefe78
			OsCl ₄ (Et ₃ P) ₂	52.6	LeBr72

O ₅ Cl ₄ (PhPMe ₂) ₂ trans	53.0	LeBr72	(PhO) ₃ PS	134.7	MSAV71
O ₅ Cl ₃ (PhPMe ₂) ₃ mer	51.7	LeBr72	(PhO) ₃ PSe	134.3	MSAV71
O ₅ Cl ₂ (PhPMe ₂) ₄ trans	50.5	LeBr72	(PhO) ₃ PO	133.6	CFRS80
			(PhO) ₃ PO	134.8	FIWe75
P 2p			Ph ₃ POBBr ₃	133.7	HVV79
P	129.9	Φ	Ph ₃ POBCl ₃	133.4	HVV79
P	130.0	NSDU75	Ph ₃ POBF ₃	133.3	HVV79
P (red)	130.0	ScBr81	Ph ₂ PO(OH)	133.3	MSAV71
Cu ₃ P	129.6	NSDU75	OPCl(OEt) ₂	134.8	FIWe75
CuP ₂	129.7	NSDU75	OPF ₂ NPh ₂	135.8	FIWe75
GaP	128.8	WaTa80, LMNN79, NIMN78	OPCl ₂ OEt	135.2	FIWe75
GaP, anodically oxid.	128.5	MIN81	OP(NMe ₂) ₃	133.4	FIWe75
GaP, thermally oxid.	129.7	MIN81	Ph ₄ PI	133.0	HVV79
InP	128.3	CFRS80	Ph ₄ PBr	133.5	LMF80, SRH72
InP	129.4	Bert81	Ph ₄ PCl	132.8	HVV79
Zn ₃ P ₂	128.3	NSDU75	MePPh ₃ Br	133.0	SRH 2
ZnP ₂	129.8	NSDU75	(Ph ₃ P) ₃ P*F ₆	136.7	LMF80
AlPO ₄	132.9	CFRS80	(Ph ₃ P*) ₃ PF ₆	133.5	LMF80
C ₅₃ PO ₄	132.1	MVS73	Pt(Ph ₃ P) ₄	131.2	Rigg72
K ₂ HPO ₄	132.8	Bert81	Ph ₃ P=CHCOPh	132.2	Dale76, STA74
K ₃ PO ₄	133.2	MVS73	Ph ₃ P=CHCOOMe	132.5	STA74
Li ₃ PO ₄	133.6	MVS73	Cl ₂ Ni(Ph ₃ P) ₂	132.4	BNSA70
Na ₂ HPO ₄	133.1	Swif82, WRDM79, WaTa80	Ni(CO) ₂ (Ph ₃ P) ₂	131.4	TRLK73
Na ₃ PO ₄	132.4	MVS73, GMD79, Swif82			
NaH ₂ PO ₄	134.2	Swif82	Pb 4f		
NaPO ₃	134.2	Swif82, GMD79	Pb	136.9	Φ
Rb ₃ PO ₄	132.5	MVS73	Pb	136.4	LKMP73
NaH ₂ PO ₂	132.6	Swif82	Pb	136.8	SFS77
Cs ₄ P ₂ O ₇	132.6	MVS73	Pb	136.8	BeFI80, KOW73, KiWi73, TLR78, WRDM79, WaTa80
K ₄ P ₂ O ₇	132.6	MVS73	Pb	136.8	HSBS81, OCH79
Li ₄ P ₂ O ₇	134.3	MVS73	Pb ₉₆ Sn ₂	136.8	HSBS81
Na ₄ P ₂ O ₇	133.2	MVS73, GMD79, Bert81	PbTe	137.4	SFS77
Rb ₄ P ₂ O ₇	133.1	MVS73	PbSe	137.4	SFS77
P ₄ O ₁₀	135.3	NIMN78, NGDS75, CFRS80, Bert81, GMD79	PbS	137.6	MoVa73, SFS77, ZiHe78
			PbI ₂	138.7	MoVa73
OPCl ₃	135.7	FIWe75	PbBr ₂	138.8	NeFe82
SPCl ₃	135.3	FIWe75	PbF ₂	139.0	MoVa73
SP(NH ₃) ₃	133.4	FIWe75	PbO	138.9	KOW73, ZiHe78, WRDM79, NFS82, NSSP80, MoVa73
Ph ₃ P	130.9	Dale76, NSMS79, TRLK73, GBMP79	PbO	138.9	MoVa73, BeFI80
Ph ₃ P	130.9	HVV79, LMF80, SRH72	Pb ₃ O ₄	138.0	MoVa73
Ph ₃ P	130.9	MSAV71, GZF73	PbO ₂	137.4	BeFI80, KOW73, TLR78, MoVa73
Ph ₃ PS	132.5	HVV79, STA74, FIWe75, MSAV71	Pb(OH) ₂	138.4	NSSP80
Ph ₃ PSe	132.6	HVV79, MSAV71	Pb(NO ₃) ₂	139.3	BeFI80, TLR78, NSSP80
Ph ₃ PO	132.5	GZF73, STA74, FIWe75, MSAV71, HVV79, BNSA70	PbSO ₃	138.6	ZiHe78
			PbSO ₄	139.4	NSSP80, ZiHe78
Ph ₃ PBI ₃	132.2	HVV79	PbS ₂ O ₃	138.4	ZiHe78
Ph ₃ PBBR ₃	132.1	HVV79	PbRh ₂ O ₄	137.3	NFS82
Ph ₃ PBCl ₃	132.2	HVV79	Ph ₄ Pb	138.2	MoVa73
Ph ₃ PBF ₃	132.0	HVV79	Ph ₃ PbCl	138.9	MoVa73
Ph ₂ PSH	132.3	NSWM80	Ph ₂ PbCl ₂	139.4	MoVa73
Ph ₂ PSeH	132.3	NSWM80	Pb(OAc) ₂	138.5	BeFI80
(PhS) ₃ :P	134.3	MSAV71	Pb(OAc) ₂	137.2	BeFI80
(PhS) ₃ :PS	133.1	MSAV71			
(PhO) ₃ :P	134.7	MSAV71			

Pd 3d			Pr 4d		
Pd	335.1	Φ	Pr ₂ O ₃	116.1	SaRa80
Pd	335.1	NyMa80	PrO ₂	116.2	SaRa80
Pd	335.2	BiSw80	Pt 4f		
Pd	335.2	BiSw80	Pt	71.2	Φ
Pd	335.5	BiSw80	Pt	71.0	JHBK73
Pd	335.2	JHBK73, Asam76	Pt	71.2	BHHK70, KWD71, Nefe78, Scho72, WRDM79, Wagn75
Pd	335.3	WRDM79, WeAn80, BHHK70, Scho72, GGM82, KBAM72	Pt	71.2	CMHL77, CaLe73, HaWi77, BACB75
Ag ₃ OPd ₅ O	334.6	WeAn80	Pt	71.2	CMHL77, CaLe73, HaWi77, BACB75
Ag ₅ OPd ₇ O	334.9	WeAn80	PtSi	73.0	GGM82
Ag ₉ OPd ₁ O	334.9	WeAn80	Pt ₂ Si	72.5	GGM82
Al ₃ OPt ₂ O	337.4	WeAn80	PtCl ₂	73.6	EPCC75
Mg ₇₅ Pt ₂₅	336.2	WeAn80	PtCl ₄	75.5	EPCC75
Pd ₂ Si	336.8	GGM82	PtO	73.8	KWD71
Pd ₃ Si	336.2	AWL80	PtO	74.2	EPCC75
PdI ₂	336.4	KBAM72	PtO ₂	74.6	KWD71
PdBr ₂	337.1	KBAM72	PtO ₂	75.0	EPCC75
PdCl ₂	337.8	KBAM72, NKBP73	Pt(OH) ₂	72.6	HaWi77
PdO	336.3	KGW74	K ₂ Pt ₆	73.4	SNMK78
PdO ₂	337.9	KGW74	K ₂ PtBr ₄	72.6	SNMK78
Na ₂ PdCl ₄	338.0	SeTs76	K ₂ PtBr ₆	74.6	SNMK78
K ₂ PdCl ₄	338.2	KBAM72, NKBP73	K ₂ PtCl ₄	73.0	CMHL77, EPCC75, SNMK78
K ₂ PdBr ₄	337.3	KBAM72	K ₂ PtCl ₄	73.4	Wagn75
K ₂ Pd(NO ₂) ₄	339.0	KBAM72	K ₂ PtCl ₆	75.4	CoHe72, EPCC75, LeBr72, SNMK78
K ₂ PdCl ₆	340.2	KBAM72, Nefe78	K ₂ PtF ₆	77.6	SNMK78
Br ₂ Pd(Ph ₃ P) ₂	337.8	KBAM72	Pt(NH ₃) ₄ Br ₂	73.4	Nefe78
Cl ₂ Pd(Ph ₃ P) ₂	337.8	KBAM72, NSMS79	Pt(NH ₃) ₂ Cl ₂	73.2	CMHL77, Nefe78
I ₂ Pd(Ph ₃ P) ₂	337.5	KBAM72	Pt(NH ₃) ₄ Cl ₂	73.4	SNMK78
(CN) ₂ Pd(Ph ₃ P) ₂	338.2	KBAM72	Pt(NH ₃) ₆ Cl ₄	76.3	SNMK78
Pd ₂ (Ph ₃ P) ₂	336.6	NSMS79	Pt(NH ₃) ₂ (NO ₂) ₂	73.7	Nefe78
Cl ₂ Pd(Ph ₃ P) ₃	342.9	BNSA70	Pt(NH ₃) ₂ (NO ₂) ₂	74.4	CMHL77
Pd(Ph ₃ P) ₄	336.0	NSMS79	K ₂ Pt(OH) ₆	75.1	SNMK78
Pd(OAc) ₂	338.6	NSMS79	K ₂ Pt(NO ₂) ₄	74.1	SNMK78
Pd(SPh) ₂	337.7	BBFR77	K ₂ Pt(NO ₂) ₆	75.9	SNMK78
Pd MNN			(NH ₄) ₂ PtCl ₄	72.4	KaEl79
Pd	327.8	WeAn80, WRDM79	Pt(Ph ₃ P) ₃	71.4	Nefe78
Ag ₃ OPd ₅ O	328.8	WeAn80	Pt(Ph ₃ P) ₄	71.4	Rigg72
Ag ₅ OPd ₇ O	329.8	WeAn80	Cl ₂ Pt(Ph ₃ P) ₂ cis	72.3	CAB71
Ag ₉ OPd ₁ O	329.7	WeAn80	Cl ₂ Pt(Ph ₃ P) ₂ cis	73.0	Rigg72
Al ₃ OPt ₂ O	325.5	WeAn80	Cl ₄ Pt(Et ₃ P) ₂	75.3	LeBr72
Mg ₇₅ Pt ₂₅	326.4	WeAn80	Cl ₄ Pt(Et ₃ P) ₂	75.9	Nefe78, Rigg72
Pm 3d			HClPt(Et ₃ P) ₂	72.6	Rigg72
PmCl ₃	1033.5	MNTB70	O ₂ Pt(Ph ₃ P) ₂	73.0	Rigg72
Pm 4d			Pt(SPh) ₂	72.8	BBFR77
PmCl ₃	128.3	MNTB70	Ph ₃ PPt(SPPH ₂)	71.8	NeSa78
Pr 3d			Cl ₂ Pt(Et ₃ P) ₂	73.1	Rigg72
Pr	931.8	Φ	I ₂ Pt(Et ₃ P) ₂	72.5	Rigg72
Pr ₂ O ₃	933.2	SaRa80	I ₂ Pt(Me ₃ P) ₂ cis	72.6	CAB71
PrO ₂	935.3	SaRa80	I ₂ Pt(Me ₃ P) ₂ trans	72.7	CAB71
			I ₂ Pt(CH ₃ CONH) ₄	74.6	NeSa78
			Br ₂ Pt(CH ₃ CONH) ₄	74.9	NeSa78
			Cl ₂ Pt(CH ₃ CONH) ₄	74.8	NeSa78

Cl ₂ Pt(H ₂ NCH ₂ CH ₂ NH ₂) ₂	73.0	YMK78	Rh ₂ WO ₆	309.4	NFS82
Cl ₂ Pt(cyclooctadien)	73.9	CMHL77	RhNbO ₄	309.2	NFS82
K ₂ PtCl ₆	318.1	EPCC75	RhTaO ₄	309.5	NFS82
Pt M₅N₇N₇			RhVO ₄	309.2	NFS82
Pt	1960.7	Wagn78	K ₃ RhCl ₆	309.8	SNMK78
Pt(M ₄ N ₇ N ₇)	2041.1	Wagn78	K ₃ RhF ₆	312.2	Nefe78
Rb 3d			K ₃ Rh(NO ₂) ₆	310.5	SNMK78
Rb	111.5	Φ	K ₃ Rh(NO ₃) ₆	311.1	SNMK78
RbCl	109.9	Φ	Rh(NH ₃) ₆ Cl ₃	310.5	Nefe78
RbN ₃	109.8	SGRS72	Rh(NO) ₆ Cl ₃	309.8	Nefe78
RbI	110.4	MVS 73	ClRh(Ph ₃ P) ₃	307.4	CWH82, Nefe78, OIIT79
RbBr	110.0	MVS 73	Cl ₃ Rh(Ph ₃ P) ₃	309.7	CWH82
RbCl	109.9	MVS 73	Cl ₆ Rh(Ph ₃ P) ₃	309.7	Nefe78
RbF	109.8	MVS 73	Br ₆ Rh(Ph ₃ P) ₃	307.9	Nefe78
Rb ₃ PO ₄	110.0	MVS 73	NORh(Ph ₃ P) ₃	308.2	Nefe78
Rb ₄ P ₂ O ₇	110.0	MVS 73	Cl ₃ Rh(Ph ₃ P) ₂ MeCN	309.6	GIWa79
RbClO ₄	110.4	MVS73	H(CO)Rh(Ph ₃ P) ₂	308.5	OIIT79
Re 4f			Cl(CO) ₂ Rh(Ph ₃ P)	308.7	Nefe78
Re	40.3	Φ	Cl(CO)Rh(Ph ₃ P) ₂	308.6	CWH82, OIIT79
Re	40.5	FHR80	Cl ₂ Rh ₂ (cyclooctadi) ₂	308.7	CMHL77, CWH82
Re	40.5	SSHU83, WRDM79	Rh ₂ (OAc) ₄ · 2H ₂ O	309.0	Nefe78
Re	41.0	BHU81	Rh(NH ₂ CH ₂ COO) ₃ · H ₂ O	310.3	NPBS74
ReO ₂	43.6	BHU81	Ru 3d		
ReO ₃	46.8	BHU81	Ru	280.1	Φ
K ₂ ReCl ₆	44.2	CoHe72, LeBr72	Ru	280.0	NyMa80
Cl ₃ ReO(Ph ₃ P) ₂	43.9	Folk73, Nefe78	Ru	280.1	Folk73, BHHK70, KiWi74, FEMY77, WRDM79
Cl ₂ ReN(Ph ₃ P) ₂	42.7	Nefe78	RuCl ₃	281.8	Folk73
Cl ₄ Re(Et ₃ P) ₂	43.3	LeBr72	RuO ₂	280.7	SaRa80, KiWi74, McGi82
Cl ₄ Re(PMe ₂ Ph) ₂	43.6	LeBr72	RuO ₃	282.5	KiWi74
Cl ₃ Re(PMe ₂ Ph) ₃ , mer	41.8	LeBr72	RuO ₄	283.3	KiWi74
Cl ₂ Re(PMe ₂ Ph) ₄ , trans	40.5	LeBr72	Ru(NH ₃) ₅ N ₂ I ₂	282.2	Folk73
ClReN ₂ (PMe ₂ Ph) ₄ , trans	40.3	LeBr72, Folk73	Ru(NH ₃) ₅ N ₂ Br ₂	280.5	Folk73
Rh 3d			Ru(NH ₃) ₅ N ₂ Cl ₂	282.5	Folk73
Rh	307.2	Φ	Cl ₃ Ru(PhPMe ₂) ₃ mer	276.6	LeBr72
Rh	307.2	NyMa80	S 2p		
Rh	307.2	OIIT79, WRDM79, FHPW73	S	164.0	Φ
RhI ₃	308.6	Nefe78	S	164.1	SNRS76, WRDM79, RiVe83, LHJG70
RhCl ₃	310.1	OIIT79	BaS	160.1	SiWo80
RhCl ₃ · 3H ₂ O	310.0	CWH82	CdS	161.7	BSRR81
RhCl ₃ · 12H ₂ O	310.1	CMHL77	CoS	162.0	Limo81
Rh ₂ O ₃	308.8	NFS82, CMHL77	Cu ₂ S	161.3	BSRR81
Rh ₂ O ₃	308.2	OIIT79	Cu ₂ S	162.4	NSSP80
BaRh ₂ O ₄	308.4	NFS82	CuS	162.0	Limo81, NSSP80
BeRh ₂ O ₄	308.9	NFS82	CuS	161.3	BSRR81
CaRh ₂ O ₄	308.8	NFS82	FeS	161.6	Bind73, Limo81
CoRh ₂ O ₄	308.8	NFS82	FeS ₂	162.9	Bind73, Limo81
PbRh ₂ O ₄	308.6	NFS82	Ga ₂ S ₃	162.2	TIWB72
KRhO ₂	308.5	NFS82	GeS	161.8	SFS77
LiRhO ₂	308.9	NFS82	GeS ₂	161.7	HKMP74
ZnRh ₂ O ₄	308.7	NFS82	HgS	162.0	NSSP80
Rh ₂ MoO ₆	309.2	NFS82	MnS	162.5	Limo81

MoS ₂	162.5	SSOT81, StEd75, PCLH76	Thiophene	164.3	LHJG70
Na ₂ S	160.6	SWH71	Ph ₃ PS	162.4	FIWe75, MSAV71
Na ₂ S	161.8	LHJG70	Ph ₃ PS	161.8	HVV79
NiS	162.2	ShRe79, NgHe76, DPS77	Ph ₃ AsS	161.7	HVV79
PbS	160.8	SFS77	PhSSPh	164.4	RiVe83, LHJG70
Sb ₂ S ₃	161.8	BCH75	PhCH ₂ SSCH ₂ Ph	164.2	RiVe83
SnS	161.1	SFS77	(PhS) ₃ P	163.6	MSAV71
US	161.5	SNRS76	(PhS) ₃ PS	163.5	MSAV71
US ₃	162.6	SNRS76	BuSSBu	164.1	RiVe83
WS ₂	162.1	NgHe76	MeSSMe	164.3	RiVe83
WS ₂	163.0	Wagn75	NH ₂ CNSH ₂	162.1	LeRa77, NBMO73, SrWa77
ZnS	164.0	Limo81	2-Mercaptobenzimidaz	162.2	YYS79
GeS ₂ TeAs ₂	161.5	HKMP74	2-Mercaptobenzimidaz	162.8	ChHa79
GeS ₃ As ₂	161.6	HKMP74	BuNH ₃ H ₂ SO ₄	167.3	EvRe81
KFeS ₂	161.6	Bind73	Bu ₄ NHSO ₄	168.0	EvRe81
Na ₂ (S*SO ₃)	162.5	Wagn75	Et ₃ NHHSO ₄	168.5	EvRe81
Na ₂ (S*SO ₃)	161.7	LHJG70	PhSCMe ₃	162.4	PiLu72
Na ₂ (SS*O ₃)	167.7	LHJG70	Tetrathionaphthalene	164.4	RiVe83
K ₂ SO ₃	167.5	TMR80	Cysteine	163.2	LiMa79, LHJG70
Na ₂ SO ₃	165.6	SWH71	Cysteine HCl hydrate	163.1	SSEW79
Na ₂ SO ₃	166.6	WaTa82, LHJG70	Cysteine HCl hydrate	163.6	LHJG70
Na ₂ SO ₃	167.2	TMR80	Methionine	162.8	BBFR77
Ag ₂ SO ₄	168.6	TMR80	NH ₂ C ₆ H ₄ SO ₃ H	167.8	HaSh73
Al ₂ (SO ₄) ₃	168.8	LHJG70	(MeOS) ₂	164.5	LHJG70
BaSO ₄	168.8	SiWo80, CLSW83	Me ₂ SO	166.5	LHJG70
CaSO ₄	169.0	CLSW83	(PhCH ₂) ₂ SO	165.9	LHJG70
CoSO ₄	169.7	Limo81	Ph ₂ SO	166.0	LHJG70
CuSO ₄	169.3	WaTa80, NSSP80, Limo81	Me ₂ SO ₂	169.0	LHJG70
FeSO ₄	168.8	Limo81, LHJG70	CH ₃ OS(O)OCH ₃	168.4	LHJG70
Fe ₂ (SO ₄) ₃	169.1	LHJG70	MeSO ₂ Cl	169.3	LHJG70
K ₂ SO ₄	169.1	TMR80	ClC ₆ H ₄ CH ₂ SO ₂ Cl	168.5	LHJG70
MnSO ₄	171.0	Limo81	PhSO ₂ Na	166.3	LHJG70
Na ₂ SO ₄	168.8	TMR80	p-NH ₂ C ₆ H ₄ SO ₂ C ₆ H ₄ NH ₂	167.9	LHJG70
NiSO ₄	169.2	Limo81, NSLS77, Nefe82, ShRe79	p-NH ₂ C ₆ H ₄ SO ₂ NH ₂	168.4	LHJG70
PbSO ₄	168.6	NSSP80	p-CH ₃ C ₆ H ₄ SO ₂ Cl	168.4	LHJG70
SrSO ₄	169.1	CLSW83	p-NH ₂ C ₆ H ₄ SO ₃ Na	168.1	LHJG70
U(SO ₄) ₂	169.1	Chad73	p-O ₂ NC ₆ H ₄ SNa	161.0	LHJG70
ZnSO ₄	169.5	Nefe82	CO ₂ NC ₆ H ₄ SH	163.5	LHJG70
NO ₂ SO ₃	166.8	BCM78	o-O ₂ NC ₆ H ₄ SH	163.9	LHJG70
S ₂ N ₂	164.6	SDIO77	p-O ₂ NC ₆ H ₄ SMe	163.5	LHJG70
SF ₆	174.4	WaTa82	o-O ₂ NC ₆ H ₄ SNH ₂	164.1	LHJG70
SF ₆	177.2	LHJG70	o-O ₂ NC ₆ H ₄ SCl	163.9	LHJG70
SO ₂	167.4	WaTa82	p-O ₂ NC ₆ H ₄ SO ₂ F	169.6	LHJG70
SO ₂	168.1	LHJG70	o-O ₂ NC ₆ H ₄ SO ₂ F	170.0	LHJG70
SOCl ₂	168.1	LHJG70	PhCH ₂ SSCH ₂ Ph	163.6	LHJG70
SOF ₂	170.0	LHJG70	PhCH ₂ S*SOCH ₂ Ph	163.7	LHJG70
SP(NH ₃) ₃	162.3	FIWe75	PhCH ₂ SS*OCH ₂ Ph	165.9	LHJG70
SPCl ₃	163.7	FIWe75	PhCH ₂ S*SO ₂ CH ₂ Ph	163.9	LHJG70
S ₂ Cl ₂	163.5	LHJG70	PhCH ₂ SS*O ₂ CH ₂ Ph	168.0	LHJG70
S ₂ Cl ₁₀	174.4	LHJG70	(CH ₃) ₃ S+I-	165.8	LHJG70
CS ₂	163.7	LHJG70	(CH ₃) ₃ S+(O)I-	168.2	LHJG70
(CH ₂ COOH) ₂ S	163.7	LHJG70	(HOOCCH ₂) ₂ S+CH ₂ COO-	166.2	LHJG70
(CH ₂ Ph) ₂ S	163.3	LHJG70			
PhSH	163.1	LHJG70			
Ph ₂ S	163.2	LHJG70			
			S KLL		
			NiS	2116.1	WaTa80
			NiW ₂ S	2115.9	Wagn78

WS ₂	2115.6	Wagn78	Sc 2p		
Na ₂ SO ₃	2108.5	WaTa82	Sc	398.6	Φ
Na ₂ (SS*O ₃)	2107.8	Wagn75	Sc ₂ O ₃	401.8	Φ
Na ₂ (S*SO ₃)	2112.5	Wagn75	Sc	398.7	SMKM77
CuSO ₄	2108.0	WaTa80	ScN	400.7	STAB76
SO ₂	2106.2	WaTa82	Sc ₂ O ₃	401.9	NGDS75, WRDM79
SF ₆	2100.5	WaTa82	ClSc(C ₃ H ₅) ₂	401.4	WeMe78
			Sc(C ₃ H ₅)(C ₃ H ₈)	400.2	WeMe78
Sb 3d_{5/2}			Se 3d		
\$b	528.3	Φ	Se	55.6	Φ
\$b	528.2	HSBS81, MSV 73, PVVA79, SFS77, WRDM79, Wagn75	Se	55.5	SFS77, BWI80, UeOd82, WRDM79, WSP77, MTHB71
AlSb	528.6	MSV73	Se	55.1	BWI80
\$b _{3/2} \$n ₅	528.0	HSBS81	As ₂ Se ₃	55.1	UeOd82, WSP77
\$b ₂ \$S ₃	529.5	MSV73, Wagn75	Ga ₂ Se ₃	54.6	ITI82, TIWB72
\$b ₂ \$S ₅	529.2	MSV73, Wagn75	GeSe	54.8	SFS77
\$bI ₃	530.4	MSV73	GeSe ₂	54.5	UeOd82
\$bCl ₅	530.9	BCH75	CuInSe ₂	54.0	KJID81
\$bF ₃	531.7	MSV73	In ₂ Se ₃	54.8	KJID81
\$b ₂ \$O ₃	530.0	MSV73, Wagn75	Nb ₃ Se ₄	54.9	Bahl75
\$b ₂ \$O ₅	530.8	MSV73	NbSe ₂	53.7	Bahl75
Rb ₃ Sb ₂ Br ₉	529.9	Tric74	PbSe	53.4	SFS77
Rb ₃ Sb ₂ I ₉	529.9	Tric74	PbSe	54.1	WSP7
Cs ₃ Sb ₂ I ₉	529.2	BCH75	SnSe	53.7	SFS77
Cs ₃ Sb ₂ Br ₉	530.0	BCH75, Tric74	SnSe	55.0	WSP77
Cs ₃ Sb ₂ Cl ₉	529.3	BCH75	MoSe ₂	54.6	BWI79
Cs ₃ Sb ₂ Cl ₉	530.5	Tric74	FeSe ₂	54.9	BWI79
C ₃ SbCl ₆	530.9	Tric74	SeO ₂	58.9	BWI81, ITI82
Co(NH ₃) ₆ SbBr ₆	530.1	Tric74	SeO ₂	59.8	MTHB71, WSP77
Co(NH ₃) ₆ SbCl ₆	530.8	Tric74	H ₂ SeO ₃	59.2	BWI81
KSbF ₆	532.3	MSV73	H ₂ SeO ₃	59.9	MTHB71
KSbF ₆	532.9	Wagn75	H ₂ SeO ₄	61.2	BWI81
NaSbF ₆	532.1	BCH75	Na ₂ SeO ₃	59.1	WSP77
CsSbF ₄	530.6	BCH75	Na ₂ SeO ₄	61.6	WSP77
KSb ₂ F ₇	531.2	Tric74	Na ₂ SeS ₄ O ₆	56.9	WSP77
K ₂ SbF ₅	531.0	Tric74	Ph ₂ Se	55.8	BWI81
Na ₂ SbF ₅	531.3	Tric74	(BrC ₆ H ₄) ₂ Se	56.4	MTHB71
BuNH ₃ SbI ₄	529.6	BCH75	Ph ₂ Se ₂	55.8	BWI81
BuNH ₃ Sb ₂ I ₉	529.9	BCH75	(BrC ₆ H ₄) ₂ Se ₂	56.0	BWI81
Et ₄ NSbF ₆	532.4	BCH75	(C ₁₄ H ₂₉ Se) ₂	56.1	MTHB71
Ph ₂ Sb	528.9	BCH75	I ₂ SePh ₂	58.1	BWI81
Bu ₃ Sb	528.1	BCH75	Br ₂ SePh ₂	57.8	BWI81
Ph ₂ SbBr ₂	529.8	BCH75	Cl ₂ SePh ₂	57.7	BWI81
Me ₃ SbBr ₂	530.3	BCH75	Cl ₂ SePh ₂	58.8	MTHB71
Ph ₂ SbS	528.7	BCH75	C ₁₆ H ₃₃ SeCN	57.7	MTHB71
(C ₁₂ H ₂₅) ₃ SSb	529.8	MSV73	HSePh ₂ P	54.5	NSWM80
Ph ₂ PSbCl ₆	531.7	MSV73	SePh ₃ P	54.3	HVV79
Sb MNN			Ph ₂ SeO	57.6	BWI81
Sb	464.1	WRDM79, PVVA79, Wagn75	(PhCH ₂) ₂ SeO	58.2	MTHB71
Sb ₂ S ₃	462.1	Wagn75	(BrC ₆ H ₄) ₂ SeO	58.4	MTHB71
Sb ₂ S ₅	462.2	Wagn75	(C ₄ H ₉ COOH) ₂ SeO	58.5	MTHB71
Sb ₂ O ₃	462.1	Wagn75	PhSeO(OH)	58.8	MTHB71
KSbF ₆	454.4	Wagn75	ClC ₆ H ₄ SeO(OH)	59.3	MTHB71

FC ₆ H ₄ SeO(OH)	59.3	MTHB71	Hydroxysodalite	101.7	WPHK82
ClC ₆ H ₄ SeO ₂ (OH)	60.2	MTHB71	Kaolinite	102.7	Barr83
(MeOC ₆ H ₄) ₂ SeO ₂	60.0	MTHB71	Kaolinite	103.0	WPHK82
(HOC ₆ H ₄ S) ₂ Se	56.2	WSP77	Mica, Muscovite	102.4	WPHK82
			Natrolite	102.2	WPHK82
			Pyrophyllite	102.9	WPHK82
Se LMM			AlSiO ₅ , sillimanite	102.7	WPHK82
Se	1307.0	BW181	LiAlSi ₂ O ₆ , spodumene	102.5	WPHK82
Se	1306.7	Wagn75	Talc, Mg ₃ Si ₄ O ₁₀ (OH) ₂	103.1	WPHK82
SeO ₂	1301.4	BW181	Wollastonii, Ca ₃ Si ₃ O ₉	102.4	WPHK82
H ₂ SeO ₃	1300.8	BW181	Mol Sieve A	101.4	WPHK82
H ₂ SeO ₄	1297.9	BW181	Mol Sieve A	101.3	Barr83
Na ₂ SeO ₃	1301.2	Wagn75	Mol Sieve A, Ca form	101.8	Barr83
Ph ₂ Se	1304.0	BW181	Mol Sieve X	102.2	WPHK82
Ph ₂ Se ₂	1304.3	BW181	Mol Sieve X	102.2	Barr83
I ₂ SePh	1302.1	BW181	Mol Sieve X, Ca form	102.7	Barr83
Cl ₂ SePh ₁	1302.9	BW181	Mol Sieve Y	102.8	WPHK82
Ph ₂ SeO	1301.9	BW181	Mol Sieve Y	102.8	Barr83
			Mol Sieve Y, Ca form	102.8	Barr83
			K ₂ SiF ₆	104.6	MoVa73
			Na ₂ SiF ₆	104.3	NSLS77
Si 2p			p-Methylsil. (linear)	102.4	WPHK82
Si	99.3	Φ	p-Methylsil. (resin)	102.9	WPHK82
SiO ₂	103.3	Φ	p-Phenylsil. (resin)	102.7	WPHK82
Si	99.5	AWL80, PADS78, WRDM79, WPHK82, Tayl81, KBHN74	Me ₄ Si	100.5	GCH76
			Ph ₄ Si	100.7	MoVa73
Si, p-type	99.0	HBBK72	Ph ₄ Si	101.2	GCH76
Si, n-type	100.0	HBBK72	Et ₃ SiH	100.7	GCH76
Si, (100)	99.7	TLR78	Et ₃ SiOH	101.1	GCH76
Fe ₃ Si	99.5	ShTr75	Et ₃ SiBr	101.0	GCH76
MoSi ₂	99.6	WPHK82	Et ₃ SiCl	101.4	GCH76
MoSi ₂	99.1	BrWh78	Et ₃ SiF	101.8	GCH76
Ni ₂ Si	98.9	GGM82	Et ₂ SiCl ₂	102.1	GCH76
NiSi	98.8	GGM82	EtSiCl ₃	102.9	GCH76
NiSi	98.4	AWL80	(CH ₂ =CH) ₄ Si	100.7	GCH76
Pd ₂ Si	99.7	GGM82	Me ₃ SiSiMe ₃	100.5	GCH76
Pd ₃ Si	99.6	AWL80	Me ₂ SiOSiMe ₃	100.9	GCH76
PdSi	99.8	WaTa80	Ph ₃ SiSiPh ₃	100.7	GCH76
Pt ₂ Si	100.5	GGM82	Ph ₃ SiOSiPh ₃	101.3	GCH76
PtSi	100.5	GGM82			
			Si (KLL)		
Si ₃ N ₄	101.8	WHMC78, WaTa80, Tayl81, TLR78	Si	1616.6	WPHK82, CDN 77
SiS ₂	103.4	MoVa73	MoSi ₂	1617.2	WPHK82
SiO ₂	103.6	KBHN74, NGDS75, MoVa73, Barr83	PdSi	1617.4	WaTa80
			Si ₃ N ₄	1612.6	WaTa80
SiO ₂ , Vycor	103.5	WPHK82	SiO ₂	1608.8	KBHN74
SiO ₂ , quartz	103.7	WPHK82, TLR 78	SiO ₂ , Vycor	1608.5	WPHK82
SiO ₂ , alpha cristobal	103.3	WPHK82	SiO ₂ , quartz	1608.6	WPHK82
SiO ₂ gel	103.4	WPHK82	SiO ₂ , alpha cristobal	1608.8	WPHK82
Ni ₂ SiO ₄	102.9	LFWS79	SiO ₂ gel	1608.3	WPHK82
NiSiO ₃	103.3	SRD79	NaAlSi ₃ O ₈ , albite	1609.3	WPHK82
Al ₂ SiO ₅ , kyanite	102.8	AnSw74	H Zeolon	1608.4	WPHK82
Al ₂ SiO ₅ , mullite	103.0	AnSw74	Hemimorphite	1610.5	WPHK82
Al ₂ SiO ₅ , sillimanite	102.6	AnSw74	Hydroxysodalite	1610.7	WPHK82
NaAlSi ₃ O ₈ , albite	102.6	WPHK82	Kaolinite	1609.0	WPHK82
Bentonite	102.9	Barr83	Mica, Muscovite	1609.6	WPHK82
H Zeolon	103.3	WPHK82			
Zn ₄ Si ₂ O ₇ (OH) ₂ · 2H ₂ O	102.0	WPHK82			

Natrolite	1609.6	WPHK82	Ph ₄ Sn	487.1	HWVV74
Pyrophyllite	1609.2	WPHK82	Ph ₃ SnI	486.3	WVV79
AlSiO ₅ , sillimanite	1609.5	WPHK82	Ph ₃ SnI	487.5	HWVV74
LiAlSi ₂ O ₆ , spodumene	1609.6	WPHK82	Ph ₃ SnBr	487.5	HWVV74
Talc, Mg ₃ Si ₄ O ₁₀ (OH) ₂	1608.9	WPHK82	Ph ₃ SnCl	486.3	WVV79
Wollastonii, Ca ₃ Si ₃ O ₉	1610.0	WPHK82	Ph ₃ SnCl	487.0	MoVa73
Mol Sieve A	1610.1	WPHK82	Ph ₃ SnCl	487.6	HWVV74
Mol Sieve X	1609.4	WPHK82	Ph ₃ SnF	486.2	WVV79
Mol Sieve Y	1608.6	WPHK82	Ph ₃ SnF	487.3	HWVV74
p-Methylsil. (linear)	1609.4	WPHK82	Ph ₃ SnOH	485.6	WVV79
p-Methylsil. (resin)	1608.8	WPHK82	Cl ₄ Sn(pyridine) ₂	487.3	WVV79
p-Phenylsil. (resin)	1610.0	WPHK82	Cl ₃ SnEt(pyridine) ₂	487.2	WVV79
			Cl ₃ SnPh(pyridine) ₂	487.2	WVV79
Sm 3d_{5/2}			Me ₃ SnF	486.7	WVV79
Sm	1081.1	Φ	Me ₂ SnF ₂	487.1	WVV79
Sm	1081.2	DKMB76	Me ₂ SnSO ₄	487.0	WVV79
Sm ₂ O ₃	1083.4	WRDM79	Bu ₂ SnO	485.6	WVV79
			Br ₆ Sn(Et ₄ N) ₂	487.0	WVV79
Sn 3d_{5/2}			Cl ₃ Sn(Me ₄ N)	486.1	GZF73
Sn	485.0	Φ	Cl ₄ Sn(Me ₂ SO) ₂	487.0	GZF73, WVV79
Sn	484.9	NyMa80			
Sn	485.1	SFS77	Sn MNN		
Sn	485.0	WRDM79, PVVA79, LAK 77, Wagn75, OCH 79	Sn	437.4	PVVA79, Wagn75, WRDM79, LAK 77
Sn alpha	485.0	Hegd82	SnS	435.7	Wagn75
Sn beta	484.6	Hegd82, HSBS81	SnO ₂	432.7	LAK77
Ag ₉₅ Sn ₅	485.6	HSBS81, Hegd82	NaSnF ₃	430.8	Wagn75
AuSn	485.2	FHPW73	Na ₂ SnO ₃	431.7	Wagn75
AuSn ₄	484.9	FHPW73			
Cd ₉₉ · 5Sn · OO ₅	485.3	Hegd82	Sr 3d		
Cd ₉₅ Sn ₅	485.6	Hegd82	Sr	134.3	Φ
In ₉₅ Sn ₅	485.2	Hegd82	Sr	134.4	VaVe80
Pb ₉₅ Sn ₅	486.4	Hegd82	SrO	135.3	VaVe80
Sb ₉₅ Sn ₅	485.2	Hegd82	SrF ₂	133.8	WRDM79
SnTe	485.6	SFS77	SrCO ₃	133.2	CLSW83
SnSe	485.7	SFS77	SrSO ₄	134.3	CLSW83
SnS	485.6	SFS77	Sr(NO ₃) ₂	134.7	CLSW83
SnBr ₂	486.9	GZF73	SrMoO ₄	133.5	NFS82
SnCl ₂	486.7	WVV79	SrRh ₂ O ₄	133.0	NFS82
SnF ₂	487.0	MoVa73			
SnF ₂	487.0	MoVa73	Ta 4f		
SnO	486.0	ADPS77	Ta	21.9	Φ
SnO	486.9	WVV79, MoVa73	Ta	21.6	VHE82
SnO ₂	486.7	LAK 77, MoVa73, WRDM79, NGDS75, WVV79	Ta	21.6	MSC73
(NH ₄) ₂ SnCl ₆	486.7	GZF73	Ta	21.9	WRDM79, WaTa80
BaSnCl ₄	486.8	WVV79	TaS	26.6	MSC73
Ba(SnCl ₃) ₂	486.8	WVV79	TaS ₂	26.7	MSC73
KSnF ₃	486.7	GZF73	TaBr ₅	26.9	MSC73
K ₂ SnF ₆	487.6	MoVa73	TaCl ₅	27.3	MSC73
NaSnF ₃	487.4	Wagn75	TaF ₅	27.8	MSC73
Na ₂ SnO ₃	486.2	MoVa73	Ta ₂ O ₅	26.7	SaRa80, MSC 73, NFS82, NGDS75
Na ₂ SnO ₃	486.7	Wagn75			
Na ₂ SnO ₃	487.2	ADPS77	KTaO ₄	25.9	MSC73
Ph ₄ Sn	485.1	WVV79	RhTaO ₄	25.8	NFS82
Ph ₄ Sn	486.3	MoVa73	K ₂ TaF ₇	29.4	MSC73

Cl ₂ Ta ₆ Cl ₁₂ (H ₂ O) ₄ · 4H ₂ O	25.8	BeWa79		
Br ₆ (Ta ₆ Cl ₁₂)(Bu ₄ N) ₂	26.3	BeWa79		
Cl ₆ (Ta ₆ Cl ₁₂)(Et ₄ N) ₂	26.2	BeWa79		
Ta MNN				
Ta	1674.8	WaTa80		
Tb 4d				
Tb	146.0	Φ		
Tb ₂ O ₃	148.7	SaRa80		
TbO ₂	149.2	SaRa80		
Tb 3d				
Tb	1242.0	Φ		
Tb ₂ O ₃	1241.5	SaRa80		
TbO ₂	1241.4	SaRa80		
Te 3d5/2				
Te	573.1	Φ		
Te	573.0	NyMa80		
Te	573.0	SFS77		
Te	573.0	PVVA79, WRDM79, BWI77, Bahl75		
Te	572.7	SNRS76, SWH71		
CdTe	572.3	SBB80		
GeTe	572.7	SFS77		
Hg _{0.8} Cd _{0.1} Te	572.3	SBB80		
Na ₂ Te	572.2	SWH71		
Nb ₃ Te ₄	572.6	Bahl75		
NbTe ₄	572.8	Bahl75		
PbTe	572.0	SFS77		
SnTe	572.3	SFS77		
U ₂ Te ₃	572.9	SNRS76		
UTe ₃	573.0	SNRS76		
ZnTe	572.9	SWH71		
TeI ₄	575.8	BWI77		
TeBr ₂	576.7	BWI77		
TeCl ₄	576.9	BWI77		
TeO ₂	575.7	GBP81, SBB80		
TeO ₃	576.6	SWH71		
Te(OH) ₆	577.1	BWI77		
(NH ₄) ₂ TeCl ₆	576.9	BWI77		
(NH ₄) ₂ TeO ₄	576.5	SWH71		
K ₂ TeO ₃	575.5	SWH71		
Na ₂ TeO ₄	576.8	Wagn75		
Cl ₂ TePh ₂	576.2	BWI77		
Br ₂ TePh ₂	576.2	BWI77		
I ₂ TePh ₂	575.4	BWI77		
I ₂ TeEt ₂	575.3	BWI77		
Ph ₂ Te ₂	573.9	BWI77		
Br ₃ TePh	576.6	BWI77		
I ₃ TePh	575.8	BWI77		
I ₂ TeMe ₂	575.6	BWI77		
p-tolyI TeOOH	576.1	BWI77		
Br ₃ TeBu	576.6	BWI77		
Te MNN				
Te	492.2		WRDM79	
TeBr ₂	487.3		BWI78	
TeCl ₄	486.1		BWI78	
TeO ₂	487.1		BWI78	
TeO ₃	485.5		BWI78	
Te(OH) ₆	485.1		BWI78	
(NH ₄) ₂ TeCl ₆	486.4		BWI78	
Na ₂ TeO ₄	485.5		Wagn75	
Cl ₂ TePh ₂	486.3		BWI78	
Br ₂ TePh ₂	486.6		BWI78	
I ₂ TePh ₂	487.8		BWI78	
I ₂ TeEt ₂	487.6		BWI78	
Ph ₂ Te ₂	488.5		BWI78	
Br ₃ TePh	486.8		BWI78	
I ₃ TePh	488.2		BWI78	
I ₂ TeMe ₂	486.6		BWI78	
p-tolyI TeOOH	486.6		BWI78	
Br ₃ TeBu	486.5		BWI78	
Th 4f7/2				
Th	333.2		Φ	
Th	333.2		WRDM79	
ThO ₂	334.4		VLDH77	
ThF ₄	336.5		WRDM79	
Th 4ds/2				
Th	675.3		FBWF74	
ThO ₂	675.5		VLDH77	
Ti 2p				
Ti	454.1		Φ	
TiO ₂	458.8		Φ	
Ti	453.7		ALMP82	
Ti	453.9		LANM81	
Ti	453.9		NSCP74, WRDM79	
TiB ₂	454.4		MECC73	
TiN	455.8		STAB76	
TiCl ₄	458.5		MRV83	
TiO	455.1		SPB76a	
TiO ₂	458.7		NSCP74, SPB76a, WRDM79, NGDS75	
TiO ₂ (anatase, rutile)	459.2		MWI75	
BaTiO ₃ (cubic, tetra.)	458.5		MWI75	
CaTiO ₃	458.9		MWI75	
PbTiO ₃	458.6		MWI75	
SrTiO ₃	458.8		MWI75	
Cl ₂ Ti(C ₅ H ₅) ₂	457.1		GSMJ74	
CITi(C ₅ H ₅) ₂	455.8		GSMJ74	
Ti(C ₅ H ₅)(C ₇ H ₇)	455.4		GSMJ74	
Ti LMM				
Ti	419.1		WRDM79	

Tl 4f			V 2p		
Tl	117.7	Φ	V	512.2	Φ
Tl	117.8	MBN80, WRDM79	V ₂ O ₅	517.4	Φ
TlI	118.5	MSC73	V	512.1	LANM81
TlBr	119.2	MSC73	V	512.3	WRDM79, NSCP74
TlCl	119.0	MSC73	V	512.9	KKL83
TlF	119.2	MSC73	V	513.4	SMKM77
Tl ₂ S	118.7	MSC73	V	512.4	RoRo76, LFS 73, FrSa75
Tl ₂ S ₃	118.7	MSC73	VB ₂	513.2	MECC73
Tl ₂ O ₃	117.5	MSC73	VN	514.4	RoRo76, STAB76
Cl ₃ Tl(pyridine) ₂	118.5	Walt77	V ₂ O ₃	515.7	CGR78
Cl ₆ Tl ₂ (PhPEt ₂) ₅	117.9	Walt77	VO ₂	516.3	KKL83
			V ₂ O ₅	517.6	NSLS77, NSCP74, WRDM79, NGDS75, NFS82
Tm 4d			VOCl ₂	516.4	LFS73
Tm	175.4	Φ	VOSO ₄	515.9	LFS73
			Cs ₃ VO ₄	516.9	NFS82
U 4f_{7/2}			Rb ₃ VO ₄	516.9	NFS82
U	377.3	Φ	Na ₃ VO ₄	517.3	NFS82
U	377.2	VRPC74, Chad73, WRDM79	Li ₃ VO ₄	517.5	NFS82
U ₂ Te ₃	380.5	SNRS76	Rh ₃ VO ₄	516.9	NFS82
U ₂ Te ₃	381.3	SNRS76	K ₄ V(CN) ₆	513.3	Vann76
U ₂ Se	380.3	SNRS76	V(acac) ₃	514.2	LFS73
U ₂ Se ₃	379.1	SNRS76	VO(acac) ₂	515.1	LFS73
US	380.1	SNRS76	ClV(C ₅ H ₅) ₂	513.8	GSMJ74
U ₂ S ₃	379.4	SNRS76	V(C ₅ H ₅) ₂	512.9	GSMJ74, BCDH73
U ₂ Br ₃	378.4	TBVL82	V(C ₅ H ₅)(C ₇ H ₇)	513.3	GSMJ74
U ₂ Br ₄	379.9	TBVL82			
U ₂ Cl ₃	378.3	TBVL82	V LMM		
U ₂ Cl ₄	380.2	TBVL82	V	472.0	WRDM79
U ₂ Cl ₅	381.9	TBVL82	VO ₂	468.6	KKL83
UF ₃	380.1	TBVL82	V ₂ O ₅	468.0	KKL83
UF ₄	382.2	TBVL82			
UF ₄	382.7	Chad73	W 4f		
UF ₅	382.6	TBVL82	W	31.4	Φ
UO ₂	380.0	VRPC74, Chad73, MSSS81	W	31.4	VHE82
U ₂ O ₈	381.0	Chad73, ChGr72	W	31.4	WRDM79, CoRa76, CGR 78, BiPo73, NSLS77
U ₂ O ₉	379.9	HoTh79	WC	31.5	CoRa76
UO ₃	381.7	MSSS81, Chad73, ChGr72	WC	32.2	MSC73
UOBr	380.1	TBVL82	WS ₂	33.2	Wagn75
UOBr ₂	380.4	TBVL82	WBr ₅	36.3	MSC73
UOCl	380.0	TBVL82	WBr ₆	35.9	MSC73
UOCl ₂	380.3	TBVL82	WCl ₆	36.9	MSC73
UO ₂ Br	380.5	TBVL82	WOCl ₄	37.2	MSC73
UO ₂ Br ₂	381.1	TBVL82	WO ₂	32.8	CGR78, CoRa76, NgHe76
UO ₂ Cl ₂	381.6	TBVL82	W ₁₈ O ₄₉	34.3	BiPo73
UO ₂ F ₂	382.9	TBVL82, Chad73	WO ₃	35.8	SaRa80, CoRa76, CGR 78, BiPo73, KMH 78
U ₂ SO ₄	381.6	Chad73	WO ₃	35.8	NFS82, NGDS75
U ₂ (NO ₃) ₂ · 6H ₂ O	382.0	Chad73	Al ₂ (WO ₄) ₃	36.1	BiPo73
U ₂ (acac) ₂	379.7	Chad73	CaWO ₄	35.0	Nefe82, NFS 82
U ₂ (AcO) ₂ · 2H ₂ O	381.0	Chad73	H ₂ WO ₄	35.3	CGR78
Ca ₂ UO ₇	380.7	Chad73	H ₂ WO ₄	36.2	BiPo73
Er ₂ UO ₇	381.4	Chad73	K ₂ WO ₄	36.0	NFS82
K ₂ UF ₆	382.4	PMDS77			

Li ₂ WO ₄	36.0	NFS 82, MSC 73	Zn ₃ P ₂	1020.6	NSDU75
Na ₂ WO ₄	36.3	Wagn75	ZnP ₂	1020.9	NSDU75
Na _{0.6} WO ₃	35.8	BiPo73	ZnI ₂	1023.0	GaWi77, SATD73
Na _{0.1} WO ₃	35.6	BiPo73	ZnBr ₂	1023.4	Wagn75, SATD73
NiWO ₄	35.4	NgHe76	ZnCl ₂	1021.9	KIHe83
Rh ₂ WO ₆	35.6	NFS82	ZnCl ₂	1023.1	SATD73
(NH ₄) ₆ W ₇ O ₂₄ · 4H ₂ O	36.3	BiPo73	ZnF ₂	1022.2	GaWi77
K ₂ WCl ₆	34.9	LeBr72	ZnF ₂	1022.8	Wagn75
Cl ₄ W(Et ₃ P) ₂	34.6	LeBr72	ZnO	1021.8	Scho73a, WRDM79
Cl ₃ SnW(CO) ₆ (C ₅ H ₅)	32.4	WVVV77	ZnO	1022.5	GaWi77
Ph ₃ PW(CO) ₃	31.6	HVV79	Zn(acac) ₂	1021.4	Wagn75
			(Me ₄ N) ₂ ZnBr ₄	1020.9	EMGK74
			ZnSO ₄	1023.1	Nefe82
			Zn ₄ Si ₂ O ₇ (OH) ₂ · 2H ₂ O	1022.0	WPHK82
			ZnCr ₂ O ₄	1022.1	BDFP81
			ZnRh ₂ O ₄	1021.7	NFS82
Xe 3d_{5/2}			Zn LMM		
Xe in graphite	669.7	Φ	Zn	992.1	GaWi77, KLMP74, MaDu77, Scho73a, KPML73, KIHe83
Xe in Ag	669.6	CiHa74	Zn	992.1	WRDM79, Wagn75
Xe in Au	668.9	CiHa74	Cu ₆₄ Zn ₃₆	992.7	VanO77
Xe in Cu	669.6	CiHa74	ZnS	989.7	GaWi77
Xe in Fe	670.2	Wagn75	ZnI ₂	988.7	GaWi77
Xe in graphite	669.7	WRDM79	ZnBr ₂	987.3	Wagn75
Na ₄ XeO ₆	674.1	Wagn77	ZnCl ₂	989.4	KIHe83
			ZnF ₂	986.2	GaWi77
Xe MNN			ZnF ₂	986.7	Wagn75
Xe in Fe	544.8	Wagn75	ZnO	988.5	Scho73a
Xe in graphite	545.2	WRDM79	ZnO	987.7	GaWi77
Na ₄ XeO ₆	541.4	Wagn77	ZnO	988.2	KIHe83
			Zn(acac) ₂	987.7	Wagn75
			Zn ₄ Si ₂ O ₇ (OH) ₂ · 2H ₂ O	987.3	WPHK82
Y 3d			Zr 3d		
Y	156.0	Φ	Zr	178.9	Φ
Y	155.8	NyMa80	Zr	178.8	NyMa80
Y ₂ O ₃	156.8	WRDM79, NGDS75	Zr	178.3	NSCP74
			Zr	178.9	WRDM79
Yb 4d			ZrO ₂	182.2	SaRa80, NGDS75, NSCP74
Yb	182.4	Φ	ZrF ₅	185.3	NKBP73
Yb	181.3	HHL70, KEML74	K ₂ ZrF ₆	184.2	NKBP73
Yb	182.7	LPWF75	K ₃ ZrF ₇	183.7	NKBP73
Yb ₂ O ₃	185.4	HHL70	KZrF ₅ · H ₂ O	184.7	NKBP73
			Br ₂ Zr(OH) ₂ CH ₃ CHNH ₂ C	182.9	KNPP74
Zn 2p_{3/2}			Cl ₂ Zr(OH) ₂ CH ₃ CHNH ₂ C	183.0	KNPP74
Zn	1021.8	Φ			
Zn	1021.9	LANM81, LKMP73			
Zn	1021.8	GaWi77, KLMP74, MaDu77, Scho73a, KPML73, KIHe83			
		WRDM79, Wagn75, SMKM77			
Zn	1021.8	VanO77			
Cu ₆₄ Zn ₃₆	1021.6	GaWi77			
ZnS	1022.0				

Appendix C. Chemical States Tables References

Note: The references in the Chemical States Tables are made with three or four letters which represent the authors' initials. Three or four capital letters indicate three or more authors; alternating upper- and lower-case letters represent two authors (the letters are the first two letters of each last name); and a capital letter followed by three lower case letters indicates a single author. The initials are followed by two digits, which represent the last two digits of the year of publication. This may be followed by a small letter, to distinguish between two otherwise identical reference notations.

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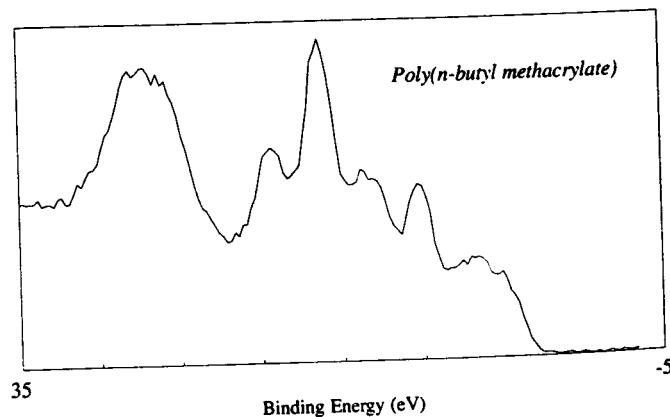
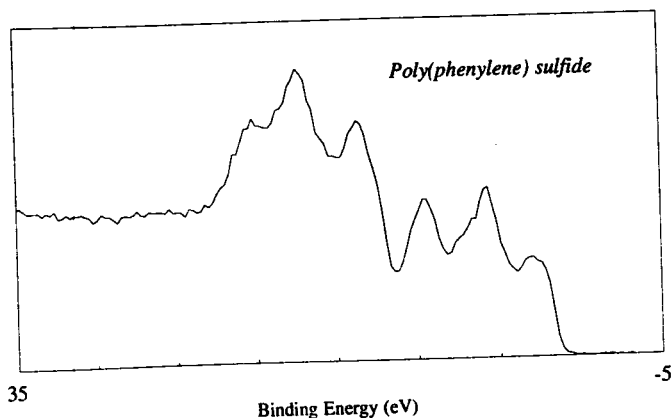
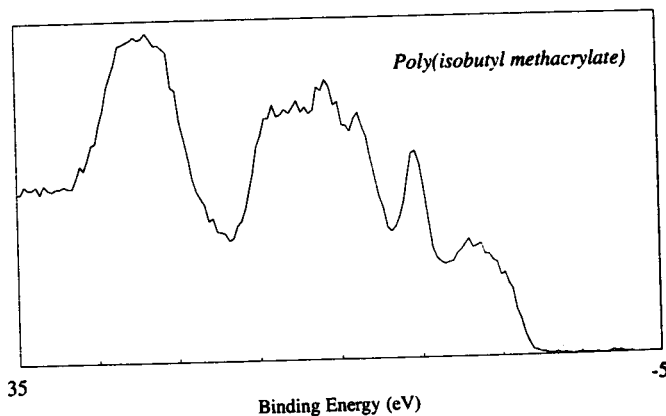
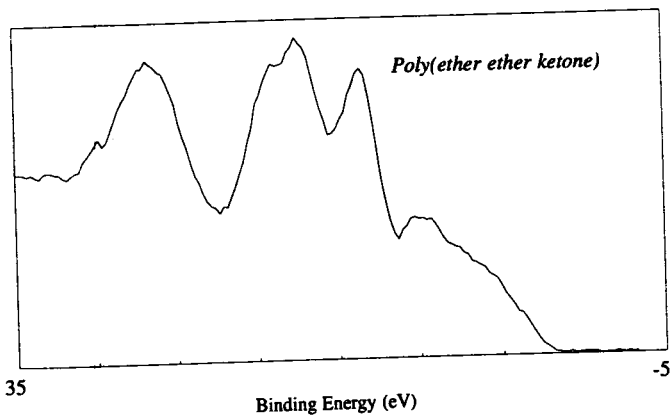
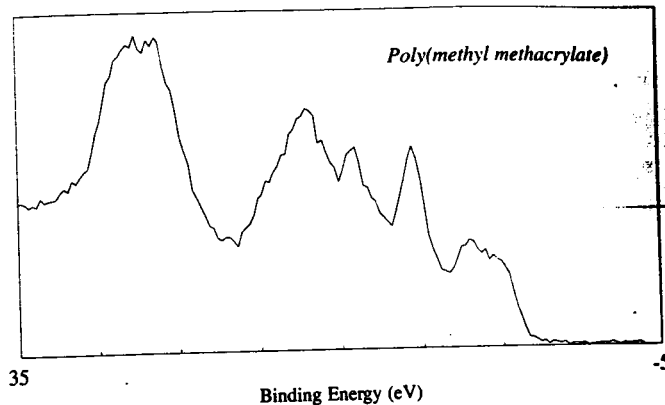
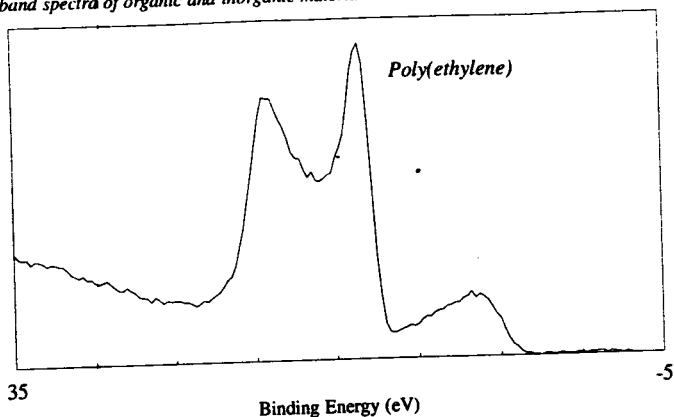
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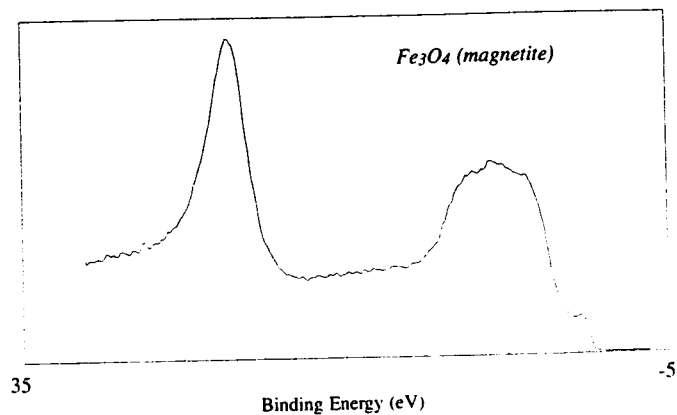
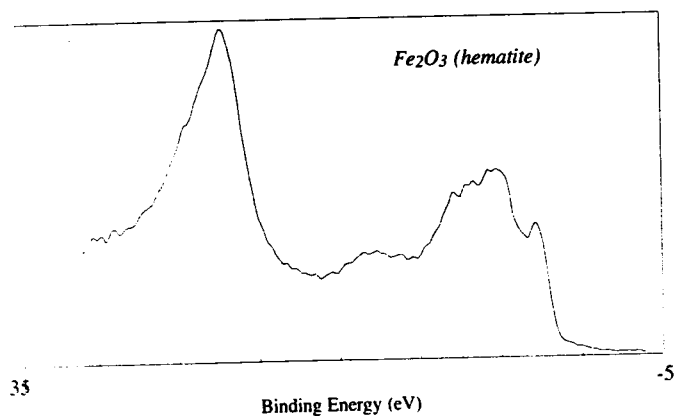
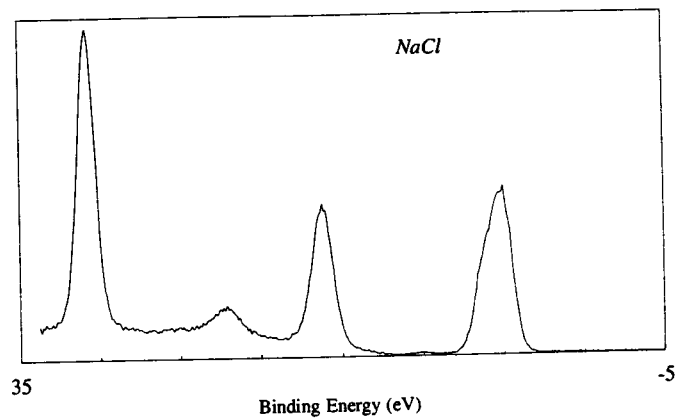
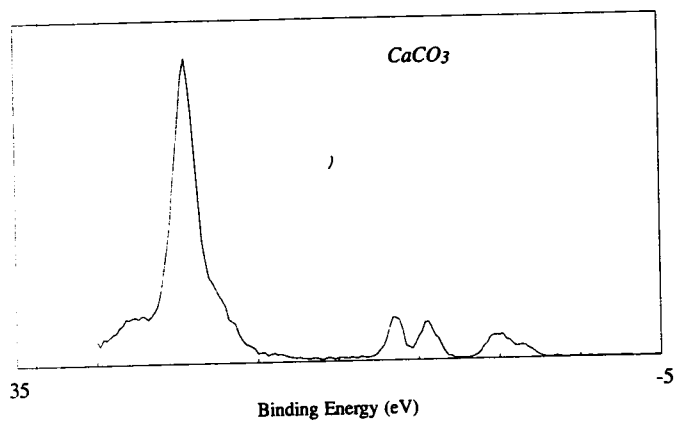
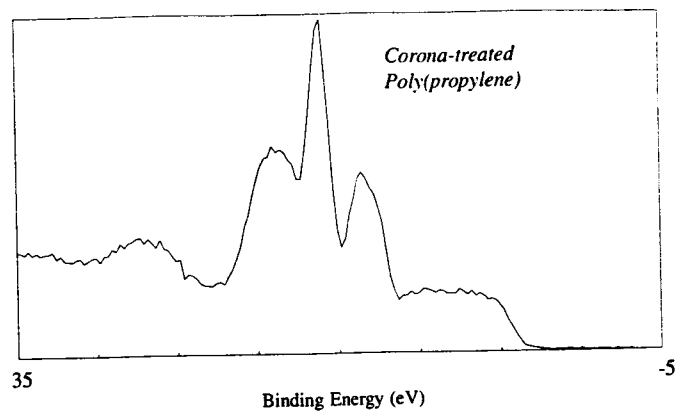
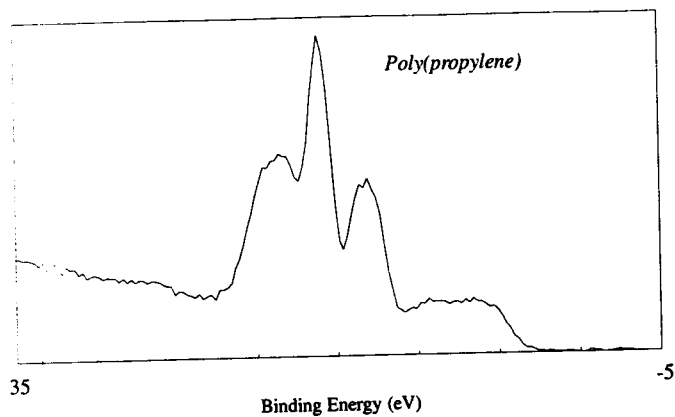
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Acknowledgment: Physical Electronics, Inc. (PHI), acknowledges Dr. Charles Wagner's contributions to the Chemical States Tables. The entries in the tables, used with his permission, were compiled by Dr. Wagner in collaboration with PHI.

Appendix D. Valence Band Spectra

In some cases, the chemical shifts observed in core level XPS are not sufficient to identify the surface chemistry of a particular sample. In the case of XPS analysis of polymers, the changes in carbon chemistry may be quite subtle in core level XPS or the chemical shifts may be only a secondary or tertiary effect. With the routine use of monochromators in XPS and the high counting rates made possible by current spectrometer technologies, many analysts use valence bands for identification of materials. In many cases, the valence bands and the high counting rates made possible by current spectrometer technologies, rather than for identifying specific molecular orbitals. The fingerprints of the valence bands may then be used to aid in both the identification of polymers and the quantification of polymer mixtures by using methods such as linear least squares fitting. The following is a small compilation of valence band spectra of organic and inorganic materials to illustrate the utility of valence band data.





Appendix E. Atomic Sensitivity Factors for X-ray Sources at 90°

This table is based upon empirical peak area values* corrected for the system's transmission function. The values are only valid for and should only be applied when the electron energy analyzer used has the transmission characteristics of the spherical capacitor type analyzer equipped with an Omni Focus III lens supplied by Physical Electronics. The data are calculated for x-rays at 90° relative to the analyzer.

Element	Line	ASF	Element	Line	ASF	Element	Line	ASF	Element	Line	ASF
Ag	3d	5.198	Eu	4d	2.210	Na	1s	1.685	Si	2p	0.283
Al	2p	0.193	F	1s	1.000	Nb	3d	2.517	Sm	3d _{5/2}	2.907
Ar	2p	1.011	Fe	2p	2.686	Nd	3d	4.697	Sn	3d _{5/2}	4.095
As	3d	0.570	Ga	2p _{3/2}	3.341	Ne	1s	1.340	Sr	3d	1.578
Au	4f	5.240	Gd	4d	2.207	Ni	2p	3.653	Ta	4f	2.589
B	1s	0.159	Ge	2p _{3/2}	3.100	O	1s	0.711	Tb	4d	2.201
Ba	4d	2.627	Hf	4f	2.221	Os	4f	3.747	Tc	3d	3.266
Be	1s	0.074	Hg	4f	5.797	P	2p	0.412	Te	3d _{5/2}	4.925
Bi	4f	7.632	Ho	4d	2.189	Pb	4f	6.968	Th	4f _{7/2}	7.498
Br	3d	0.895	I	3d _{5/2}	5.337	Pd	3d	4.642	Ti	2p	1.798
C	1s	0.296	In	3d _{5/2}	3.777	Pm	3d	3.754	Tl	4f	6.447
Ca	2p	1.634	Ir	4f	4.217	Pr	3d	6.356	Tm	4d	2.172
Cd	3d _{5/2}	3.444	K	2p	1.300	Pt	4f	4.674	U	4f _{7/2}	8.476
Ce	3d	7.399	Kr	3d	1.096	Rb	3d	1.316	V	2p	1.912
Cl	2p	0.770	La	3d	7.708	Re	4f	3.327	W	4f	2.959
Co	2p	3.255	Li	1s	0.025	Rh	3d	4.179	Xe	3d _{5/2}	5.702
Cr	2p	2.201	Lu	4d	2.156	Ru	3d	3.696	Y	3d	1.867
Cs	3d _{5/2}	6.032	Mg	2s	0.252	S	2p	0.570	Yb	4d	2.169
Cu	2p	4.798	Mn	2p	2.420	Sb	3d _{5/2}	4.473	Zn	2p _{3/2}	3.354
Dy	4d	2.198	Mo	3d	2.867	Sc	2p	1.678	Zr	3d	2.216
Er	4d	2.184	N	1s	0.477	Se	3d	0.722			

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Appendix F. Atomic Sensitivity Factors for X-ray Sources at 54.7°

This table is based upon empirical peak area values corrected for the system's transmission function. The values are only valid for and should only be applied when the electron energy analyzer used has the transmission characteristics of the spherical capacitor type analyzer equipped with an Omni Focus III lens supplied by Physical Electronics. The data are calculated for x-rays at 54.7° relative to the analyzer.*

Element	Line	ASF	Element	Line	ASF	Element	Line	ASF	Element	Line	ASF
Ag	3d	5.987	Eu	4d	2.488	Na	1s	1.685	Si	2p	0.339
Al	2p	0.234	F	1s	1.000	Nb	3d	2.921	Sm	3d _{5/2}	3.611
Ar	2p	1.155	Fe	2p	2.957	Nd	3d	5.671	Sn	3d _{5/2}	4.725
As	3d	0.677	Ga	2p _{3/2}	3.720	Ne	1s	1.340	Sr	3d	1.843
Au	4f	6.250	Gd	4d	2.484	Ni	2p	4.044	Ta	4f	3.082
B	1s	0.159	Ge	2p _{3/2}	3.457	O	1s	0.711	Tb	4d	2.477
Ba	3d _{5/2}	7.469	Hf	4f	2.639	Os	4f	4.461	Tc	3d	3.776
Be	1s	0.074	Hg	4f	6.915	P	2p	0.486	Te	3d _{5/2}	5.705
Bi	4f	9.140	Ho	4d	2.469	Pb	4f	8.329	Th	4f _{7/2}	9.089
Br	3d	1.053	I	3d _{5/2}	6.206	Pd	3d	5.356	Ti	2p	2.001
C	1s	0.296	In	3d _{5/2}	4.359	Pm	3d	4.597	Tl	4f	7.691
Ca	2p	1.833	Ir	4f	5.021	Pr	3d	7.627	Tm	4d	2.454
Cd	3d _{5/2}	3.974	K	2p	1.466	Pt	4f	5.575	U	4f _{7/2}	10.315
Ce	3d	8.808	Kr	3d	1.287	Rb	3d	1.542	V	2p	2.116
Cl	2p	0.891	La	3d	9.122	Re	4f	3.961	W	4f	3.523
Co	2p	3.590	Li	1s	0.025	Rh	3d	4.822	Xe	3d _{5/2}	6.64
Cr	2p	2.427	Lu	4d	2.441	Ru	3d	4.273	Y	3d	2.175
Cs	3d _{5/2}	7.041	Mg	2s	0.252	S	2p	0.666	Yb	4d	2.451
Cu	2p	5.321	Mn	2p	2.659	Sb	3d _{5/2}	5.176	Zn	2p _{3/2}	3.726
Dy	4d	2.474	Mo	3d	3.321	Sc	2p	1.875	Zr	3d	2.576
Er	4d	2.463	N	1s	0.477	Se	3d	0.853			

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Appendix H. Line Positions^{a)} by Element for Mg K α X-rays

Atomic Number/Element	Photoelectron Lines										Auger Lines							
	1s	2s	2p _{1/2}	2p _{3/2}	3s	3p _{1/2}	3p _{3/2}	3d _{3/2}	4s	4p _{1/2}	4p _{3/2}	KL ₁ L ₁	KL ₁ L ₂₃	KL ₂₃ L ₂₃ ^{b)}				
3 Li	56																	
4 Be	112																	
5 B	189																	
6 C	285																	
7 N	398																	
8 O	531	23									780	766		745				
9 F	685	30									645	626		599				
10 Ne	863	41	14								492	469		436				
11 Na	1072	64	31								328	299		260				
12 Mg	1308	89	50								148	114		68				
13 Al		118	73								L ₃ M ₂₃ M ₂₃ ^{c)}	L ₂ M ₂₃ M ₂₃ ^{c)}	L ₃ M ₂₃ M ₄₅ (P)	L ₃ M ₂₃ M ₄₅ (P)	L ₂ M ₂₃ M ₄₅ (P)	L ₃ M ₄₅ M ₄₅ ^{d)}	L ₂ M ₄₅ M ₄₅	
14 Si		151	100	99							1186							
15 P		188	131	130	14						1161							
16 S		228	165	164	18						1134							
17 Cl		271	201	199	17	6					1103							
18 Ar		320	244	242	24						1071							
19 K		380	297	294	35		19				1039							
20 Ca		440	351	347	45		26				1006							
21 Sc		499	404	399	51		29				964							
22 Ti		561	460	454	59		33				916							
23 V		627	520	512	66		37				865							
24 Cr		696	583	574	75		43				815							
25 Mn		769	650	639	83		48				781							
26 Fe		845	720	707	92		53				764							
27 Co		925	793	778	101		60				726							
28 Ni		1009	870	853	111		67				667							
29 Cu		1097	953	933	123	77	75				606							
30 Zn		1195	1045	1022	140	91	89				605	598						
31 Ga			1144	1117	160	107	104				545	539						
32 Ge			1248	1217	181	126	122	30	29		486	479						
33 As					205	146	141	43	42		427	419						
34 Se					232	169	163	57	56		364	356						
35 Br					256	189	182	70	69	15	301	292	211	200	179			
36 Kr					287	216	208	88	87	21								
37 Rb					325	249	240	113	111	31								
38 Sr					360	281	270	136	134	39								
39 Y					394	311	299	158	156	45								
40 Zr					430	343	330	181	179	51								
											M ₂₃ M ₄₅ N ₂₃							
											1153							
											1152							
													M ₄₅ N ₂₃ V					
													1123					
													1164					

a) Lines enclosed in boxes are the ones which are most useful for identifying chemical states.

b) Includes KVV designation when L₂₃ is not a core level.

c) Designation is oversimplified.

d) Includes LVV when M levels are not in core and MVV when N levels are not in core.

e) No simple 4p_{1/2} line exists for this group of elements.

f) The 4d doublet for these elements is complex and is variable with chemical state because of multiplet splitting and multi-electron processes.

g) The 5s is of low intensity and is often in the shake-up structure of the 4f lines. These values are estimates of the energy.

Appendix J. Line Positions in Numerical Order

For photoelectron lines, the spin orbit splitting is indicated in parentheses. Auger lines are in italics, and the photon source for the Auger excitation is indicated in parentheses.

7	Lu 4f _{7/2}	(2)	89	Mg 2s		175	Tm 4d		299	Y 3p _{3/2}	(12)
14	Hf 4f _{7/2}	(2)	90	Ba 4d _{5/2}	(3)	179	Zr 3d _{5/2}	(2)	301	<i>Mg</i>	(Al)
23	O 2s		98	<i>Er</i>	(Al)	181	<i>Se</i>	(Al)	307	Rh 3d _{5/2}	(5)
22	Ta 4f	(2)	99	Si 2p _{3/2}	(1)	182	Yb 4d		309	Ho 4p _{3/2}	(44)
25	Sn 4d		101	Hg 4f _{7/2}	(4)		Br 3p _{3/2}	(7)	315	Pt 4d _{5/2}	(17)
29	Ge 3d _{5/2}	(1)	103	La 4d _{5/2}	(3)	186	<i>Ga</i>	(Mg)	320	Ar 2s	
30	F 2s		104	Ga 3p _{3/2}	(3)	188	P 2s		321	Er 4p _{3/2}	(47)
31	W 4f _{7/2}	(2)	109	Ce 4d _{5/2}	(3)	189	B 1s		330	Zr 3p _{3/2}	(14)
37	V 3p			<i>Ge</i>	(Mg)	196	Lu 4d _{5/2}	(10)	333	Th 4f _{7/2}	(9)
40	Re 4f _{7/2}	(2)	112	Rb 3d _{5/2}	(1)	199	Cl 2p _{3/2}	(2)		Tm 4p _{3/2}	(51)
41	Ne 2s			Be 1s		202	Nb 3d _{5/2}	(3)	335	Pd 3d _{5/2}	(5)
42	As 3d _{5/2}	(1)	115	Pr 4d		208	Kr 3p _{3/2}	(8)		Au 4d _{5/2}	(18)
43	Cr 3p		117	<i>Ho</i>	(Al)	211	Hf 4d _{5/2}	(11)		<i>Cu</i>	(Mg)
48	Mn 3p		118	Tl 4f _{7/2}	(4)	226	Ta 4d _{5/2}	(12)	341	Yb 4p _{3/2}	(48)
49	I 4d _{5/2}	(2)		Al 2s		228	S 2s		342	<i>Ge</i>	(Al)
50	Mg 2p		121	Nd 4d			Mo 3d _{5/2}	(3)	347	Ca 2p _{3/2}	(3)
51	Os 4f _{7/2}	(3)	122	Ge 3p _{3/2}	(4)	240	Rb 3p _{3/2}	(9)	360	Lu 4p _{3/2}	(53)
53	Fe 3p		128	Eu 4d		242	Ar 2p _{3/2}	(2)	361	Hg 4d _{5/2}	(20)
56	Li 1s		129	Sm 4d		243	W 4d _{5/2}	(13)		Nb 3p _{3/2}	(15)
	Se 3d _{5/2}	(1)	131	P 2p _{3/2}	(1)	260	Re 4d _{5/2}	(14)	368	Ag 3d _{5/2}	(6)
60	Co 3p		134	Sr 3d _{5/2}	(2)		<i>Na</i>	(Mg)	369	<i>Gd</i>	(Mg)
61	Ir 4f _{7/2}	(3)	137	Pb 4f _{7/2}	(5)		<i>Tb</i>	(Al)	377	U 4f _{7/2}	(11)
	Xe 4d _{5/2}	(2)	140	Gd 4d		262	<i>Zn</i>	(Mg)	380	K 2s	
64	Na 2s		141	As 3p _{3/2}	(5)		<i>As</i>	(Al)	385	Tl 4d _{5/2}	(21)
67	Ni 3p		146	Tb 4d		270	Sr 3p _{3/2}	(11)	394	Mo 3p _{3/2}	(17)
69	Br 3d _{5/2}	(1)	151	Si 2s		271	Cl 2s		398	N 1s	
71	Pt 4f _{7/2}	(3)	152	Dy 4d		279	Os 4d _{5/2}	(14)	399	Sc 2p _{3/2}	(5)
73	Al 2p		156	Y 3d _{5/2}	(2)	280	Ru 3d _{5/2}	(4)	404	<i>Eu</i>	(Mg)
75	Cu 3p _{3/2}	(2)	157	Bi 4f _{7/2}	(5)	285	Tb 4p _{3/2}	(37)	405	Cd 3d _{5/2}	(7)
77	Cs 4d _{5/2}	(3)	160	Ho 4d			C 1s		408	<i>Ni</i>	(Mg)
84	Au 4f _{7/2}	(4)	163	Se 3p _{3/2}	(6)	294	K 2p _{3/2}	(3)	412	Pb 4d _{5/2}	(22)
87	Kr 3d _{5/2}	(1)	164	S 2p _{3/2}	(1)	297	Dy 4p _{3/2}	(40)	419	<i>Ga</i>	(Al)
89	Zn 3p _{3/2}	(2)	167	Er 4d			Ir 4d _{5/2}	(15)	436	<i>Ne</i>	(Mg)

440	Ca 2s		669	Ne	(Al)	874	N	(Mg)	1103	Cd	(Al)
449	Sm	(Mg)	670	Xe 3d _{5/2}	(13)	884	Ce 3d _{5/2}	(18)	1107	N	(Al)
441	Bi 4d _{5/2}	(24)	676	Th 4d _{5/2}	(37)	886	Ba	(Al)	1117	Ga 2p _{3/2}	(27)
444	In 3d _{5/2}	(8)	682	Sm	(Al)	896	Ag	(Mg)	1126	Eu 3d _{5/2}	(30)
454	Ti 2p _{3/2}	(6)	685	F 1s		900	Mn	(Al)	1129	Ag	(Al)
462	Ru 3p _{3/2}	(22)		Cs	(Mg)	916	Sc	(Mg)	1149	Sc	(Al)
480	Co	(Mg)	696	Cr 2s		918	Cs	(Al)	1154	Bi	(Mg)
485	Sn 3d _{5/2}	(8)	707	Fe 2p _{3/2}	(13)	926	Pd	(Mg)	1159	Pd	(Al)
493	Na	(Al)	709	Xe	(Mg)	932	Pr 3d _{5/2}	(20)	1161	Pb	(Mg)
495	Zn	(Al)	713	Co	(Al)	933	Cu 2p _{3/2}	(20)	1168	Tl	(Mg)
497	Rh 3p _{3/2}	(24)	715	Sn 3p _{3/2}	(42)	942	Xe	(Al)	1179	Hg	(Mg)
499	Sc 2s		726	Cs 3d _{5/2}	(14)	952	Rh	(Mg)	1183	Au	(Mg)
512	V 2p _{3/2}	(8)		Cr	(Mg)	959	Cr	(Al)	1185	Rh	(Al)
525	Nd	(Mg)	736	U 4d _{5/2}	(42)	964	Ca	(Mg)	1186	Gd 3d _{5/2}	(32)
526	Dy	(Al)	738	I	(Mg)	971	U	(Mg)	1197	Ca	(Al)
528	Sb 3d _{5/2}	(9)	745	O	(Mg)		I	(Al)	1204	U	(Al)
531	O 1s		758	Nd	(Al)	978	O	(Al)	1212	Ru	(Al)
533	Pd 3p _{3/2}	(27)	767	Sb 3p _{3/2}	(46)	979	Ru	(Mg)	1217	Ge 2p _{3/2}	(31)
551	Fe	(Mg)	772	Te	(Mg)	981	Nd 3d _{5/2}	(21)	1223	C	(Al)
561	Ti 2s		778	Co 2p _{3/2}	(15)	990	C	(Mg)	1239	Th	(Al)
564	Pr	(Mg)	781	Ba 3d _{5/2}	(15)	1005	Te	(Al)		K	(Al)
568	Cu	(Al)		V	(Mg)	1006	K	(Mg)	1241	Tb 3d _{5/2}	(35)
573	Ag 3p _{3/2}	(31)	784	Fe	(Al)		Th	(Mg)	1272	Ar	(Al)
	Te 3d _{5/2}	(10)	797	Pr	(Al)	1014	V	(Al)	1296	Dy 3d _{5/2}	(37)
574	Cr 2p _{3/2}	(9)	799	Sb	(Mg)	1022	Zn 2p _{3/2}	(23)	1299	Mo	(Al)
599	F	(Mg)	816	Sn	(Mg)	1032	Sb	(Al)	1303	Mg 1s	
600	Ce	(Mg)	820	Te 3p _{3/2}	(51)	1039	Ar	(Mg)	1304	Cl	(Al)
602	Gd	(Al)	832	F	(Al)	1049	Sn	(Al)	1310	B	(Al)
619	Cd 3p _{3/2}	(34)	833	Ce	(Al)	1068	Ti	(Al)	1319	Nb	(Al)
	I 3d _{5/2}	(12)	835	Ti	(Mg)	1071	Cl	(Mg)	1324	As 2p _{3/2}	(35)
634	La	(Mg)	836	La 3d _{5/2}	(17)	1072	Na 1s		1336	S	(Al)
637	Eu	(Al)	843	In	(Mg)	1076	In	(Al)	1387	Bi	(Al)
639	Mn 2p _{3/2}	(11)	853	Ni 2p _{3/2}	(18)	1077	B	(Mg)	1394	Pb	(Al)
641	Ni	(Al)	863	Ne 1s		1081	Sm 3d _{5/2}	(27)	1401	Tl	(Al)
653	Ba	(Mg)	867	La	(Al)	1086	Nb	(Mg)	1412	Hg	(Al)
665	In 3p _{3/2}	(38)	870	Cd	(Mg)	1103	S	(Mg)	1416	Au	(Al)
667	Mn	(Mg)									

Appendix K. Periodic Table

Atomic number **9** PHI sensitivity factor for designated photoelectron transition **1.0**

Element symbol **F**

Most intense photoelectron transition **1s 685**
Most intense Auger transition **KLL 647**

Binding energy, most intense photoelectron transition
Kinetic energy, most intense Auger transition

1 H																	2 He
3 Li 1s 56 KLL 43	4 Be 1s 112 KLL 103											5 B 1s 187 KLL 177	6 C 1s 285 KLL 264	7 N 1s 402 KLL 380	8 O 1s 531 KLL 509	9 F 1s 685 KLL 665	10 Ne 1s 863 KLL 818
11 Na 1s 1072 KLL 994	12 Mg 2p 50 KLL 1186											13 Al 2p 73 LMM 98	14 Si 2p 99 LMM 93	15 P 2p 130 LMM 120	16 S 2p 164 LMM 151	17 Cl 2p 198 LMM 183	18 Ar 2p 242 LMM 215
19 K 2p 294 LMM 248	20 Ca 2p 347 LMM 290	21 Sc 2p 398 LMM 338	22 Ti 2p 454 LMM 418	23 V 2p 512 LMM 473	24 Cr 2p 574 LMM 528	25 Mn 2p 638 LMM 587	26 Fe 2p 707 LMM 703	27 Co 2p 778 LMM 774	28 Ni 2p 853 LMM 846	29 Cu 2p 933 LMM 919	30 Zn 2p _{1/2} 1022 LMM 992	31 Ga 2p _{1/2} 1117 LMM1068	32 Ge 2p _{1/2} 1217 LMM1145	33 As 3d 42 LMM1225	34 Se 3d 56 LMM1306	35 Br 3d 69 MNV 101	36 Kr 3d 87
37 Rb 3d 111 MNN 102	38 Sr 3d 134	39 Y 3d 156 MNV 131	40 Zr 3d 179 MNV 150	41 Nb 3d 202 MNV 168	42 Mo 3d 228 MNV 188	43 Tc 3d 253 MNN 246	44 Ru 3d 280 MNN 275	45 Rh 3d 307 MNN 302	46 Pd 3d 335 MNN 328	47 Ag 3d 368 MNN 358	48 Cd 3d _{5/2} 405 MNN 384	49 In 3d _{5/2} 444 MNN 411	50 Sn 3d _{5/2} 485 MNN 438	51 Sb 3d _{5/2} 528 MNN 465	52 Te 3d _{5/2} 573 MNN 492	53 I 3d _{5/2} 619 MNN 516	54 Xe 3d _{5/2} 670 MNN 545
55 Cs 3d _{5/2} 728 MNN 568	56 Ba 3d _{5/2} 781 MNN 601	57 La 3d 836 MNN 633	72 Hf 4f 14 NNN 181	73 Ta 4f 22 NNN 181	74 W 4f 31 NNN 180	75 Re 4f 40 NNN 178	76 Os 4f 51 NNN 176	77 Ir 4f 61 NNN 153	78 Pt 4f 71 NNN 170	79 Au 4f 84 NNN 163	80 Hg 4f 101 NOO 81	81 Tl 4f 118 NOO 88	82 Pb 4f 137 NOO 96	83 Bi 4f 157 NOO 104	84 Po	85 At	86 Rn
87 Fr	88 Ra	89 Ac															
			58 Ce 3d 884 MNN 654	59 Pr 3d 932 MNN 690	60 Nd 3d 981 MNN 729	61 Pm 3d 1034 MNN 773	62 Sm 3d _{5/2} 1081 MNN 805	63 Eu 4d 128 MNN 850	64 Gd 4d 140 MNN 885	65 Tb 4d 146 MNN1076	66 Dy 4d 152 MVV1119	67 Ho 4d 160 MVV1173	68 Er 4d 167 MVV1214	69 Tm 4d 175	70 Yb 4d 182	71 Lu 4f 7	
			90 Th 4f _{7/2} 333 NOV 68	91 Pa	92 U 4f _{7/2} 337 NOV 75	93 Np	94 Pu	95 Am	96 Cm	97 Bk	98 Cf	99 Es	100 Fm	101 Md	102 No	103 Lr	

*The values are for area measurements of the designated transitions and are only valid when the electron energy analyzer used has the transmission characteristics of the spherical capacitor type analyzer equipped with an Omni Focus III lens supplied by Physical Electronics and with x-rays at 90° relative to the analyzer. When a spin-orbit splitting is not designated, the value is for a measurement including both spin-orbit components.